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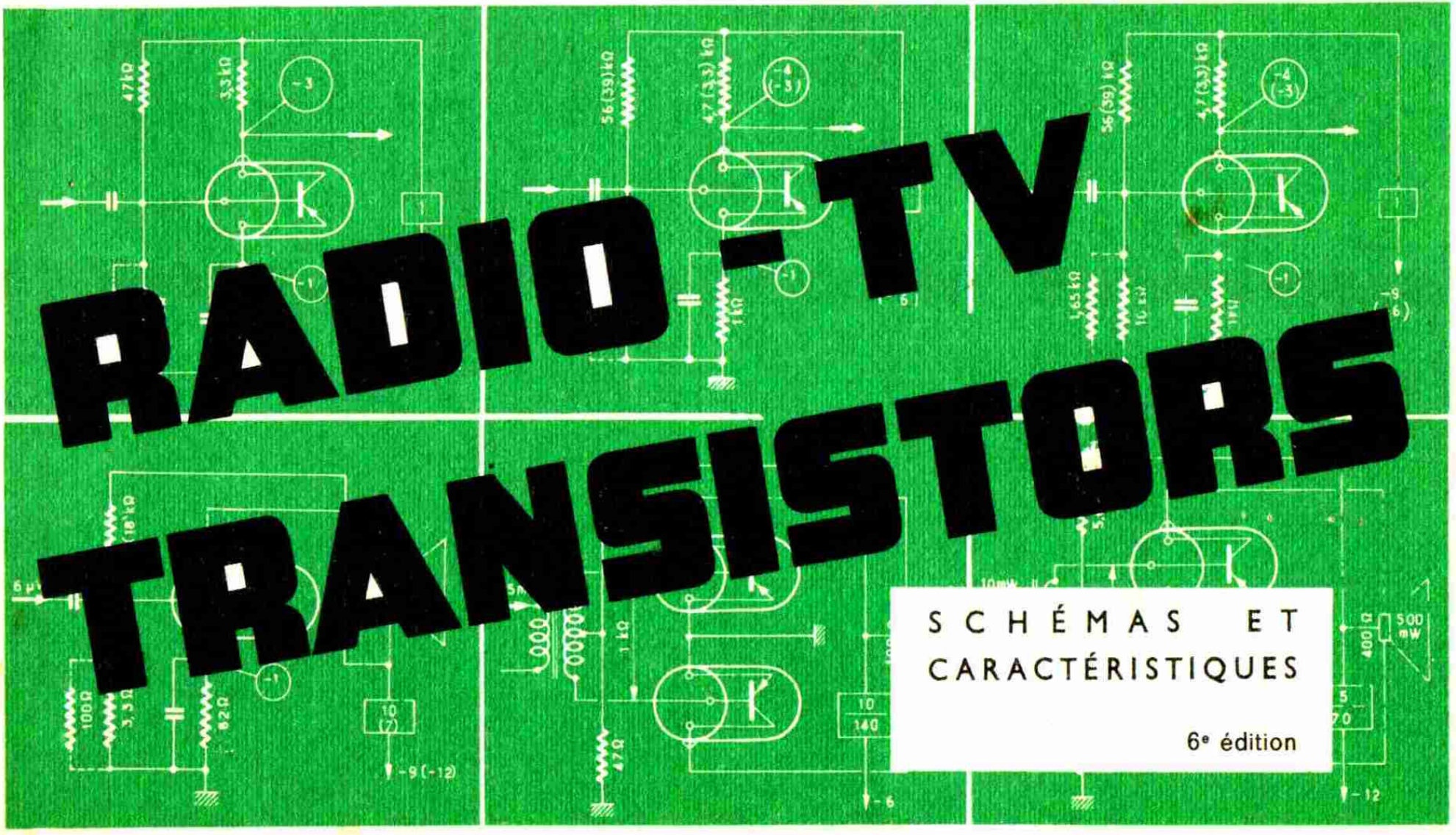

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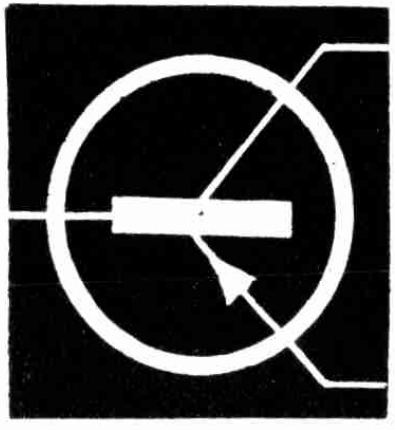

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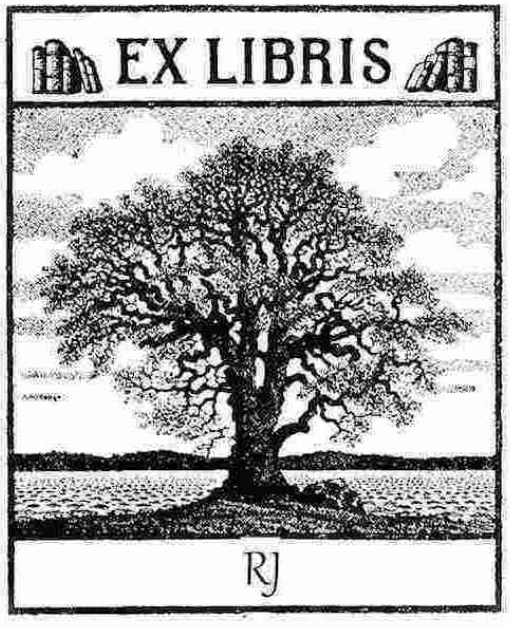

OUVRAGES DU MEME AUTEUR

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Initiation à la Pratique des Récepteurs à Transistors

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Technique de la modulation de fréquence *(épuisé)*

Technique et Applications des Transistors

Réparation des récepteurs à transistors

Les montages à transistors au laboratoire et dans l'industrie

Editeur n° 529 - Imprimé en France par LES PROCEDES DOREL - Paris - N° 54.547.

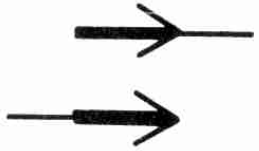
Préface

RADIO-TRANSISTORS ne supplante pas les recueils de caractéristiques tels que le GUIDE MONDIAL DES TRANSISTORS (principales caractéristiques limites et de fonctionnement de tous les transistors) ou la collection des CARACTÉRISTIQUES UNIVERSELLES DES TRANSISTORS (courbes et données détaillées sur les transistors les plus courants). Mais, étant de conception tout à fait différente, il les complète harmonieusement.

RADIO-TRANSISTORS est une collection de schémas d'utilisation de tous les transistors employés actuellement en radio. Ces schémas sont classés par ordre alphanumérique de l'appellation du transistor; *les lettres ont priorité sur les chiffres*. Ils indiquent, avec les valeurs des éléments essentiels d'utilisation, certaines caractéristiques importantes, tels que les gains en courant et en puissance, facteur de bruit, fréquence de travail, etc. Un coup d'œil rapide sur un petit schéma permet de connaître immédiatement toutes les données pratiques d'utilisation.

Dans *RADIO-TRANSISTORS*, seuls des signes conventionnels et bien connus ont été utilisés. Tout le monde doit donc pouvoir comprendre les renseignements contenus dans cet ouvrage, et cela sans avoir lu la présente introduction... ou après l'avoir oubliée. Malgré cela, et pour la tranquillité de sa conscience, l'auteur préfère rappeler le principe des notations utilisées.

■ Le branchement des transistors est présenté vu par en dessous.



■ Pour faciliter la lecture des schémas, des flèches indiquent l'entrée et la sortie des signaux à amplifier.

■ L'appellation du transistor est indiquée au coin supérieur gauche de chaque schéma. Elle peut être suivie d'une autre appellation; cela signifie que les deux transistors mentionnés ont des caractéristiques suffisamment voisines pour que le même schéma d'utilisation soit valable. Si la deuxième appellation est mise entre parenthèses, les valeurs correspondantes du schéma apparaissent également entre parenthèses. De la même façon, la parenthèse peut encore être utilisée pour caractériser différentes conditions de fonctionnement dans un même montage (valeur des éléments pour différentes tensions d'alimentation, etc.). En dessous de l'appellation du transistor, se trouve l'indication de la *fonction* suivant les symboles classiques :

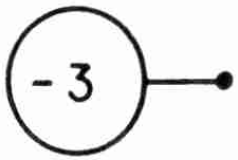
Osc : Oscillateur.
HF : Haute fréquence.
Conv : Conversion de fréquence.
MF : Moyenne fréquence.
BF : Basse fréquence.
P : Amplification de puissance (étage de sortie).
VHF : Transistor utilisable aux très hautes fréquences.

■ En haut de chaque schéma, sont indiqués les caractéristiques essentielles du transistor et du montage :

β	:	**Gain de courant (en basse fréquence, sauf indication spéciale).**
F_b	:	**Facteur de bruit.**
GP	:	**Gain en puissance du montage.**
GC	:	**Gain de conversion.**
f_t	:	**Fréquence de transition (à laquelle $\beta = 1$).**
		Dans le cas des transistors à effet de champ (F.E.T.), on trouve les notations :
I_{DSS}	:	**Courant de drain à tension de gate nulle.**
s	:	**Pente, transconductance, ou conductance mutuelle.**
V_{GSO}	:	**Tension de blocage ou de cut-off du gate.**
ρ	:	**Résistance interne de sortie.**

■ La *fréquence de travail* est indiquée dans le cas des montages amplificateurs HF ou MF, ainsi que dans certains *quadripôles* dont les éléments dépendent de la fréquence. Ces dessins de quadripôles contiennent également la mention de la tension de collecteur (V_c) et du courant de collecteur (I_c) correspondant aux valeurs indiquées.

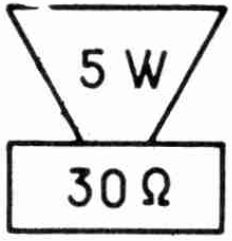
■ Plusieurs schémas peuvent être consacrés à un même transistor lorsque celui-ci peut avoir plusieurs fonctions ou travailler sous différentes conditions d'utilisation.



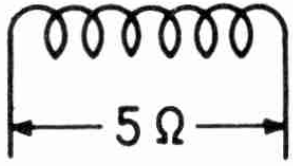
■ Les chiffres enfermés dans des cercles indiquent, *en volts*, les *tensions continues* qui existent entre le point d'attache du cercle et la masse. La polarité est exprimée par les signes + ou —.

■ Les intensités continues sont indiquées da des carrés intercalés dans les circuits comı des appareils de mesure; elles sont toujou exprimées en *milliampères*. Dans le cas d amplificateurs classe AB, les intensités mi male et maximale sont indiquées l'une dessous de l'autre, dans le même carré.

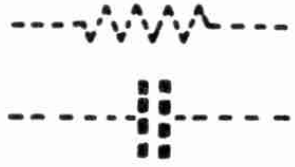
■ Les chiffres enfermés dans des *triangles* in quent des *tensions alternatives*.



■ Le dessin du *haut-parleur* contient des ch fres exprimant l'*impédance de charge* et *puissance* maximale de *sortie*. Cette dernie n'est pas la valeur théorique extrême, m celle qu'on peut obtenir avec un transforn teur de sortie de faibles pertes.



■ La valeur ohmique apparaissant entre les b nes de sortie ou d'entrée d'un transformate indique l'*impédance d'adaptation* de l'enro lement correspondant.



■ Les éléments dessinés en *pointillé* indique les résistances ou capacités *internes* que p sède le montage entre les points correspo dants.

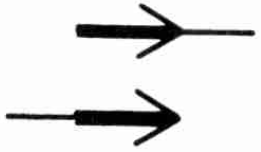
Preface

RADIO-TRANSISTORS does not replace the handbooks such as the GUIDE MONDIAL DES TRANSISTORS (principal characteristics and applications of all transistors) or the manual CARACTÉRISTIQUES UNIVERSELLES DES TRANSISTORS (graphs and complete data on the main types). But being of a conception totally different, *RADIO-TRANSISTORS* completes them harmoniously.

RADIO-TRANSISTORS is a collection of schematic diagrams of all the transistors used at present in radio. These diagrams are classified by the alphabetical and numerical designation of the transistors *letters having priority over the numbers*. They indicate, along with the values of the components used, certain important characteristics, such as gain in current and power, noise factor, working frequency, etc. A glance at the diagram gives all the practical details.

In *RADIO-TRANSISTORS* only usual and well-known symbols are used. Everyone should therefor be able to grasp the information contained in this handbook even without having read the present introduction or after having forgotten it. Nevertheless to sooth his conscience, the author prefers enumerating the following notations.

■ The connections of the transistors are as seen from below.



■ To facilitate the comprehension of the diagrams, the arrows indicate the input and output of the signals being amplified.

■ The designation of the transistor is indicated in the upper left-hand corner of each diagram. It may be followed by another; this means that both transistors mentioned are sufficiently similar so that the same diagram can be used. If the second designation is between parenthesis, the corresponding values of the diagram are similarly indicated between parentheses. In a like manner, the parenthesis can be used to indicate different conditions of operation in the same layout (values for different voltages applied, etc.). Below the designation of the transistor, will be found the classic indication of the *function* :

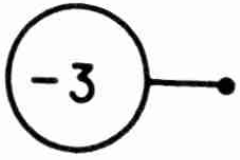
OSC : Oscillator.
HF : High-frequency.
Conv : Frequency converter.
MF : Intermediate frequency.
BF : Audio frequency.
P : Power amplification (output stage).
VHF : Very high frequency application.

■ At the top of each diagram, the main indications of the transistor and its allied components are indicated.

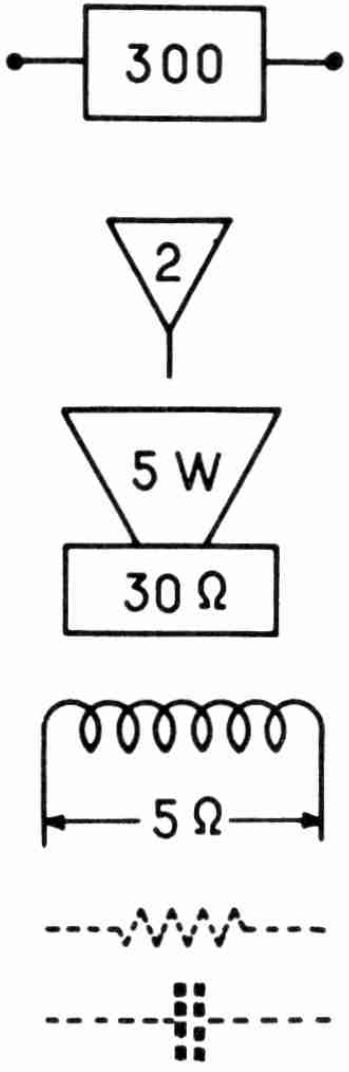
β	:	Current gain (at audio frequencies except special indication).
F_b	:	Noise factor.
GP	:	Power gain of the set-up.
GC	:	Conversion gain.
f_t	:	Transition frequency (at which $\beta = 1$).
		In the case of field effect transistors (F.E.T.), the following indications are given :
I_{DSS}	:	Drain current at null gate voltage.
s	:	Slope, transconductance, or mutual conductance.
V_{GSO}	:	Gate blockage or cut-off voltage.
ρ	:	Internal output resistance.

■ The *working frequency* is indicated in the case of high or intermediate frequency amplifiers as well as in certain *four-pole units* of which the elements are dependent on the frequency. These drawings of the four-pole units also contain the mention of the collector voltage (V_c) and collector current (I_c) corresponding to the values indicated.

■ Several diagram may be devoted to the same transistor when it has several functions or can work under different conditions of utilisation.



■ The figures in the circles indicate *in volts. the D.C. voltages*, that exist between the point where the circle is attached and the bus. Polarity is expressed by the signs + or —.



■ The *D.C. currents* are indicated in the squ res that are intercalated in the circuits as many measuring instruments; they are alwa expressed in *milliamps*. In the case of cla AB amplifiers, the minimum and maximu currents are indicated one below the oth in the same box.

■ The figures enclosed in the *triangles* indica *A.C. voltages*.

■ The drawing of the loud-speaker contai the figures expressing the *impedance load* a maximum *power output*, the latter not bei the extreme theoretical value but the one th can be obtained with a low-loss output tra former.

■ The ohms value that appears at the input output lugs of a transformer indicate t *adaptation impedance* of the correspondi winding.

■ The elements drawn in *dotted lines* indica the internal resistances or capacities that exi between the corresponding points.

Vorwort

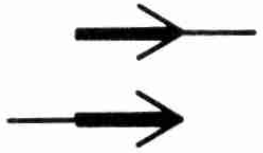
RADIO-TRANSISTORS ergänzt harmonisch zwei bereits gut bekannte Sammlungen von Transistor-Kenndaten : GUIDE MONDIAL DES TRANSISTORS (wichtigste Grenz- und Betriebswerte aller Transistoren) und CARACTÉRISTIQUES UNIVERSELLES DES TRANSISTORS (Kennlinien und Parameter der gebräuchlichsten Transistoren).

RADIO-TRANSISTORS ist eine Schaltungssammlung mit Anwendungsbeispielen aller zur Zeit in der Rundfunk- und Niederfrequenztechnik verwendeten Transistoren. Die Schaltungen sind alphanummerisch nach den Bezeichnungen der Transistoren eingeordnet; die *Buchstaben sind den Ziffern vorangesetzt*. Neben den Werten der hauptsächlichsten Schaltelemente enthalten diese Zeichnungen Angaben über einige wichtige Daten, wie Strom- und Leistungsverstârkung, Rauschfaktor, Betriebsfrequenz, usw. Ein kurzer Blick auf die kleine Schaltung genügt, um sofort alle praktischen Angaben über die Verwendung des Transistors zur Verfügung zu haben.

RADIO-TRANSISTORS enthält nur allgemein bekannte und gebräuchliche Zeichen und Symbole. Somit kann jeder ohne weiteres die in dieser Broschüre enthaltenen Angaben verstehen, und das selbst, wenn er diese Einführung nicht gelesen... oder bereits wieder vergessen hat.

Trotzdem möchte der Verfasser, auch in Hinsicht auf sein ruhiges Gewissen, das Prinzip der verwendeten Bezeichnungen kurz erläutern.

■ Die *Anschlüsse* der Transistoren sind von der *unteren* (Anschluss-) Seite aus gesehen.



■ Das Lesen der Schaltungen wird durch *Pfeile* vereinfacht, die Ein- und Ausgang der zu verstärkenden Signale angeben.

■ Die Typenbezeichnung des Transistors ist in der linken oberen Ecke jeder Schaltung angegeben. Eine zweite Bezeichnung kann darauf folgen; es handelt sich dann um zwei Transistoren deren Kennwerte so ähnlich sind, dass ein gleiches Anwendungsbeispiel für beide gültig ist. Wenn die zweite Bezeichnung in Klammern steht, dann erscheinen die entsprechenden Angaben im Schaltbild ebenfalls in Klammern. Ähnlich werden die Klammern auch verwendet, um in einer Schaltung mehrere Betriebsbedingungen anzugeben (Dimensionierung für verschiedene Speisespannungen, usw.). Unter der Typenbezeichnung wird die *Funktion* wie folgt angegeben:

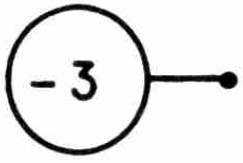
Osc : Oszillator.
HF : Hochfrequenzverstärker.
Conv : Mischstufe.
MF : Zwischenfrequenzverstärker.
BF : Niederfrequenzverstärker.
P : Leistungs- (End-) Stufe.
VHF : Bei sehr hohen Frequenzen verwendbarer Transistor.

■ Im oberen Teil jedes Schaltbildes sind folgende wichtige Kennwerte des Transistors oder der Schaltung angegeben :

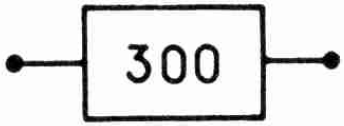
β	:	**Stromverstärkung bei Niederfrequenz (oder bei der hinter dem Wert angegebenen Frequenz).**
F_b	:	**Rauschfaktor.**
GP	:	**Leistungsgewinn der Schaltung.**
GC	:	**Mischverstärkung.**
f_t	:	**Transitfrequenz (Frequenz, bei der $\beta = 1$).**
		Bei Feldeffekttransistoren (F.E.T.) werden folgende Abkürzungen verwendet :
I_{DSS}	:	**Drainstrom bei Gatespannung null.**
s	:	**Steilheit oder Transkonduktanz.**
V_{GSO}	:	**Sperr - oder cut-off-Spannung des Gates.**
ρ	:	**Innerer Ausgangswiderstand.**

■ Die *Betriebsfrequenz* ist bei den Hoch- und Zwischenfrequenzverstärker-Schaltungen angegeben; sie ergänzt auch gewisse *Vierpoldarstellungen* deren Elemente frequenzabhängig sind. Diese Vierpole sind auch mit Angaben über die entsprechende Kollektorspannung (V_c) und den Kollektorstrom (I_c) versehen.

■ Mehrere Schaltbilder können sich auf denselben Transistor beziehen, wenn dieser mehrere Funktionen haben oder unter verschiedenen Bedingungen verwendet werden kann.

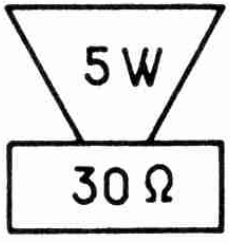


■ Von *Kreisen* umgebene Zahlen geben, in *Volt*, die *Gleichspannungen* an, die man zwischen Masse und dem mit dem Kreise verbundenen Punkt der Schaltung misst. Die Zeichen + oder — geben die Polarität an.

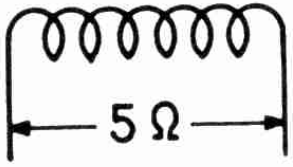


■ *Gleichstromwerte* sind in *Vierecken* angeg ben, die wie Messinstrumente in die Stro kreise eingelegt sind. Die Angabe folgt imm in Milliampère. Bei AB-Verstärkern si Ruhe- und Spitzenstrom untereinander i selben Viereck angegeben.

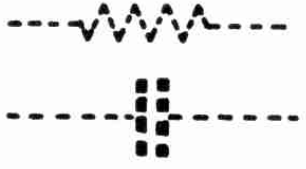
■ Wechselspannungen sind in Dreiecke ein schrieben.



■ Das Schaltzeichen des *Lautsprechers* enth Angaben über den *Anpassungwiderstand* u die maximale *Ausgangsleistung*. Letzte entspricht nicht dem theoretischen Höch wert, sondern der Leistung, die man n einem Ausgangstransformator guter Qualit erzielen kann.



■ Eine Widerstandsangabe zwischen den Ei oder Ausgangsklemmen eines Transformato gibt den *Anpassungswiderstand* der entspr chenden Wicklung an.



■ Mit unterbrochenem Strich gezeichne Schaltzeichen stellen die *inneren* Widerstän oder Kapazitäten dar, welche die Schaltu zwischen den entsprechenden Punkten a weist.

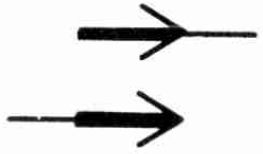
Prefacio

RADIO-TRANSISTORS no suplanta las colecciones de caracterís-icas tales como el GUIDE MONDIAL DES TRANSISTORS (*Guia Mundial de ransistores*) (principales características límites y de funcionamiento de odos los transistores) o la colección de las CARACTÉRISTIQUES UNIVER-ELLES DES TRANSISTORS (*Características Universales de los Transistores*) curvas y datos detallados sobre los transistores mas corrientes) pero. iendo de concepción completamente diferente, las completa armonio-amente.

RADIO-TRANSISTORS es una colección de esquemas de empleo de odos los transistores utilizados actualmente en radio. Estos esquemas stán clasificados por orden alfa-numérico de la apelación del transistor : *as letras tienen prioridad sobre las cifras*. Indican, con los valores de los lementos esenciales de empleo, ciertas características importantes, tales omo las ganancias en corriente y en potencia, factor de ruido, frecuencia e trabajo, etc. Una rápida ojeada sobre un pequeño esquema permite onocer immediatamente todos los datos prácticos de utilización.

En *RADIO-TRANSISTORS*, sólo se utilizan signos convencionales y erfectamente conocidos. Así pues, todo el mundo debe poder com-render las informaciones contenidas en esta obra, y sin haber leido la resente introducción... o después de haberla olvidado. A pesar de ello y ara tranquilidad de su conciencia, el autor prefiere recordar el principio e las anotaciones utilizadas.

- La conexión de los transistores se ha presentado vista por debajo.



- Para facilitar la lectura de los esquemas, las flechas indican la entrada y la salida de las señales a amplificar.

- La apelación del transistor está indicada en el extremo superior izquierda de cada esquema. Puede estar seguida de otra apelación, lo cual significa que los dos transistores mencionados tienen características suficientemente próximas para que el mismo esquema de empleo sea utilizable. Si la segunda apelación está dispuesta entre paréntesis, los valores correspondientes del esquema aparecen igualmente entre paréntesis. De igual manera, el paréntesis puede también ser utilizado para caracterizar diferentes condiciones de funcionamiento en un mismo montaje (valores de los elementos para diferentes tensiones de alimentación, etc.). Debajo de la denominación del transistor, se encuentra la indicación de la *función*, según los símbolos clásicos :

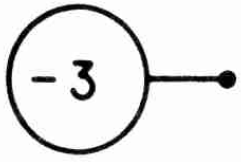
Osc : Oscilador.
HF : Alta frecuencia.
Conv : Conversión de frecuencia.
MF : Frecuencia intermedia.
BF : Baja frecuencia.
P : Amplificación de potencia (etapa de salida).
VHF : Transistor utilizable para muy altas frecuencias.

■ En la parte superior de cada esquema, se indican las características esenciales del transistor y del montaje :

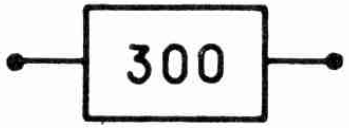
β	:	Ganancia de corriente (en baja frecuencia, salvo indicación especial).
F_b	:	Factor de ruido
GP	:	Ganancia en potencia del montaje.
GC	:	Ganancia de conversión.
f_t	:	Frecuencia de transición (en la que $\beta = 1$).
		En los casos en que se trata de transistores de efecto de campo (F.E.T.), se encuentran notaciones :
I_{DSS}	:	Corriente de drenaje de tensión de umbral nula.
s	:	Pendiente, transconductancia o conductancia mutua.
V_{GSO}	:	Tensión de bloqueo o de corte del umbral (gate).
ρ	:	Resistencia interna de salida.

■ La *frecuencia de trabajo* se indica en el caso de los montajes amplificadores AF o FI, asi como en ciertos *quadripolos* cuyos elementos dependen de la frecuencia. Estos dibujos de cuadripolos contienen igualmente la mención de la tensión de colector (V_C) y de la corriente de colector (I_C) correspondiente a los valores indicados.

■ Varios esquemas pueden ser consagrados a un mismo transistor cuando este puede tener varias funciones o trabajar bajo diferentes condiciones de empleo.

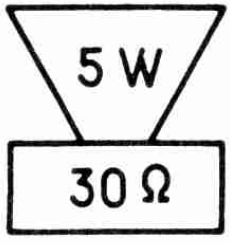


■ Las cifras encerradas en círculos indican, *en voltios*, las *tensiones contínuas* que existen entre el punto de ataque del círculo y masa. La polaridad se expresa por los signos + o —.

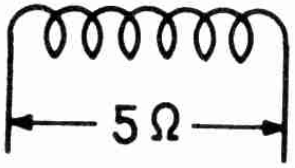


■ Las intensidades continuas se indican cuadrados intercalados en los circuitos c aparatos de medición; siempre se expre en *miliamperios*. En el caso de los ampli dores clase AB, las intensidades mínim máxima se indican una debajo de la otra el mismo cuadrado.

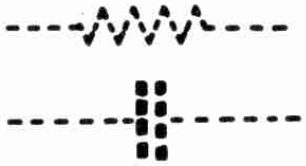
■ Las cifras encerradas en *triángulos* indi *tensiones alternas*.



■ El dibujo del *altavoz* contiene cifras ex sando la *impedancia de carga* y la *pote* máxima de *salida*. Esta última no es el v teórico extremo, sino el que se puede obte con un transformador de salida de reduc pérdidas.



■ El valor óhmico que aparece en los borne salida o de entrada de un transforma indica la *impedancia de adaptación* devanado correspondiente.



■ Los elementos dibujados en *punteado* i can las resistencias o capacidades *inter* que posee el montaje entre los puntos cor pondientes.

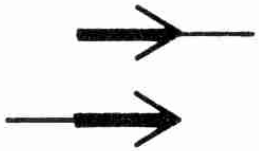
Voorwoord

RADIO-TRANSISTORS vervangt niet de verzameling van gegevens zoals de GUIDE MONDIAL DES TRANSISTORS (*Transistor-Wereldgids*) (voornaamste eigenschappen en funkties van alle transistors) of de verzameling CARACTÉRISTIQUES UNIVERSELLES DES TRANSISTORS (*Universele Transistor-Karakteristieken*), doch zijnde van geheel andere aard vult deze harmonisch aan.

RADIO-TRANSISTORS is een verzameling praktijk-schemas van alle thans voor radio in gebruik zijnde transistors. Deze schemas zijn in alfabetisch-numerieke volgorde naar type-benaming gerangschikt, *waarbij letters voorrang hebben boven de cijfers*. Zij vermelden, met de waarden der wezenlijke gebruiksbestanddelen, zekere belangrijke gegevens zoals de stroom- en energieversterking, ruisfaktor, werkfrekwentie, enz. Een vluchtige blik op een klein schema doet onmiddellijk alle gegevens voor het praktische gebruik zien.

In *RADIO-TRANSISTORS* zijn slechts gangbare en welbekende tekens gebruikt. Iedereen zal dus de in deze uitgave vervatte inlichtingen kunnen begrijpen, zelfs zonder deze inleiding te hebben gelezen... of na haar te hebben vergeten. Desondanks en voor de gerustheid van zijn geweten, geeft de samensteller er de voorkeur aan het principe der gebruikte tekens in herinnering te brengen.

■ De aansluiting der transistors is voorgesteld van onderen gezien.



■ Om het lezen der schemas te vergemakkelijken wordt de ingang en de uitgang der signalen van de versterker door pijlen aangegeven.

■ De benaming van de transistor is vermeld in de linker bovenhoek van elk schema. Zij kan gevolgd worden door een andere type-aanduiding, hetgeen betekent dat de twee genoemde transistors elkander voldoend naderbij komende karakteristieken hebben om het zelfde gebruikschema te doen gelden. Indien de tweede benaming tussen haakjes geplaatst is, zijn de dienovereenkomstige waarden van het schema eveneens tussen haakjes. Op dezelfde wijze kunnen haakjes nog gebruikt worden om verschillende funktievoorwaarden in een zelfde konstruktie te karakteriseren (waarden der elementen voor verschillende voedingsspanningen, enz.). Onder de benaming van de transistor bevindt zich de aanduiding der *funktie* volgens de klassieke symbolen :

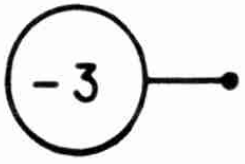
Osc : Oscillator.
HF : Hoge frekwentie.
Conv : Conversie.
MF : Midden frekwentie.
BF : Lage frekwentie.
P : Eindversterking.
VHF : Transistor bruikbaar voor zeer hoge frekwenties.

■ Boven elk schema zijn de belangrijkste gegevens van de transistor en van de schakeling aangeduid :

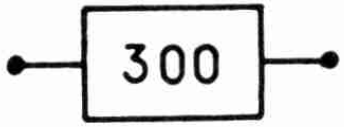
β	:	**Stroomversterking (op lage frekwenties, behoudens speciale aanduiding).**
F_b	:	**Ruisfaktor.**
GP	:	**Energieversterking van de schakeling.**
GC	:	**Conversieversterking.**
f_t	:	**Overgangsfrequentie (waarbij $\beta = 1$).**
		In het geval van transistors met veld effect (F.E.T.) treft men de volgende noteringen aan :
I_{DSS}	:	**Draineerstroom zonder gate spanning.**
s	:	**Helling, transconductantie, of onderling geleidingsvermogen.**
V_{GSO}	:	**Blokkeringsspanning of gate afsluitingsspanning.**
ρ	:	**Inwendige uitgangsweerstand.**

■ De *werkfrekwentie* is aangeduid in geval van HF of MF versterkerschakelingen, zoals ook in zekere *vierpolen* waarvan de elementen van de frekwentie afhangen. Deze tekeningen van vierpolen bevatten eveneens de vermelding van de kollektorspanning (V_c) en van de kollektorstroom (I_c) overeenkomstig de aangegeven waarden.

■ Verschillende schemas kunnen gebruikt worden voor een zelfde transistor, wanneer deze verschillende funkties kan hebben of onder verschillende voorwaarden kan werken.

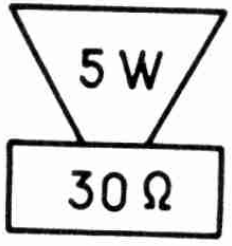


■ Door de cijfers in cirkels worden aangeduid, *in volts*, de *gelijkspanningen* tussen het aansluitpunt van de cirkel en de massa. De polariteit is aangeduid door de tekens + of —.

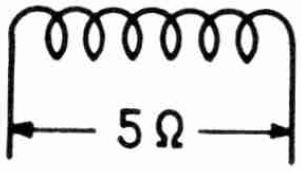


■ De gelijkstroomwaarden zijn aangeduid vierkanten welke als meetinstrumenten de stroomkring ingelast zijn; zij zijn steeuitgedrukt in *milliampères*. In het geval vaklasse AB versterkers, worden de minima en maximale waarden onder elkander hetzelfde vierkant aangeduid.

■ De cijfers in de *driehoeken* geven de *wisse spanningen*.



■ De tekening van de *luidspreker* bevat cijfe welke de *belastingsimpedantie* en het maxmale *uitgangsvermogen* weergeven. Dit laatsis niet de theoretisch uiterste waarde, maidie welke men met een uitgangstransformatomet zwakke verliezen kan verkrijgen.

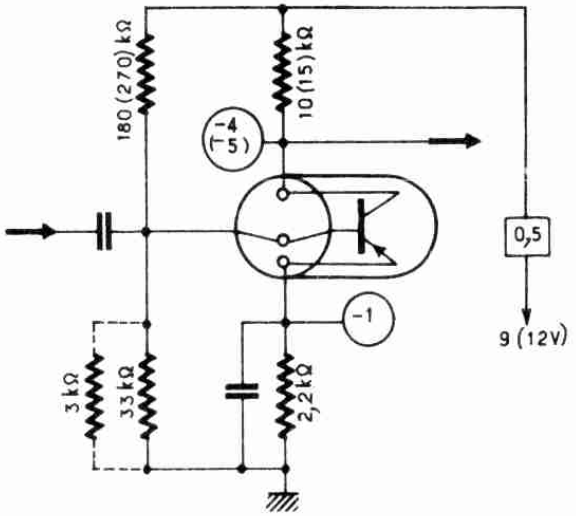


■ De tussen de uitgangs- of ingangsaansluitigen van een transformator genoemde ohmwaarde geeft de *aanpassingsimpedantie* vade betreffende wikkeling.

■ Door de met een stippellijn getekende elmenten worden de *inwendige* weerstandeof kapaciteiten van de schakeling tussen dbetreffende punten aangegeven.

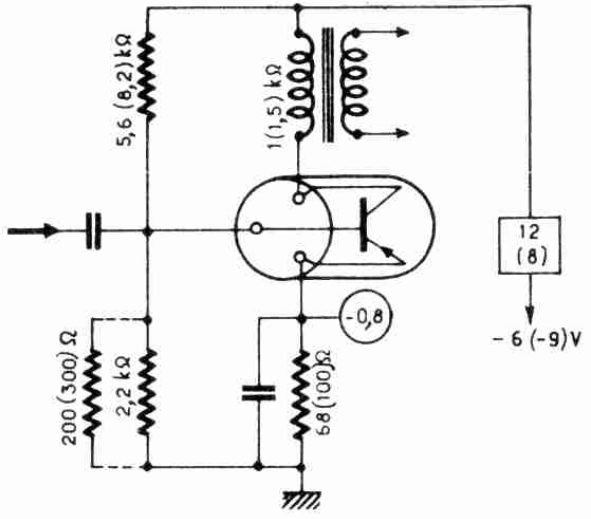
AC107
BF

β = 40
F_b = < 8 dB



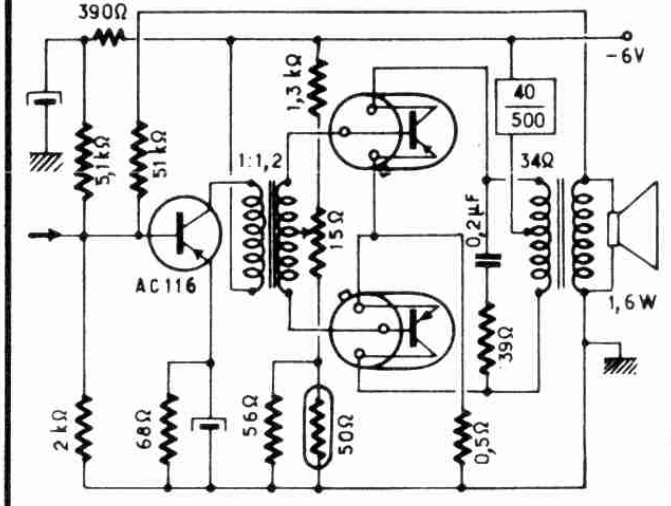
AC116
BF

β = 85
GP = 30 dB



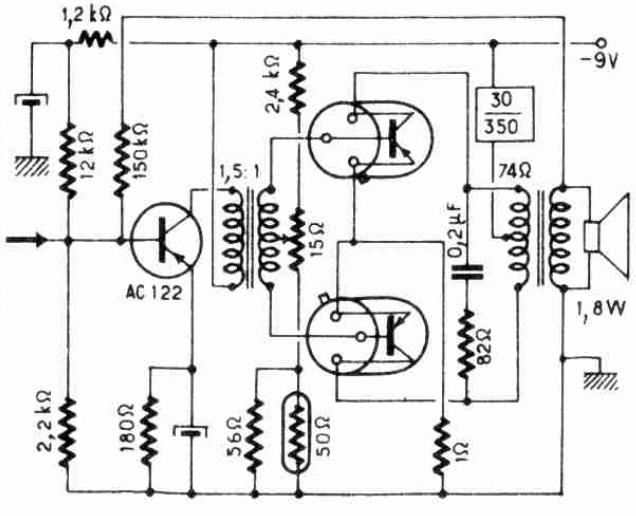
AC117
BF

β = 70



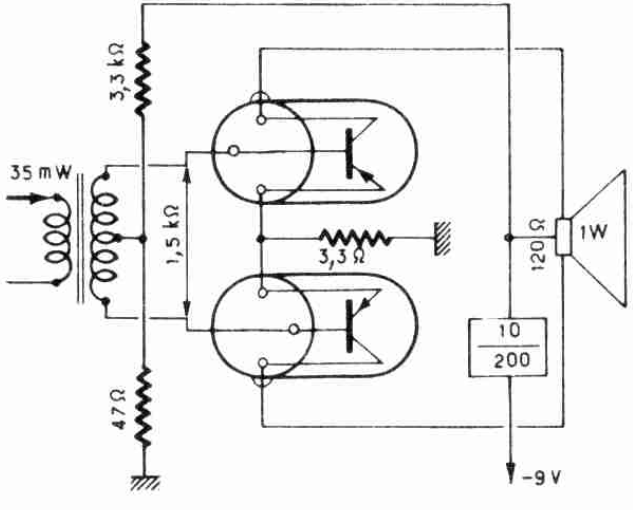
AC117
BF

β = 70



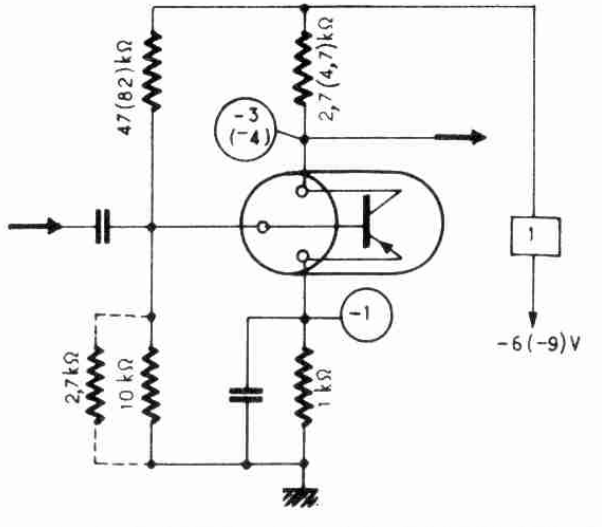
AC121
BF

β = 30 ... 250
GP = 15 ... 20 dB



AC122
BF

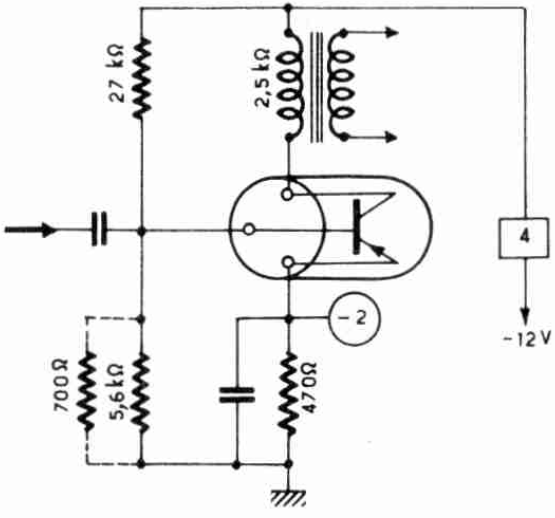
β = 85
F_b = 5,5 dB



AC123

BF

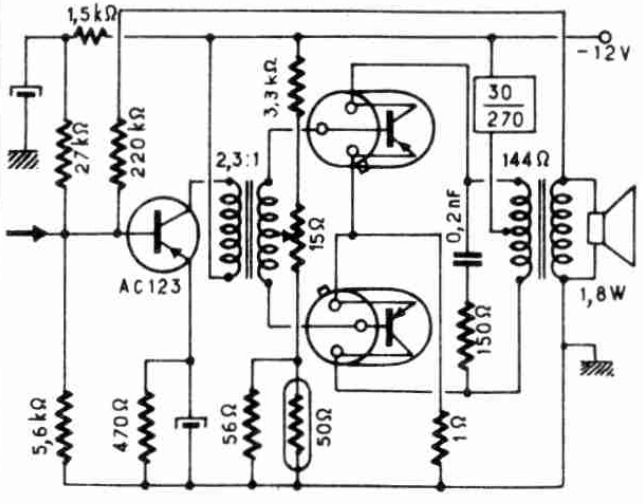
β = 85
GP = 32 dB



AC124

BF

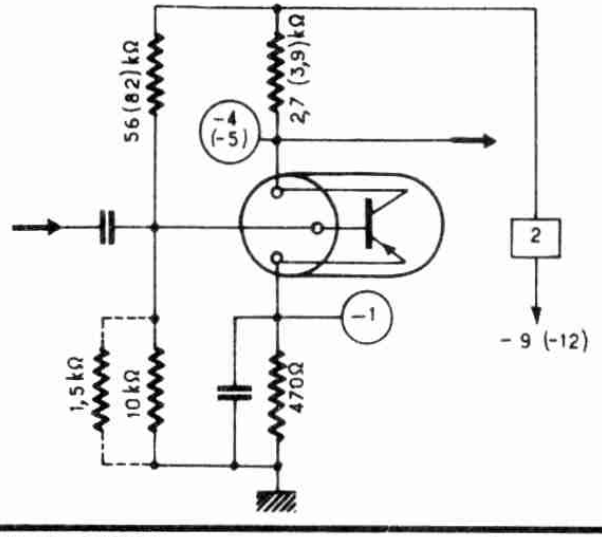
β = 50



AC125

BF

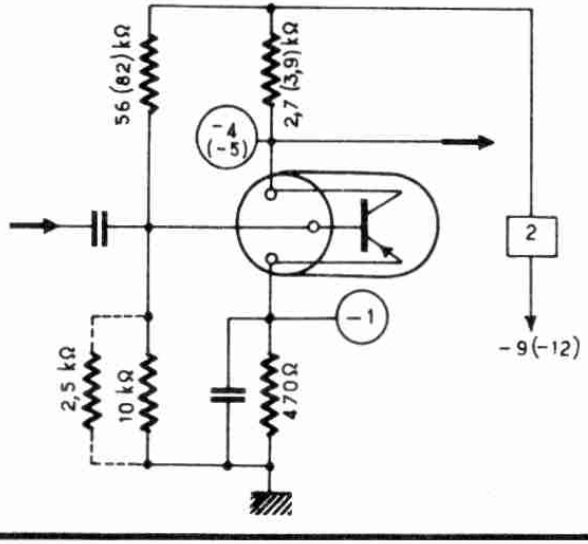
β = 80...160



AC126

BF

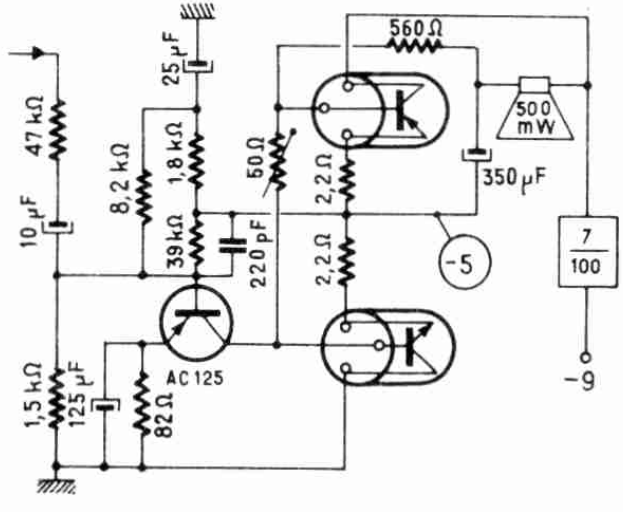
β = 130...300



AC 127
AC 128

n-p-n
p-n-p

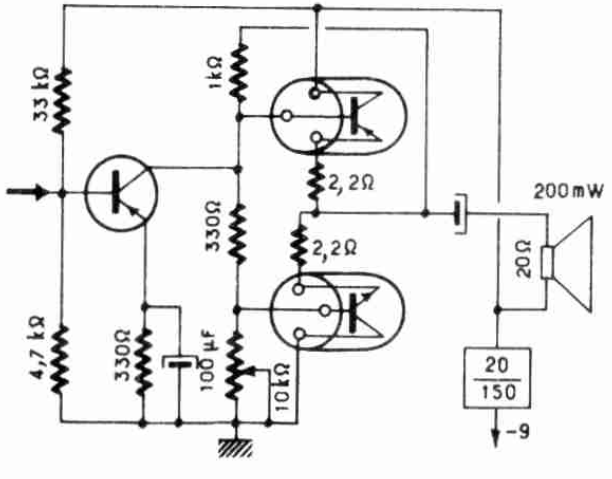
β = 115
β = 55... 175



AC 127
AC 132

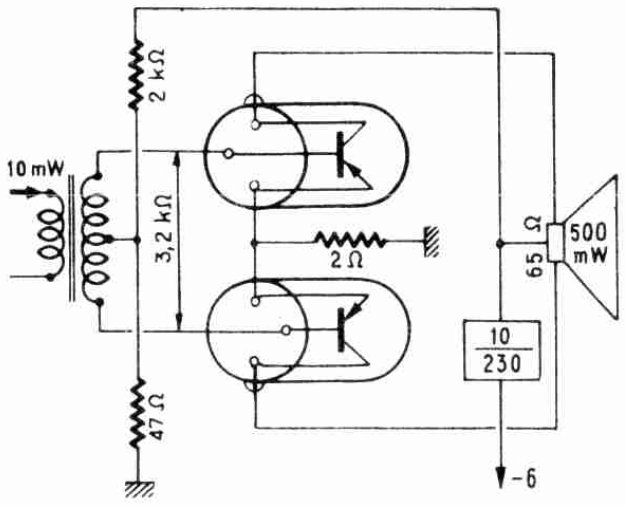
n-p-n
p-n-p

β = 115



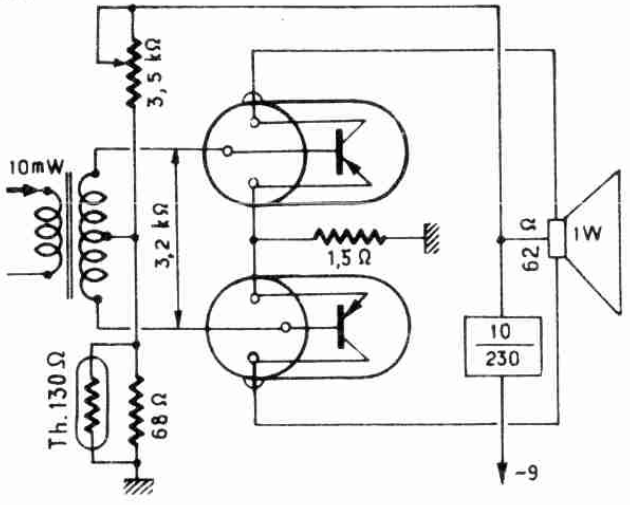
AC 128
BF

β = 50... 175
GP = 11.... 14 dB



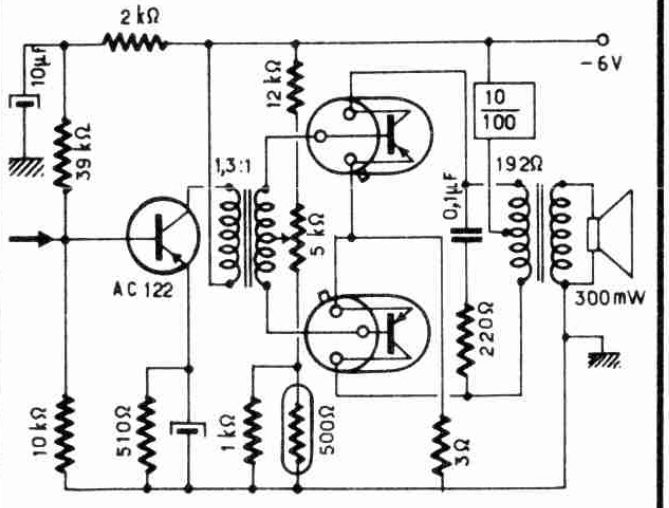
AC 128
BF

β = 50...175
GP = 18...21 dB



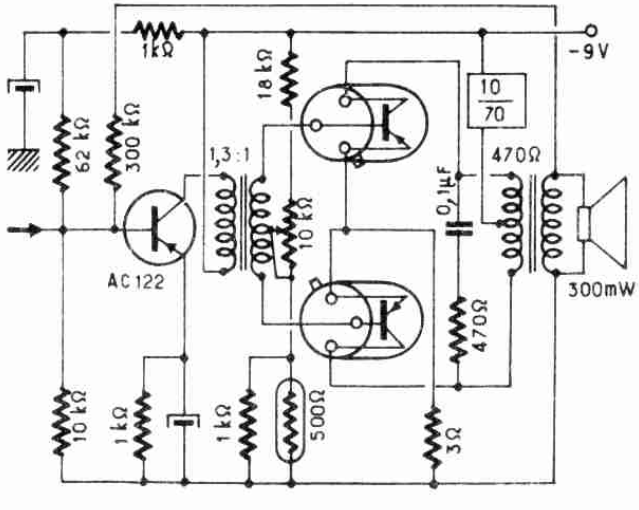
AC 131
BF

β = 67



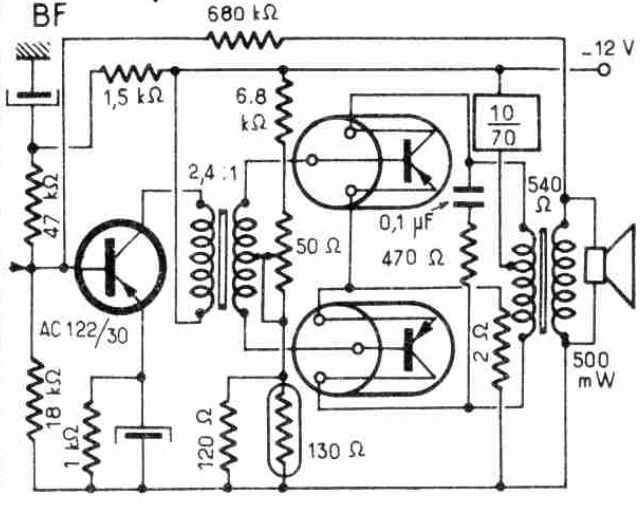
AC 131
BF

β = 67



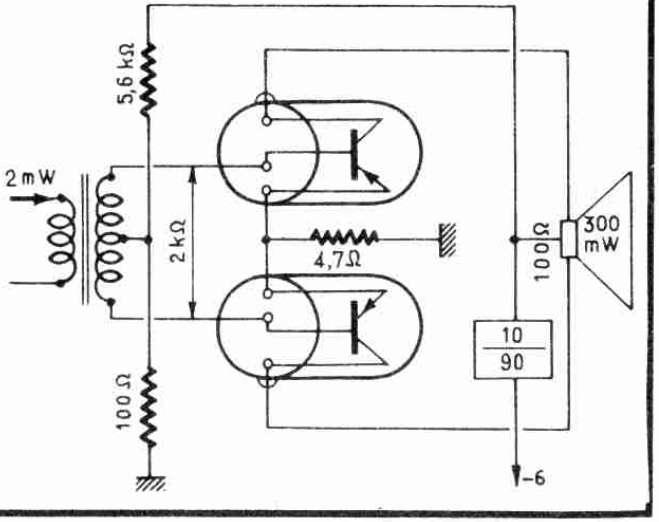
AC 131/30
BF

β = 67



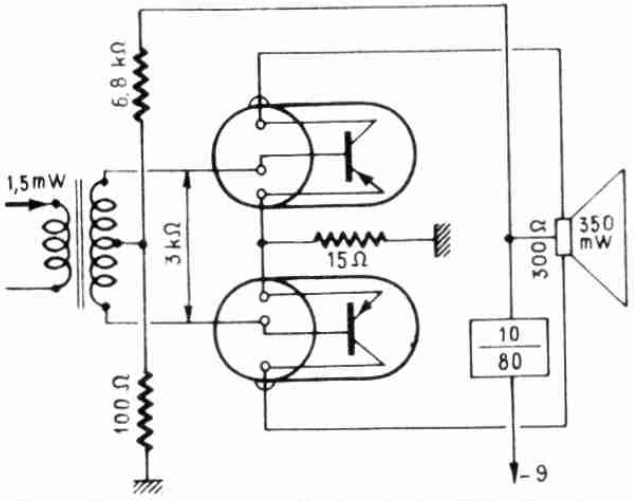
AC 132
BF

β = 115
GP = 22 dB



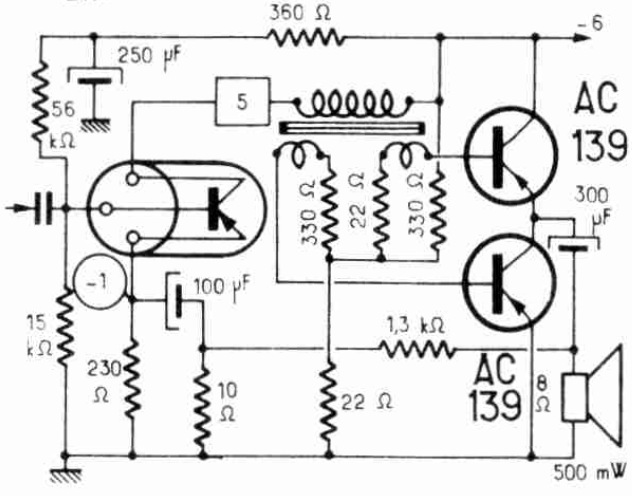
AC 132
BF

β = 115
GP = 25 dB



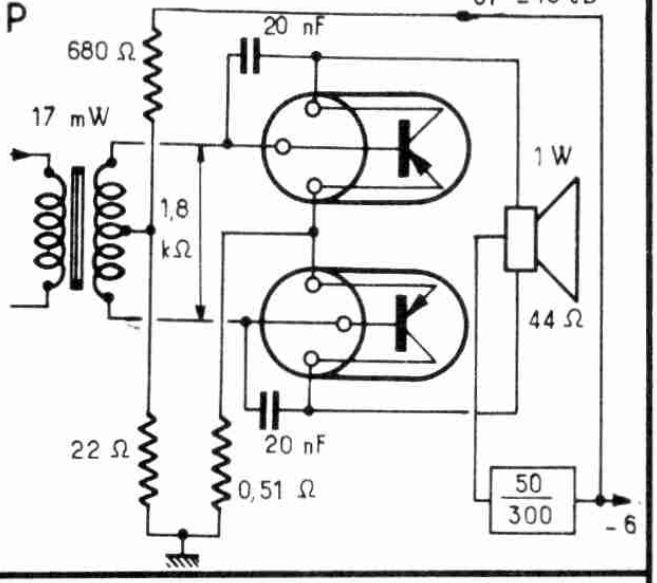
AC 138
B.F.

β = 100



AC 139
P

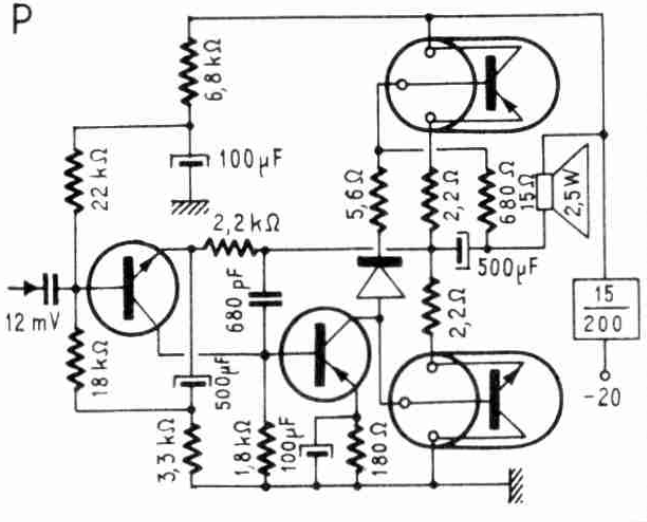
β = 85
GP = 18 dB



AC 141
AC 142
P

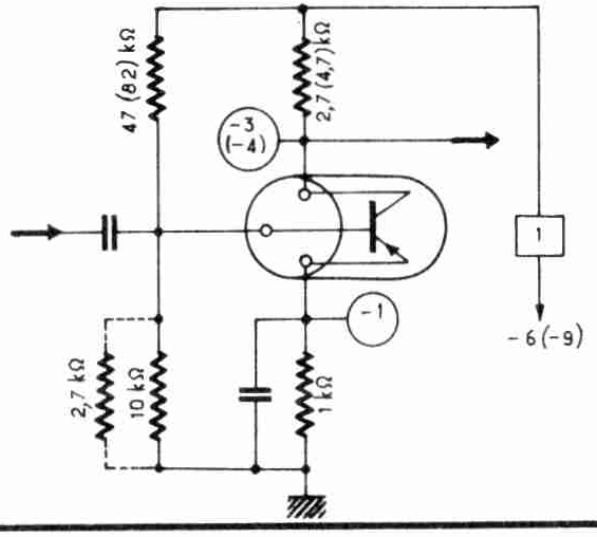
n-p-n
p-n-p

β = 40...180



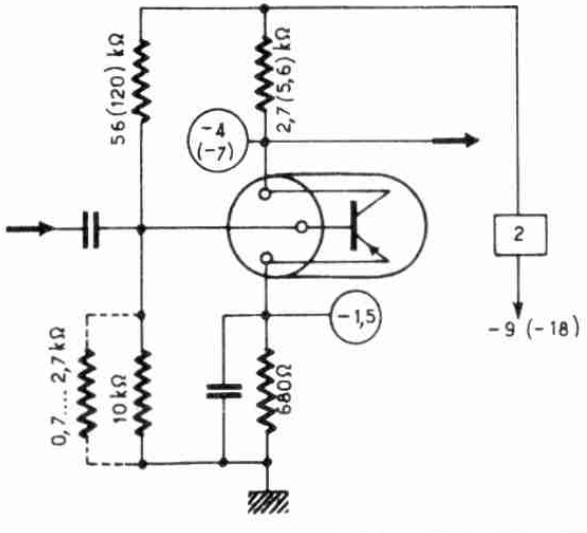
AC 150
BF

β = 85
F_b = <5 dB



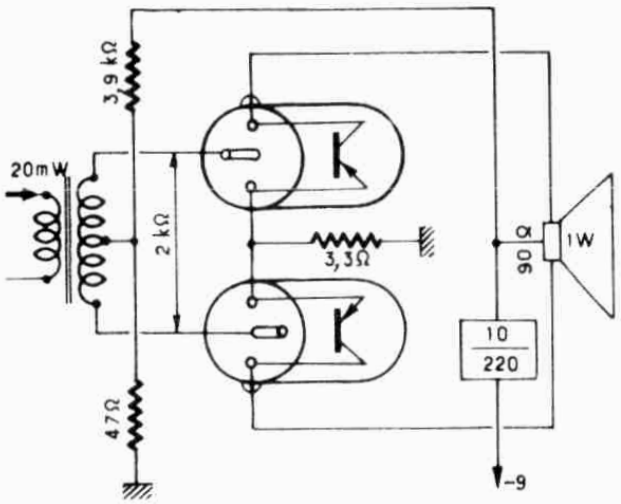
AC 151
BF

β = 45...170



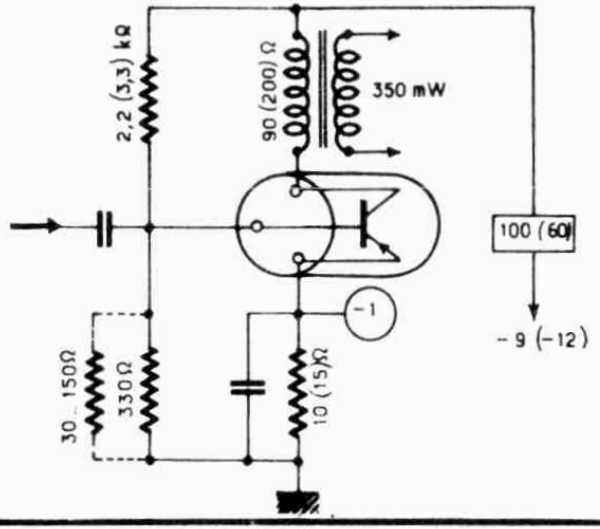
AC152
BF

β = 30...150
GP = 18 dB



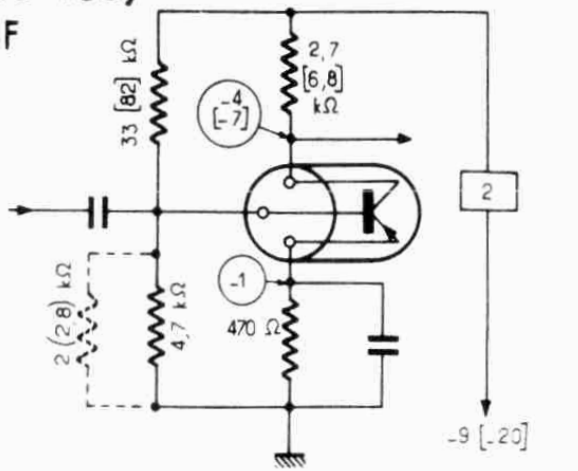
AC153
BF

β = 50...250
GP = 35...45dB



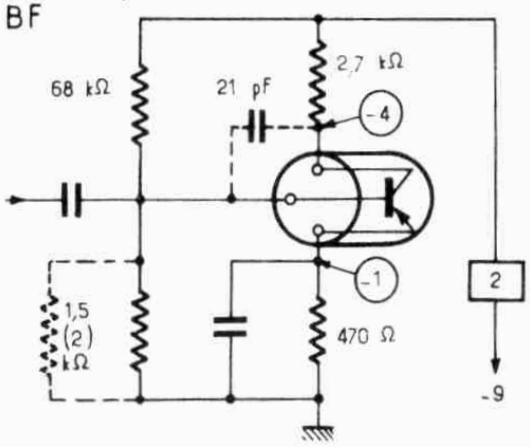
AC 162
(AC 163)
BF

β = 80...170
(130...300)
F_b = 4 dB



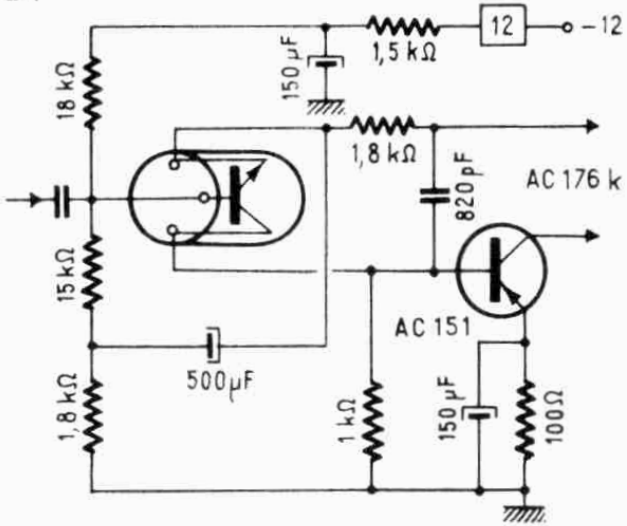
AC 170
(AC 171)
BF

β = 80...170
(130...300)
F_b = 5 dB



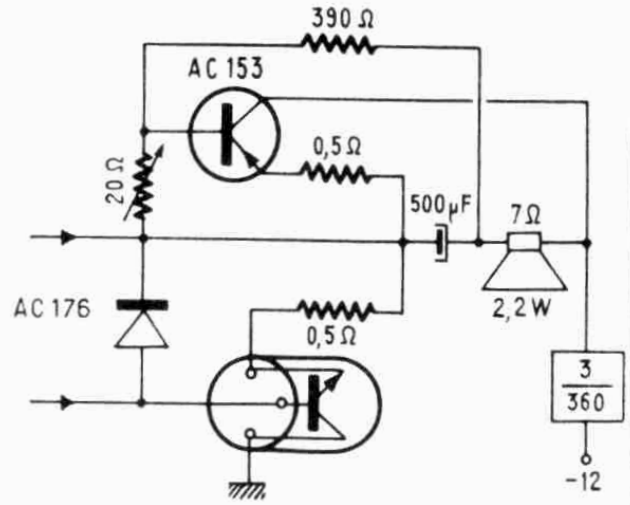
AC176
n-p-n
BF

β = 100 (>50)



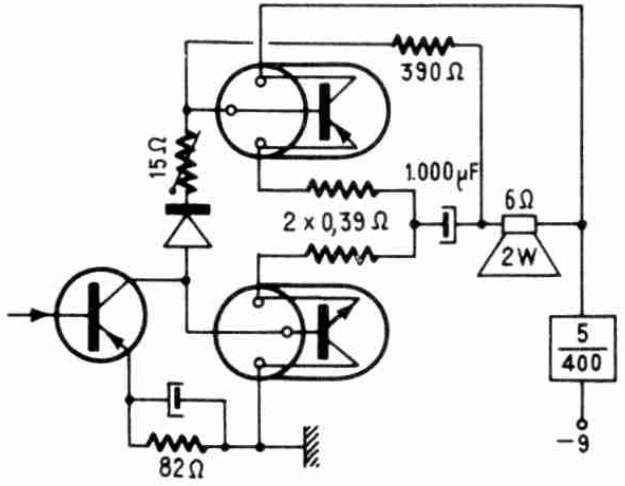
AC176 k
n-p-n
P

β = 100 (>50)



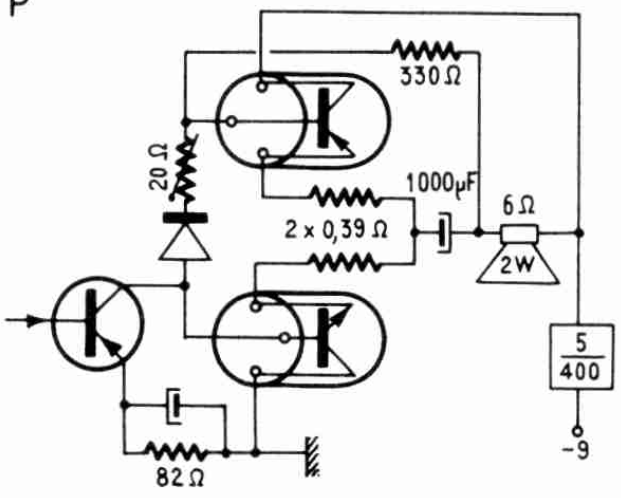
AC178 / AC179

p-n-p / n-p-n — β = 60...400



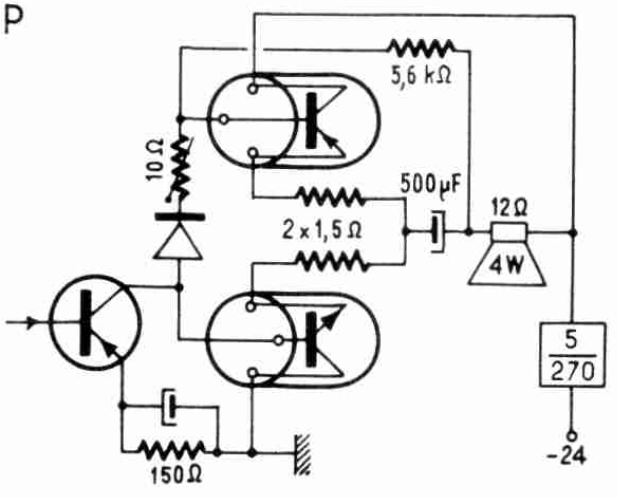
AC180 / AC181 P

p-n-p / n-p-n — β = 50...250



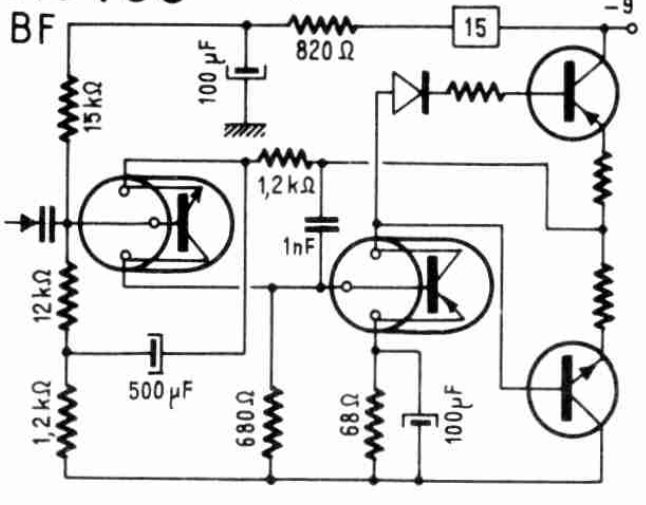
AC180 k / AC181 k P

p-n-p / n-p-n — β = 50...250



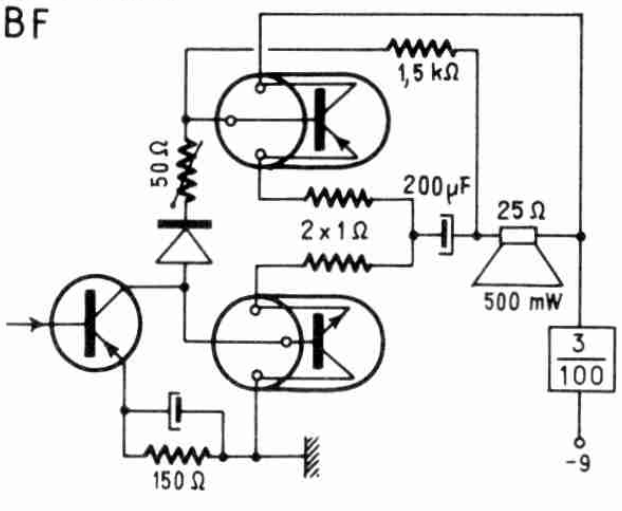
AC182 / AC183 BF

p-n-p / n-p-n — β = 50...250



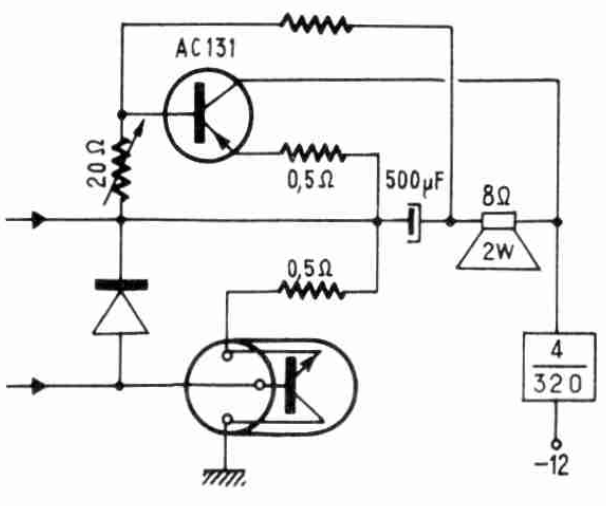
AC184 / AC185 BF

p-n-p / n-p-n — β = 50...250



AC186 P

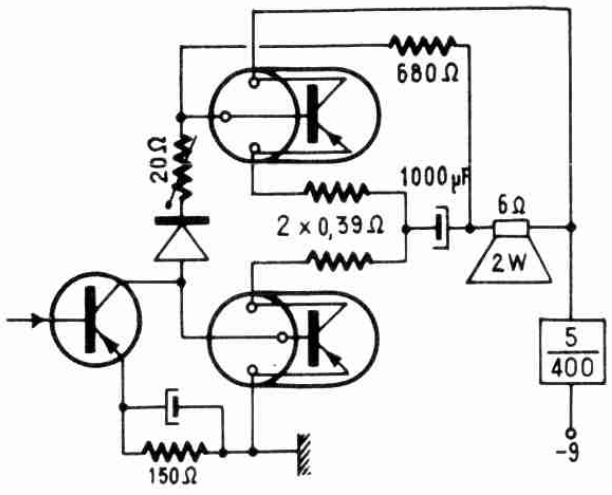
n-p-n — β = 120 (>60)



AC 187
AC 188

n-p-n
p-n-p

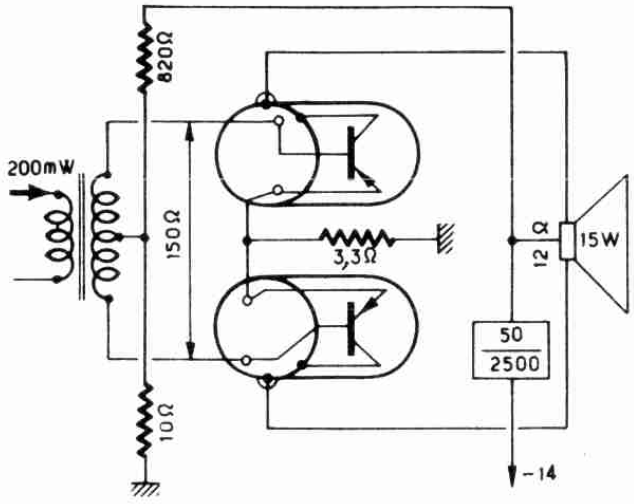
$\beta > 100$



AD 130

P

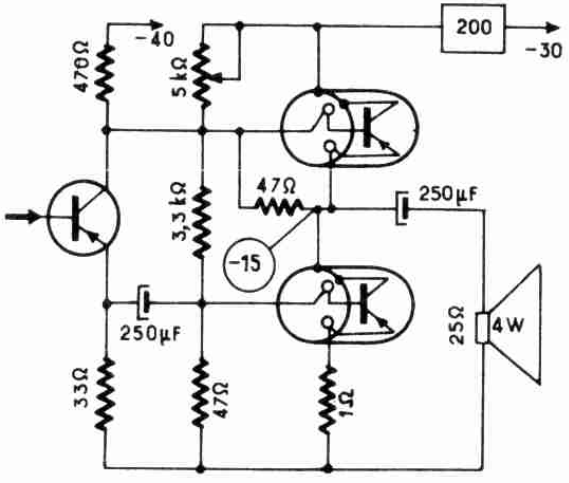
ß = 20.....100
GP = 16.....19 dB



AD 131

P

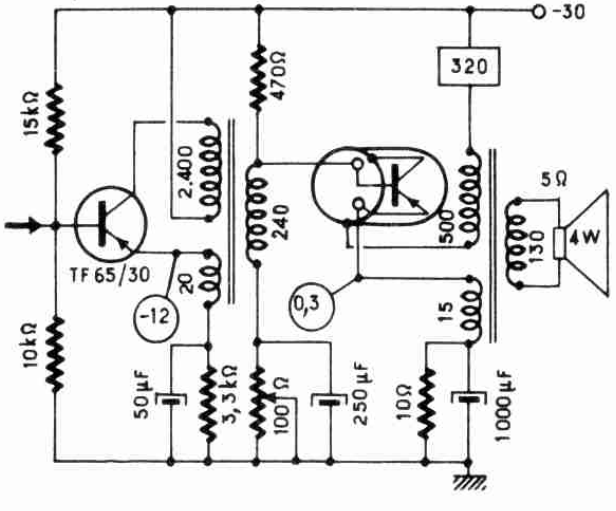
ß = 20.....40(III)
30.....60(IV)
50.....100(V)



AD 132

P

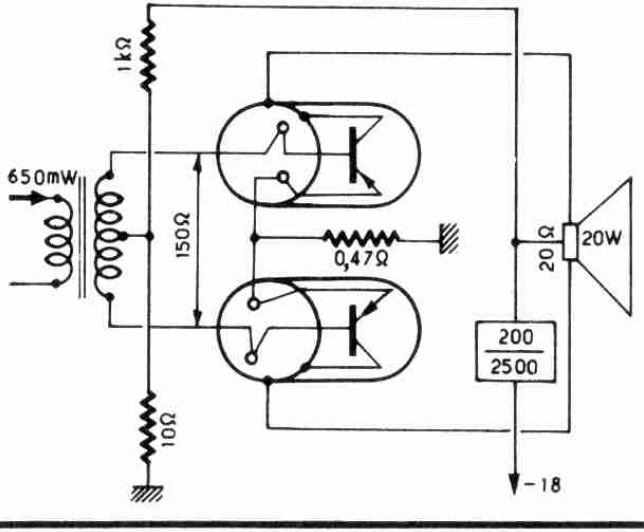
ß = 15.....60



AD 133

P

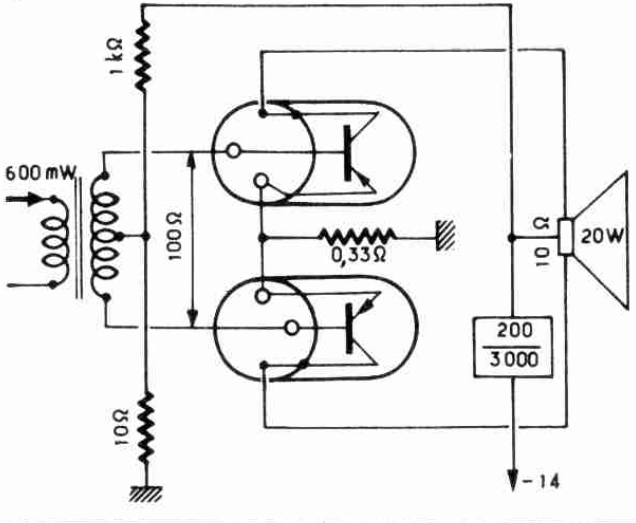
β = 20...60
GP = 15 dB



AD 136

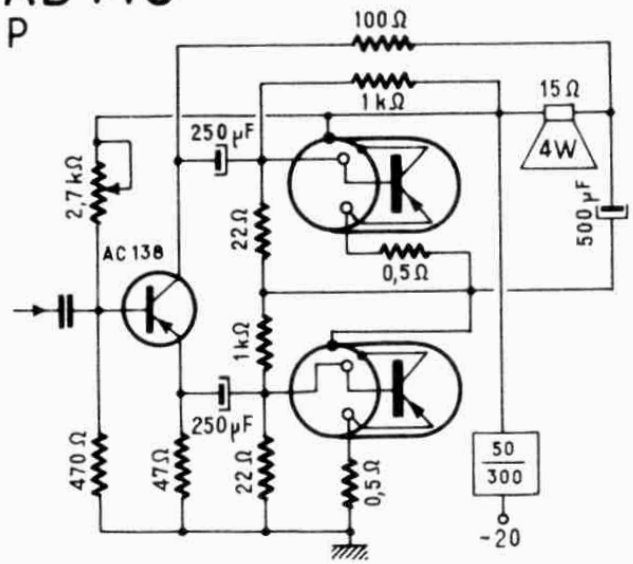
P

β 20...100
GP > 16 dB



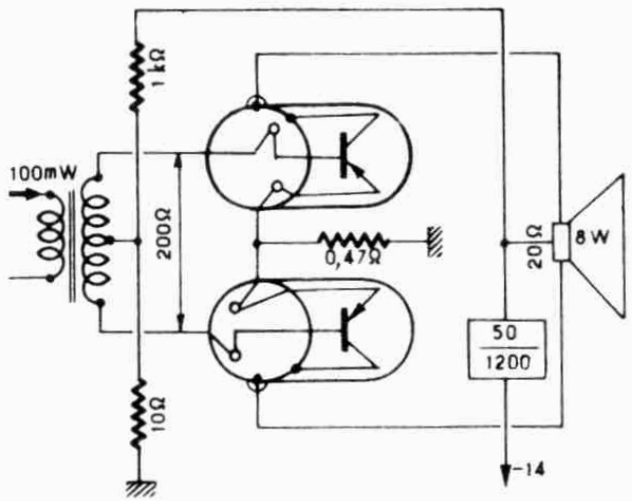
AD145
P

β > 30



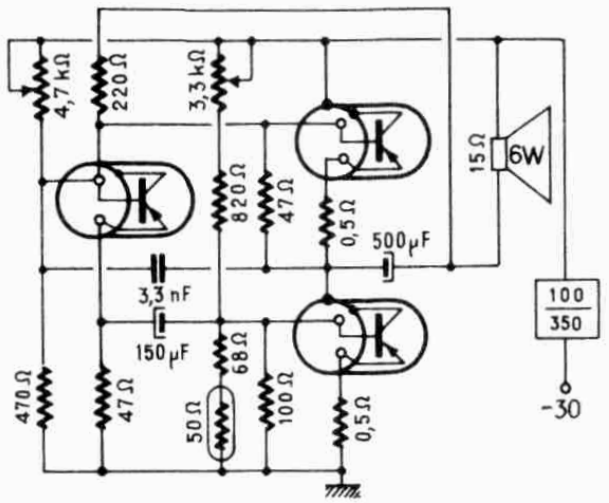
AD148
P

β = 30...100
GP = 19 dB



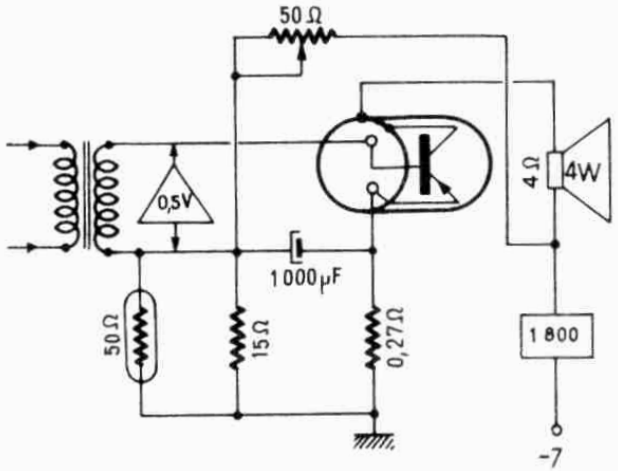
AD148
P

β = 30... 100



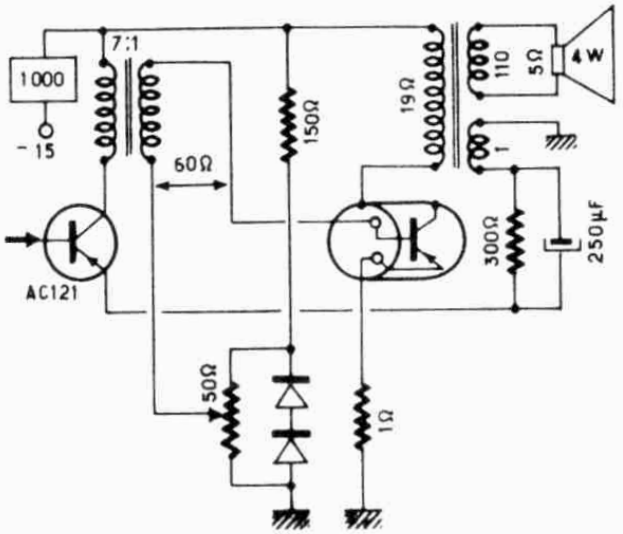
AD149
P

β = 30... 100
GP = 15... 18 dB



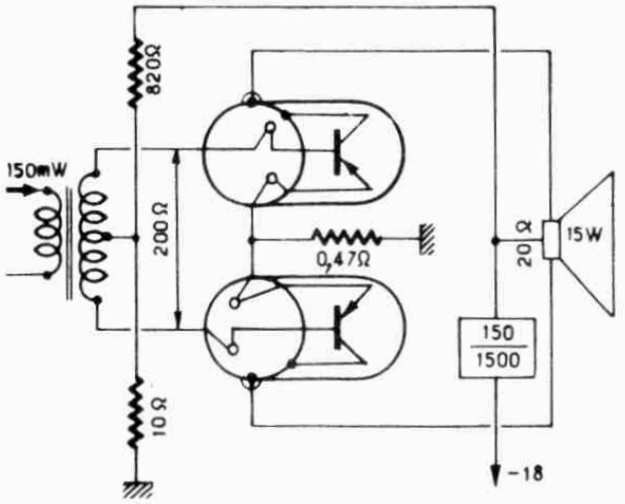
AD149
P

β = 30...100
GP = 20 dB



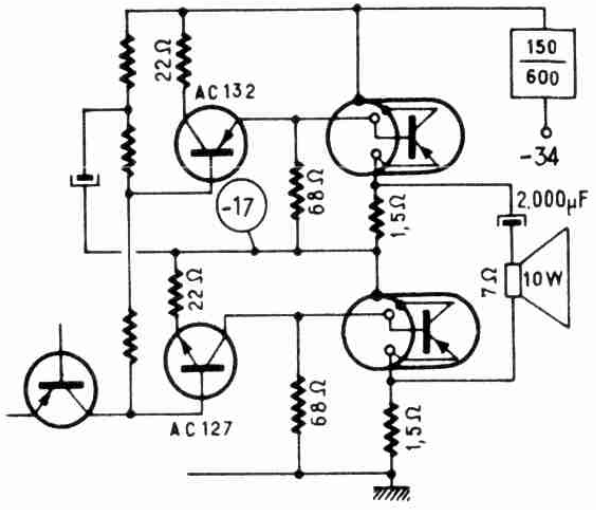
AD149
P

β = 30...100
GP = 20 dB



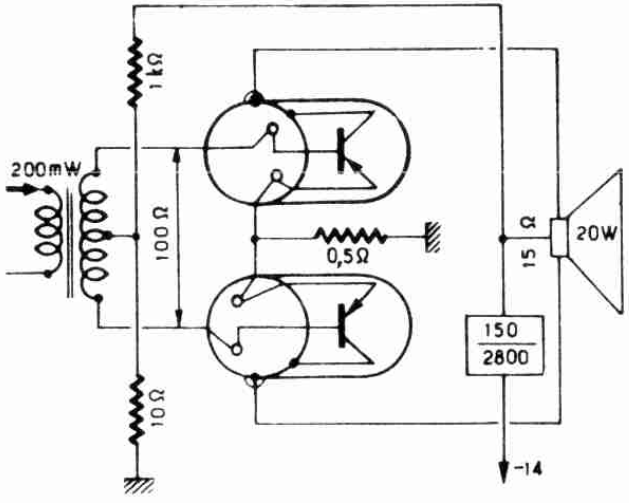
AD 149
P

β = 30... 100



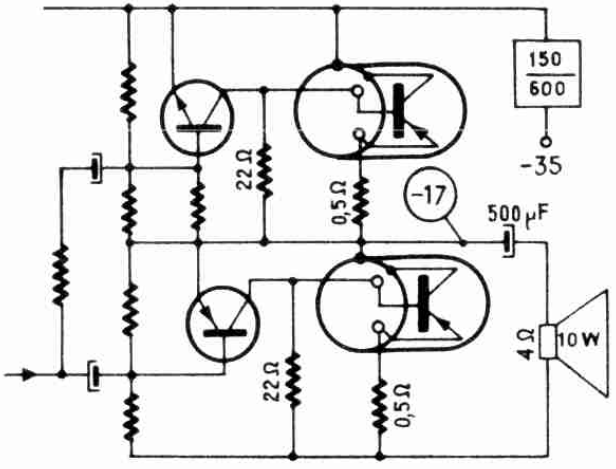
AD 150
P

β = 30...100
GP = 20 dB



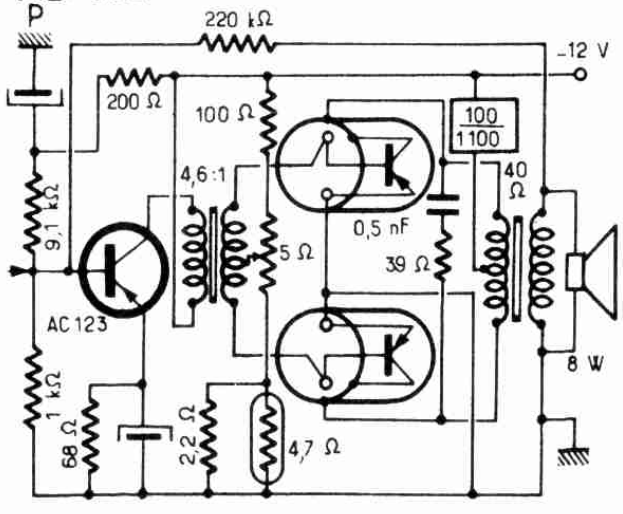
AD 150
P

β = 30... 100



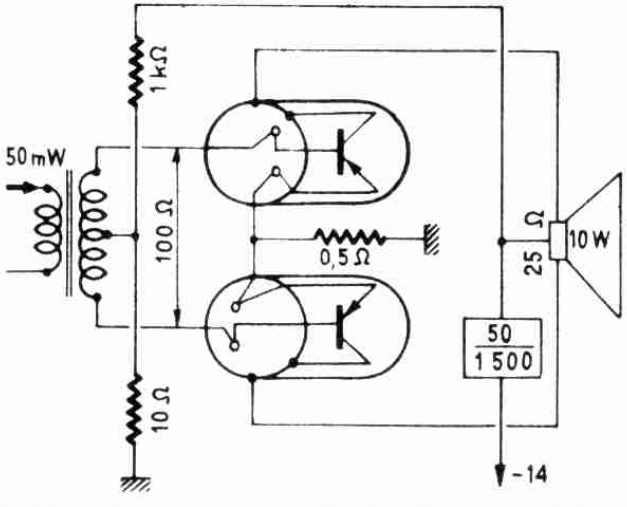
AD 152
P

β = 50... 150



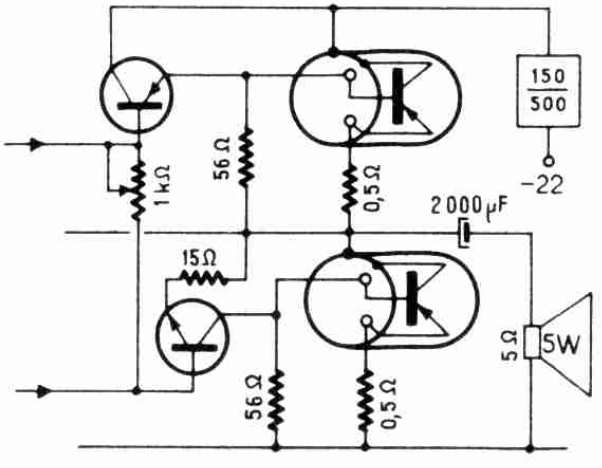
AD 153
P

β = 50
GP = 23 dB



AD 155
P

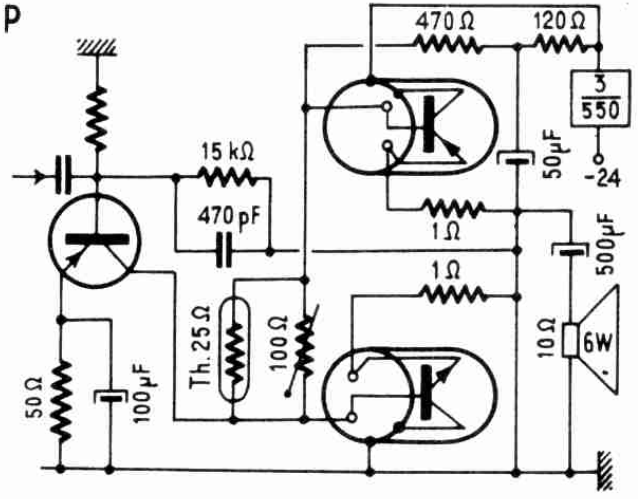
β = 115(>40)



AD161
AD162
P

n-p-n
p-n-p

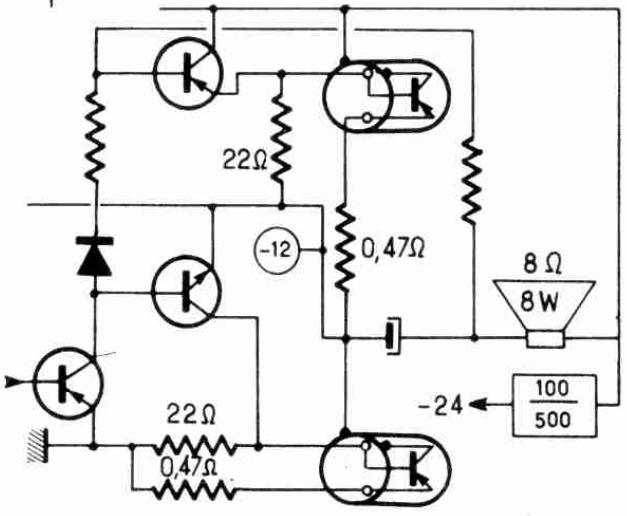
β = 50... 250



AD162
(AD164)
P

p-n-p

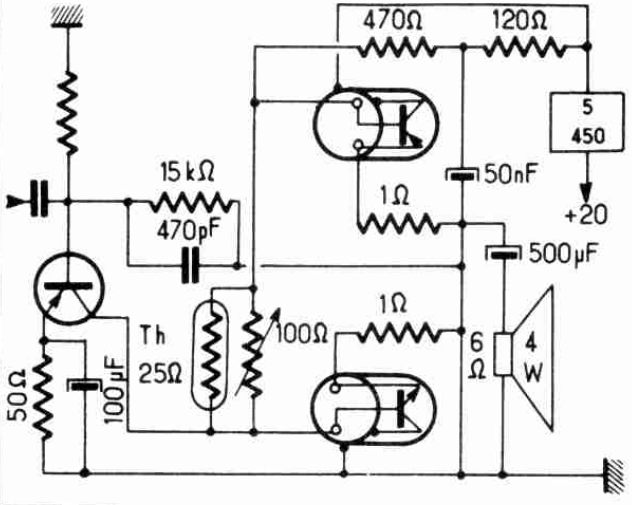
β = 50....250
(>60)



AD164
AD165
P

p-n-p
n-p-n

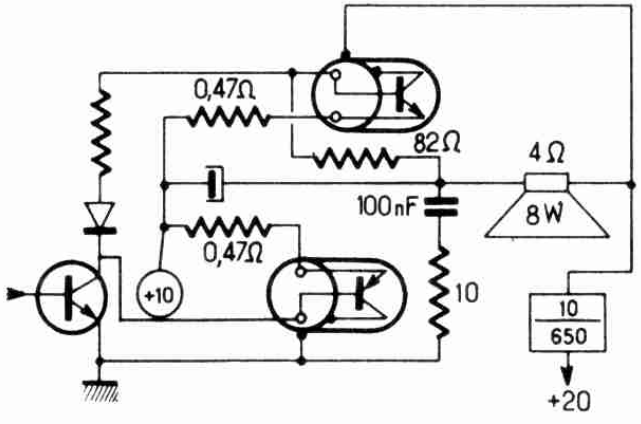
β = 185 (>60)



AD 262
BD 162
P

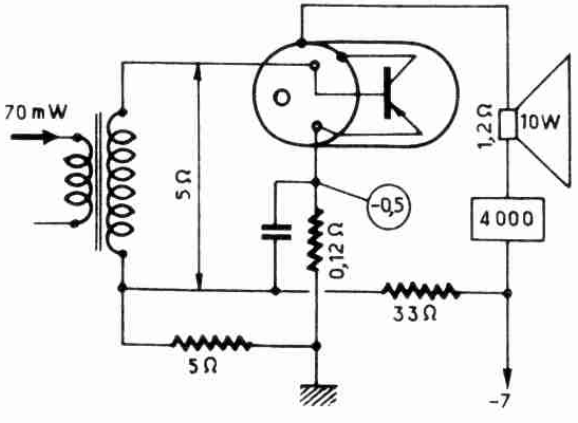
p-n-p Ge
n-p-n Si

β > 30



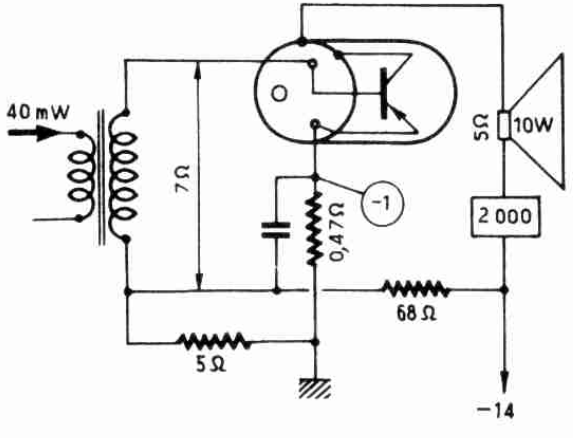
ADZ11
P

β = 35
GP = 22 dB



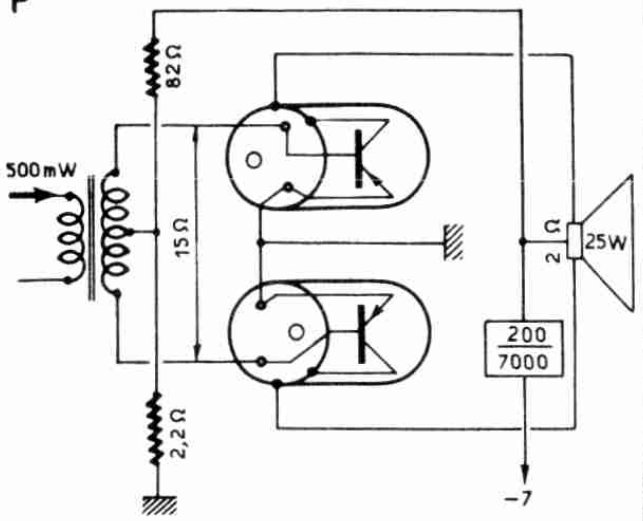
ADZ11
P

β = 35
GP = 24 dB



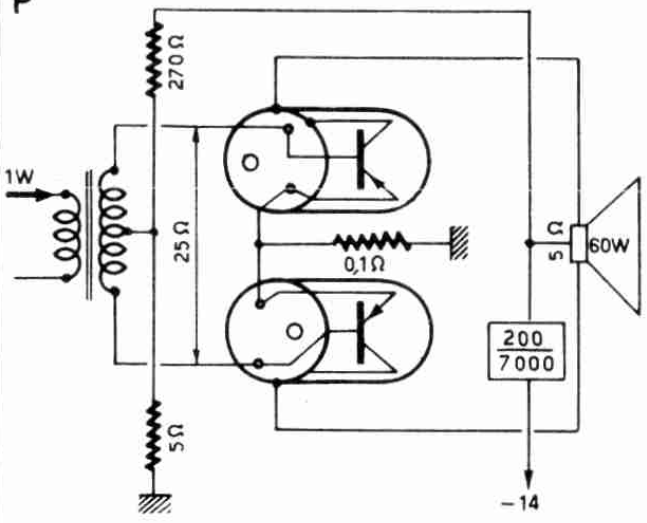
ADZ11
P

β = 35
GP = 17 dB



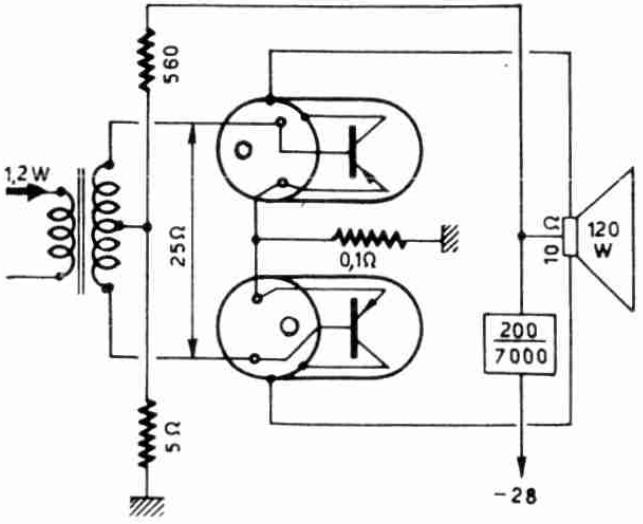
ADZ11
P

β = 35
GP = 18 dB



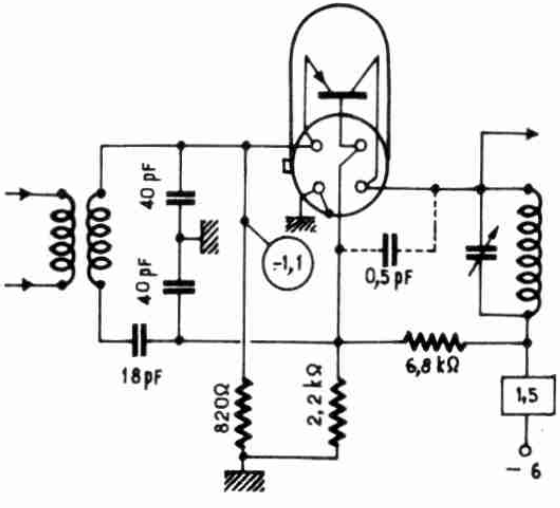
ADZ 12
P

β > 15
GP = 20 dB



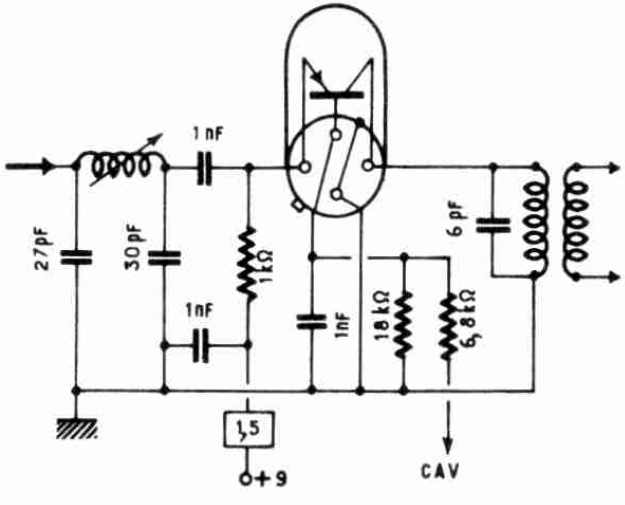
AF106
100 MHz

β = 50...120
F_b = 5,5 dB



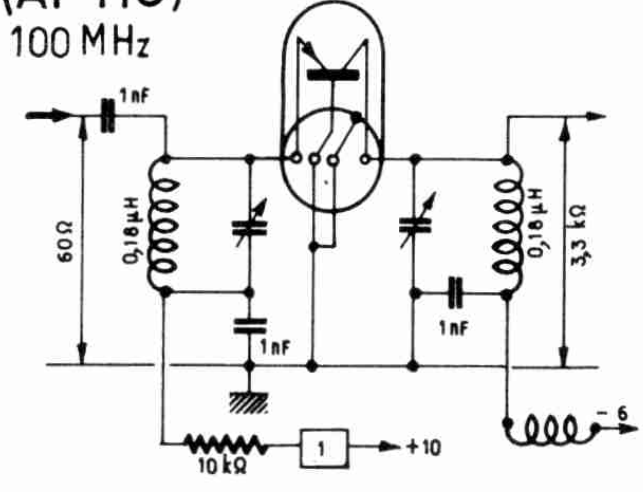
AF106 (AF109)
200 MHz

β = 50...120
F_b = 5,5 dB
GP = 14 (13) dB



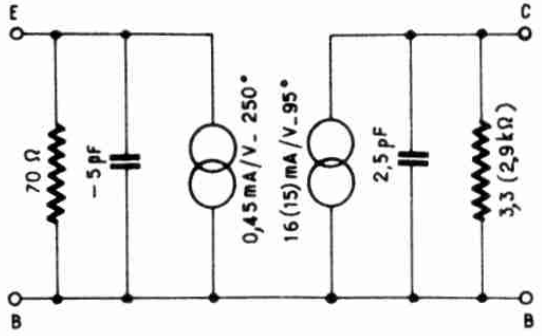
AF 114 (AF 115)
100 MHz

β = 150
Fb = 8 dB (100 MHz)
GP = 14 (13) dB



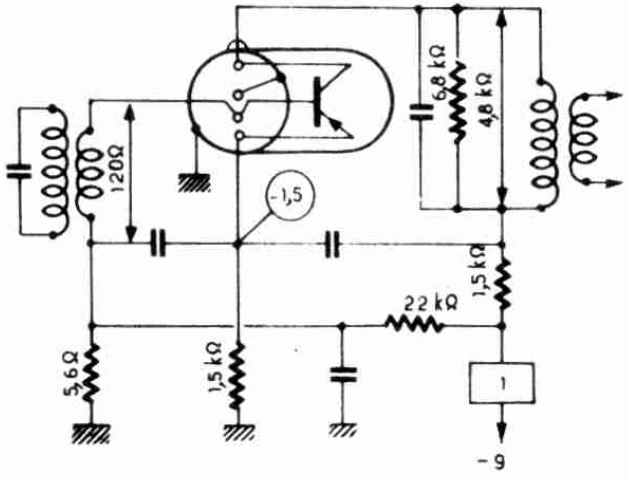
AF 114 (AF 115)

Vc = 6 V
Ic = 1 mA
f = 100 MHz



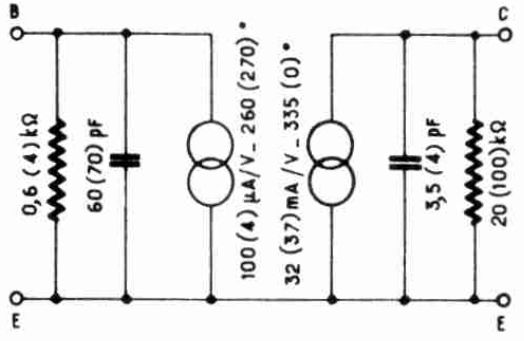
AF 116
10,7 MHz

β = 150
Fb = 3dB10(MHz)
GP = 25 dB



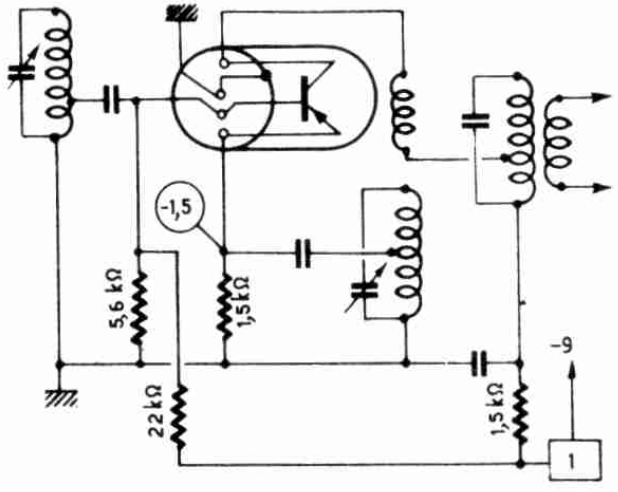
AF 116
10,7 (0,45) MHz

Vc = 6V
Ic = 1 mA



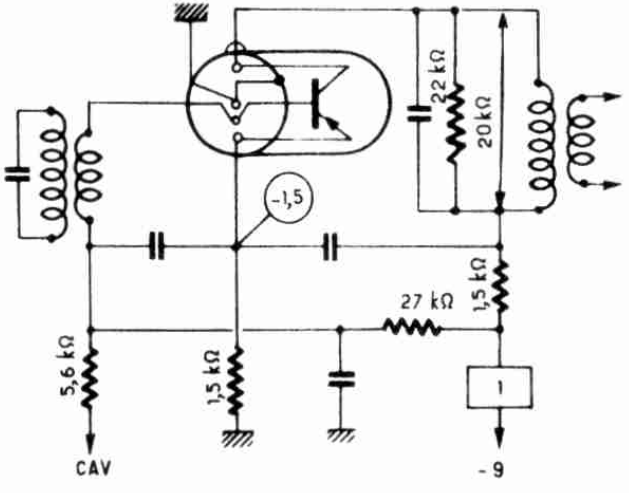
AF 117
Conv. < 2 MHz

β = 150
Fb = 4 dB (Conv.)



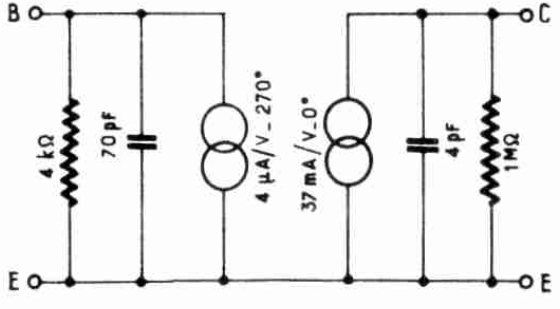
AF 117
MF 450 kHz

β = 150
Fb = 1,5 dB (1 MHz)
GP = 42 dB



AF 117

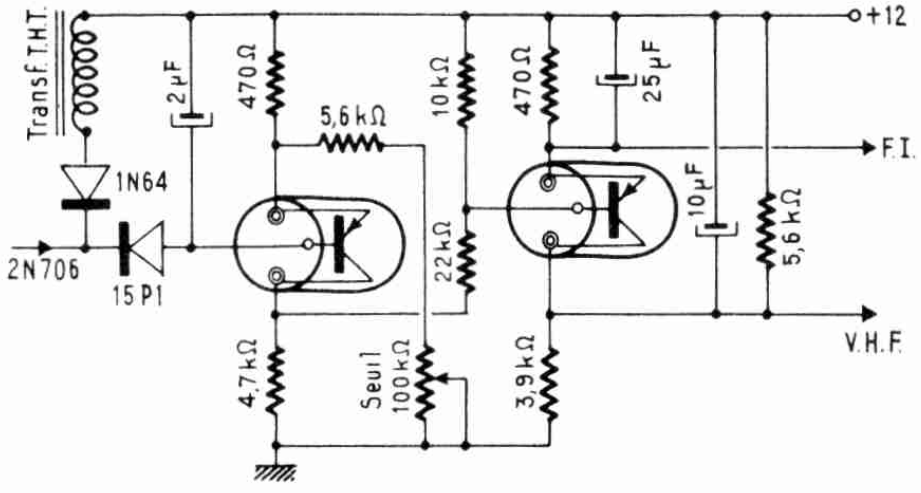
Vc = 6V
Ic = 1 mA
f = 450 kHz



2 N 396

p-n-p Ge β = 30...150

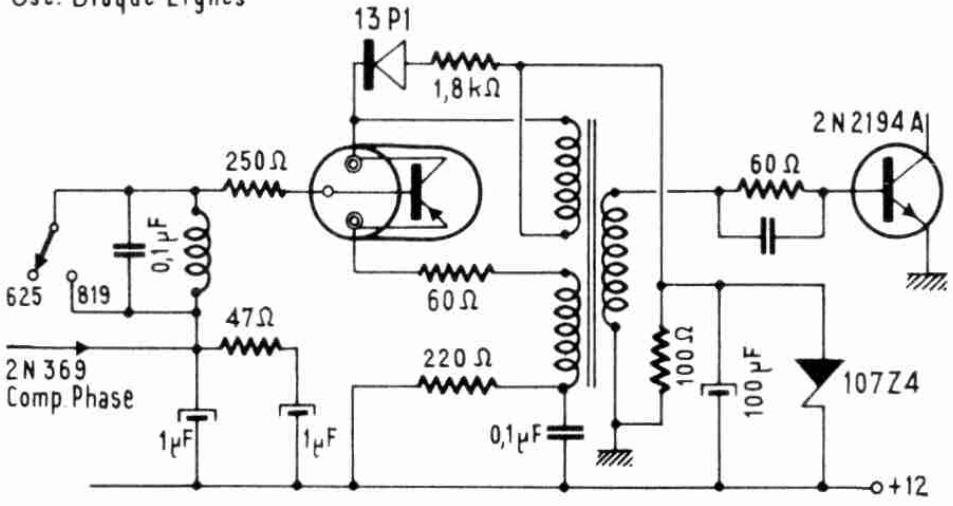
C.A.G.



2 N 397

p-n-p Ge β = 40...150

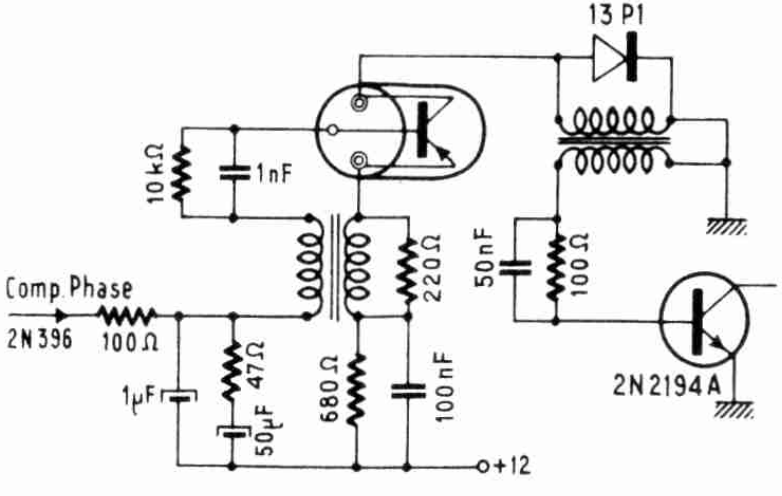
Osc. Bloqué Lignes



2 N 397

p-n-p Ge β = 40...150

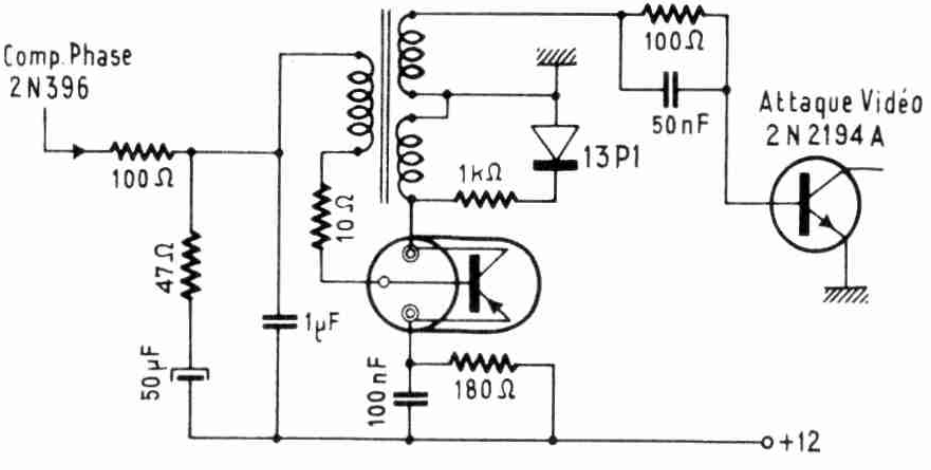
Osc. Bloqué Lignes



2 N 397

p-n-p Ge β = 40...150

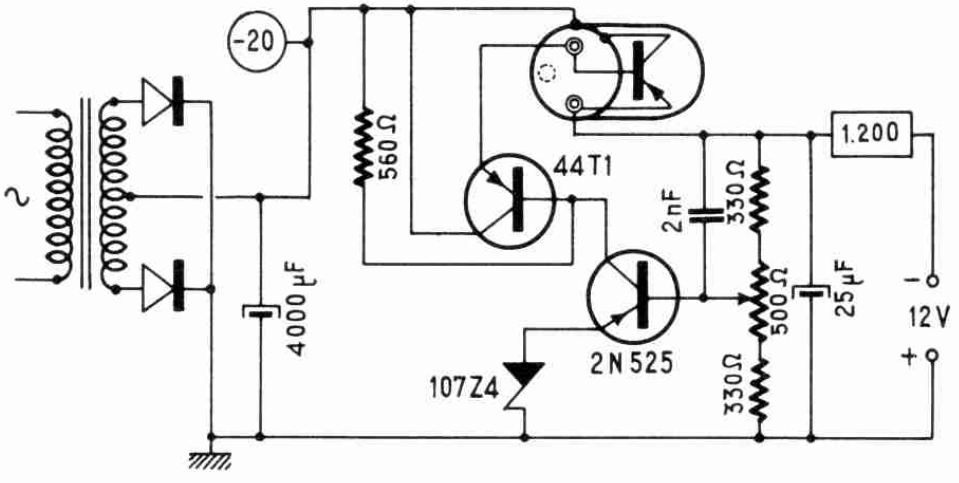
Osc. Bloqué Lignes



2N 441

p-n-p Ge Alliage β = 20...40 à I_C = 5A

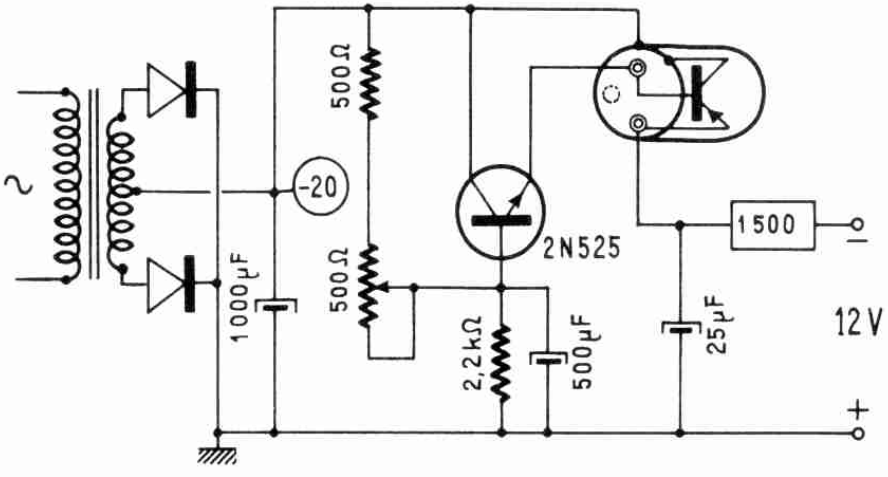
Alim. Stabilisée



2N 441

p-n-p Ge Alliage β = 20...40 à I_C = 5A

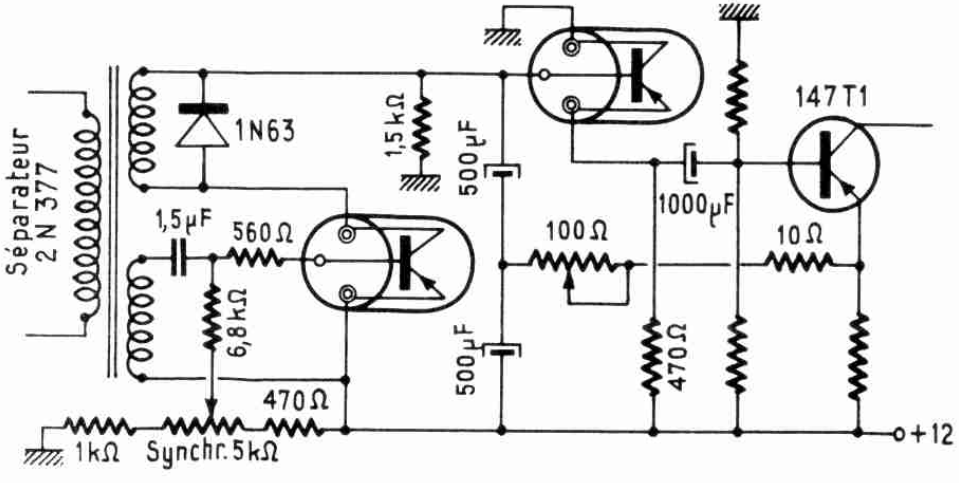
Alim. Filtrée



2N 525

p-n-p Ge Alliage β = 30...64

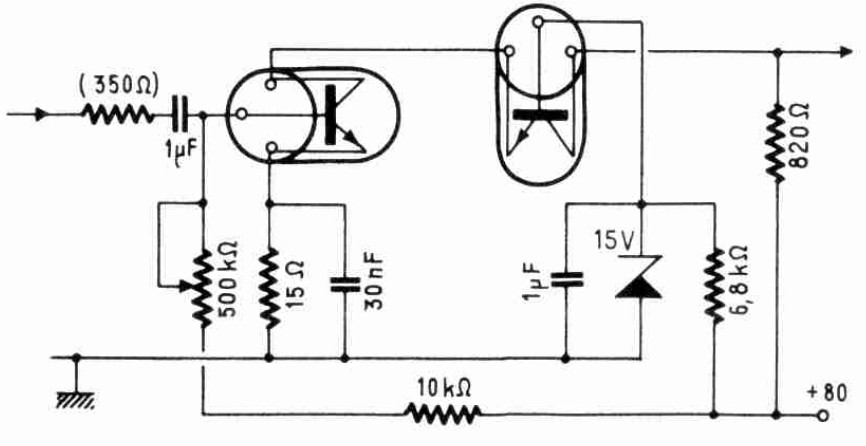
Osc. Bloqué Im. 819L



2N 697

n-n-n Si Planar β = 40...120 GV = 50 tr = 70 ns

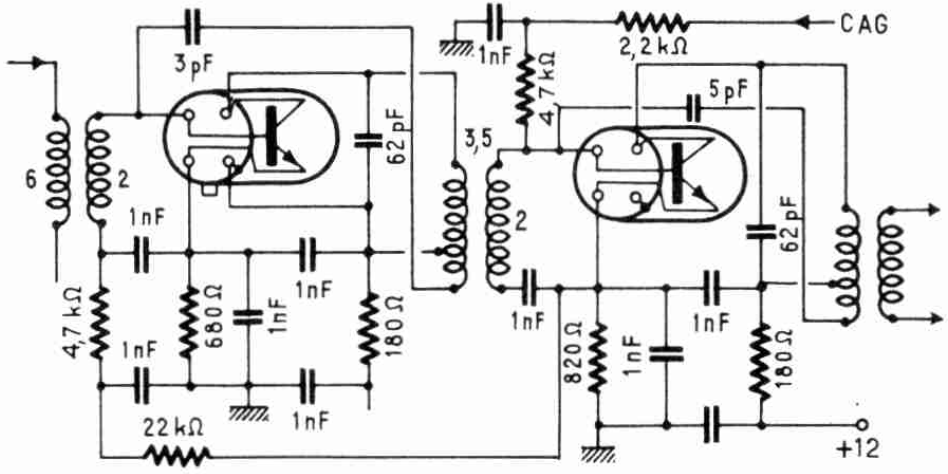
Vidéo



2N918

n-p-n Si Pl. Epit. $\beta = 50\ (>20)$ (9 à 100 MHz)
$F_b = 3$ dB (60 MHz)
GP = 30 dB

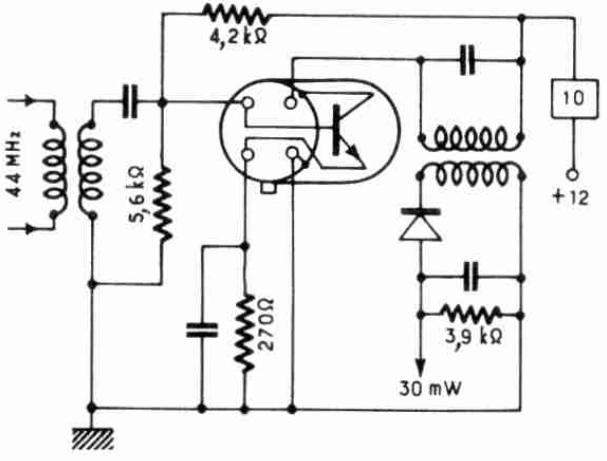
FI 45 MHz $\Delta F = 4$ MHz



2N918

n-p-n Si Pl. Epit. $\beta < 20$
GP = 30 dB

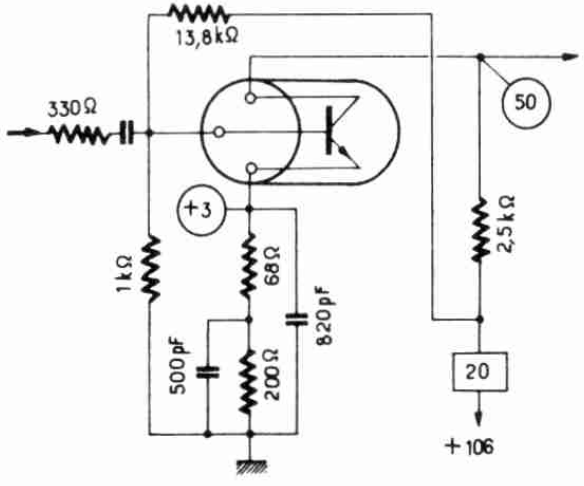
FI Image (III)



2N1335, 36, 37

n-p-n Si $\beta = 15$
GV = 18 dB

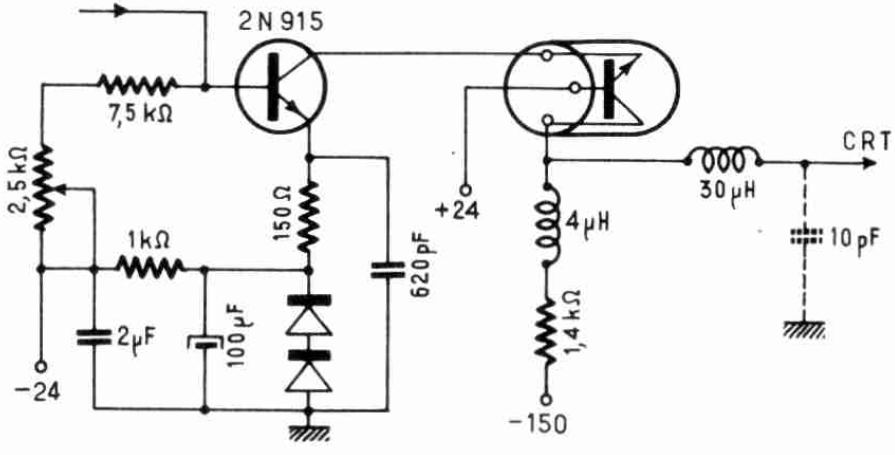
Vidéo < 6,5 MHz



2N1974

n-p-n Si Planar $\beta = 70$

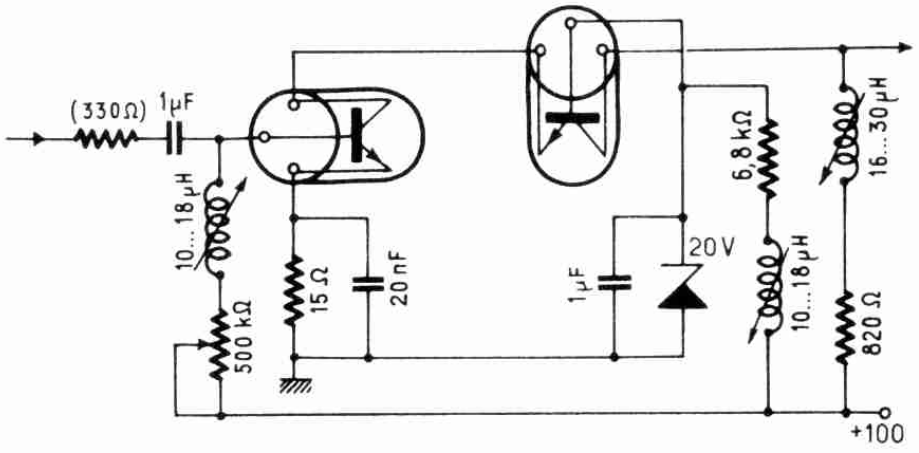
Sortie Vidéo



2N699

n-p-n Si Planar β = 40...120 GV = 50 tr = 60 ns

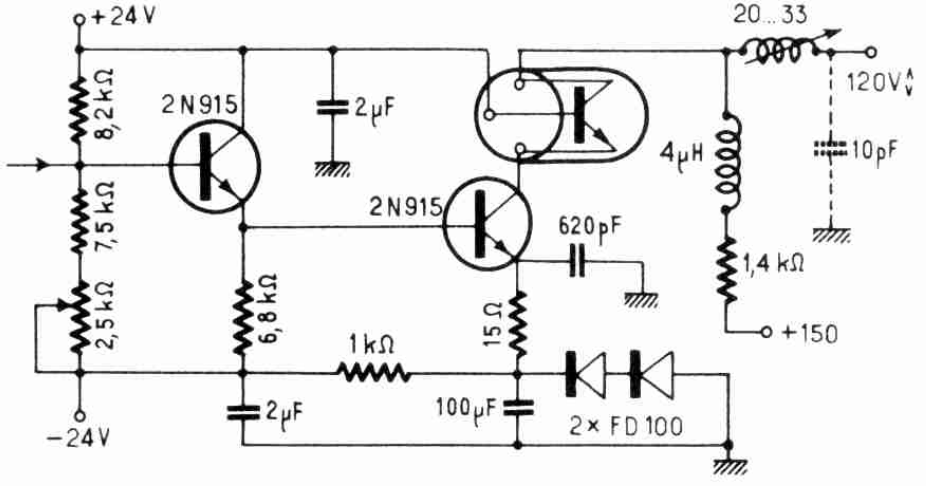
Vidéo



2N699B

n-p-n Si Planar β = 40... 120 tr = 40 ns

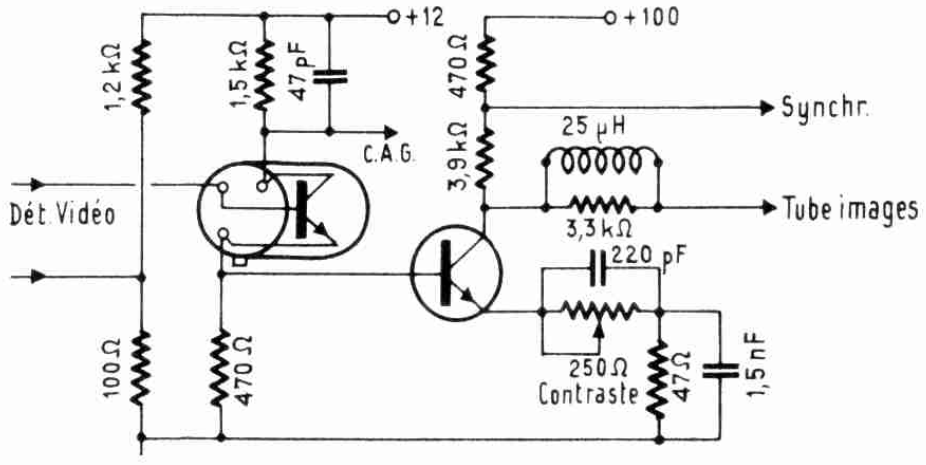
Vidéo



2N706

n-p-n Si Planar β > 20

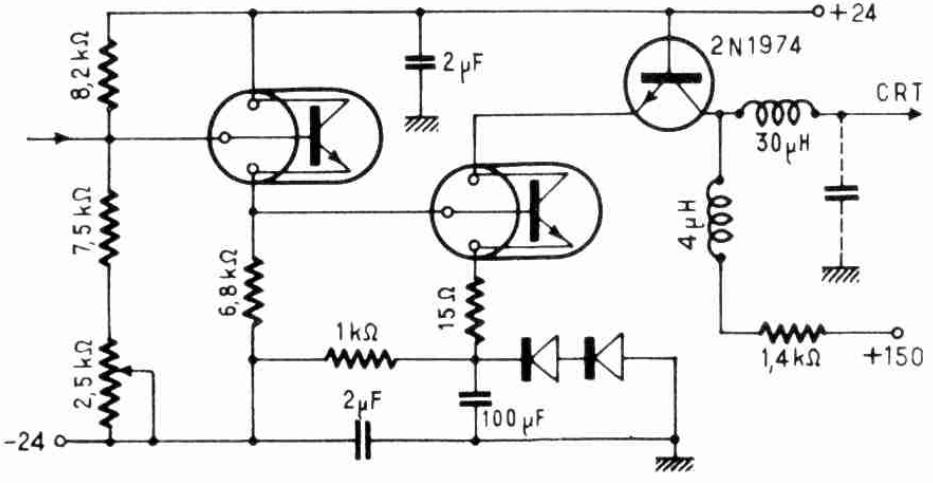
Préamplif. Vidéo 819 L



2N915

n-p-n Si Planar β = 50...200

Vidéo

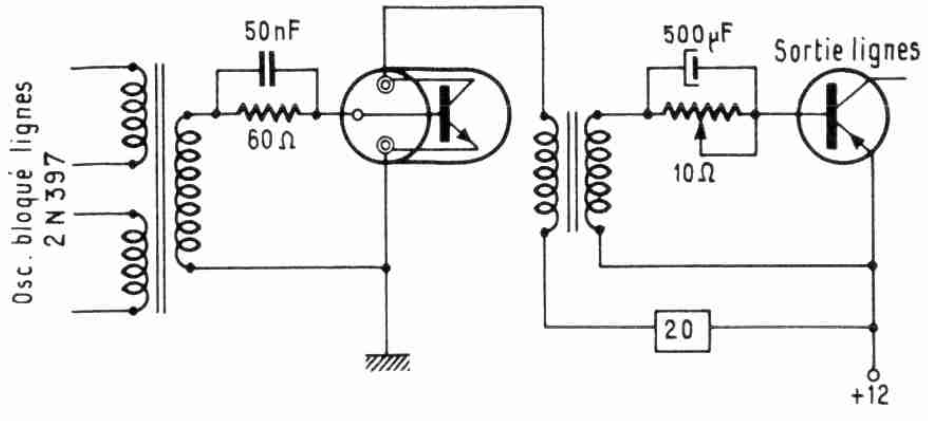


2N2194A

n-p-n Si
Planar épitaxial

β > 15

Attaque Dév. Hor. 819L

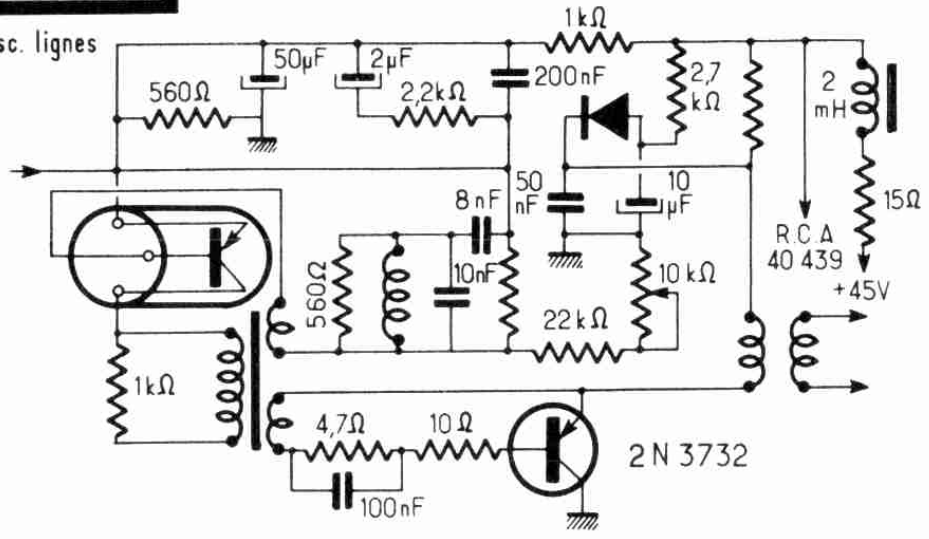


2N2614

p-n-p Ge

β = 160 f_t = 10 MHz

Osc. lignes

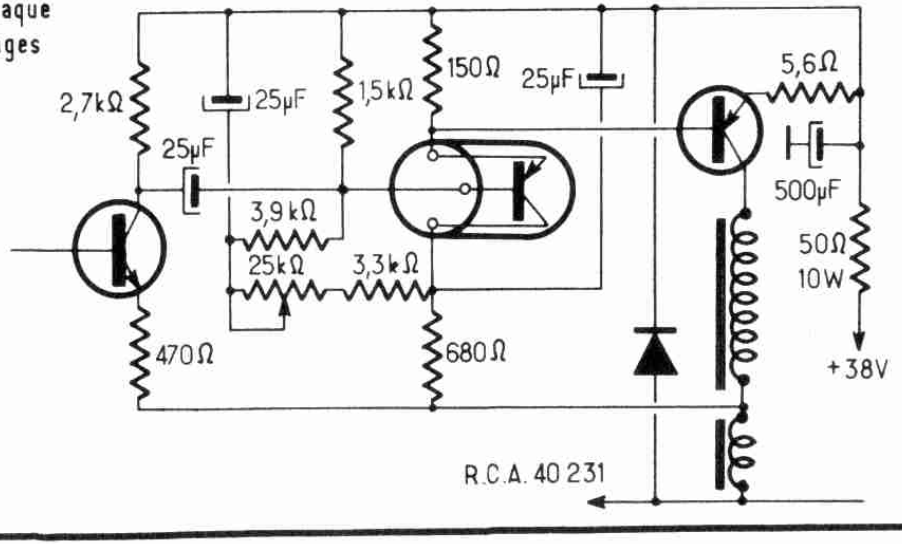


2N2614

p-n-p Ge All.

β = 160

Attaque images

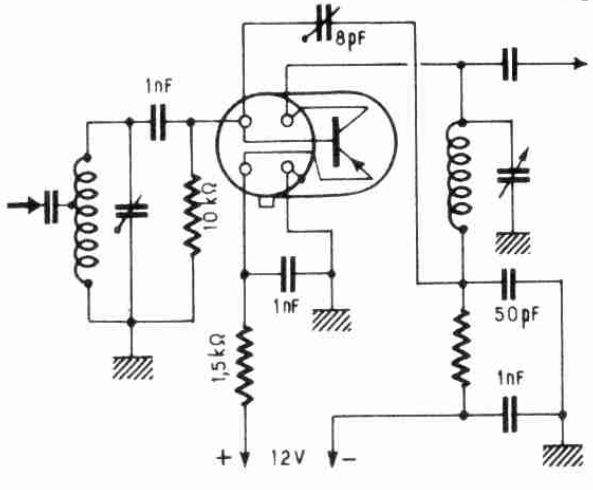


2N2708

200 MHz

p-n-p Ge

β = 30 ... 180
GP = 15 ... 22 dB
F_b = < 8,5 dB

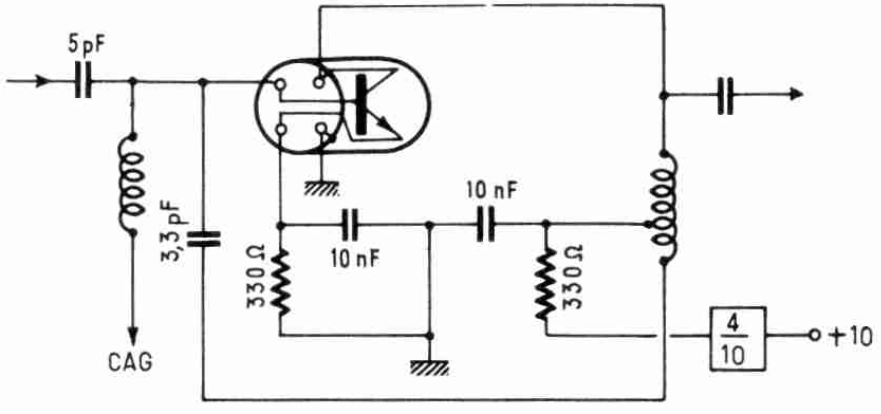


2N3337

n-p-n Si Planar

β => 30 (> 4 à 100 MHz)
GP = 30 dB
CAG = −30 dB

45 MHz

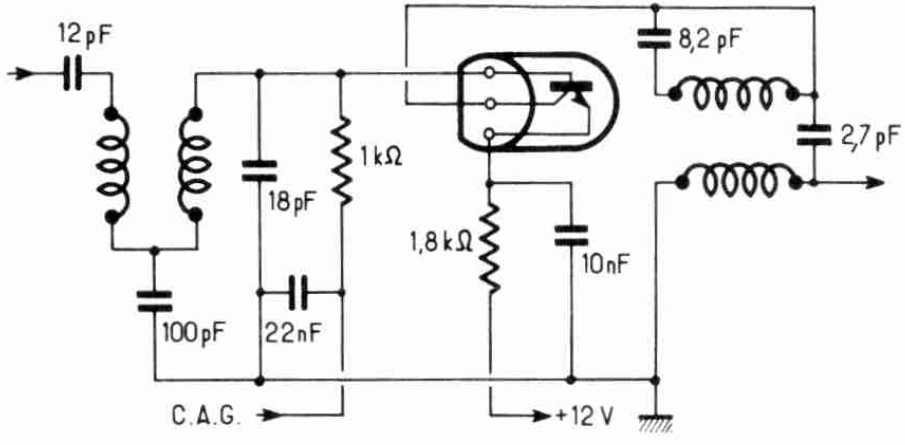


2N3663

n-p-n Si

β > 20
f_T = 700 MHz

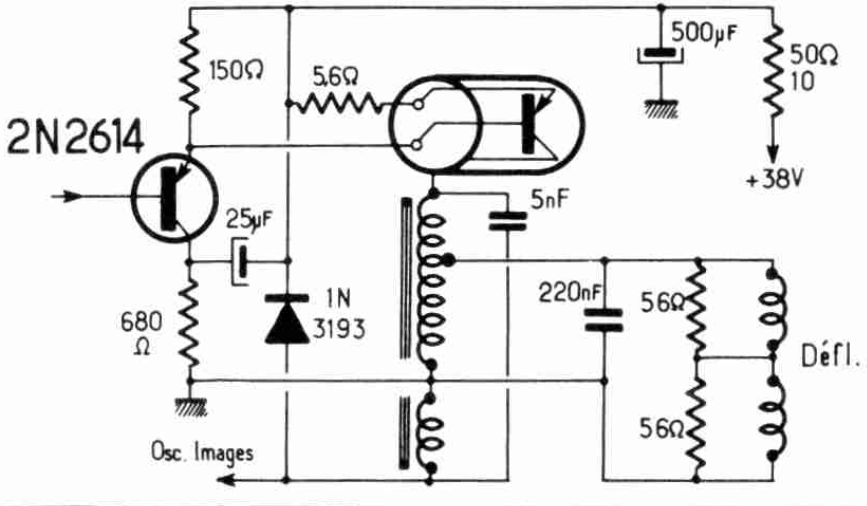
F. I. image



2N3730

p-n-p Ge Diff.

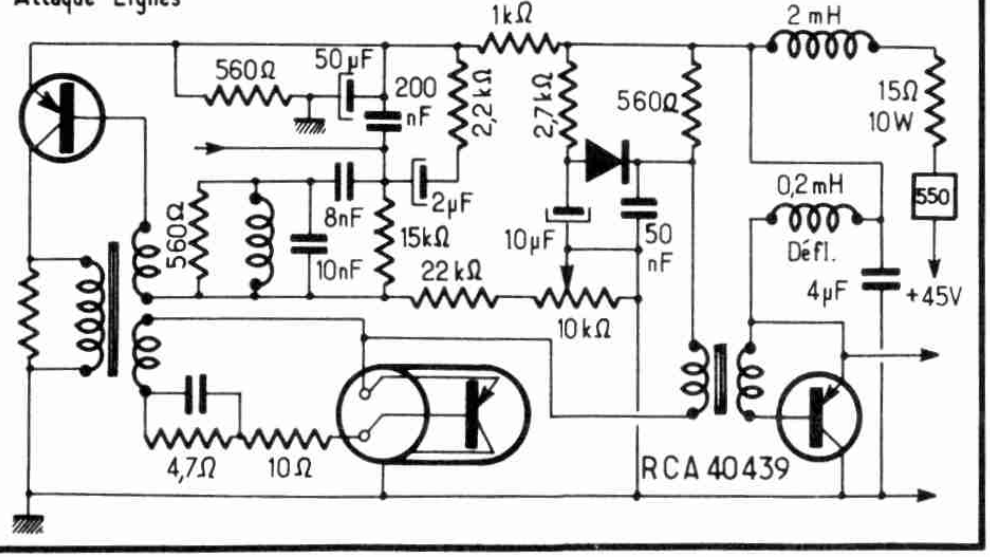
Sortie Images



2N3732

p-n-p Ge Diff.

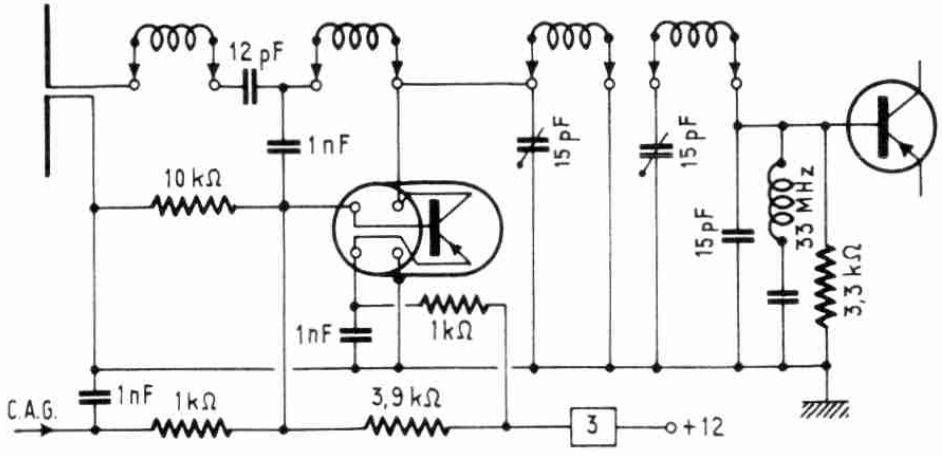
Attaque Lignes



2N3783

p-n-p Ge F_b<6,5 dB ß>20 f_T>800MHz GP>20dB

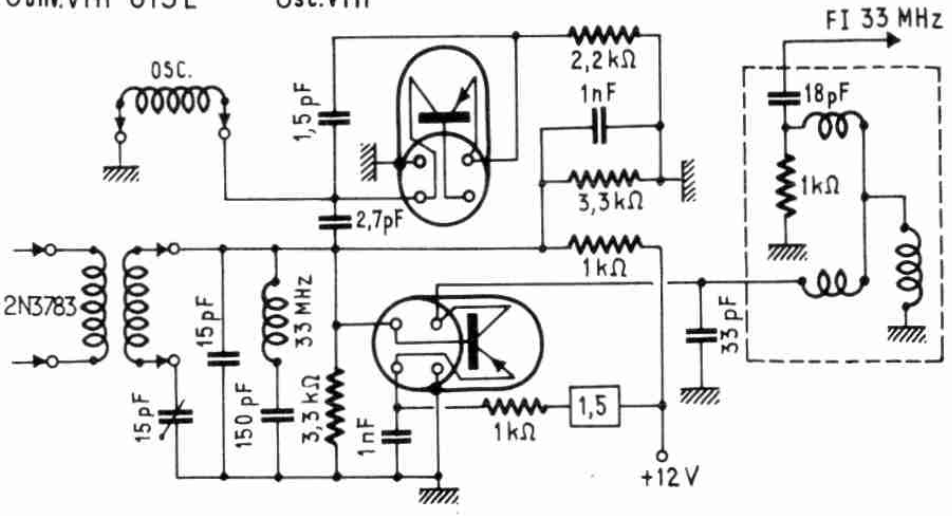
Entrée VHF



2N3784 2N3785

p-n-p Ge ß>20(>13)

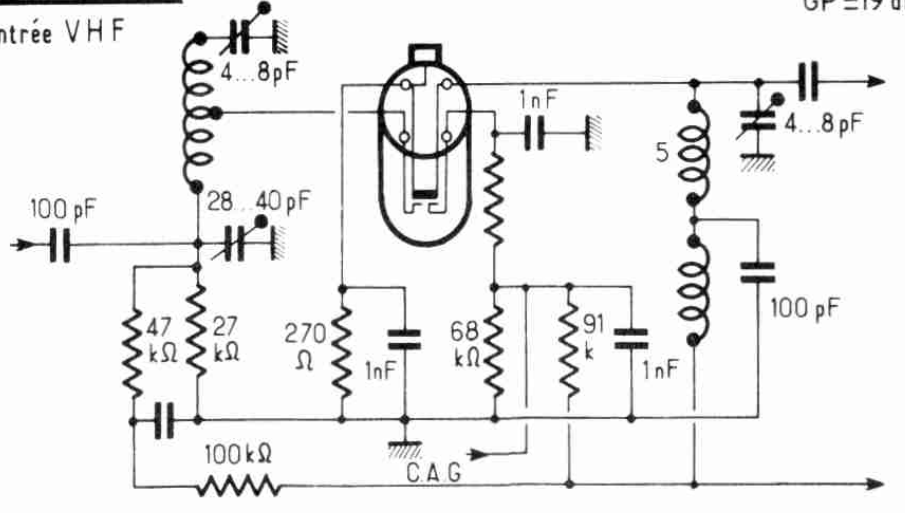
Conv.VHF 819 L Osc.VHF



3N140

MOS Canal N s=6...10mA/V F_b=3,5 dB GP=19 dB

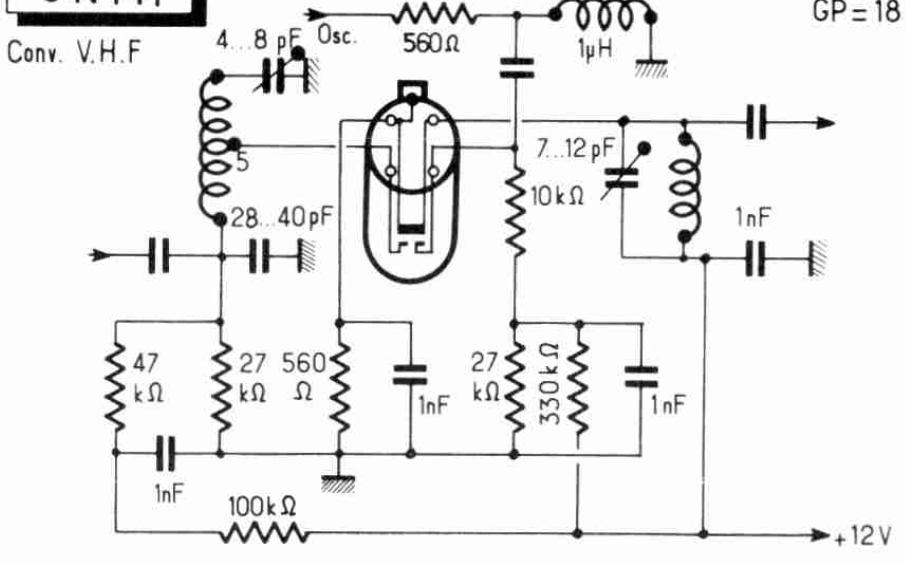
Entrée VHF



3N141

MOS Canal N s=6....10mA/V GP=18 dB

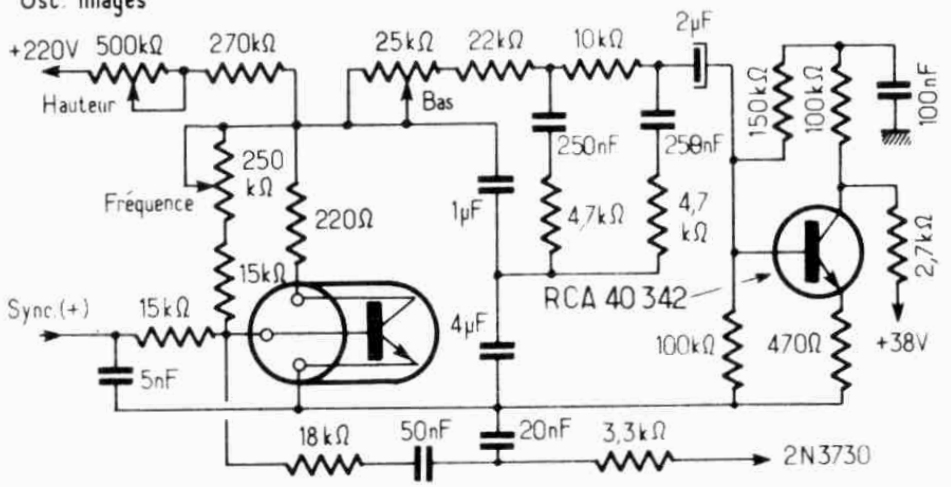
Conv. V.H.F



40231 RCA

n-p-n Si Planar β=80

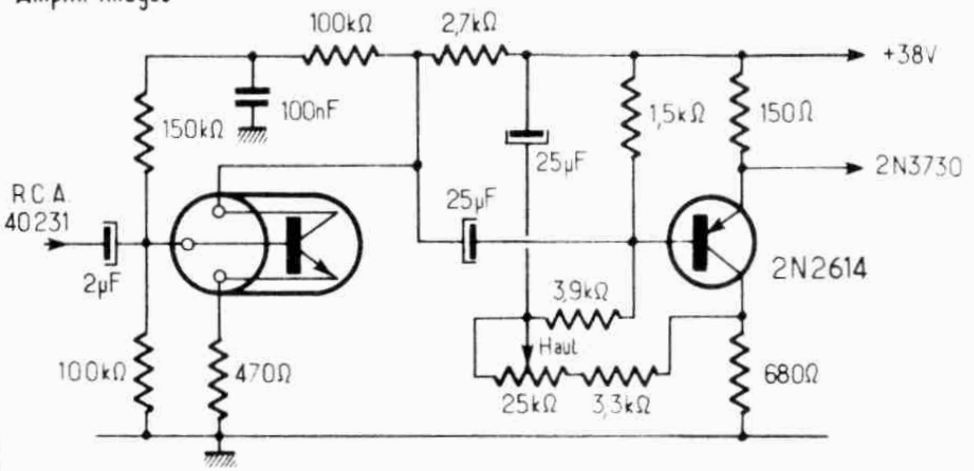
Osc. images



40232 RCA

n-p-n Si Planar β=175

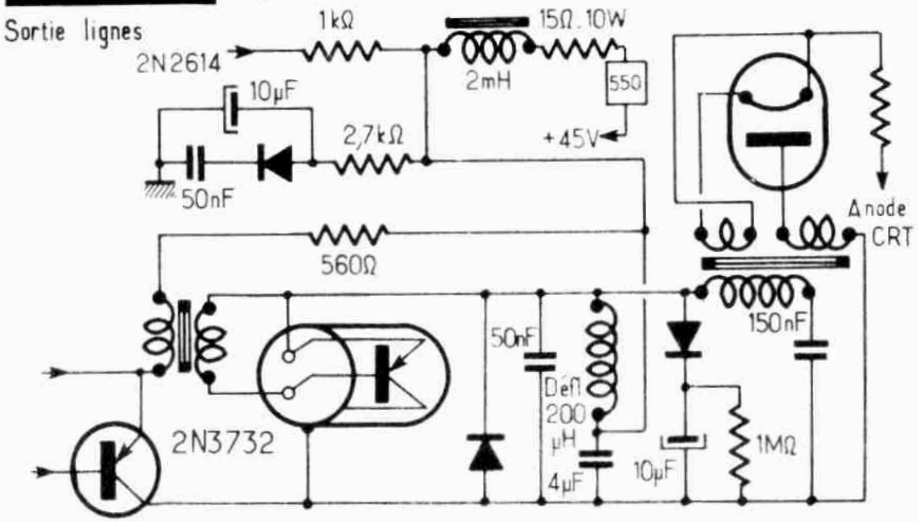
Amplif. images



40439 RCA

p-n-p Ge Diff.

Sortie lignes



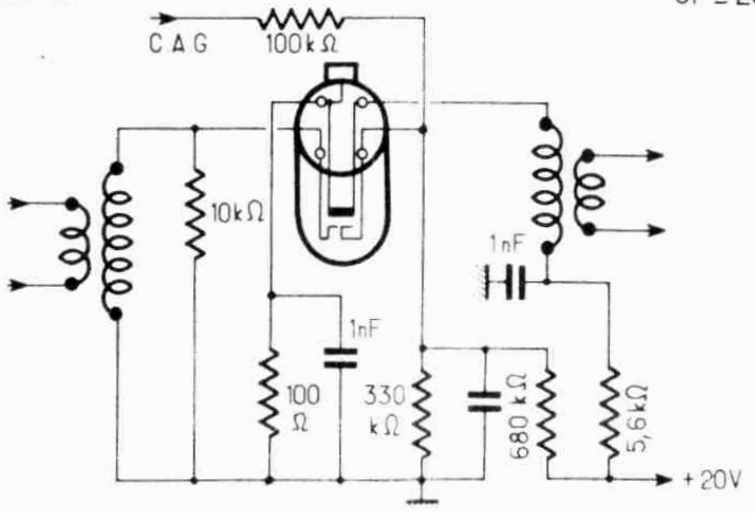
40602RCA

MOS Canal N

s = 10 mA/V

GP = 28 dB

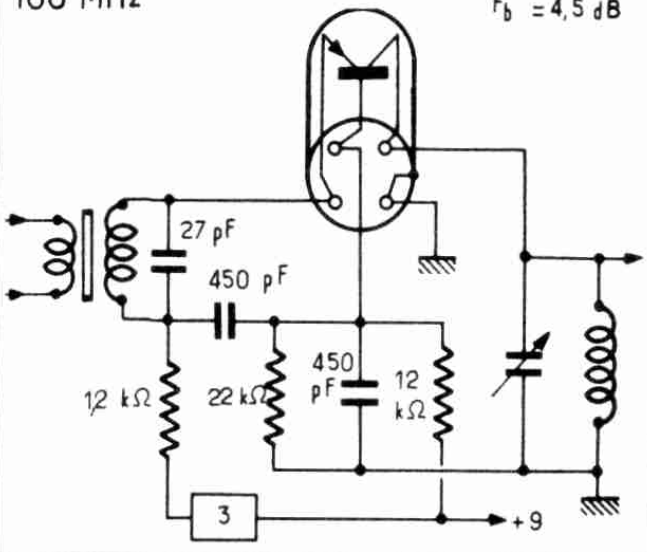
F.I. image



AF 121

100 MHz

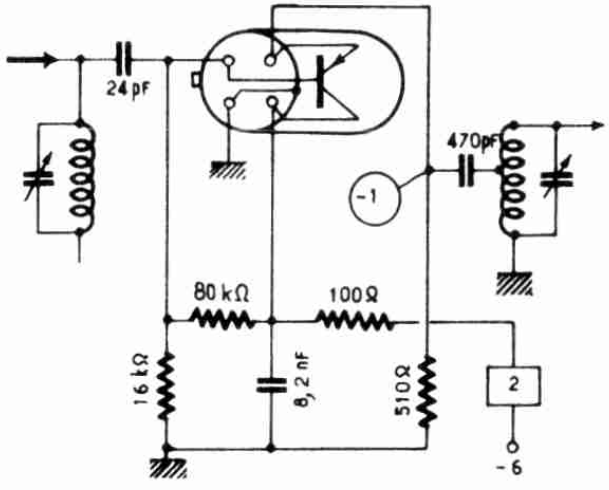
$\beta = 80$
GP = 19 dB
F_b = 4,5 dB



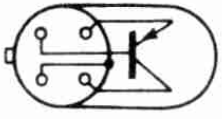
AF124 (= AF 114)

100 MHz

β = 150
F_b = 8 dB
GP = 14 dB



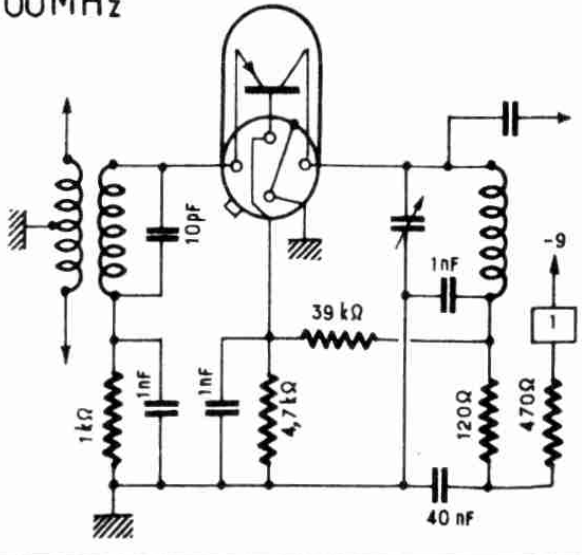
AF125 = AF115
AF126 = AF116
AF127 = AF117



AF134

100 MHz

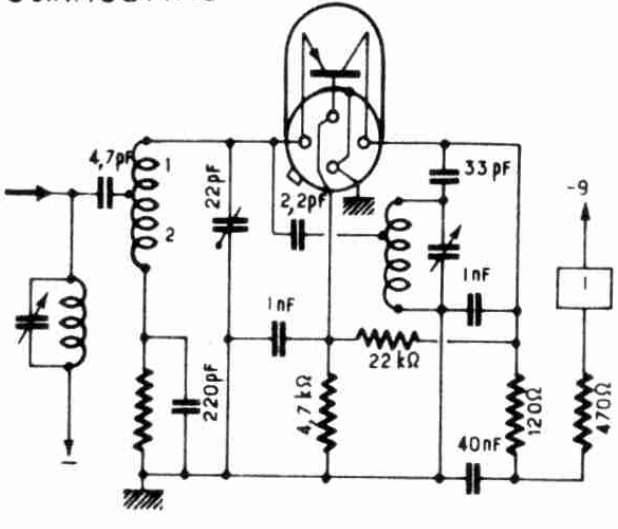
β = 110



AF135

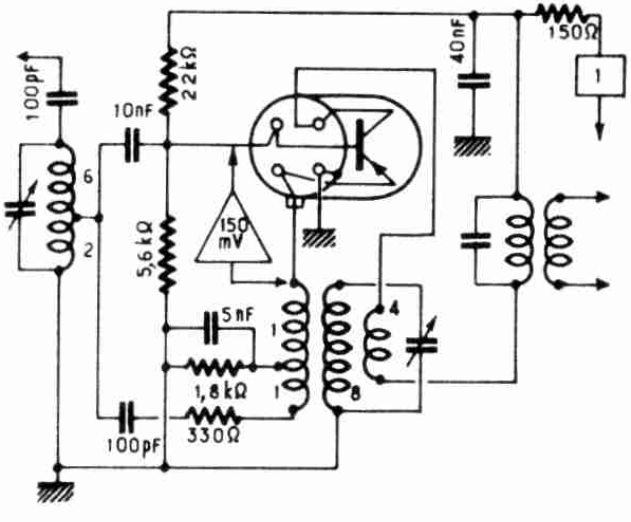
Conv. 100 MHz

β = 100



AF136

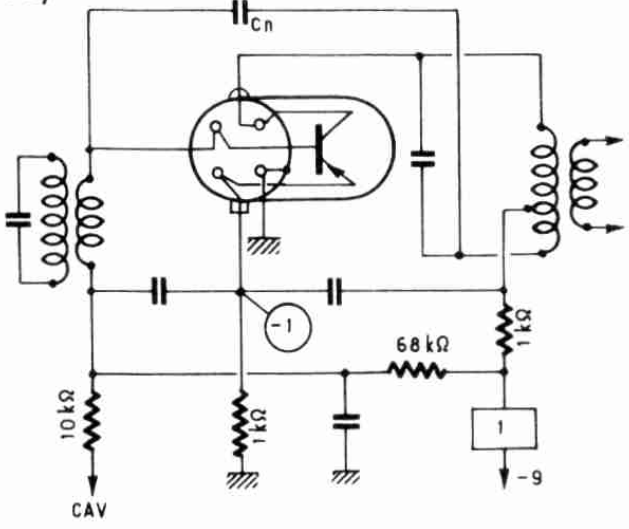
Conv. < 23 MHz



AF 137

10,7 MHz

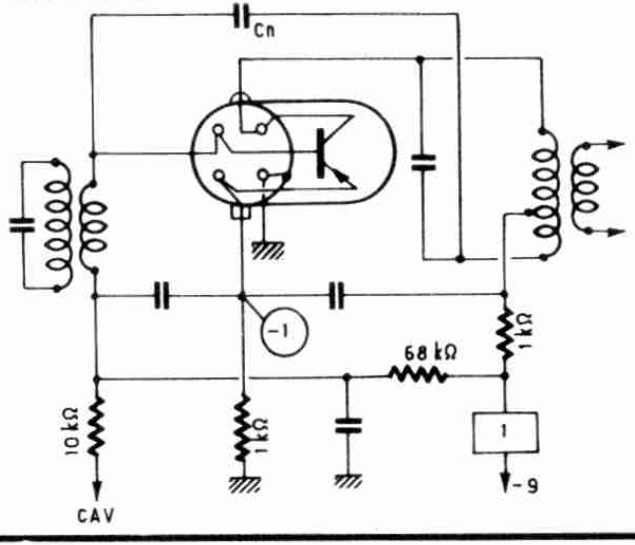
β = 60



AF138

455 kHz

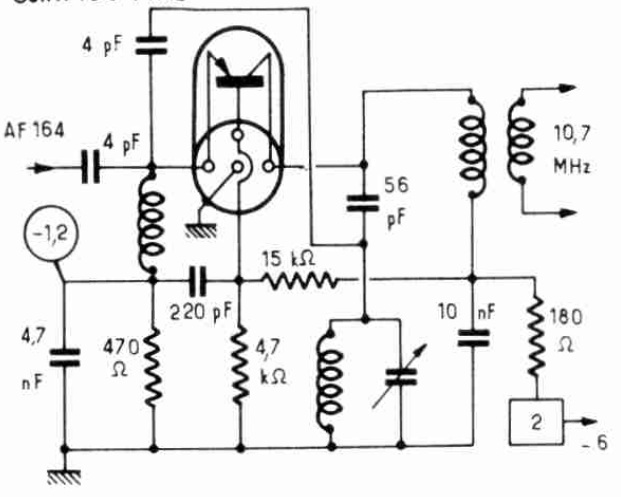
β = 80



AF 165

Conv. 100 MHz

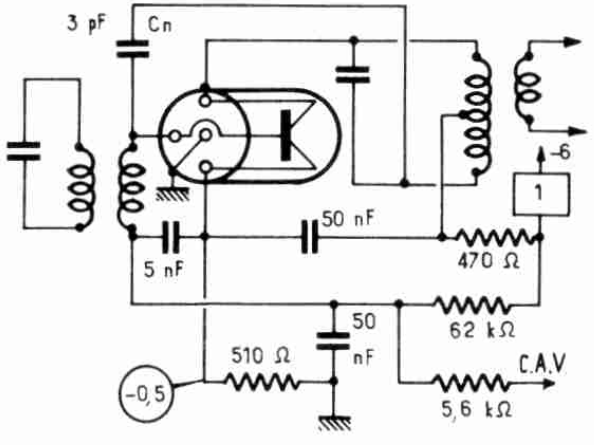
β = 85



AF 166

10,7 MHz

β = 85

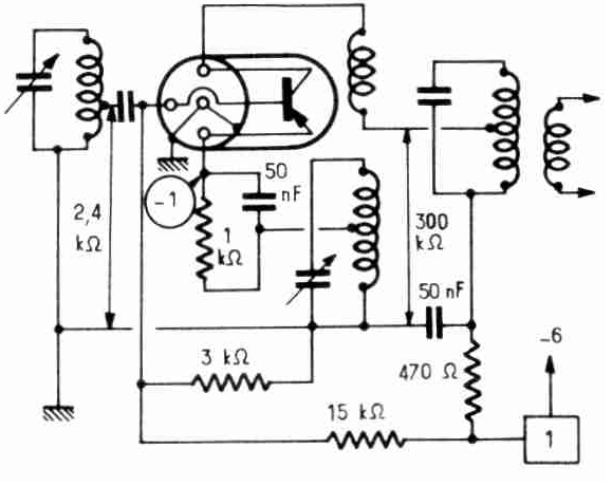


AF 170

Conv. < 2 MHz

β = 80

GP = 33 dB

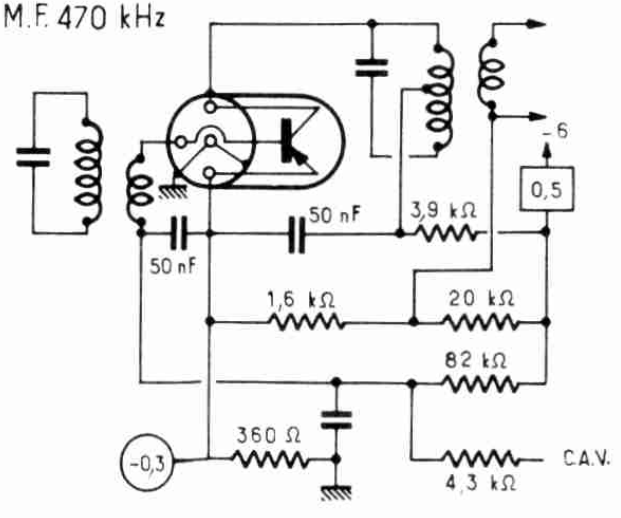


AF 172

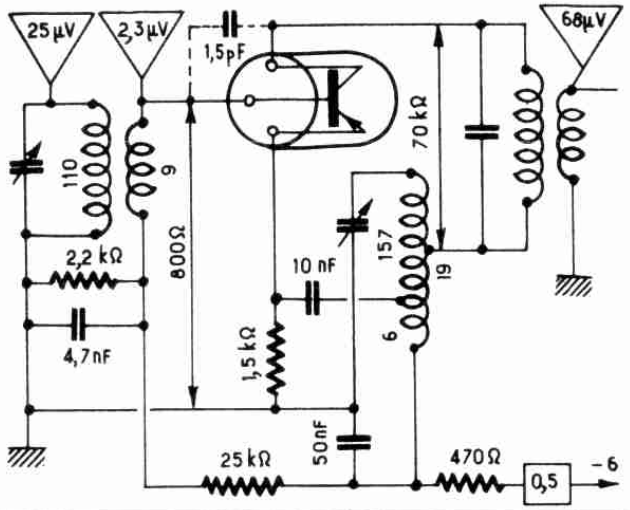
M.F. 470 kHz

β = 70

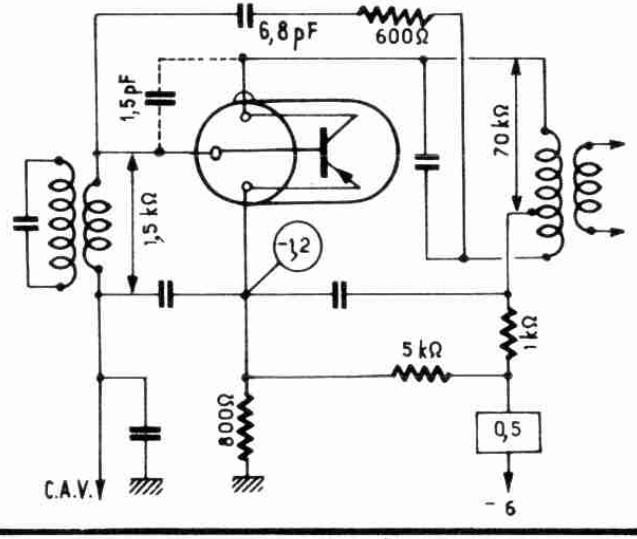
GP = 27 dB



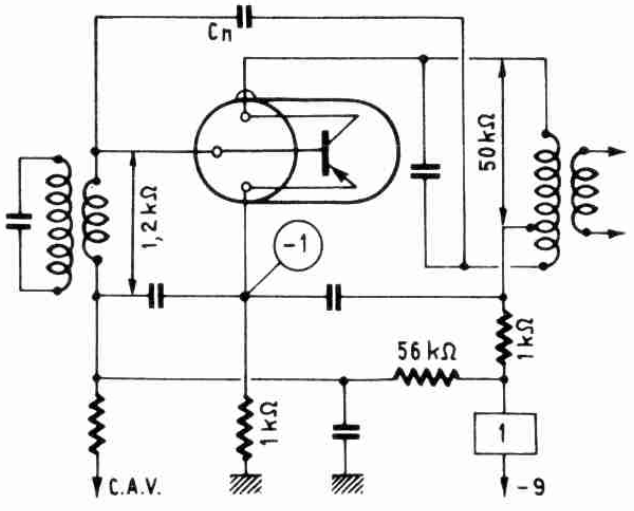
AF 185
Conv.< 2MHZ



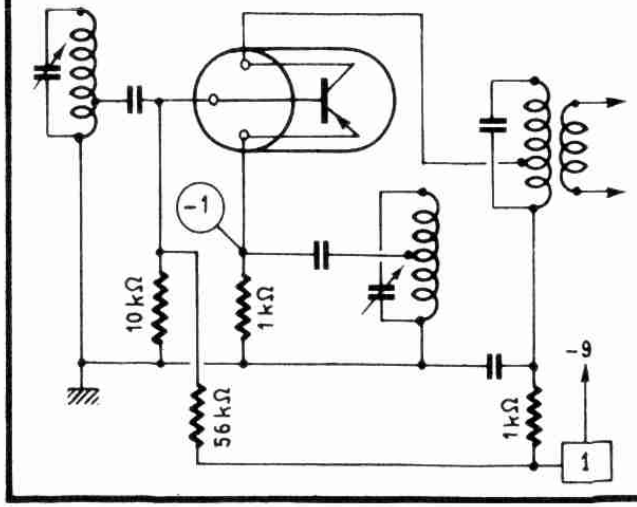
AF 185
MF 470 kHz



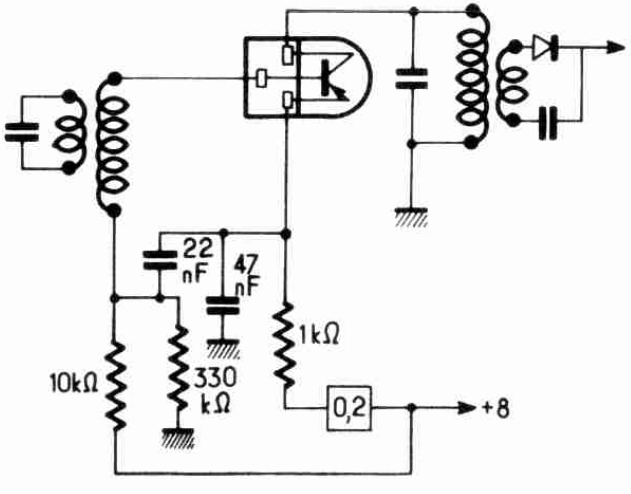
AF 187
MF 470kHz



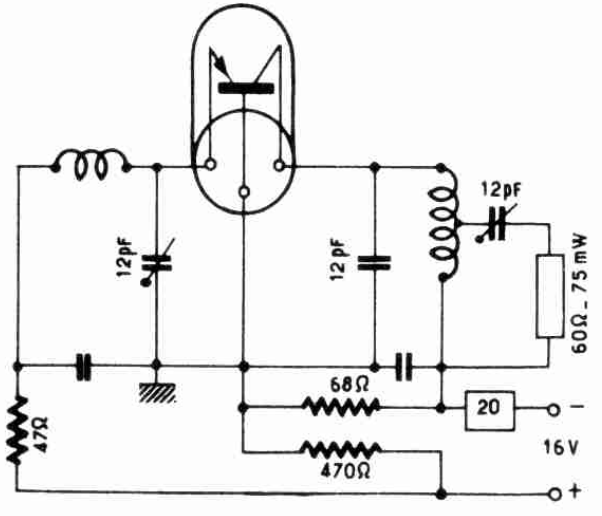
AF 188
β = 70
Conv.< 2 MHz



AF256
ß=30 (>10)
f_t > 170 MHz
455 kHz

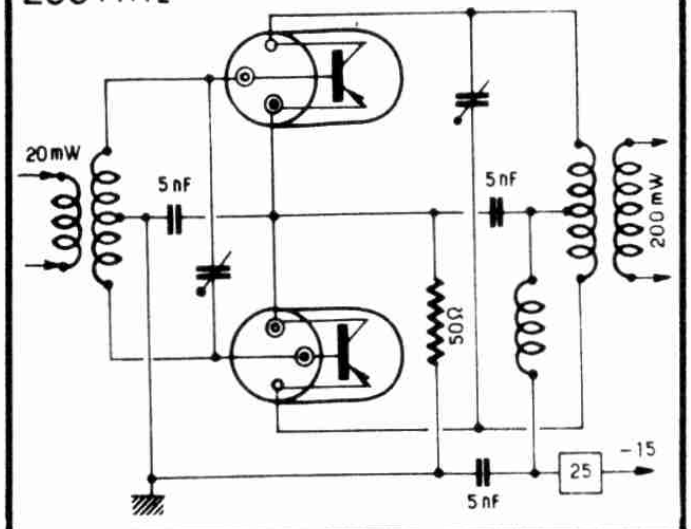


AFY 10
β = 60
β = 1 (250MHz)
Osc. 200 MHz



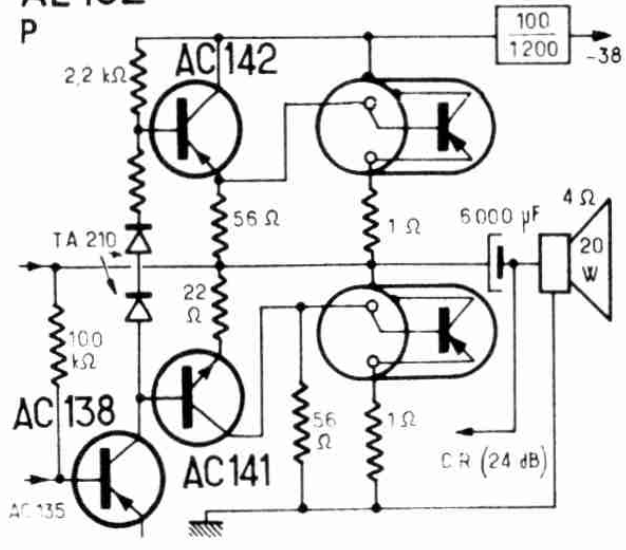
AFY11
200 MHz

β = 60
β = 1 (300MHz)
GP = 10 dB

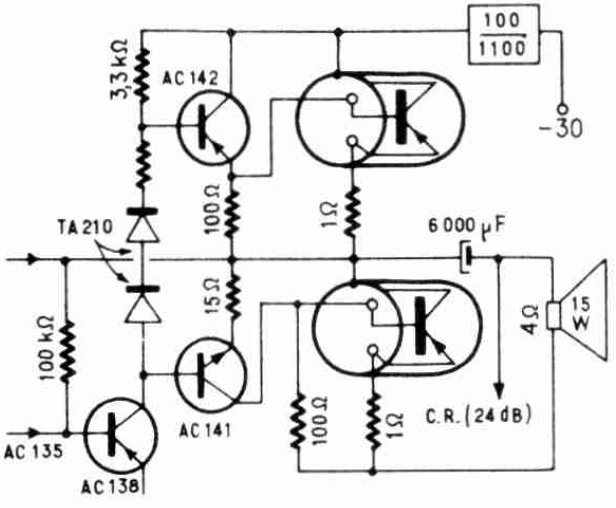


AL102
P — Base diff.

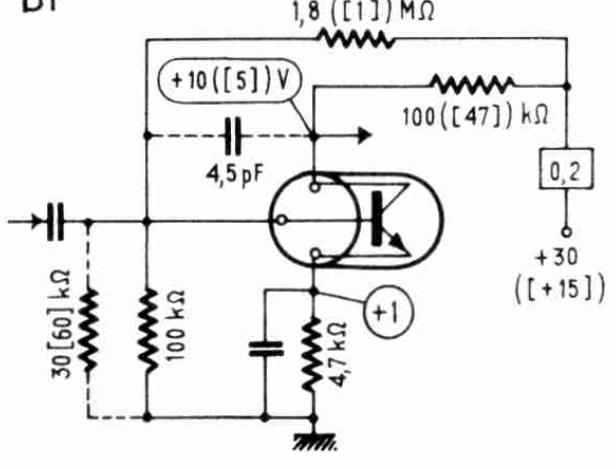
β = 150 à I_c = 1 A



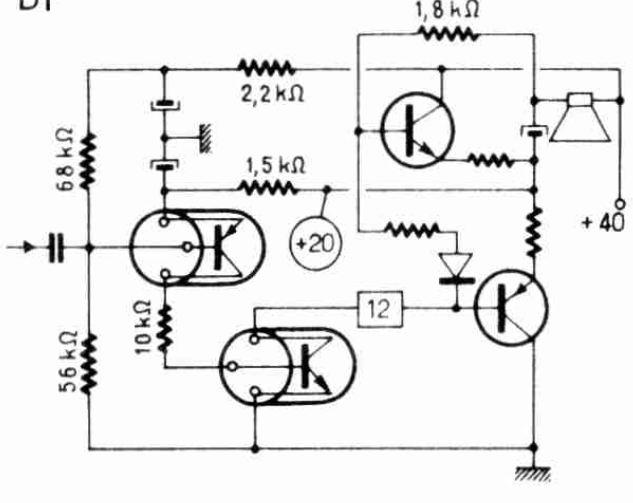
AL103
P — Base diff. — β = 40....250



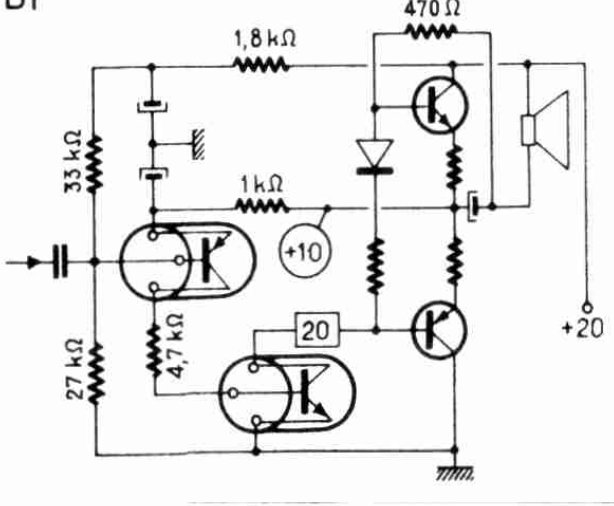
BC107 (BC108) [BC109]
BF — n-p-n Si — β = 125...500 [240...900] — F_b = <6 [<4] dB



BC107 BC177
BF — n-p-n p-n-p Si — β = 20...300



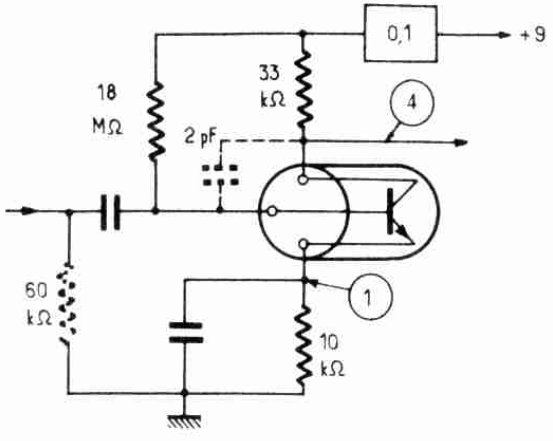
BC108 BC178
BF — n-p-n p-n-p Si — β = 80...500



BC 113 [BC 114]

n-p-n Si Planar

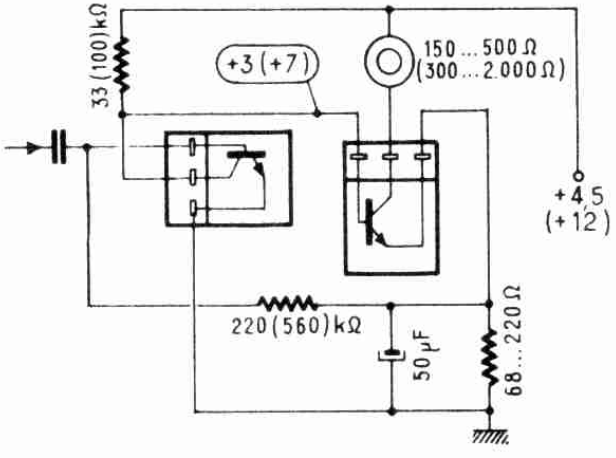
β = 200 ... 1000 (à I_C = 1 mA)
[F_b = 1,5 dB]



BC 121 (BC 122) BF

n-p-n Si

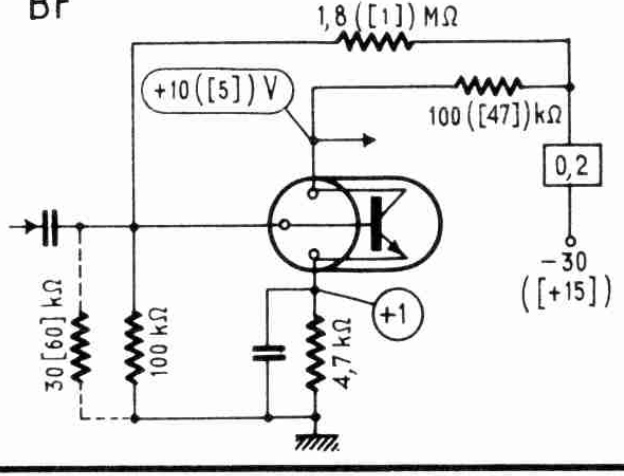
β = 70 ... 600



BC 129 (BC 130) [BC 131] BF

n-p-n Si

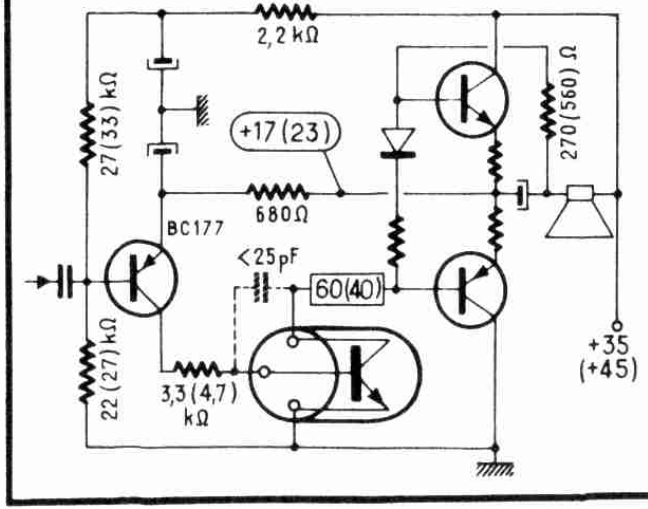
β = 125 ... 500
[240 ... 900]
F_b = <6 [4] dB



BC 140 (BC 141) BF

n-p-n Si

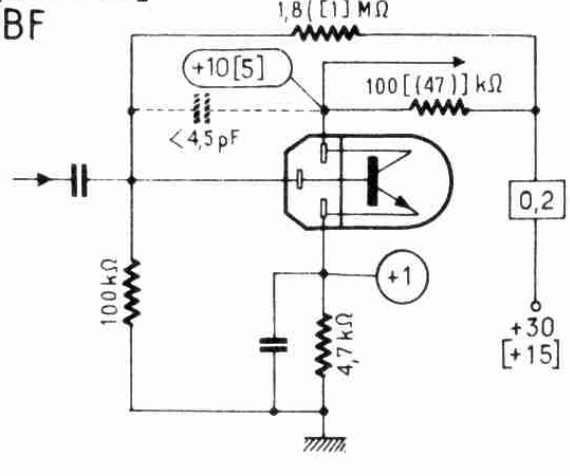
β = 40 ... 120
f_t > 60 MHz



BC 147 (BC 148) [BC 149] BF

n-p-n Si

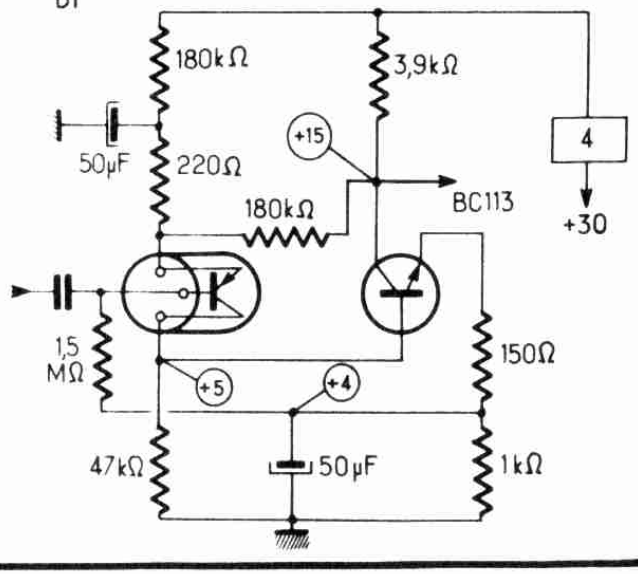
β = 125 ... 500
[240 ... 900]
F_b < 10 [<4] dB
f_t > 150 MHz



BC 154 BF

p-n-p Si

β = 200
F_b < 2,5 dB

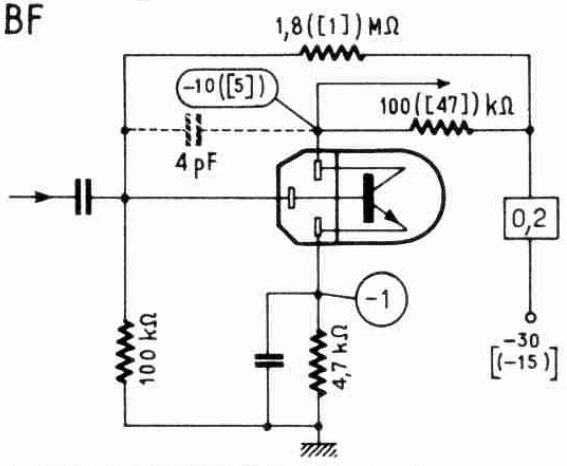


BC 157 (BC 158) [BC 159]

p-n-p Si

BF

β = 50...350 [150...350]
F_b < 10 [<4] dB
f_t = 200 MHz

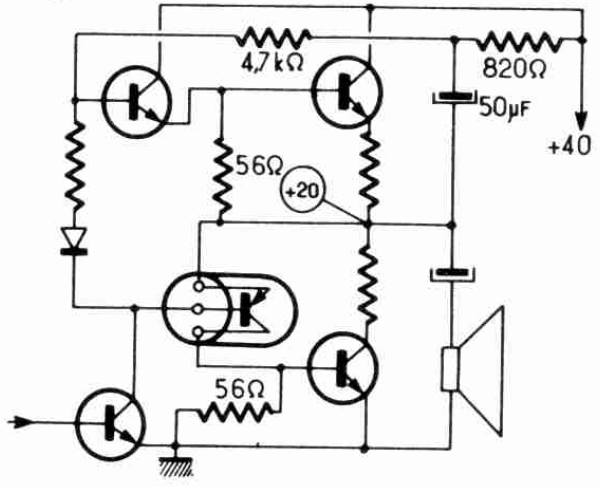


BC 160-6 (BC160-10)(BC160-16)

p-n-p Si

BF

ß=40.....100 (63.....160) [100.....250]

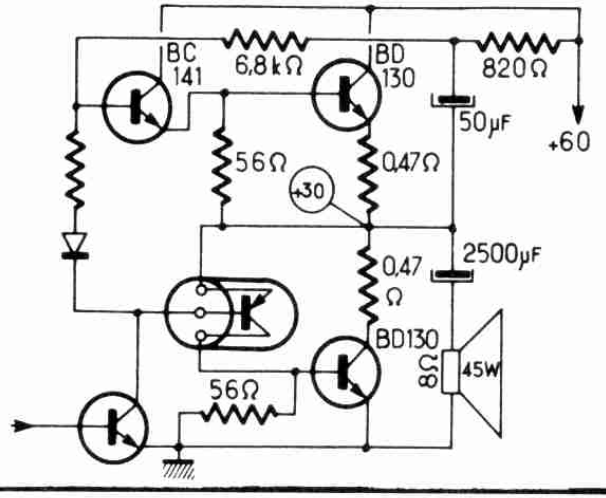


BC161-6 (BC161-10)(BC161-16)

p-n-p Si

BF

ß=40.....100 (63.....160) [100.....250]

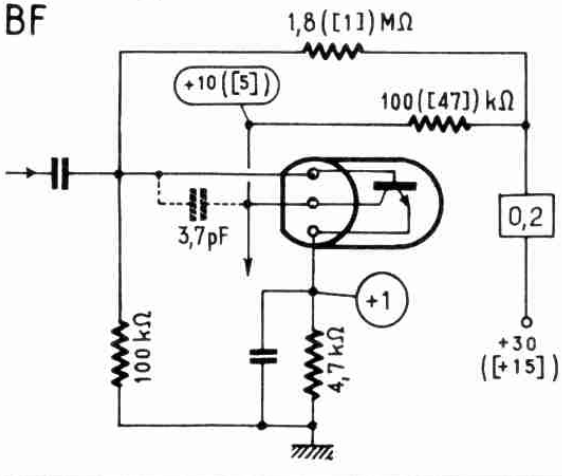


BC 167 (BC 168) [BC 169]

n-p-n Si

BF

β = 125... 500 [240... 900]
F_b <10 [<4] dB
f_t >150 MHz

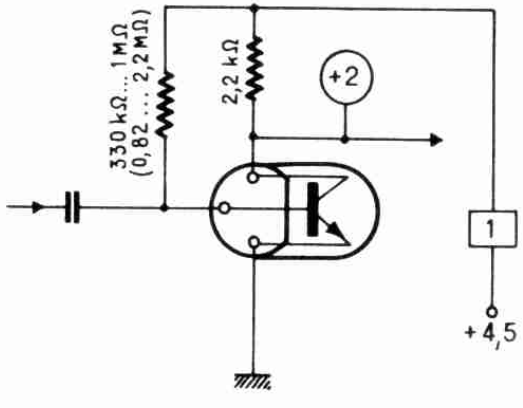


BC 170 A (BC 170 B)

n-p-n Si

BF

β = 80.... 250 (200...600)

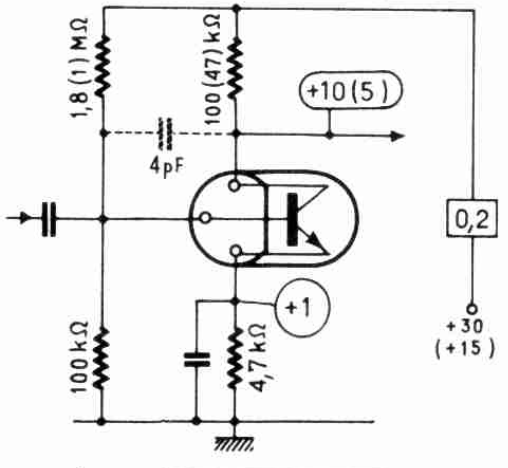


BC 171 (BC 172)

n-p-n Si

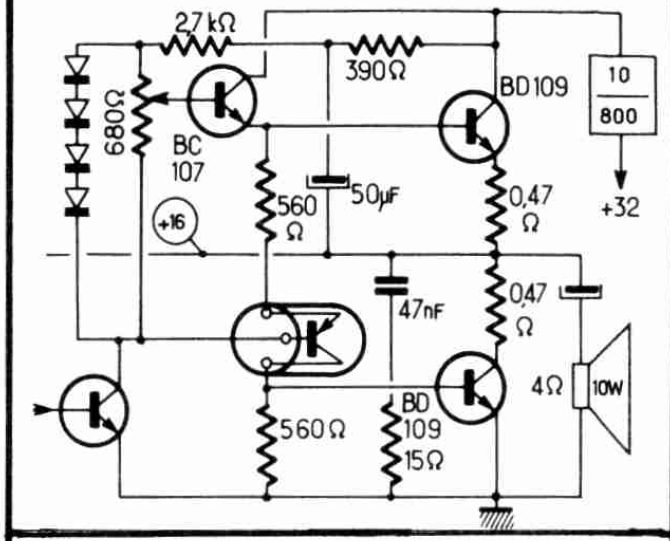
BF

β = 125...260[A]
= 240...500[B]
= 450...900[C]
F_b < 6dB
f_t > 150 MHz



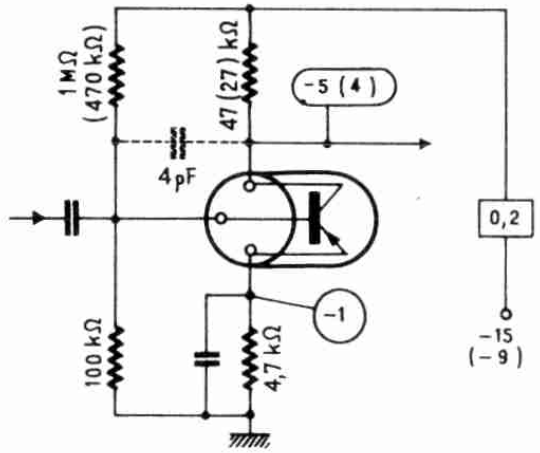
BC177 p-n-p Si BF

ß=75...260
f_T=130MHz



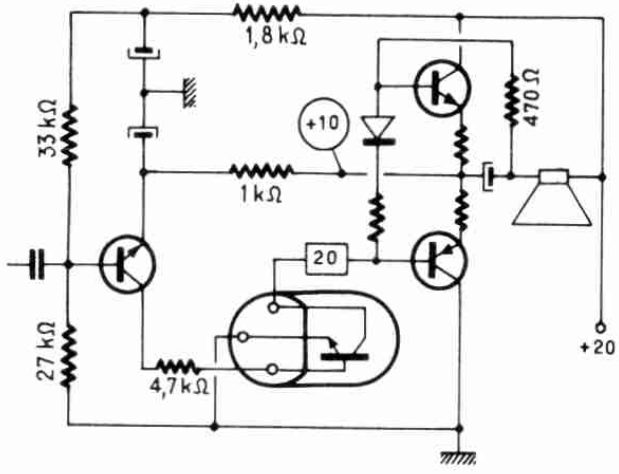
BC179 p-n-p Si BF

β = 240...500
F_b = < 4 dB
f_t = 200 MHz



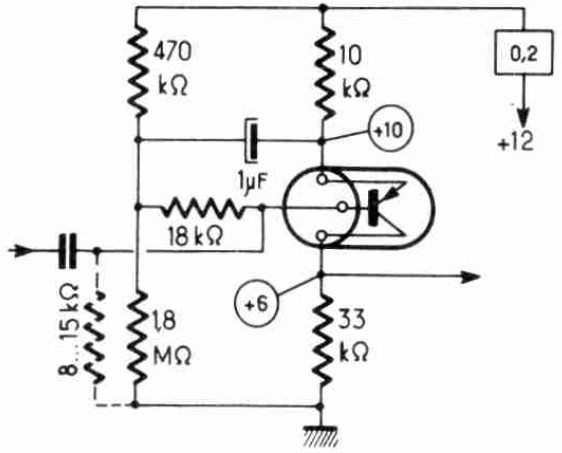
BC 181 (BC 181 A) n-p-n Si BF

β > 60 (>100)



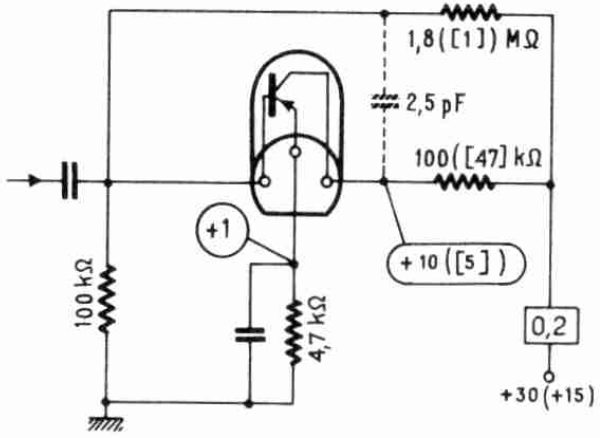
BC 181 A p-n-p Si (BC181B)(BC181C) BF

ß=50.....200
(100.....300)(150.....600)
F_b = 1 (0,8) (0,7) dB



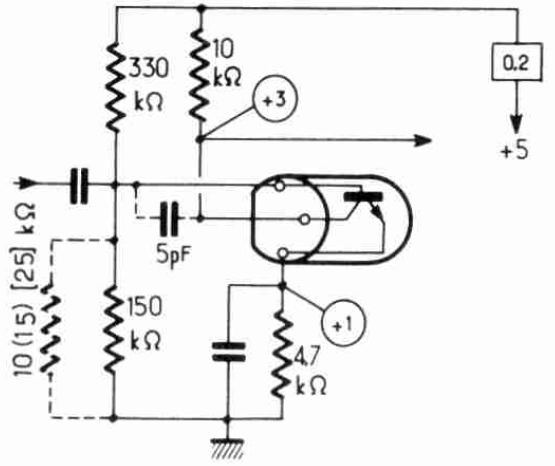
BC 182 (BC 183) [BC 184] n-p-n Si

β = 100...480
(100...850)
[> 250]
F_b < 10 [<4] dB
f_t > 150 MHz



BC200-01 n-p-n Si (BC200-02)(BC200-03) BF

ß=50.....100
(85...200)(165...400)
F_b = 2 (1,5) [2] dB



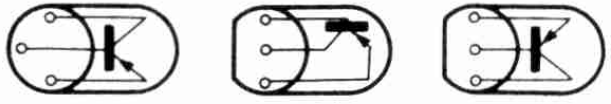
BC 177 → BC107, BC 140 BC 178 → BC108

BC 204 = BC 257 = BC 307 = BC 157

BC 205 = BC 258 = BC 308 = BC 158

BC 206 = BC 259 = BC 309 = BC 159

p-n-p



BC 204,5,6 BC 257,8,9 BC 157,8,9

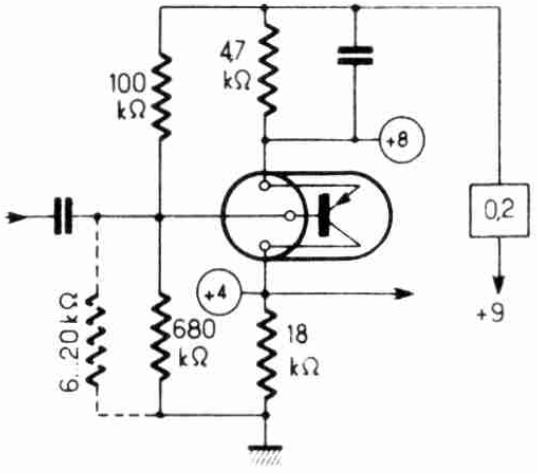
BC 206

p-n-p

BF

Si

β = 50 ... 500
F_b < 4 dB
f_T = 200 MHz



BC 207 = BC 237 = BC 167

BC 208 = BC 238 = BC 168

BC 209 = BC 239 = BC 169

n-p-n

BC 207, 8, 9 BC 237, 8, 9

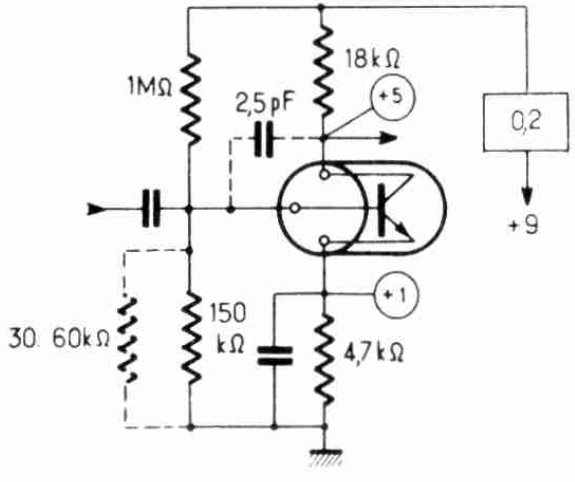
BC 209

n-p-n

BF

Si

β = 240 ... 900
F_b < 4 dB
f_T = 300 MHz



BC 211

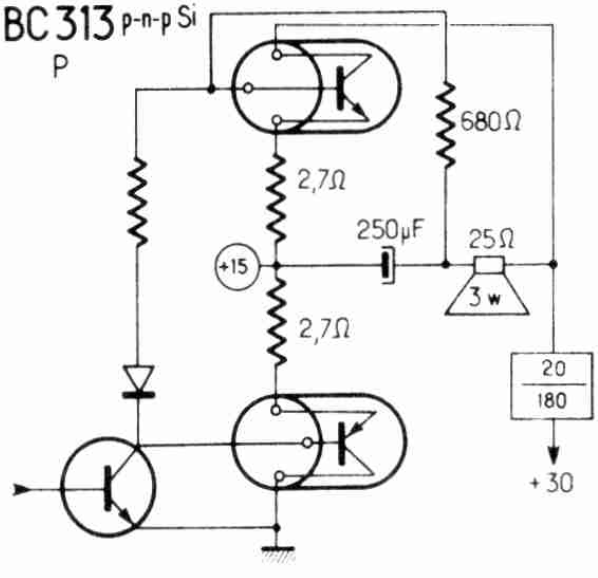
n-p-n Si

BC 313

p-n-p Si

P

β > 50



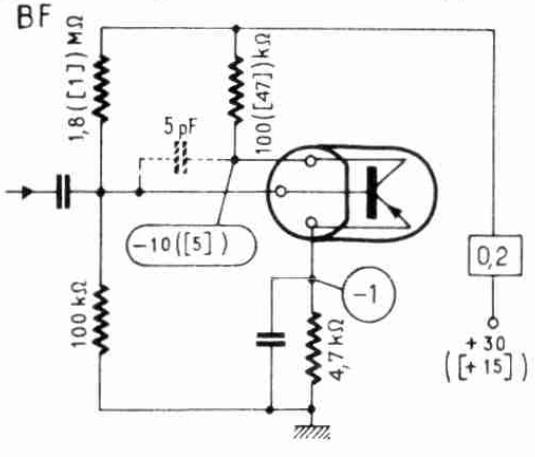
BC 212 (BC 213) [BC 214]

p-n-p

Si

β = 60....300
(50....400)
[140...400]
F_b = 2,5 [>2] dB
f_t > 200 MHz

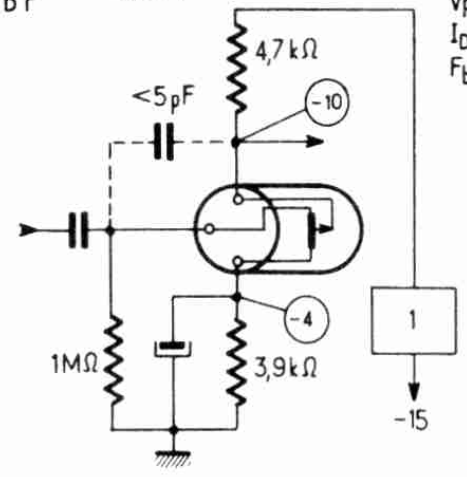
BF



BC219

FET Si
Canal P
BF

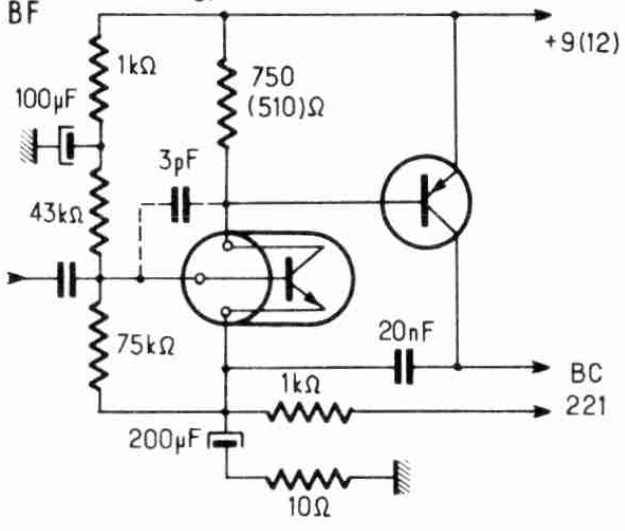
s=2...8mA/V
ρ>10kΩ
Vp>10V
I_{DSS}=3...30mA
F_b=01dB



BC220

n-p-n
Si
BF

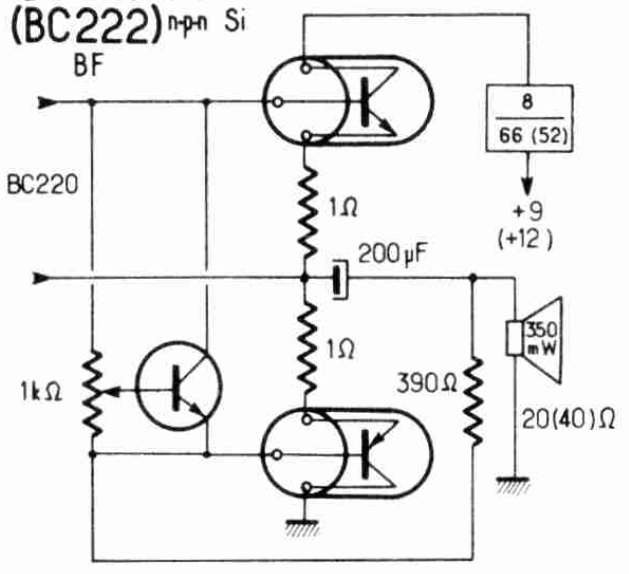
ß=225 (>100)



BC221 (BC222)

p-n-p Si
n-p-n Si
BF

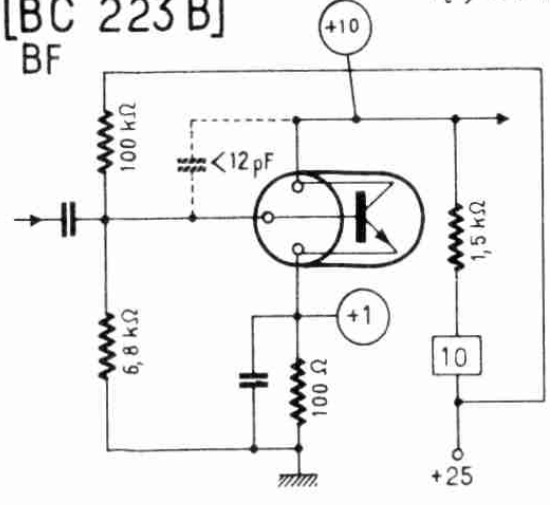
ß=115 (>50)



BC 223 (BC 223A) [BC 223B]

n-p-n
Si
BF

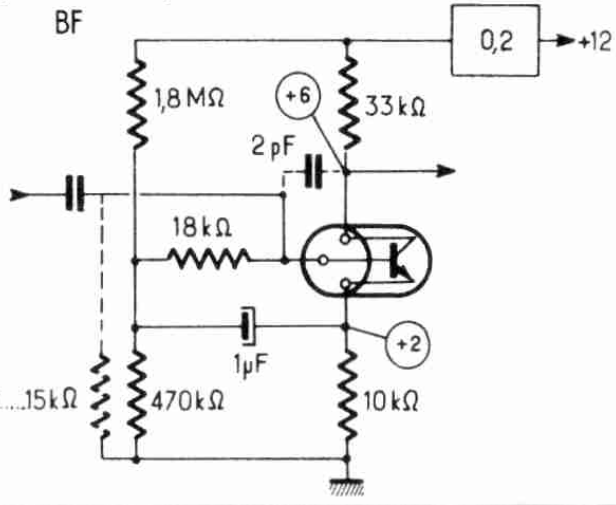
β=100... 400
(100... 300)
[200...450]
f_t >100 MHz



BC280A (BC280B) [BC280C]

n-p-n
Si
BF

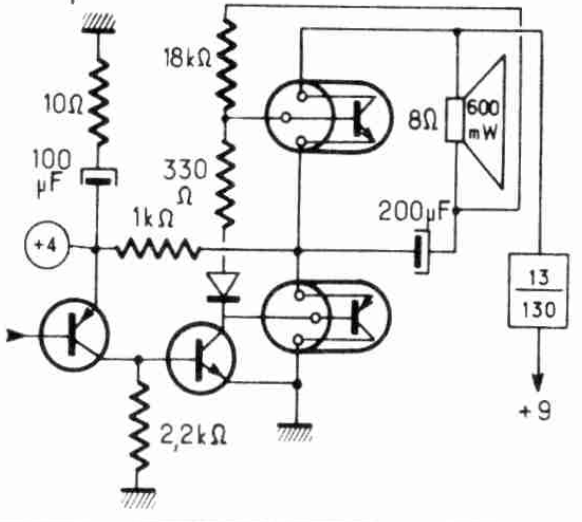
ß=100.....300 [(200....600)]
F_b=2,5 (2) [1,5] dB



BC282 BC283

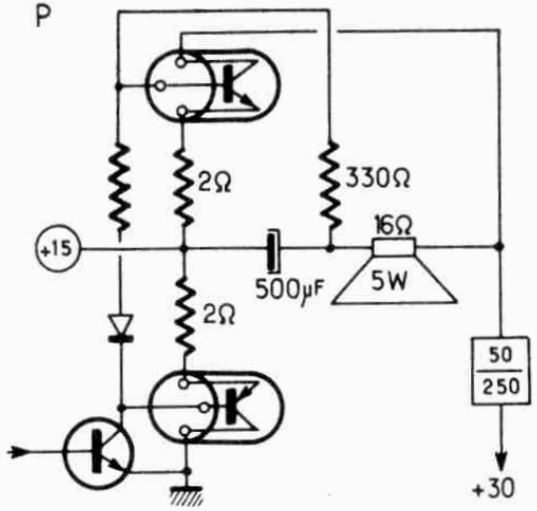
n-p-n Si
p-n-p Si
P

ß=40 300



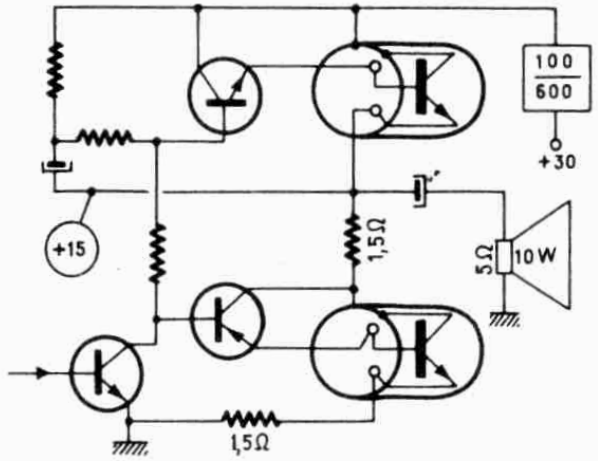
BC 286
BC 287

n-p-n Si
p-n-p Si
β = 20 200
P



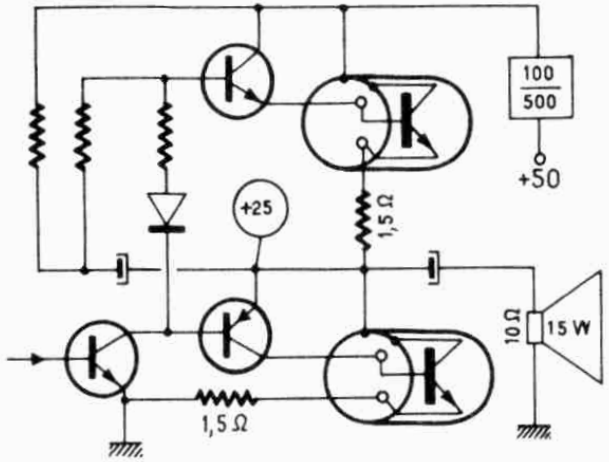
BD 106 A
(BD 106 B)

n-p-n Si
β = 50 150
(100...300)
f_t = 100 MHz
P



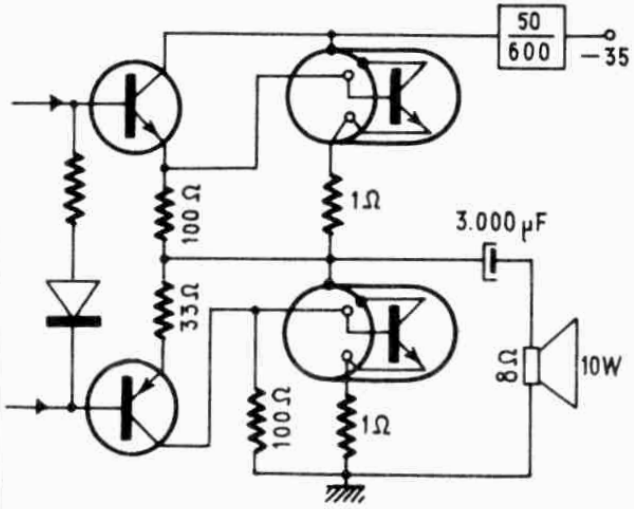
BD 107 A
(BD 107 B)

n-p-n Si
β = 50 ... 150
(100...300)
f_t = 100 MHz
P



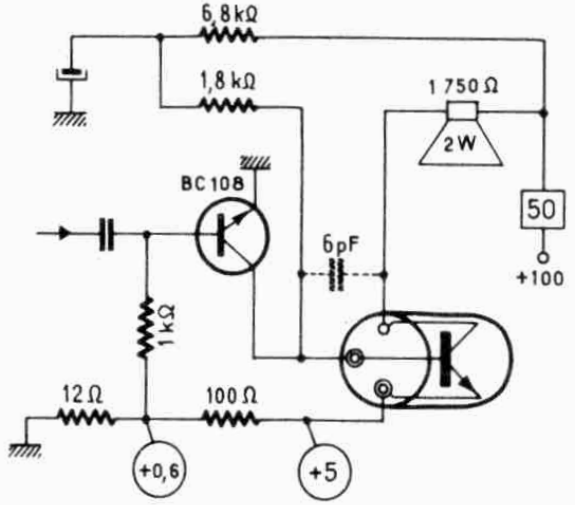
BD 109

n-p-n Si
β = 20...120
P



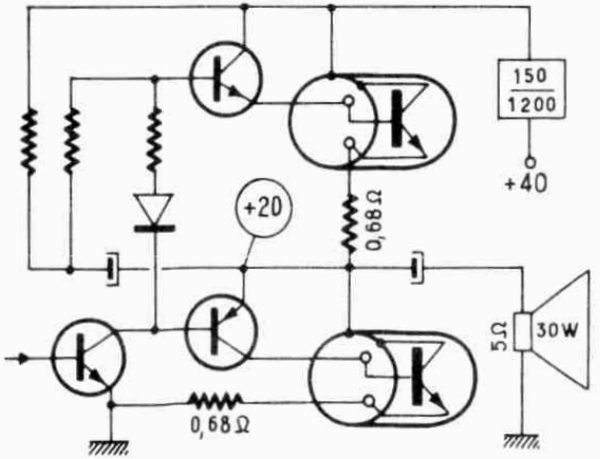
BD 115

n-p-n Si
β = 50 (>20)
f_t = 120 MHz
P



BD 117

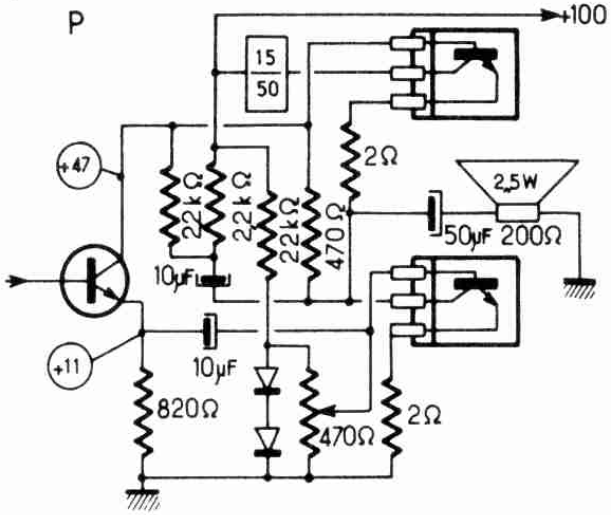
n-p-n Si
β = 20...100
f_t > 50 MHz
P



BD 127
BD 128
P

n-p-n Si

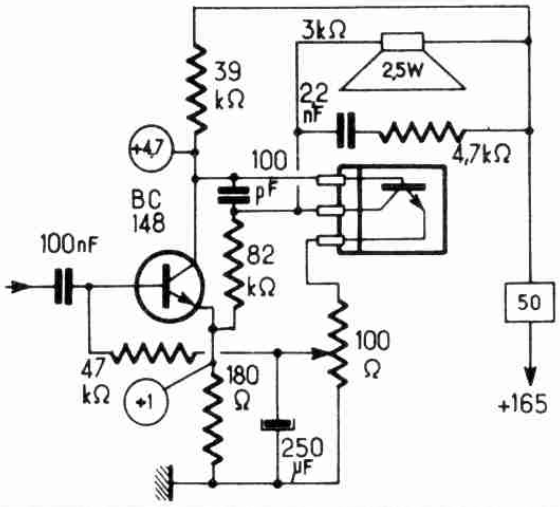
B = 30



BD 129
P

n-p-n Si

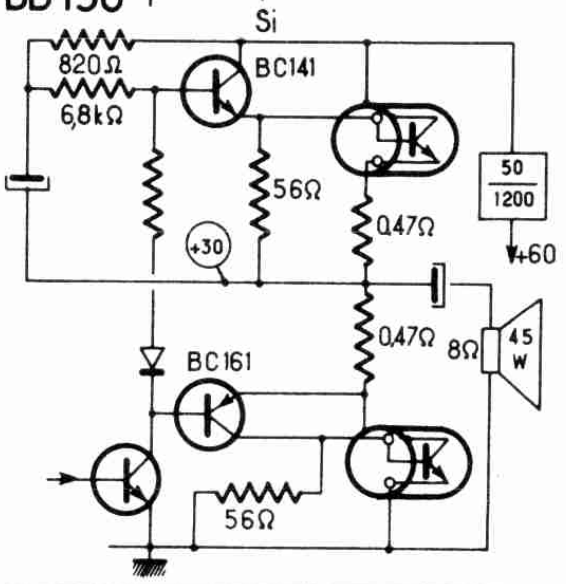
B = 30
GP = 58dB



BD 130
P

n-p-n Si

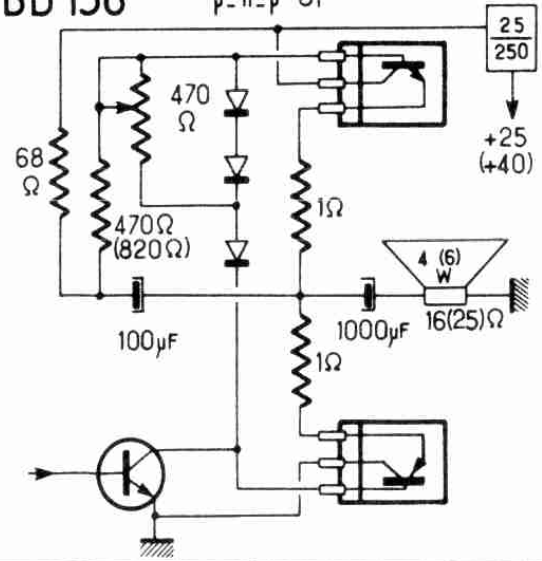
B = 20...70



BD 135
BD 136
P

n-p-n Si
p-n-p Si

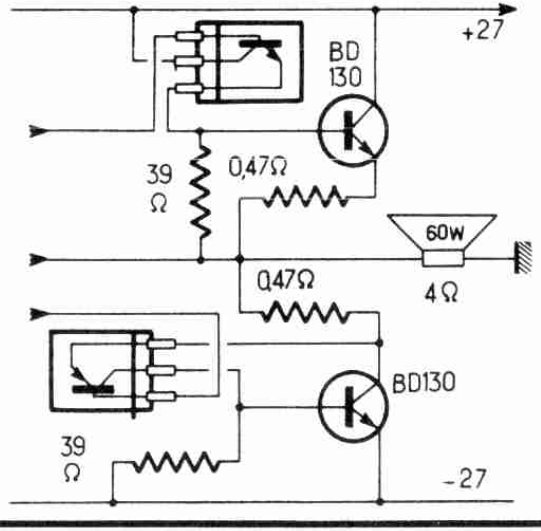
B = 40....250



BD 137
BD 138
P

n-p-n Si
p-n-p Si

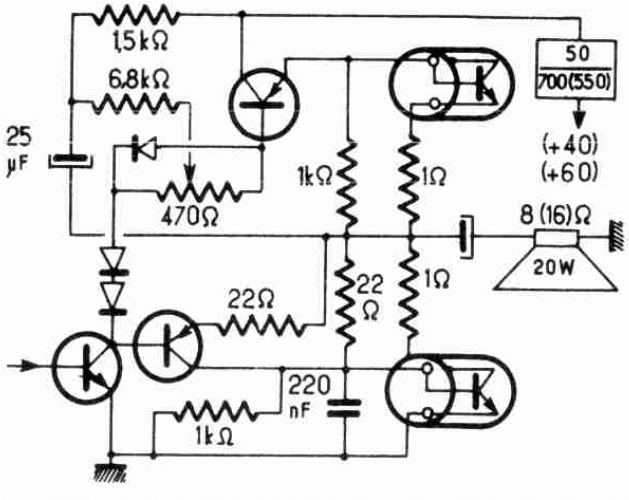
B = 40....160



BDY 23
P

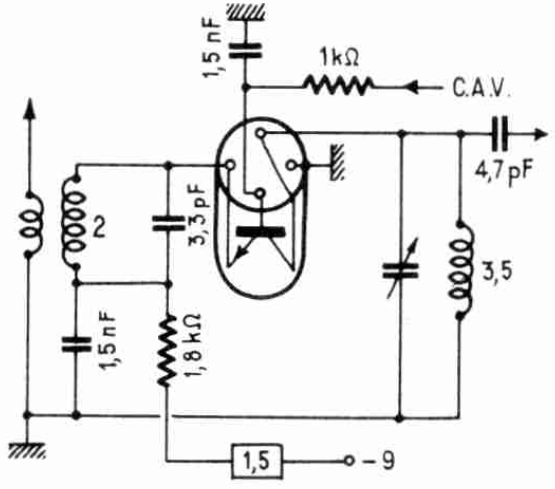
n-p-n Si

B = 15 180



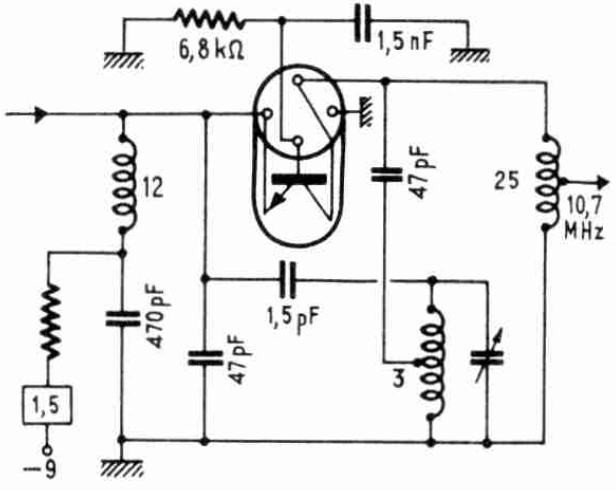
BF 115
100 MHz n-p-n Si

β = 45...165
F_b = 3,5 dB



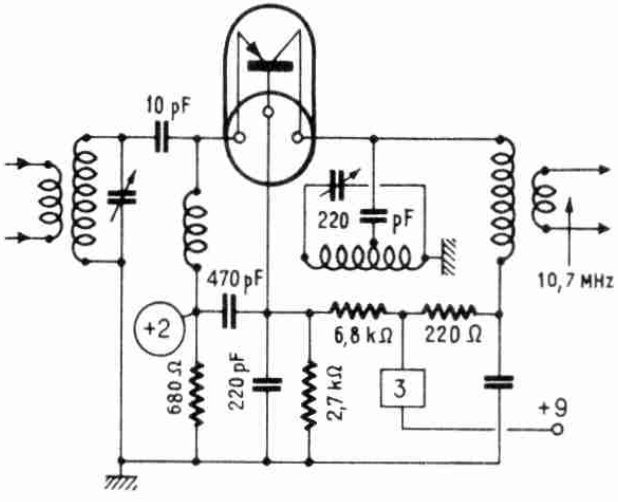
BF 115
Conv. 100 MHz n-p-n Si

β = 45...165



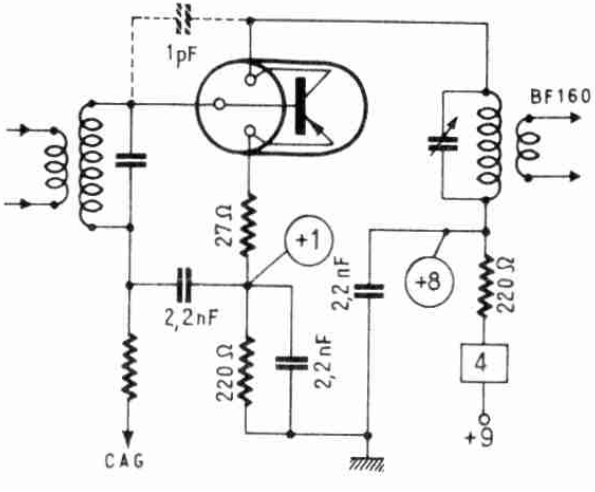
BF160
Conv. 100 MHz n-p-n Si

β = 50 (>20)
f_t >400 MHz



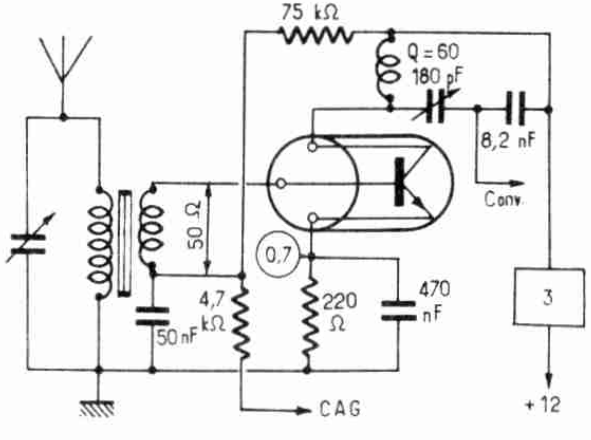
BF 162
100 MHz n-p-n Si

β = 70 (>30)
f_t >400 MHz
F_b = 4 bB



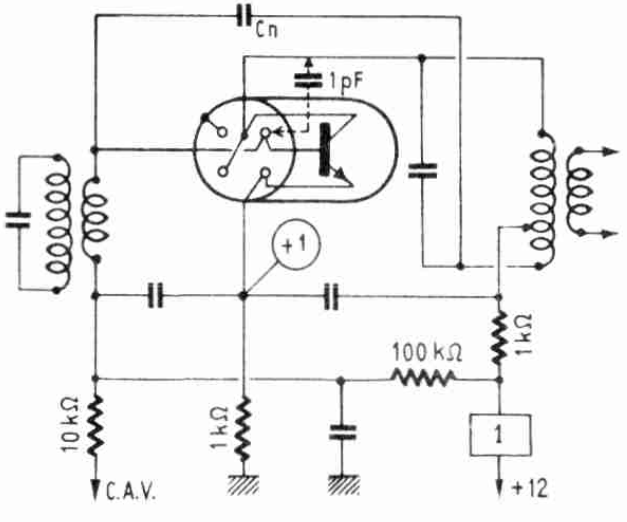
BF 165
< 2 MHz n-p-n Si Planar

β = 35 (>20)
(>2 à 100 MHz)
GP = 42 dB (1 MHz)
F_b = 3,7 dB



BF 184
MF 470 kHz n-p-n Si

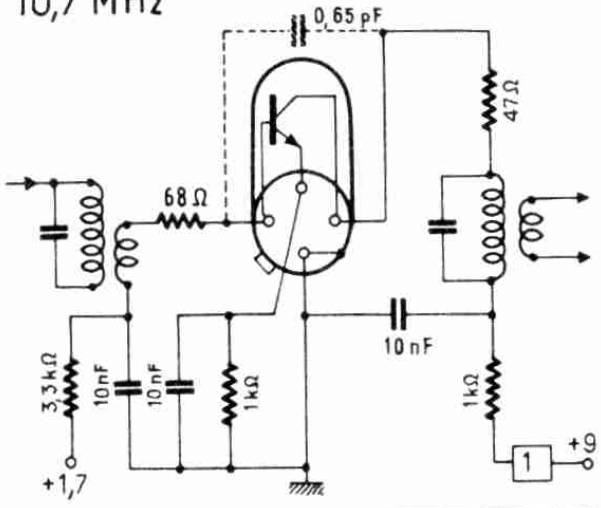
β = 90...650



BF 184 (BF 185) 10,7 MHz

n-p-n Si

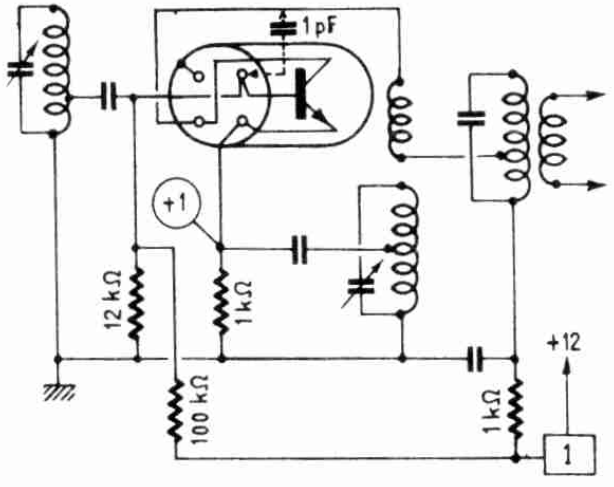
β 75 ... 750 (40 ... 125)
f_t = 300 (220 MHz)



BF 185 Conv. < 20 MHz

n-p-n Si

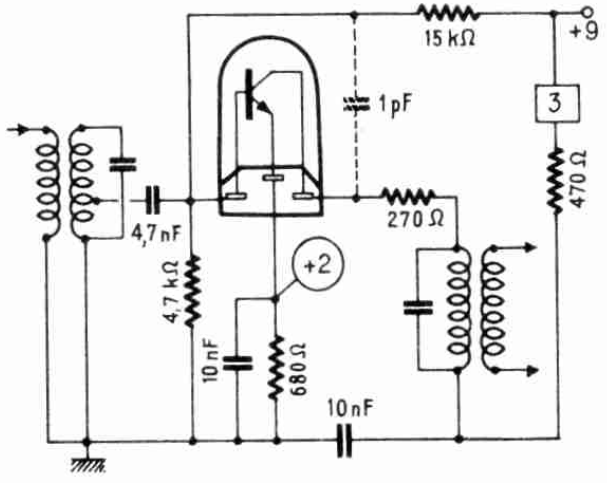
β = 40...125
F_b = 4 dB (5 MHz)



BF 194 10,7 MHz

n-p-n Si

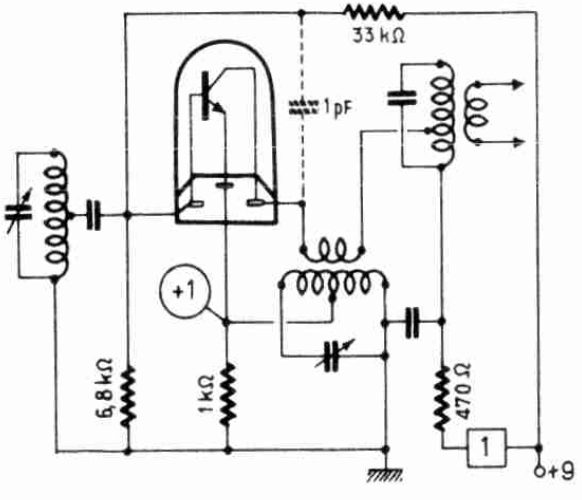
β = 115
f_t = 300 MHz



BF 195 Conv. < 20 MHz

n-p-n Si

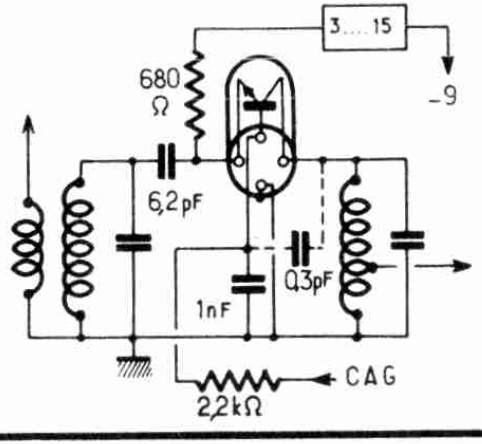
β = 67
f_t = 220 MHz
F_b = 2,5 dB



BF 200 100 MHz

n-p-n Si

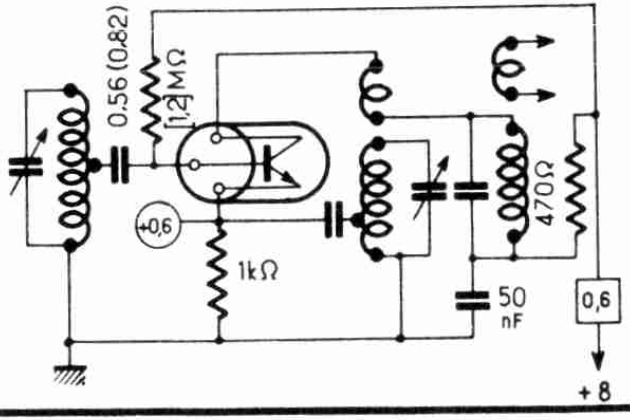
β > 15
GP = 28 dB
F_b = 2 dB
f_T = 650 MHz



BF 233-2 (BF 233-3) (BF 233-4) Conv. < 20 MHz

n-p-n Si

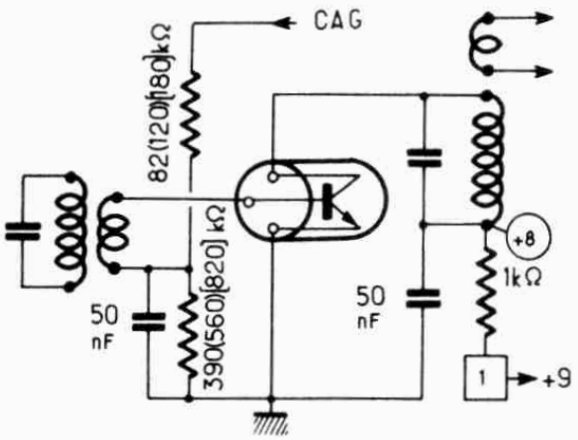
β = 40 70
(60 .....100)
(90 .....150)
F_b = 35 dB



BF 233-3 (BF233-4)(BF233-5)

n-p-n Si ß = 60.....100 (90.....150)(140.....220)

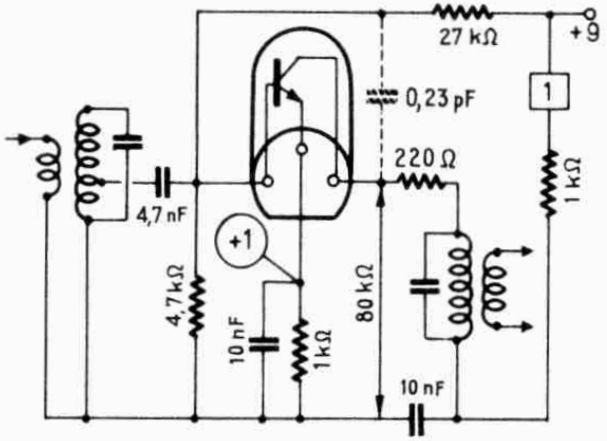
455 kHz



BF 237 (BF 238)

n-p-n Si β > 30 (>70)

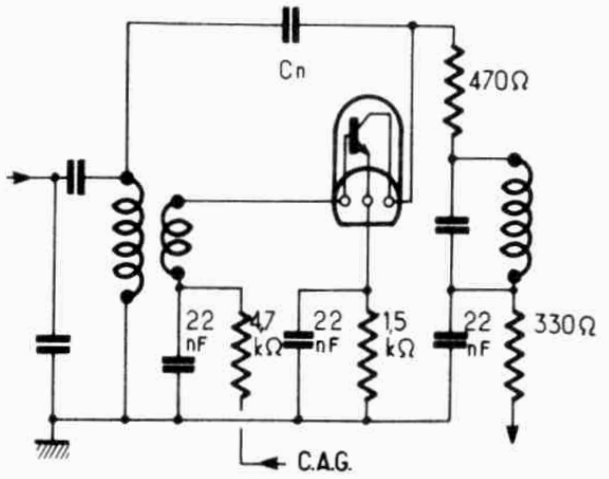
10,7 MHz



BF 241

n-p-n Si ß > 35 f_T = 400 MHz

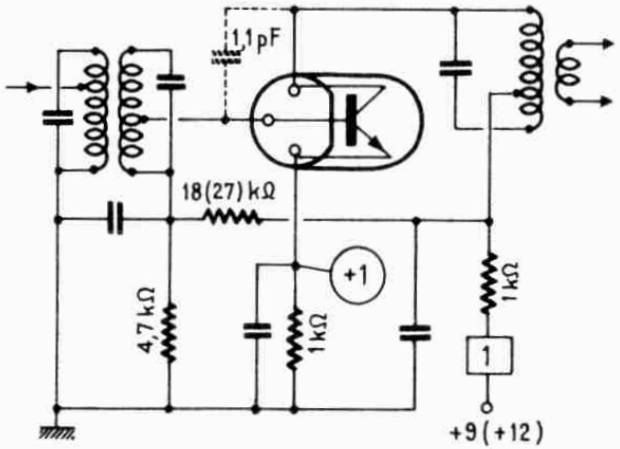
10,7 MHz



BF 243

n-p-n Si β > 30 f_T > 80 GP = 35 dB F_b = 1 dB

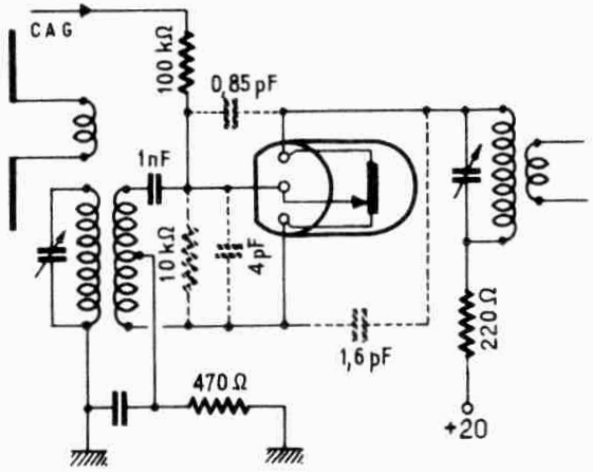
455 kHz



BF 245

F.E.T. Si Canal N δ = 3...6,5 mA/V I_{DSS} = 2...25 mA

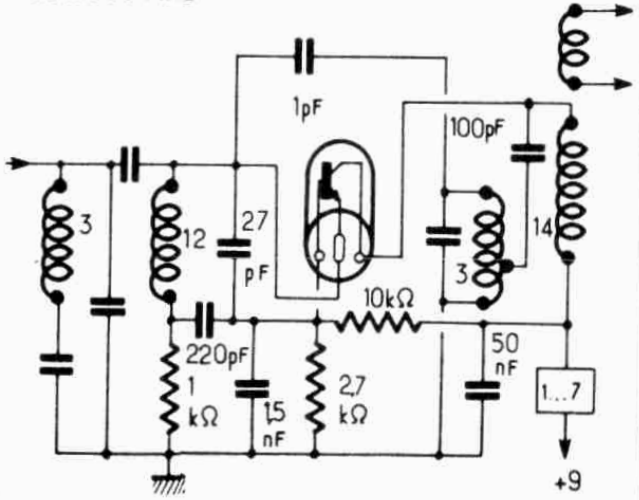
100 MHz



BF 255 (≃BF195)

ß = 67 (>30) f_T = 200MHz F_b = 4 dB

Conv. 100 MHz

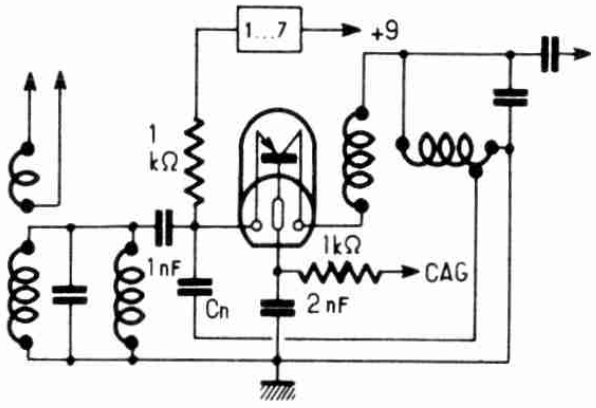


BF 314

n-p-n
Si

100 MHz

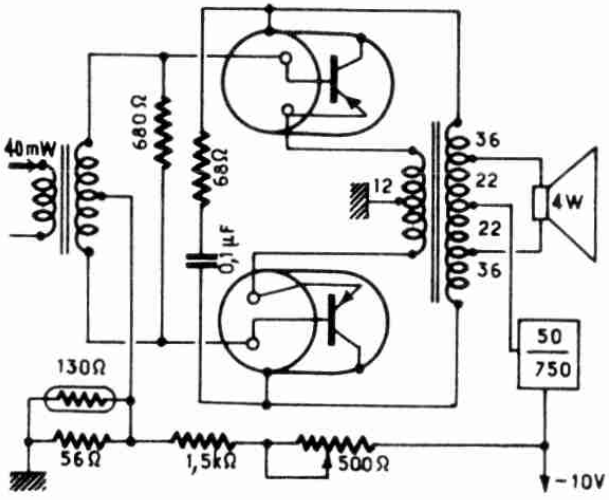
$\beta > 30$
$f_T = 450$ MHz
$F_b < 2$ dB



OC 22

P

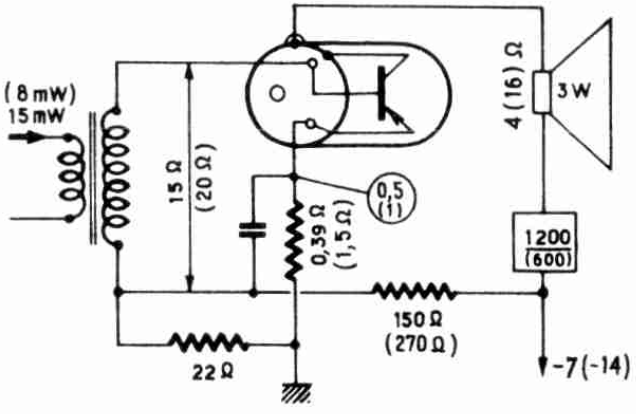
$\beta = 150$
GP = 20 dB



OC 26

P

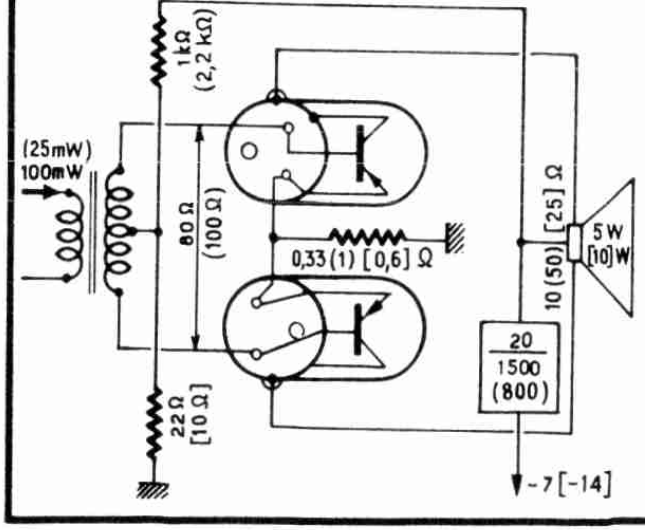
$\beta = 30$
GP = 23 dB
(26 dB)



OC 26

P

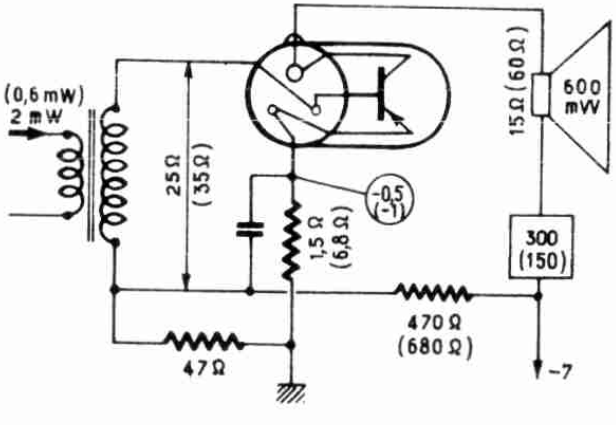
$\beta = 30$
GP = 17dB
(23dB)
[20dB]



OC 30

P

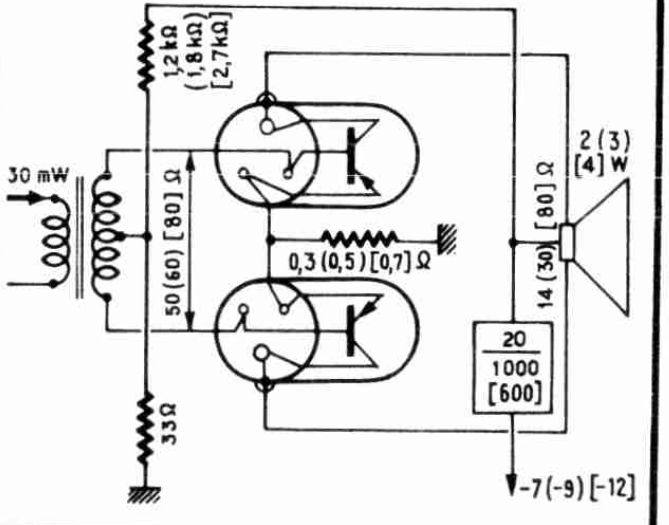
$\beta = 30$
GP = 25dB
(30dB)



OC 30

P

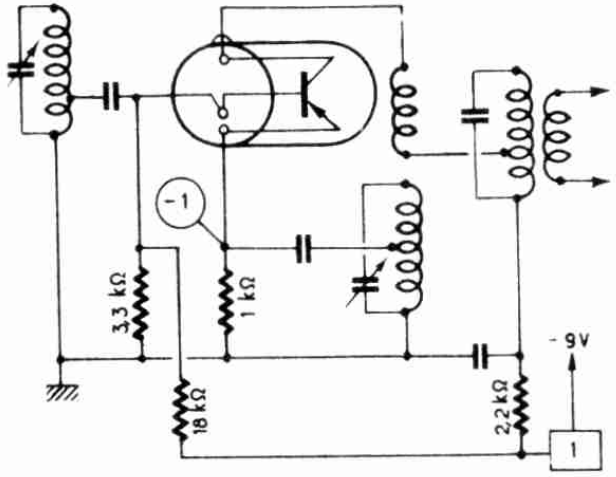
$\beta = 30$
GP = 18dB
(20dB)
[22dB]



OC 44

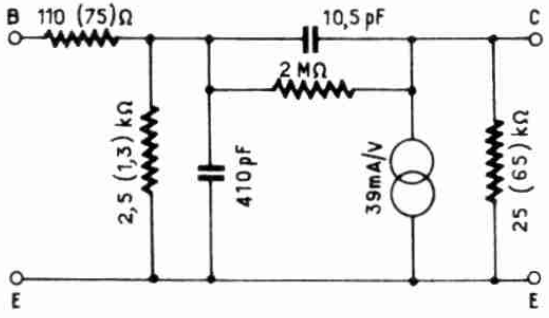
Conv. < 2 MHz

β = 100
GC = 28 dB



OC44 (OC45)

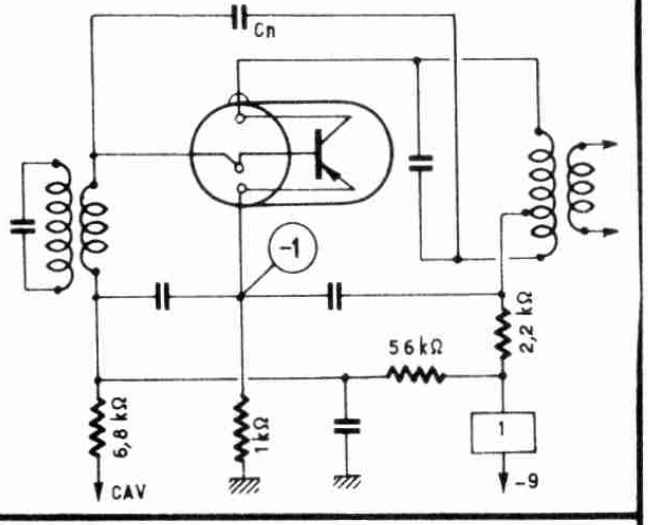
Vc = 6 V
Ic = 1 mA



OC 45

MF 470 kHz

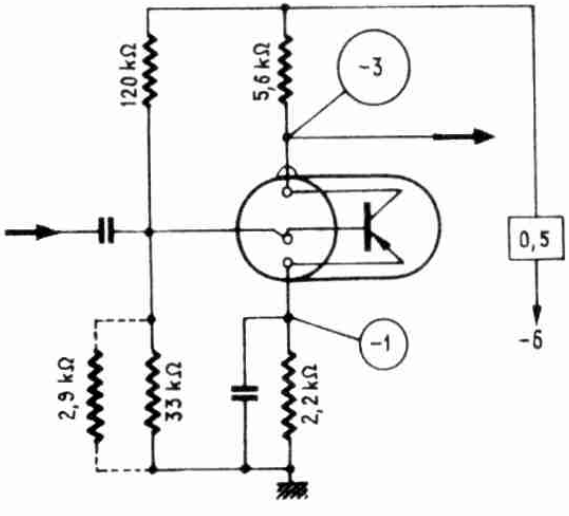
β = 50
GP = 38 dB



OC 57

BF

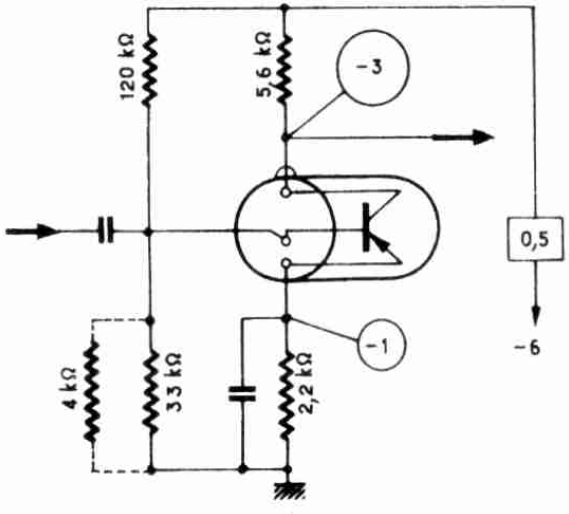
β = 35
Fb = 10 dB



OC 58

BF

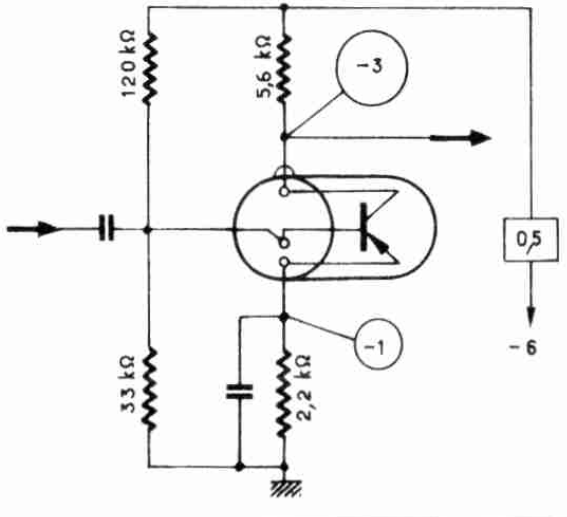
β = 55
Fb = 10 dB



OC 59

BF

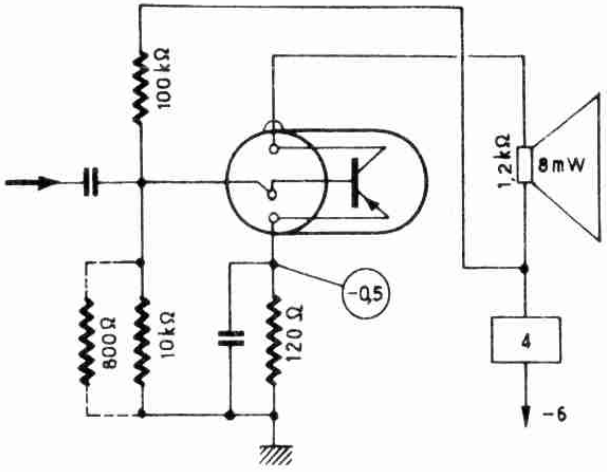
β = 80
Fb = 10 dB



OC 60

BF

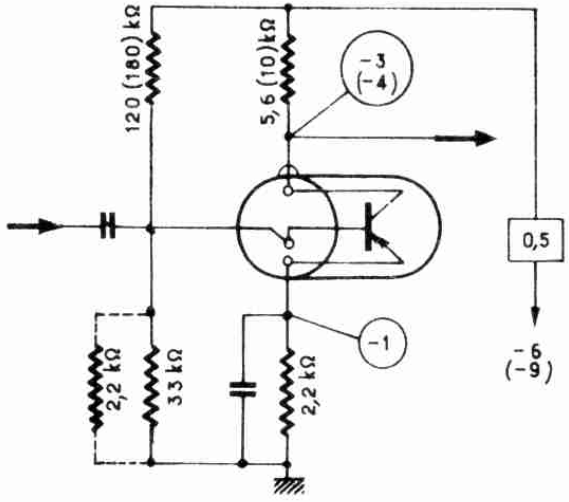
β = 60



OC 70

BF

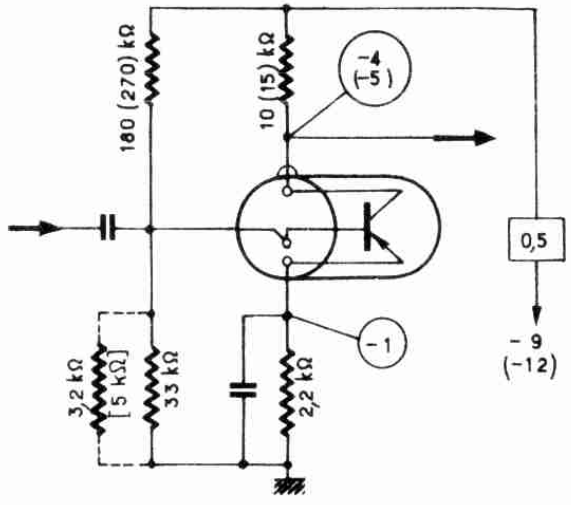
β = 30
Fb = 10 dB



OC 71 [OC 75]

BF

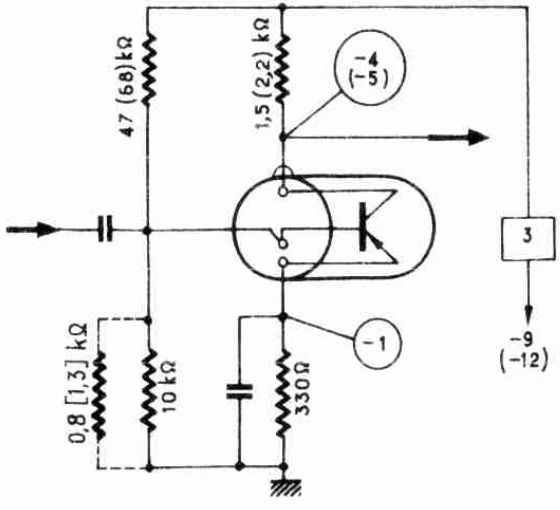
β = 50 [90]
Fb = 10 dB



OC 71 [OC 75]

BF

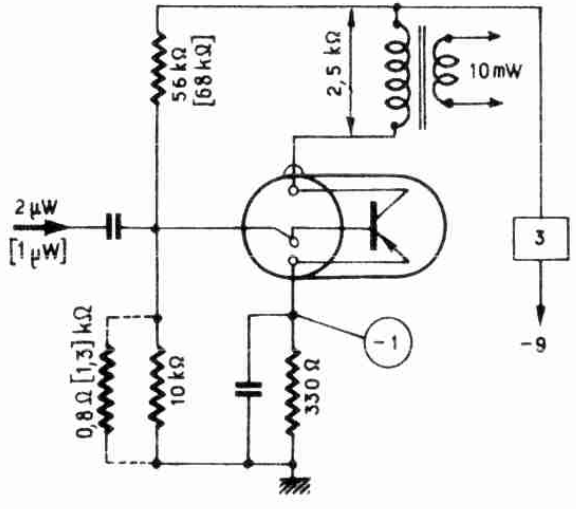
β = 50 [90]
Fb = 10 dB



OC 71 [OC 75]

BF

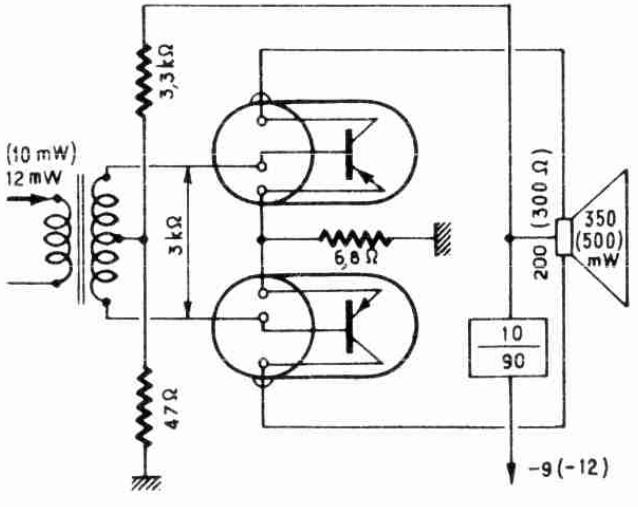
β = 50 [90]
GP = 37 dB [40 dB]



OC 72

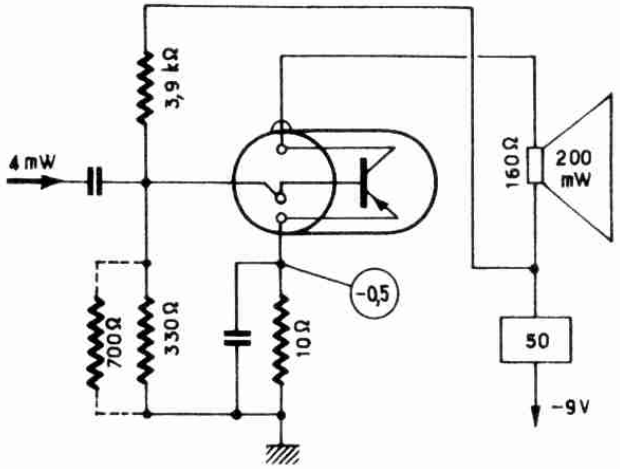
BF

β = 70
GP = 15 dB (17 dB)



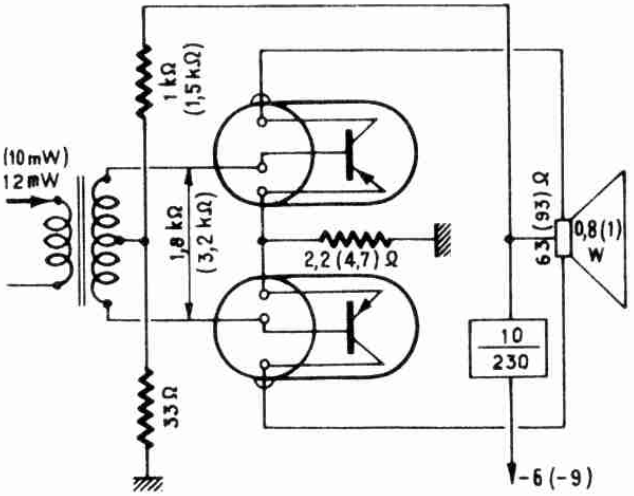
OC 74
BF

β = 100
GP = 27dB



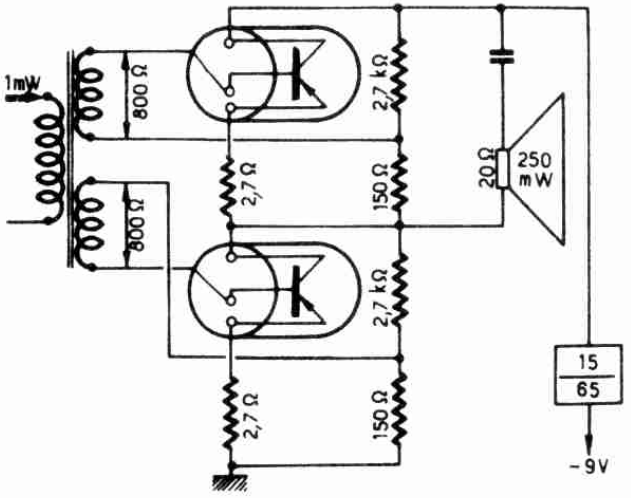
OC 74
BF

β = 100
GP = 18dB (20dB)



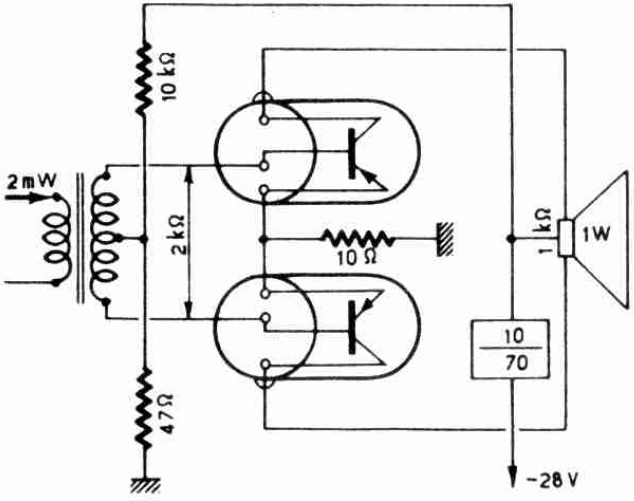
OC 74
BF

β = 100
GP = 24dB



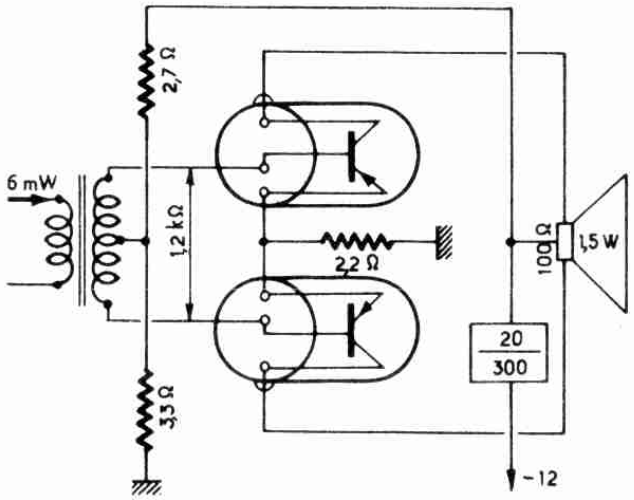
OC 77
BF

β = 50
GP = 27dB



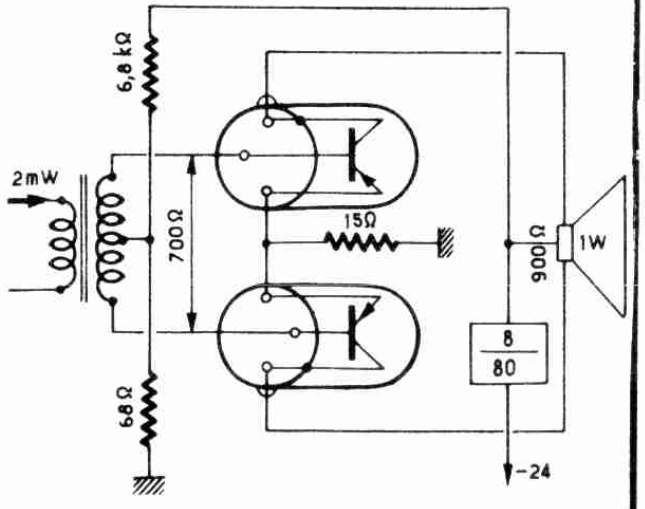
OC 80
BF

β = 85
GP = 24dB



SFT234
BF

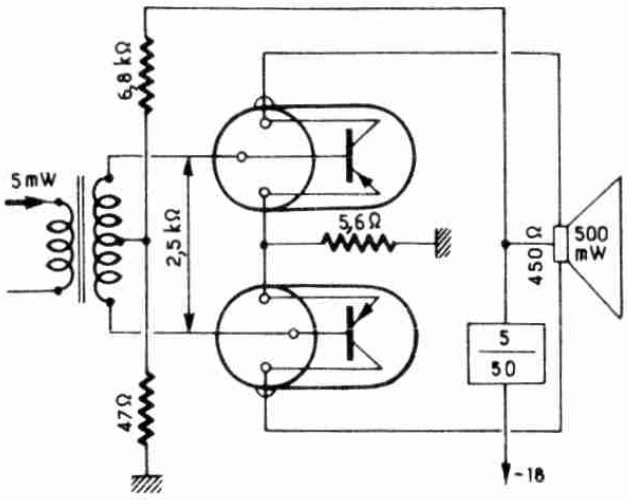
β = 40
GP = 27dB



SFT243

BF

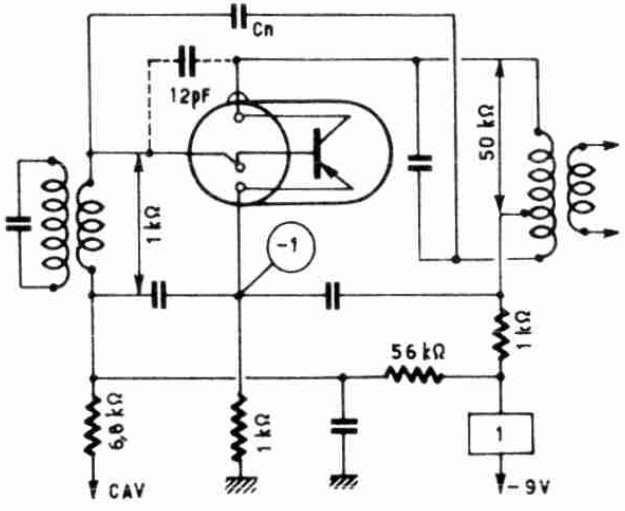
β = 30...60
GP = 20 dB



SFT306

MF 470 kHz

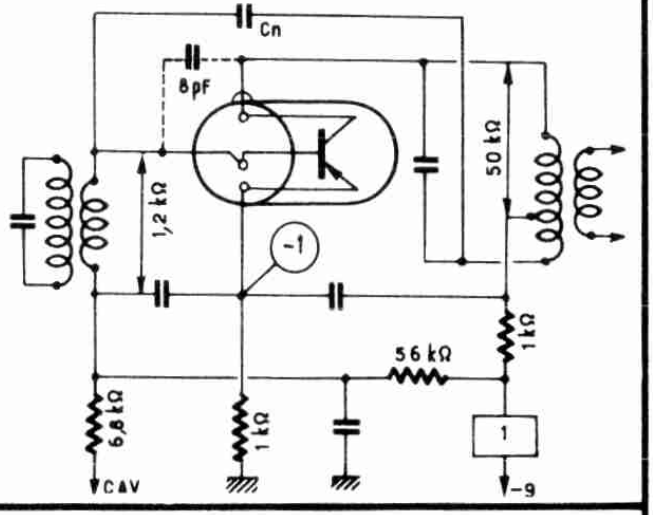
β = 30
GP = 36dB



SFT307

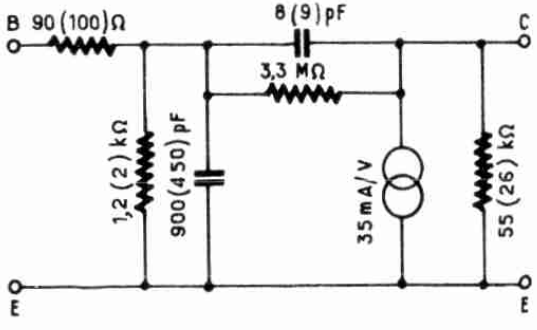
MF 470 kHz

β = 40
GP = 38 dB



SFT307 (SFT 308)

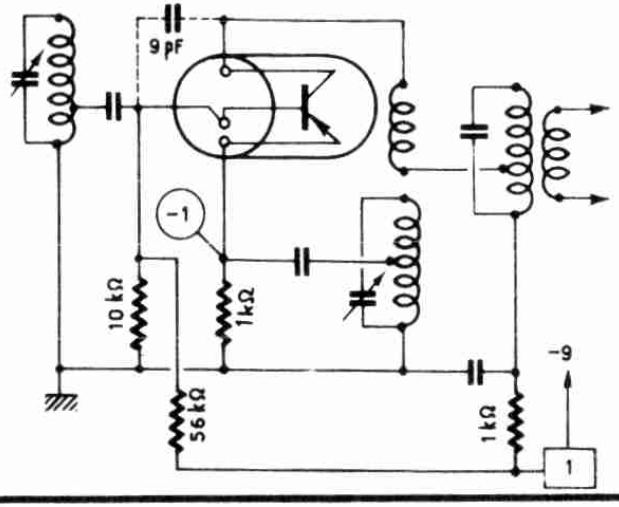
Ve = 6V
Ic = 1mA



SFT308

Conv. <2 MHz

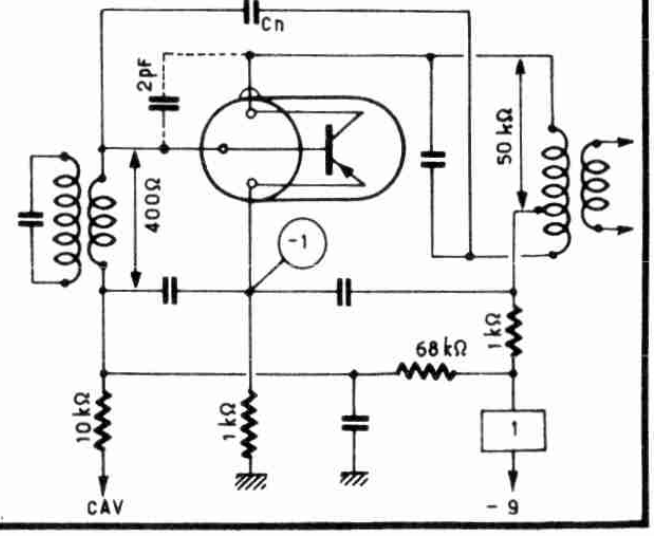
β = 70



SFT316

MF 10,7 MHz

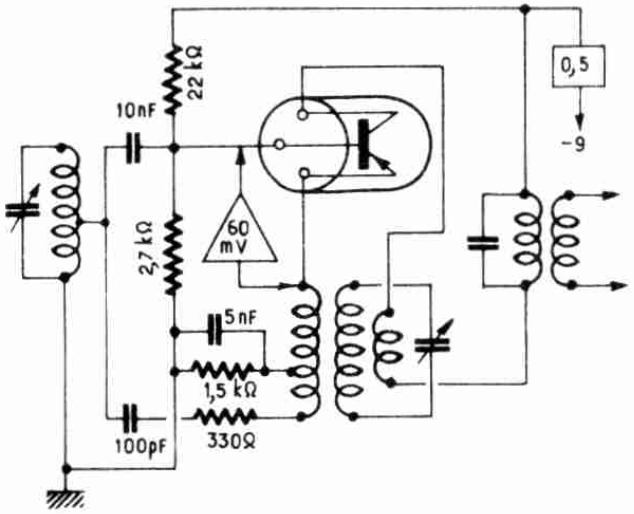
β = 120
GP = 25 dB



SFT 317

Conv. <18 MHz

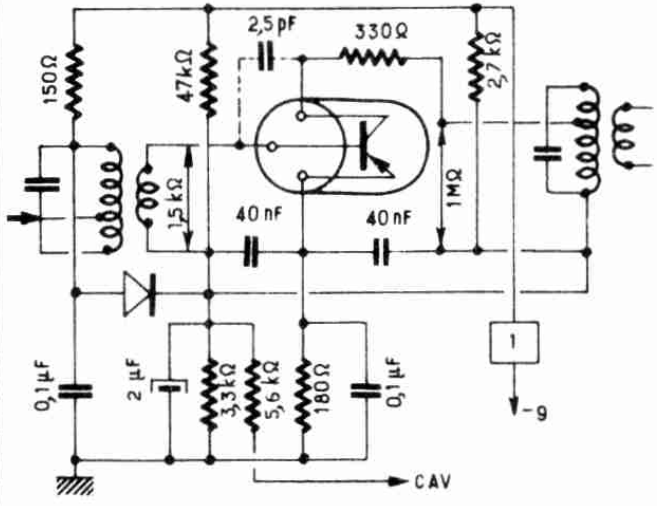
β = 20...100



SFT 319

MF 470 kHz

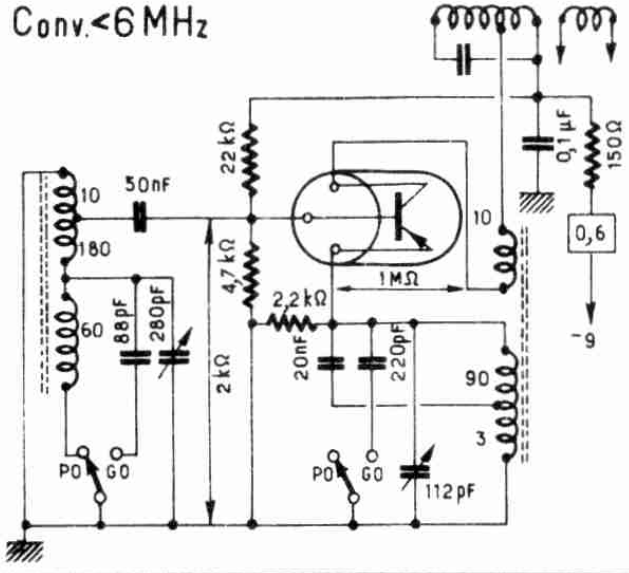
β = > 20
GP = 30dB



SFT 320

Conv. <6 MHz

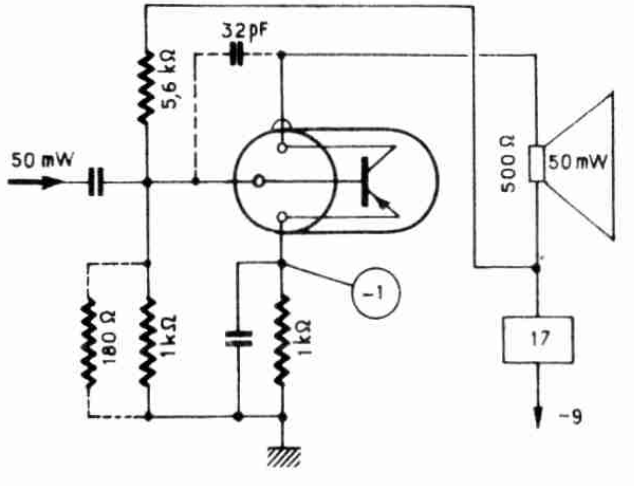
β = 80



SFT 321

BF

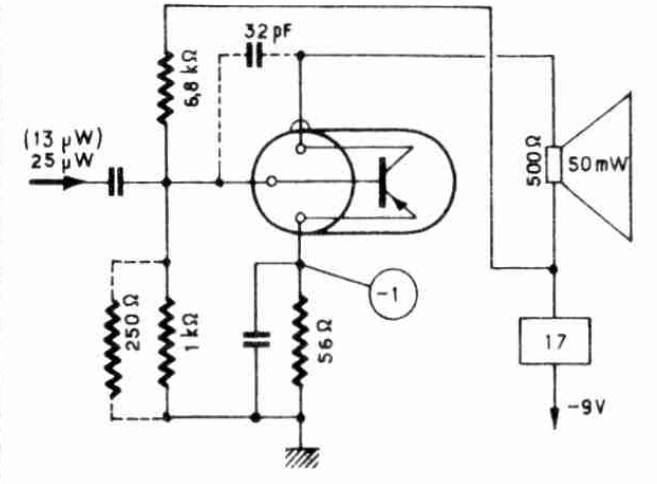
β = 30
GP = 30dB



SFT 322 (SFT 323)

BF

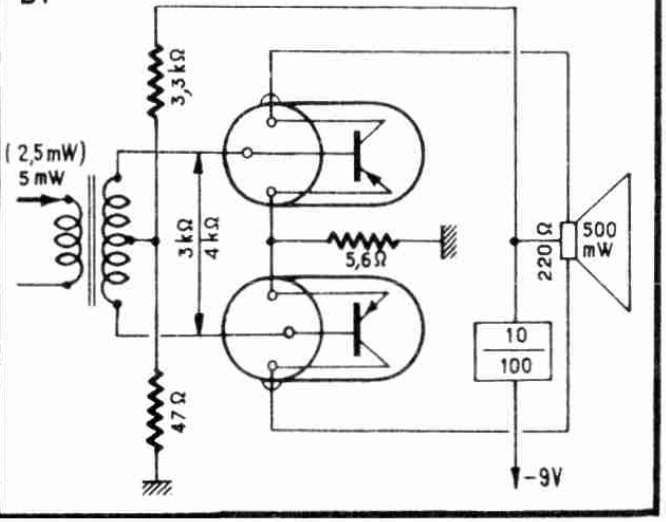
β = 50 (80)
GP = 33dB (36dB)



SFT 322 (SFT 323)

BF

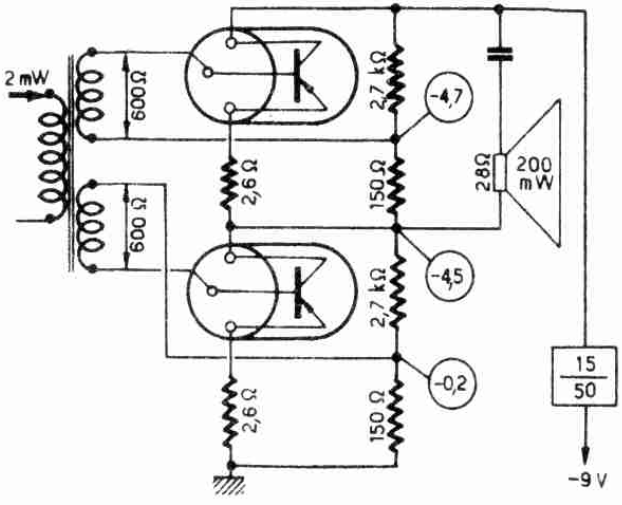
β = 50 (80)
GP = 20dB (23dB)



SFT 322

BF

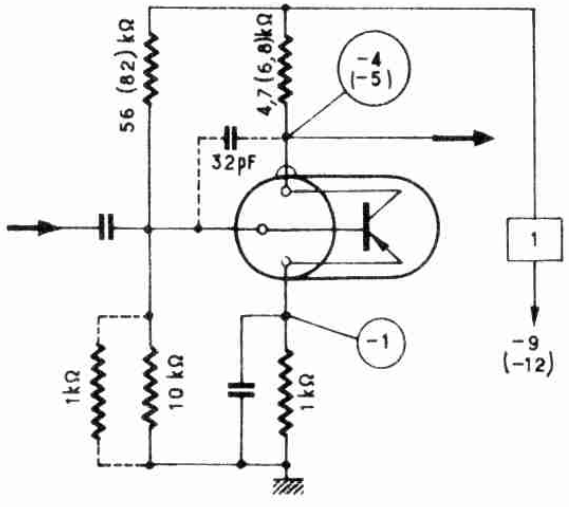
β = 50
GP = 20 dB



SFT 351

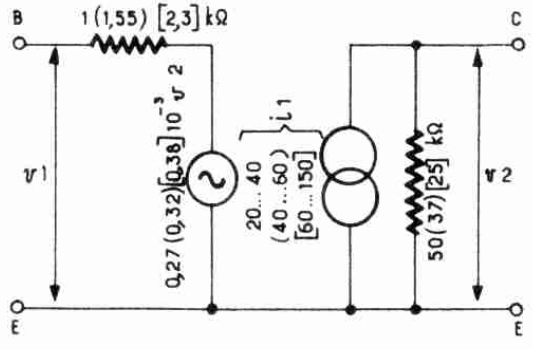
BF

β = 30
Fb = 8 dB



SFT 351 (SFT 352) (SFT 353)

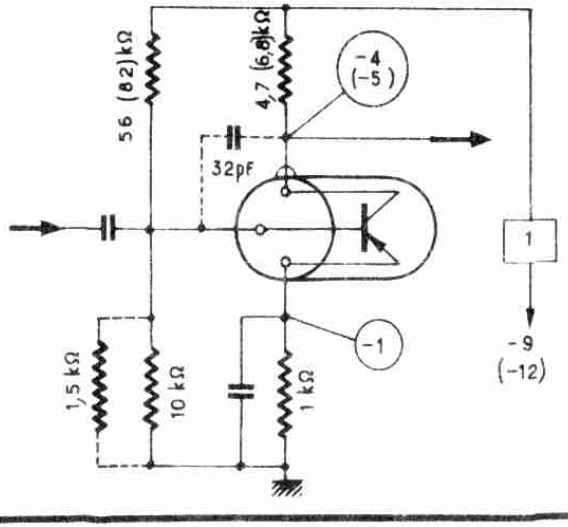
Vc = -6 V
Ic = 1 mA
f = 1 kHz
Fb = 8 dB



SFT 352

BF

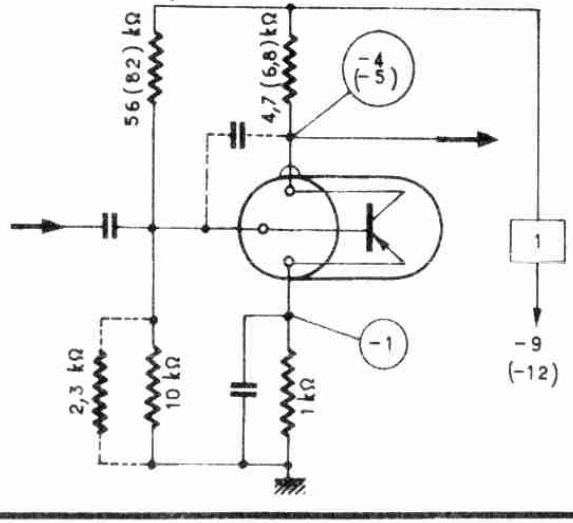
β = 50
Fb = 8 dB



SFT 353

BF

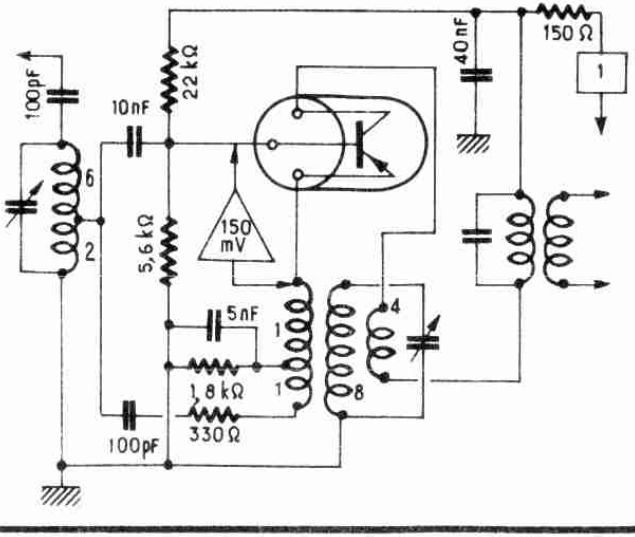
β = 80
Fb = 8 dB



SFT 354

β = 100

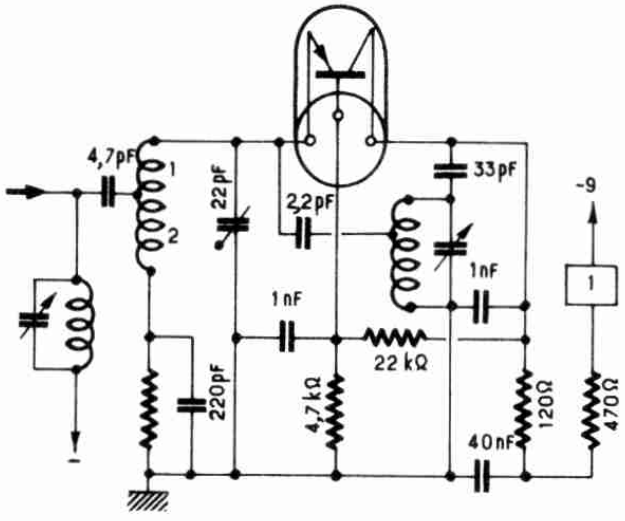
Conv. < 23 MHz



SFT357

Conv. 100MHz

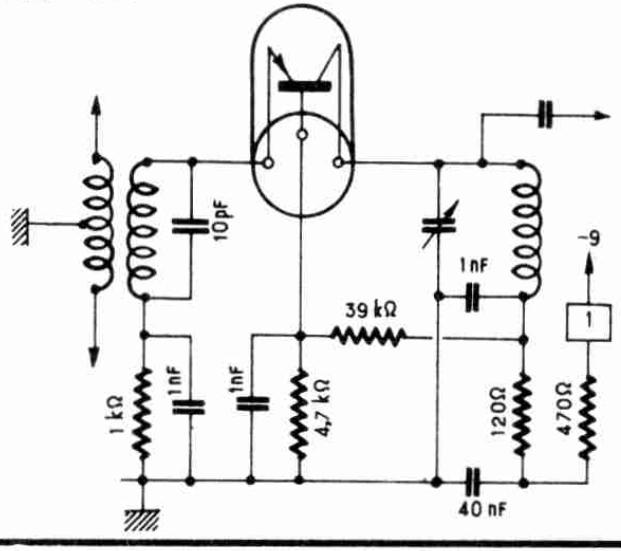
β = 100



SFT358

100 MHz

β = 150
GP = 14 dB
Fb = 7dB

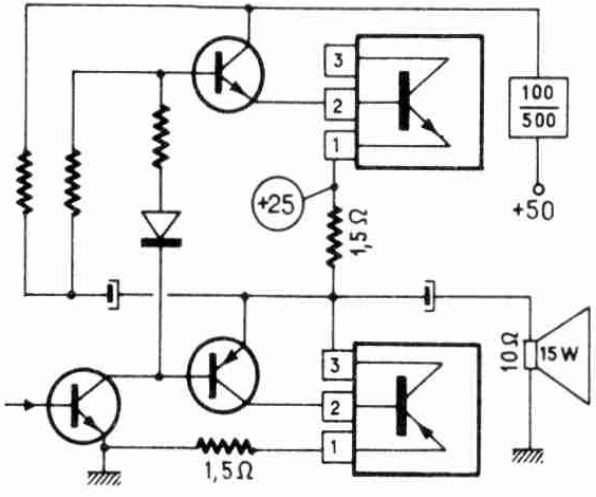


TIP 14,24

P

n-p-n
Si

β > 20
f_t > 40 MHz

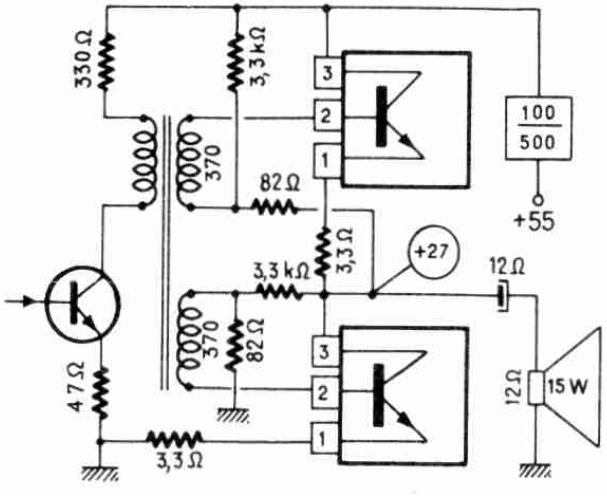


TIP 24

P

n-p-n
Si

β > 20

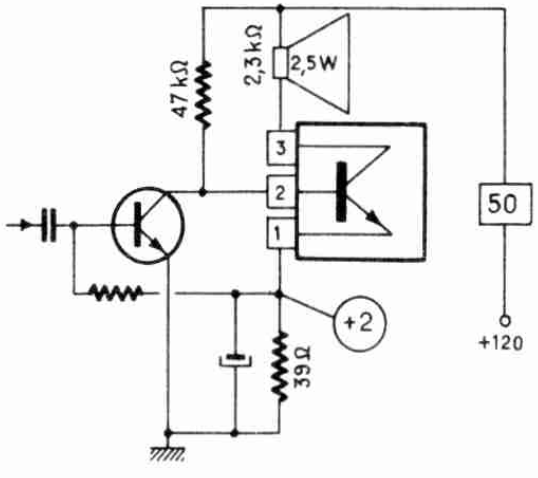


TIP 27

P

n-p-n
Si

β = 25...150

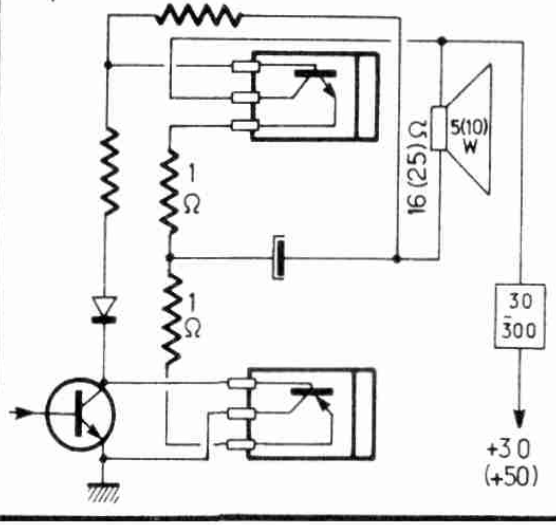


TIP29(A)
TIP30(A)

P

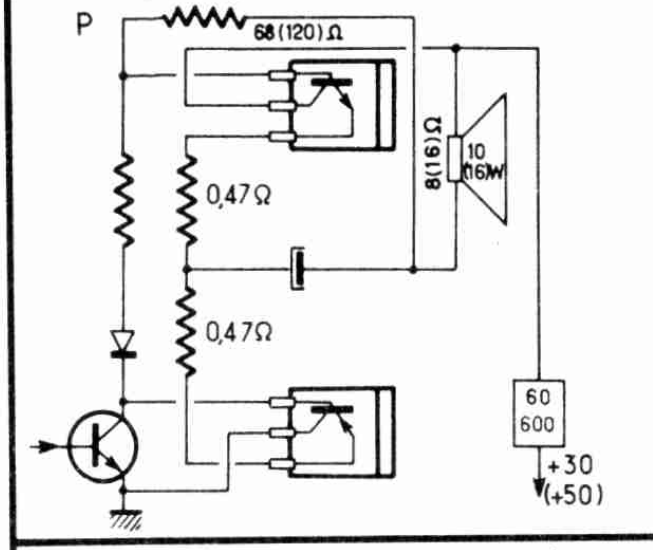
n-p-n Si
p-n-p Si

ß=40.....200



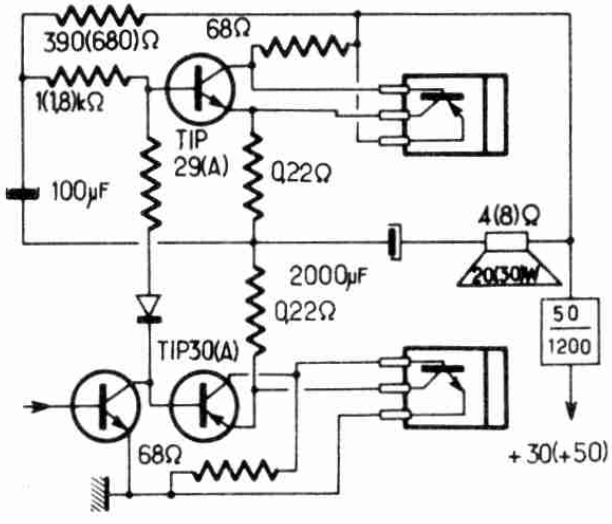
TIP 31 (A) n-p-n Si
TIP 32(A) p-n-p Si

ß = 20 100

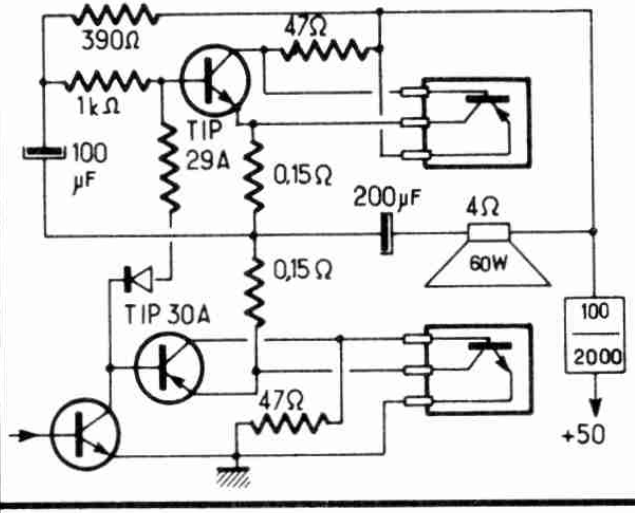


TIP 33(A) P n-p-n Si
TIP 34(A) p-n-p Si

ß = 25...125



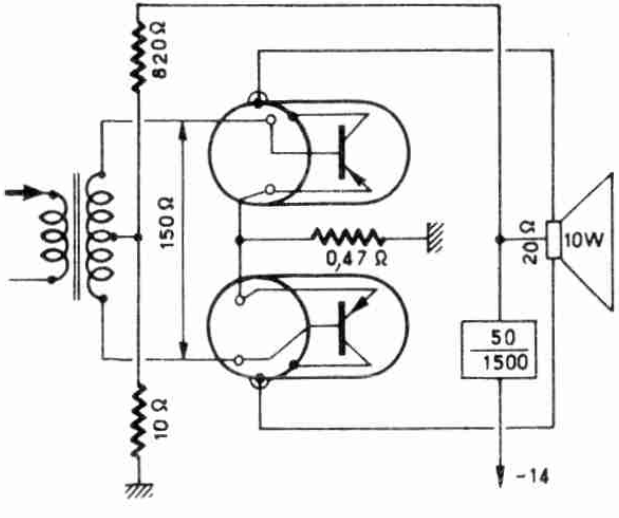
TIP 35 A P n-p-n Si
TIP 36 A p-n-p Si



2 N 155

P

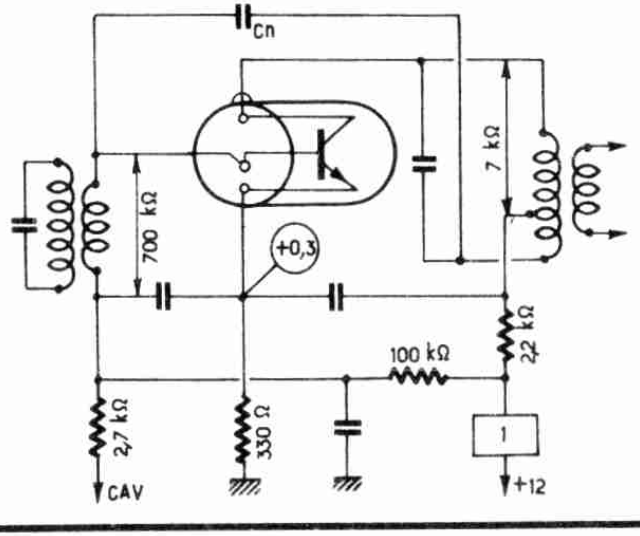
ß > 24
GP = 17dB



2N 169 A n-p-n

MF 470 kHz

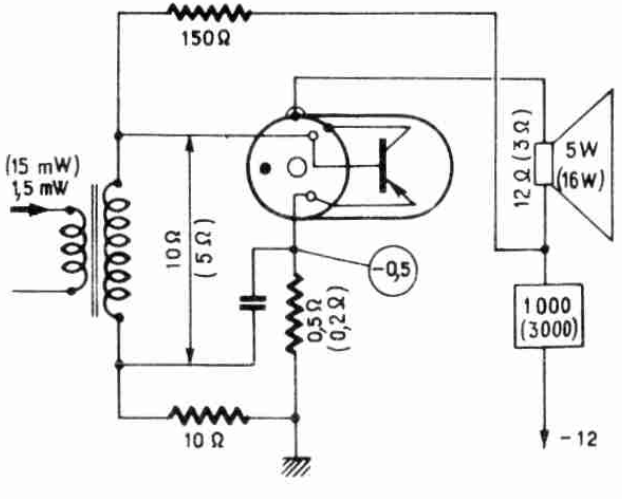
ß = 72
GP = 24dB



2 N 173

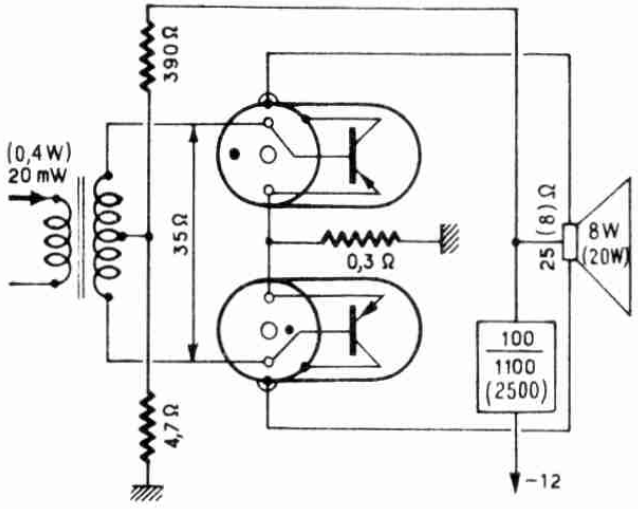
P

ß = 85
GP = 36dB
(30dB)



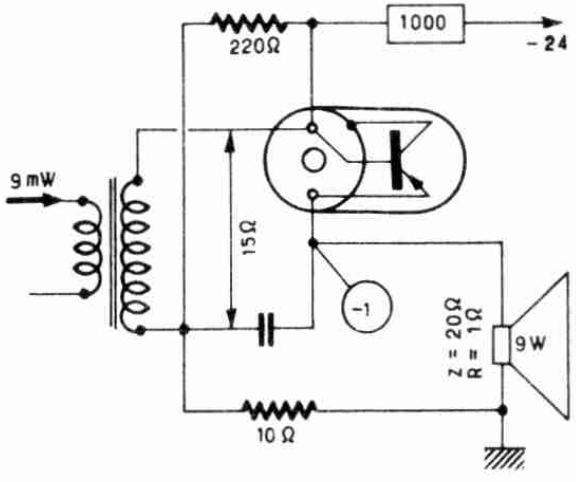
2N 173
P

β = 50...85
GP = 27dB (17dB)



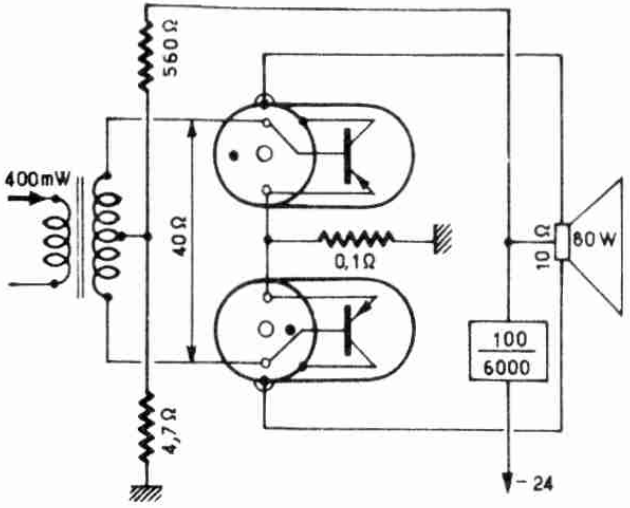
2N174
P

β = 40
GP = 30dB



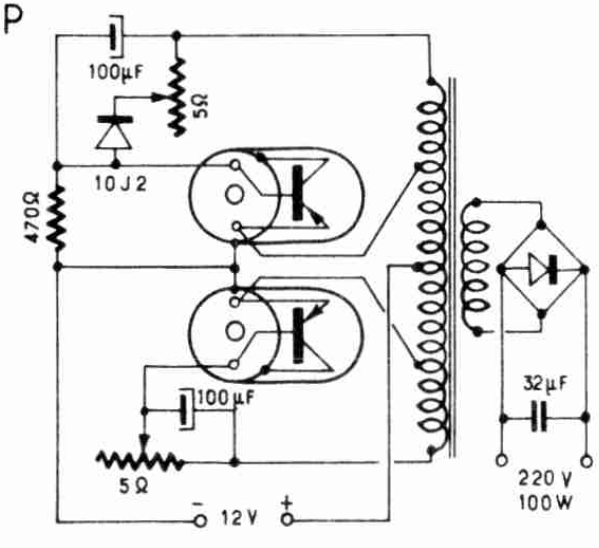
2N 174
P

β = 40
GP = 23dB



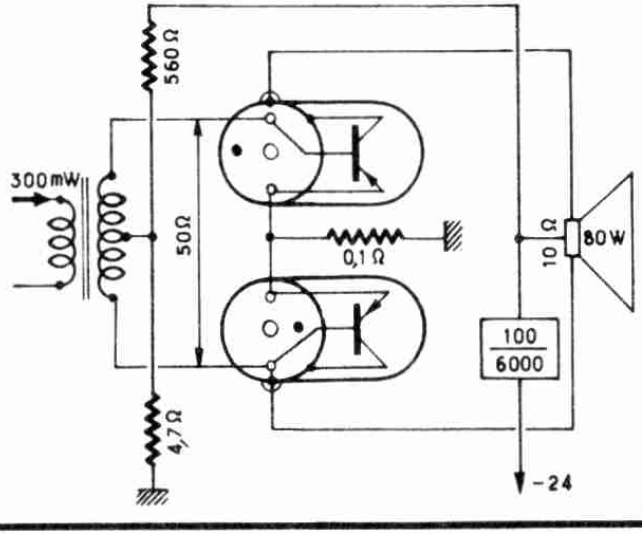
2N174
P

β = 40



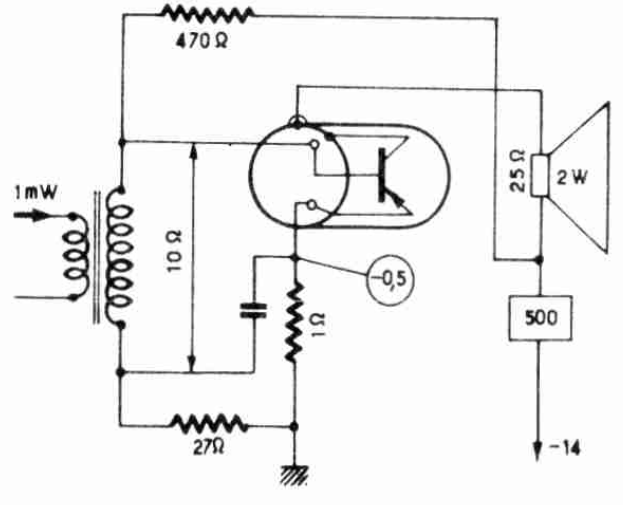
2N 174 A
P

β = 50
GP = 24dB



2N 176
P

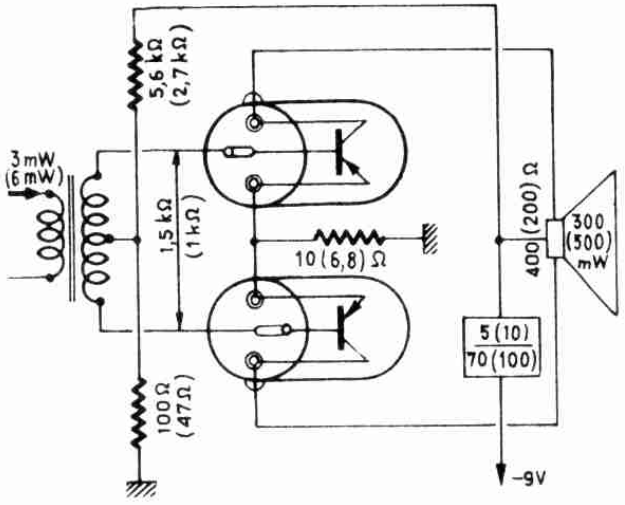
β = 63
GP = 35dB



2N 186,(A)

BF

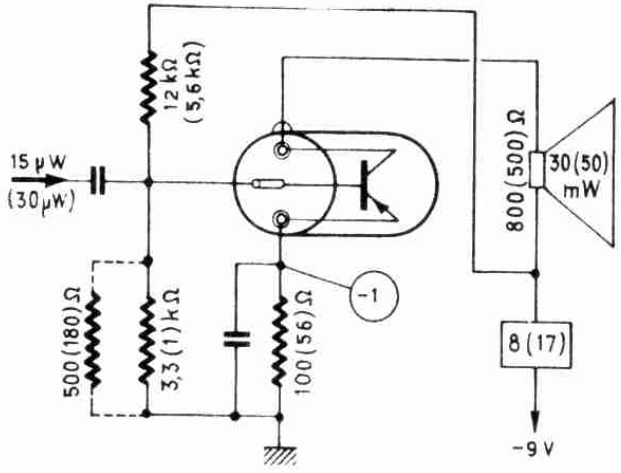
β = 24
GP = 20(18)dB



2N 187,(A)

BF

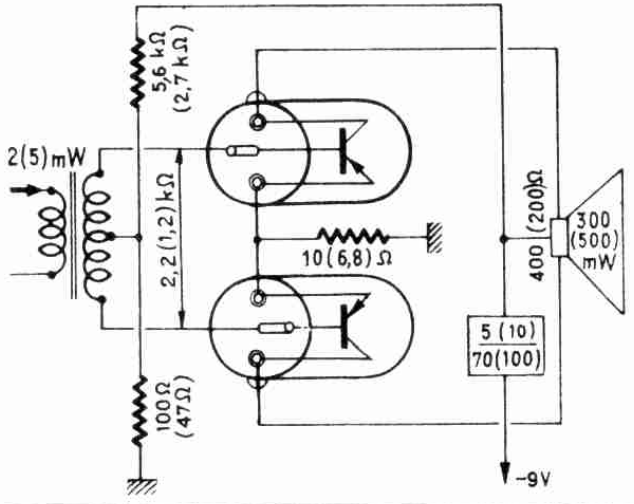
β = 36
GP = 33(30)



2N 187,(A)

BF

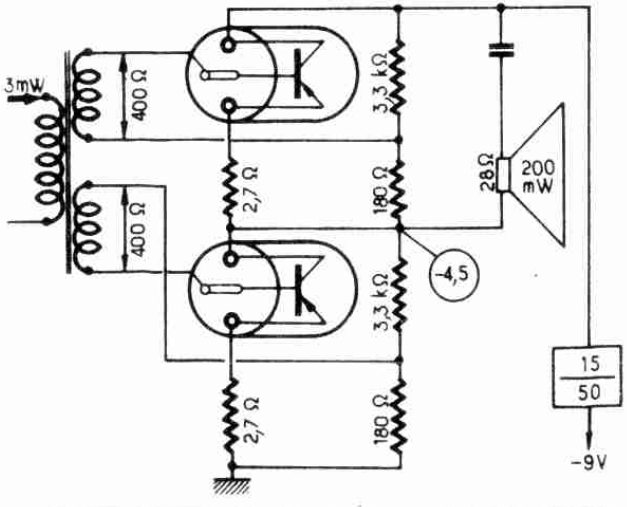
β = 36
GP = 22(20)dB



2N 187A

BF

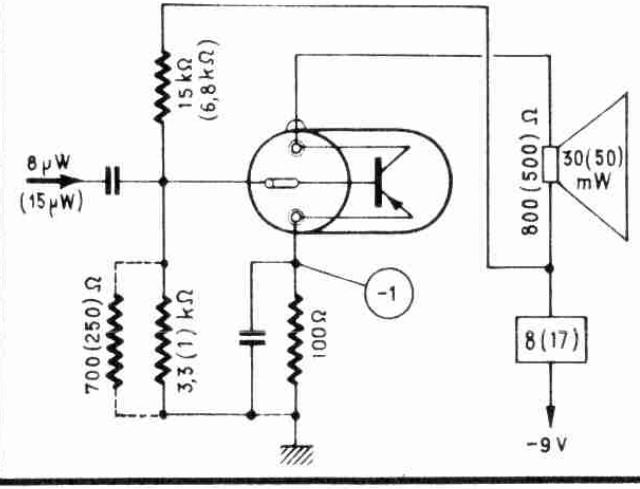
β = 36
GP = 18 dB



2N 188,(A)

BF

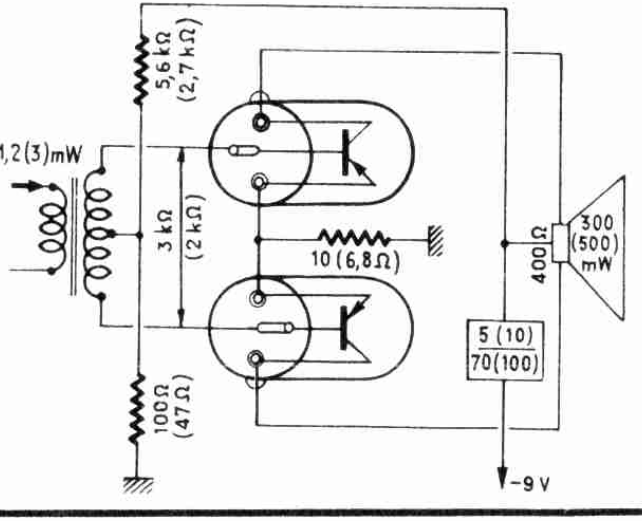
β = 54
GP = 36(24)dB



2N 188,(A)

BF

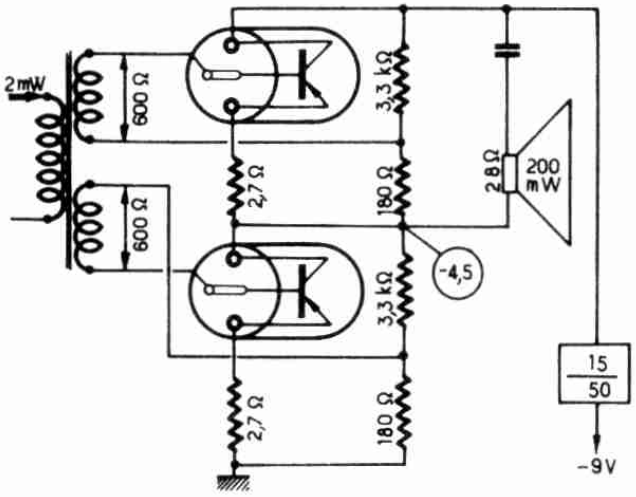
β = 54
GP = 24(22)dB



2N 188A

BF

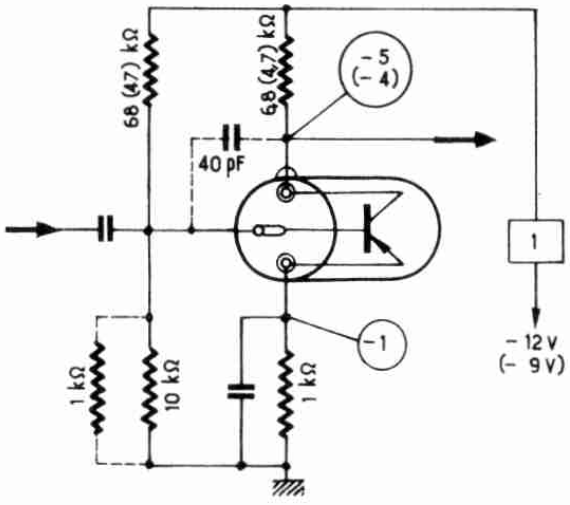
β = 54
GP = 20 dB



2N 189

BF

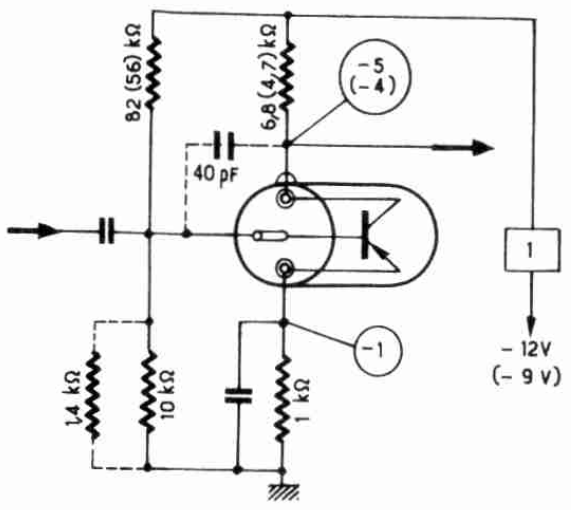
β = 24
GP = 15 dB



2N 190

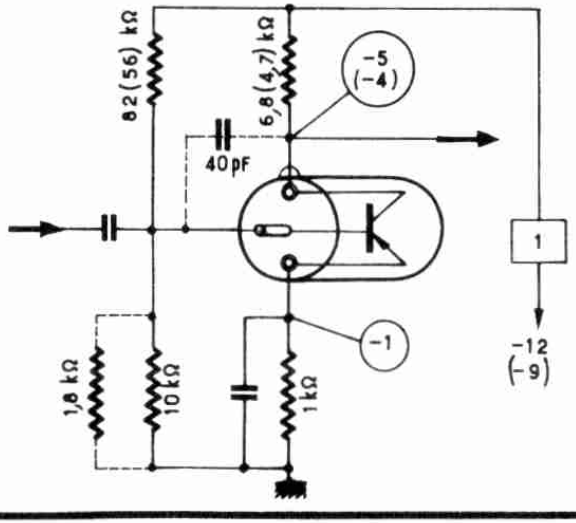
BF

β = 36
Fb = 15 dB



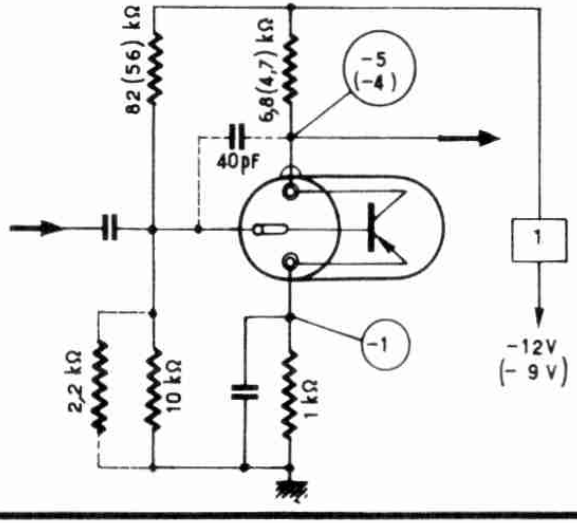
2N 191

β = 54
Fb = 15 dB



2N 192

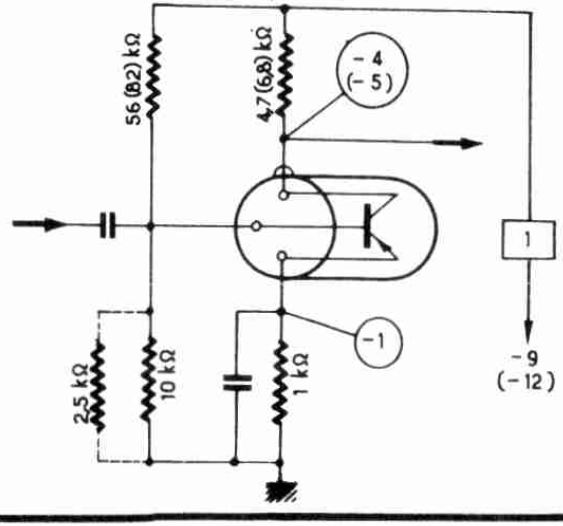
β = 75
Fb = 15 dB



2N 217

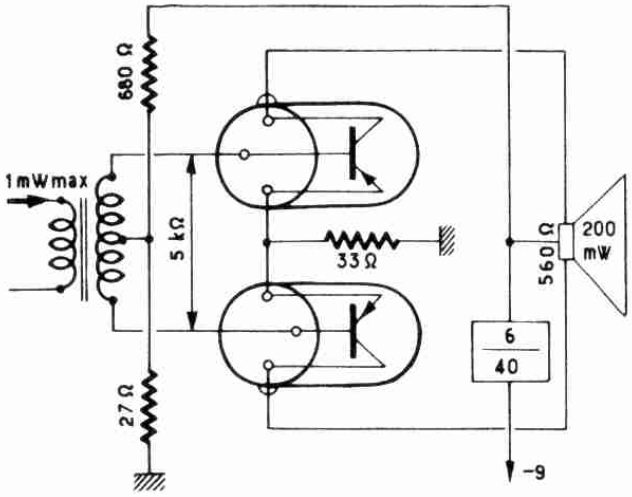
BF

β = 75



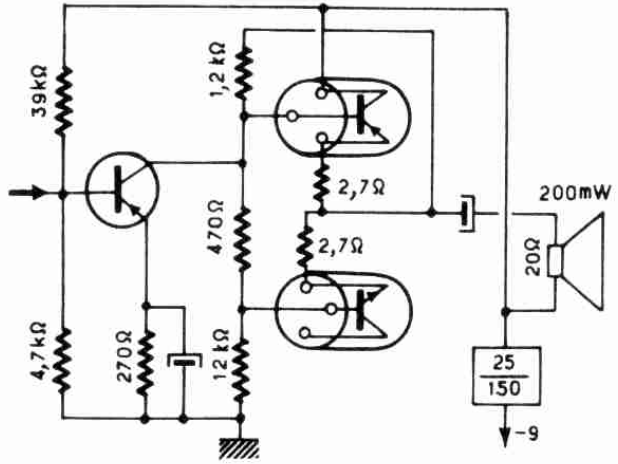
2N 217
BF

β = 75
GP = 30 dB max



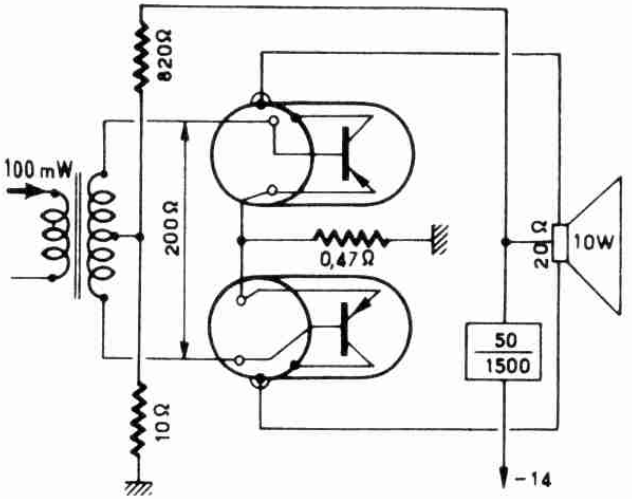
2N229 n-p-n
2N226 p-n-p

= 25...100



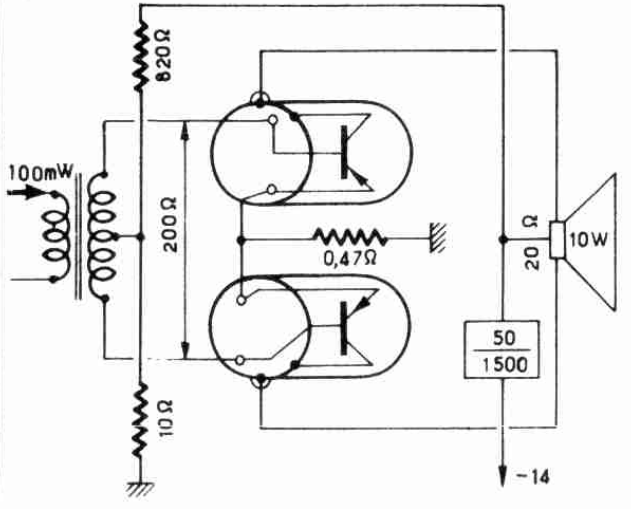
2N 235 A,B
P

β = 50
GP = 20 dB



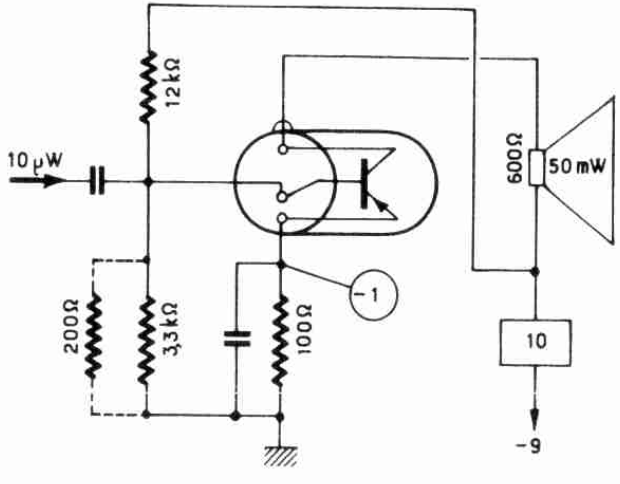
2N 236 B
P

β = 60
GP = 20 dB



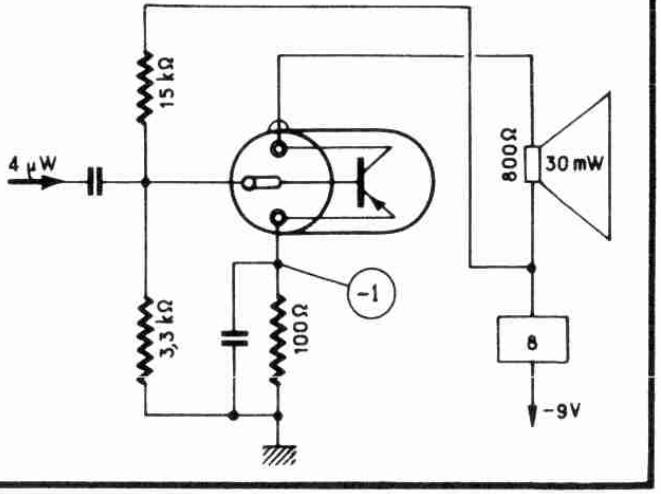
2N 238
BF

β = 50
GP = 33 dB



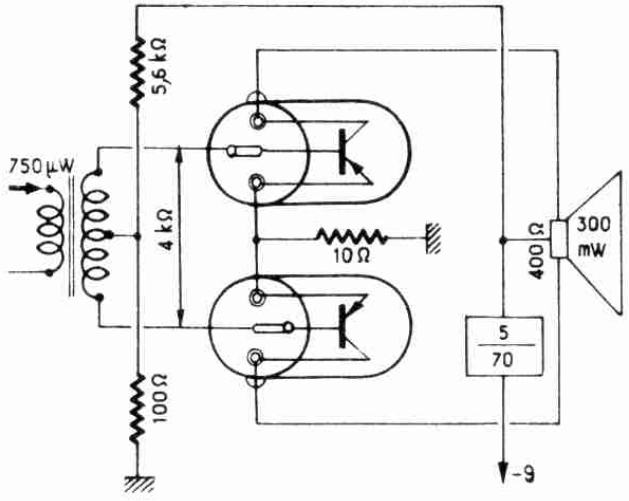
2N 241
BF

β = 73
GP = 39 dB



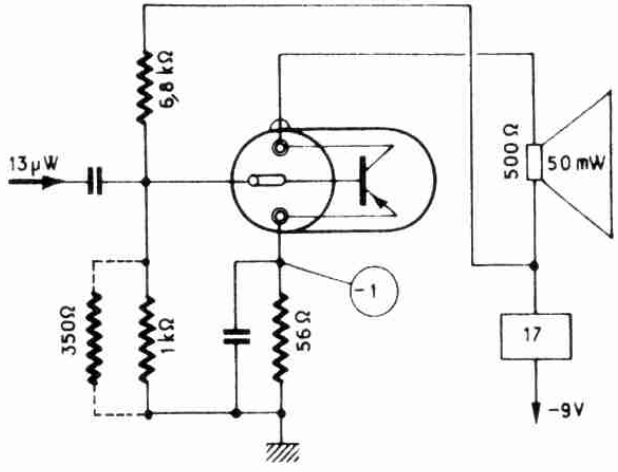
2N 241
BF

β = 73
GP = 26 dB



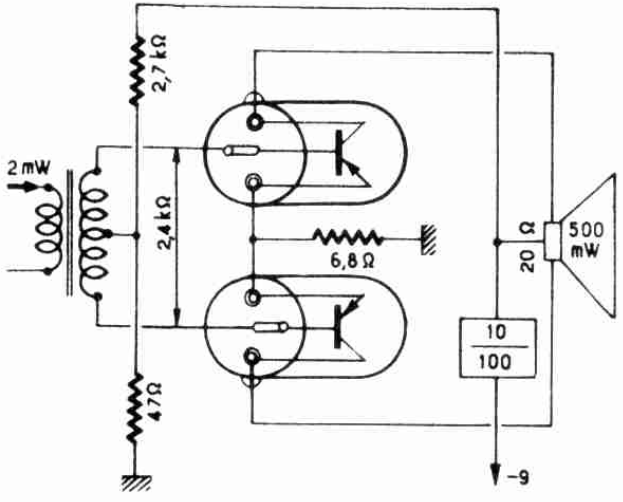
2N 241 A
BF

β = 73
GP = 36 dB



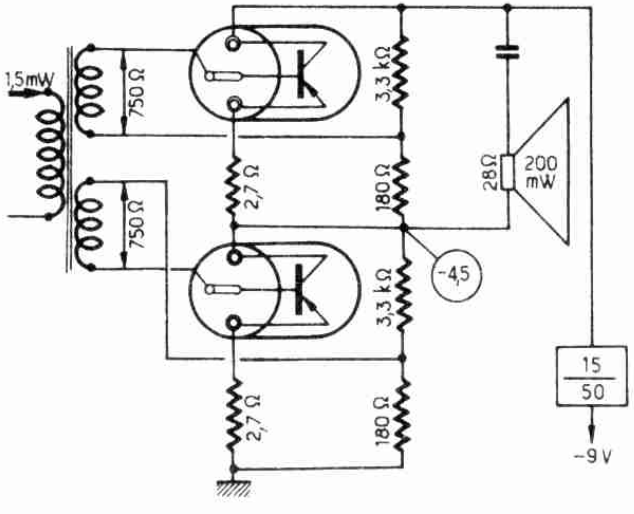
2N 241 A
BF

β = 73
GP = 24 dB

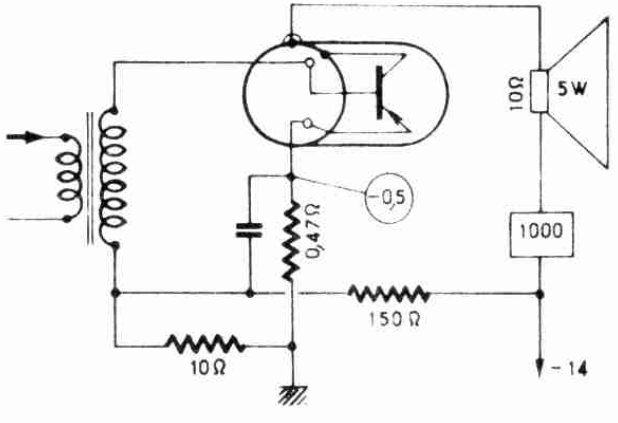


2N 241 A
BF

β = 73
GP = 22 dB

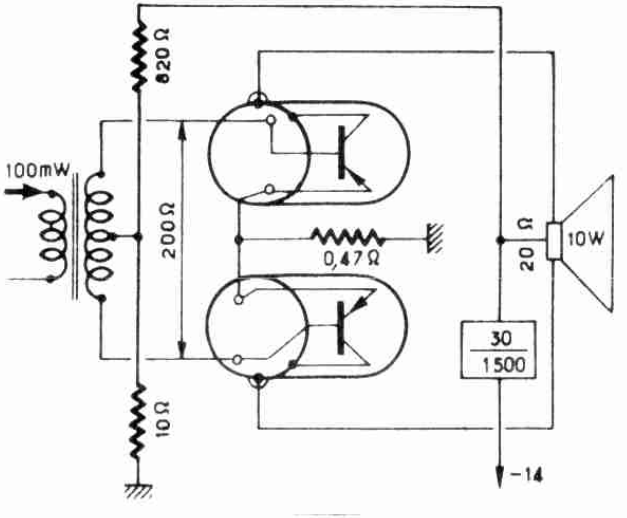


2N 242
P



2N 250
P

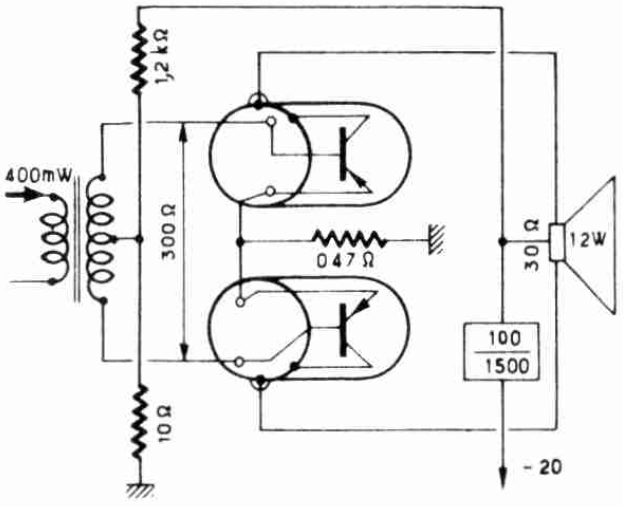
β = 50
GP = 20dB



2N 251

P

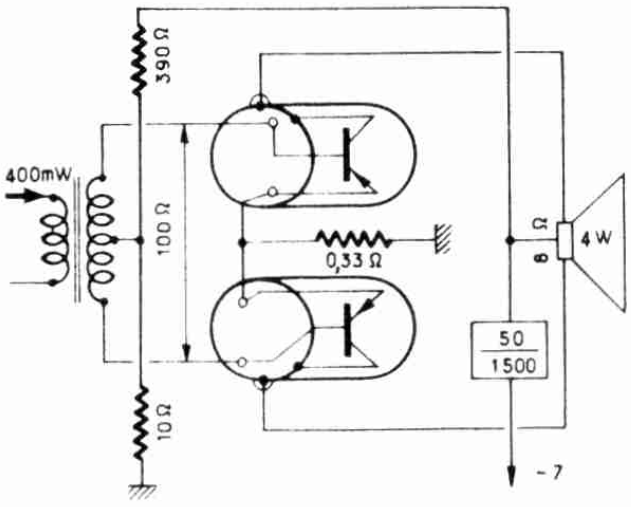
β = 30
GP = 15 dB



2N 255

P

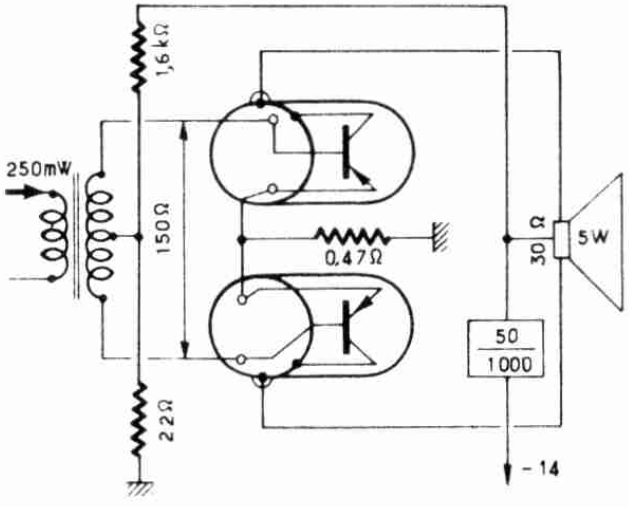
β > 15
GP > 10 dB



2N 256

P

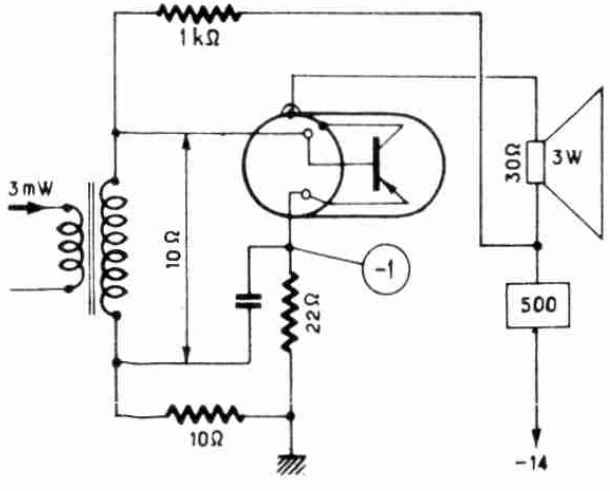
β > 15
GP > 13 dB



2N 257

P

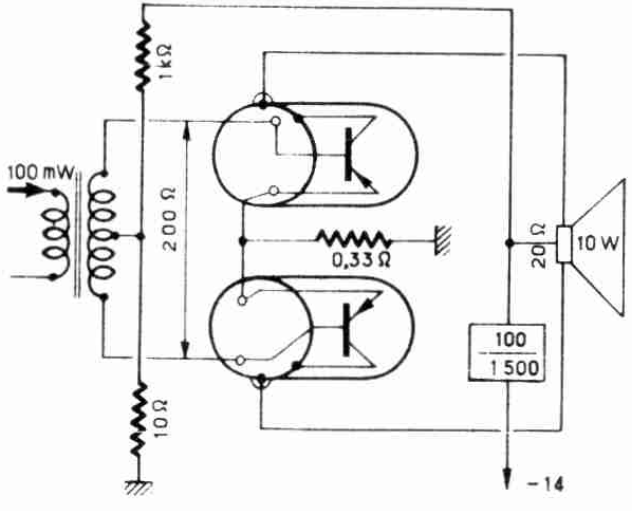
β = 50
GP = 30 dB



2N 257

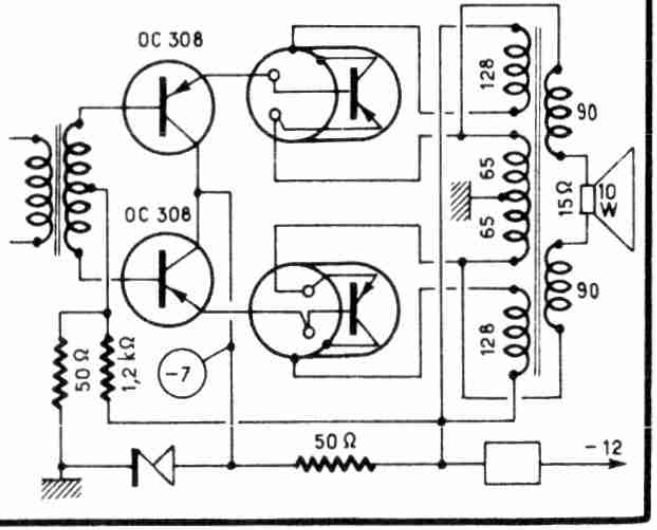
P

β = 50
GP = 20 dB



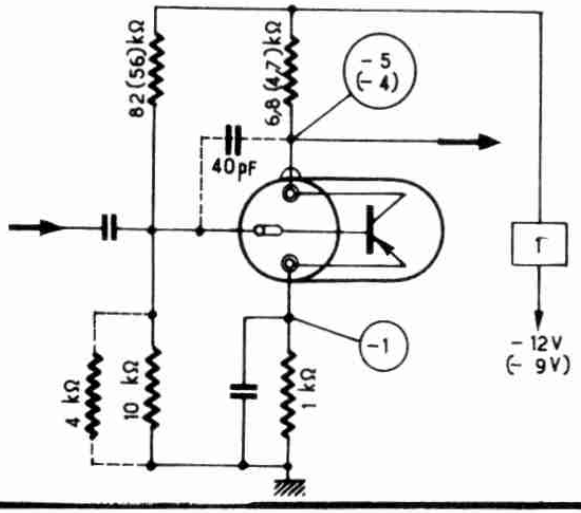
2N 257

P



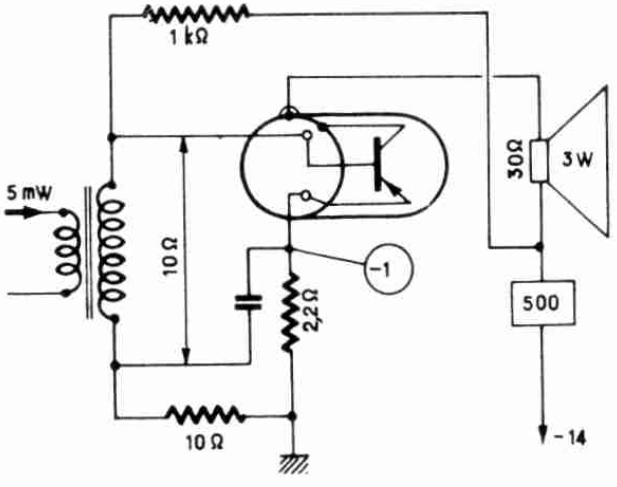
2 N 265
BF

β = 110
F = 15 dB



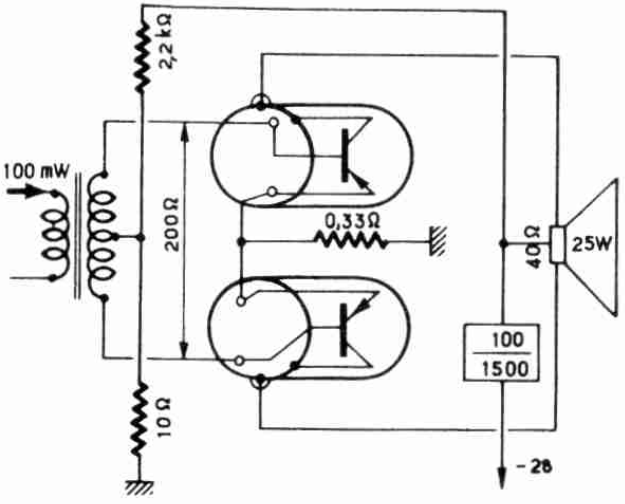
2N 268
P

β = 50
GP = 28 dB

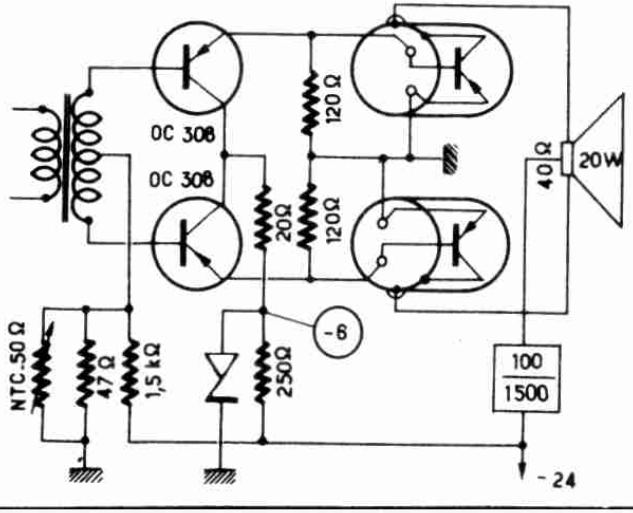


2N 268
P

β = 50
GP = 25 dB

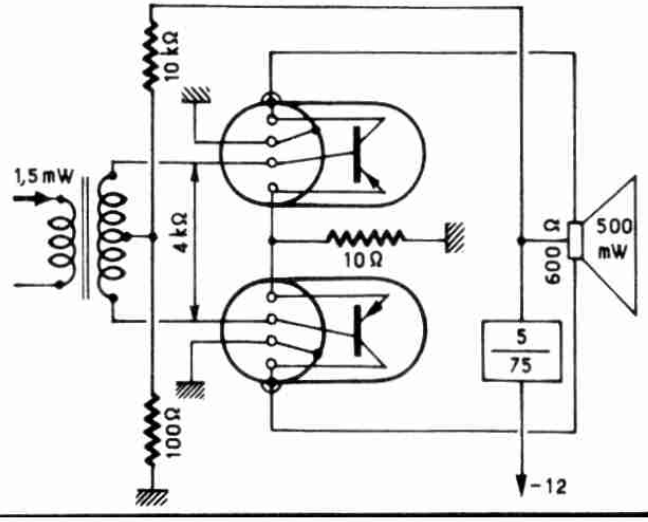


2N 268
P



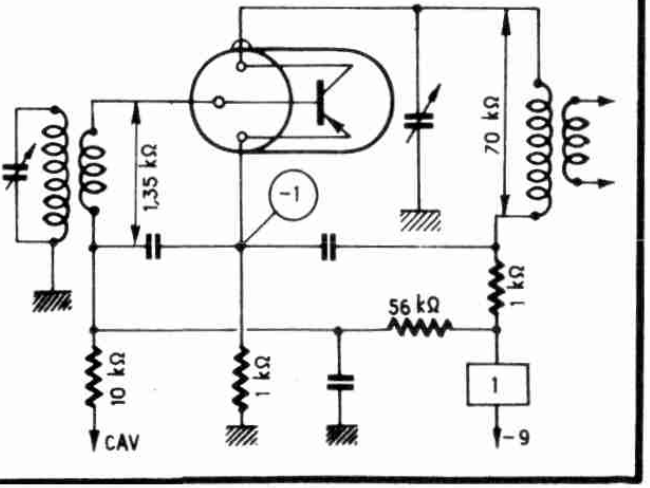
2N 270
BF

β = 70
GP = 25 dB



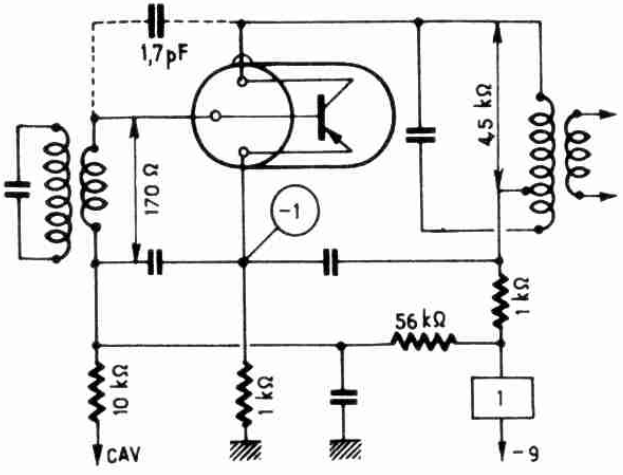
2N 274
H.F_0,5... 1,6 MHz

β = 60
GP = 37dB



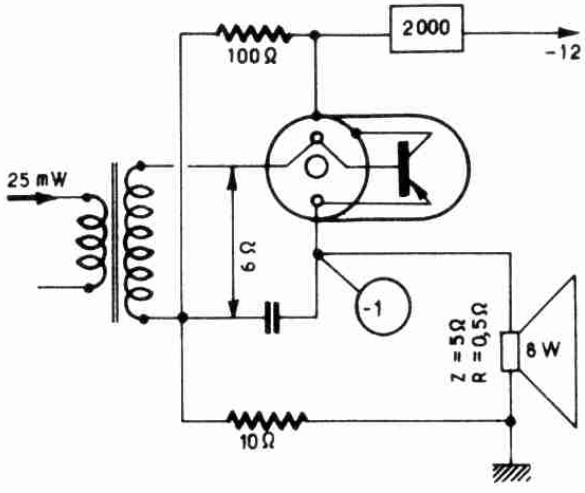
2N 274
MF_10 MHz

β=60



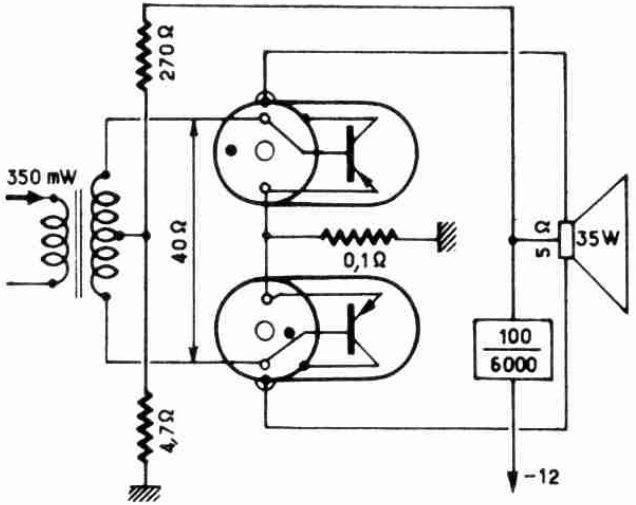
2N277
P

β = 40
GP = 25dB



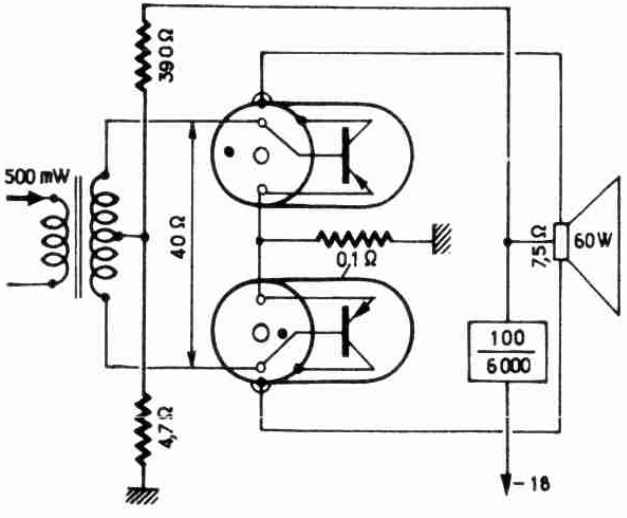
2N 277
P

β = 40
GP= 20dB



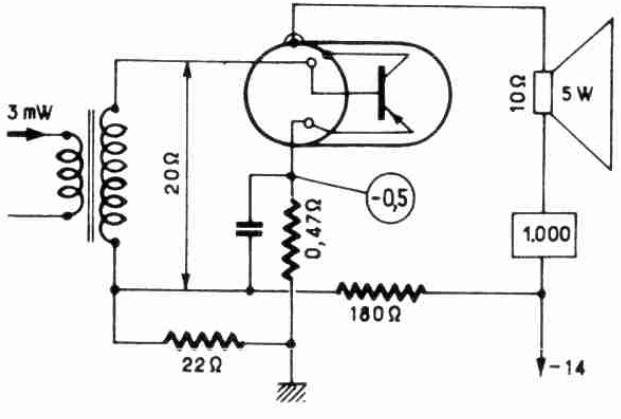
2N 278
P

β = 40
GP = 21dB



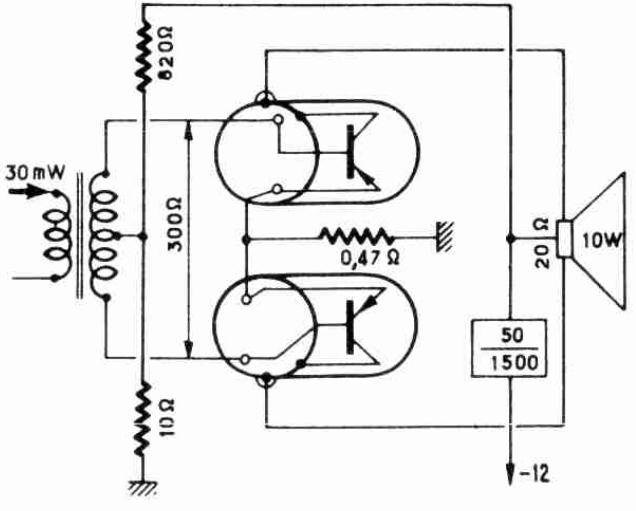
2N 285 A
P

β = 150
GP = 33 dB



2N 285 A
P

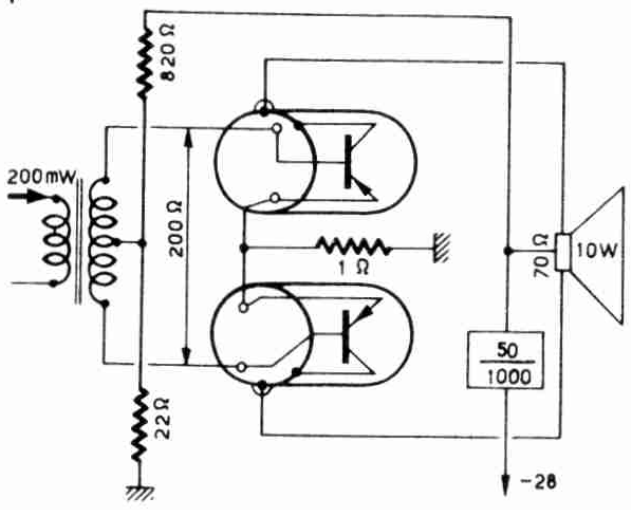
β = 150
GP = 26dB



2N 296

P

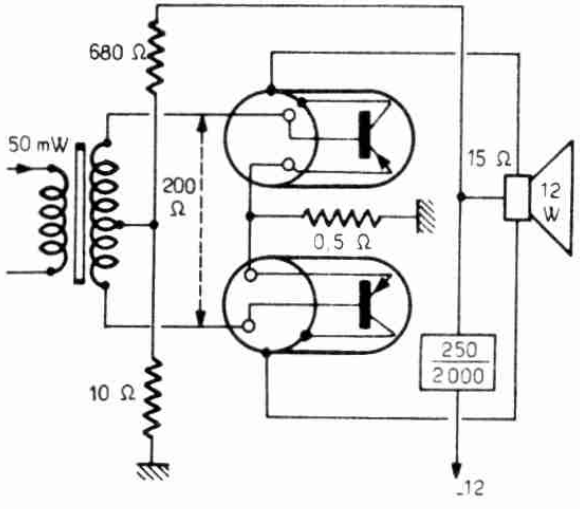
$\beta > 20$
GP> 17 dB



2N 297A

P

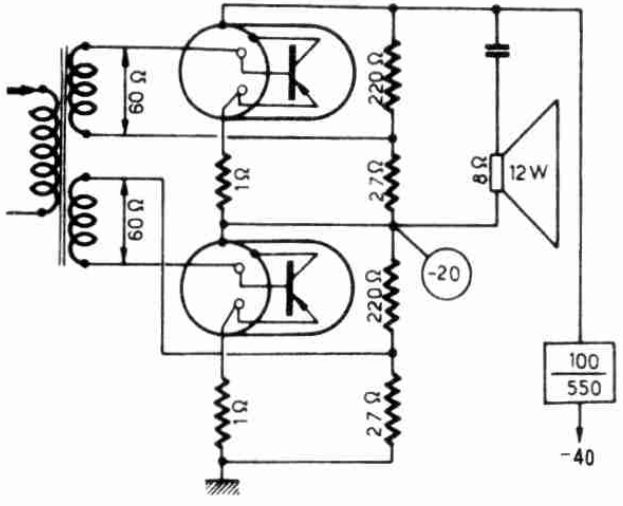
β = 40 . . 100
GP = 24 dB



2N 301

P

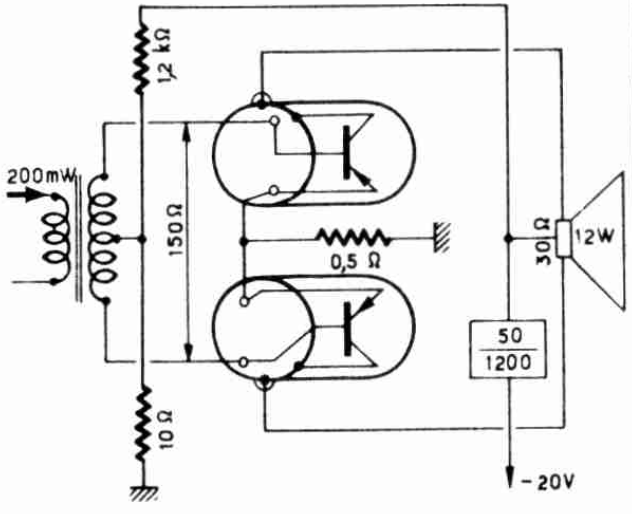
β = 70



2N 301,A

P

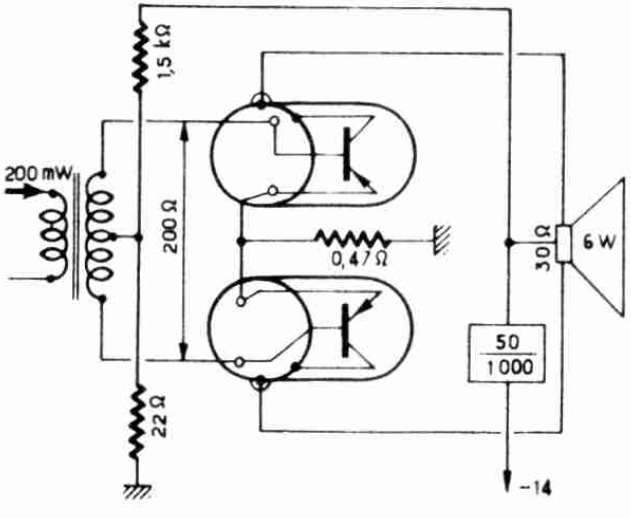
β = 70
GP = 18 dB



2N 307, A

P

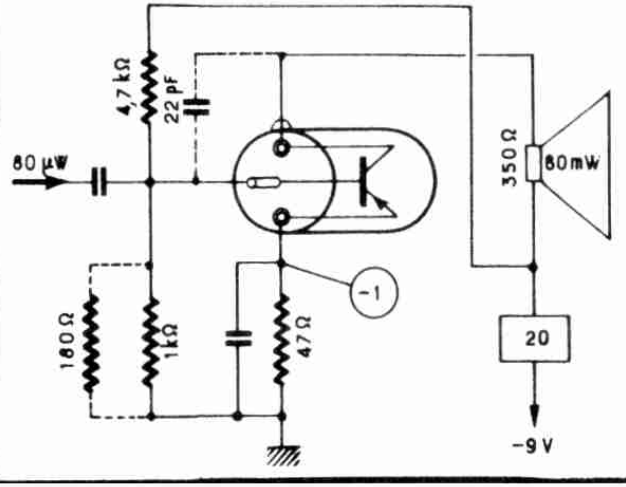
$\beta > 20$
GP > 15 dB



2N 319

BF

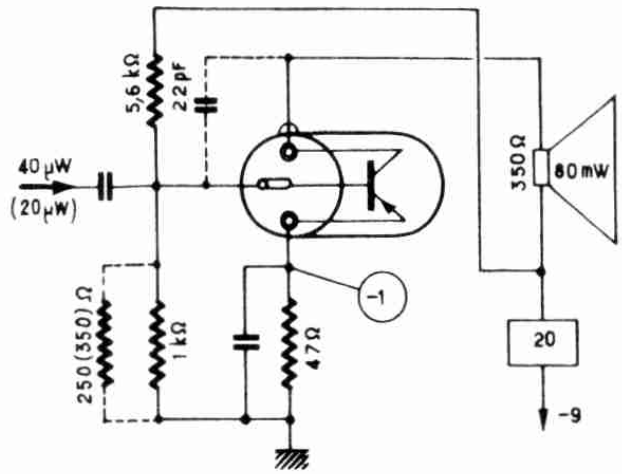
β = 16...41
GP = 30 dB



2 N 320,(21)

BF

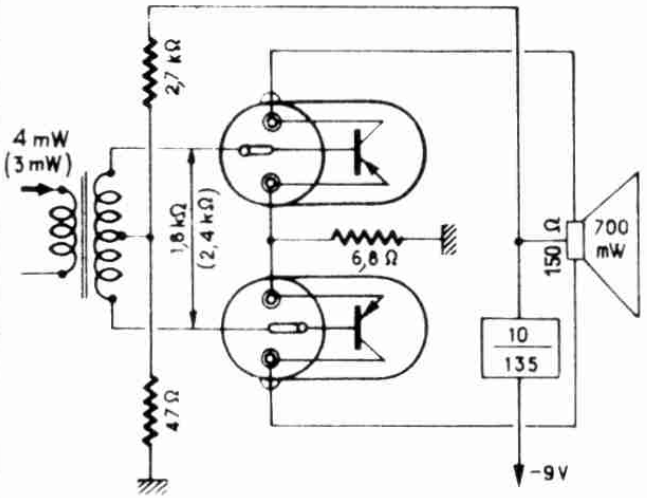
β = 30...64 (44...80)
GP = 33 (36) dB



2 N 320,(21)

BF

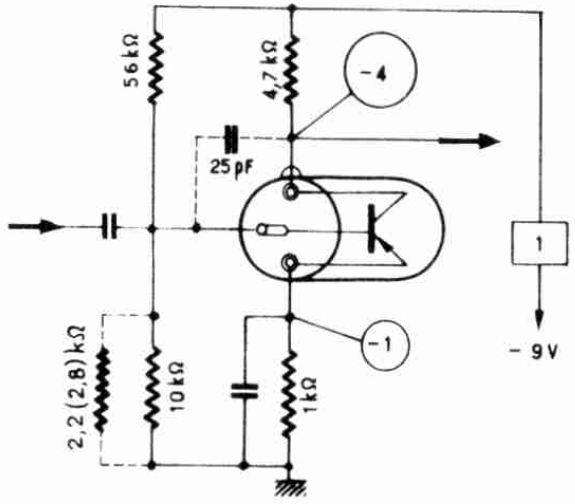
β = 30...64 (44...80)
GP = 22 (24) dB



2 N 322,(3)

BF

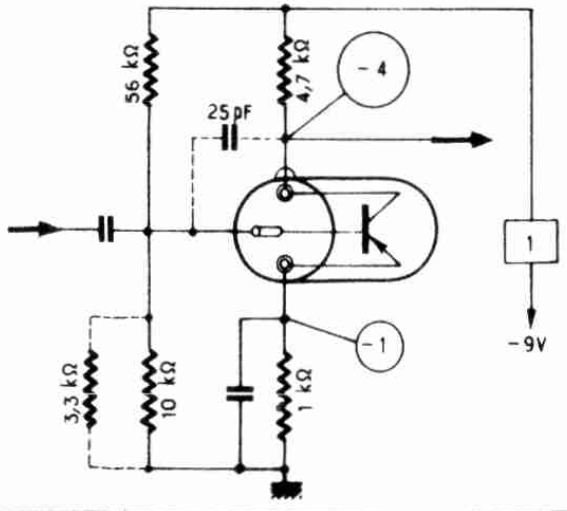
β = 48 (70)
Fb = 6 dB



2 N 324

BF

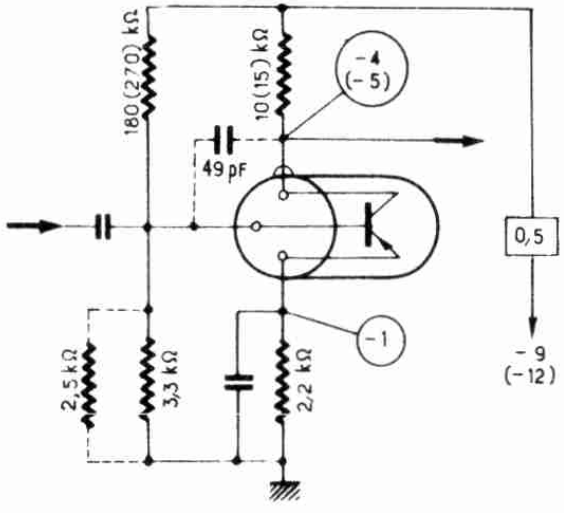
β = 90
Fb = 6 dB



2 N 331

BF

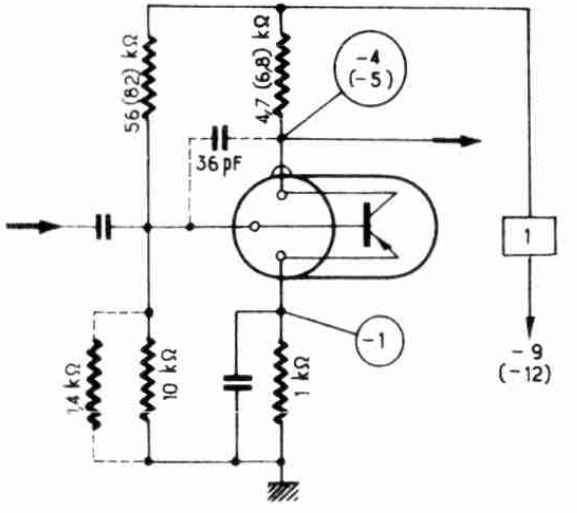
β = 50
Fb = 9 dB



2 N 331

BF

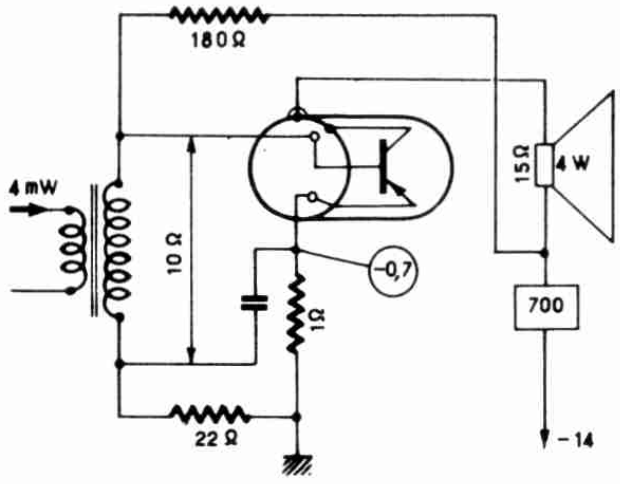
β = 50
Fb = 9 dB



2 N 350 A

P

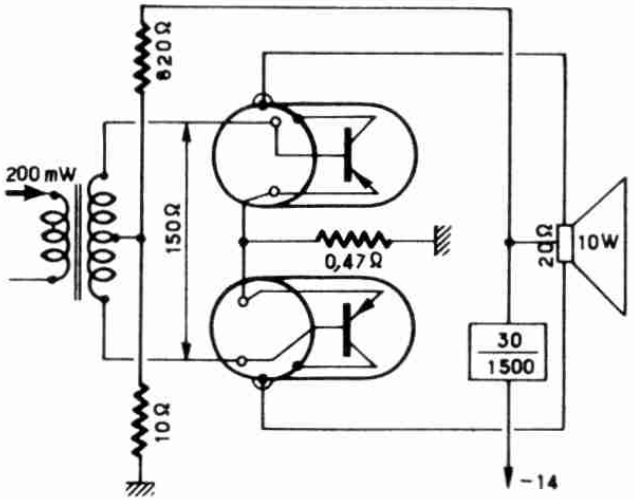
β = 30
GP = 31 dB



2 N 350 A

P

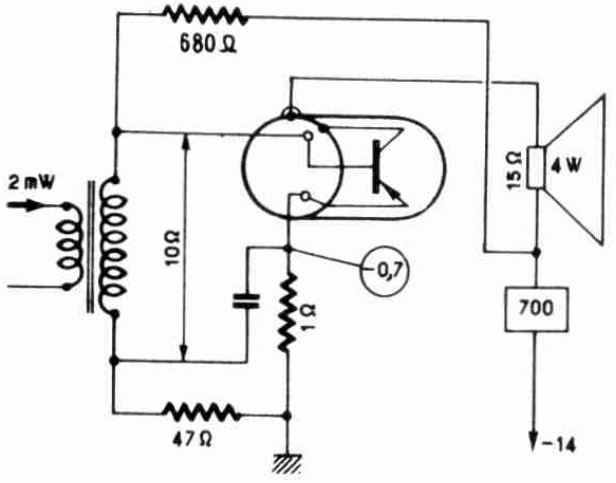
β = 30
GP = 17 dB



2 N 351, A

P

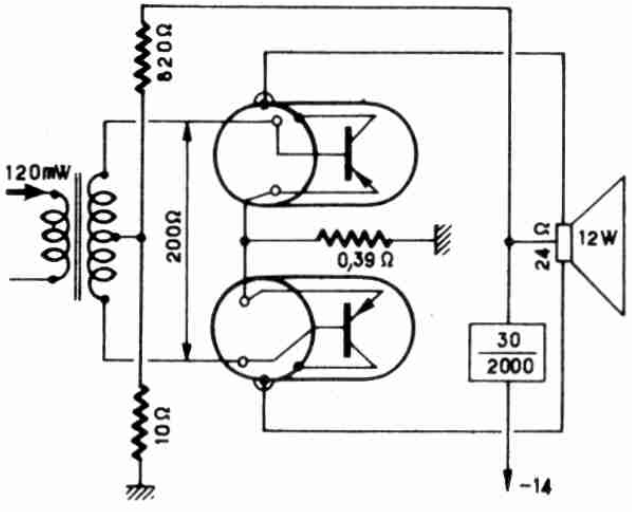
β = 65
GP = 33,5 dB



2 N 351A

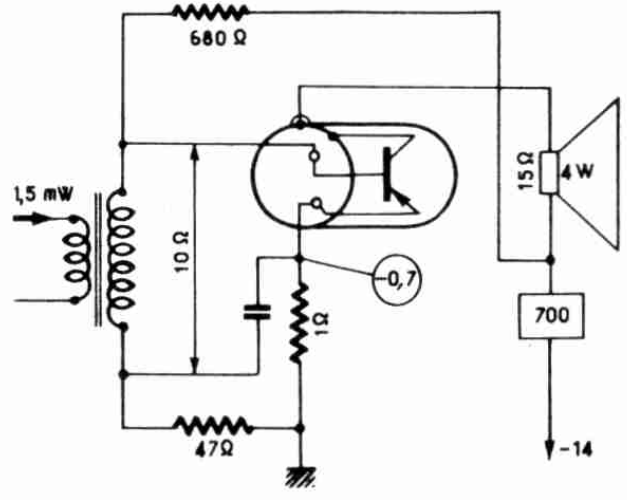
P

β = 45
GP = 20 dB



2 N 376

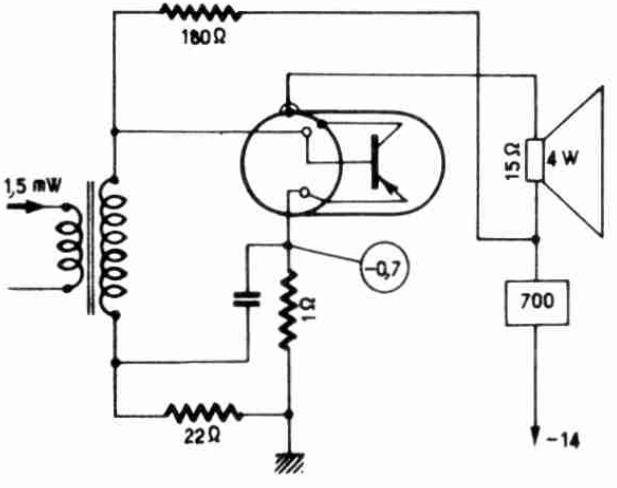
β = 78
GP = 35 dB



2 N 376 A

P

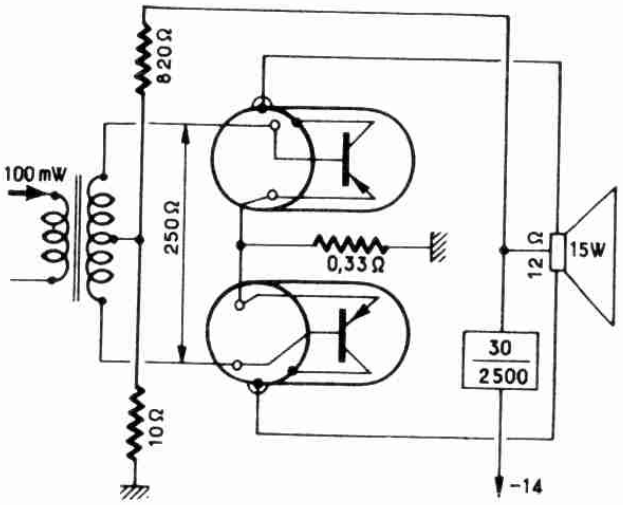
β = 60
GP = 35 dB



2N376A

P

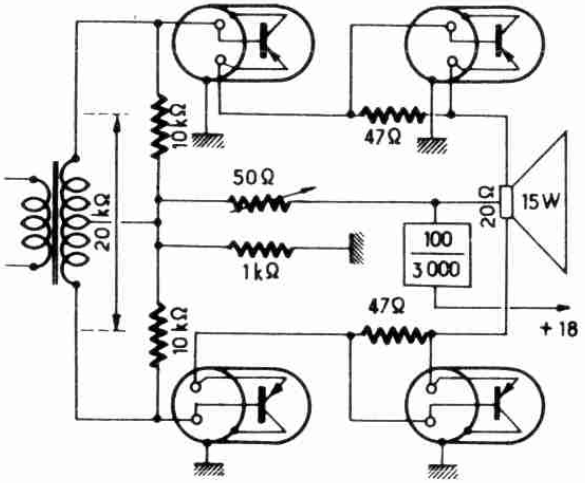
β = 60
GP = 22 dB



2N376A

P

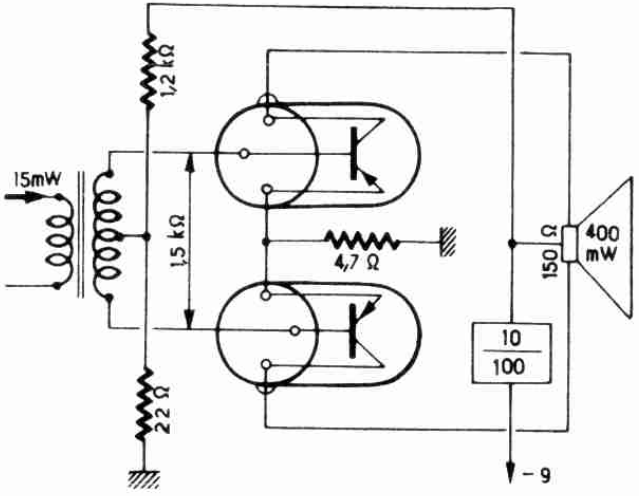
β = 65
GP tot = 26dB



2N381

BF

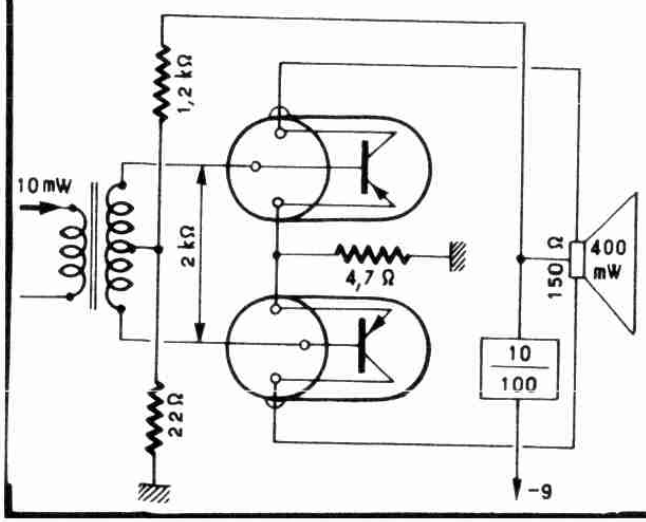
β = 24... 45
GP > 15 dB



2N382

BF

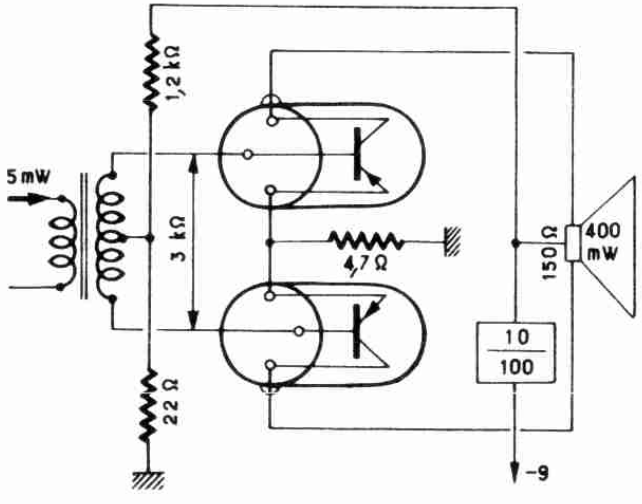
β = 40... 76
GP > 17 dB



2N383

BF

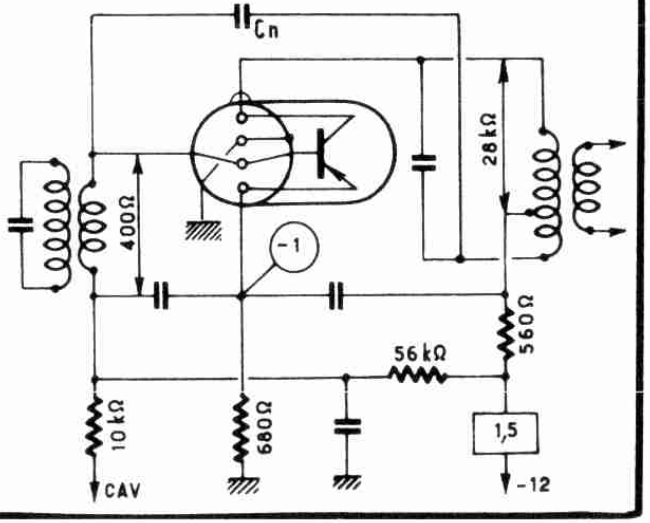
β = 55... 110
GP > 20 dB



2N384

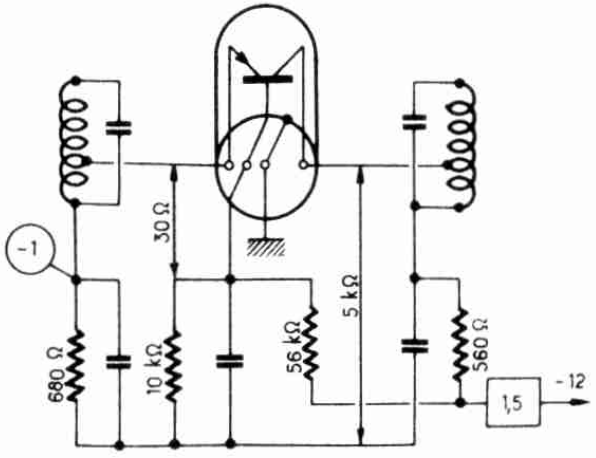
10 MHz

β = 60
GP = 34



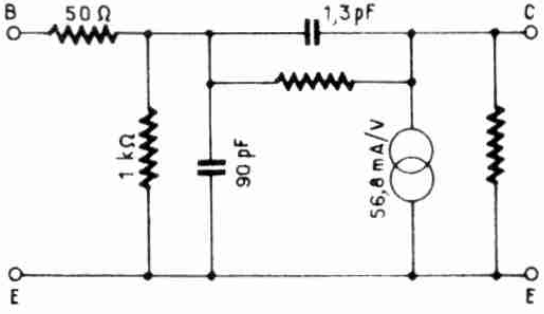
2N 384
VHF_50 MHz

α = 0,984
GP = 15 dB



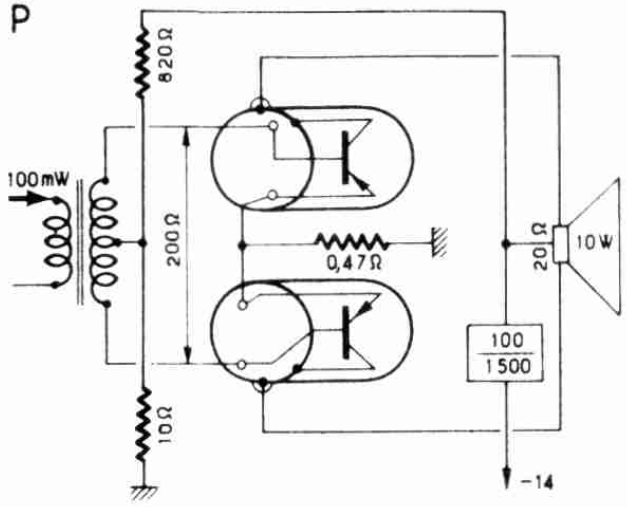
2N 384
VHF

V_C = -12 V
I_C = 1,5 mA



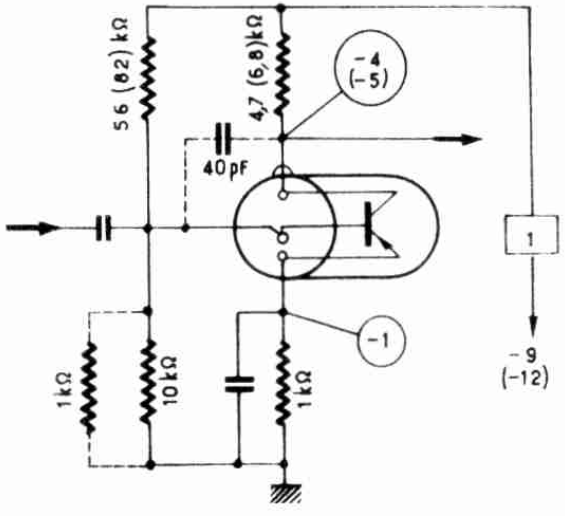
2N 399
2N 401
P

β = 40
GP = 20 dB



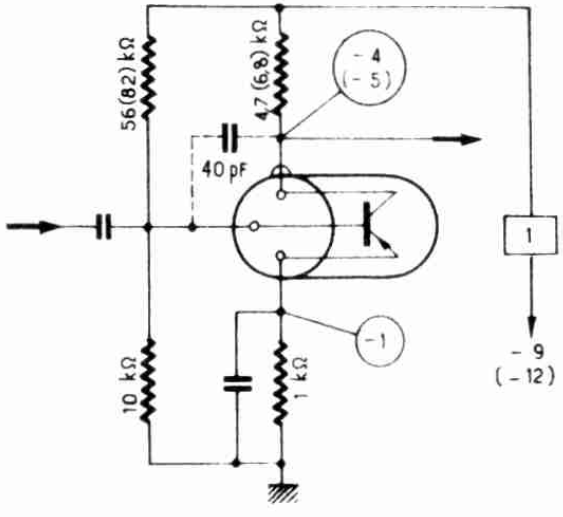
2N 405
BF

β = 35



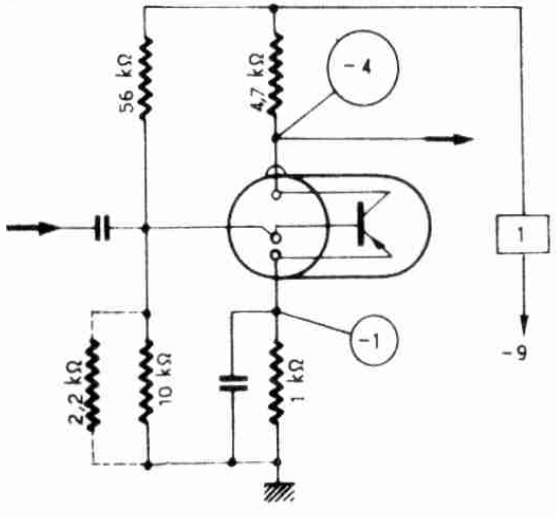
2N 406
BF

β = 35



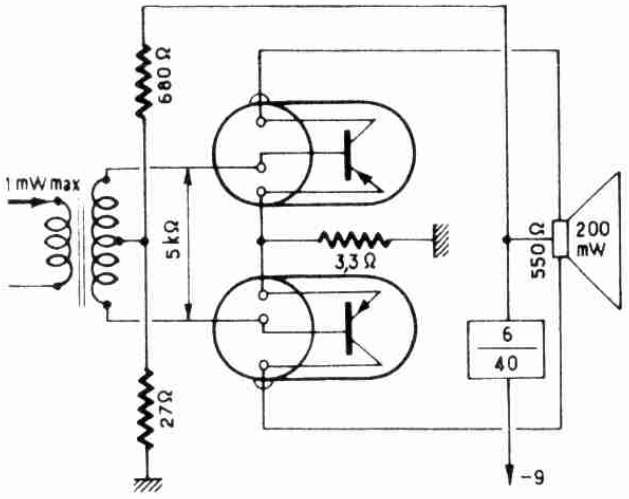
2N 407
BF

β = 65



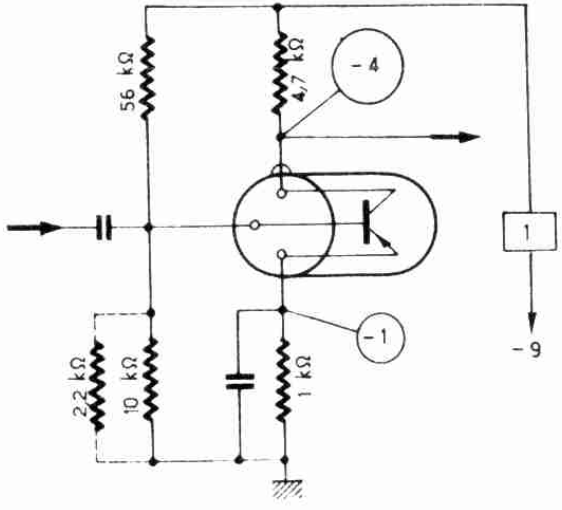
2 N 407
BF

β = 65
GP = 30 dB max



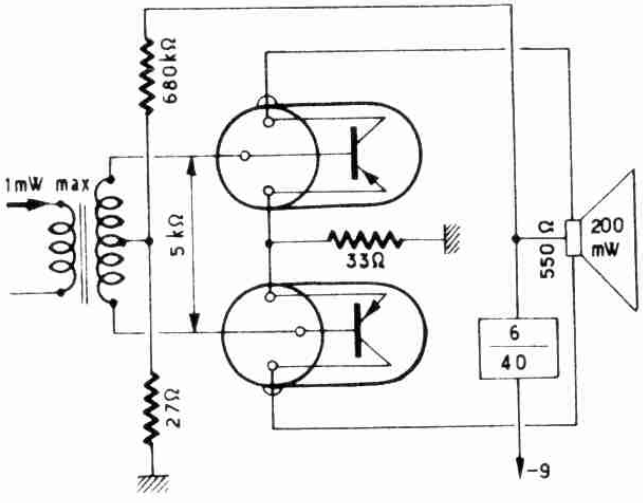
2 N 408
BF

β = 65



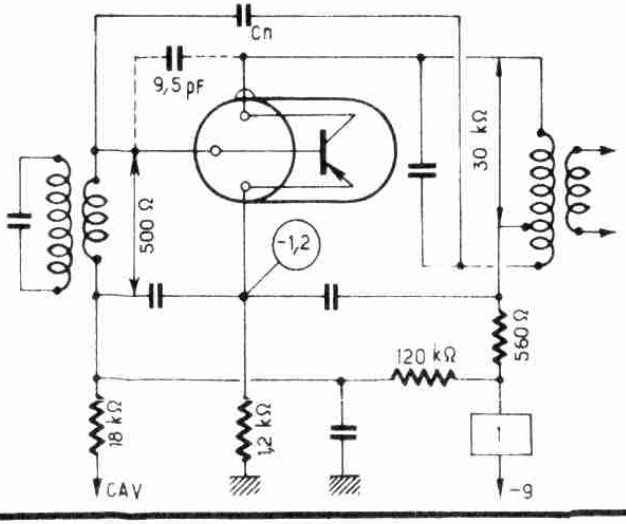
2 N 408
BF

β = 65
GP = 30 dB max



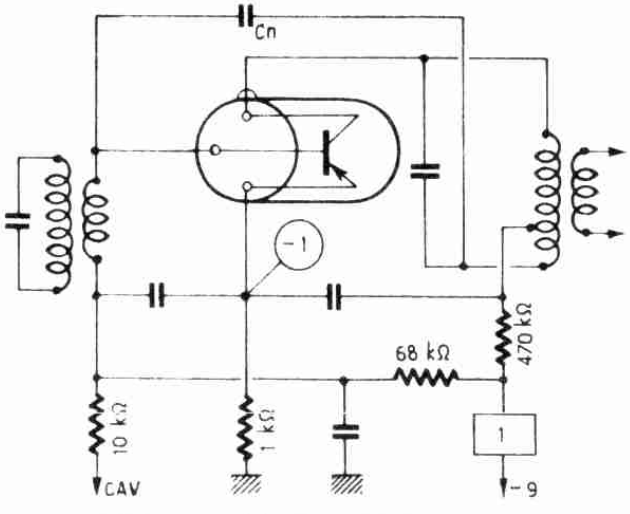
2 N 410
MF_470 kHz

β = 48
GP = 31 dB



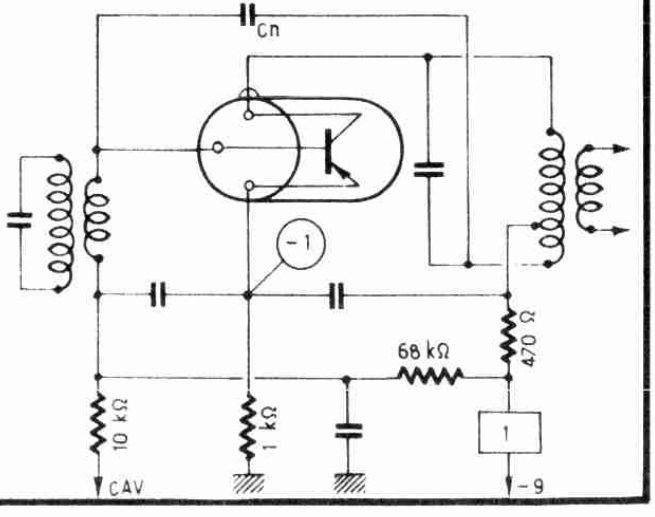
2 N 413 A
MF_470 kHz

β = 30
GP = 30 dB



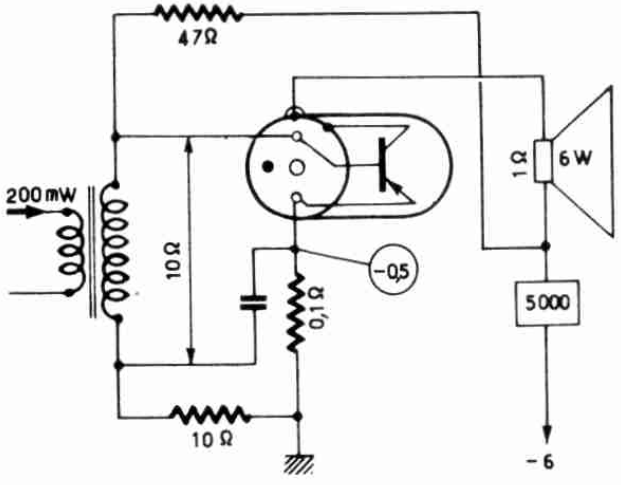
2 N 414 A
MF_470 kHz

β = 60
GP = 32 dB



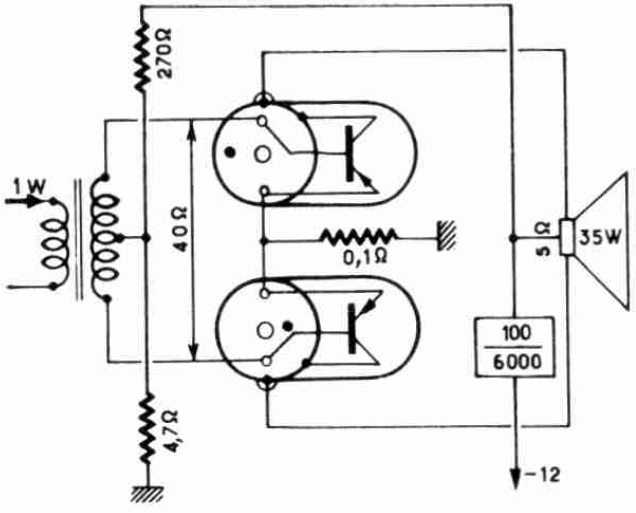
2 N 441
P

β = 30
GP = 16 dB



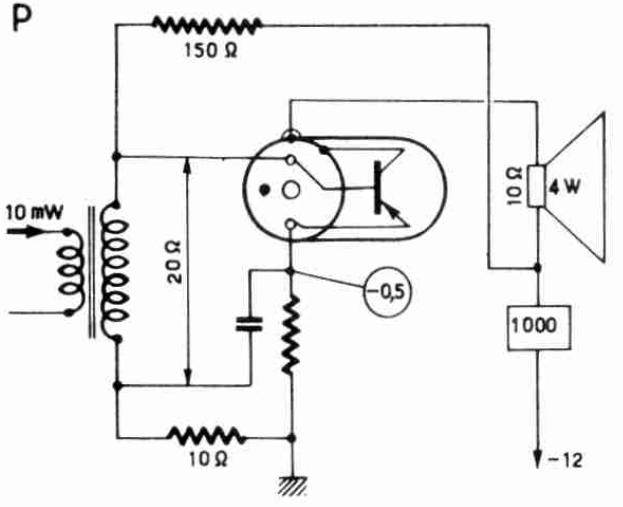
2 N 441
P

β = 30
GP = 16 dB



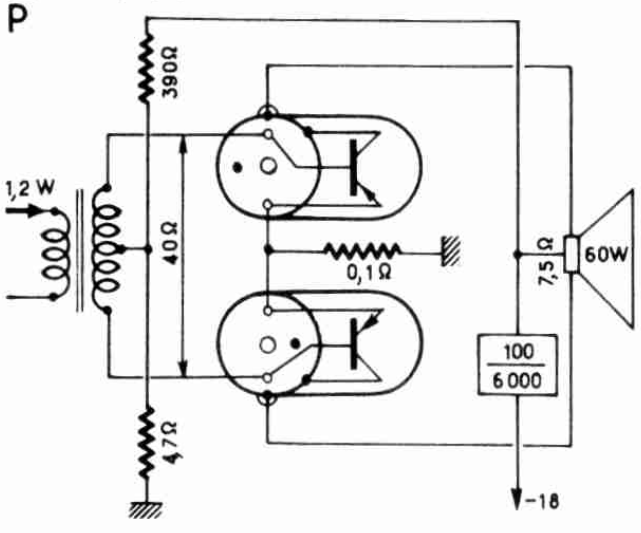
2 N 442
2 N 443
P

β = 35
GP = 27 dB



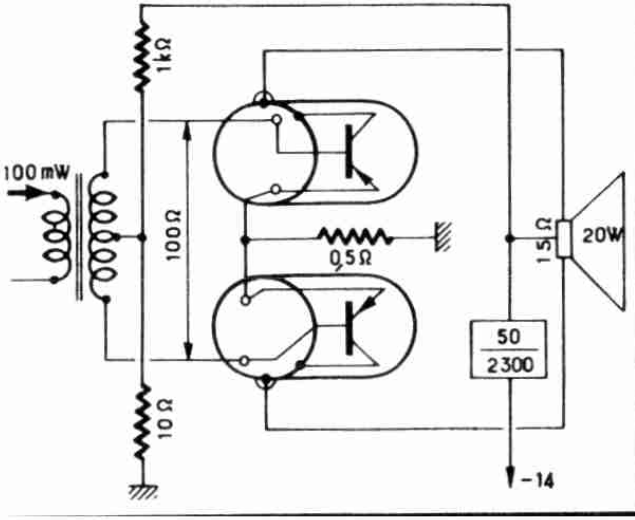
2 N 442
2 N 443
P

β = 30
GP = 17 dB



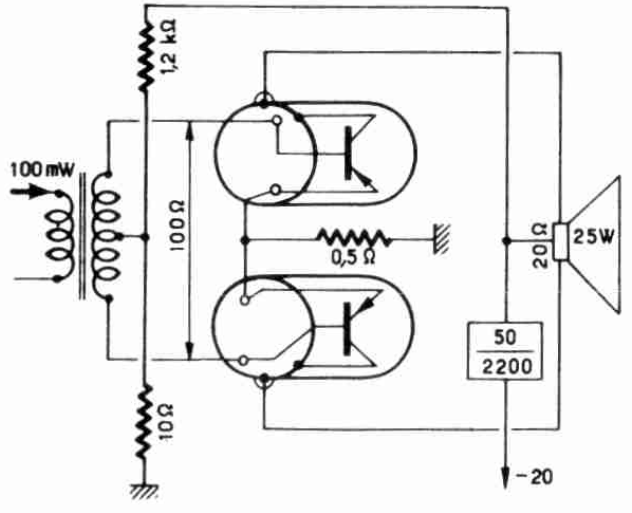
2 N 456
P

β = 52
GP = 23 dB



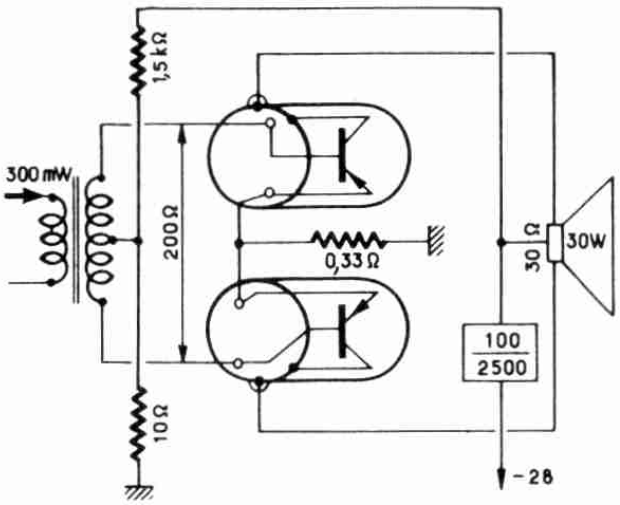
2 N 457
P

β = 52
GP = 24 dB



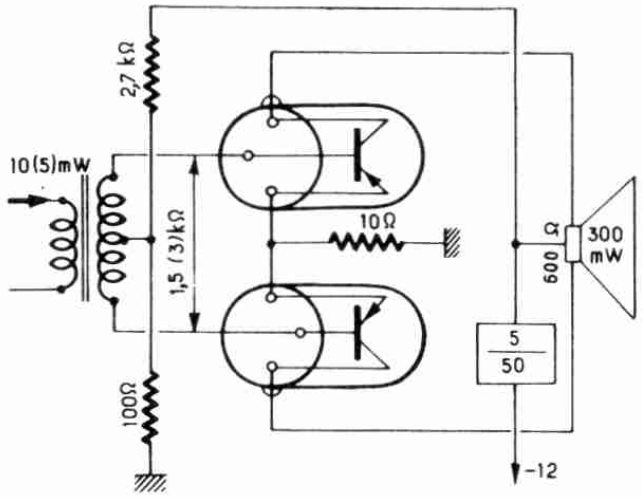
2N458
P

β = 40...200
GP = 20 dB



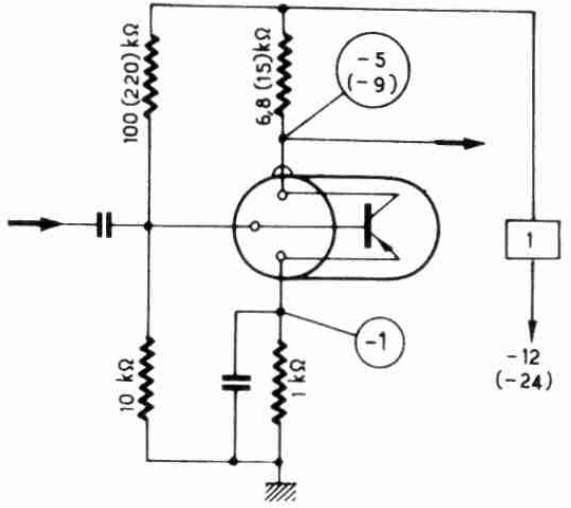
2N460
2N461

β = 24 (49)
GP = 15 (18) dB



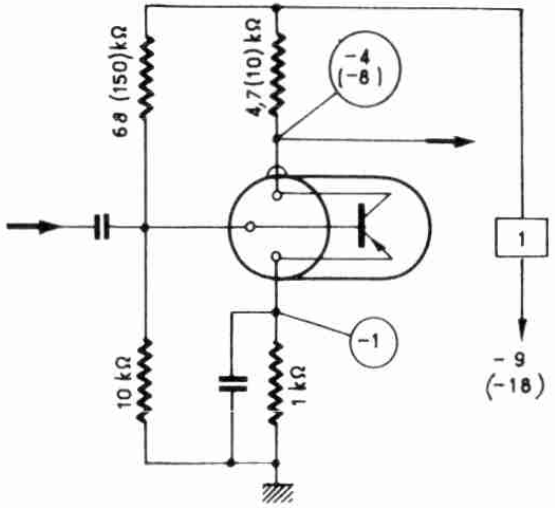
2N464
BF

β = 22
Fb = 12 dB



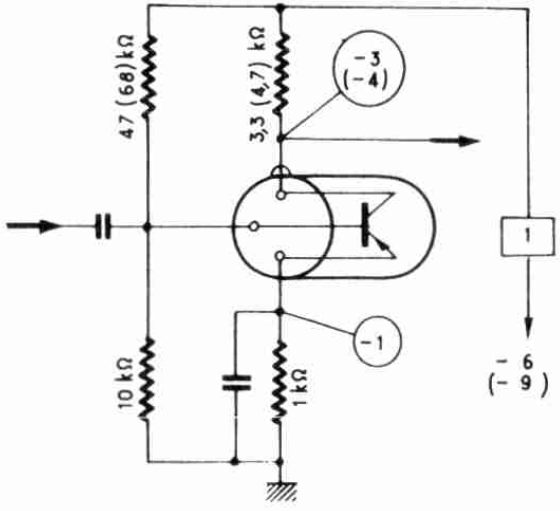
2N465
BF

β = 45
Fb = 12 dB



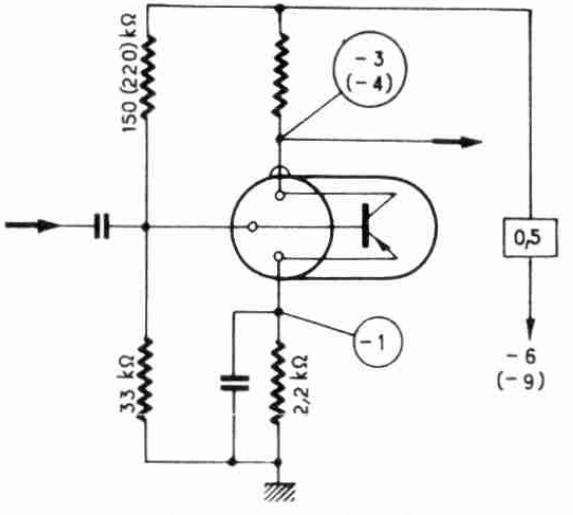
2N466
BF

β = 90
Fb = 12 dB



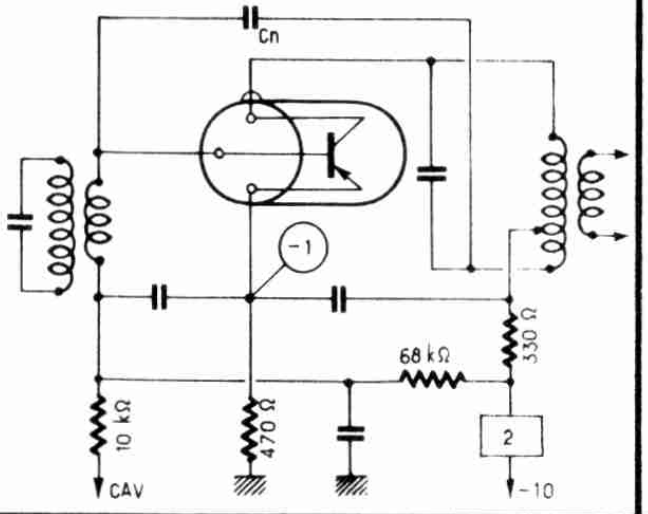
2N467
BF

β = 180
Fb = 12 dB



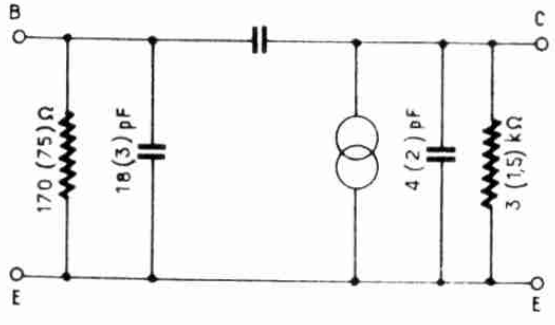
2N499
VHF

β = 8,5 / 20 MHz
GP = 10 dB/100 MHz



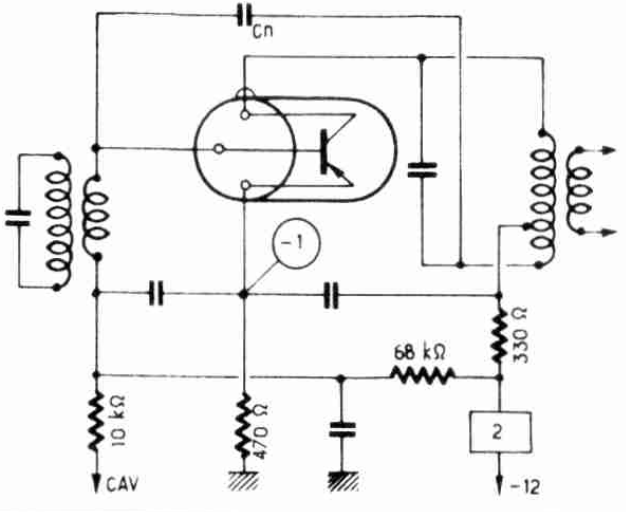
2N499
30 (100) MHz

Vc = 10 V
Ic = 3 mA
GP = 20 (10) dB



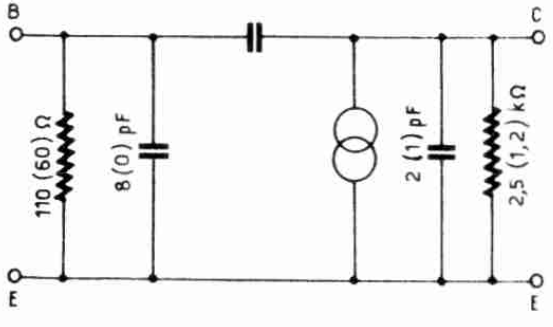
2N502,A
VHF

β = 5,5 / 40 MHz
GP = 10 dB / 200 MHz
Fb = 5 dB / 10 MHz



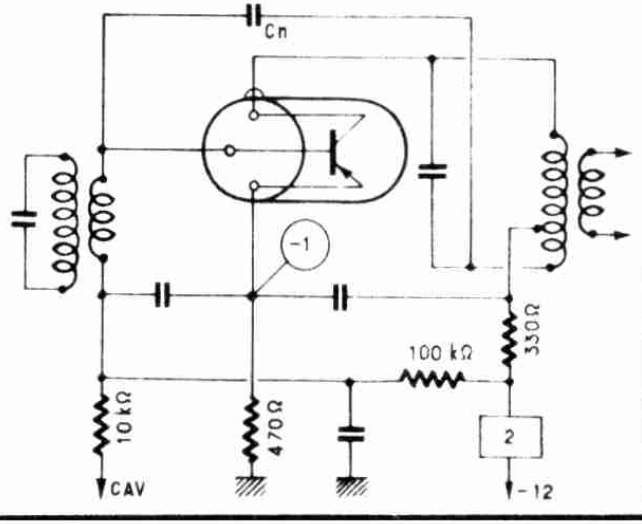
2N502 A
70 (200) MHz

Vc = 12 V
Ic = 3 mA



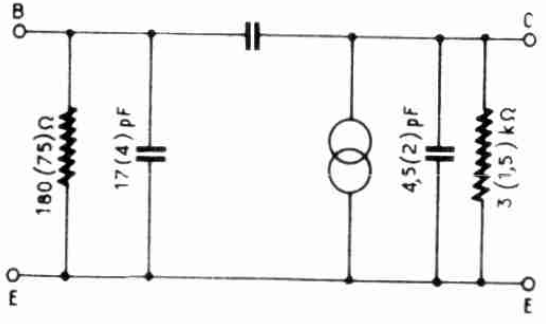
2N503
VHF_100 MHz

β = 4,2 / 40 MHz
GP = 12,5 dB / 100 MHz



2N503
30 (100) MHz

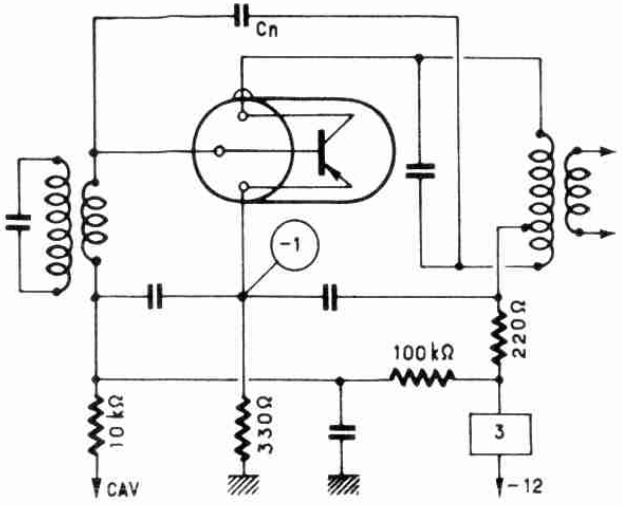
Vc = 10 V
Ic = 2 mA
GP = 23 (12,5) dB



2N 504

MF 470 kHz

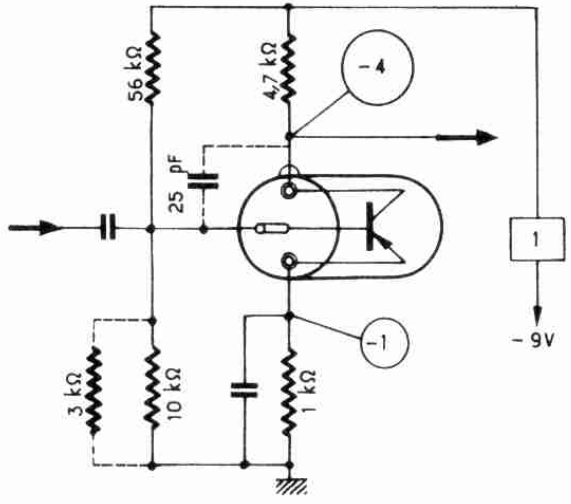
β > 16
GP = 43 dB



2N 508

BF

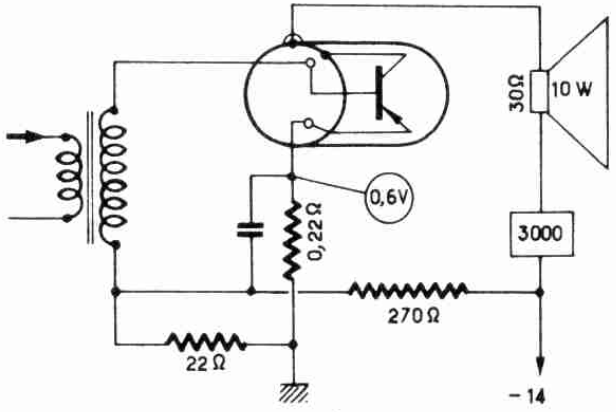
β = 112
Fb = 6 dB



2N 511

P

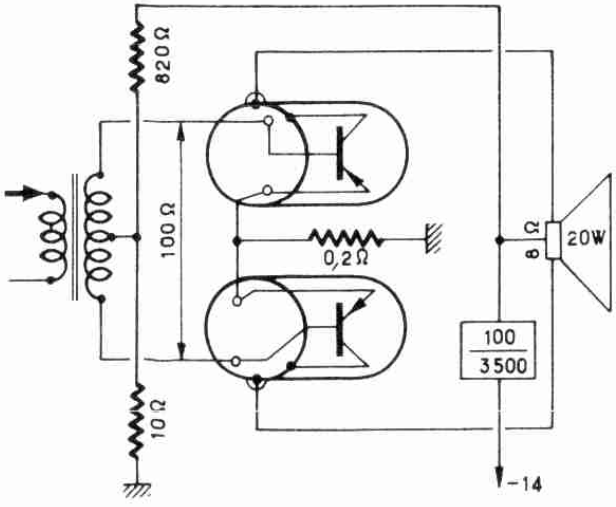
β > 10



2N 511

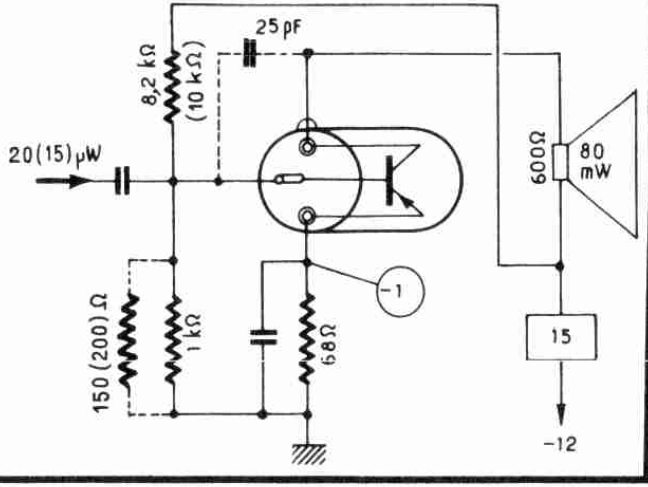
P

β > 10
GP > 10 dB



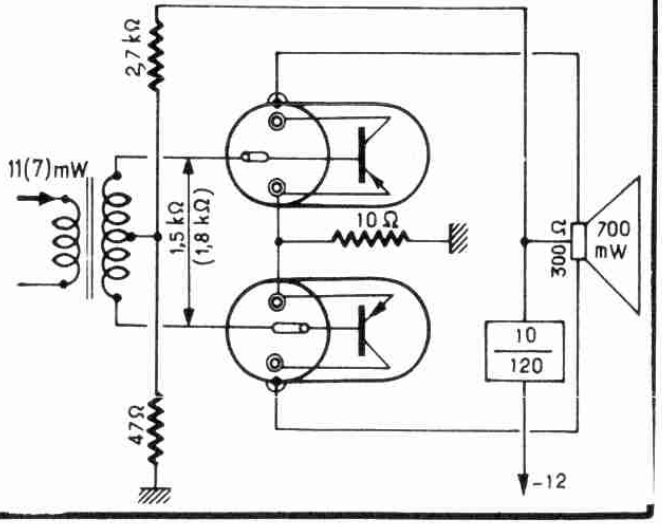
2N524, (25)

BF



2N524, (25)

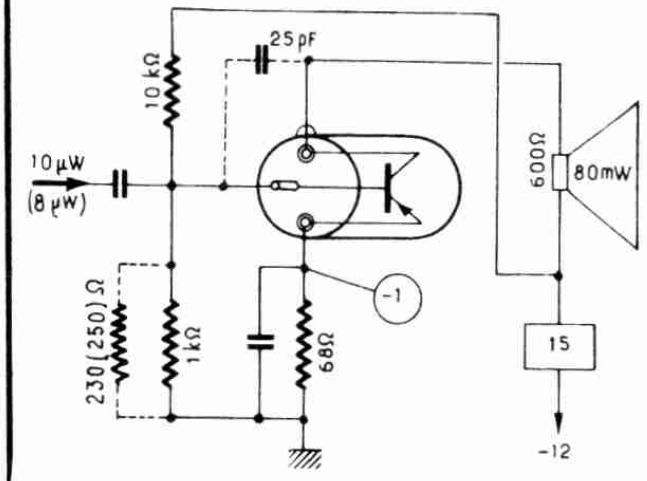
BF



2N526,(27)

BF

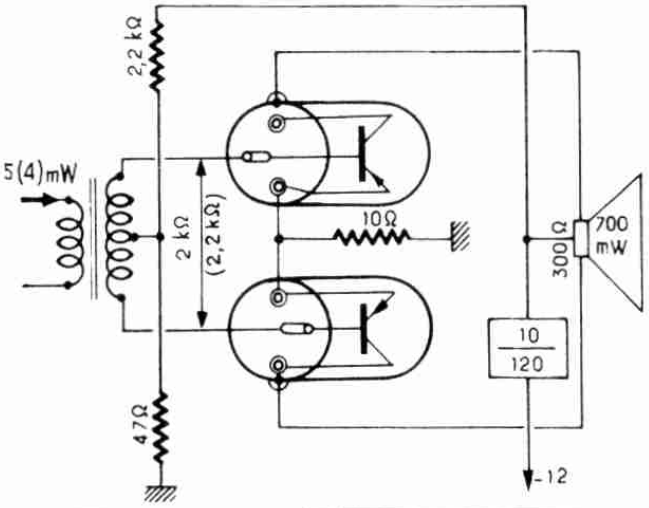
β = 44...88 (60...120)



2N526,(27)

BF

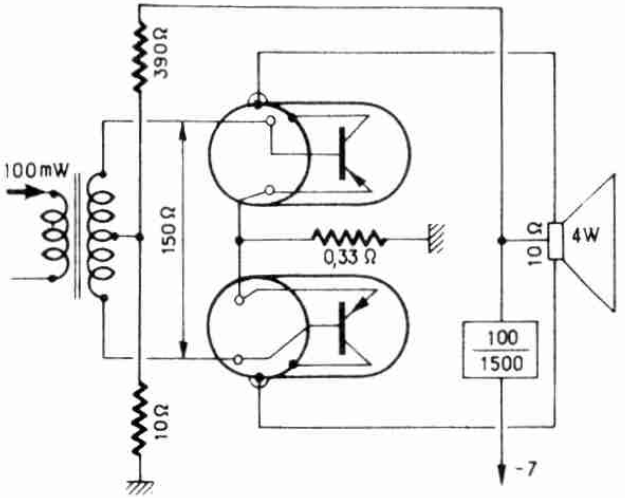
β = 44...88 (60...120)
GP = 21 (22 dB)



2N554

P

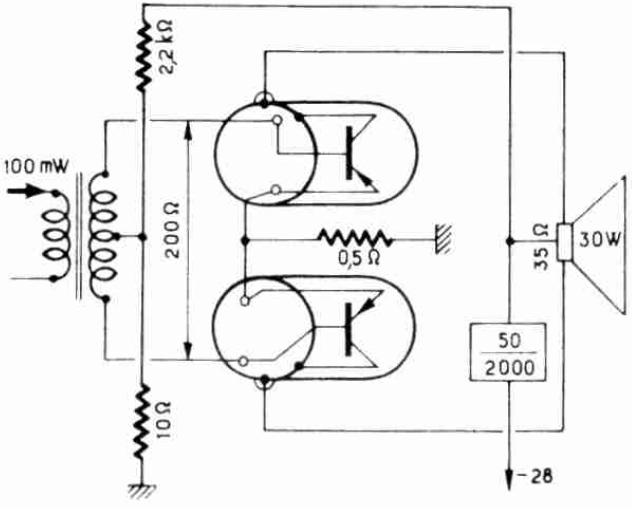
β = 30
GP = 16 dB



2N561

P

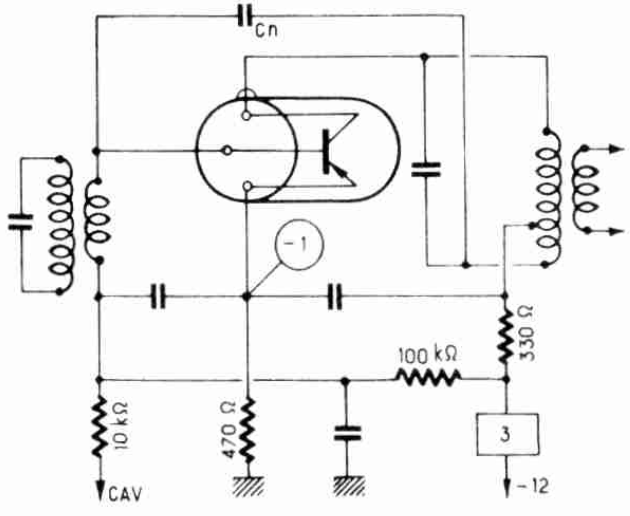
β = 75
GP = 25 dB



2N588

VHF 30 MHz

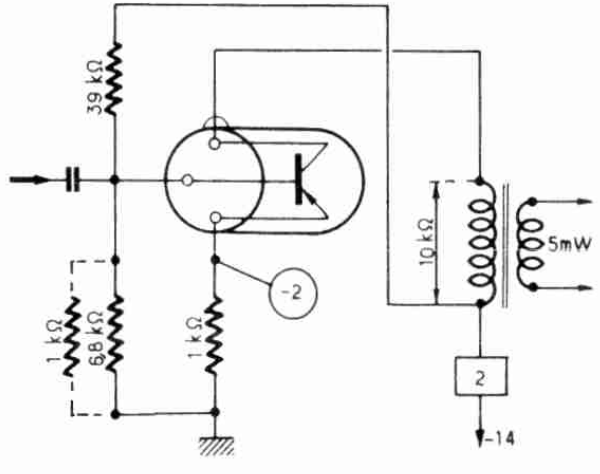
GP= 18 dB
Fb = 5 dB/10 MHz



2N591

BF

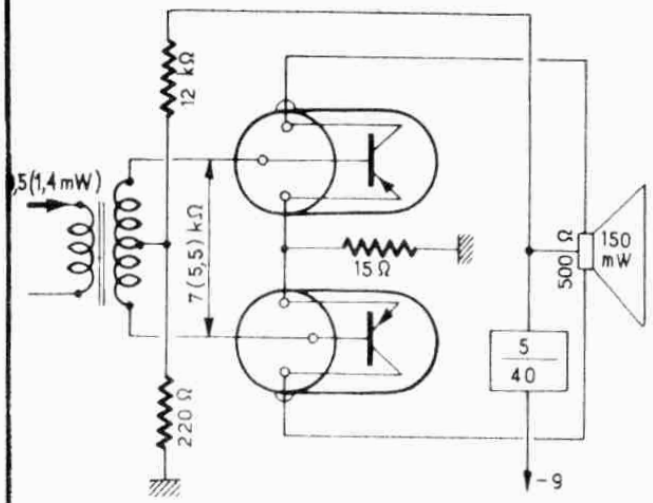
β = 70
GP = 40 dB



2N 632, (33)

BF

β = 100 (60)
GP = 25 dB (21 dB)

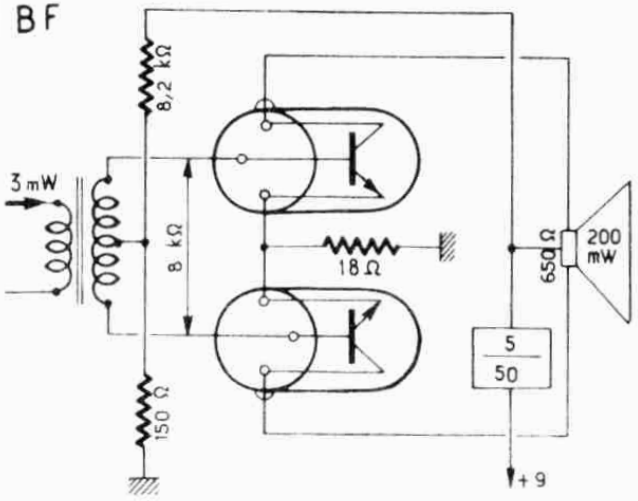


2N 647
2N 649

n-p-n

BF

β = 70
GP = 17 dB

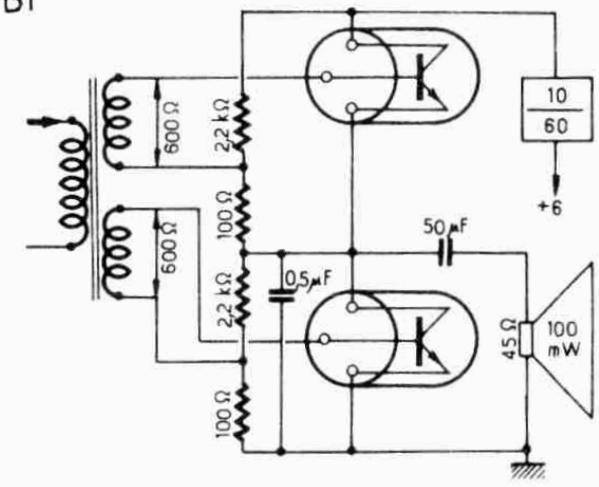


2N 647
2N 649

n-p-n

BF

β = 70

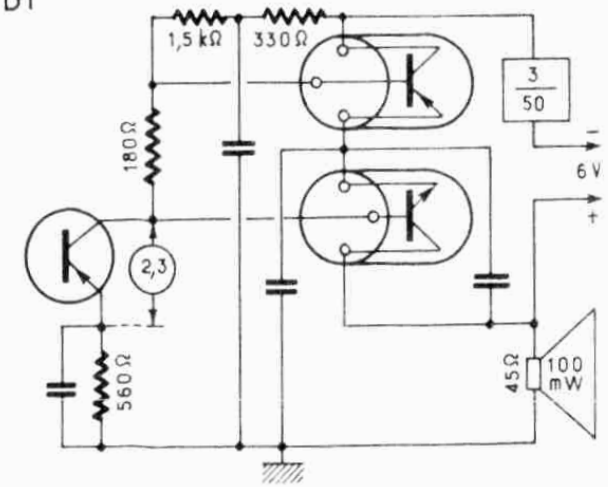


2N 647
2N 217

n-p-n
p-n-p

BF

β = 70

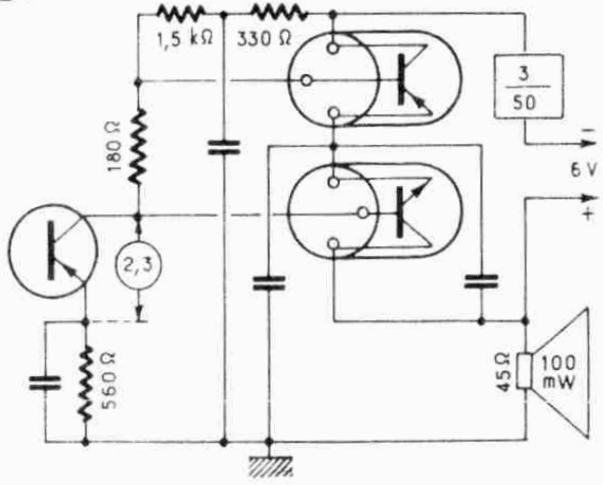


2N 649
2N 408

n-p-n
p-n-p

BF

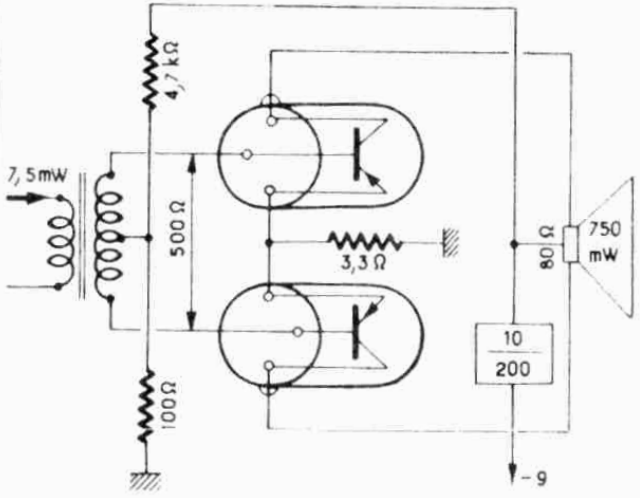
β = 65



2N 650

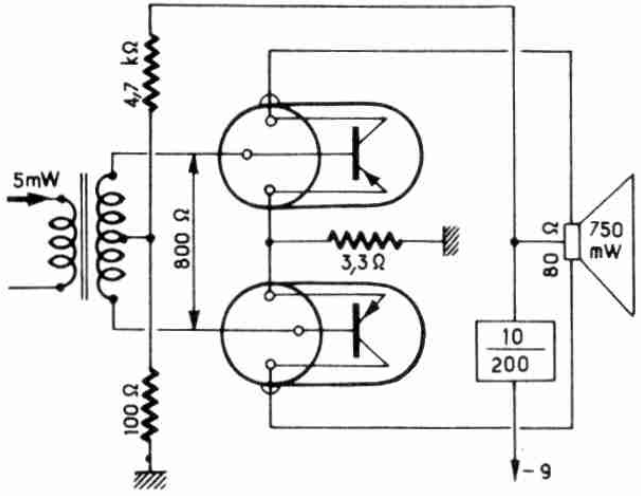
BF

β = 45
GP = 20 dB



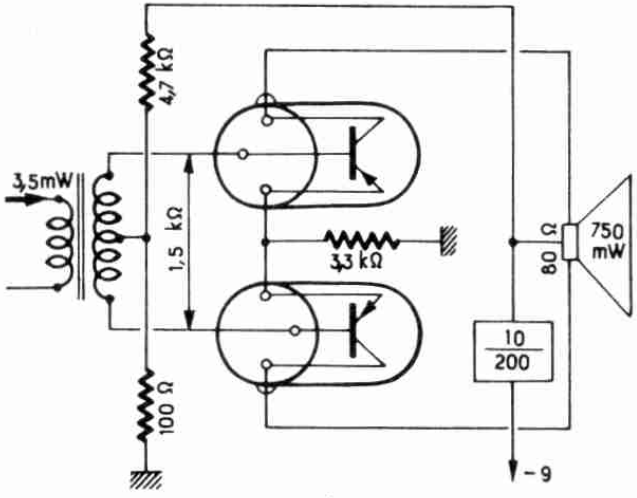
2 N 651
BF

β = 70
GP = 22 dB



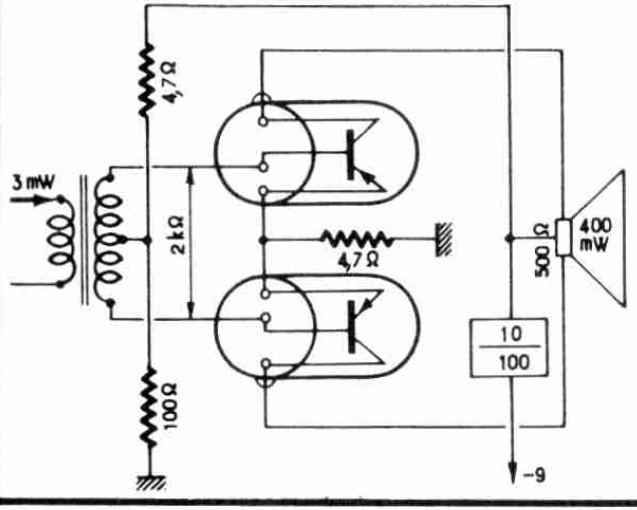
2 N 652
BF

β = 120
GP = 24 dB



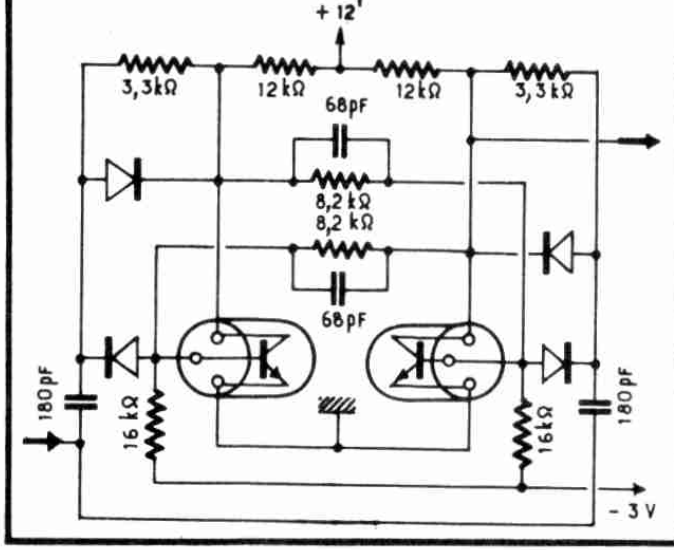
2 N 680
BF

β = 35
GP = 21 dB



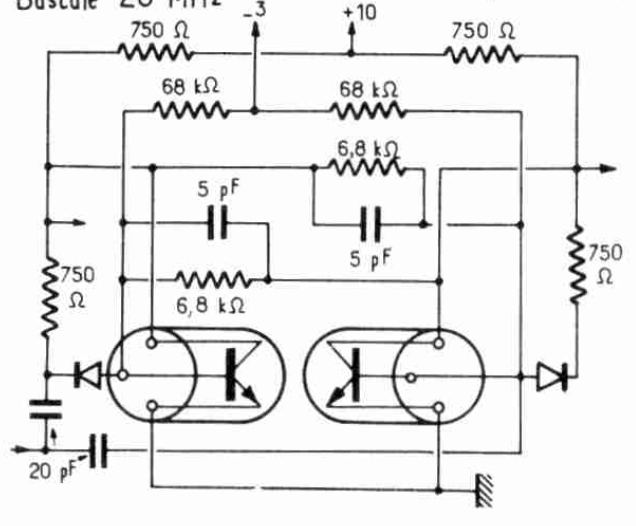
2N702 (753) Si
Bascule 5 MHz n-p-n

β = 20...60



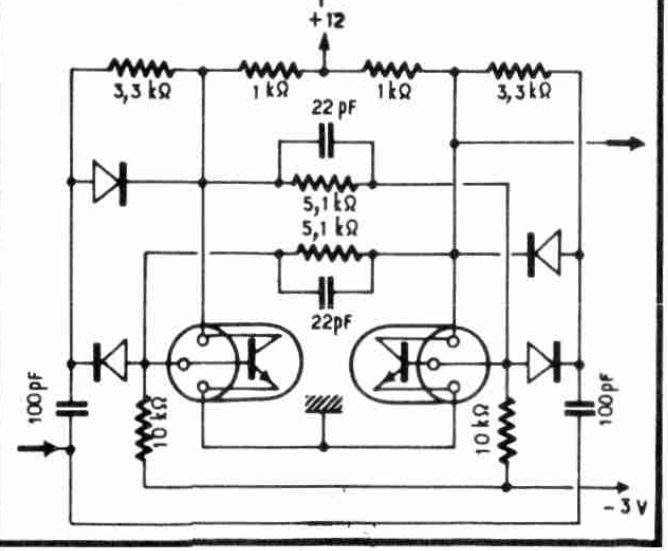
2N 706 n-p-n Si
Planar
Bascule 20 MHz

β > 20
(>2 à 100 MHz)



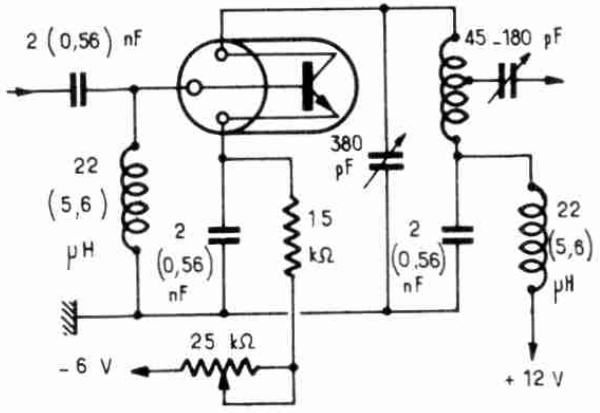
2N 706A Si
Bascule 10MHz n-p-n

β = 20...6



2N743 n-p-n Si $\beta = 20...60$

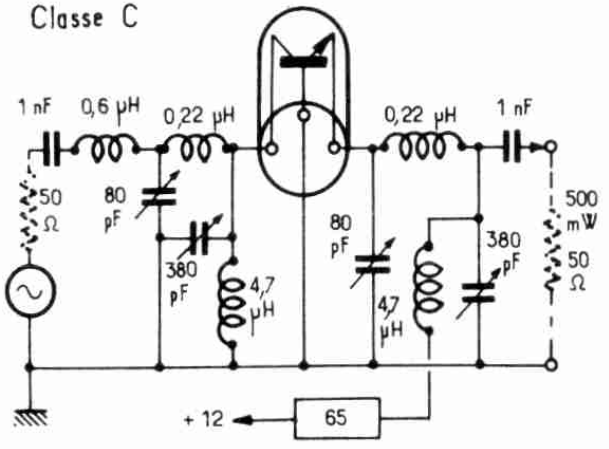
Amplif. 30 (60) MHz



2N743 n-p-n Si $\beta = 20...60$ $G_p = 6$ dB

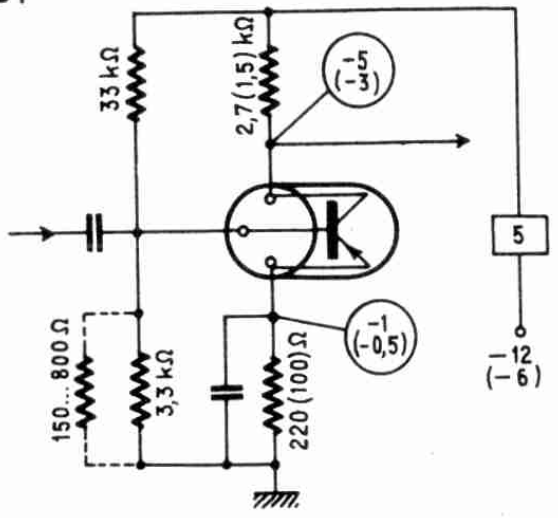
Amplif. 70 MHz

Classe C



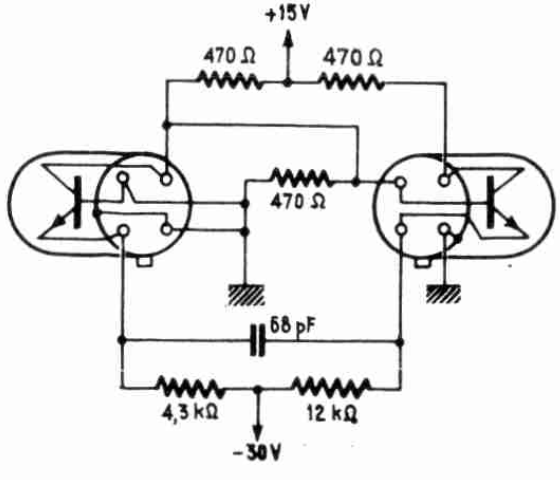
2N 863, (64) $\beta = 20...100$

BF



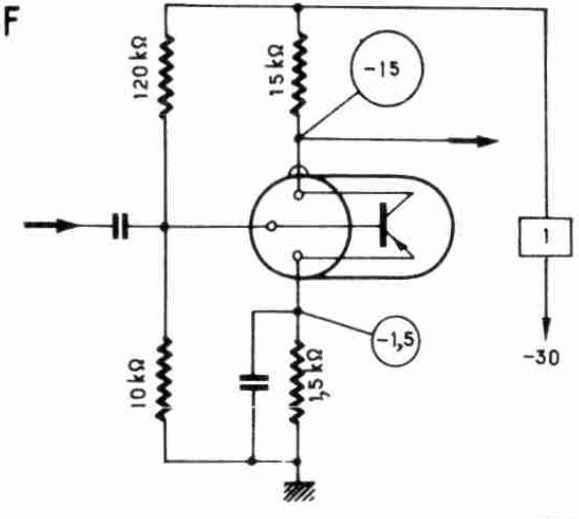
2N918 Si $\beta < 20$

Multiv. 2 MHz n-p-n



2N923 (2N924) Si $\beta = 21$ (47)

BF

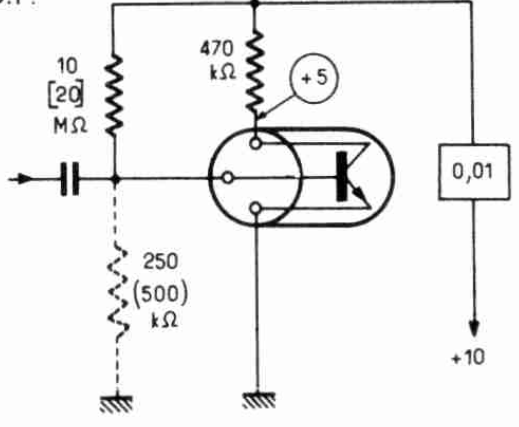


2N 929 [2N 930] n-p-n Si Planar

$\beta = 40...120$ (10 µA) 60...350 (0,5...10 mA)

[100...300 (10 µA)] [150...600 (0,5...10 mA)]

B.F.

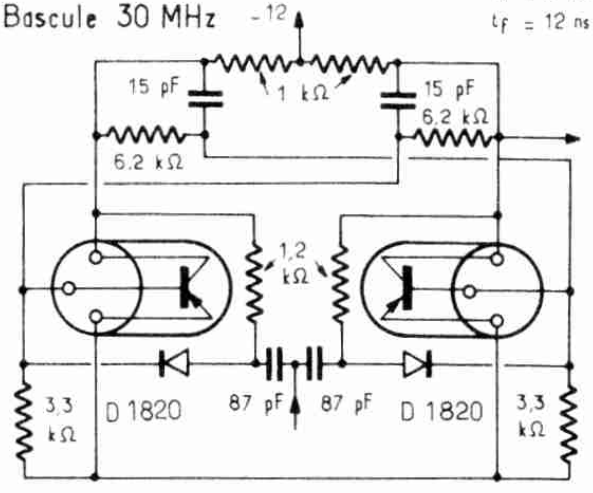


2N 964

Mésa

Bascule 30 MHz

$\beta = 70$
$t_r = 6$ ns
$t_f = 12$ ns

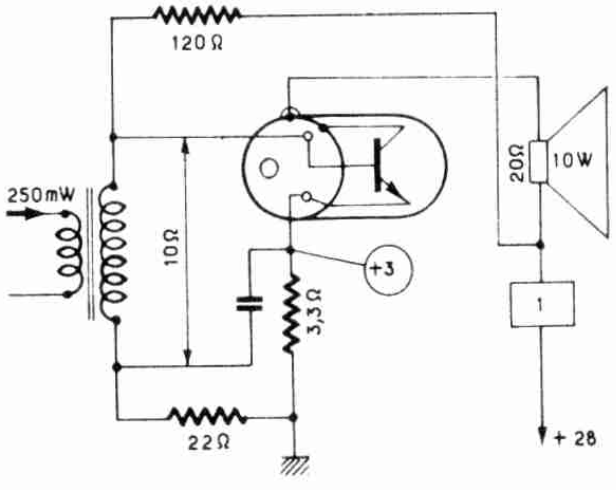


2N 1015 B

n-p-n Si

P

$\beta > 10$
GP = 16dB

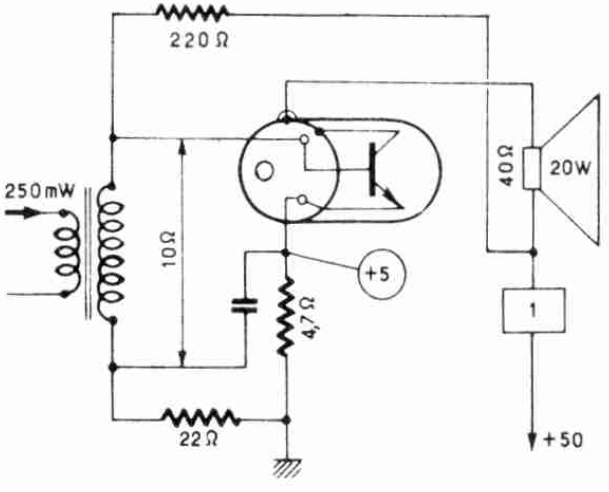


2N 1015 C

n-p-n Si

P

$\beta > 10$
GP = 19dB

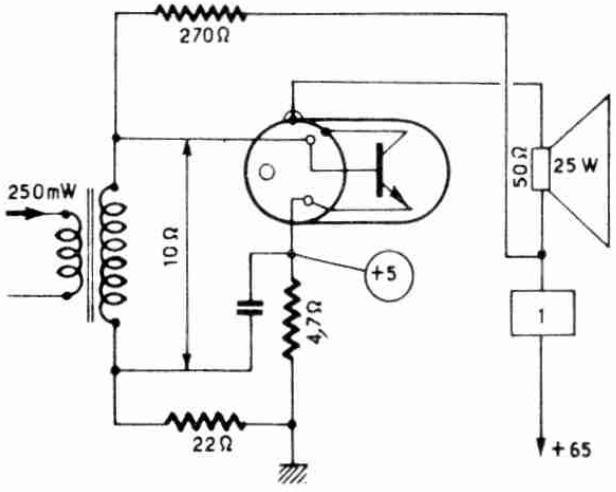


2N 1015 D

n-p-n Si

P

$\beta > 10$
GP = 20dB

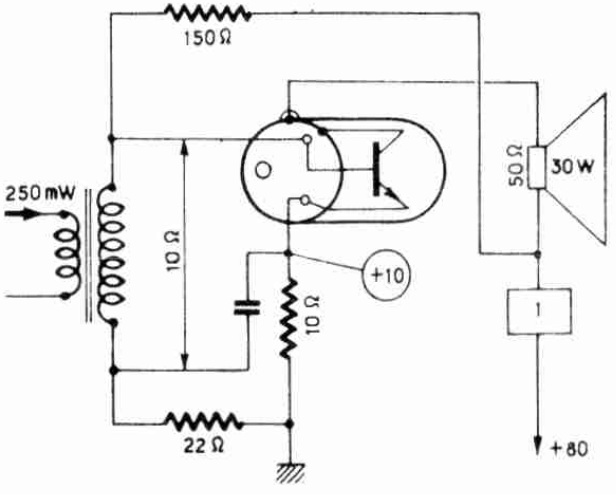


2N 1015 E

n-p-n Si

P

$\beta > 10$
GP = 21dB

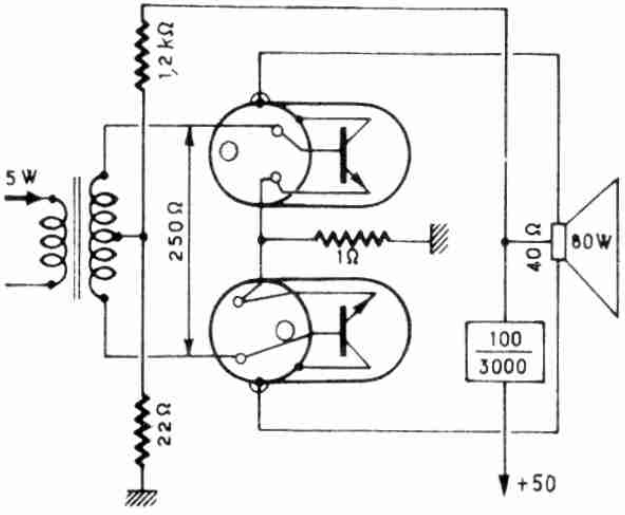


2N 1016 C

n-p-n Si

P

$\beta > 10$
GP = 12dB

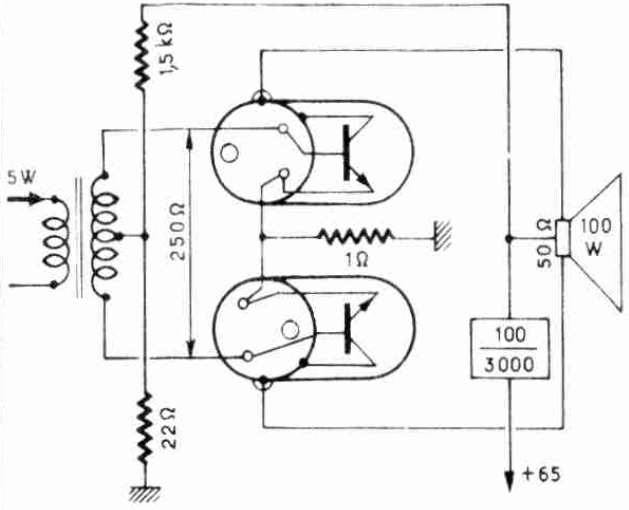


2N1016 D

n-p-n Si

$\beta > 10$

GP = 13dB

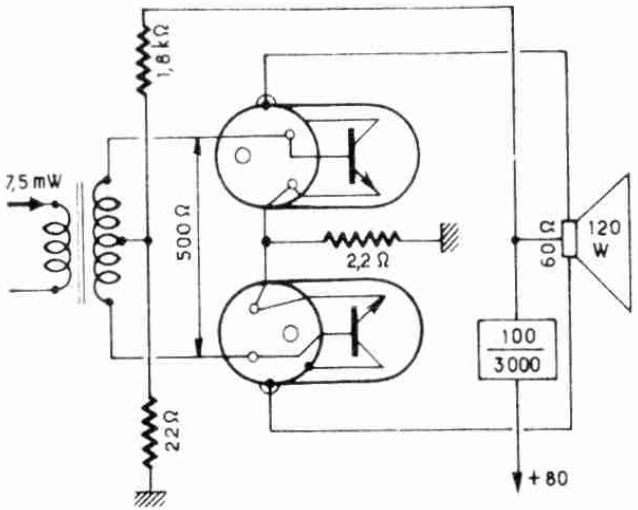


2N1016 E

P n-p-n Si

$\beta > 10$

GP = 12dB

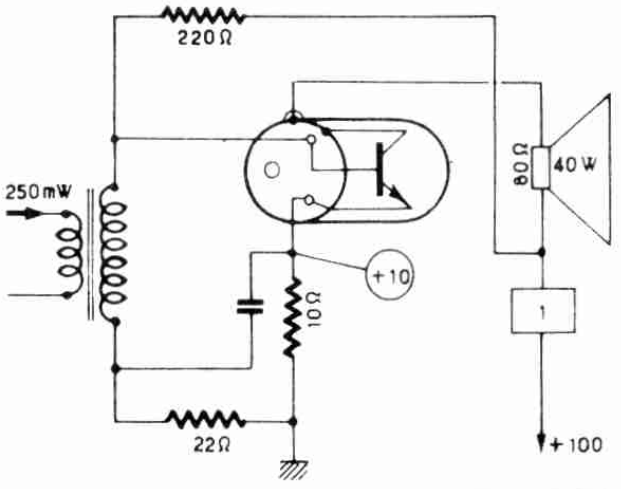


2N1016 F

P n-p-n Si

$\beta > 10$

GP = 22dB

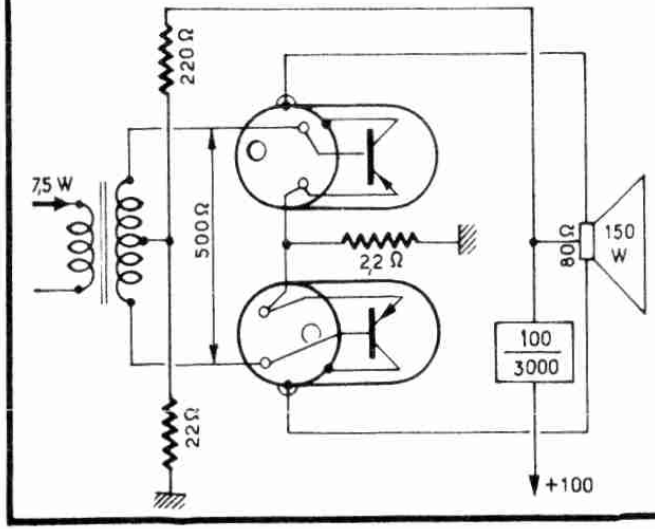


2N1016 F

P n-p-n Si

$\beta > 10$

GP = 13dB

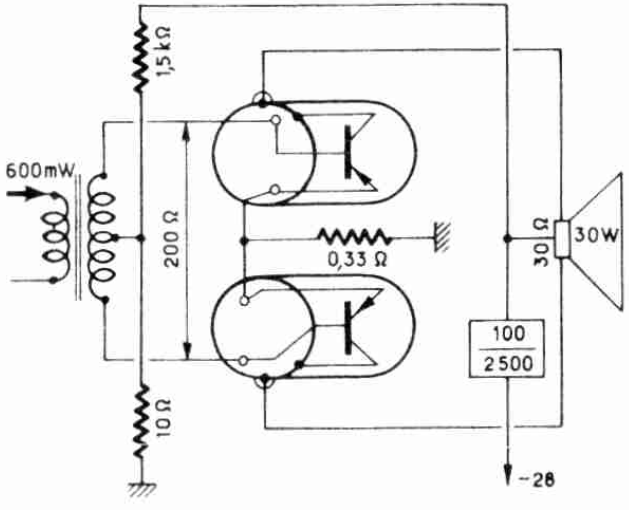


2N1021

P

$\beta = 23$

GP = 17dB

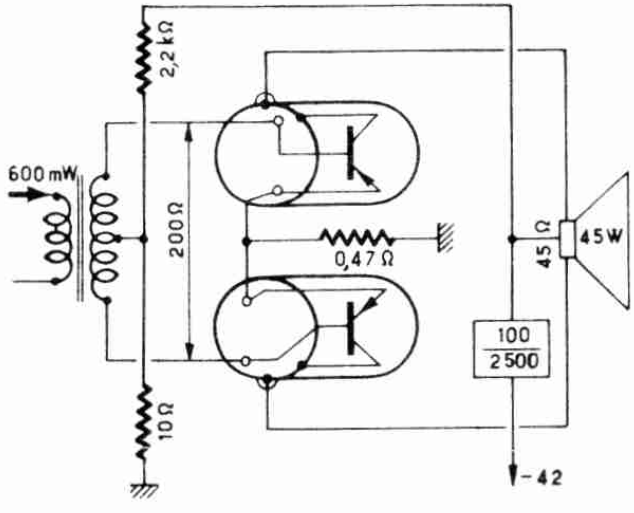


2N 1022

P

$\beta = 23$

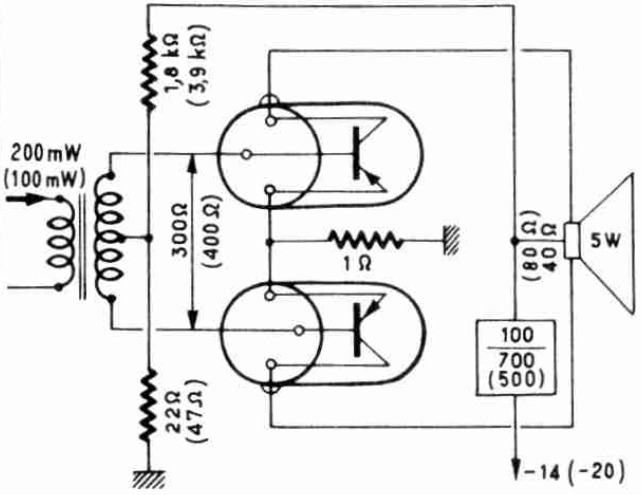
GP = 19 dB



2 N 1038,(39)

P

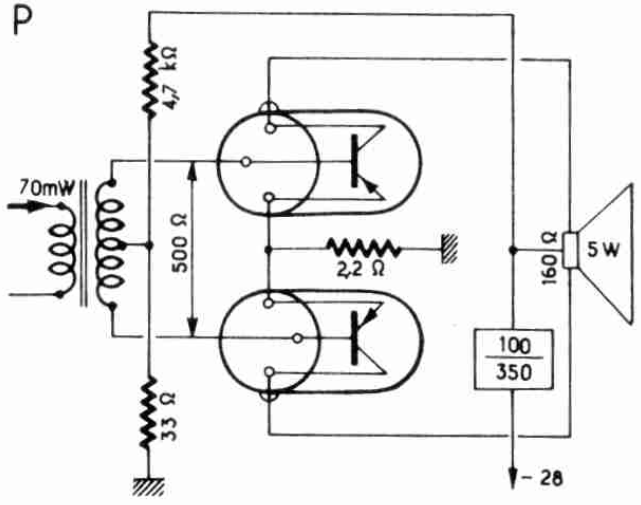
β = 20...60
GP = 15dB (17dB)



2 N 1040
2 N 1041

P

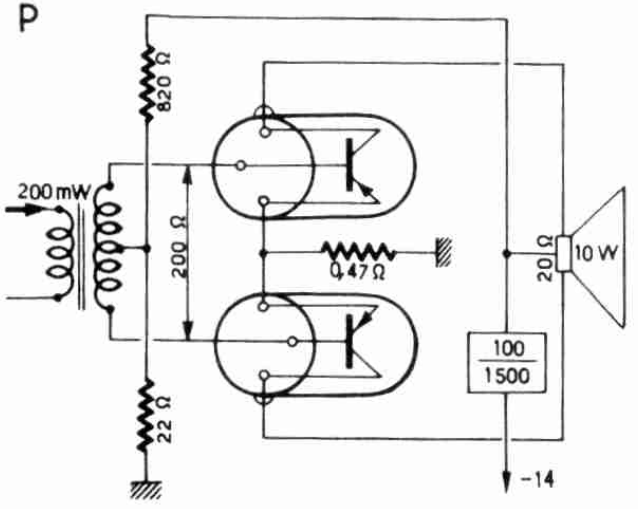
β = 20...60
GP = 19 dB



2 N 1042
2 N 1043

P

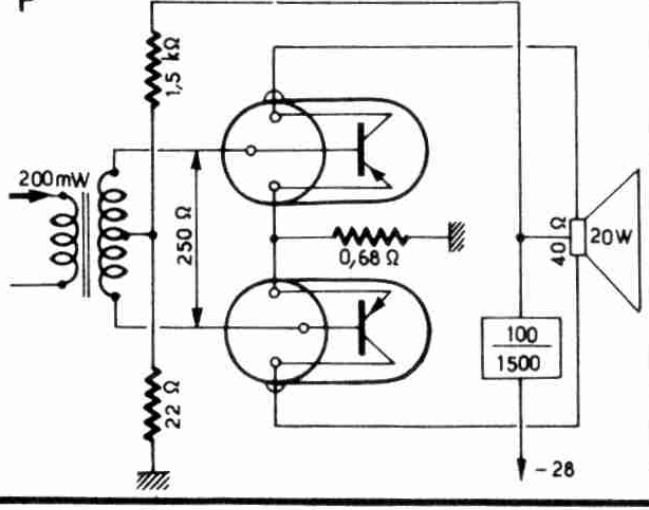
β = 20...60
GP = 17 dB



2 N 1044
2 N 1045

P

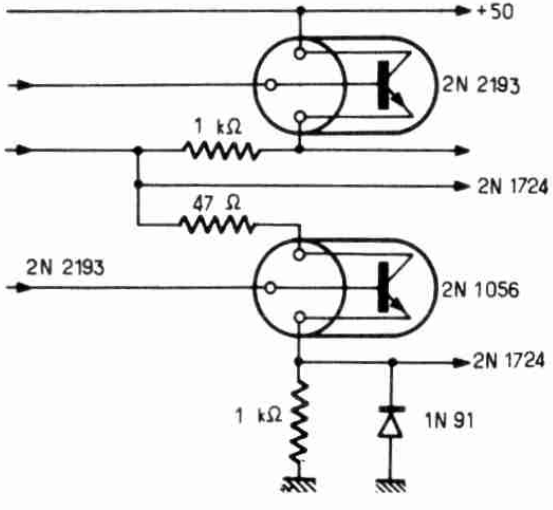
β = 20...60
GP= 20 dB



2N 1056

B.F.

β = 25
F_b < 20 dB

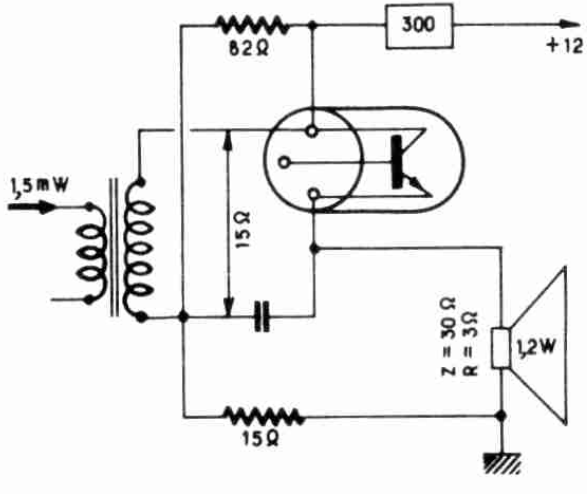


2N1067

P

n-p-n
Si

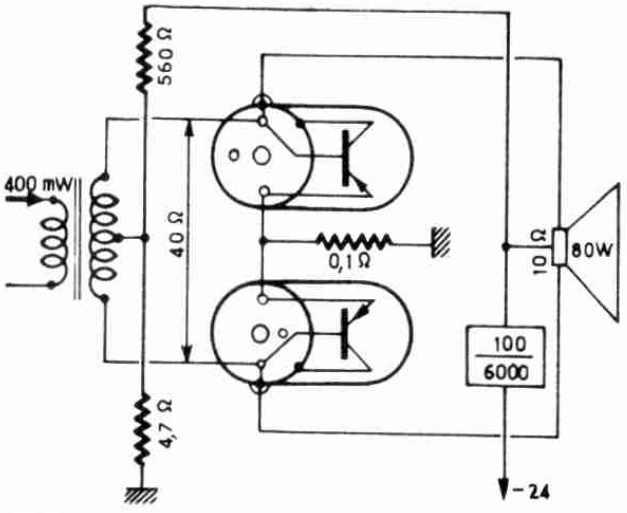
β = 15...75
GP = 29 dB



2N 1099

P

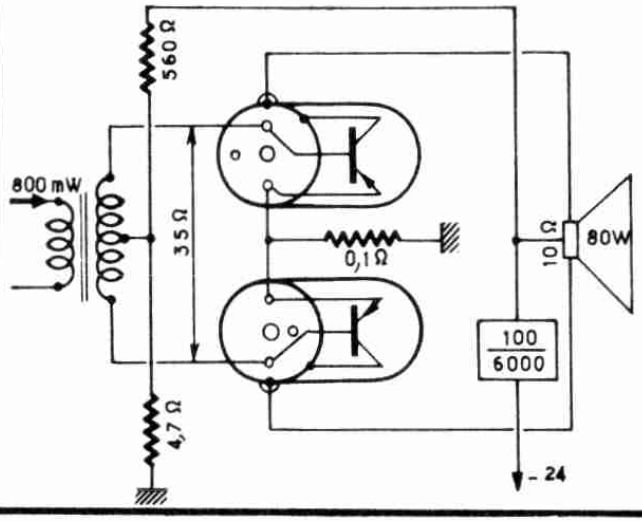
β = 40
GP = 23 dB



2N 1100

P

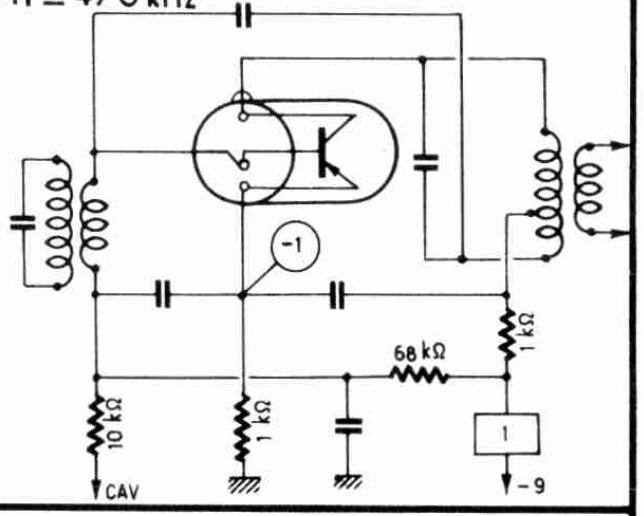
β = 30
GP = 20 dB



2N 1109 (2N 1110)

MF_470 kHz

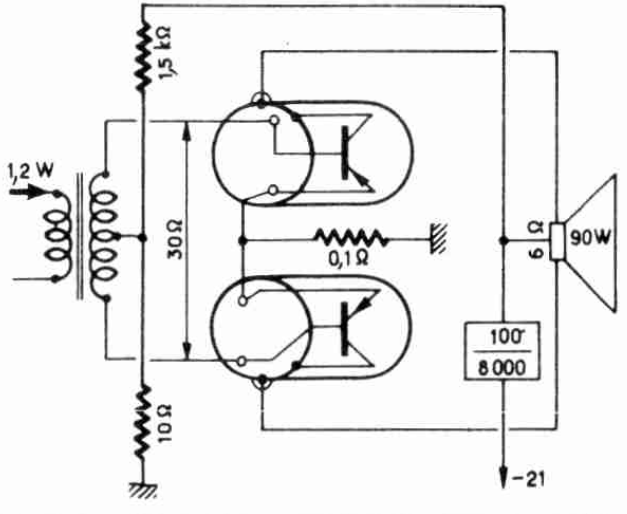
GP = 30 (29) dB



2N 1146 A

P

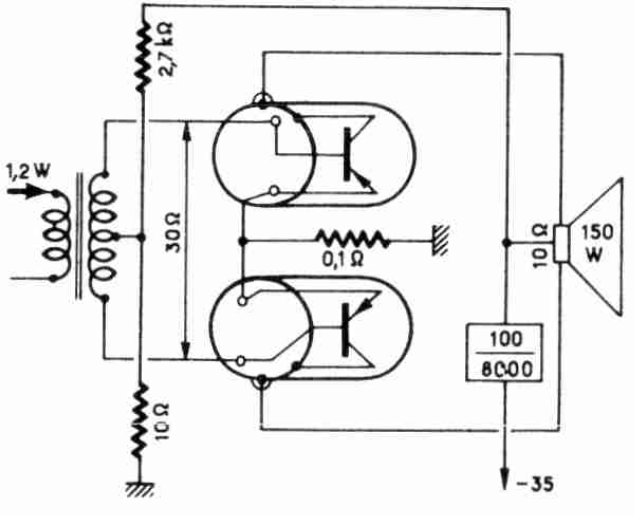
β = 30...200
GP = 18 dB



2N 1146 C

P

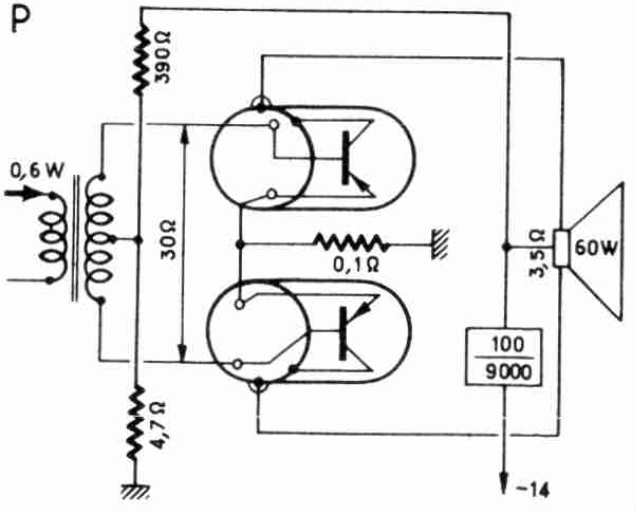
β = 30...200
GP = 21 dB



2N 1162
2N 1163

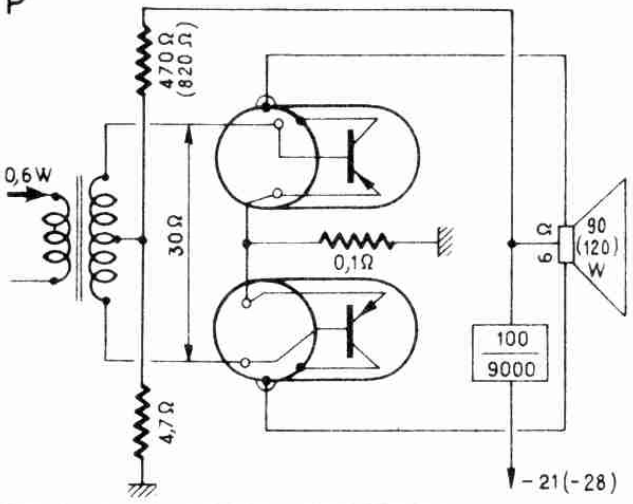
P

β = 65
GP = 20 dB



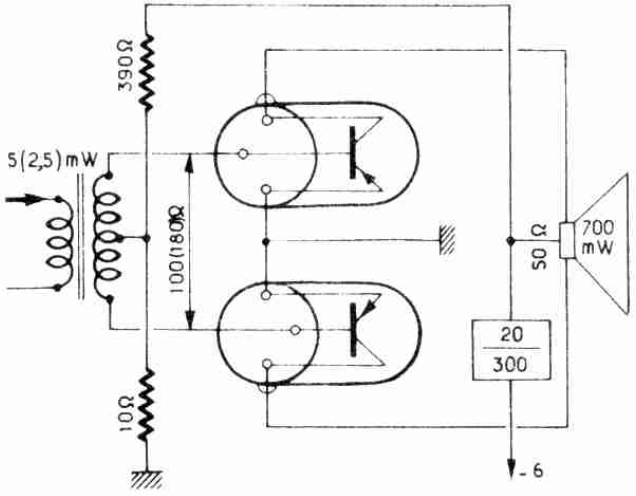
2N 1164, (66)
2N 1165, (67)
P

β = 65
GP = 22 dB
(23 dB)



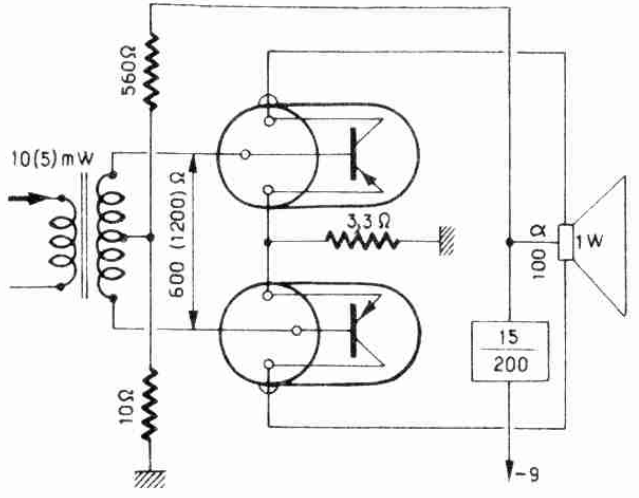
2N1183
(2N1184)

β => 20 (> 40)
GP = 21 (24) dB



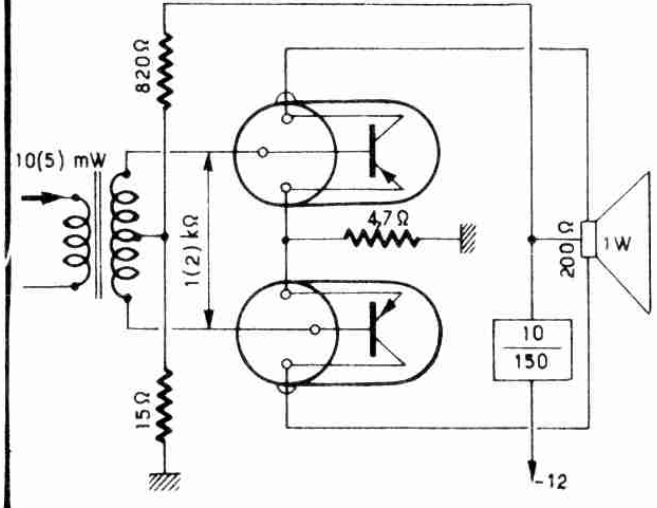
2N1183 A
(2N1184 A)

β > 20 (>40)
GP = 20 (23) dB



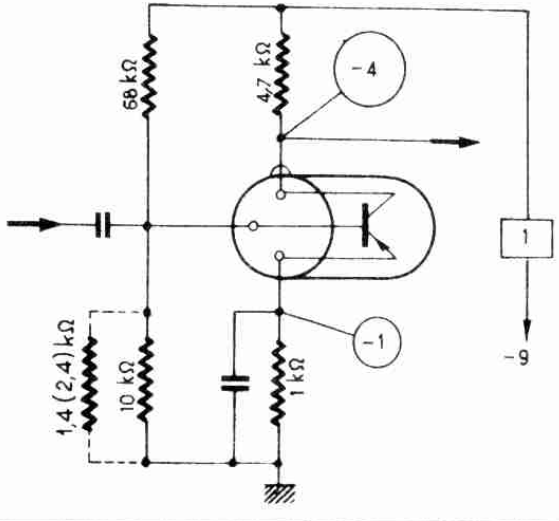
2N1183 B
(2N1184 B)

β > 20 (> 40)
GP = 20 (23) dB



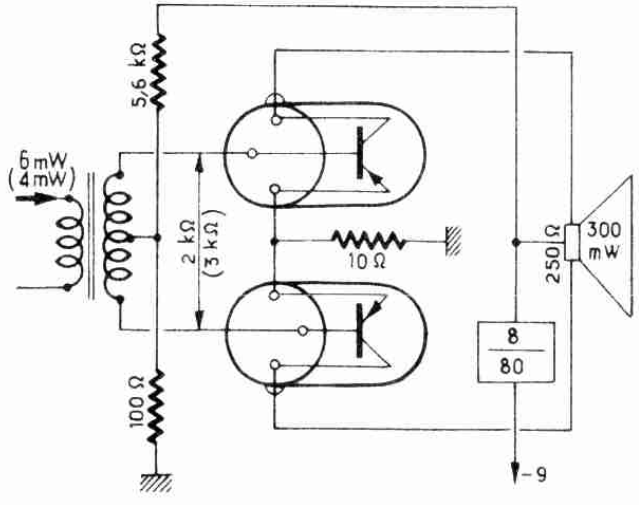
2N 1191, (92)
BF

β = 40 (75)
Fb = 10 dB



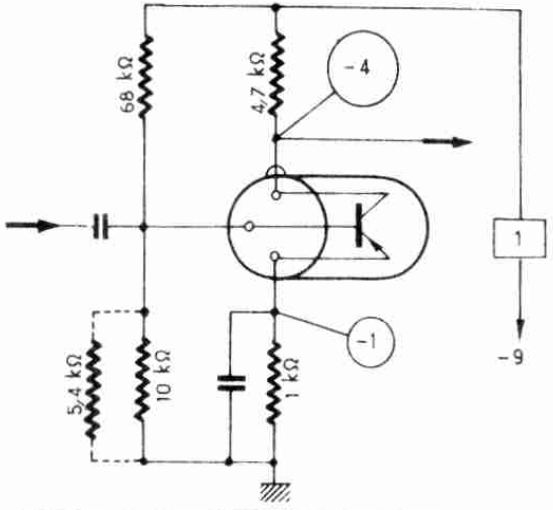
2N 1191, (92)
BF

β = 40 (75)
GP = 17 dB
(19 dB)



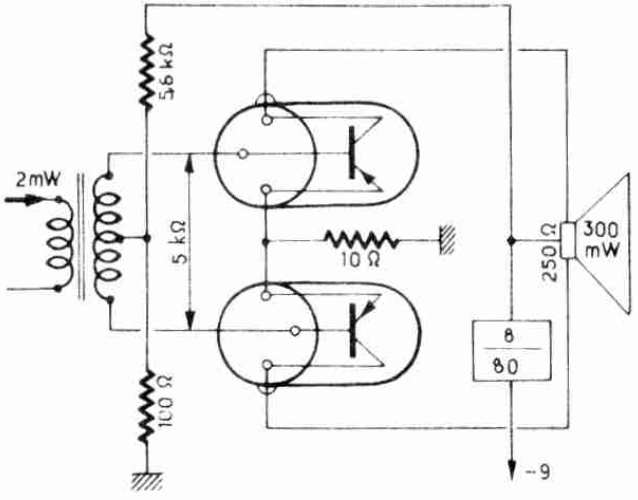
2 N 1193
BF

β = 160
Fb = 10 dB



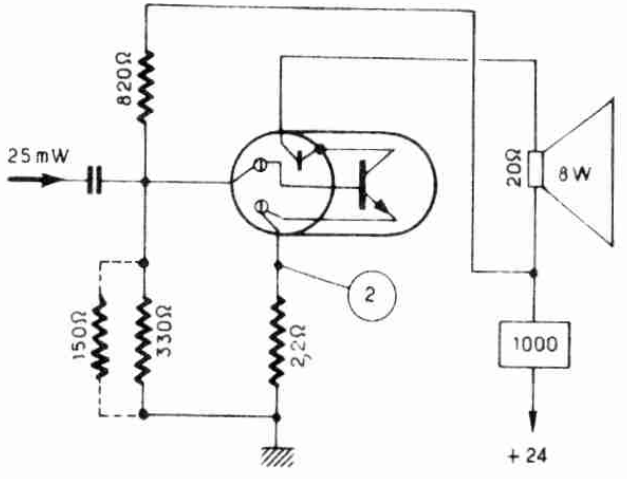
2 N 1193
BF

β = 160
GP = 22 dB



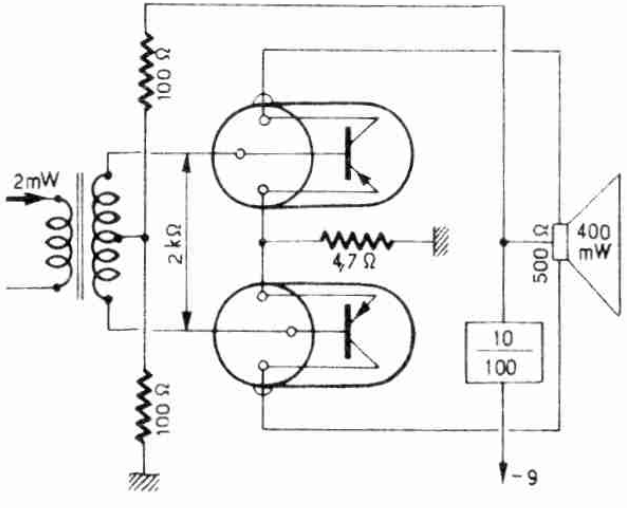
2N1208
n-p-n
Si

β = 40
GP = 25 dB



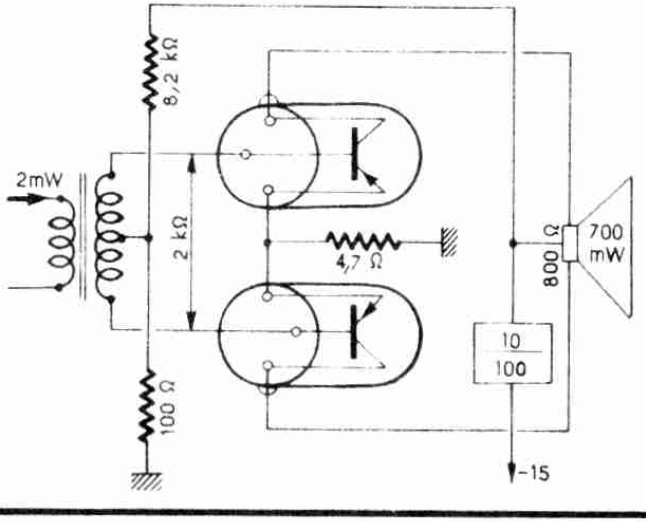
2 N 1273
BF

β = 50
GP = 24 dB



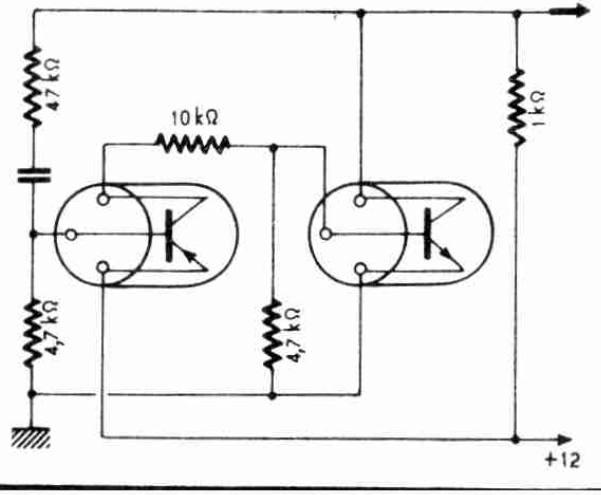
2 N 1274
BF

β = 50
GP = 26 dB



2N1302 n-p-n
2N1303 p-n-p
Multivibrateur

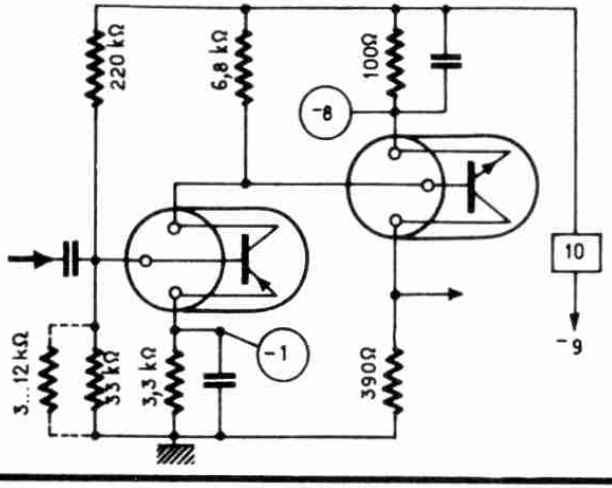
β > 20



2N1304 n-p-n
2N1305 p-n-p

β = 40...200

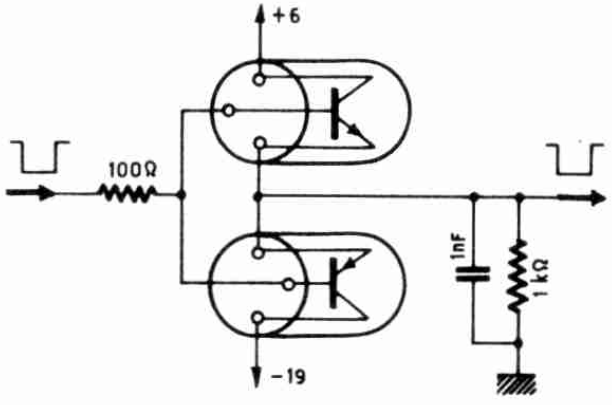
BF



2N1306 n-p-n
2N1307 p-n-p

β = 60...300

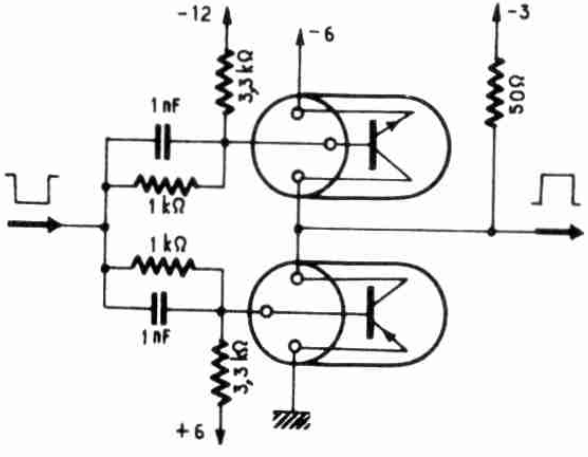
Adapt. impéd.



2N1308 n-p-n
2N1309 p-n-p

β > 80

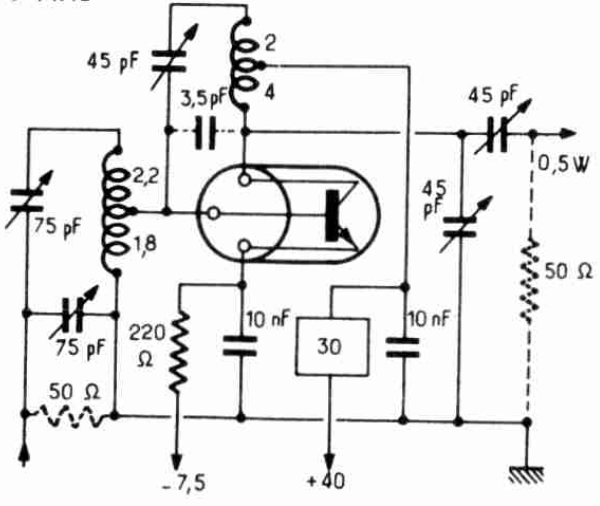
Inverseur



2N 1338

GP = 10 dB

70 MHz

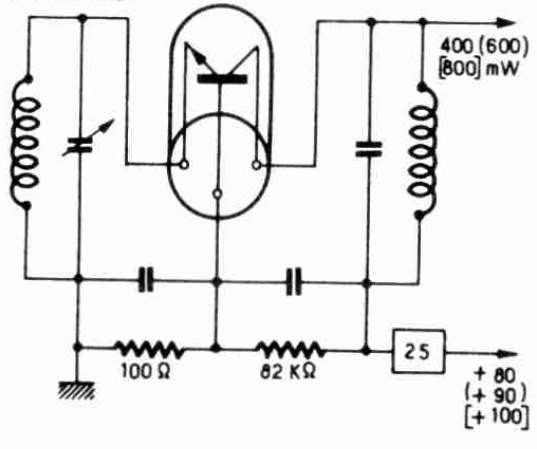


2 N 1339
(2 N 1340)
[2 N 1341]

n-p-n
Si

β = 15

Osc. 70 MHz

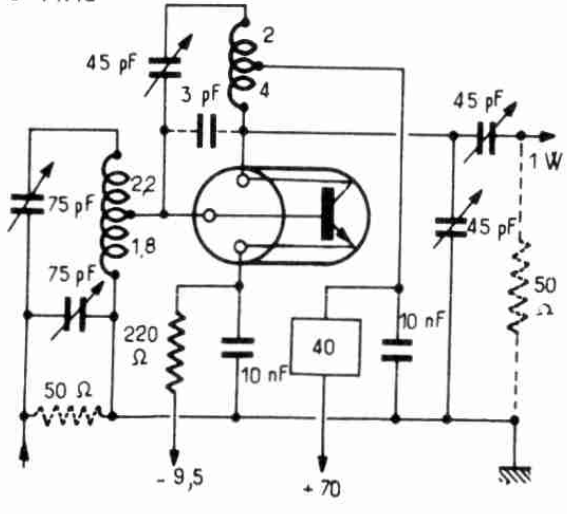


2N 1342

β = 15

GP = 10 dB

70 MHz

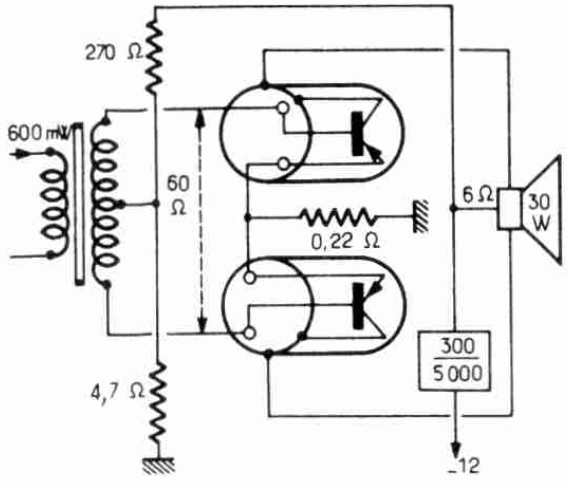


2N 1358

P

$\beta = 50$

GP = 23 dB

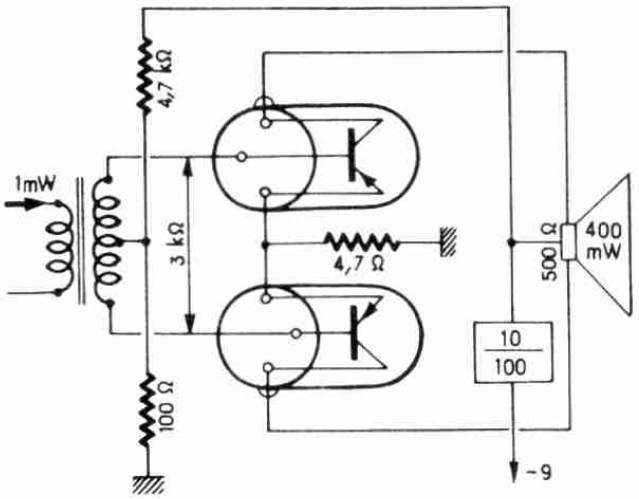


2N 1370

BF

$\beta = 80$

GP = 26 dB

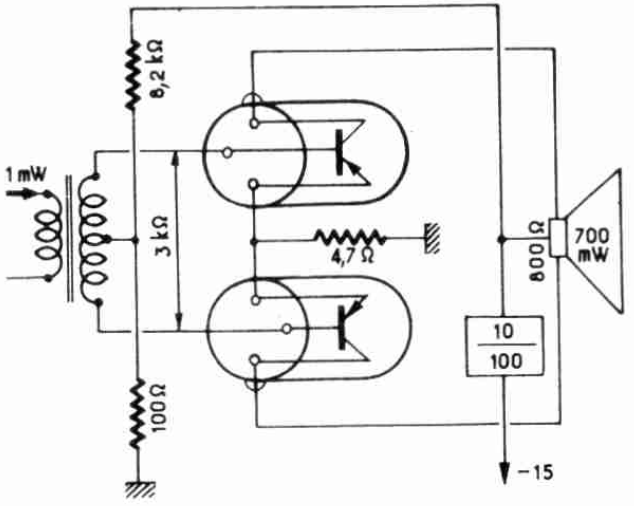


2N 1371

BF

$\beta = 80$

GP = 26 dB

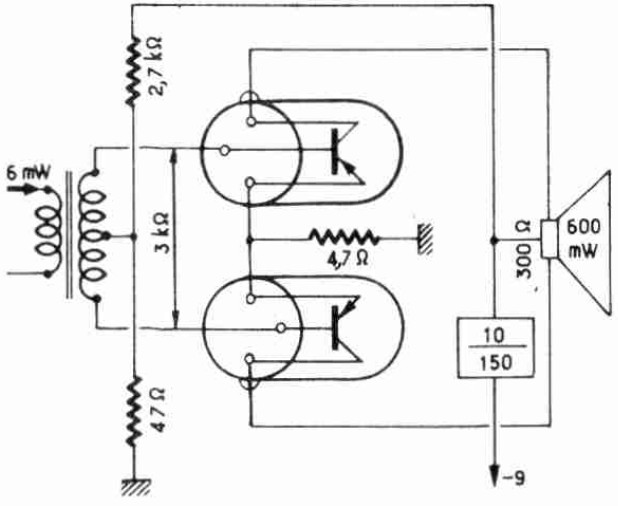


2N 1372

BF

$\beta = 45$

GP = 20 dB

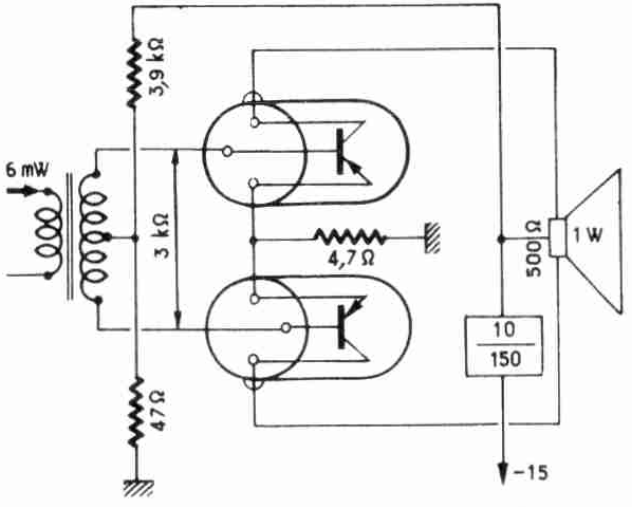


2N 1373

BF

$\beta = 45$

GP = 22 dB

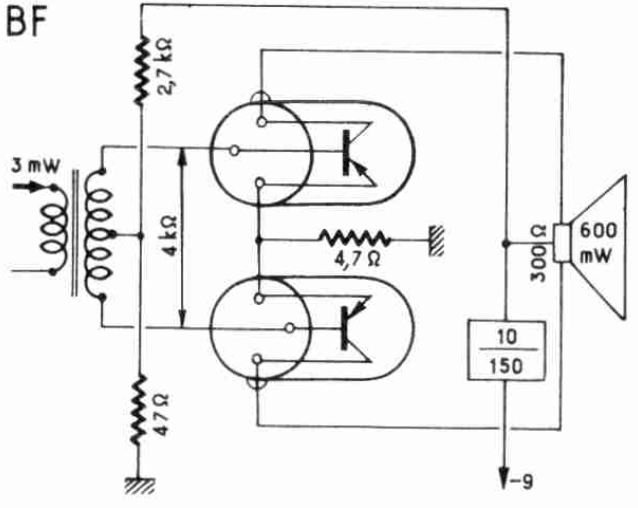


2N 1374 (2N 1376)

BF

$\beta = 80$ (95)

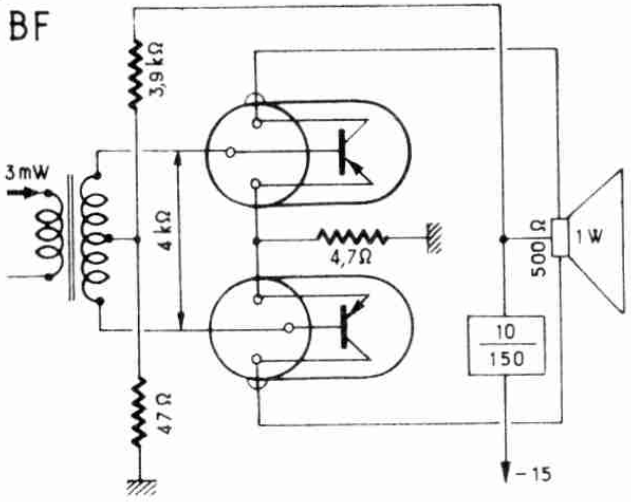
GP = 23 dB



2N 1375 (2N 1377)

BF

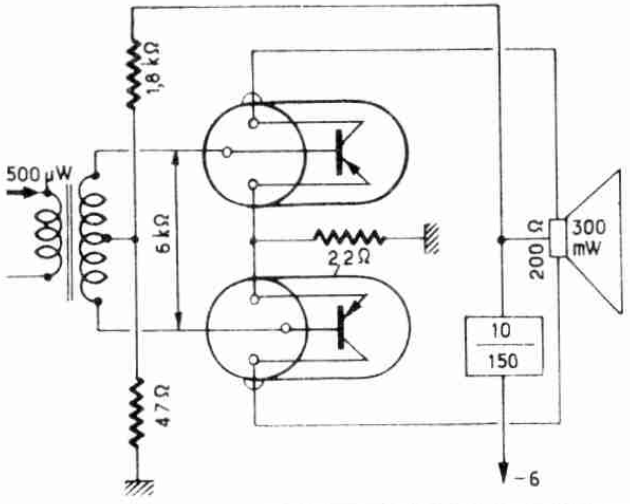
β = 80 (95)
GP = 25 dB



2N 1378

BF

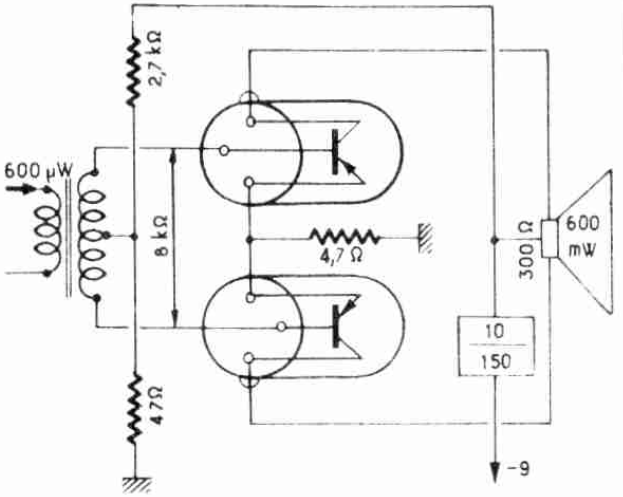
β = 200
GP = 28 dB



2N 1379

BF

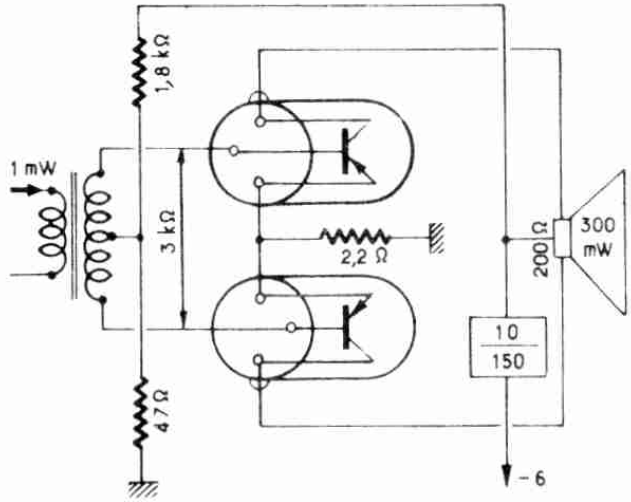
β = 200
GP = 22 dB



2N 1380

BF

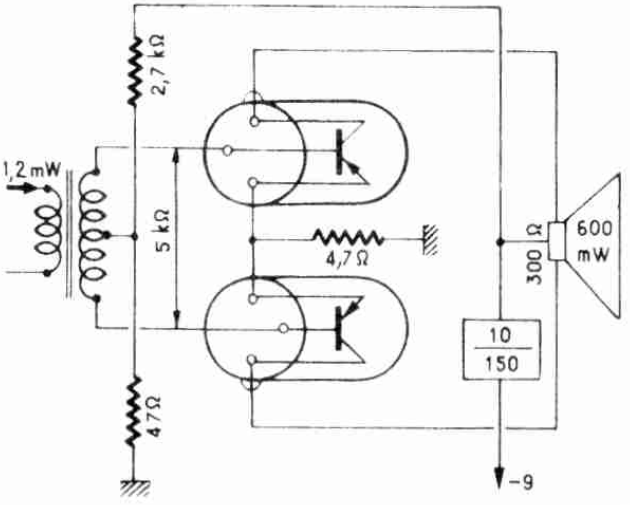
β = 100
GP = 25 dB



2N 1381

BF

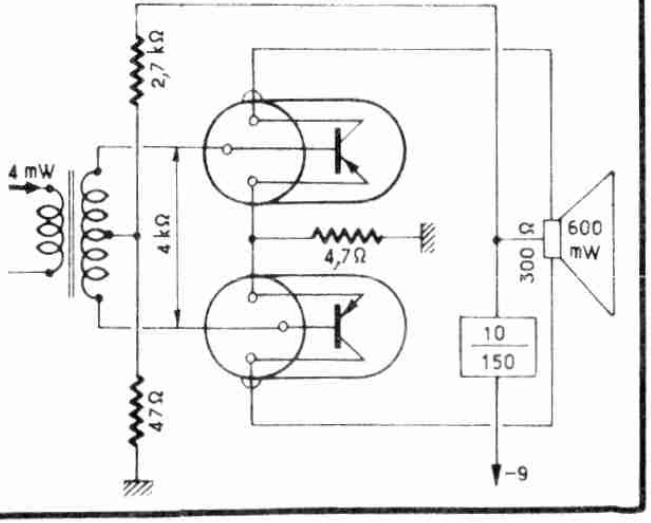
β = 100
GP = 27 dB



2N 1382

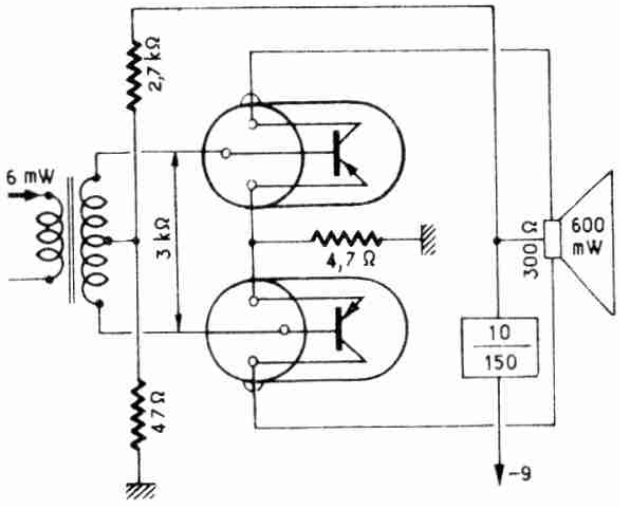
BF

β = 80
GP = 22 dB



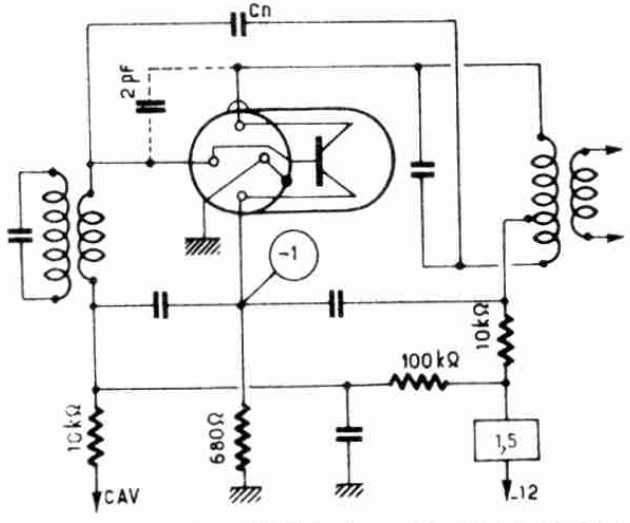
2N 1383
BF

β = 50
GP = 20 dB



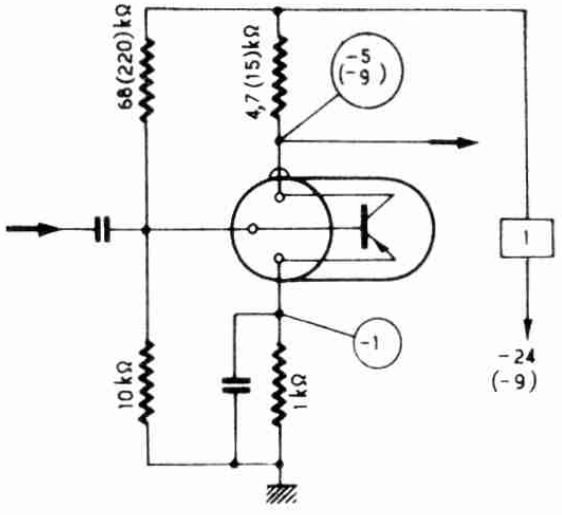
2N1395
MF470 kHz

β = 90
GP = 45 dB



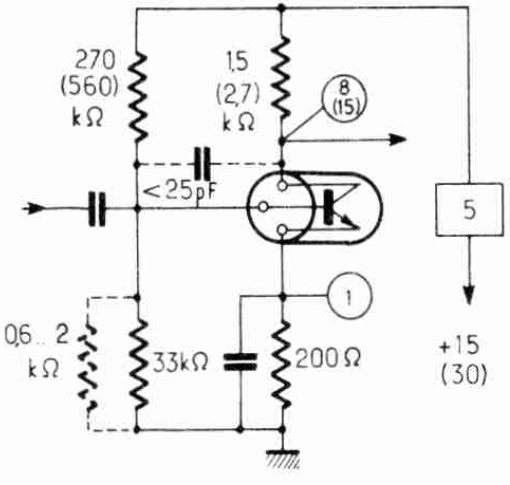
2N1413, 14, 15

β = 30, 44, 64



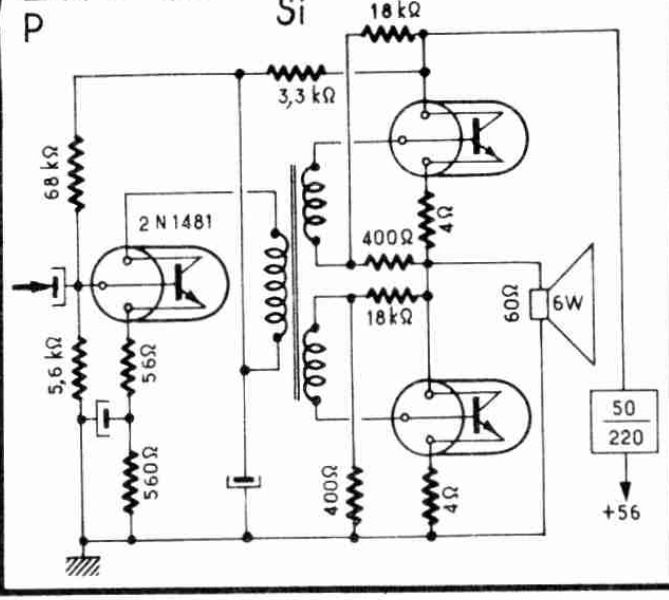
2N1420
BF-HF

β = 100.....300
f_T = 100 MHz



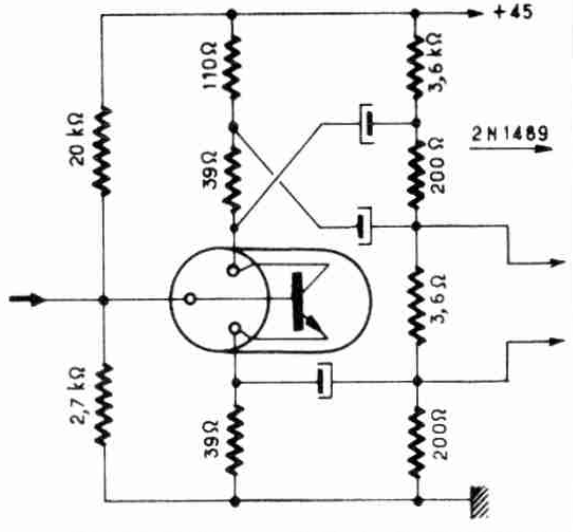
2N1485
n-p-n
Si
P

β => 35
GP = 60 dB



2N1485
n-p-n
Si
BF

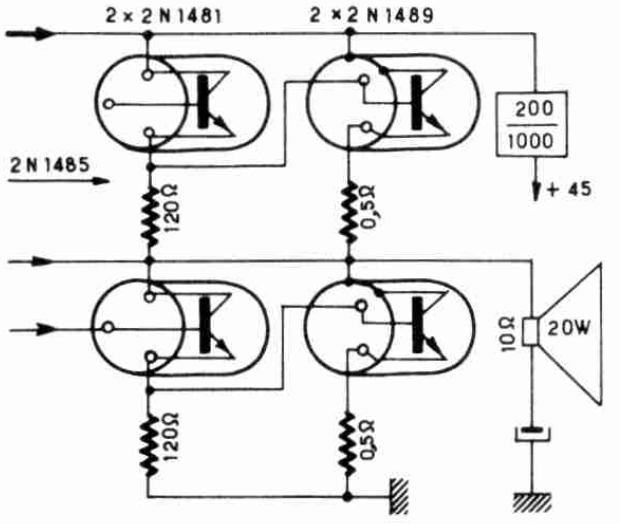
β => 35



2N1489

n-p-n
Si
P

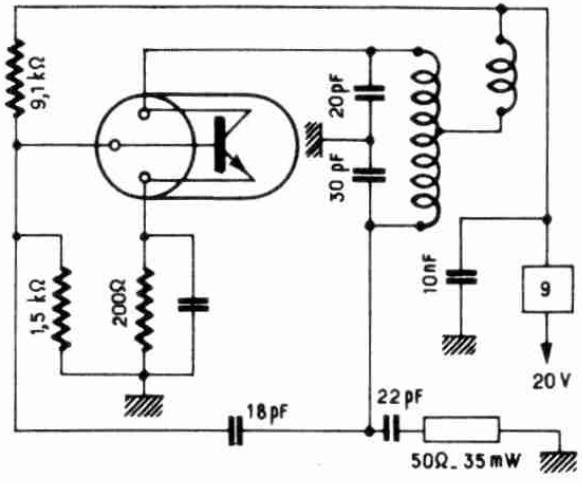
β = >25
GP = 36dB



2N1491

n-p-n
Si
HF Osc.
70MHz

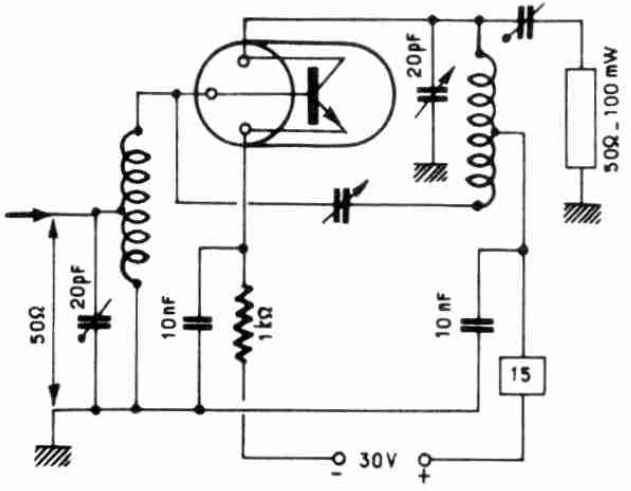
β = 50



2N1492

n-p-n
Si
HF 70MHz

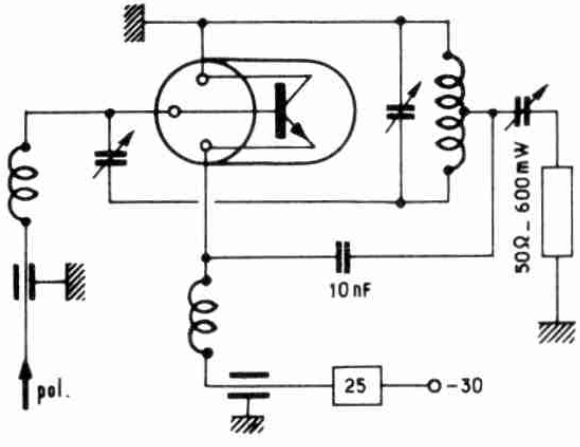
β = 50
GP = 15 dB



2N1493

n-p-n
Si
P. Osc.
70 MHz

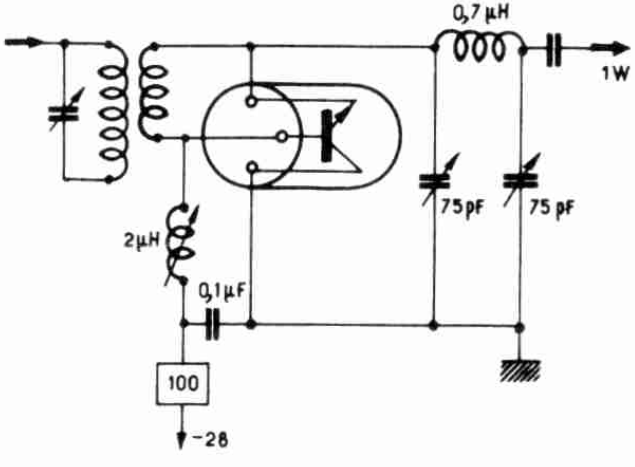
β = 50



2N1506

n-p-n
Si
30 MHz

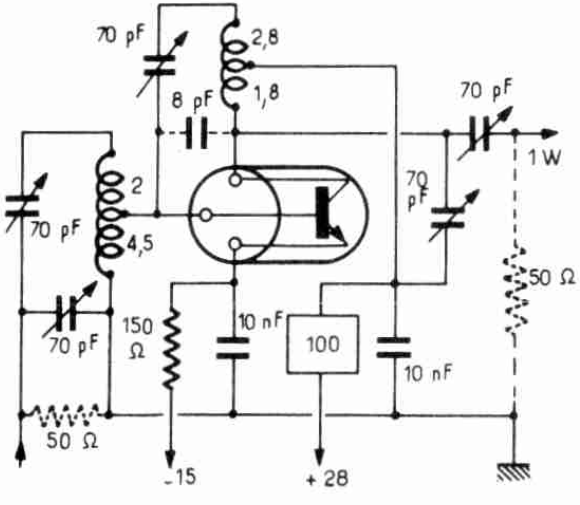
β = 10...50
GP = 18 dB



2N 1506

70 MHz

β > 15
GP = 9...12 dB

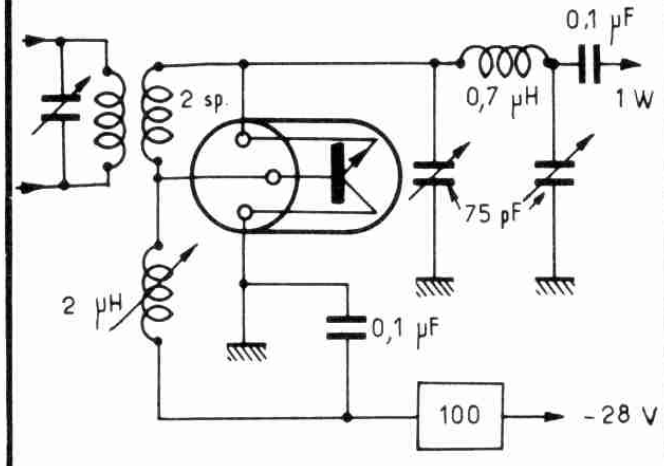


2N 1506 A

30 MHz

n-p-n Si
triple diffusion

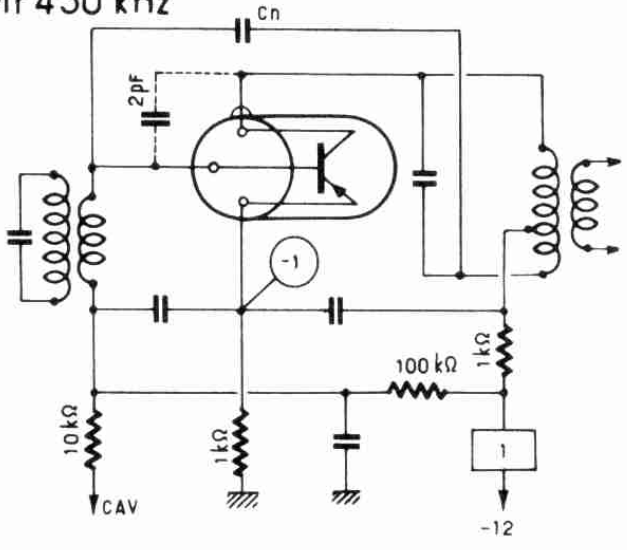
β = 40
GP = 18 dB



2N1524

MF450 kHz

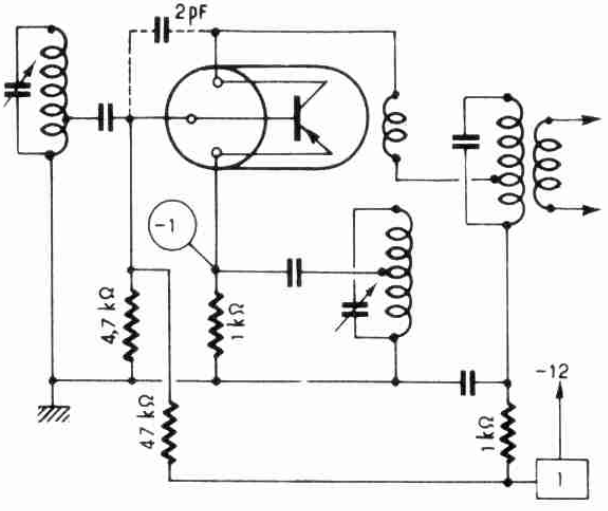
β = 60
GP = 33 dB



2N1526

Conv.<6 MHz

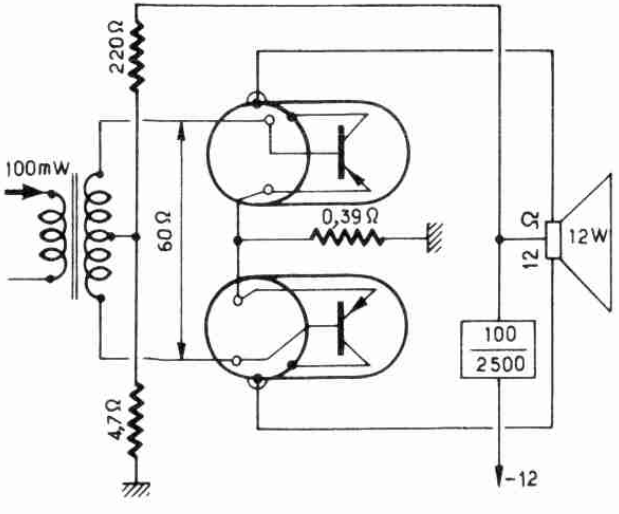
β = 130
GC = 31dB



2N1529,30A

P

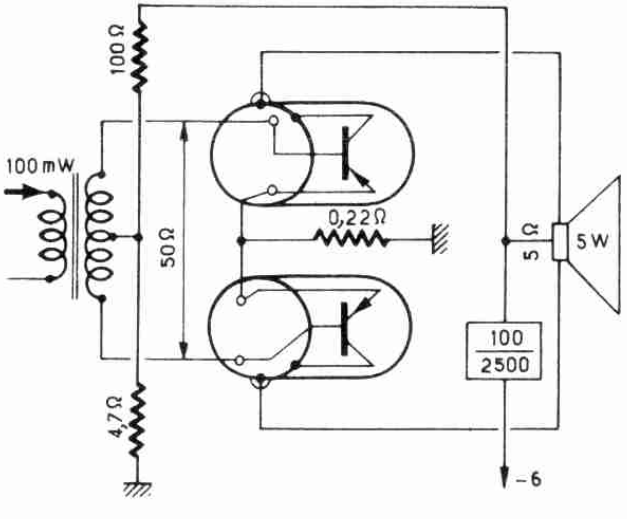
β = 20...40
GP = 21 dB



2N1529A

P

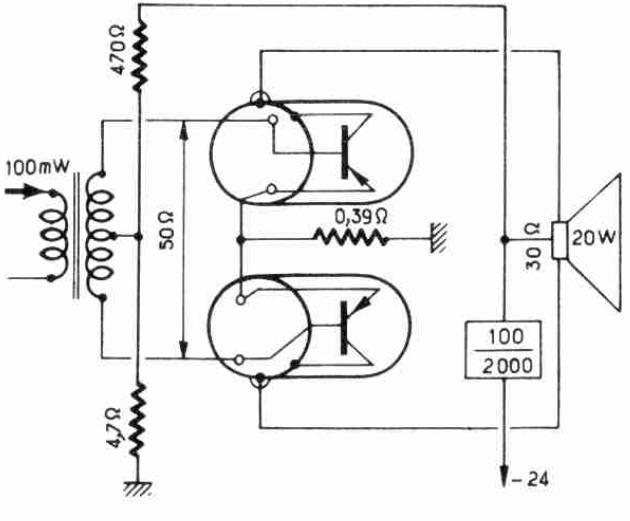
β = 20...40
GP = 17 dB



2N1531

P

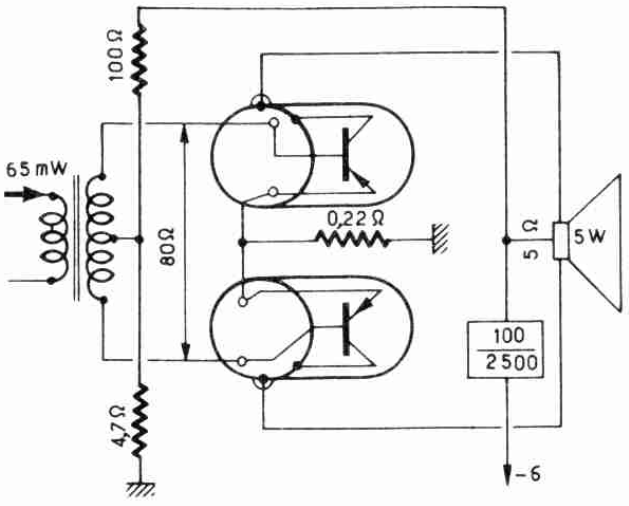
β = 20...40
GP = 23 dB



2N1534,A

β = 35...70
GP = 19 dB

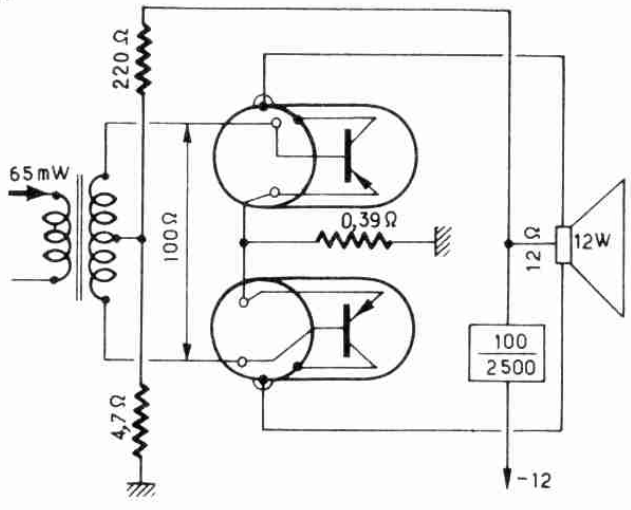
P



2N1535,A

β = 35...70
GP = 23 dB

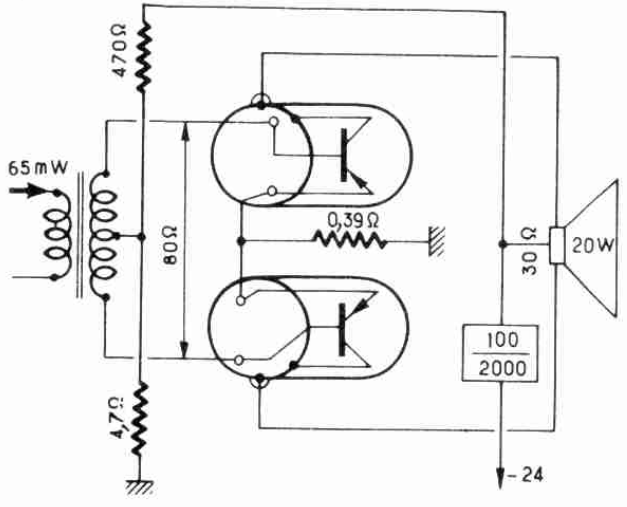
P



2N1536

β = 35...70
GP = 25 dB

P

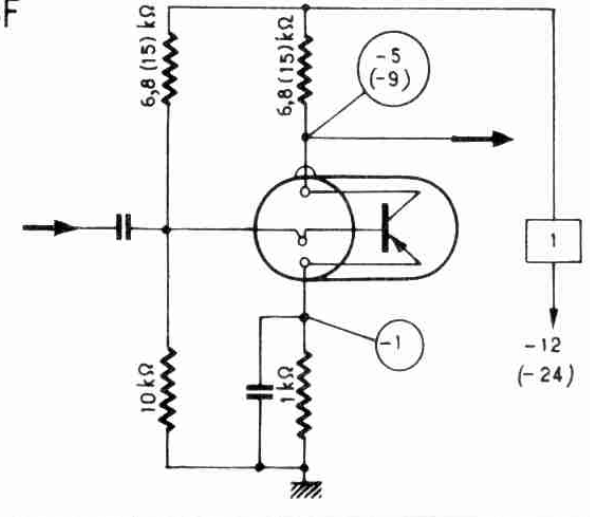


2N1592 (2N1593)

Si

β = 140

BF

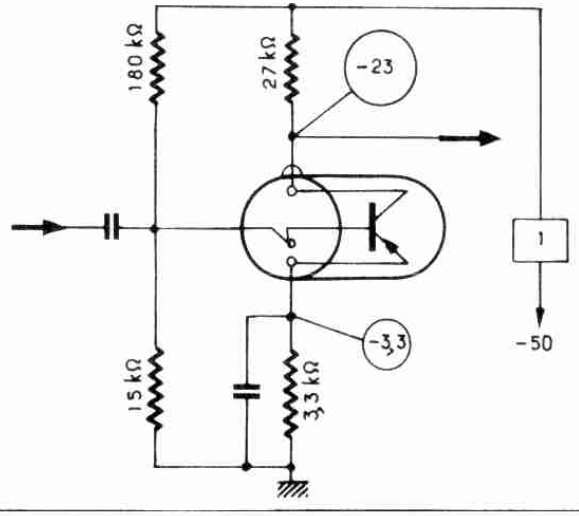


2N1594

Si

β = 140

BF

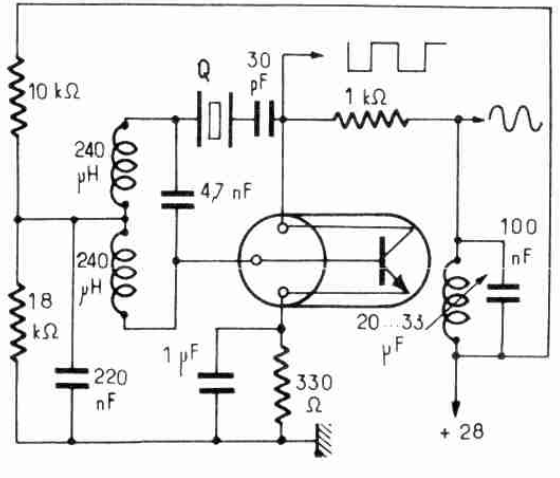


2N1613

n-p-n Si
Planar

β = 40...120

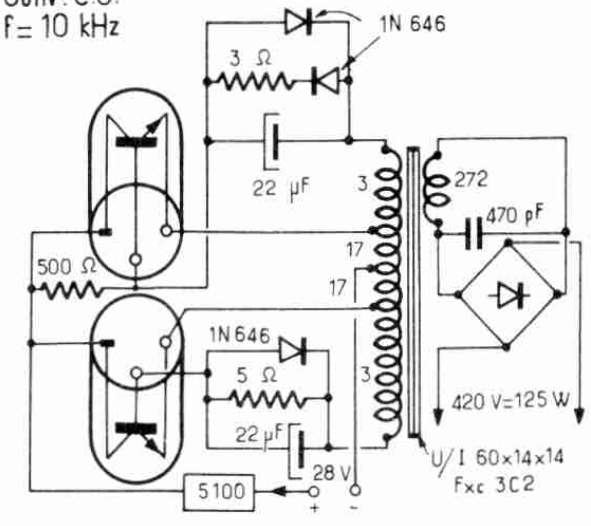
Osc. 100 kHz



2N 1618

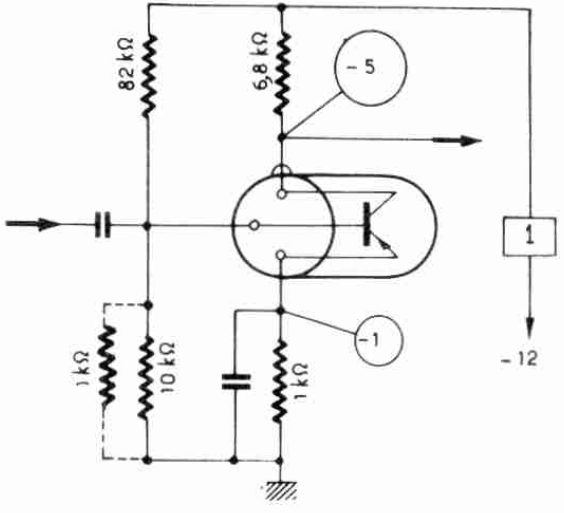
n-p-n Si β = 15...75
Mesa

Conv. C.C.
f = 10 kHz



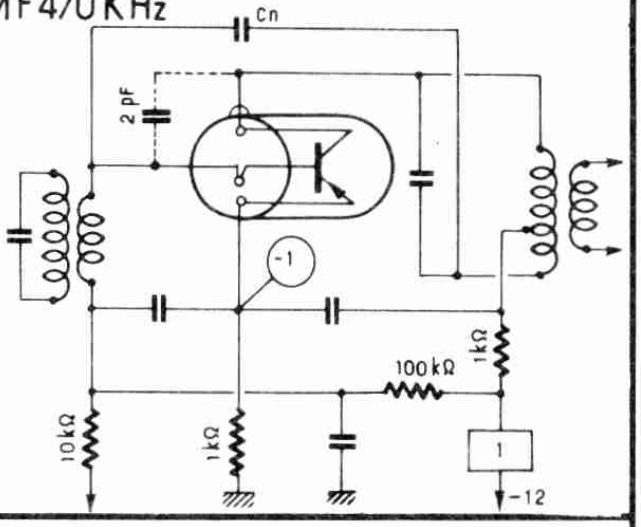
2N1623

Si β = 25
Fb < 18 dB



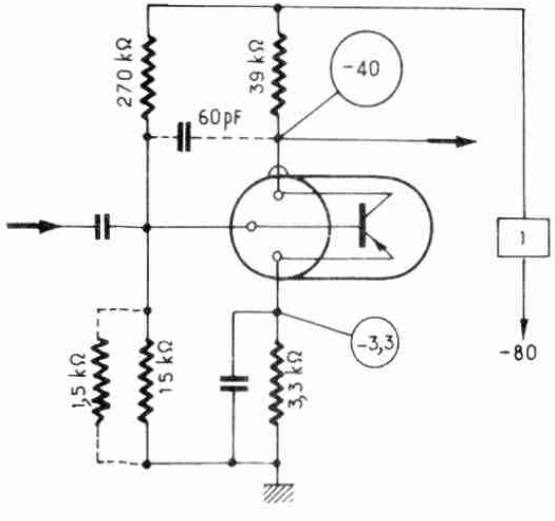
2N1632 (2N1634)

β = 80(75)
GP = 46(38) dB
MF 470 KHz



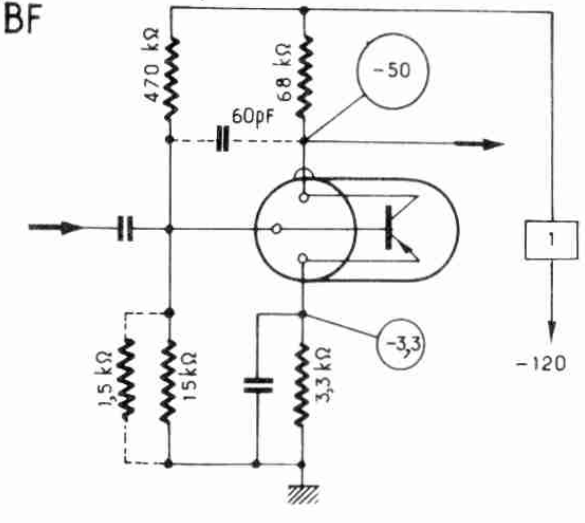
2N1654

Si β = 30
BF



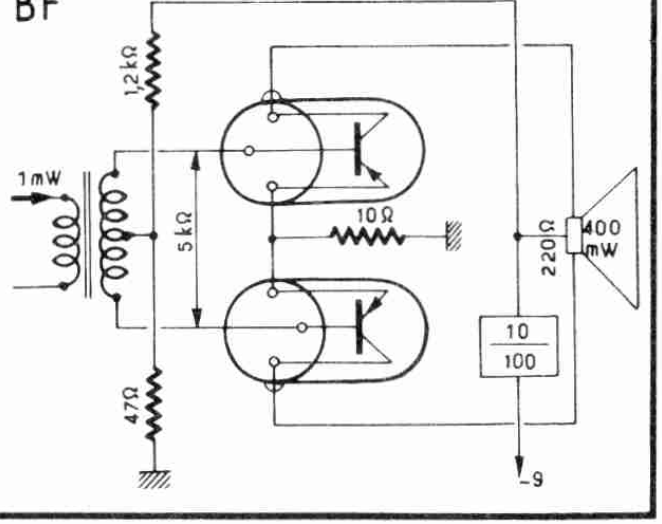
2N1655 (2N1656)

Si β = 15(30)
BF



2N1706 (2N1707)

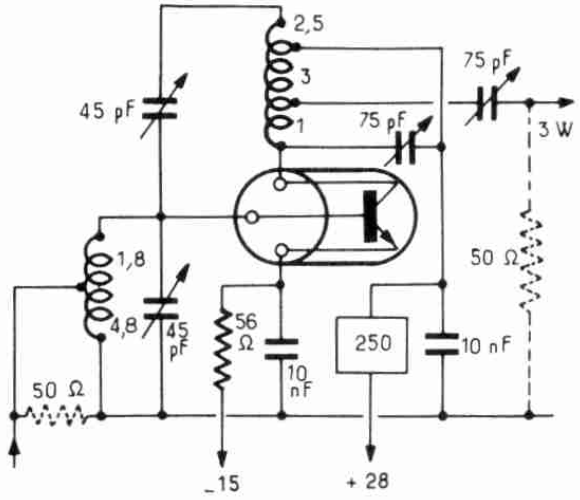
β = 90(95)
GP = 26 dB
BF



2N 1709

β = 75 ... 75

70 MHz

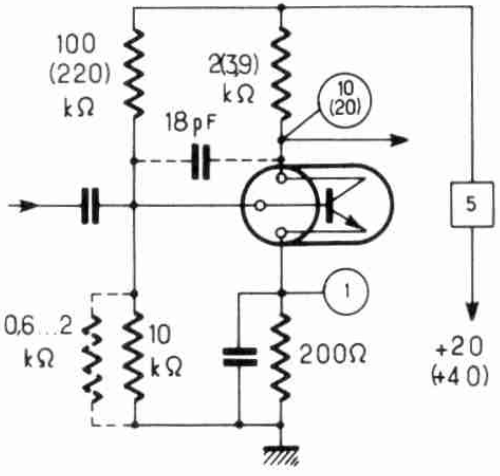


2N1711

BF-HF n-p-n Si

β = 100 300

f_T = 100 MHz

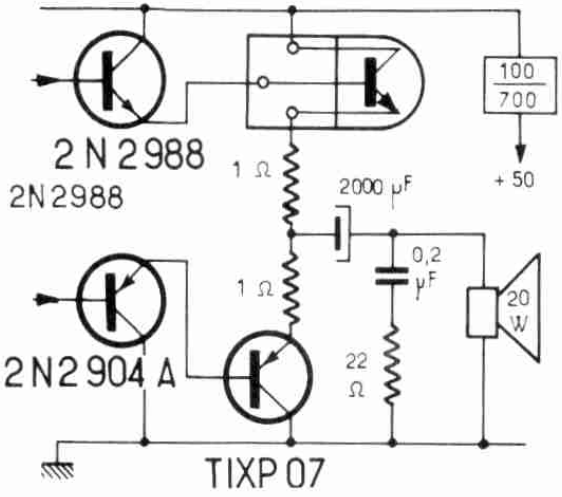


2N1722

n-p-n Si

mesa

β = 20 .. 90



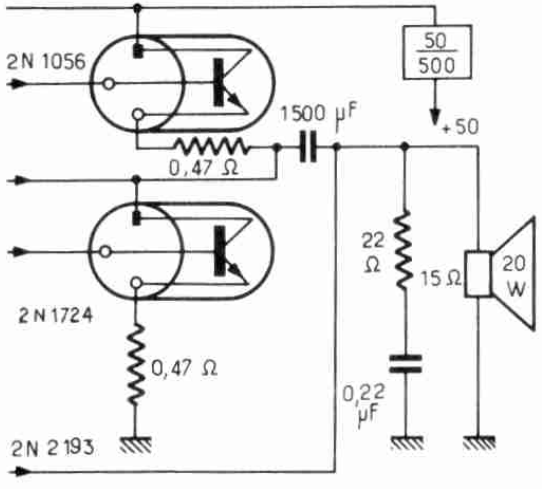
2N 1724

P

n-p-n Si

Mesa

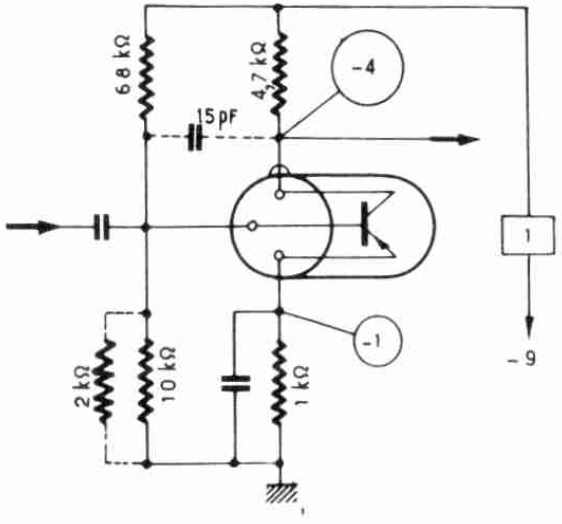
β = 20 ... 90



2N1808

BF

β = 60

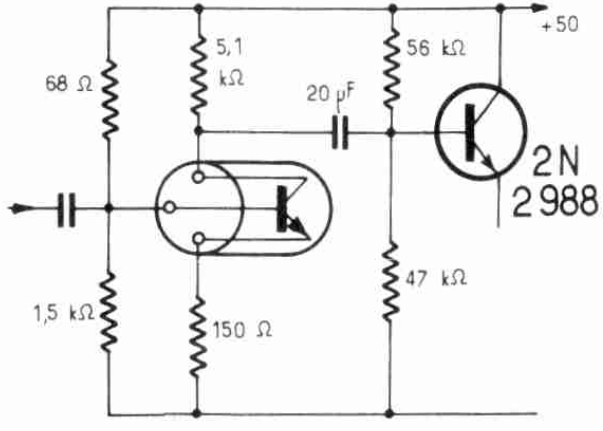


2N1893

BF

n-p-n Si

β = 40 .. 120

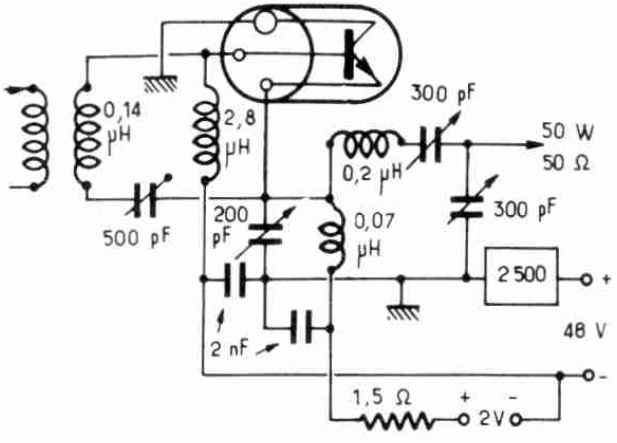


2N 1900, 03

30 MHz

n-p-n Si

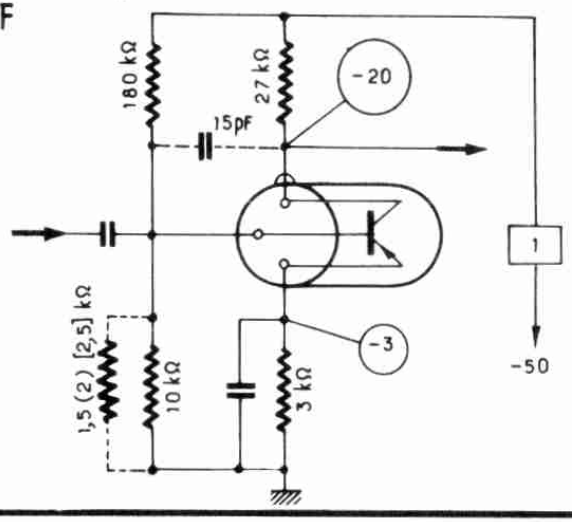
$\beta > 8$



2N 1924 (2N 1925) [2N 1926]

BF

β = 45(65)[80]

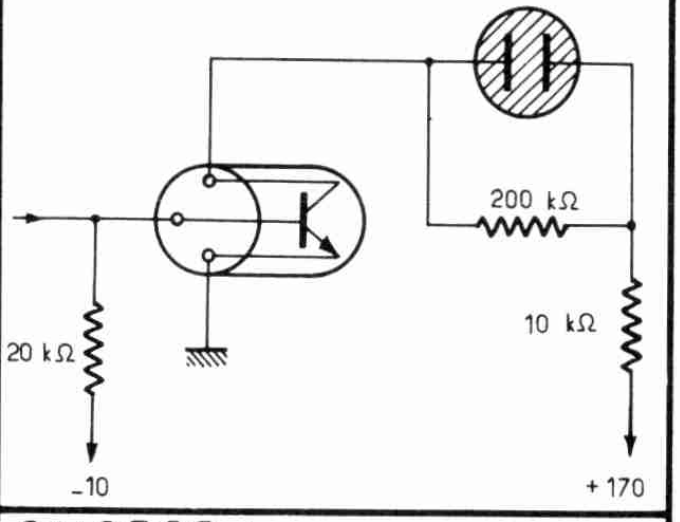


2N 1990

Commande Néon

n-p-n Planar Si

$\beta > 20$

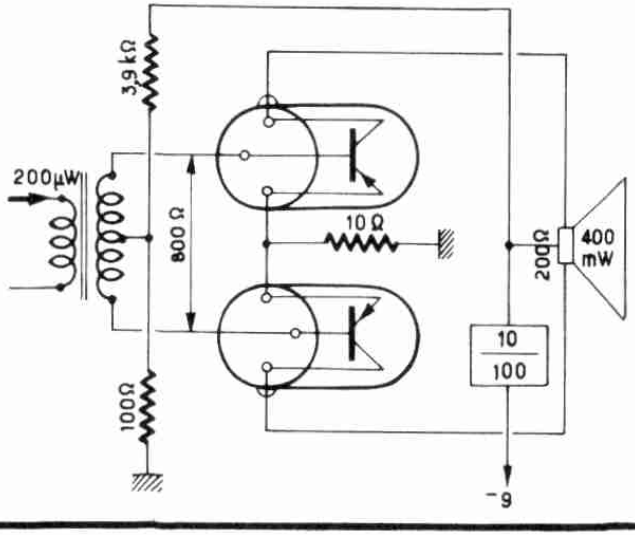


2N 2000

BF

β = 150

GP = 33 dB



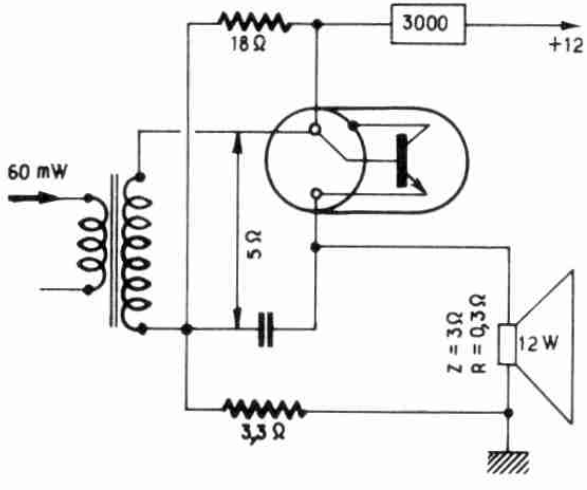
2N 2015

P

n-p-n Si

β = 15... 50

GP = 23 dB

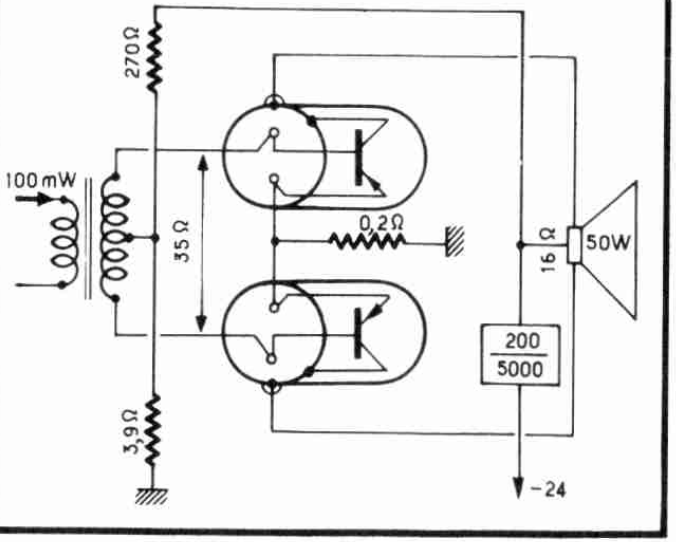


2N2080, A

P

β = 35...70

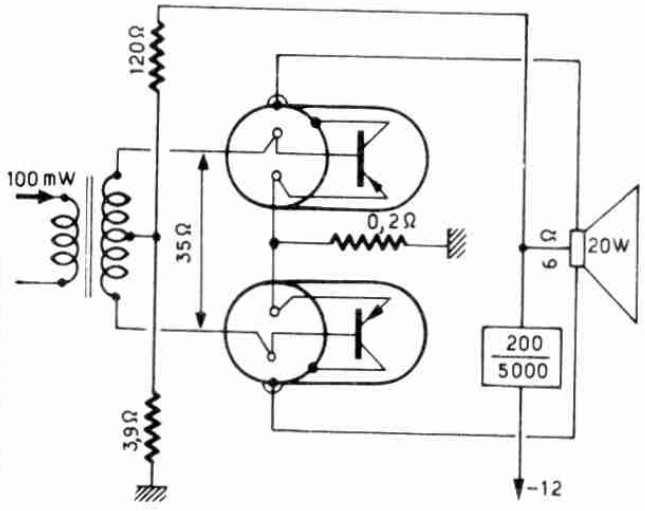
GP = 27 dB



2N 2082,A

P

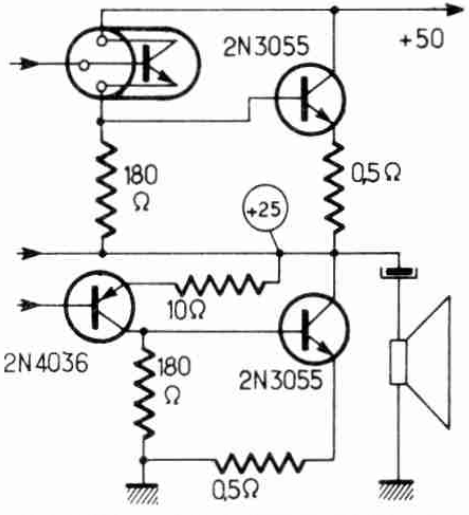
β = 35...70
GP = 23dB



2N2102

BF n-p-n Si

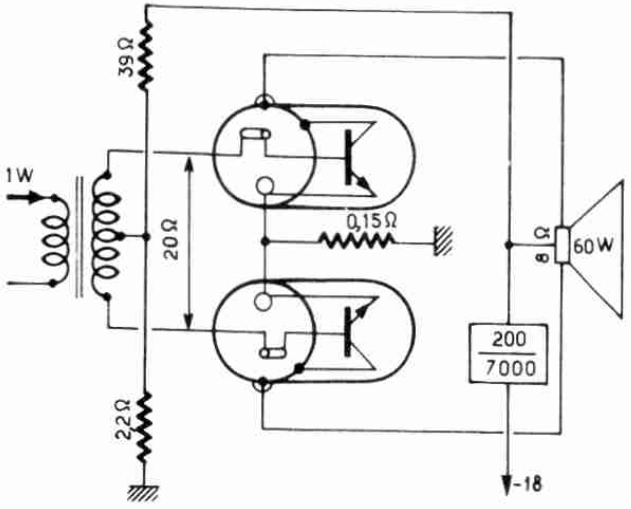
n = 40...120
f_T = 60 MHz



2N 2109

P n-p-n Si

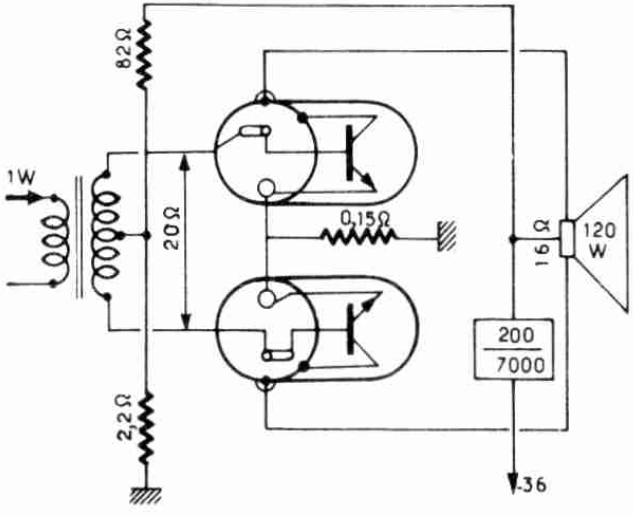
β = 14
GP = 18 dB



2N 2110

P n-p-n Si

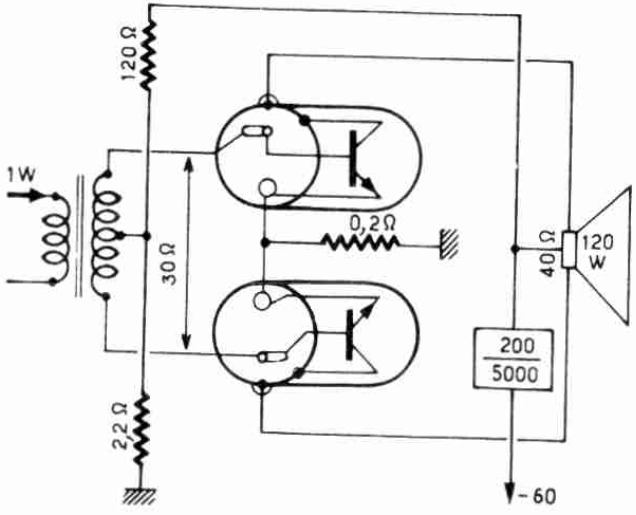
β = 14
GP = 21 dB



2N 2111

P n-p-n Si

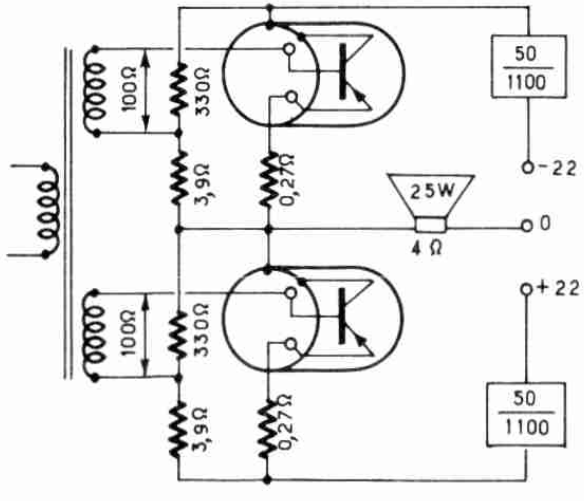
β = 14
GP = 21dB



2N2147

P

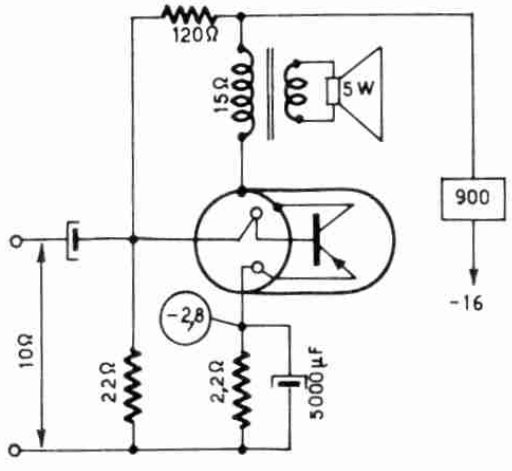
β = 75...300
GP = 32 dB



2N2148

P

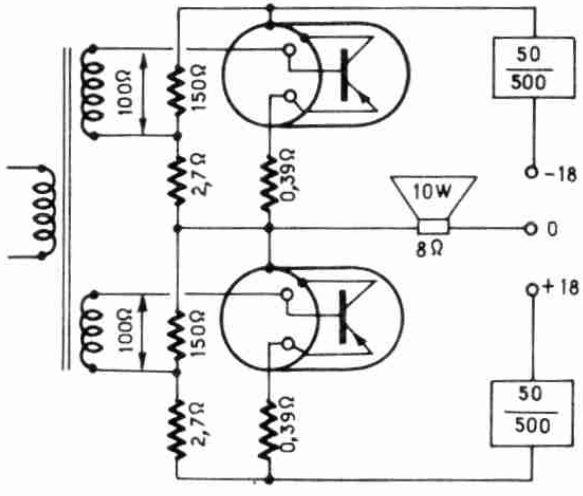
β = 30...100
GP = 36 dB



2N2148

P

β = 30...100
GP = 29 dB

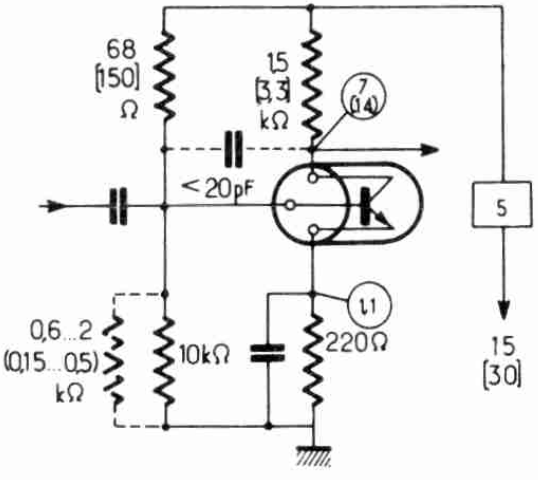


2N2192 (2N2194)

n-p-n Si

BF-HF

β = 100.....300 (20.....60)
f_T = 50MHz

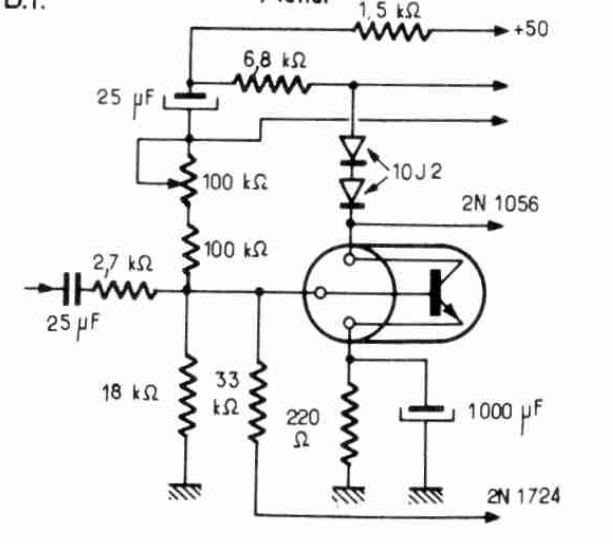


2N 2193

B.F.

n-p-n Si Planar

β = 20...120

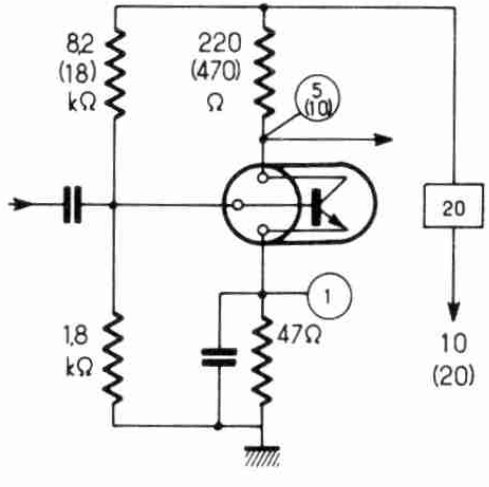


2N2195

BF-HF

n-p-n Si

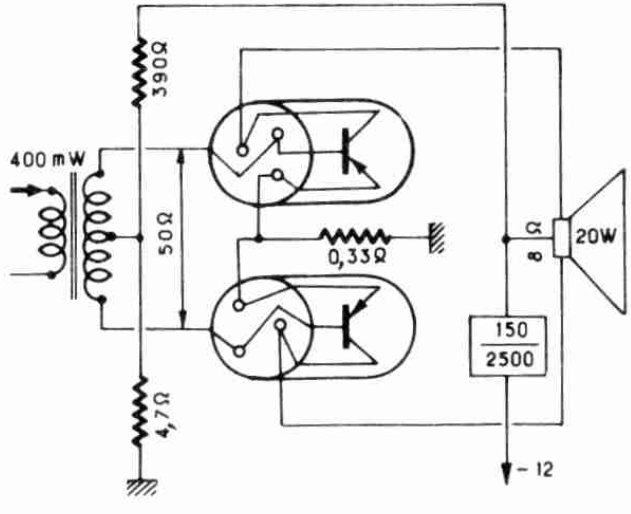
β>20



2N2266...69

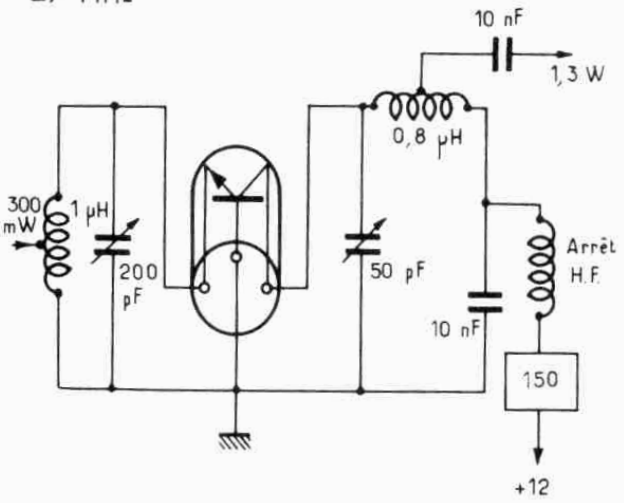
P

β = 25...75
GP = 17 dB



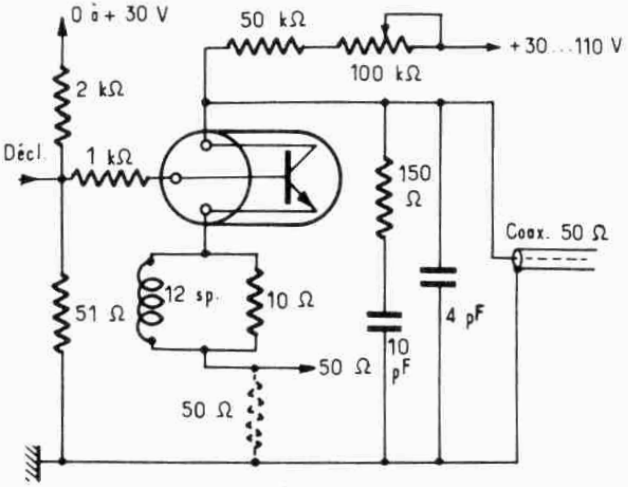
2N2297

n-p-n Si β = 40 ... 120
Planar Epitax. GP = 6,5 dB
27 MHz



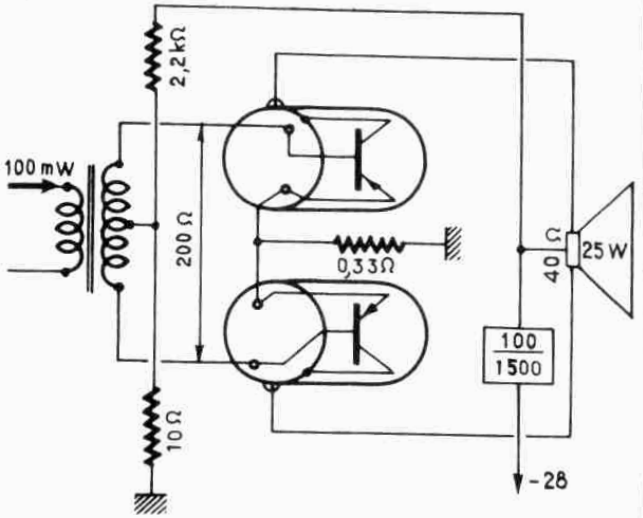
2N2369

Gen. Avalanche
n-p-n Si β = 40...120
Planar Epitax. t_r < 1 ns



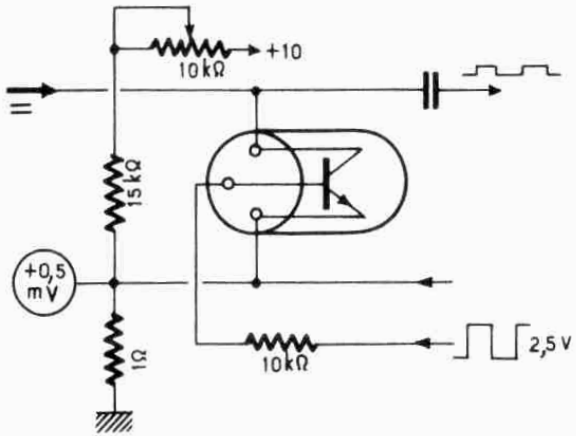
2N2423

P
β = 20...100
GP = 25 dB



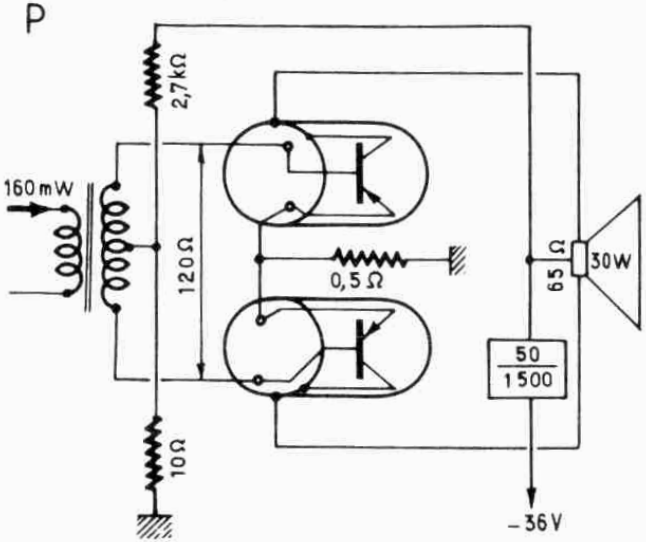
2N2432

Chopper Si n-p-n
β > 2



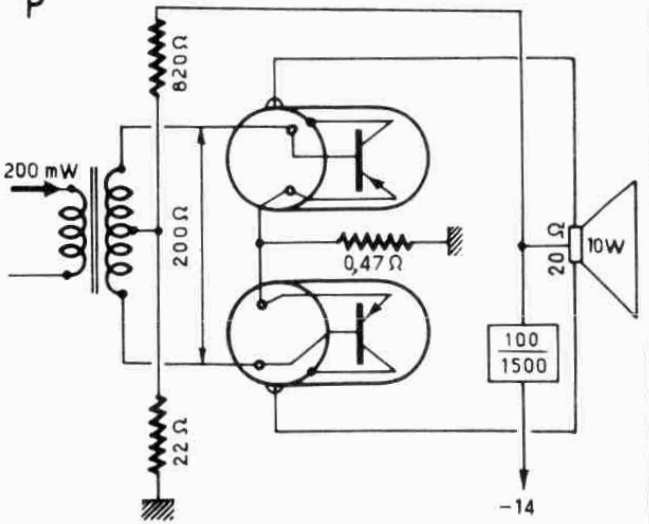
2N2526, 27

P
β = 20...50



2N2552, 53

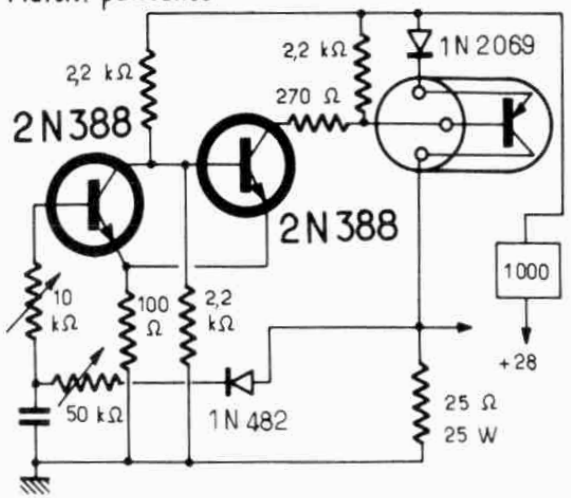
P
β = 20...60
GP = 17 dB



2 N 2557

β = 20.... 60

Multiv. puissance

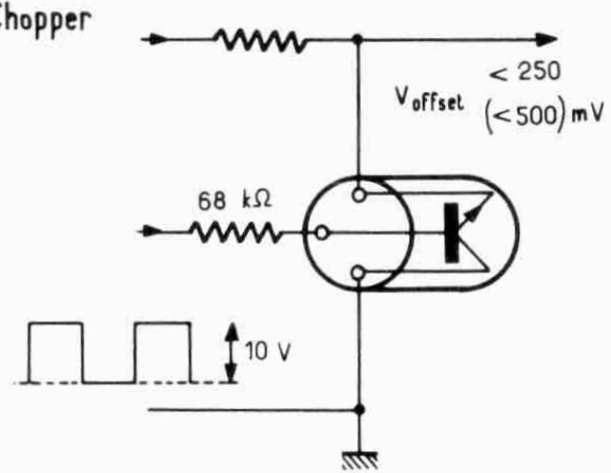


2N 2569 (2N 2570)

n-p-n Si β = 50

Planar Epitaxial β_{inv} = 4...10

Chopper

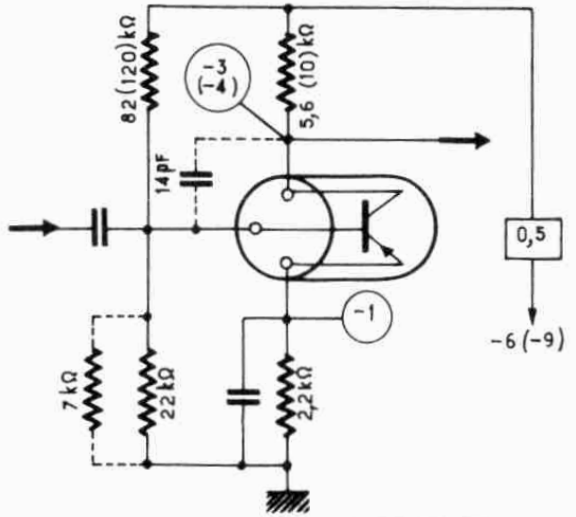


2N2613

β = 125

F_b < 5 dB

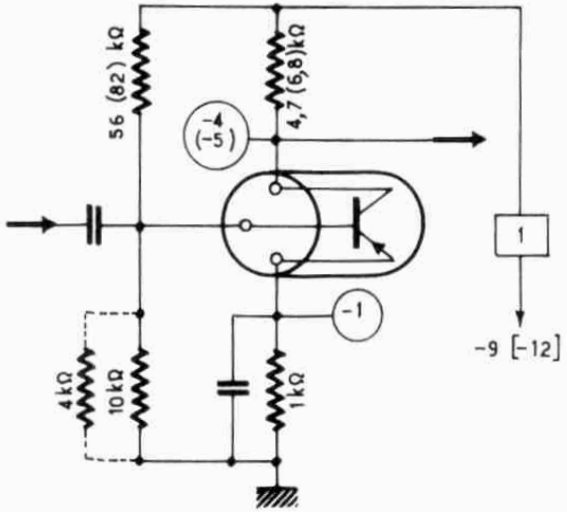
BF



2N2614

β = 160

BF



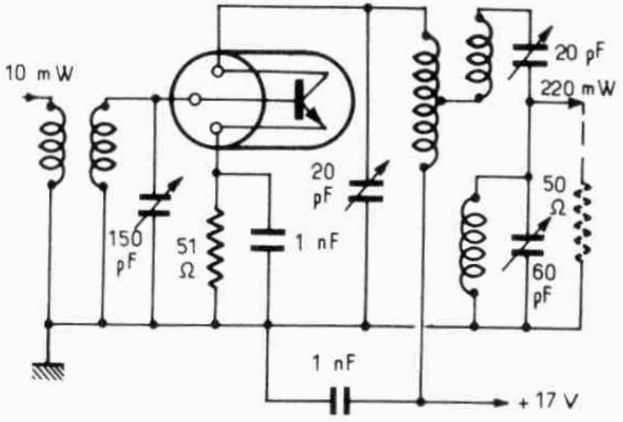
2N 2656

β = 65

GP = 3,5 dB

Doubleur 130 - 260 MHz

n-p-n Si planar épitaxial

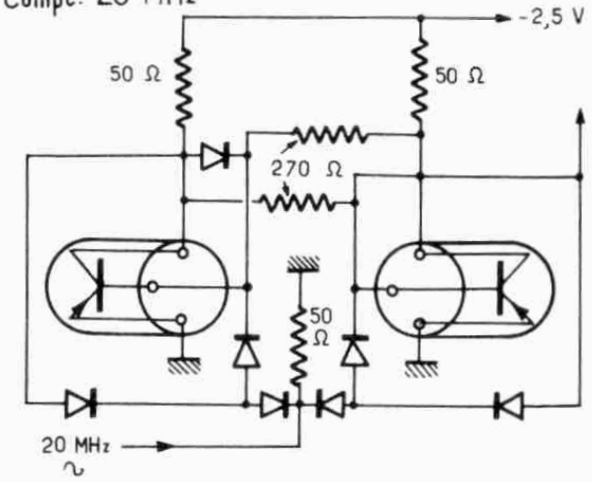


2 N 2695 2 N 2696

p-n-p Si β = 30...130

Planar Epitax.

Compt. 20 MHz



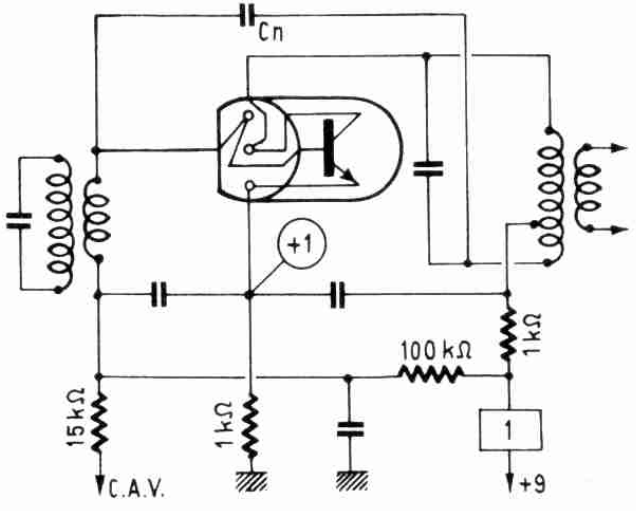
2 N 2711

MF 470 kHz

n-p-n Si

β = 30...90

GP = 37 dB



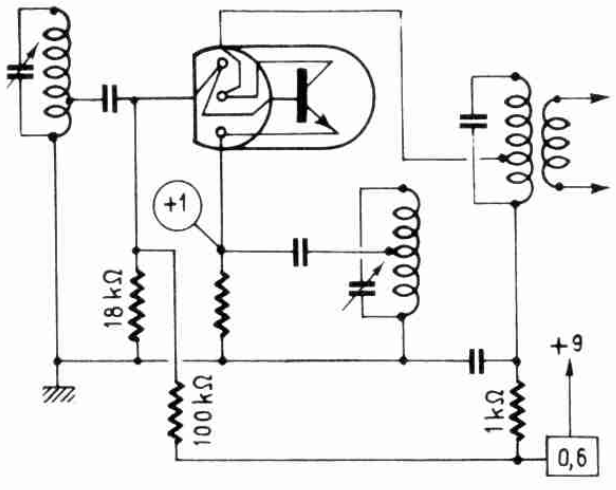
2 N 2712

Conv. < 10 MHz

n-p-n Si

β = 75...225

GP => 20 dB (6 MHz)

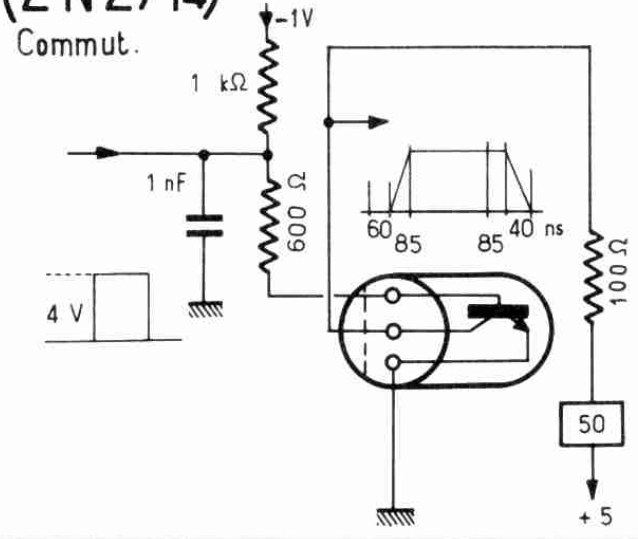


2 N 2713 (2 N 2714)

Commut.

n-p-n Si Planar

β = 30...90 (75...225)



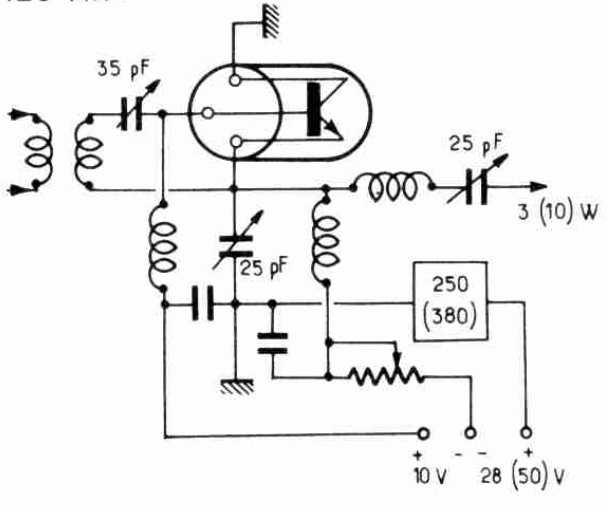
2 N 2781, 2, 3

125 MHz

n-p-n Si

β = 40

GP = 4,8 (5,2) dB



2 N 2784

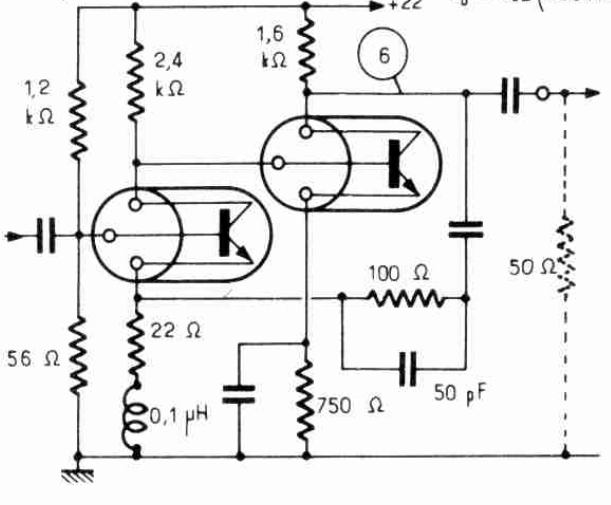
Amplif. < 150 MHz

n-p-n Si

β = 40....120

GV = 13,5 dB

F_b = 4 dB (200 MHz)

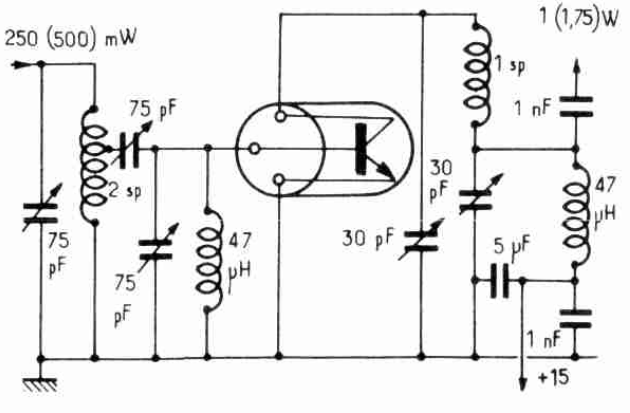


2 N 2883 2 N 2884

200 MHz

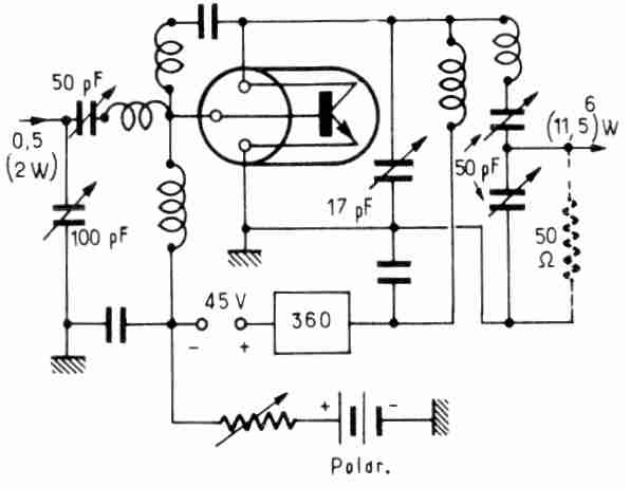
n-p-n Si Planar Epitax.

β > 20 (> 4 à 100 MHz)



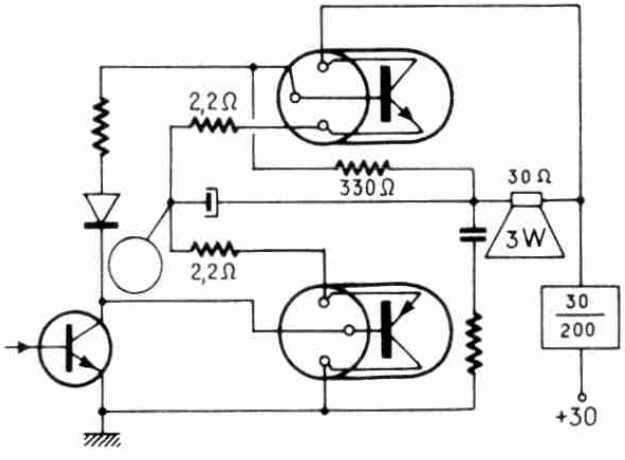
2N 2887 n-p-n Si

β = 50
GP = 9 dB
100 MHz triple diffusion



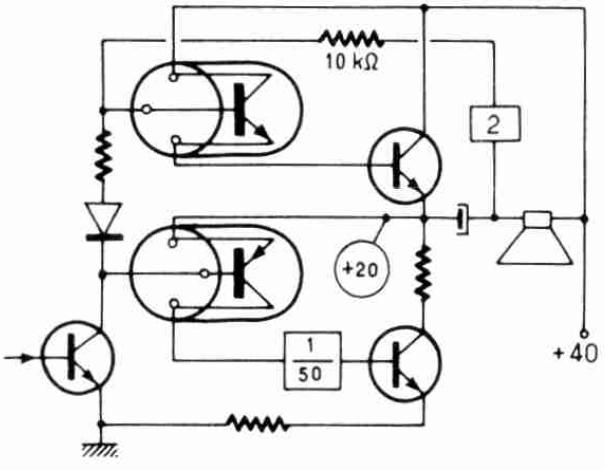
2 N 2904 p-n-p
2 N 2218 n-p-n Si
P

β = 40...120
f_t > 200 MHz



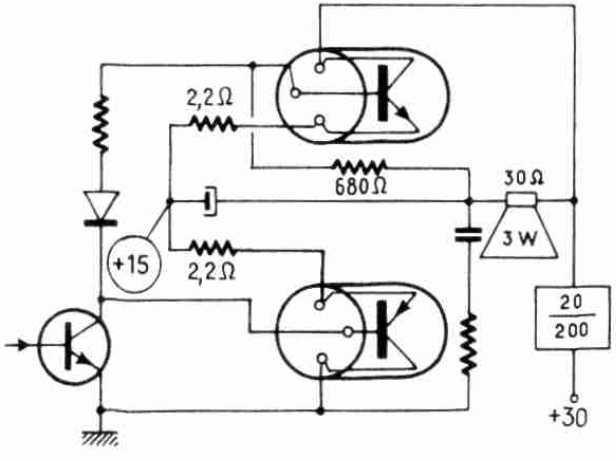
2 N 2904 p-n-p
2 N 2410 n-p-n
BF

β = 40...120



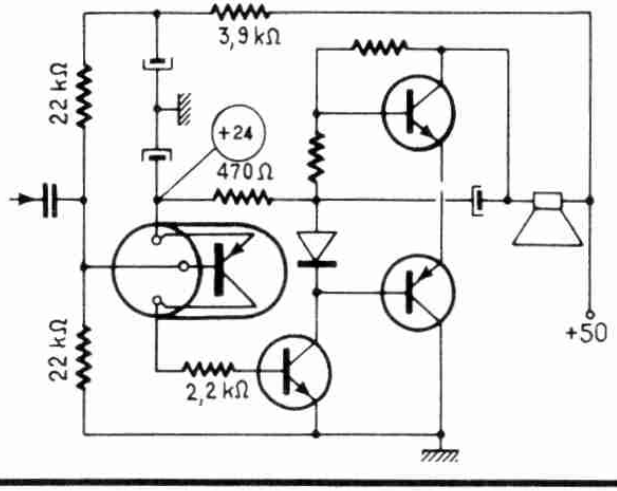
2 N 2905 p-n-p
2 N 2219 n-p-n Si
P

β = 100...300



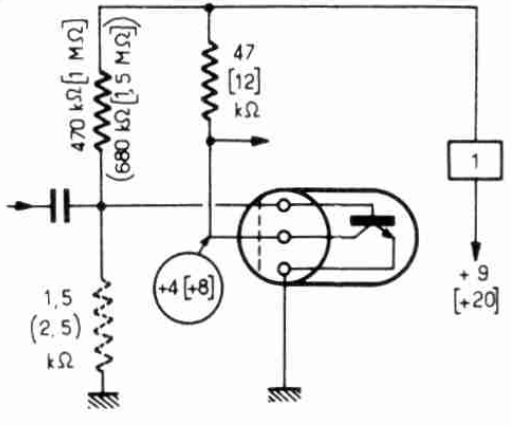
2 N 2906 p-n-p
(2 N 2907) Si
BF

β = 40.... 120
(100...300)



2N2921 n-p-n Si
(2 N 2922) Planar
B.F

β = 35...70
(55...110)
F_b = 2,8 dB



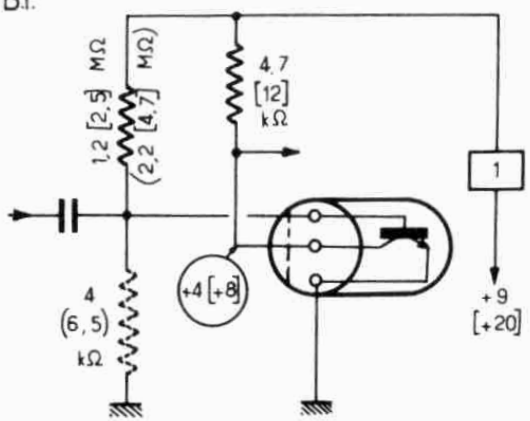
2N2923 (2N2924)

n-p-n Si Planar

β = 90...180 (150...300)

F_b = 2,8 dB

B.F.



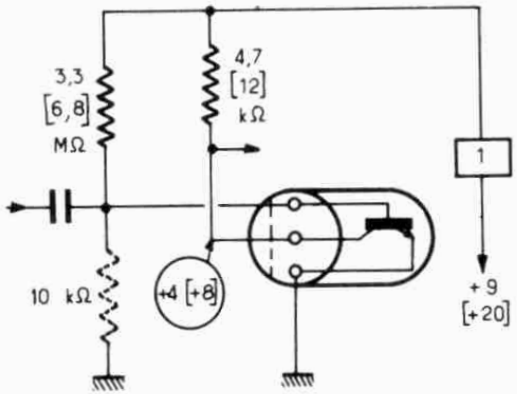
2N2925

n-p-n Si Planar

β = 235...470

F_b = 2,8 dB

B.F.



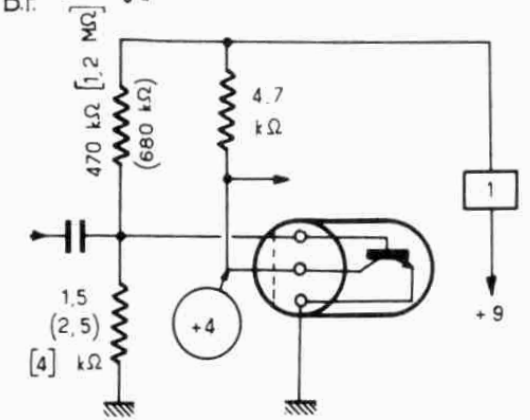
2N2926

marron (rouge) [orange]

n-p-n Si Planar

β = 35...70 (55...110) [90...180]

B.F.



2N2926

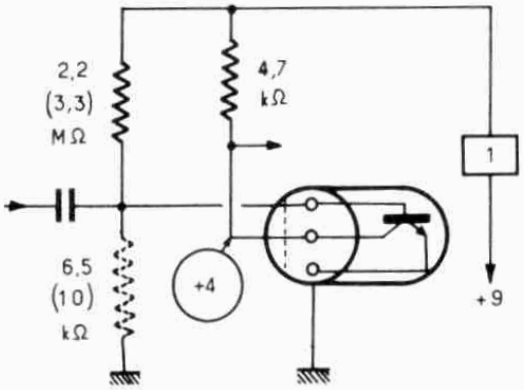
jaune (vert)

n-p-n Si Planar

β = 150...300 (235...470)

F_b = 2,8 dB

B.F.



2N2927

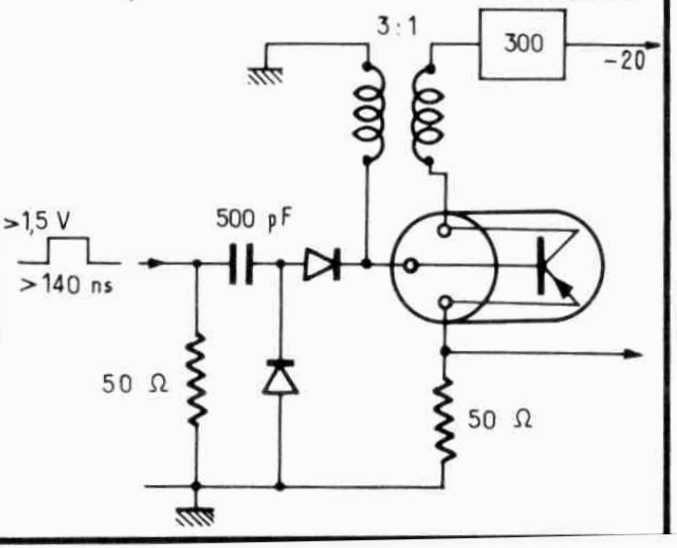
Osc. bloqué

p-n-p Si Planar Epitax.

β = 30...130

t_r = 40 ns

t_f = 20 ns

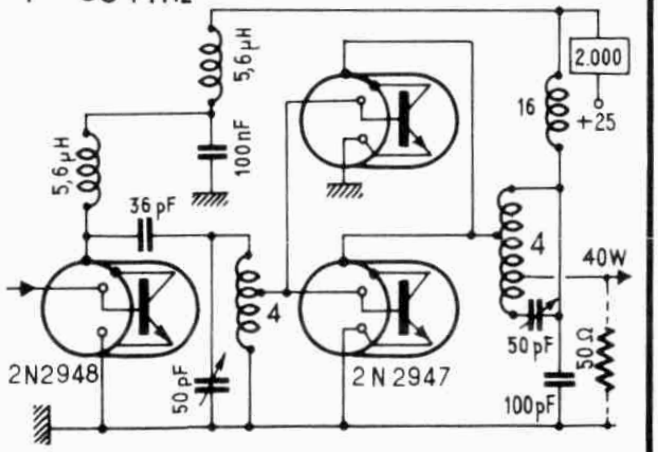


2N 2947 (2N 2948)

n-p-n Si

β = 25.... 35 (2,5....100)

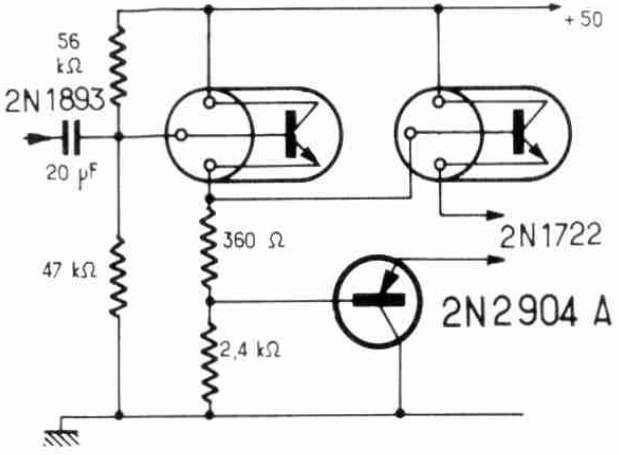
P 50 MHz



2N2988

n-p-n Si $\beta = 25 \ldots 75$

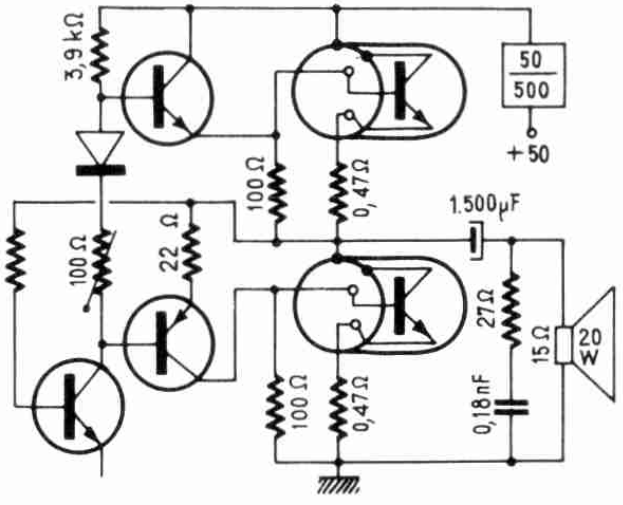
BF



2N3055

P

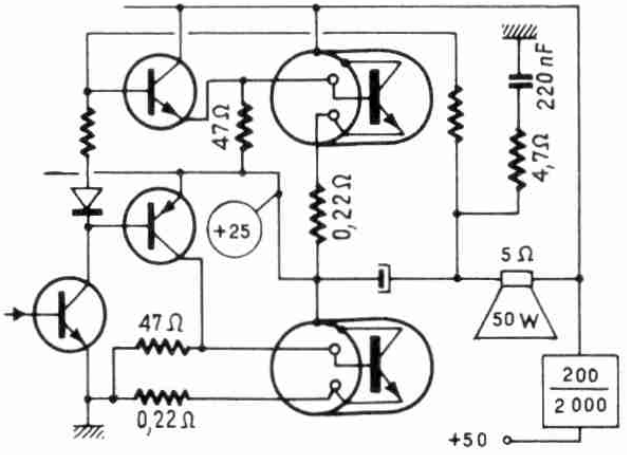
n-p-n Si $\beta = 20 \ldots 70$



2N3055

P

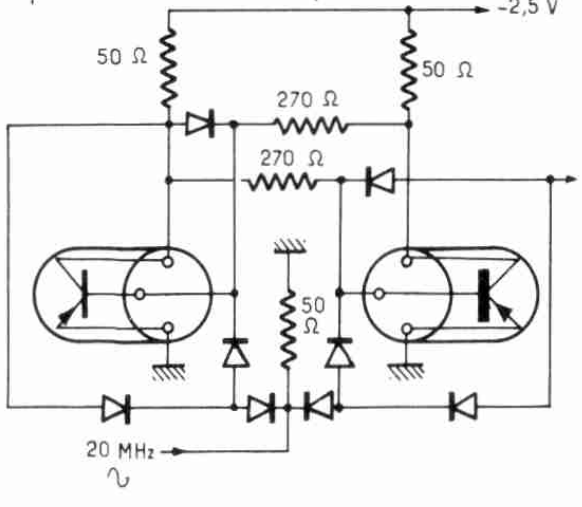
n-p-n Si $\beta = 20 \ldots 70$



2N3073

Compt. 20 MHz Planar Epitax.

p-n-p Si $\beta = 30 \ldots 130$ (>1,3 à 100 MHz)

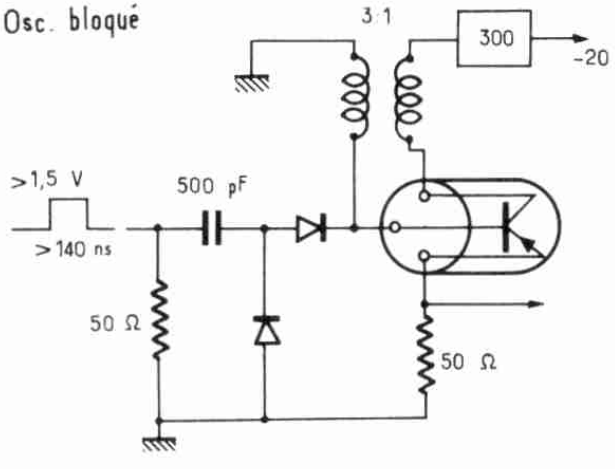


2N3120
2N3121

Osc. bloqué

p-n-p Si Planar Epitax.

$\beta = 30 \ldots 130$
$t_r = 40$ ns
$t_f = 20$ ns

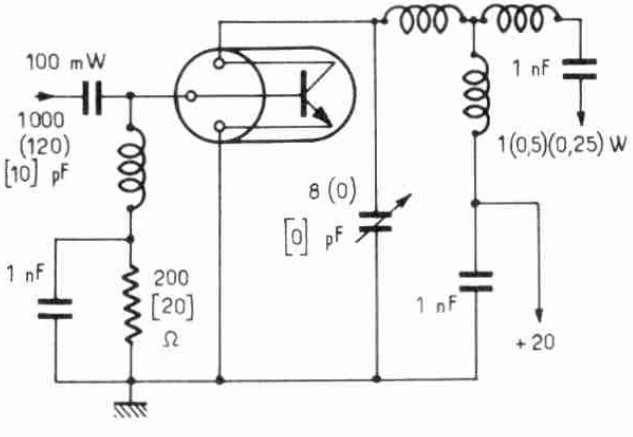


2N3137

125 (250) [500] MHz

n-p-n Si Planar Epitax.

$\beta = 20 \ldots 120$ (>5 à 100 MHz)
GP = 10 (7) [4] dB

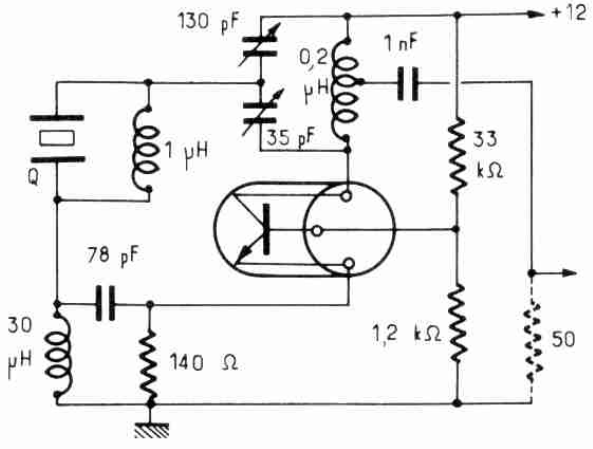


2 N 3137

n-p-n Si Planar Epitax

β = 20 ... 120 (>5 à 100 MHz)

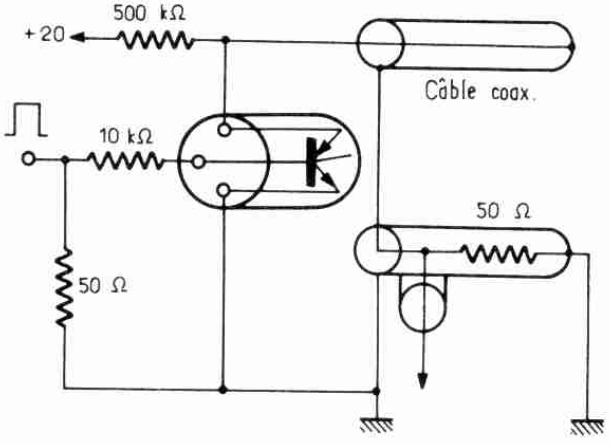
Osc. 80 MHz



2 N 3255

Gén. impuls.

t_r = 18 ... 28 ns



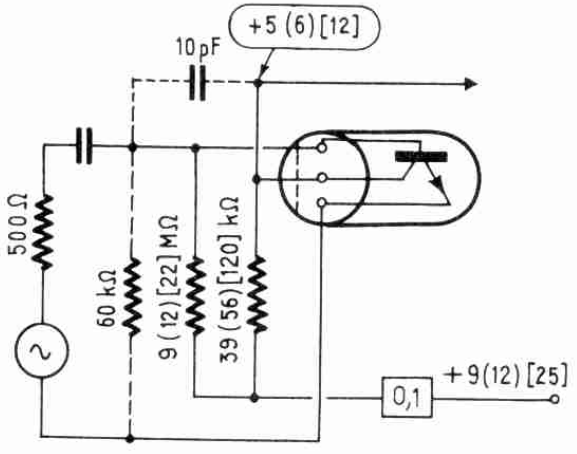
2 N 3391

BF

n-p-n Si

β = 170 à Ic = 0,1 mA

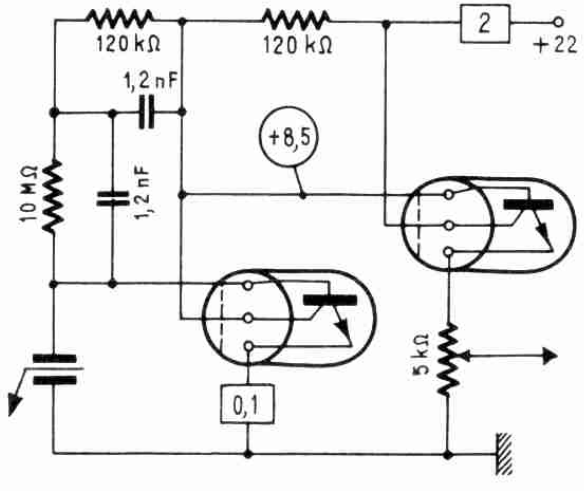
F_b = 1,9 dB



2 N 3392 (95), [96]

P.U. Piézoél. n-p-n Si

β = 150 ... 500 (150 ... 800) [90 ... 800]



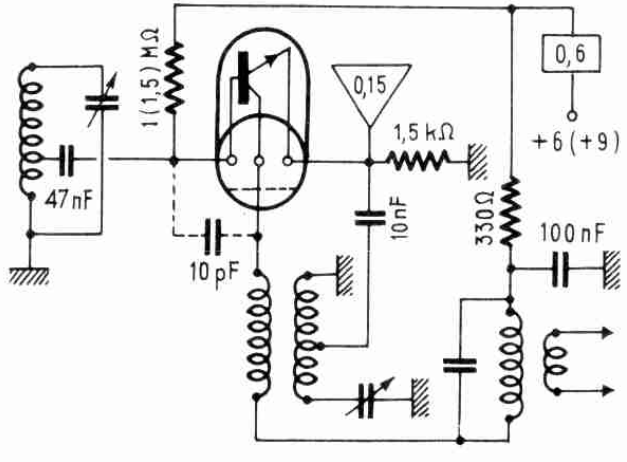
2N3393

Conv. <2 MHz

n-p-n Si

β = 90 ... 400

GP = 30 ... 35 dB



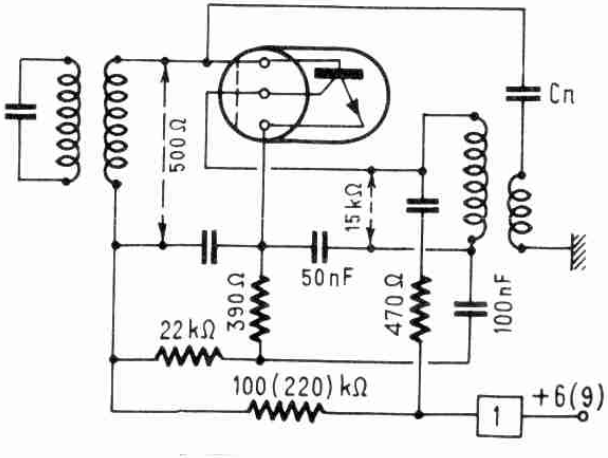
2N3393 (2N3394)

MF 470 kHz

n-p-n Si

β = 90 ... 400 (55 ... 300)

GP = 37 ... 41 dB

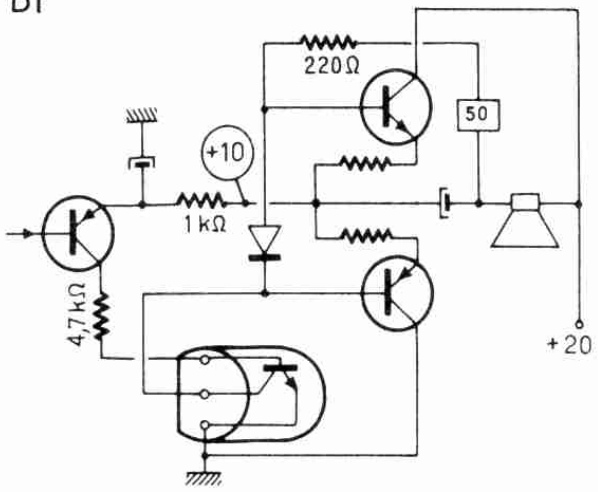


2N3402 (2N3403)

n-p-n Si

β = 75....225 (180...540)

BF

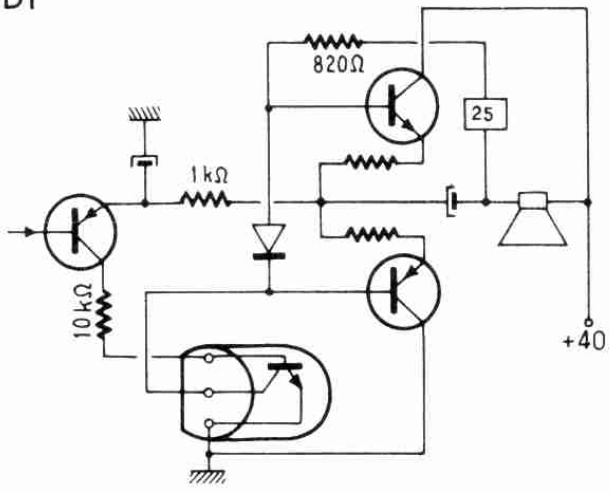


2N3404 (2N3405)

n-p-n Si

β = 75....225 (180...540)

BF

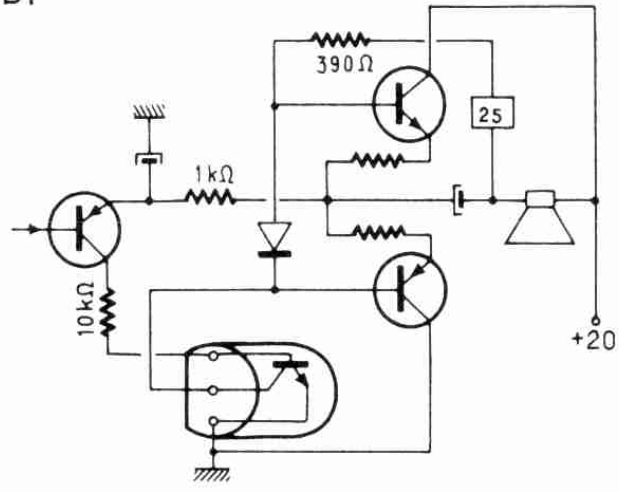


2N3414 (2N3415)

n-p-n Si

β = 75....225 (180...540)

BF

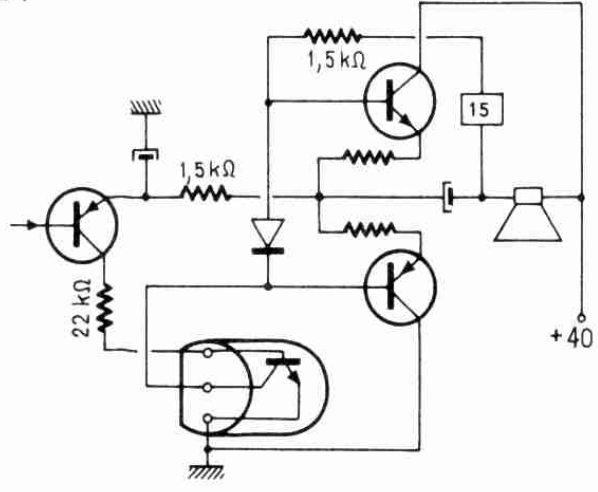


2N3416 (2N3417)

n-p-n Si

β = 75....225 (180...540)

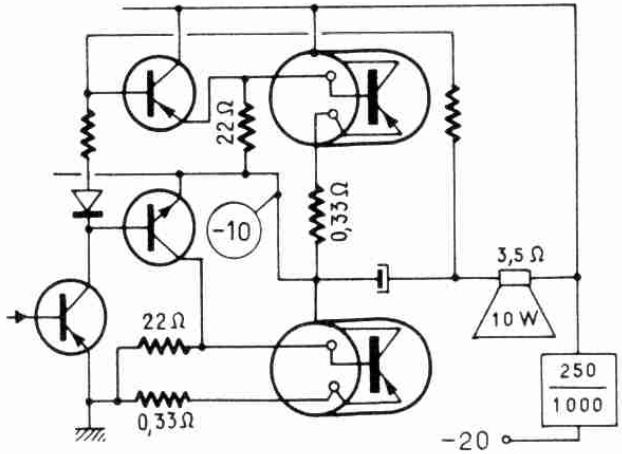
BF



2N3611 (2N3613)

β = 40...100 (60...150)

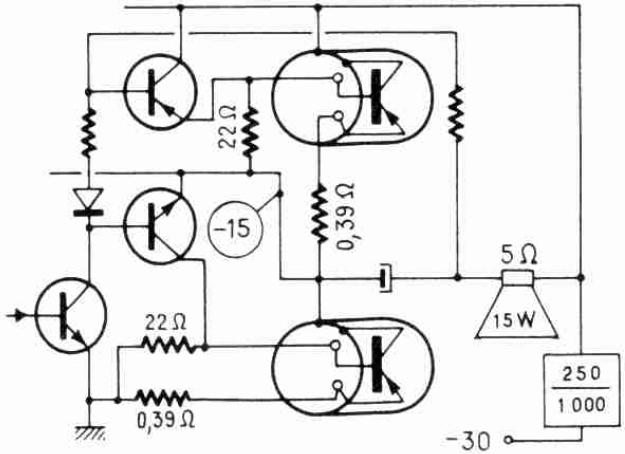
P



2N3612 (2N3614)

β = 40...100 (60...150)

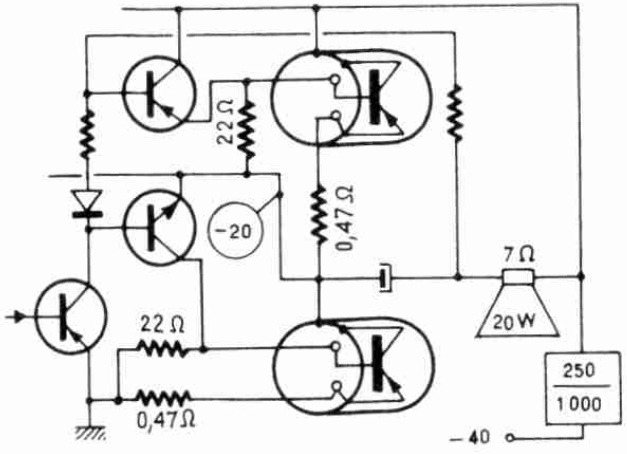
P



2N 3615 (2N 3617)

P

β = 40...100 (60...150)

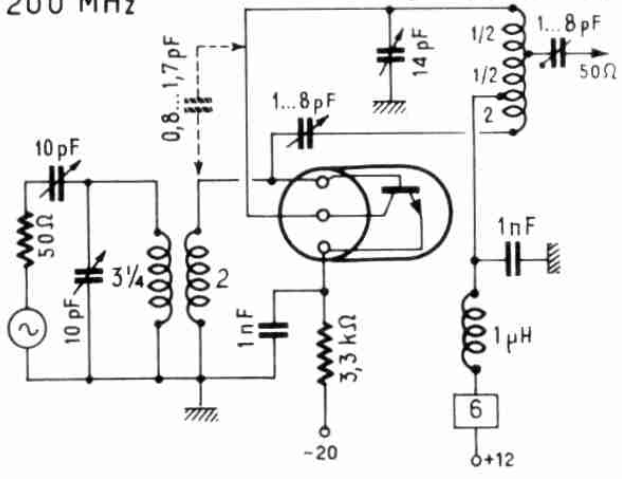


2N 3662 (2N 3663)

200 MHz

n-p-n Si

β = 20... 75
f_t = 0,7... 2,1 GHz
GP = 16 (19 dB)
F_b = 4 dB (60 MHz)

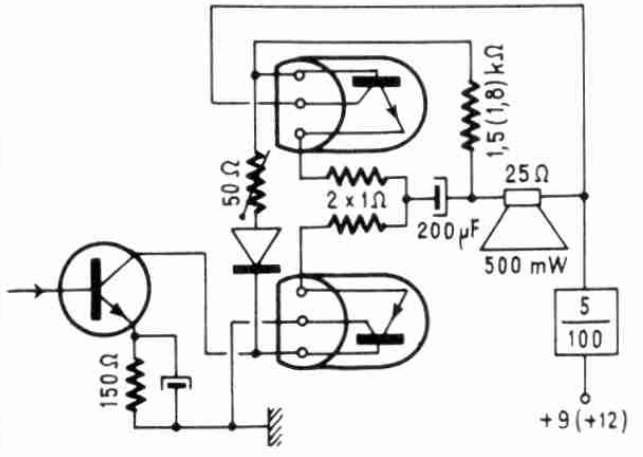


2N3702 2N3704

BF

p-n-p
n-p-n
Si

β = 60...300

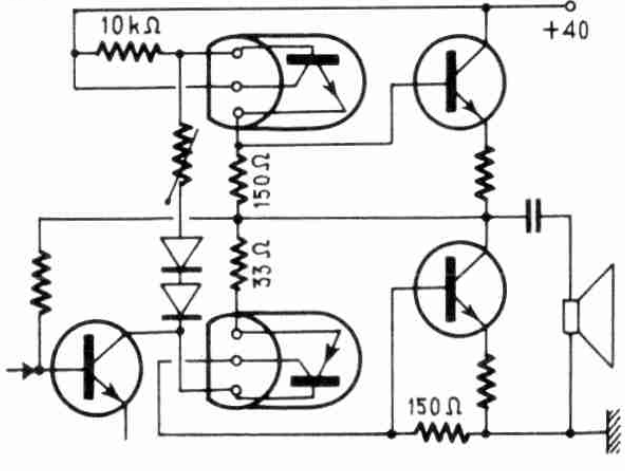


2N3703 2N3705

BF

p-n-p
n-p-n
Si

β = 30....150

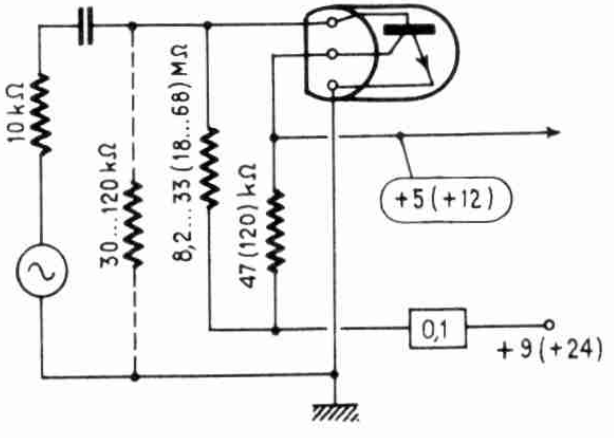


2N 3707

BF

n-p-n Si

β = 100...550
F_b = 1,9 dB

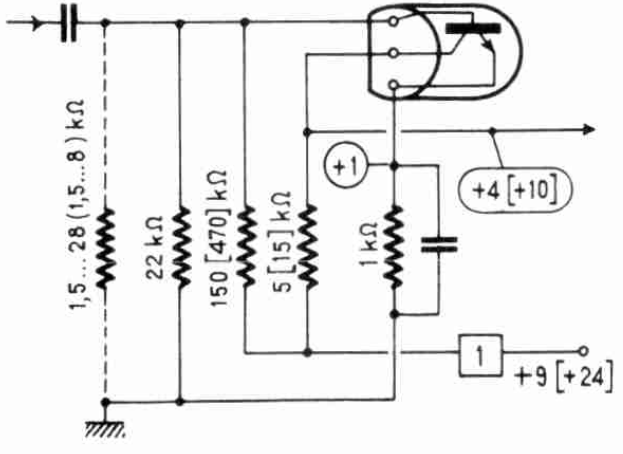


2N3708 (2N3709)

BF

n-p-n Si

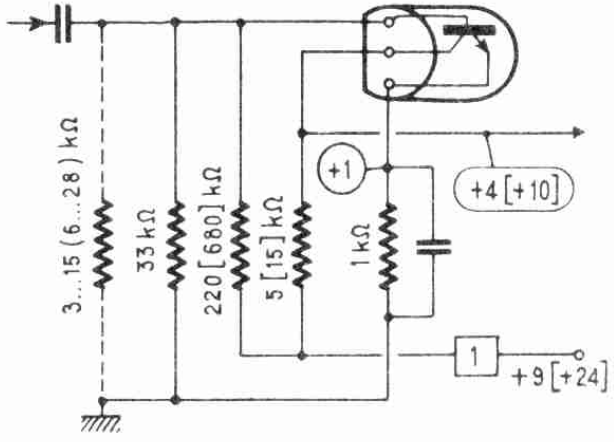
β = 45...800 (45...250)



2N3710 (2N3711)

n-p-n Si

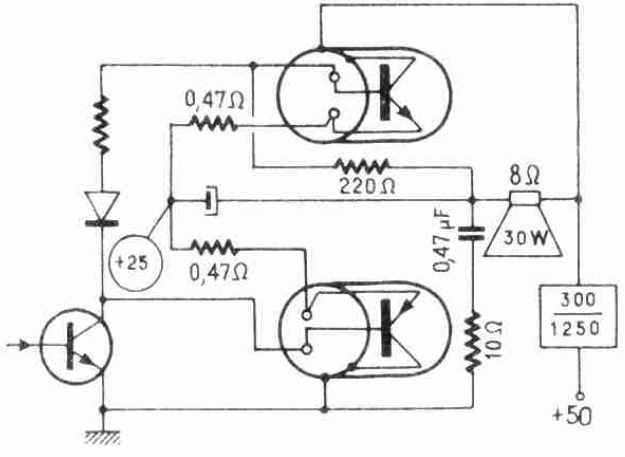
$\beta = 90...450$ (180...800)



2N3715 2N3791 P

n-p-n p-n-p Si

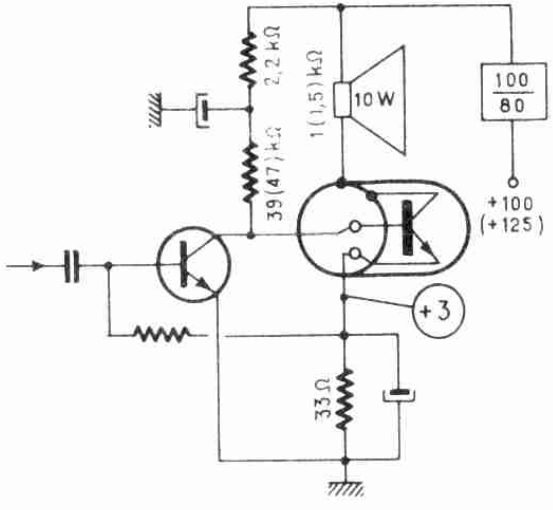
$\beta > 30$ à $I_c = 3A$
$f_t > 4$ MHz



2N3738 (2N3739)

n-p-n Si

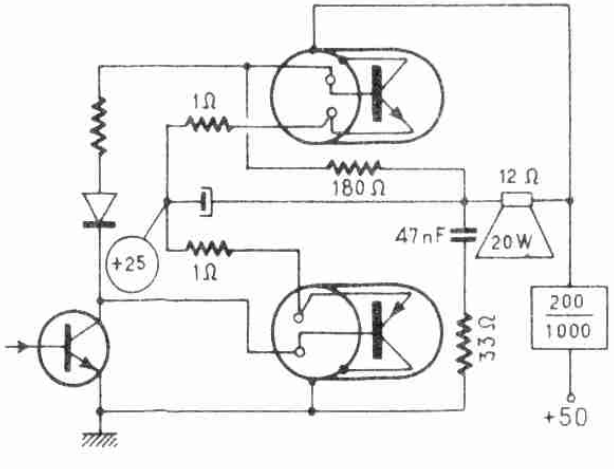
$\beta = 40...200$
$f_b > 15$ MHz



2N3740 2N3766 P

p-n-p n-p-n Si

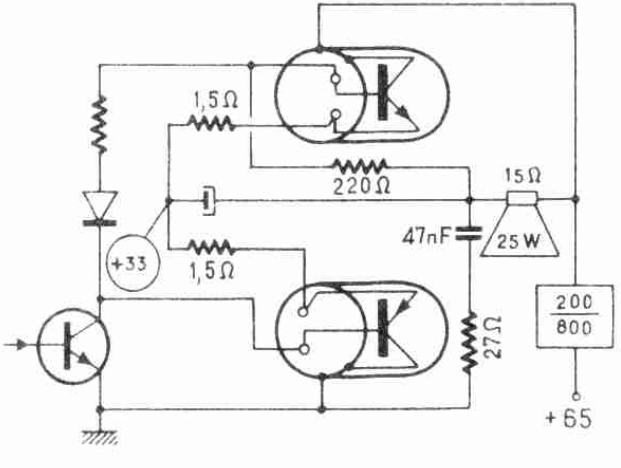
$\beta = 30...100$
$f_t > 15$ MHz



2N3741 2N3767 P

p-n-p n-p-n Si

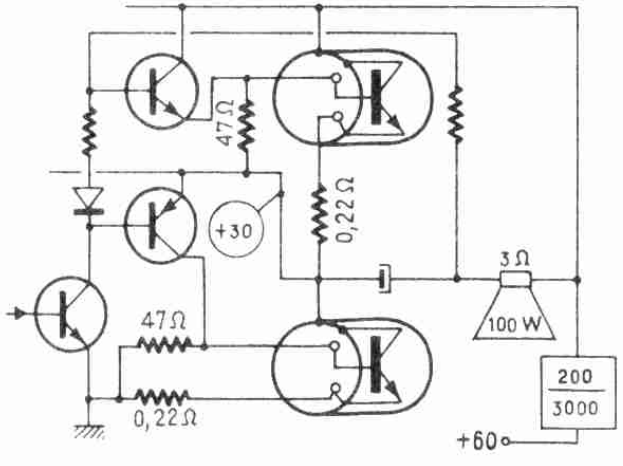
$\beta = 30...100$
$f_t > 15$ MHz



2N3772 P

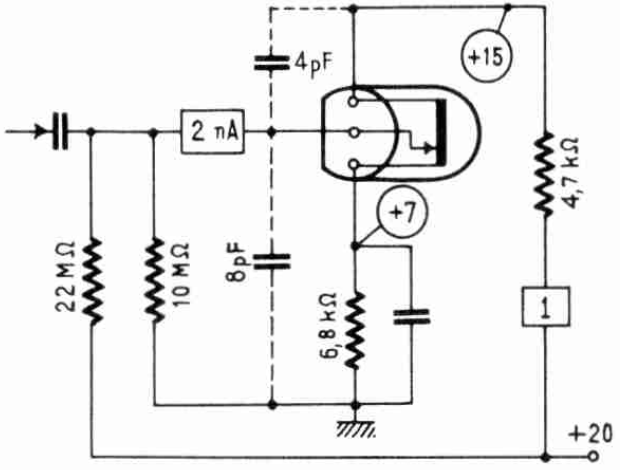
n-p-n Si

$\beta = 15...60$



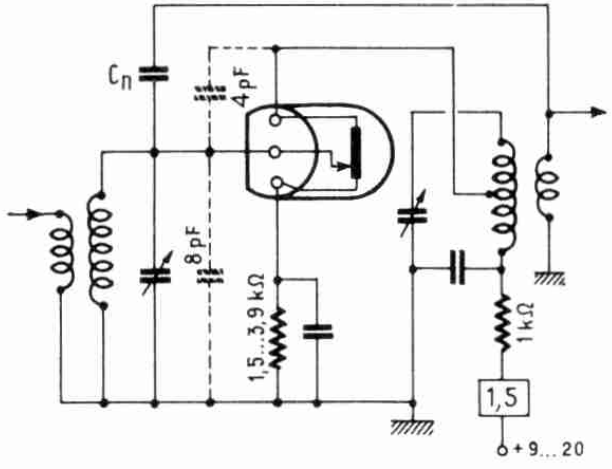
2N3819 FET BF Canal N

$\mathcal{S}$ = 2...6,5mA/V
V_{GSO} < −8 V
ρ < 20 kΩ



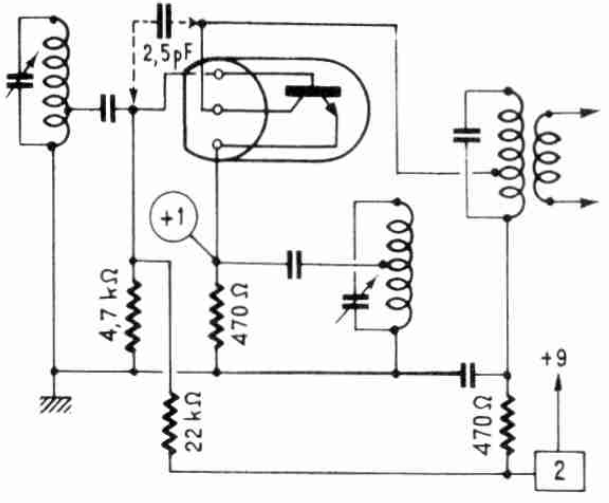
2N3819 FET Si HF Canal N

$\mathcal{S}$ = 2...6,5 mA/V
V_{GSO} < −8 V
I_{DSS} = 2...20 mA
ρ < 20 kΩ



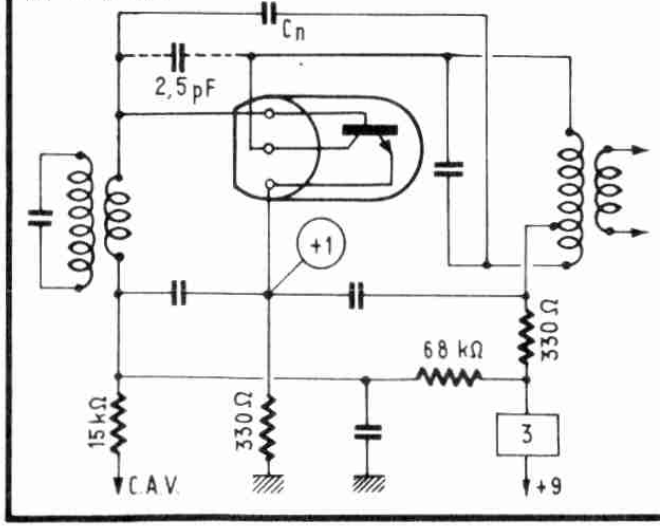
2N3825 n-p-n Si Conv. < 2 MHz

β > 20 (2...8 à 100 MHz)
F_b < 5,5 dB



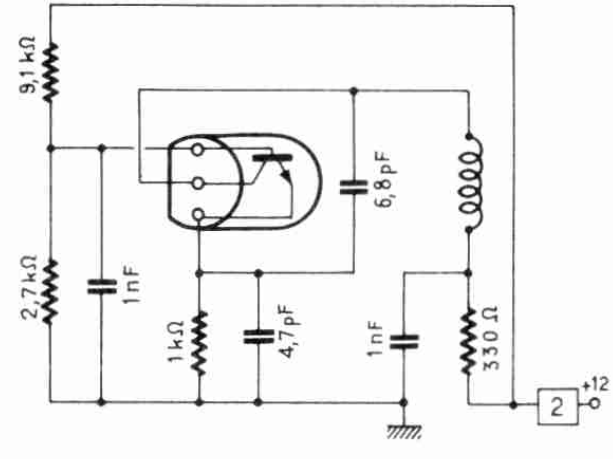
2N3826 (2 N 3827) n-p-n Si MF 470 kHz

β = 40... 160 (100...400)
GP = 42 (45) dB



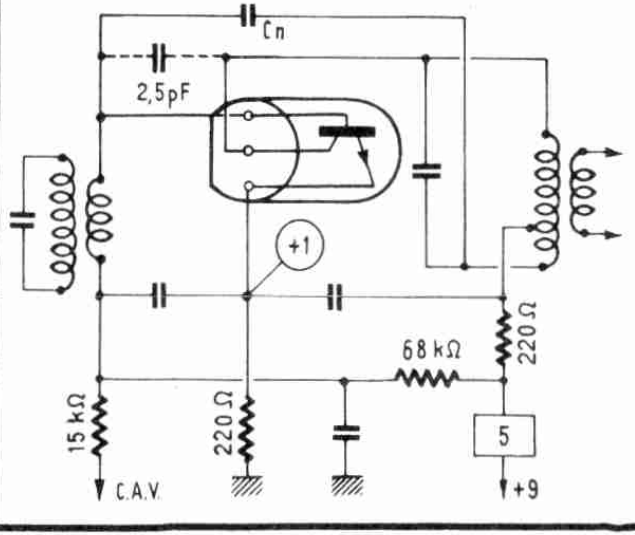
2N3826 n-p-n Si Osc. 100 MHz

β = 40.... 160
f_t = 200... 800 MHz



2N3827 n-p-n Si 10,7 MHz

β = 100...400
GP = 34 dB

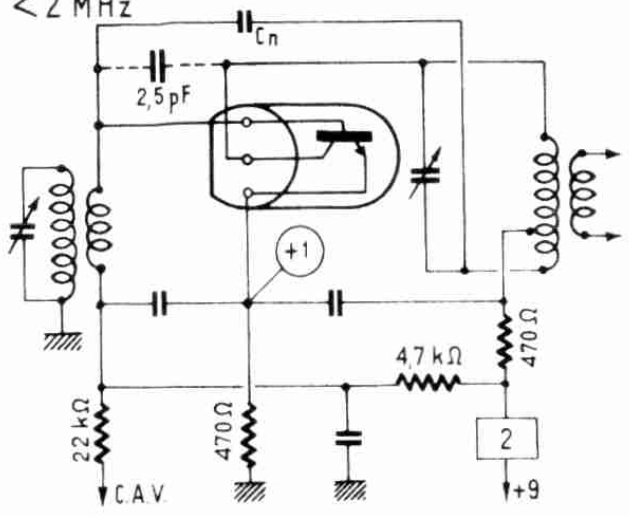


2N3843A (2N3845A)

n-p-n Si

β = 20...40 (60...120)

< 2 MHz

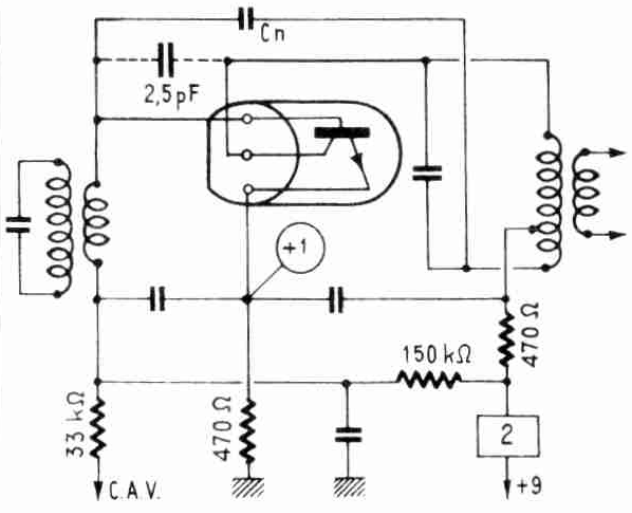


2N3860

MF 470 kHz

n-p-n Si

β = 150...300

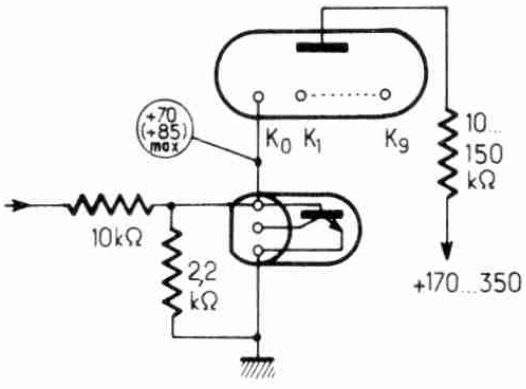


2N3877 (2N3877A)

Néon

n-p-n Si

β > 20.....250



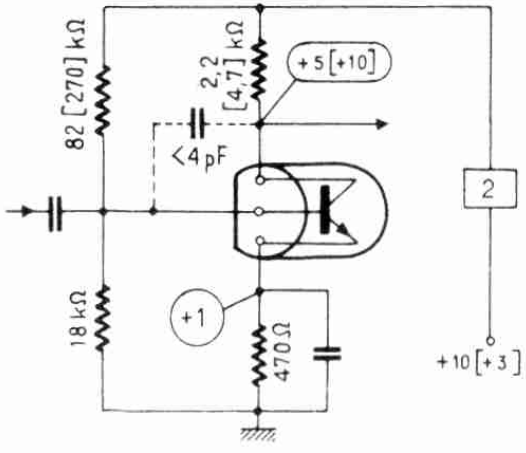
2N3903 (2N3904)

BF

n-p-n Si

β = 50....150 (100...300)

f_t > 250 MHz



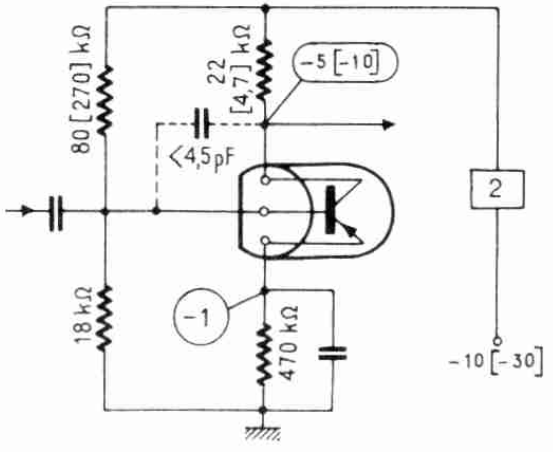
2N3905 (2N3906)

BF

p-n-p Si

β = 50....150 (100...300)

f_t > 250 MHz



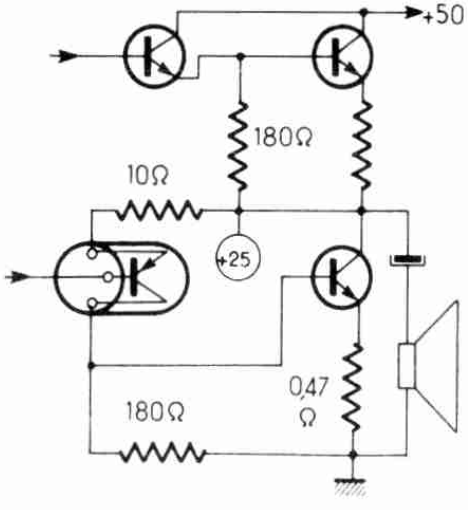
2N4036

BF

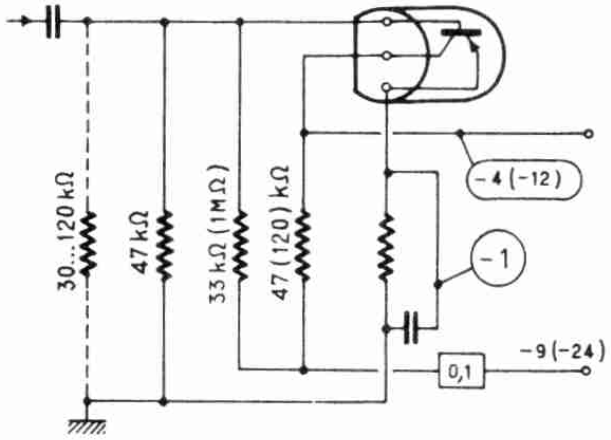
n-p-n Si

β = 14....140

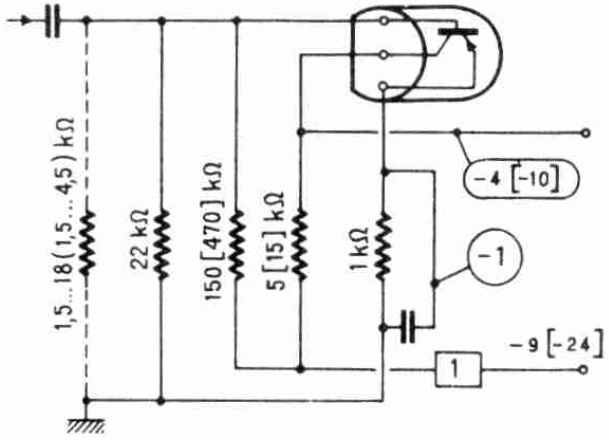
f_T > 60MHz



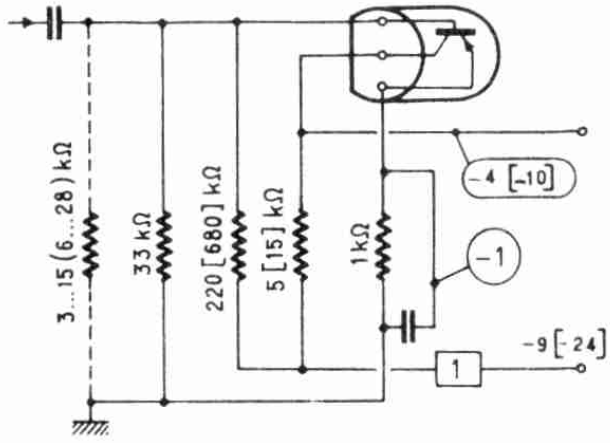
2N4058
p-n-p Si
BF
β = 100...400
F_b = 1,7 (<5) dB



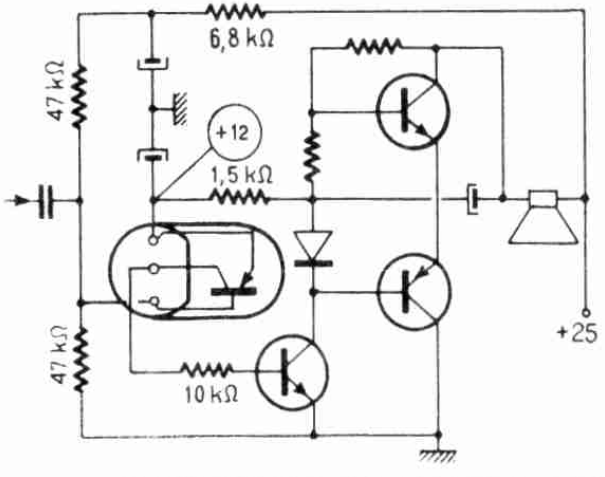
2N4059 (2N4060)
p-n-p Si
BF
β = 45...660 (45...165)



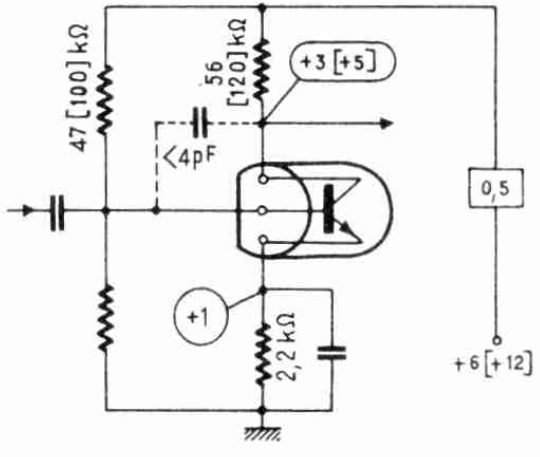
2N4061 (2N4062)
p-n-p Si
BF
β = 90.... 450 (180...800)



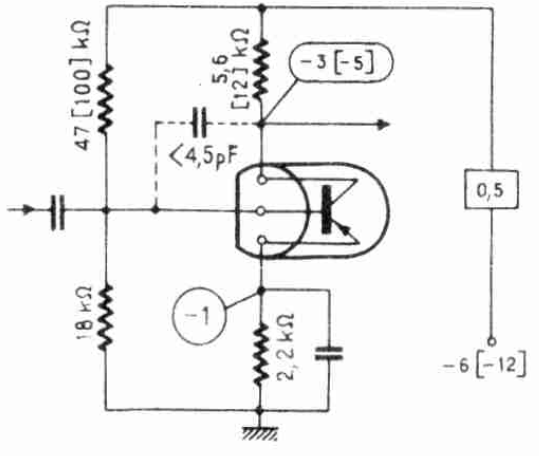
2N4061
p-n-p Si
BF
β = 90...450



2N4123 (2N4124)
n-p-n Si
BF
β = 50.... 150 (120...360)
F_b < 6 dB



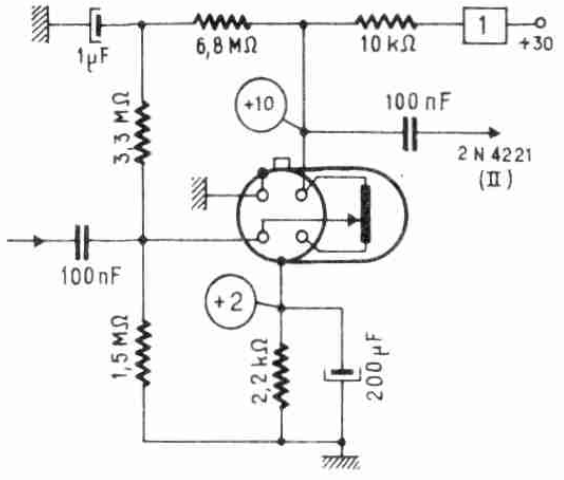
2N4125 (2N4126)
p-n-p Si
B
β = 50...150 (120...360)
f_t > 200 MHz
F_b < 5 dB



2N4221 BF(I)

FET Si Canal N

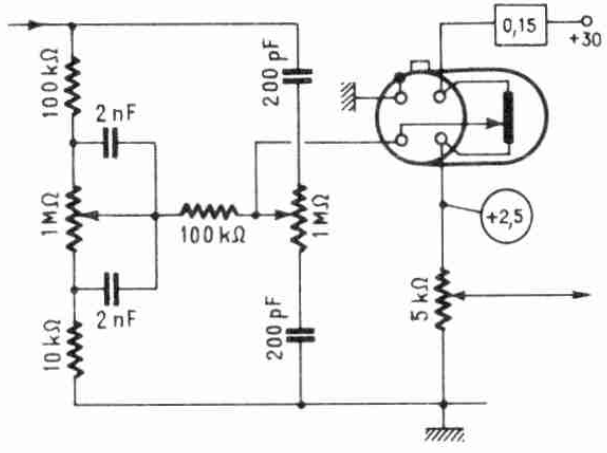
$\mathcal{S}$ = 2...5 mA/V
ρ = 50 kΩ
I_{DSS} = 2...6 mA



2N4221 BF(II)

FET Si Canal N

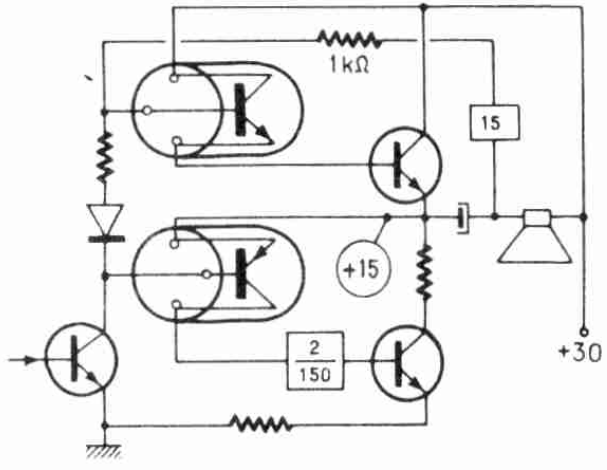
$\mathcal{S}$ = 2...5 mA/V
ρ > 50 kΩ
I_{DSS} = 2...6 mA



2N4234 2N4237 BF

p-n-p n-p-n Si

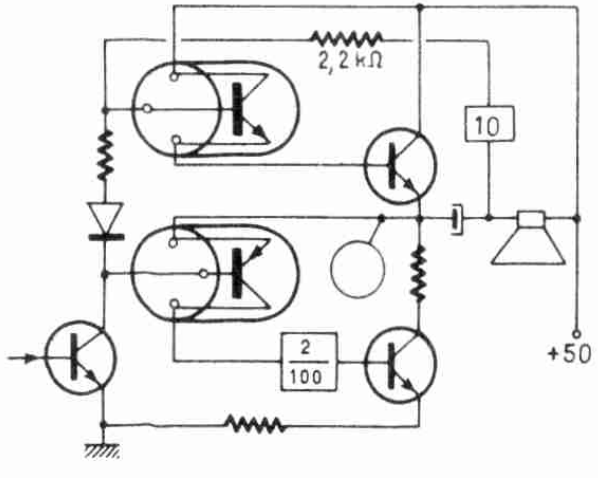
β = 30...150
f_t > 3 MHz



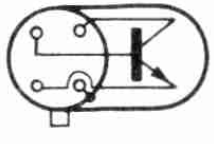
2N4235 2N4238 BF

p-n-p n-p-n Si

β = 30...150
f_t = 3 MHz



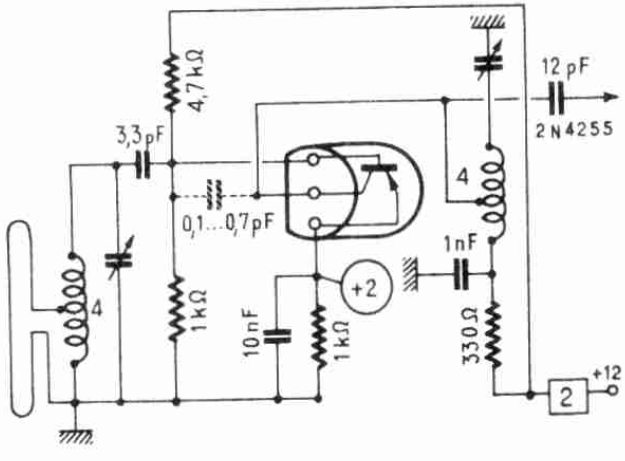
2N4252 = 2N4254 2N4253 = 2N4255



2N4254 100 MHz

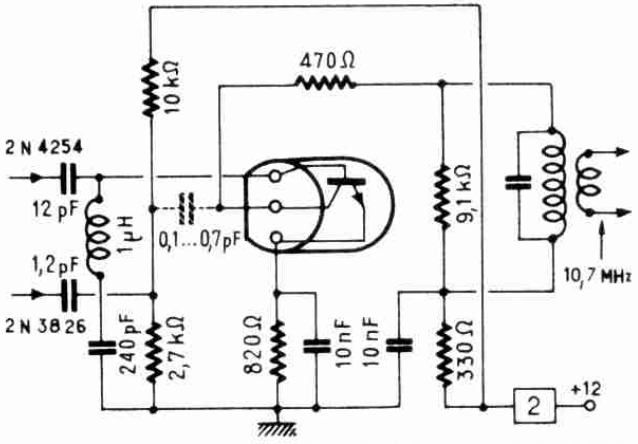
n-p-n Si

β > 50
f_t = 0,6...1,4 GHz
F_b = 2,5 dB



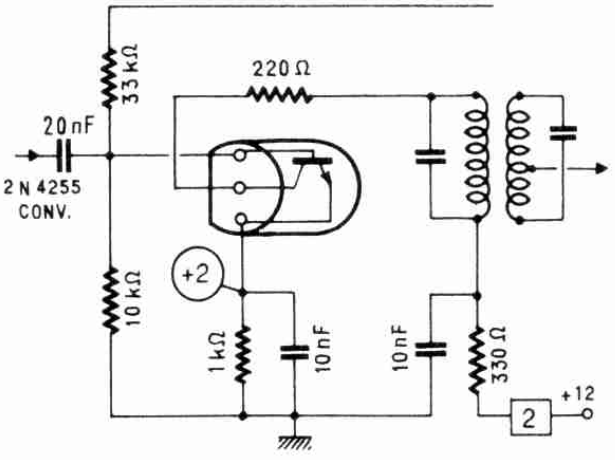
2N 4255
n-p-n Si
Conv. 100 MHz

β = 30... 150
f_t = 0,6... 1,4 GHz
GP (2N4254 + 2N4255) = 25 dB



2N 4255
10,7 MHz

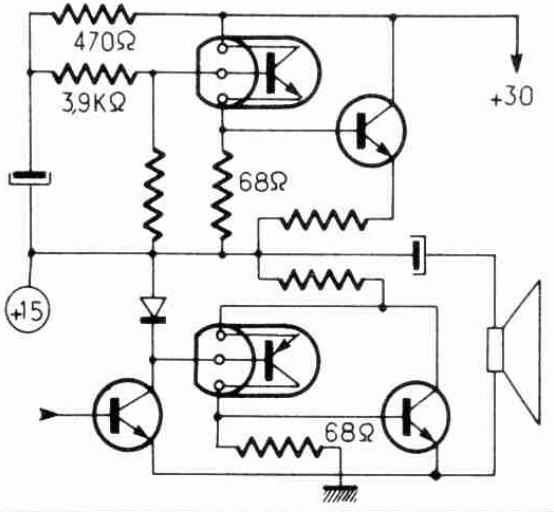
β = 30... 150
f_t = 0,6...1,4 GHz



2N4400
2N4402
BF

n-p-n Si
p-n-p Si

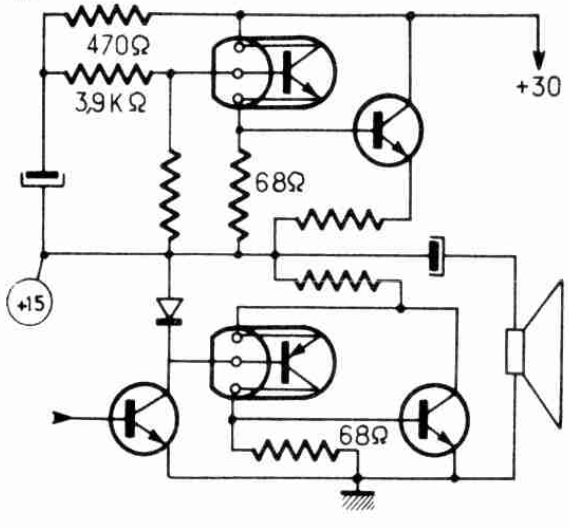
β = 50.....150
f_T >150 MHz



2N4401
2N4403
BF

n-p-n Si
p-n-p Si

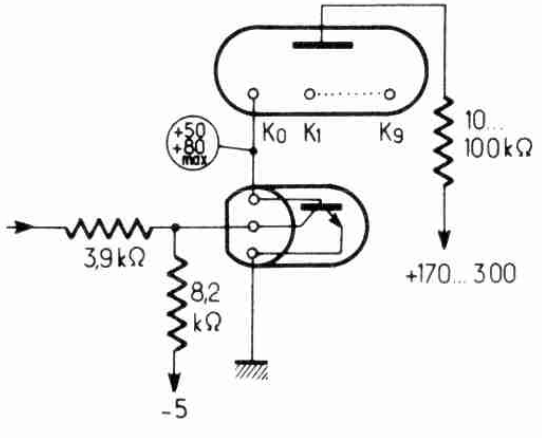
β = 100.....300
f_T >200MHz



2N4409
(2N4410)
Néon

n-p-n Si

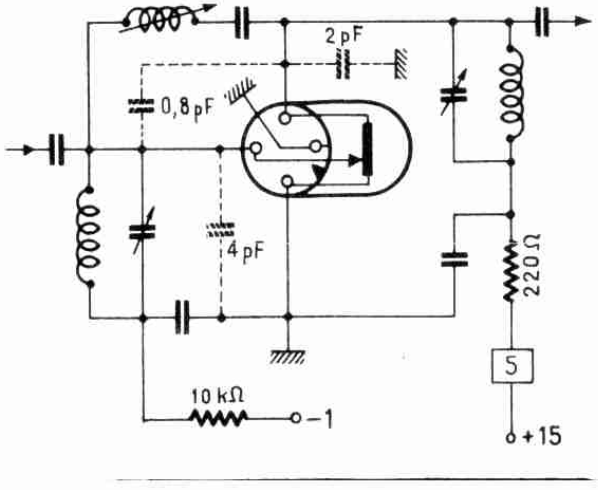
β = 60.....400



2N 4416
VHF

FET Si
Canal N

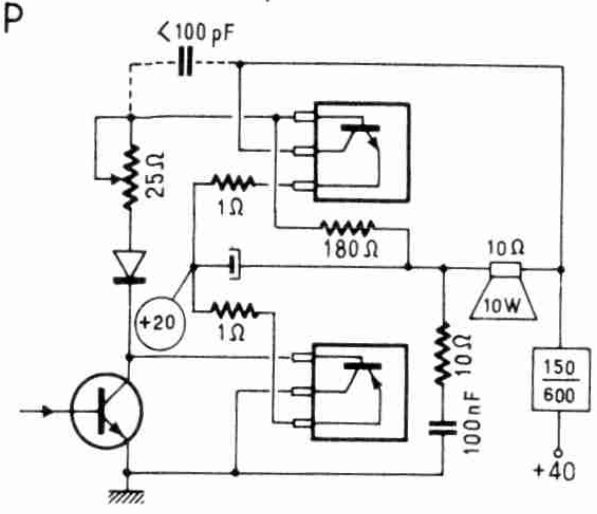
S = 4,5...7,5 mA/V
I_{DSS} < 15 mA



2N4918 / 2N4921 P

p-n-p / n-p-n Si

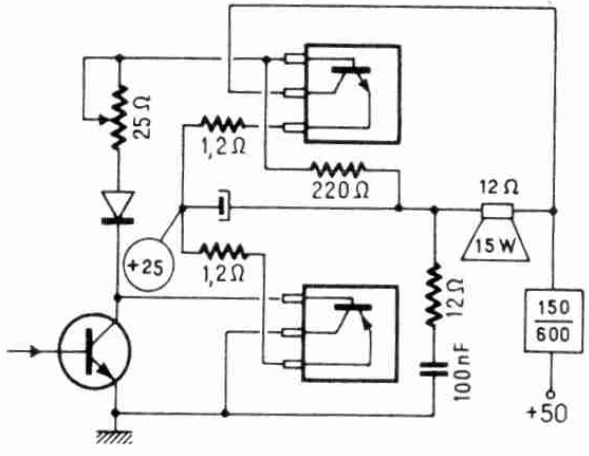
$\beta = 20...100$
$f_t > 3$ MHz



2N4919 / 2N4922 P

p-n-p / n-p-n Si

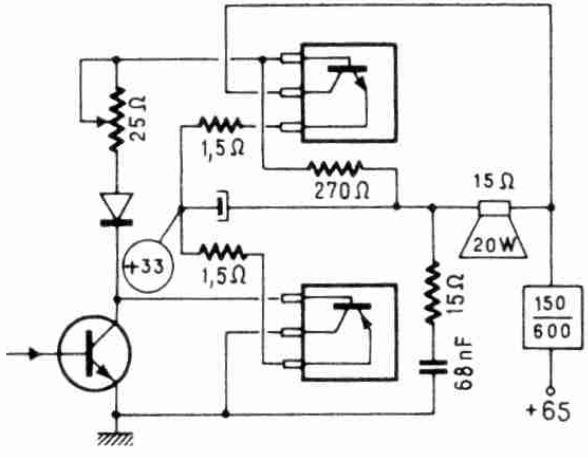
$\beta = 20...100$
$f_t > 3$ MHz



2N4920 / 2N4923 P

p-n-p / n-p-n

$\beta = 20...100$
$f_t > 3$ MHz

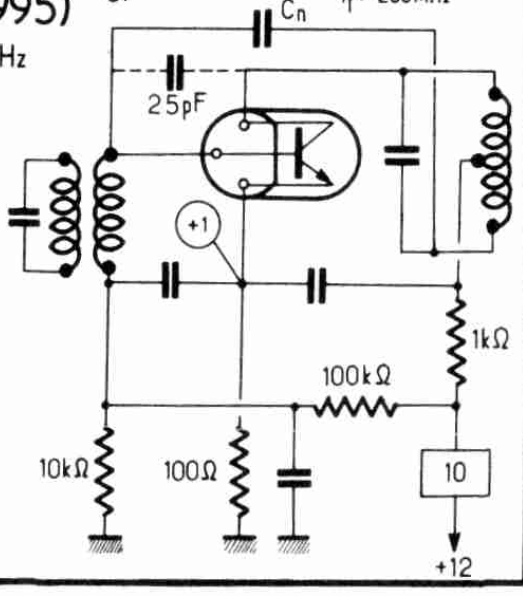


2N4994 (2N4995)

n-p-n Si

10,7 MHz

GP = 42 (45) dB (470 kHz)
GP = 34 dB (10,7 MHz)
$f_T > 200$ MHz

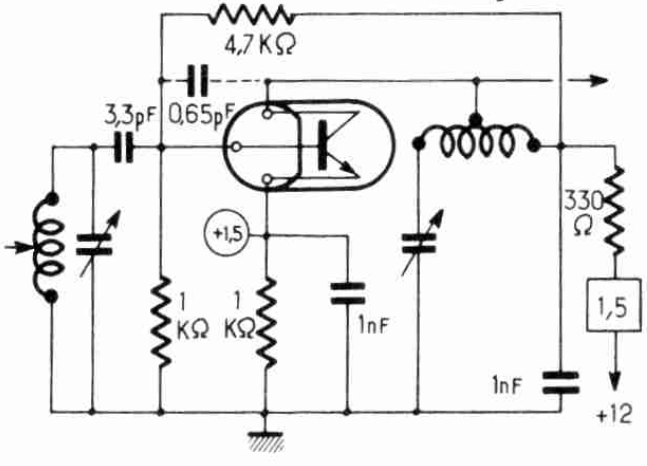


2N4996

n-p-n Si

100 MHz

$\beta > 50$
$f_T > 600$ MHz
$F_b = 2,5$ dB

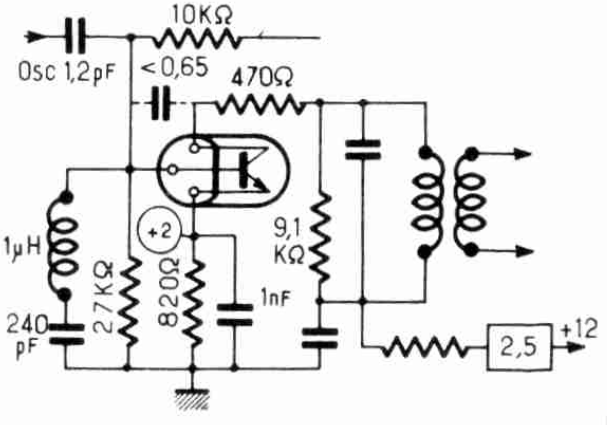


2N4997

Conv. 100 MHz

n-p-n Si

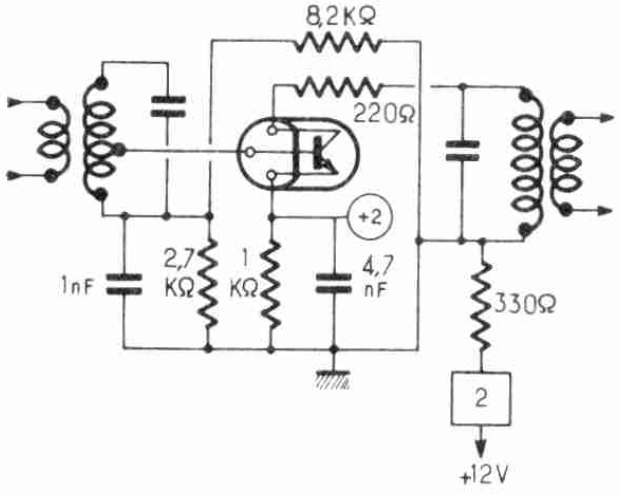
$\beta = 30.....150$
$f_T > 600$ MHz



2N4997

10,7 MHz

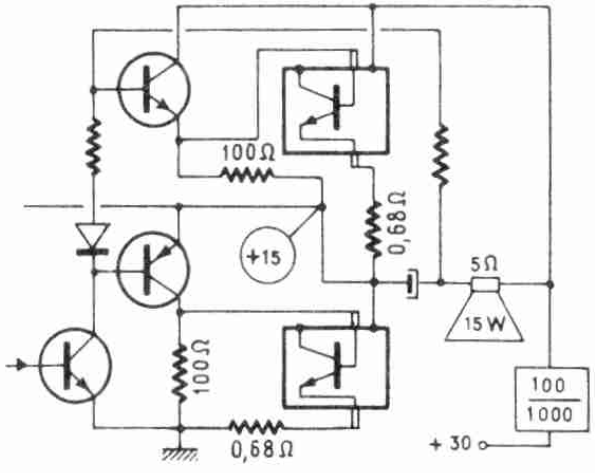
ß=30.....150
f_T >600MHz
GP=23 dB



2N5034
2N5035
P

n-p-n Si

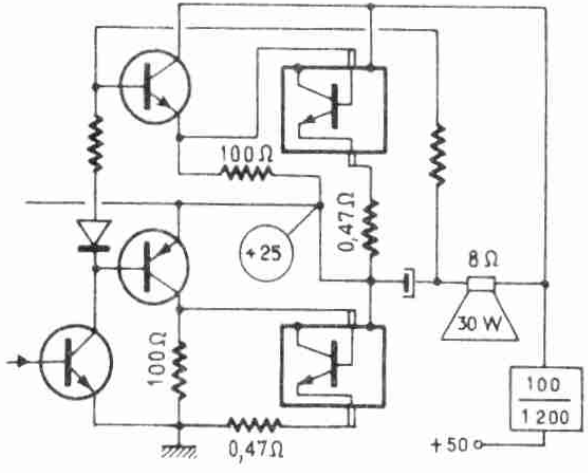
β>20



2N5036
2N5037
P

n-p-n Si

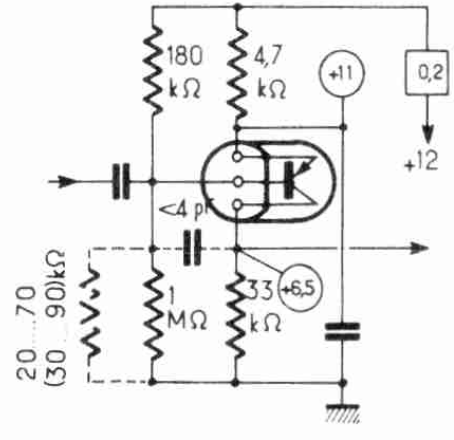
β>20



2N5086
(2N5087)
BF

p-n-p Si

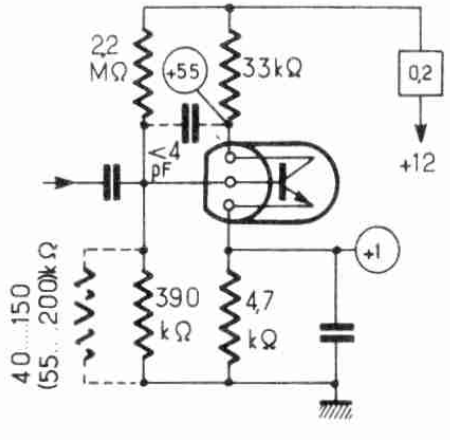
ß=150.....500
(250.....800)
F_b>3(2)dB



2N5088
(2N5089)
BF

n-p-n Si

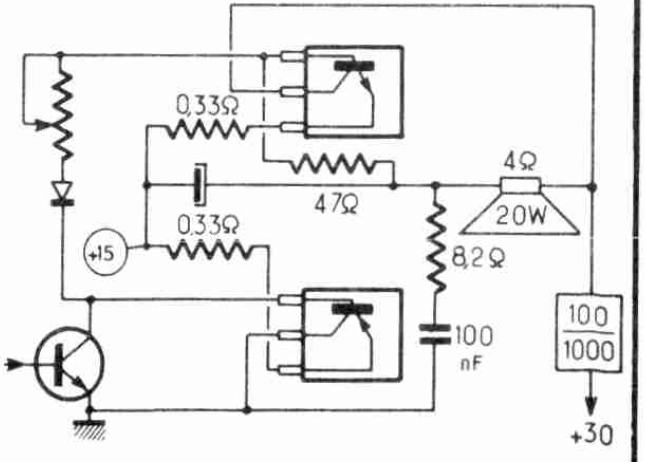
ß=350.....1400
(450.....1800)
F_b<3(2)dB



2N5190
2N5193
P

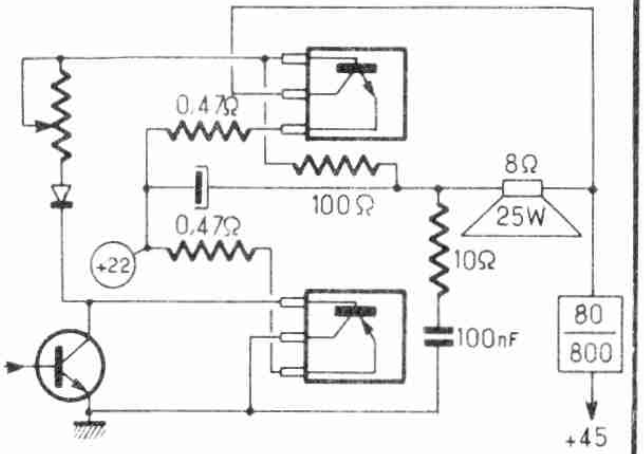
n-p-n Si
p-n-p Si

ß=25.....100
f_T>2 MHz



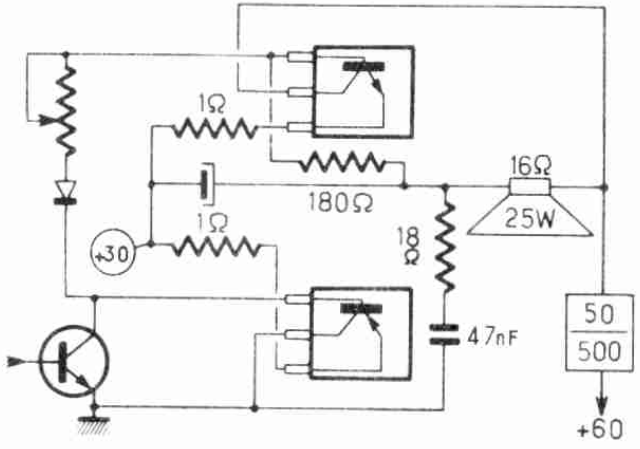
2N5191 n-p-n Si
2N5194 p-n-p Si
P

ß = 25.....100
f_T > 2 MHz



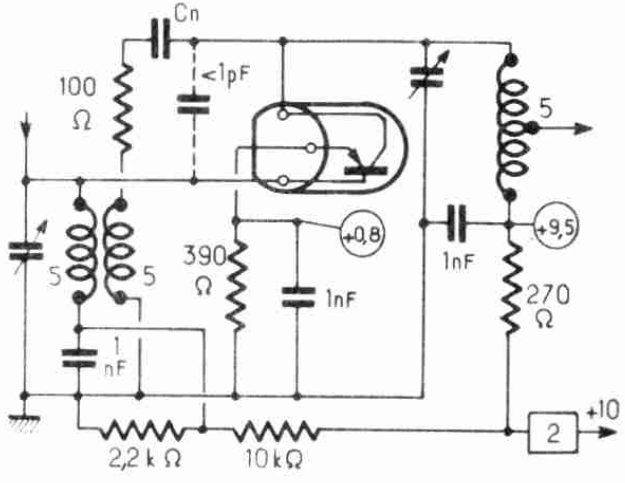
2N5192 n-p-n Si
2N5195 p-n-p Si
P

ß = 20.....80
f_T > 2 MHz



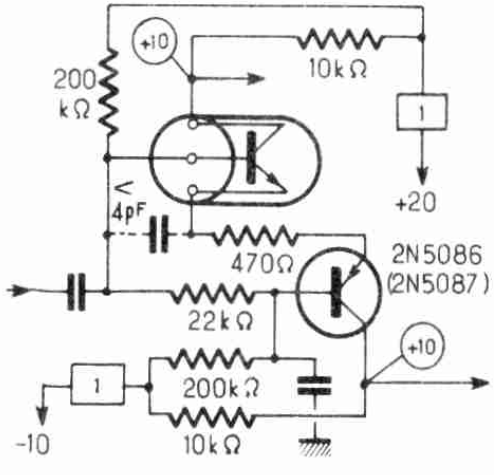
2N5208 p-n-p Si
100 MHz

ß = 20.....120
f_T > 300 MHz
F_b < 3 dB
GP > 22 dB



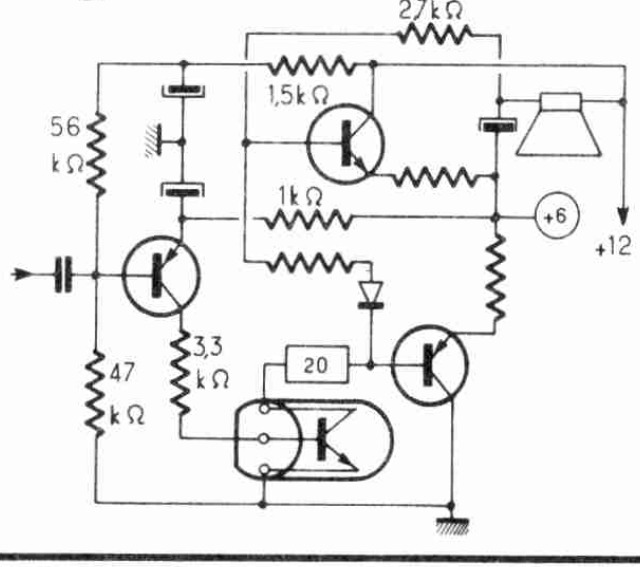
2N5209 (2N5210) n-p-n Si
BF

ß = 150.....600 (250.....900)
f_T > 30 MHz
F_b < 4 (≤ 3) dB



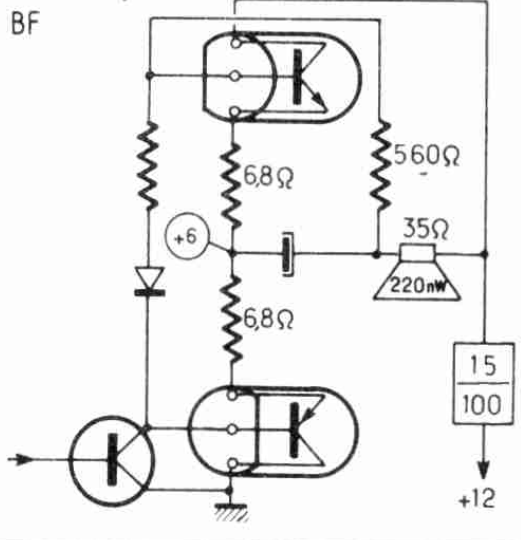
2N5219 n-p-n Si
BF

ß = 35.....500
F_T > 150 MHz



2N5220 (2N5221) n-p-n Si
p-n-p Si
BF

ß = 35.....500
F_T > 150 MHz



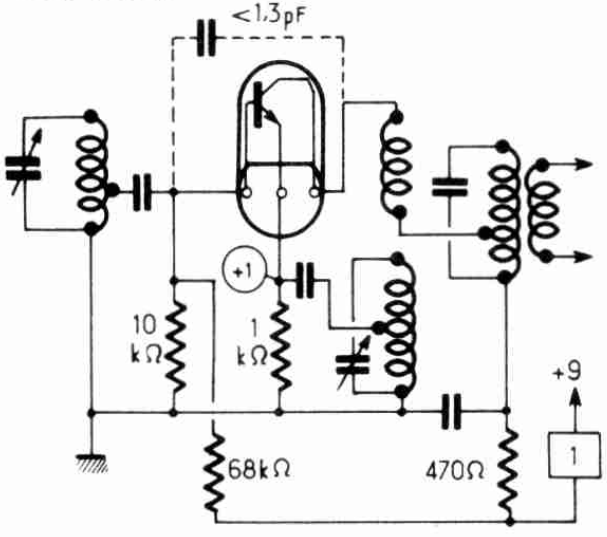
2N5222

n-p-n Si

Conv<30MHz

β=20.....1500

f_T >400 MHz



2N5225 2N5226

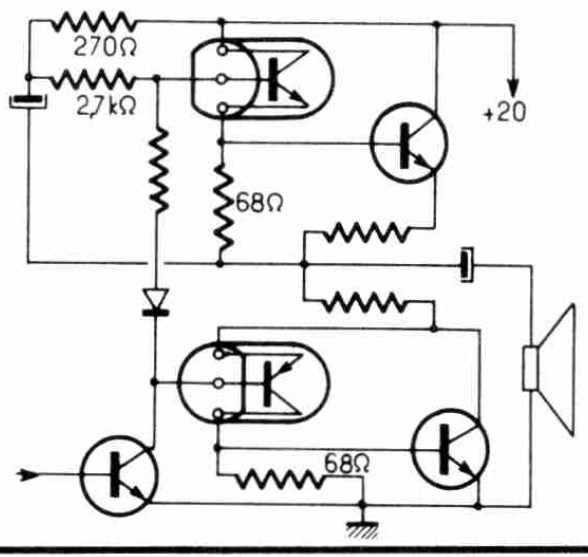
BF

n-p-n Si

p-n-p Si

β=30.....600

f_T >50 MHz



2N5227

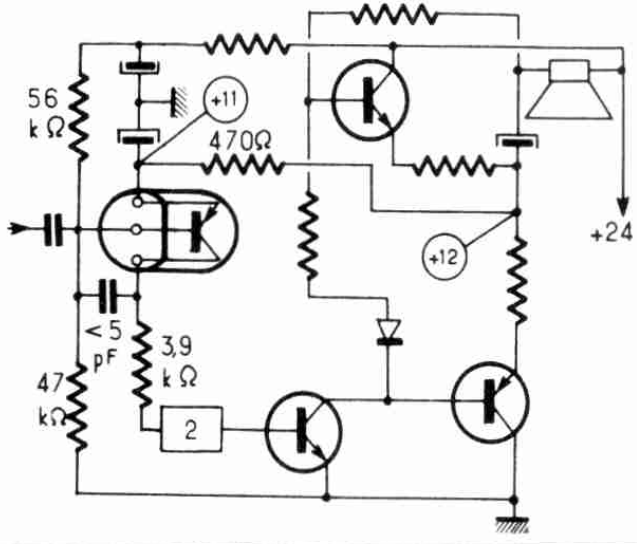
BF

p-n-p

Si

β=50.....700

f_T >100MHz



2N5245

100 MHz

FET Si

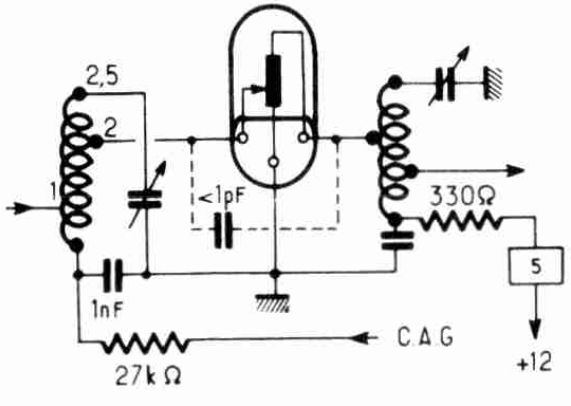
Canal N

s = 4,5....7,5mA/V

Vp=1....6mA/V

GP >18 dB

F_b <2 dB

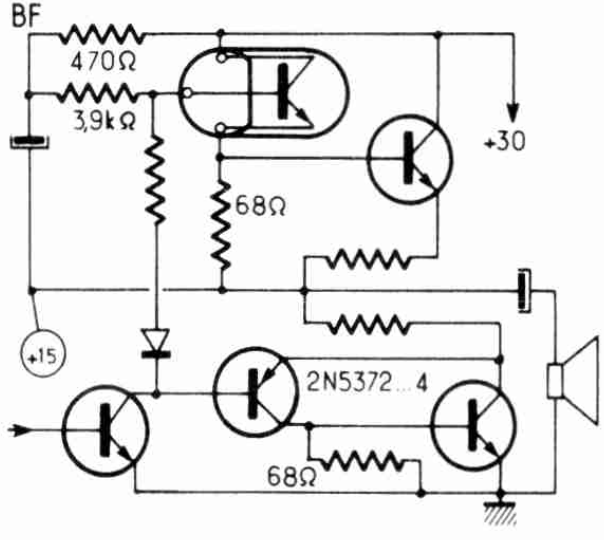


2N5368 (2N5369) (2N5370)

n-p-n Si

β=60.....200 (100.....300) (200.....600)

BF

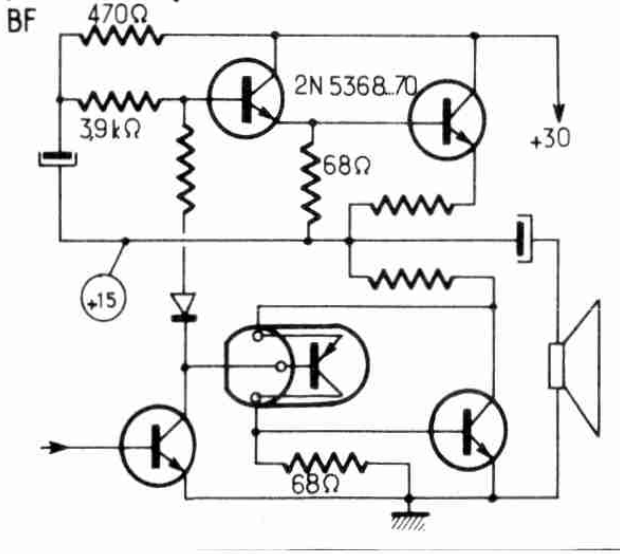


2N5372 (2N5373) (2N5374)

p-n-p Si

β=40.....120 (100.....300) (200.....400)

BF



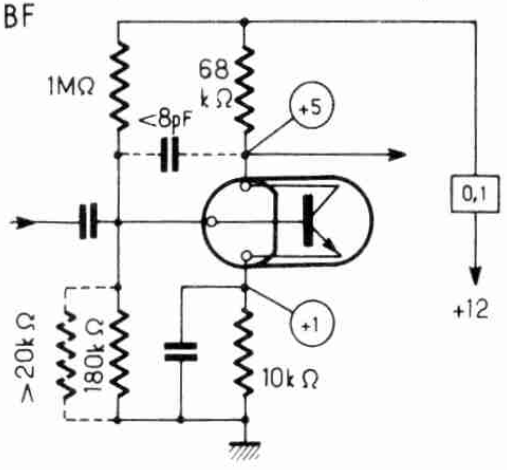
2N5376 (2N5377)

n-p-n Si

BF

ß=120.....600 (100.....500)

F_b<2 (<3) dB



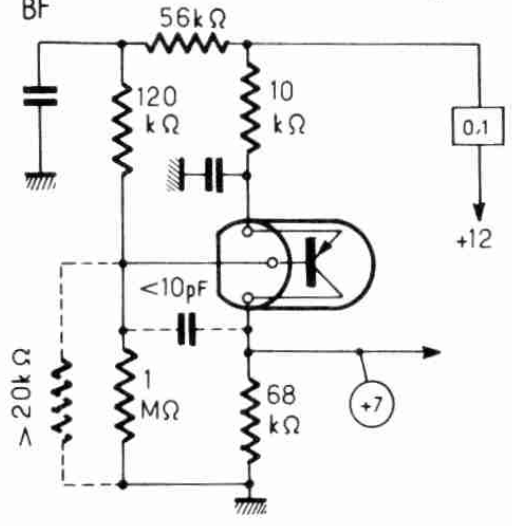
2N5378 (2N5379)

p-n-p Si

BF

ß=150.....600 (100.....500)

F_b<2 (<3) dB

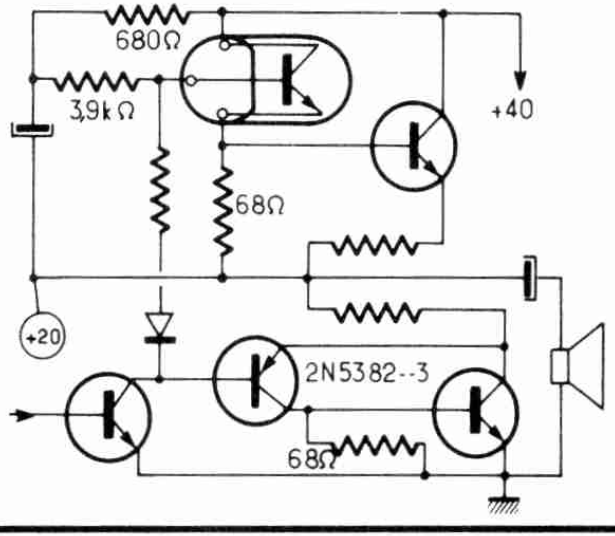


2N5380 (2N5381)

n-p-n Si

BF

ß=50.....150 (100.....300)

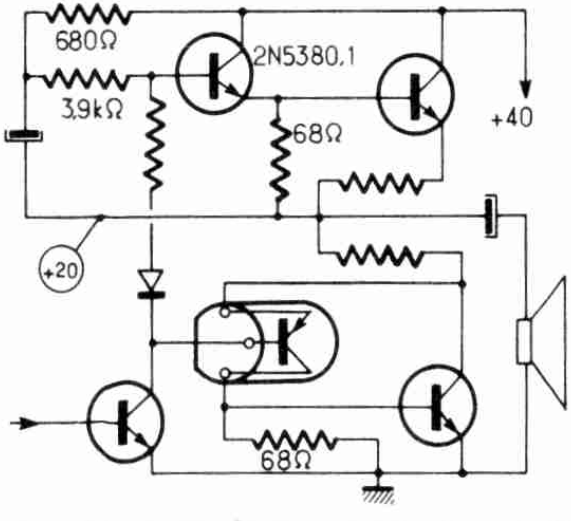


2N5382 2N5383

BF

p-n-p Si

ß=50.....150 (100.....300)



2N5447 2N5449

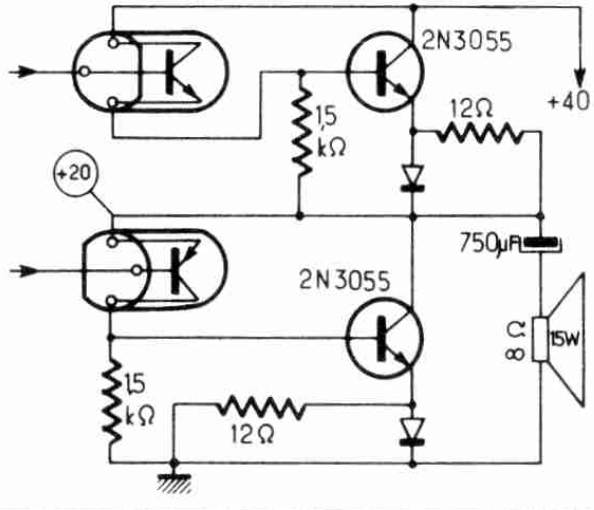
BF

p-n-p Si

n-p-n Si

ß=100.....300

f_T > 100MHz



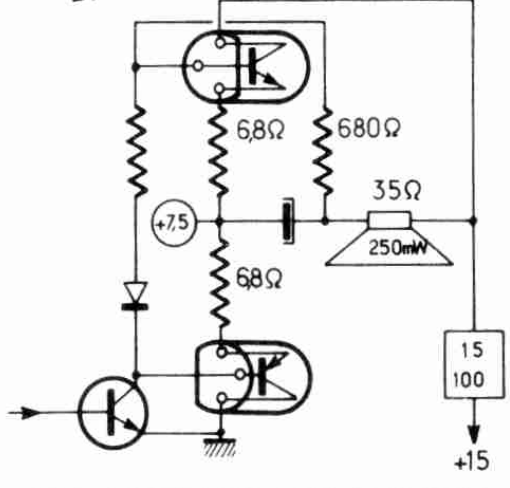
2N5447 2N5451

BF

p-n-p Si

n-p-n Si

ß=30.....600

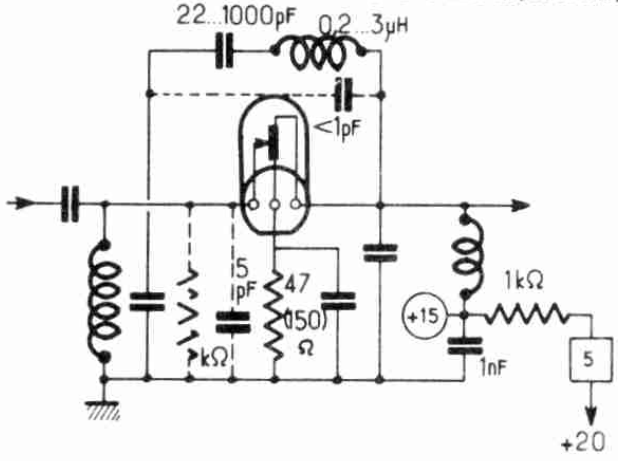


2N5485 (2N5486)

FET Si Canal N

100--- 400 MHz

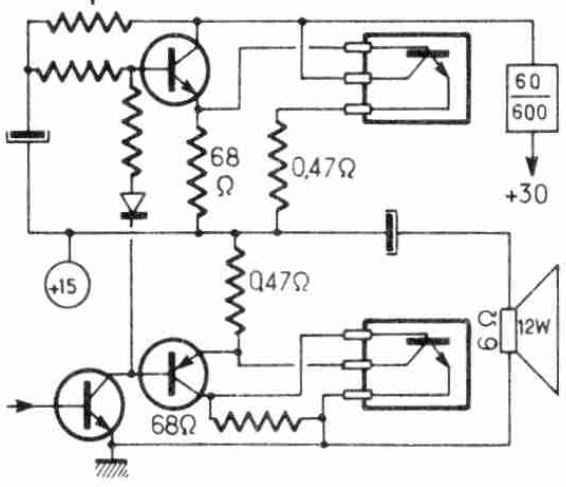
s = 3,5...7(4...8)mA/V
I_{DSS} = 4...10(8...20)mA
F_b = 2...4 dB (max)
GP = 18...30dB (100MHz)
GP = 10...20dB (400MHz)



2N5490 2N5491

n-p-n Si

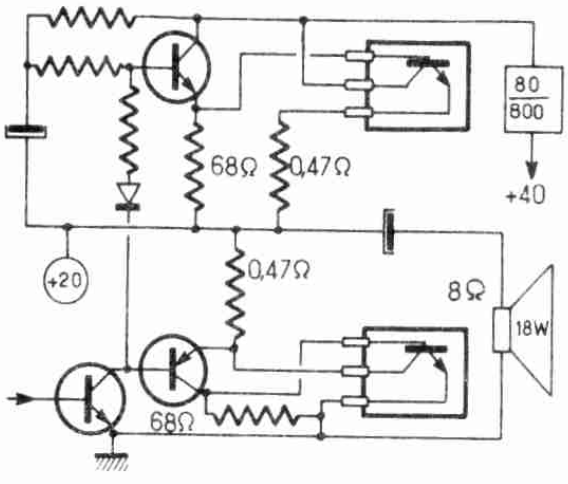
β = 20.....100
f_T = 1 MHz



2N5492 2N5493

P n-p-n Si

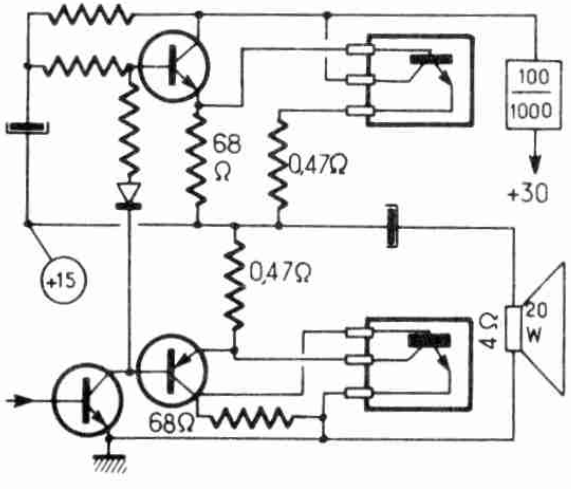
β = 20.....100
f_T = 1 MHz



2N5494 2N5495

P n-p-n Si

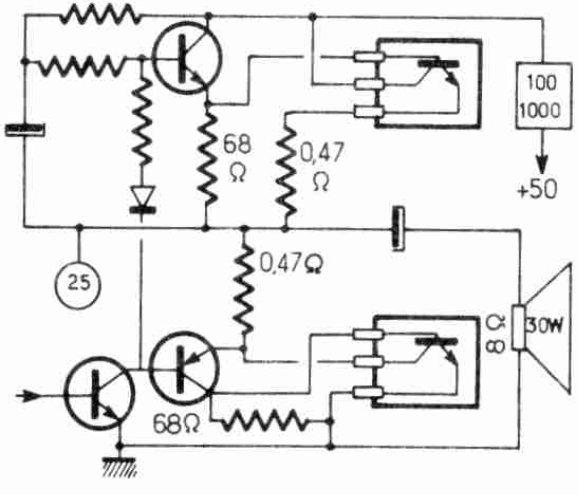
β = 20.....100
f_T = 1 MHz



2N5496 2N5497

P n-p-n Si

β = 20.....100
f_T = 1 MHz

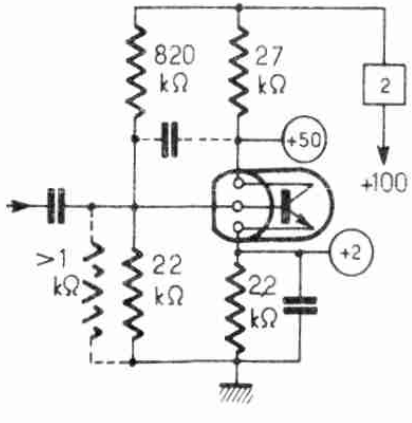


2N5550 (2N5551)

BF

n-p-n Si

β = 60.....250
(80.....250)
f_T >100 MHz



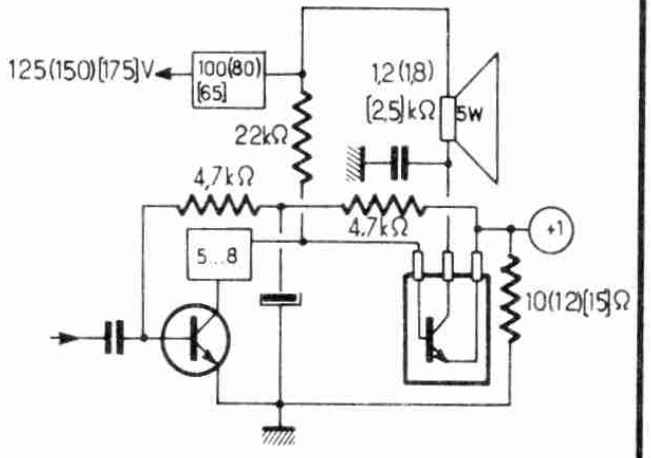
2N5655 (2N5656)(2N5657)

n-p-n Si

P

$\beta = 25 \ldots 250$

$f_T > 10$ MHz



2N5668 (2N5669)(2N5670)

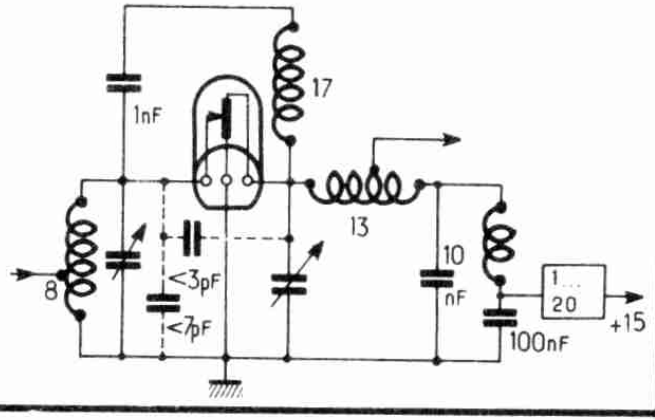
FET Si Canal N

100 MHz

$s = 1{,}5 \ldots 6{,}5$ (2...6,5)(3...7,5)mA/V

$G_P > 16$ dB

$F_b < 2{,}5$ dB



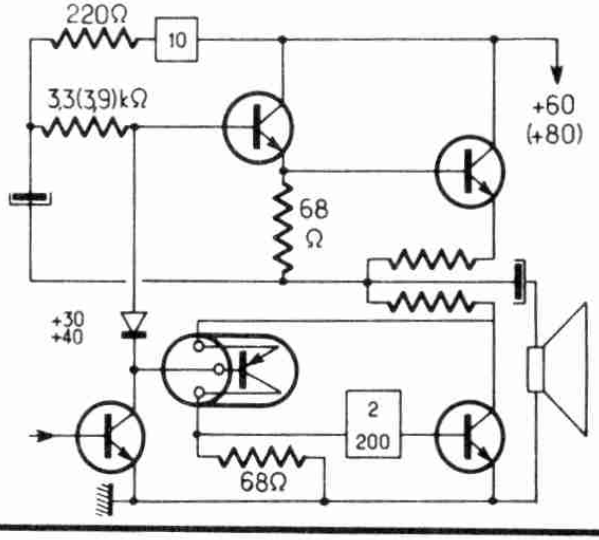
2N5855 (2N5857)

BF

p-n-p Si

$\beta = 50 \ldots 300$

$f_T > 15$ MHz



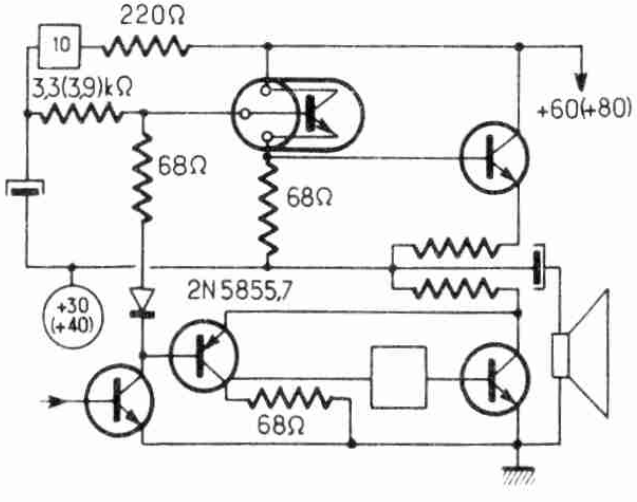
2N5856 (2N5858)

BF

n-p-n Si

$\beta = 50 \ldots 300$

$f_T > 200$ MHz



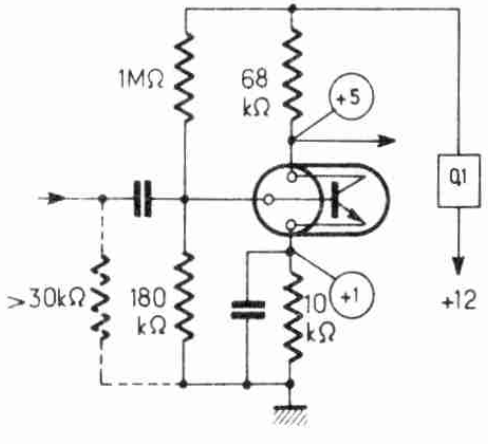
2N5961 (2N5962)(2N5963)

BF

n-p-n Si

$\beta = 150 \ldots 950$ (600...1500)[1200...2200]

$F_b = 2{,}5$ dB



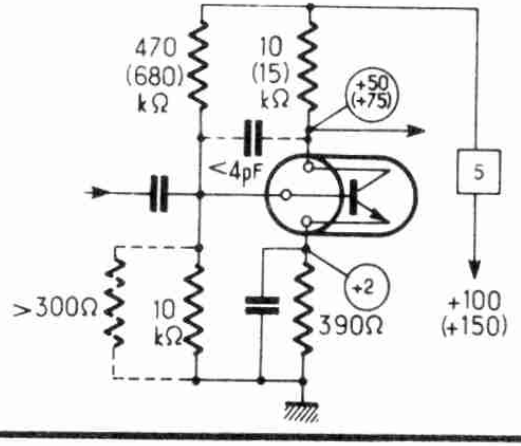
2N5964 (2N5965)

BF

n-p-n Si

$\beta = 50 \ldots 250$

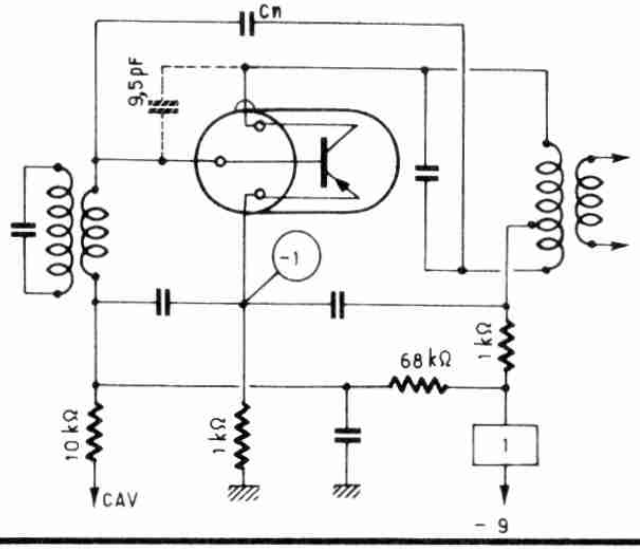
$f_T > 100$ MHz



2 SA 31,36

MF 470 kHz

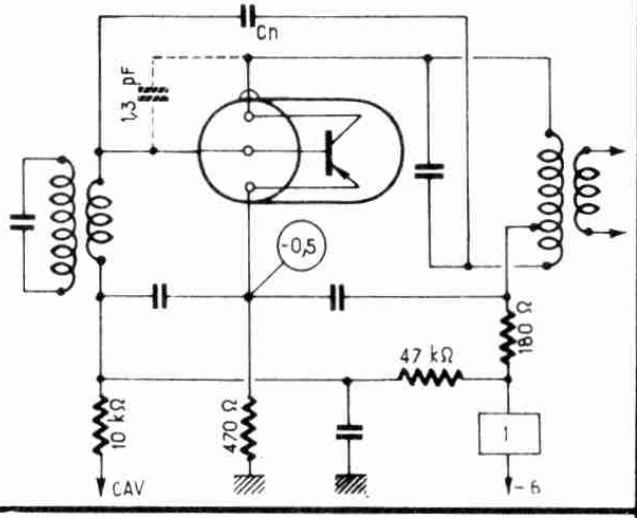
β = 50
GP = 37 dB



2 SA 121 (2 SA 122) [2 SA 123]

10 MHz

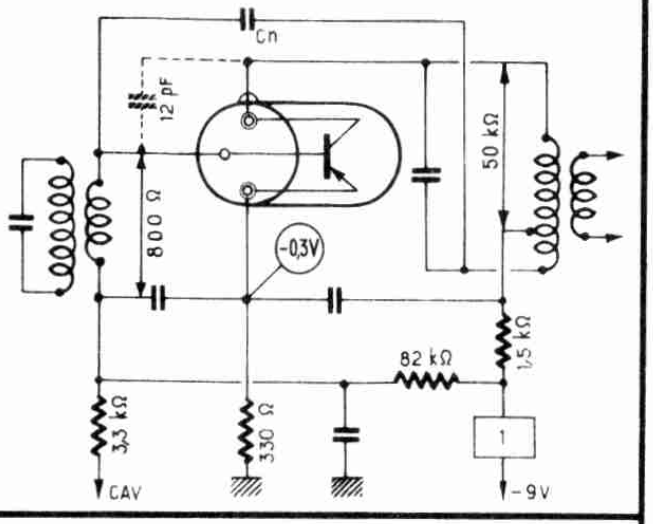
β = 9...82
GP = 24 (30) [35] dB



2 SA 141

MF 470 KHz

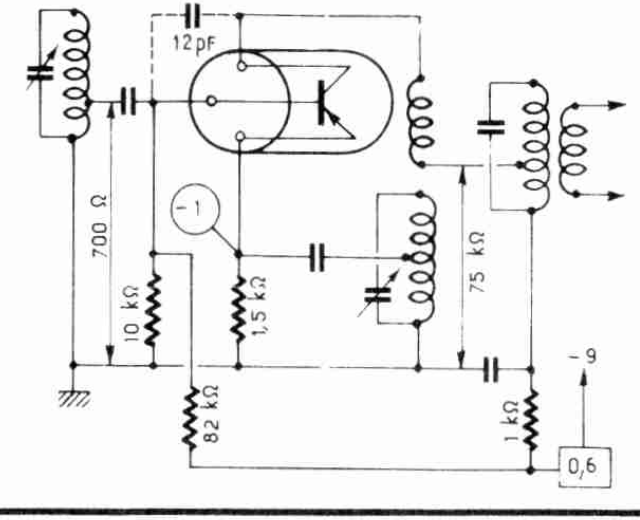
β = 70
GP = 33 dB



2 SA 142

Conv. < 2 MHz

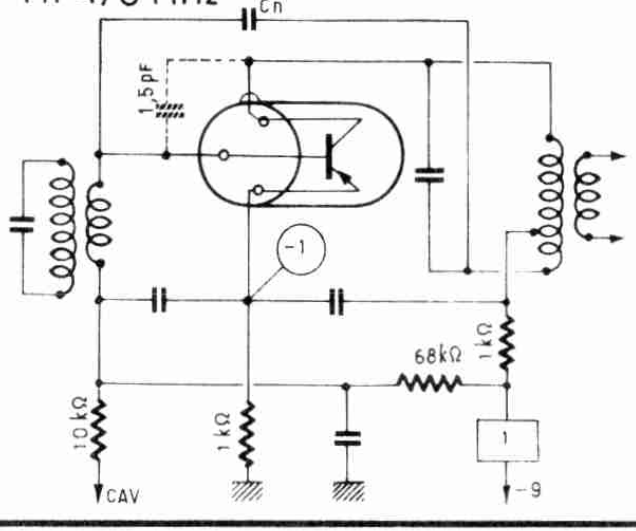
β = 75



2 SA 155 (2 SA 156)

MF 470 MHz

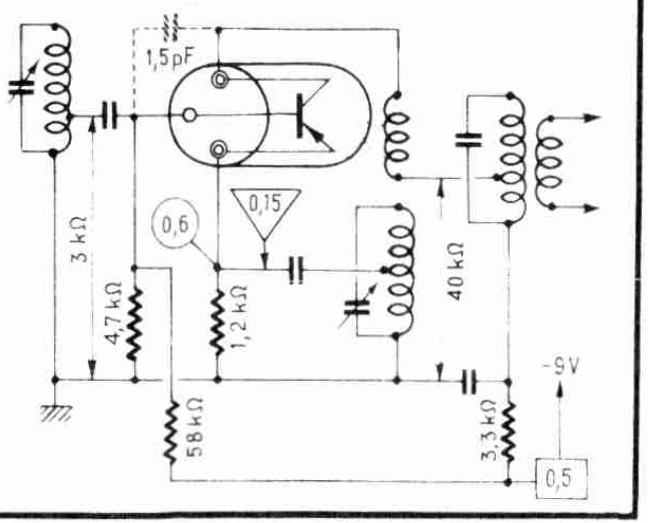
β = 30 (50)
GP = 39 (42) dB



2 SA 159 (2 SA 160)

Conv. 2 MHz

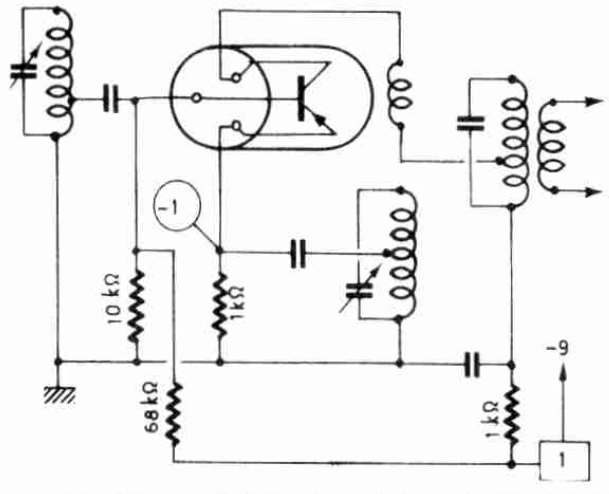
β = 50 (60)
GC = 36 (39) dB



2SA188,189

Conv.<2 MHz

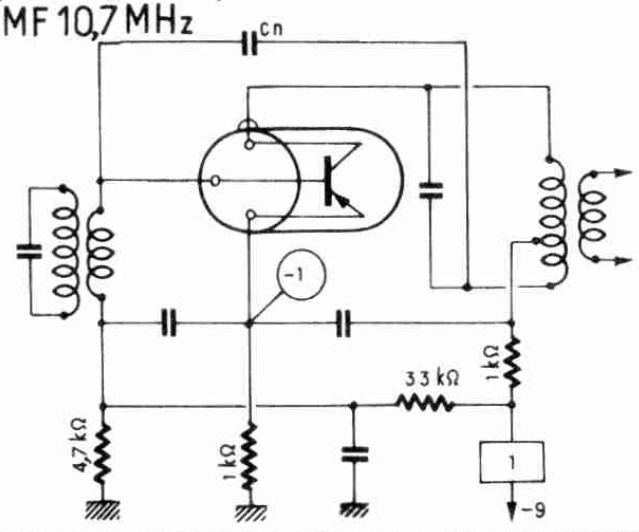
β = 65
GC = 30 dB



2SA201 (2SA202)

MF 10,7 MHz

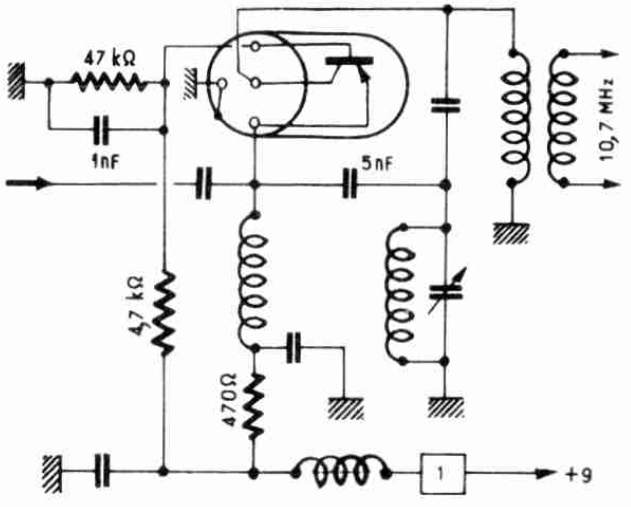
β = 50
GP = 24(27) dB



2SA 444

Conv. 100 MHz

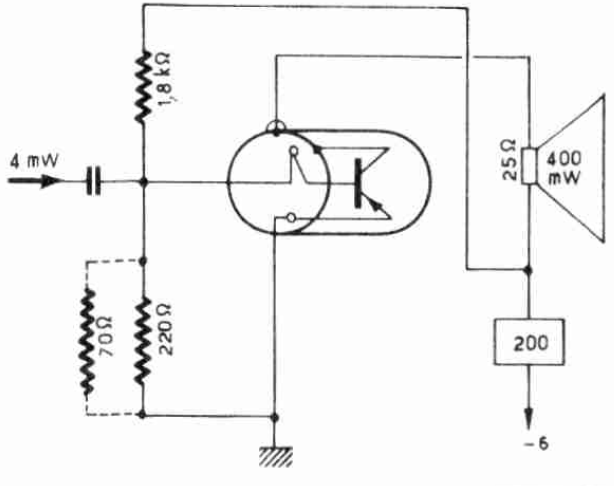
β = 80



2SB 27

P

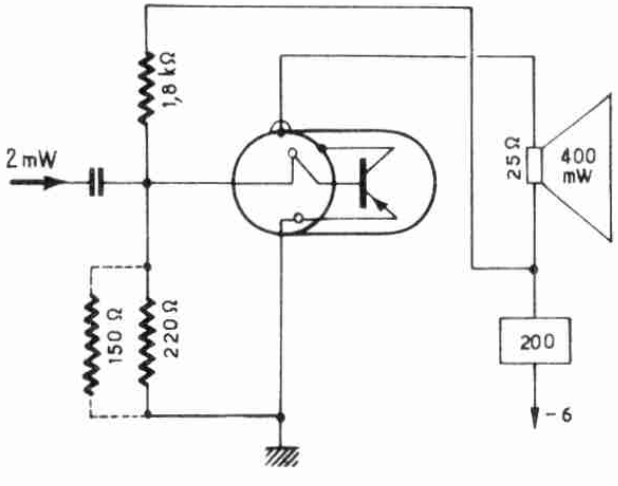
β = 29
GP = 20 dB



2SB 28

P

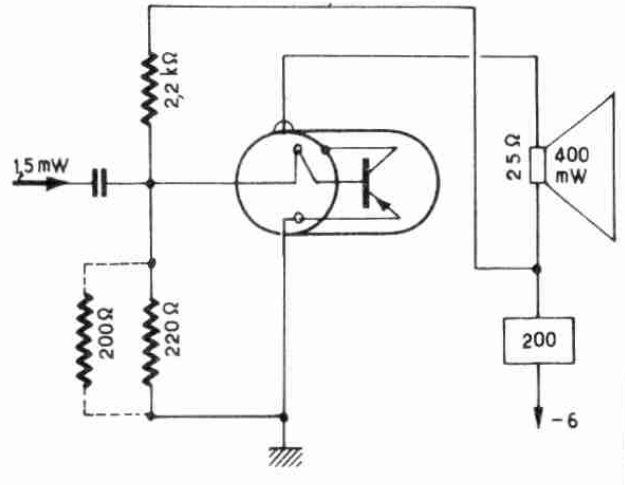
β = 68
GP = 23 dB



2SB 29

P

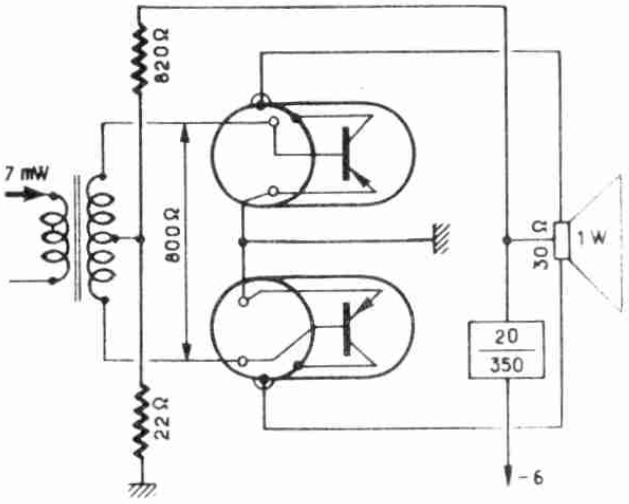
β = 115
GP = 25 dB



2 SB 31

BF

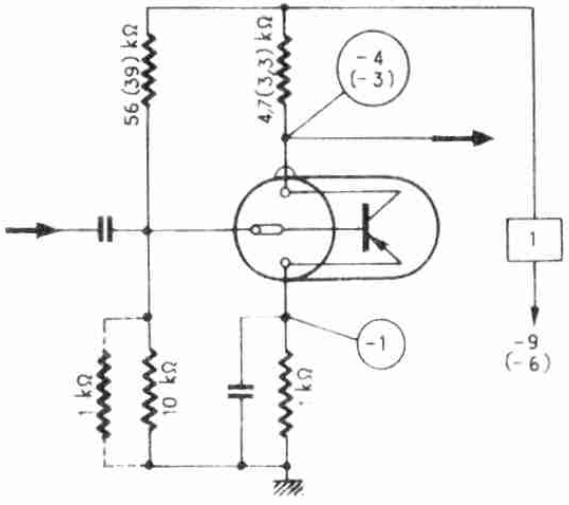
β = 115
GP = 22 dB



2 SB 48

BF

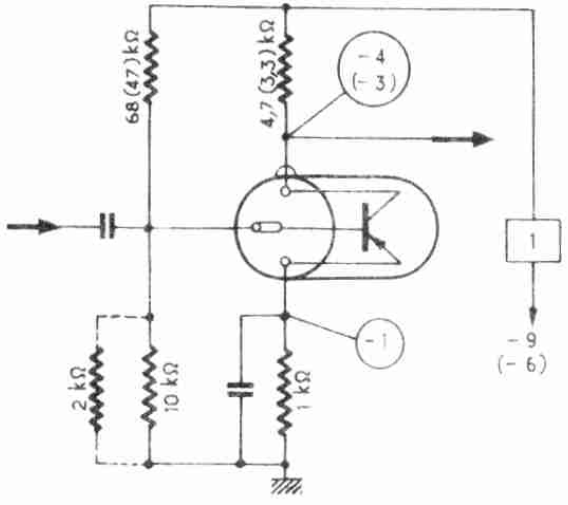
β = 36
Fb = 6 dB



2 SB 49

BF

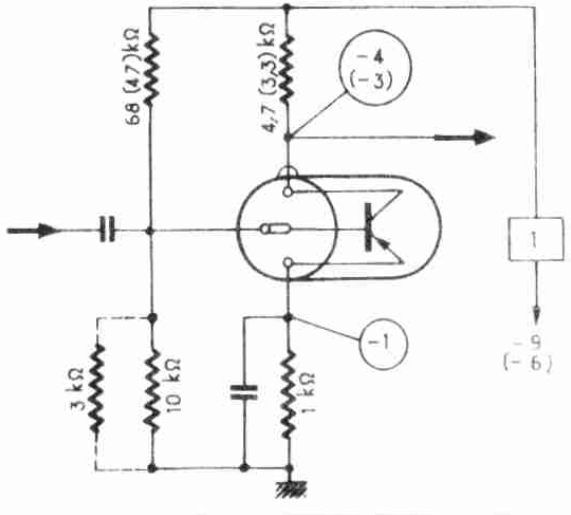
β = 66
Fb = 6 dB



2 SB 50

BF

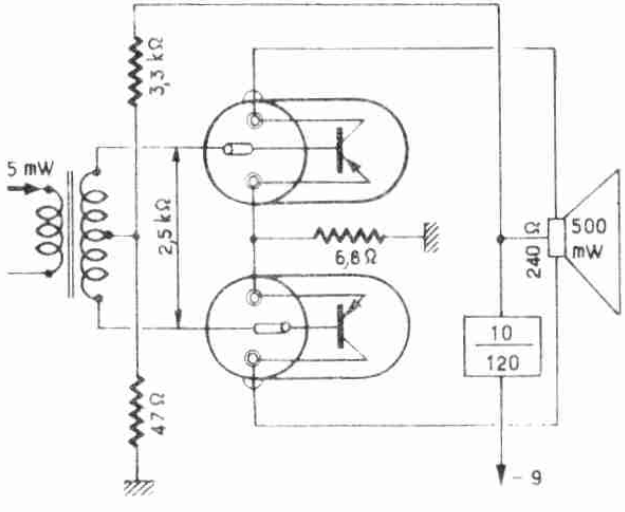
β = 100
Fb = 6 dB



2 SB 51

BF

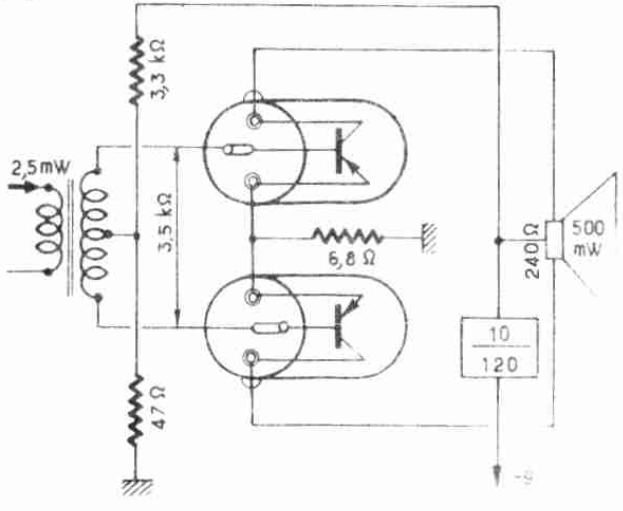
β = 36
GP = 20 dB



2 SB 52

BF

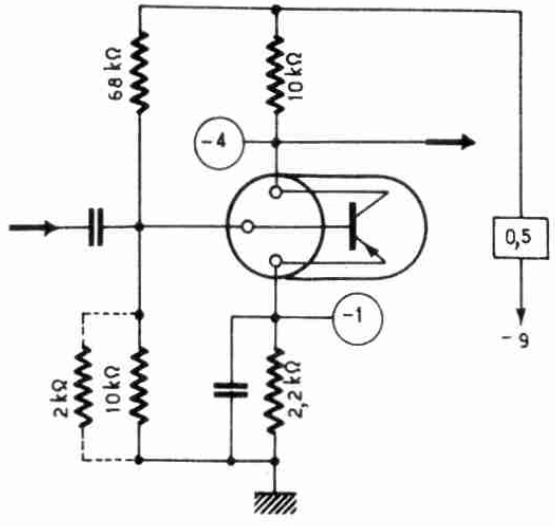
β = 66
GP = 23 dB



2SB56,59,60A

β = 60...90

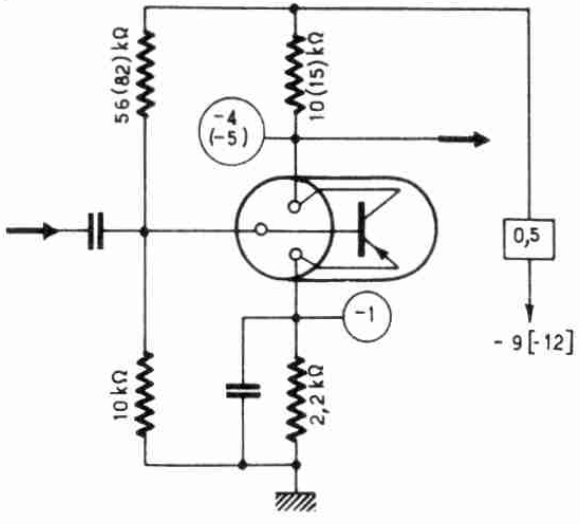
BF



2SB61

β = 50

BF

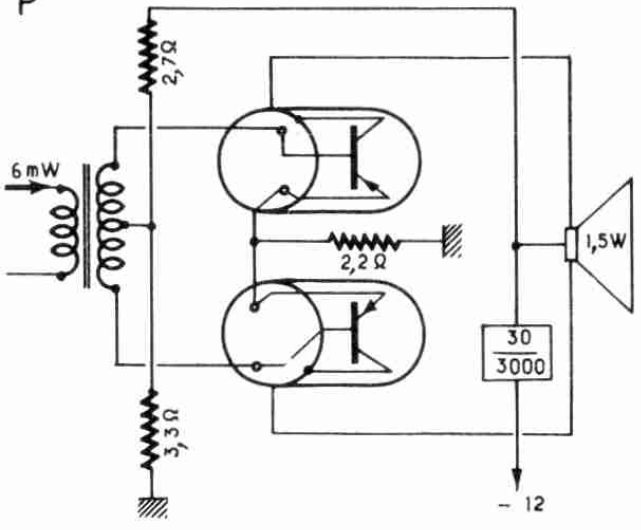


2SB62,63

β = 30...120

GP = 24 dB

P

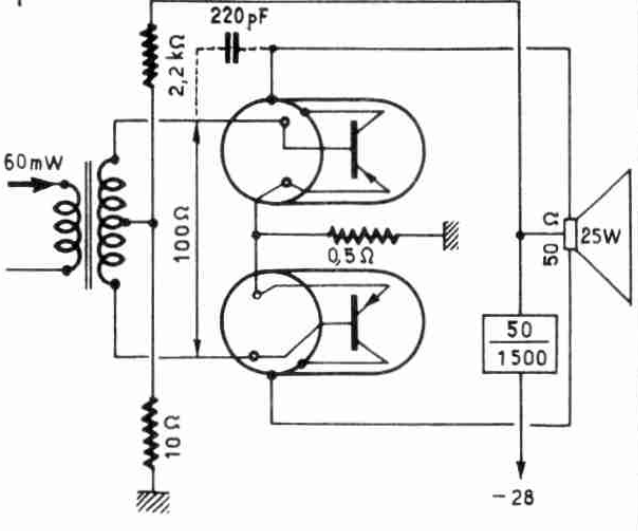


2SB64

β = 60

GP = 26 dB

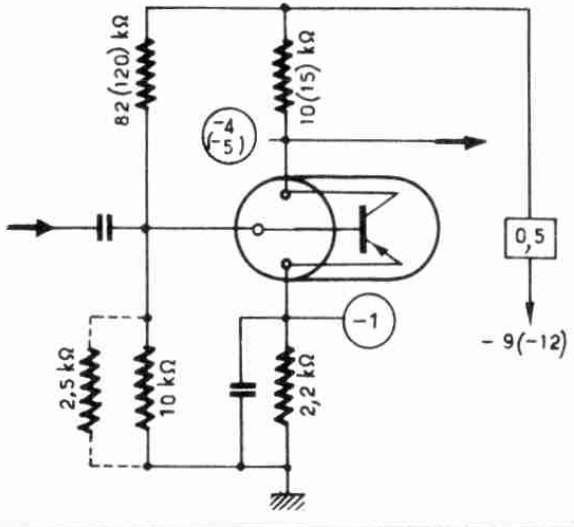
P



2SB66

β = 75

BF

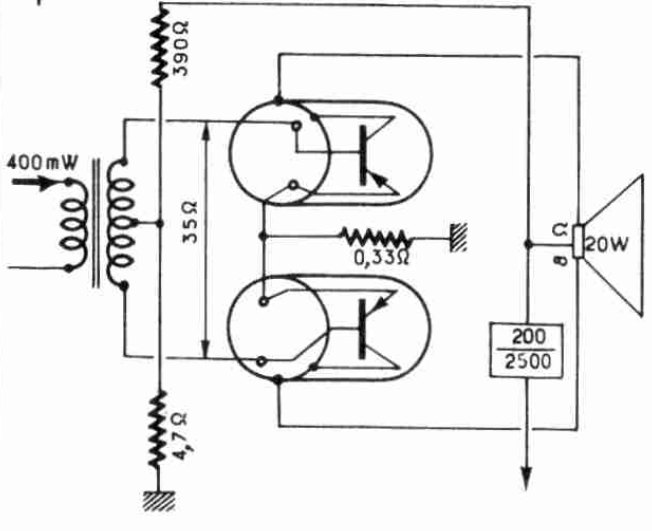


2SB69

β = 60

GP = 17 dB

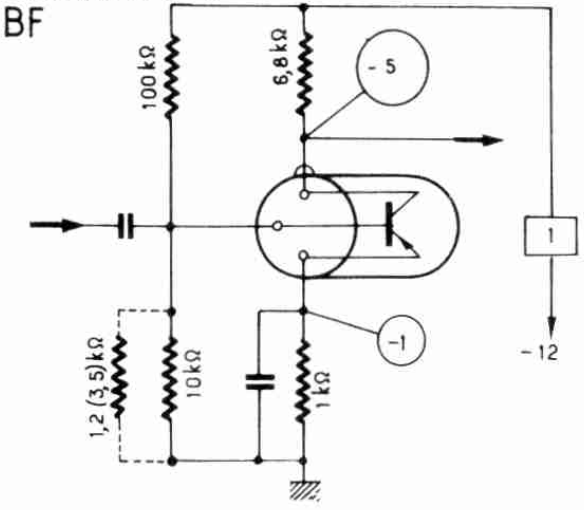
P



2SB98 (2SB99)

BF

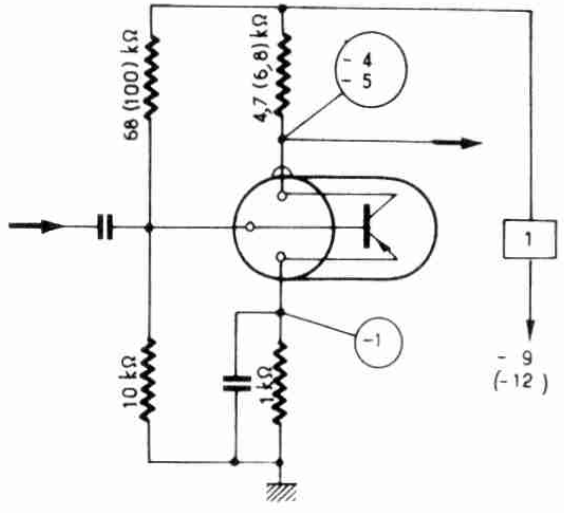
β = 40 (120)



2SB110, 11, 12, 13

BF

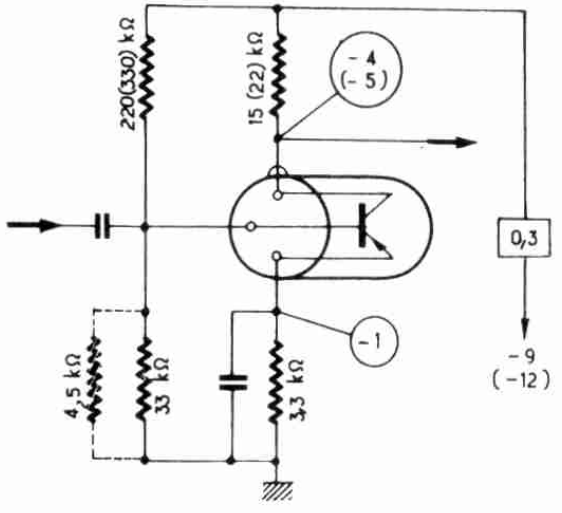
β=30,45, 60, 80



2SB134

BF

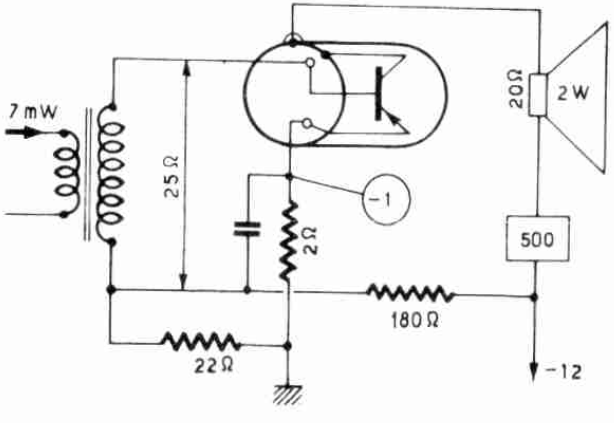
β = 70
Fb = 4 dB



2SB 142

P

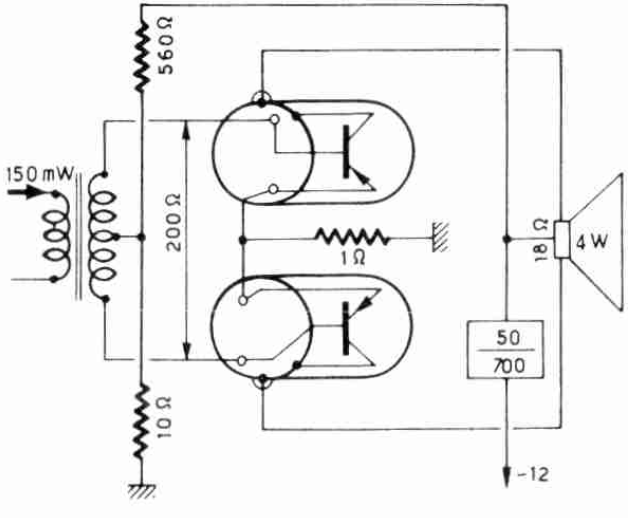
β = 24
GP = 25 dB



2SB 142

P

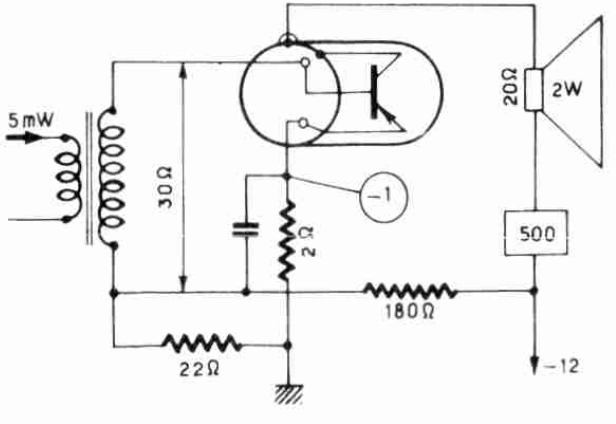
β = 24
GP = 15 dB



2SB 143

P

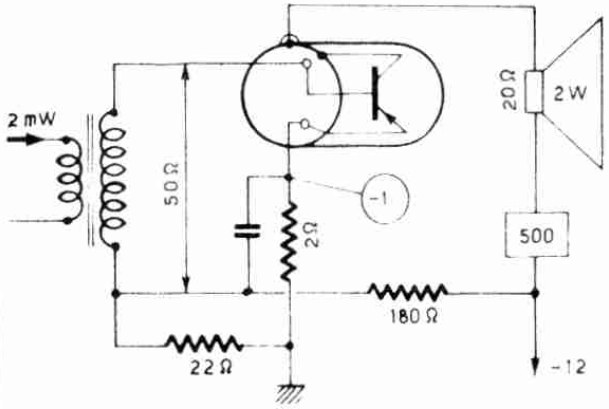
β = 37
GP = 27dB



2 SB 144

P

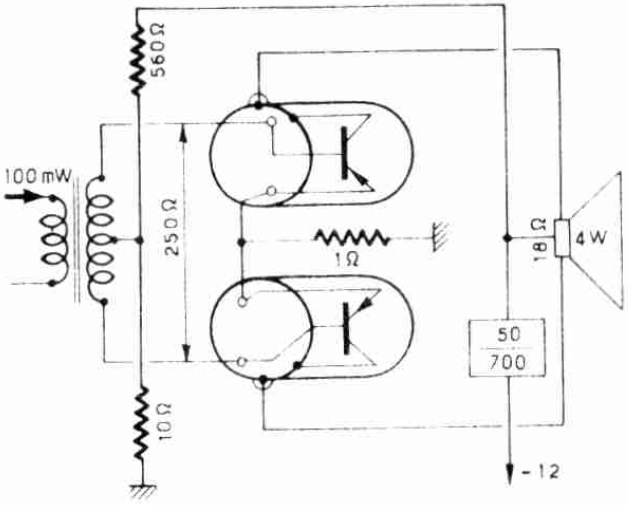
β = 75
GP = 30 dB



2 SB 145

P

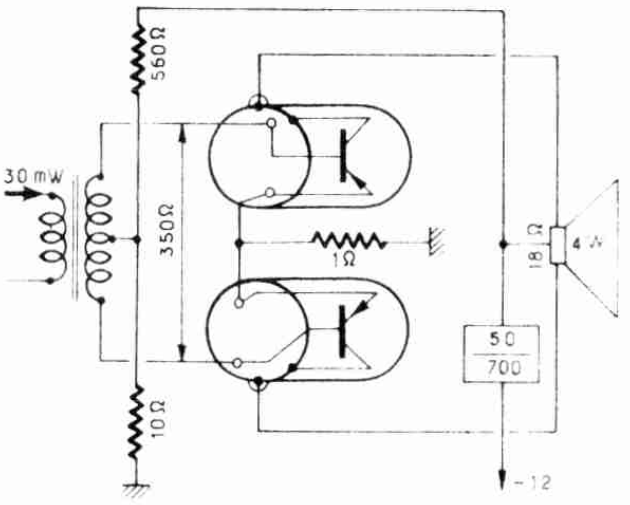
β = 37
GP = 18 dB



2 SB 146

P

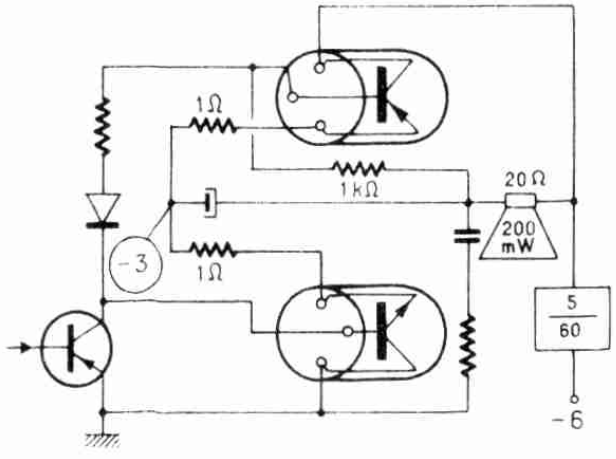
β = 75
GP = 21 dB



2 SB 181
2 SD 181

p-n-p
n-p-n

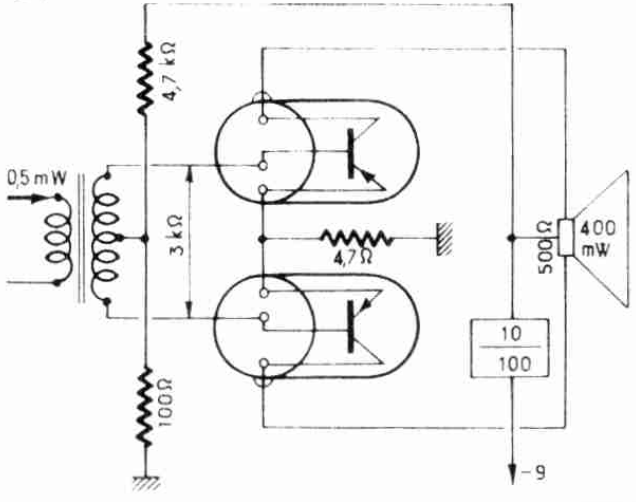
β = 100



2 SB 221
(2 SB 222)

BF

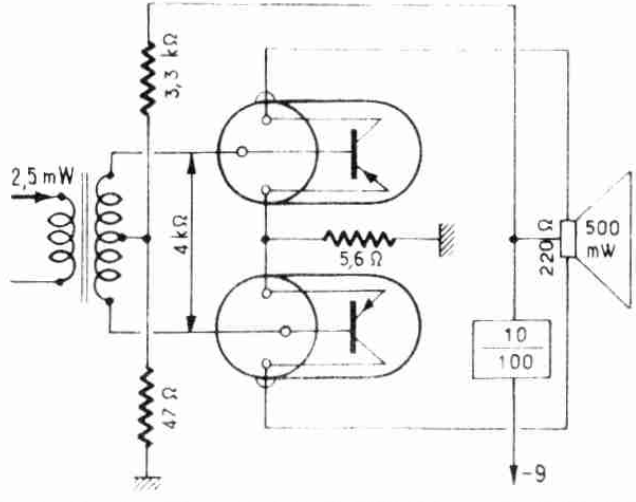
β = 50 ... 90
(70 ... 120)
GP = 29 dB



2 SB 221A
(2 SB 222A)

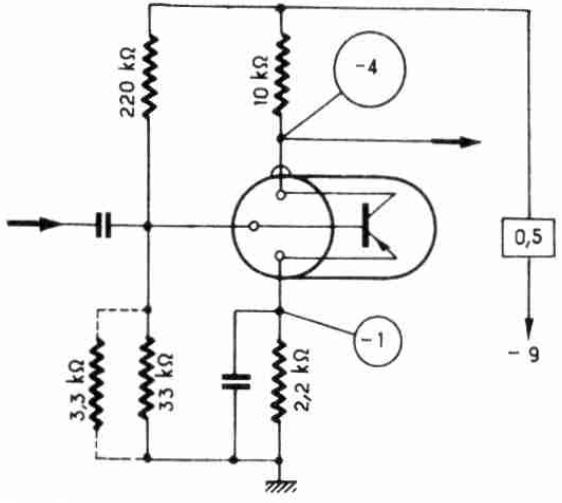
BF

β = 50 ... 90
(70 ... 120)
GP = 23 dB



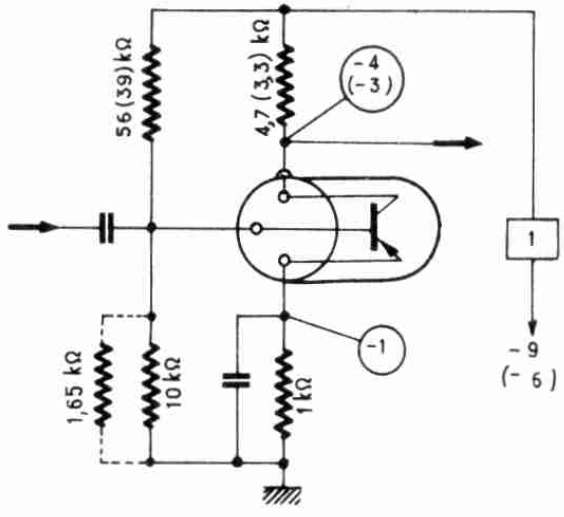
2 SB 264
BF

β = 45....100
F_b = 3 dB



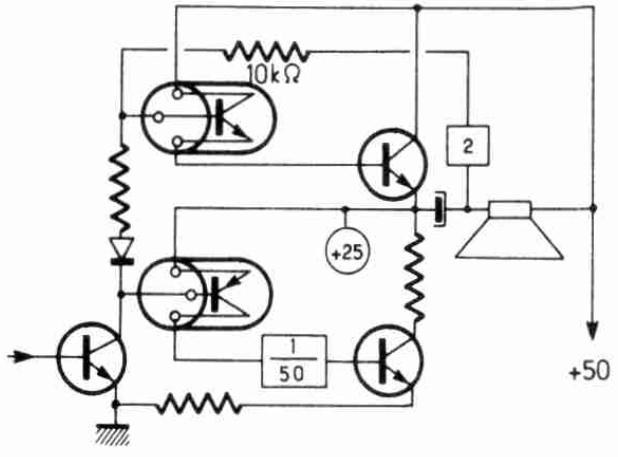
2 SB 400
BF

β = 120



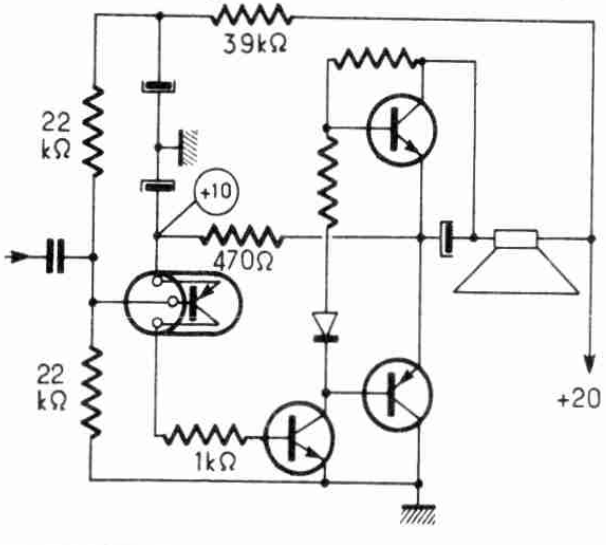
2 SB 421
2 SC 292
BF

p-n-p Ge
n-p-n Si
ß = 70



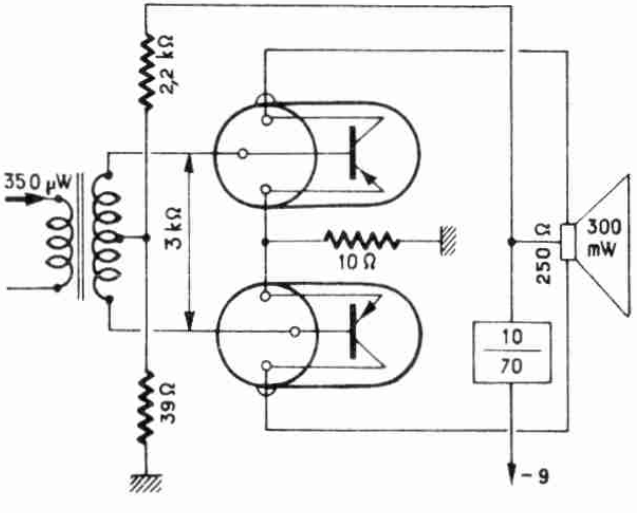
2 SB 439
(2 SB 440)
BF

ß = 70....270
F_b < 7 (< 5) dB



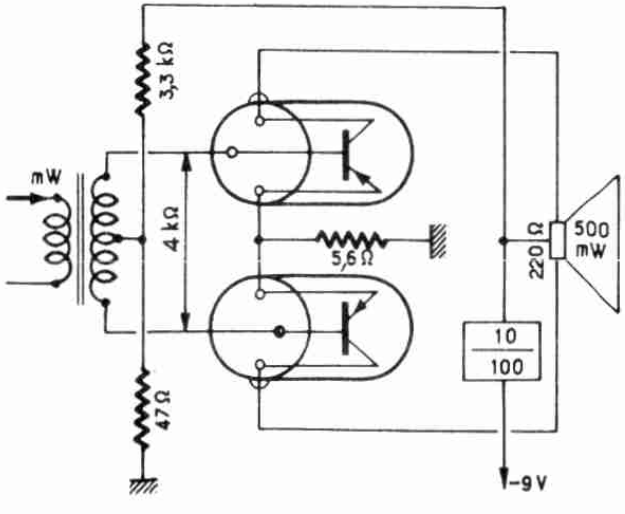
2 SB 457
BF

β = 110
GP = 29 dB

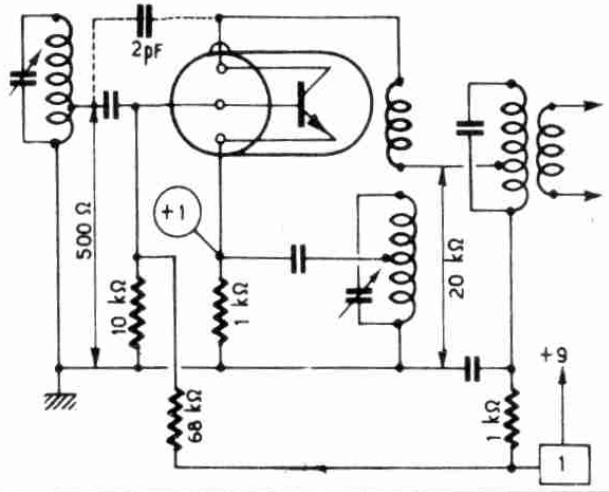


2 SB 494
BF

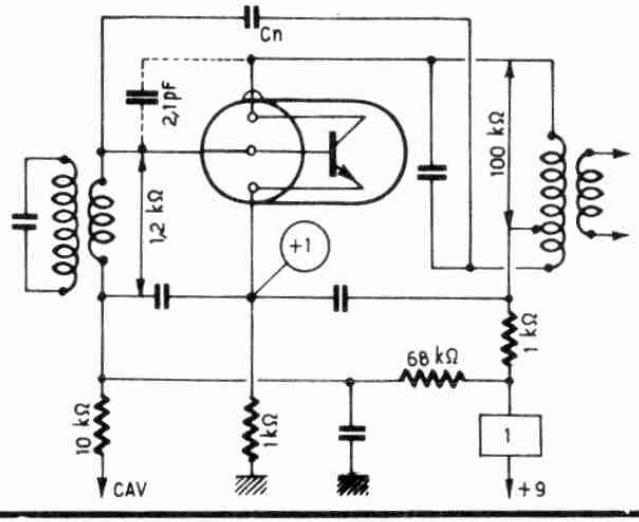
β = 0
GP = dB



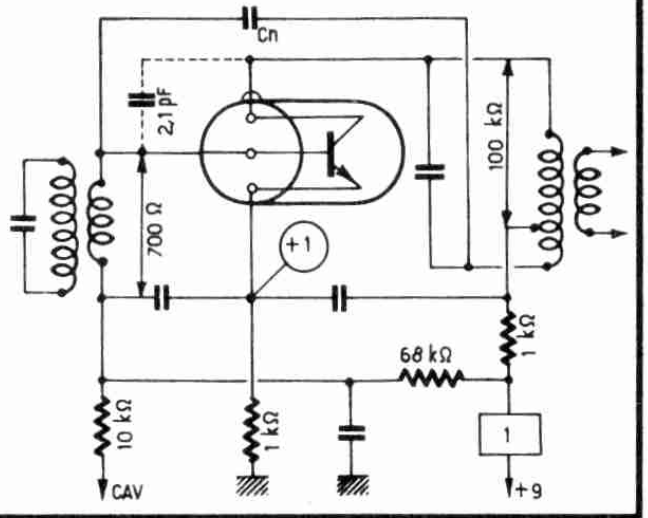
2SC 73
n-p-n
Conv. <2 MHz
β = 41
GC = 27dB



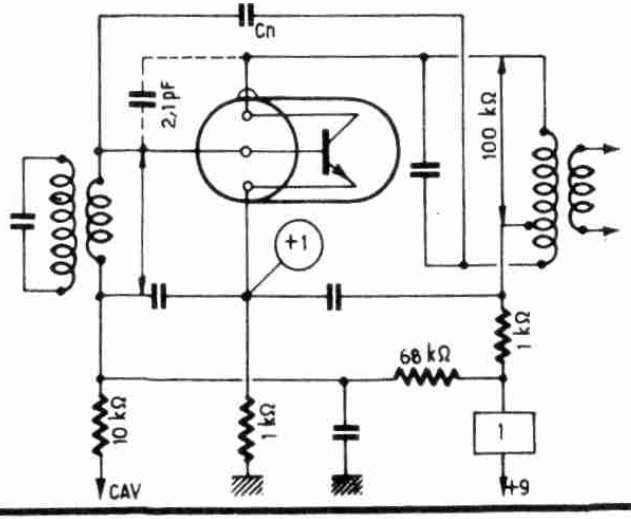
2SC 75
n-p-n
MF_470 kHz
β = 9...82
GP = 41dB



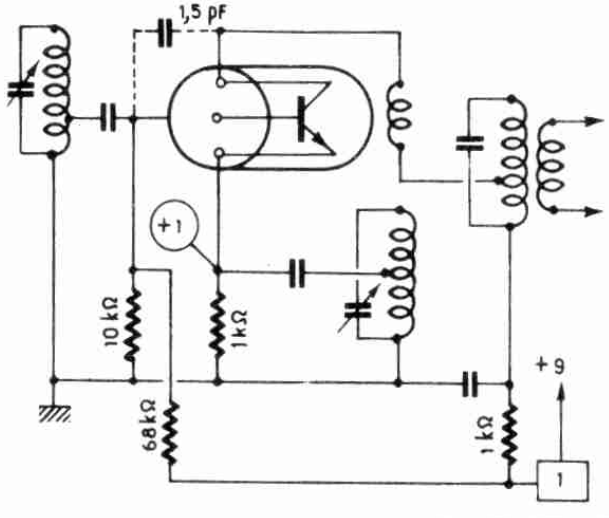
2SC 76
n-p-n
MF_470 kHz
β = 9... 82
GP = 37dB



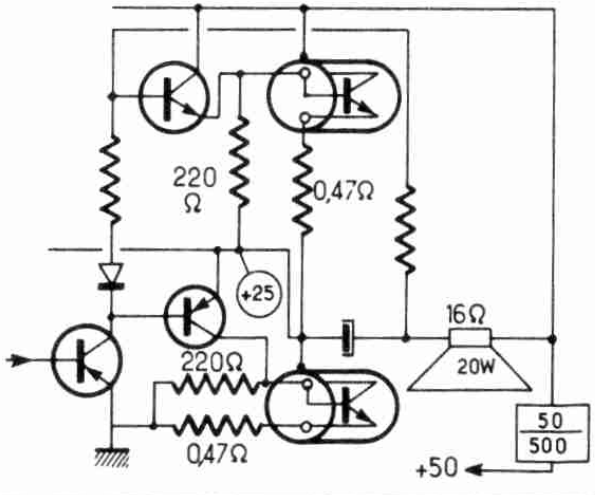
2SC 77
n-p-n
MF_470 kHz
β = 9..82
GP = 32 dB



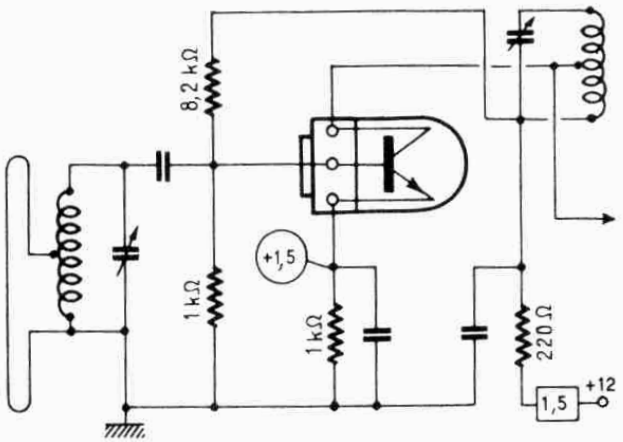
2SC 78
n-p-n
Conv. <2MHz
β = 49
GC = 26dB



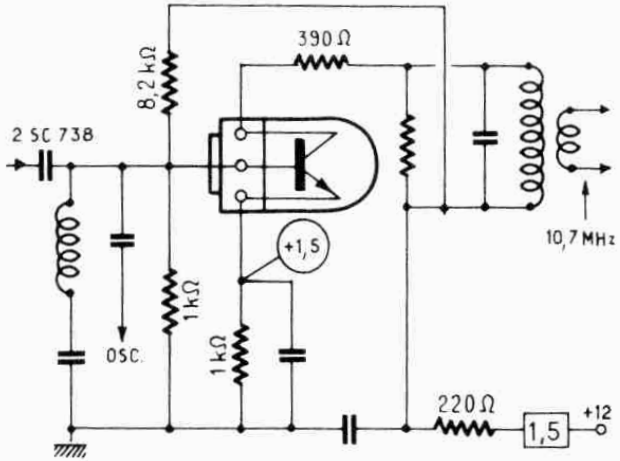
2SC 245
P
n-p-n
Si
ß = 40(>15)
f_T = 35MHz



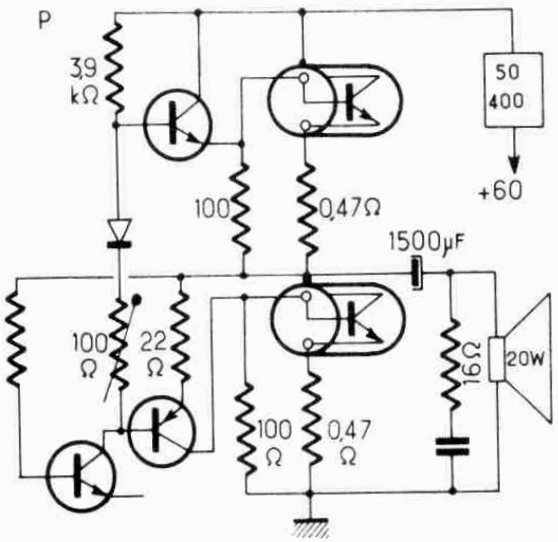
2 SC 738
n-p-n
100 MHz
Si
β = 20... 300
f_t = 400 MHz



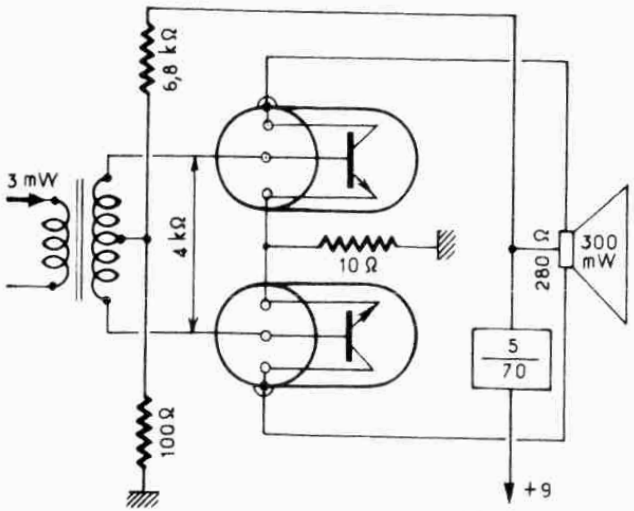
2 SC 739
n-p-n
Conv. 100 MHz
Si
β = 20... 300
f_t = 350 MHz



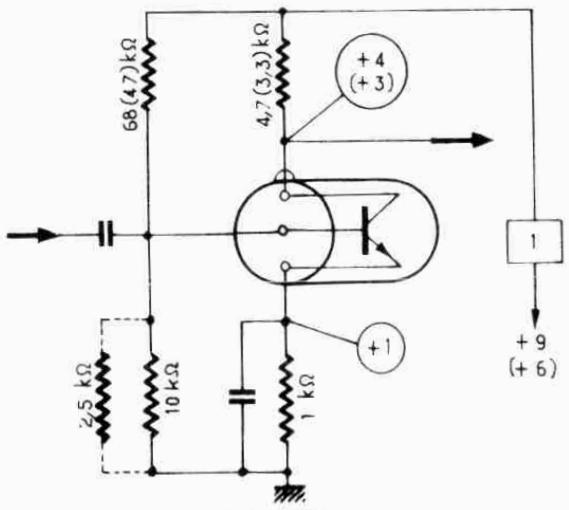
2 SD 45
n-p-n Si
n = 12 ...120
P



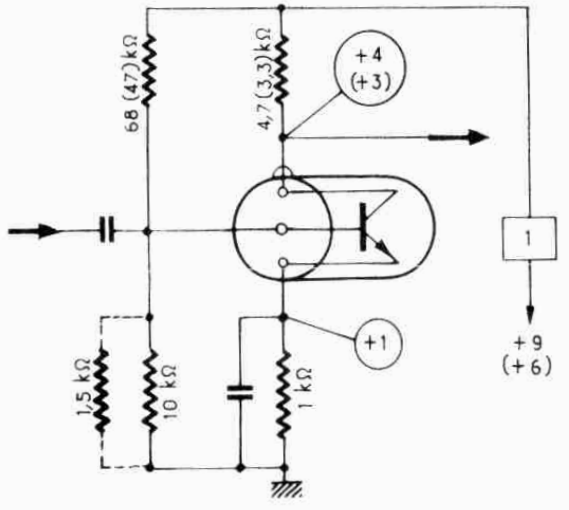
2 SD 63
n-p-n
BF
β = 50
GB = 20dB



2 SD 64
n-p-n
BF
β = 76
Fb = 8dB



2 SD 65
n-p-n
BF
β = 43
Fb = 8dB



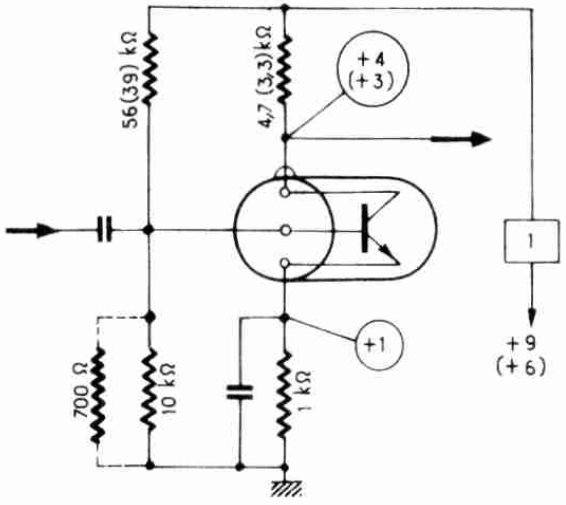
2 SD 66

n-p-n

BF

β = 23

Fb = 8dB

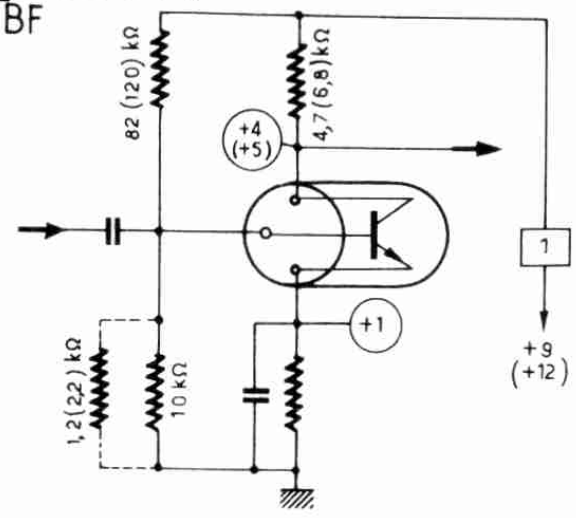


2SD75 [2SD77]

n-p-n

BF

β = 40 [70]

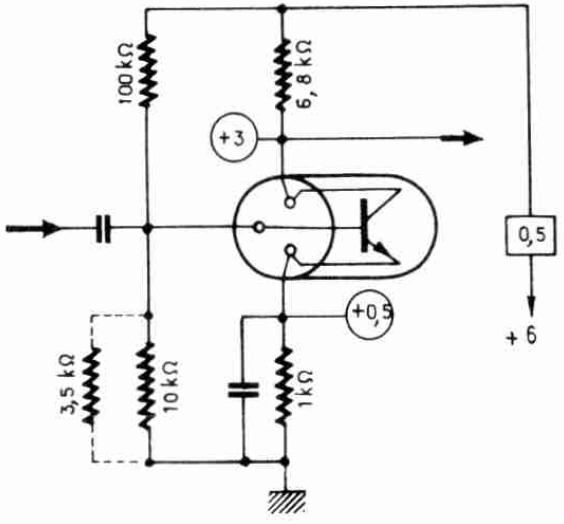


2SD162

n-p-n

BF

β = 60



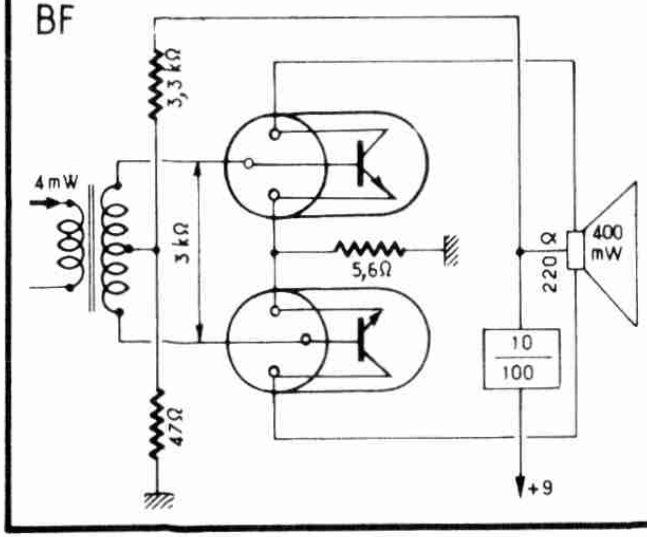
2SD186 2SD187

n-p-n

BF

β = 150

GP = 20 dB



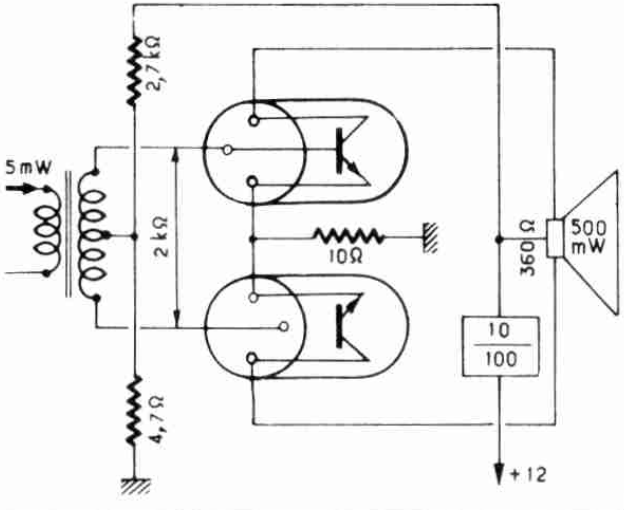
2 SD 193

n-p-n

BF

β = 100

GP = 20dB



3N142

FET Si

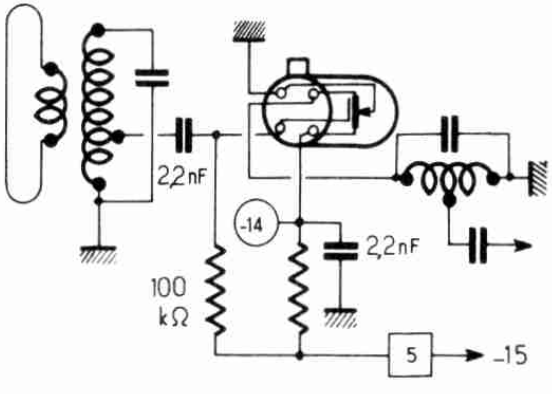
Canal N

100MHz

S = 7,5(>4) mA/V

GP = 14 dB

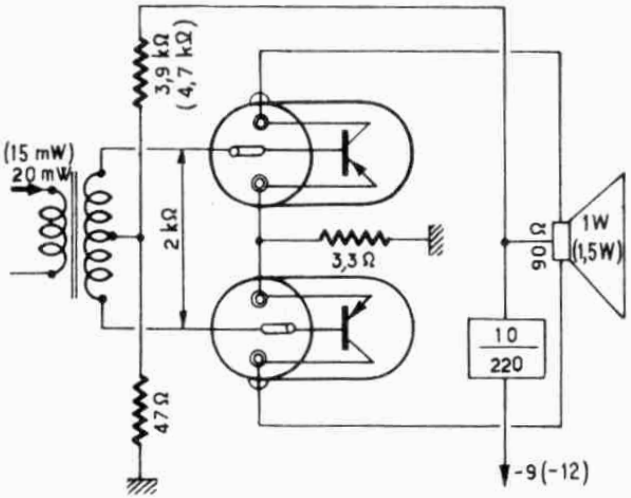
Fb < 5dB



2 SD 181 → 2 SB 181

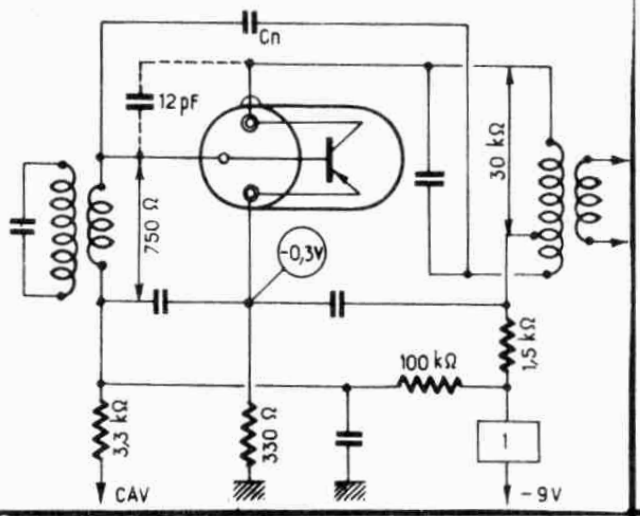
44 T1
P

β = 54
GP = 18dB (20dB)



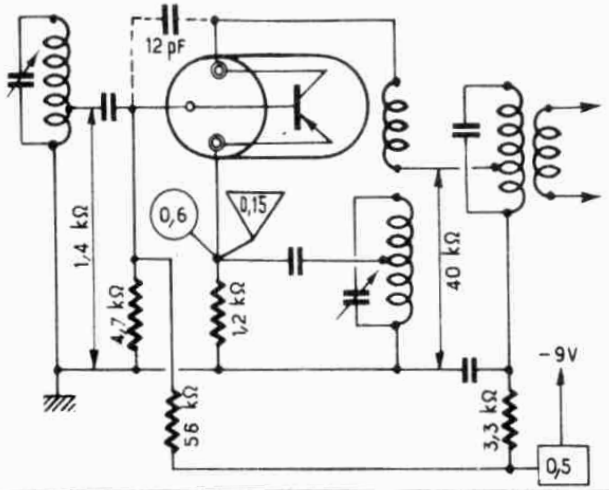
36T1
MF470 kHz

β = 60
GP = 30dB



37T1
Conv. < 2MHz

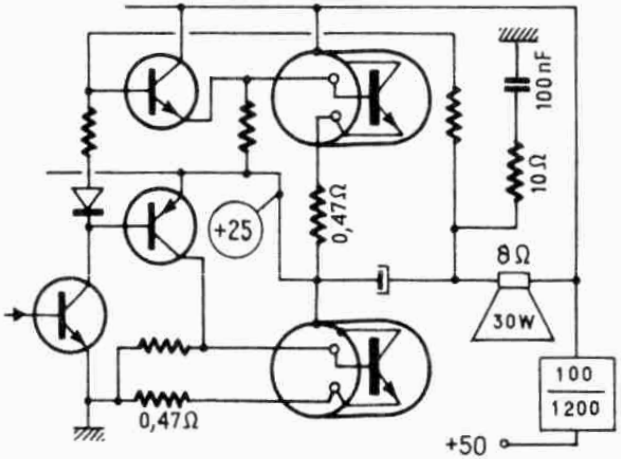
β > 25
GC = 30dB



180 T1
A, (B), [C]
P

n p n
Si

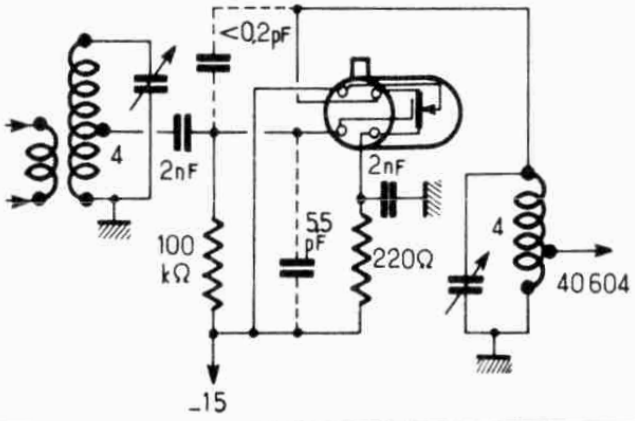
β = 15...45 (30...90) [75...180]



40468 A
100MHz

MOS
Canal N

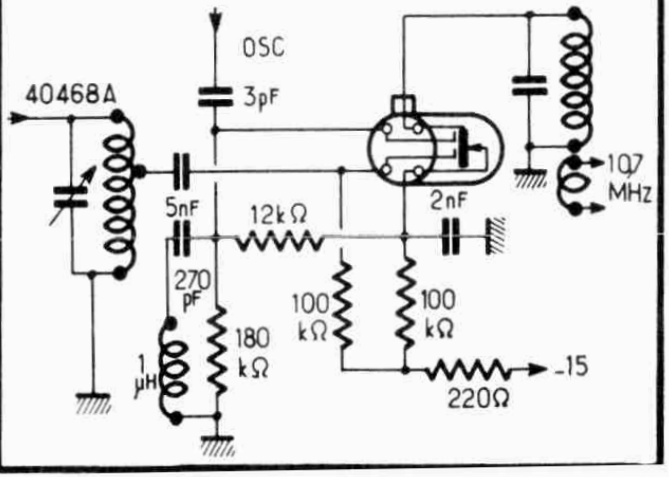
S 7,5 mA/V
GP = 14dB
Fb < 5 dB



40604
Conv. 100 MHz

MOS
Canal N

s_c = 2,8 mA/V
GP = 23 dB



TV - TRANSISTORS

ABREVIATIONS

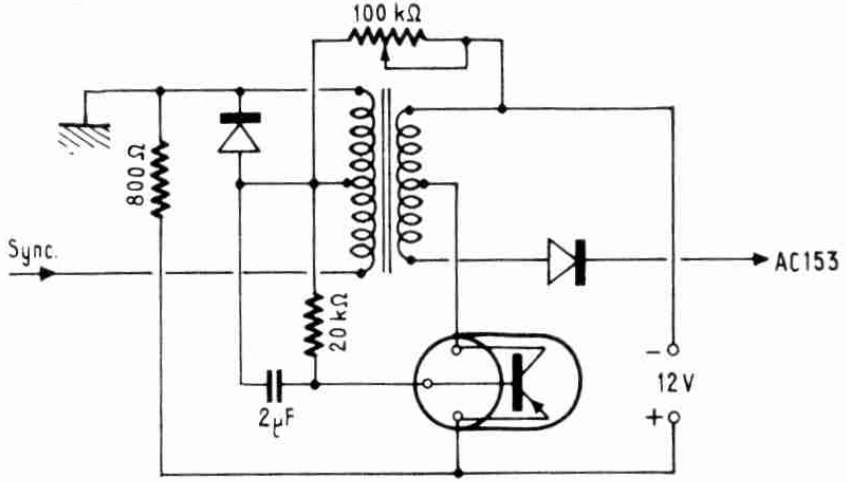
Alim.	Alimentation	Power Supply	Speiseeinheit	Alimentación	Voeding
All.	Alliage	Alloy	Legierungstransistor	Aleación	Legering
A.M.	Modulation d'amplitude	Amplitude Modulation	Amplitudenmodulation	Modulacion de amplitud	Geluidsterkte modulator
Amplif.	Amplificateur	Amplifier	Verstärker	Amplificador	Versterker
Ant.	Antenne	Antenna	Antenne	Antena	Antenne
Arrêt	Bobine d'arrêt	Stop reel	Drosselspule	Bobina de parada	Regelingsspoel
Attaque	Etage d'attaque	Attack Stage	Treiberstufe	Fase de ataque	Aanvangverdiep
Bal.	Balayage	Scanning	Ablenkung	Exploración	Wegdrijven
Bande	Bande de fréquence	Frequency band	Frequenzband	Faja de frecuencia	Frequentie band
BC	Base commune	Common Base	Basisschaltung	Base común	Grondbasis
Blank.	Blanking	Blanking	Austastimpuls	Supresión de haz	Blanking
Câble	Câble coaxial	Coaxial cable	Koaxialkabel	Cable coaxial	Co-axiale kabel
CAF	Commande automatique de fréquence	Automatic Frequency Control	Automatische Frequenzreglung	Mando automático de frecuencia	Automatische frekwentieregeling
CAG	Commande automatique de gain	Automatic Gain Control	Automatische Verstärkungsregelung	Mando automático de ganancia	Automatische versterkingsregeling
C.V.	Capacité variable	Variable capacity	Veränderliche Kapazität	Capacidad variable	Veranderlijke kracht
Comp.	Comparateur	Comparator	Vergleichsstufe	Comparador	Vergelijker
Contr.	Contraste	Contrast	Kontrast	Contraste	Contrast
Conv.	Conversion	Conversion	Mischstufe	Conversión	Omzetting
Corr.	Correction	Correction	Korrektur	Corrección	Correctie

CRT	Tube cathodique	Cathode Tube	Katodenstrahlröhre	Tubo catódico	Katodische buis
Défl.	Bobine de déflexion	Déflection coil	Ablenkspule	Bobina de deflección	Deflectie Spoolen
Diff.	Base diffusée	Diffused Base	Diffudierte Basis	Base difundida	Verspreide basis
E.C.	Emetteur commun	Common Transmitter	Emitterschaltung	Emisor común	Gemene uitzender
Epitax.	Epitaxial	Epitaxial	Epitaxial	Epitaxial	Epitaxial
Entrée	Etage d'entrée	Input Stage	Eingangsstufe	Fase de entrada	Ingangsverdiep
F_b	Facteur de bruit	Noise factor	Rauschfaktor	Factor de ruido	Geruchtsfactor
f_t	Fréquence de transition	Transition frequency	Transitfrequenz	Frecuencia de transición	Transitie frequentie
FI	Fréquence intermédiaire	Intermediate Frequency	Zwischenfrequenz	Frecuencia intermedia	Tussenfrekwentie
Ge	Germanium	Germanium	Germanium	Germanio	Germanium
GP	Gain en puissance	Power gain	Leistungsverstärkung	Ganancia de potencia	Krachtversterking
GV	Gain en tension	Voltage Gain	Spannungsverstärkung	Ganancia en tensión	Spanningsversterking
Hauteur	Hauteur d'image	Image height	Bildhöhe	Altura de imagen	Beeldhoogte
I_C	Courant de collecteur	Collector current	Kollektorstrom	Corriente de colector	Collectorstroom
Im.	Image	Image	Bild	Imagen	Beeld
L, Lig.	Ligne	Line	Zeile	Linea	Lijn
Lin.	Linéarité	Linearity	Linearität	Linearidad	Lijnvorming
Osc.	Oscillateur	Oscillator	Oszillator	Oscilador	Oscillator
Osc.bloqué	Oscillateur bloqué	Blocked Oscillator	Sperrschwinger	Oscilador bloqueado	Vastgelegde oscillator
Pl.	Planar	Planar	Planar	Planar	Planar
Préamplif.	Préamplificateur	Pre-amplifier	Vorverstärker	Preamplificador	Voorversterker
Redr.	Redresseur	Rectifier	Gleichrichter	Rectificador	Gelijkrichter
Retour	Ligne de retour	Feedback line	Rückführung	Linea de regreso	Terugvoerlijn
Sép.	Séparateur	Separatur	Impulstrennung	Separador	Onderscheider
Si	Silicium	Silicon	Silizium	Silicio	Silicium
Son	Son	Sound	Ton	Sonido	Geluid
Sortie	Etage de sortie	Out put Stage	Ausgangsstufe	Fase de salida	Uitgangsverdiep
THT	Très haute tension	Very High Voltage	Höchstspannung	Muy alta tensión	Zeer hoge spanning
Tr.	Transformateur	Transformer	Transformator	Transformador	Transformator
t_r	Temps de montée	Rise time	Anstiegszeit	Tiempo de subida	Opvoertijd

AC 121

p-n-p Ge Alliage β = 30... 250

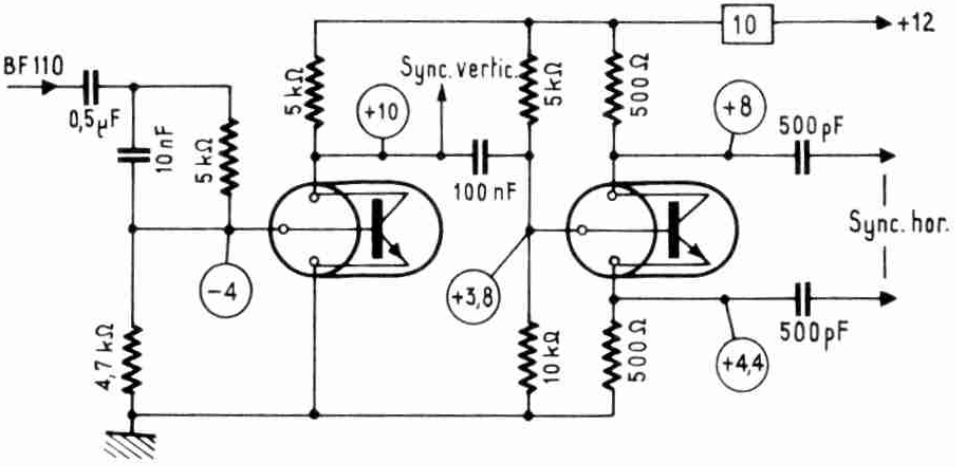
Osc. Images



AC 127

n-p-n Ge Alliage β = 65... 200

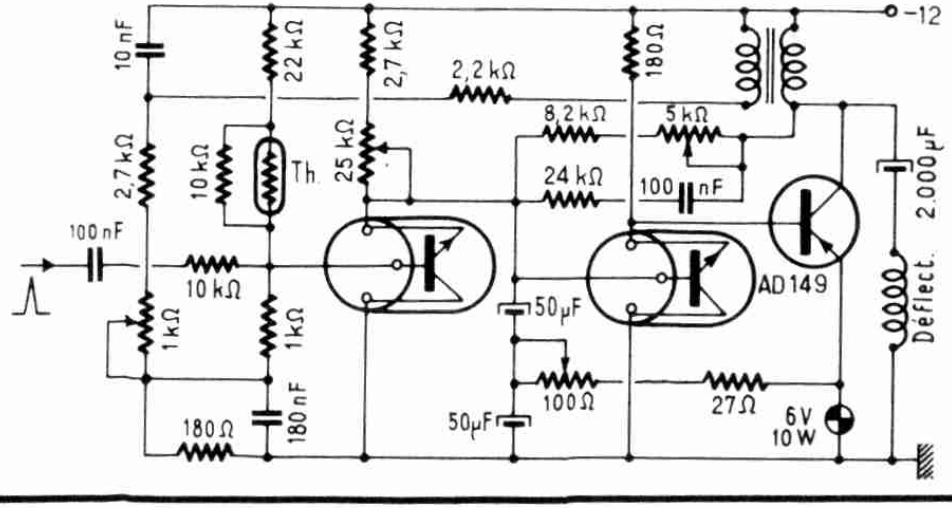
Séparateur



AC 127

n-p-n Ge All. β = 65... 200

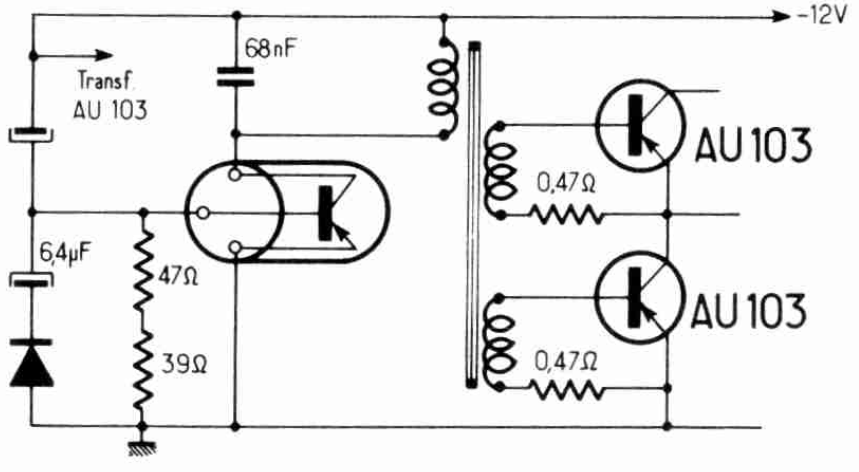
Bal. Images



AC 128

p-n-p Ge. All. β = 60... 175

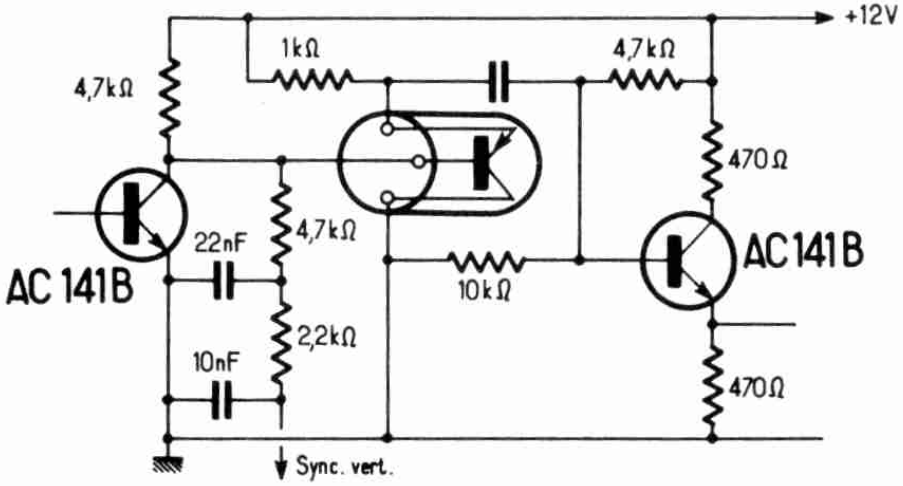
Bal. 625 I.



AC 137

p-n-p Ge All. ß=170

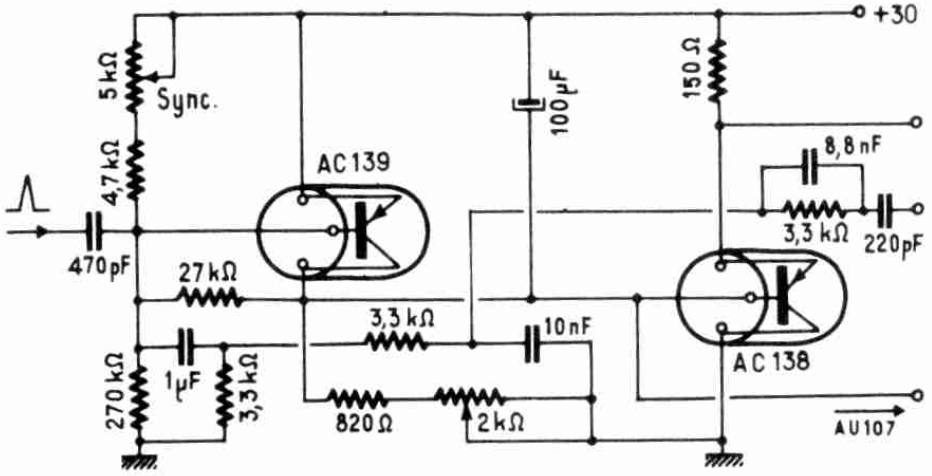
Amplif. sync.



AC 138 AC 139

p-n-p Ge All. β = 100

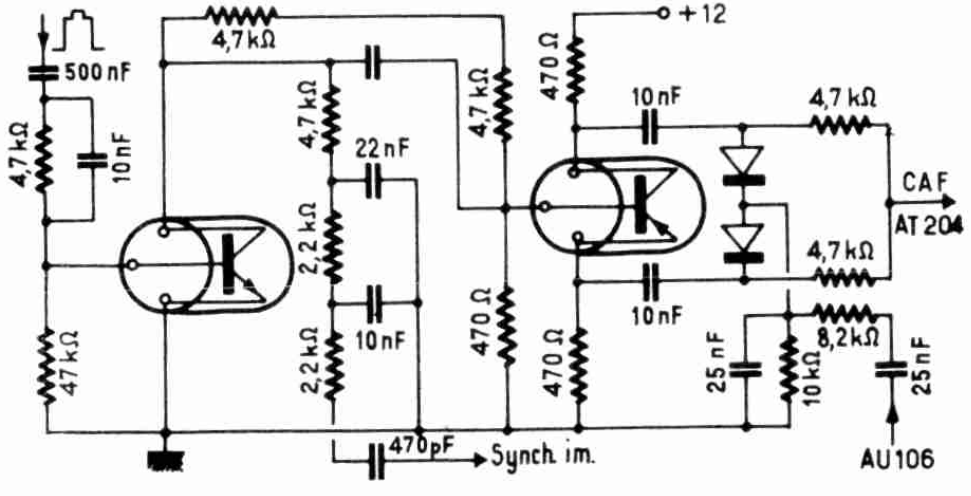
Bal. Images



AC 141

n-p-n Ge All. β = 40..180

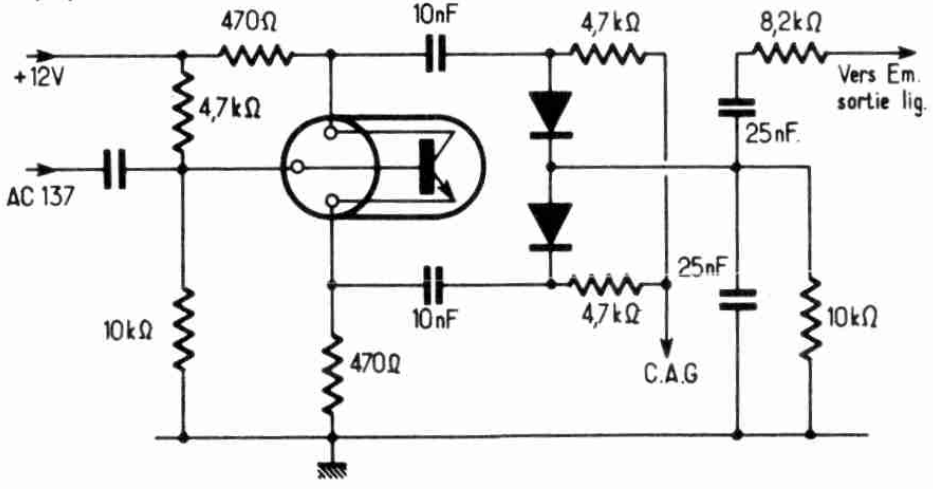
CAF Lignes



AC 141 B

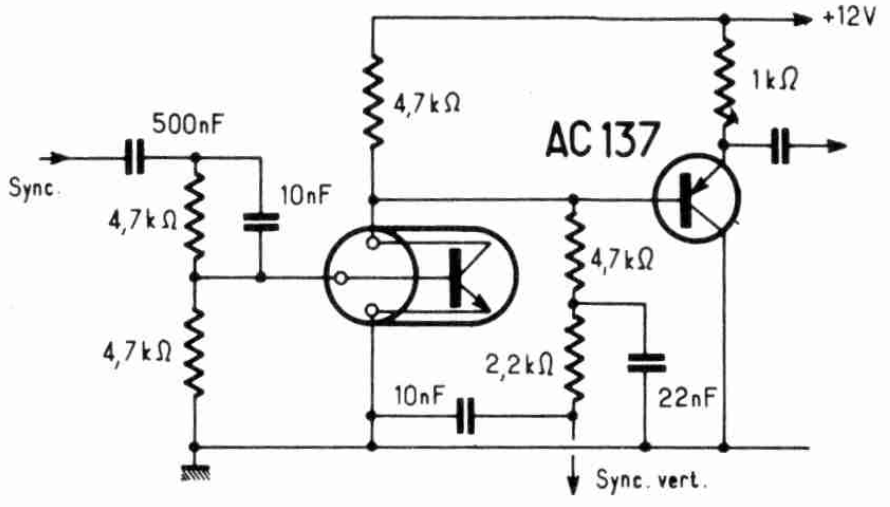
n-p-n Ge All. ß = 30...250
ft = 3MHz

Comp. phase



AC 141 B

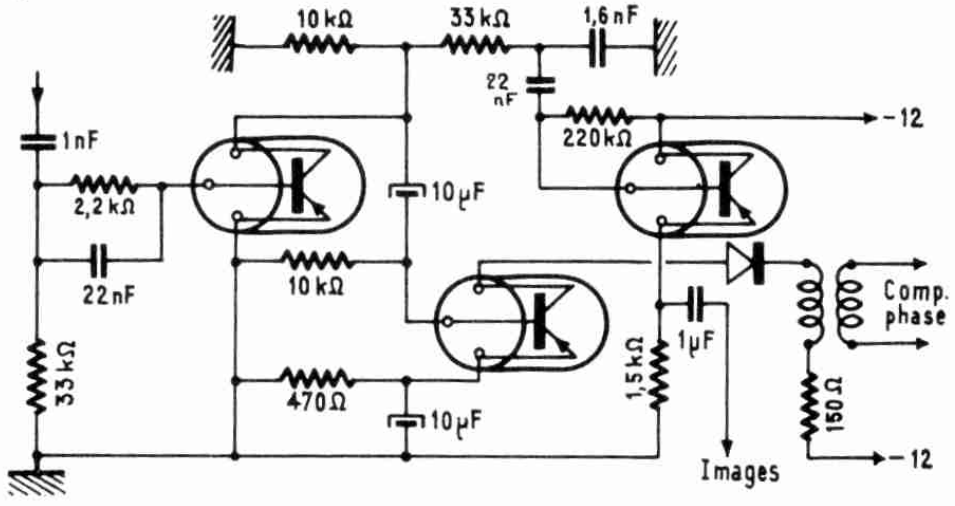
n-p-n Ge. All. ß = 30....250 ft = 3 MHz



AC 151

Séparateur

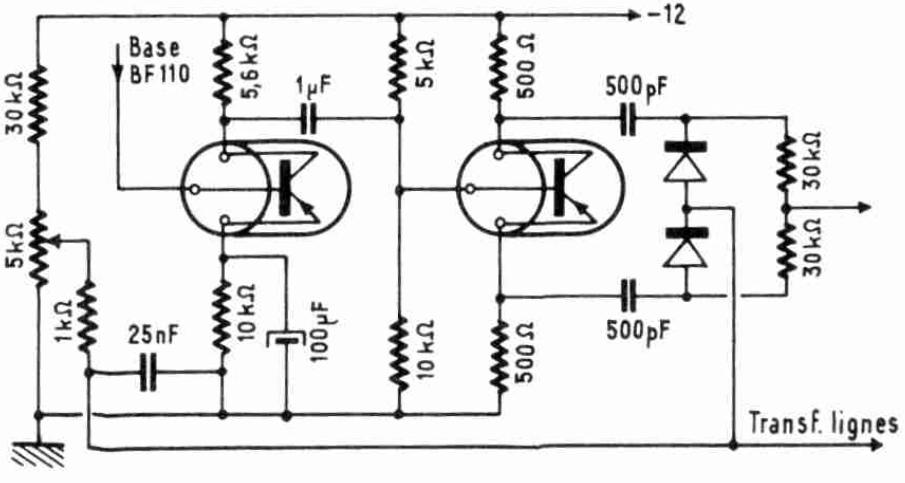
p-n-p Ge Alliage β =50



AC 151

Comp. phase (I)

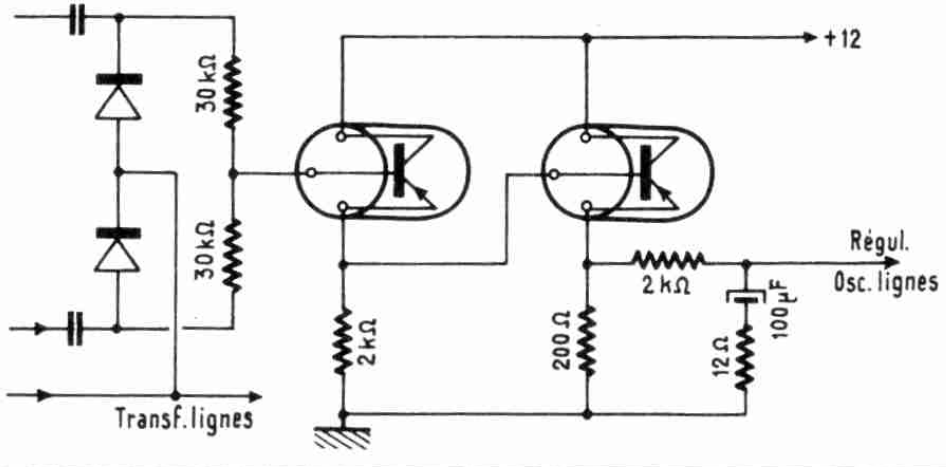
p-n-p Ge Alliage β =50



AC 151

Comp. Phase (II)

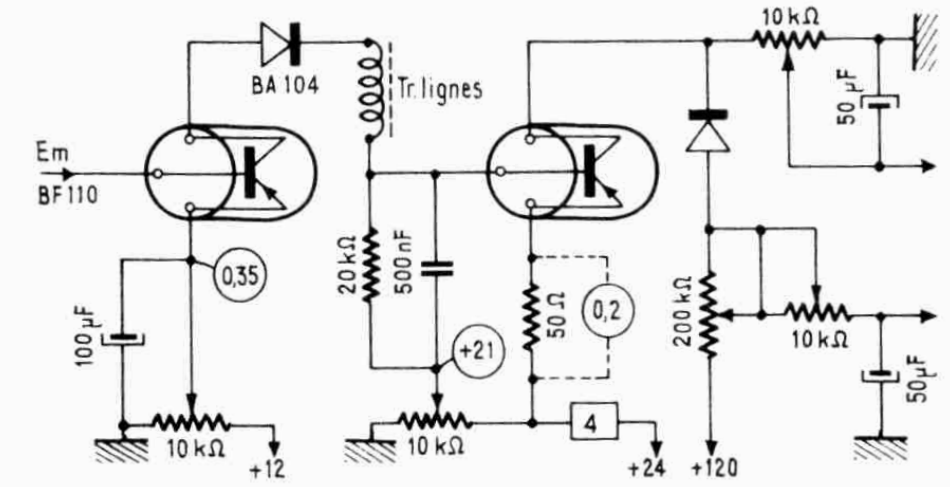
p-n-p Ge Alliage β =50



AC 152

p-n-p Ge Alliage β = 30...150

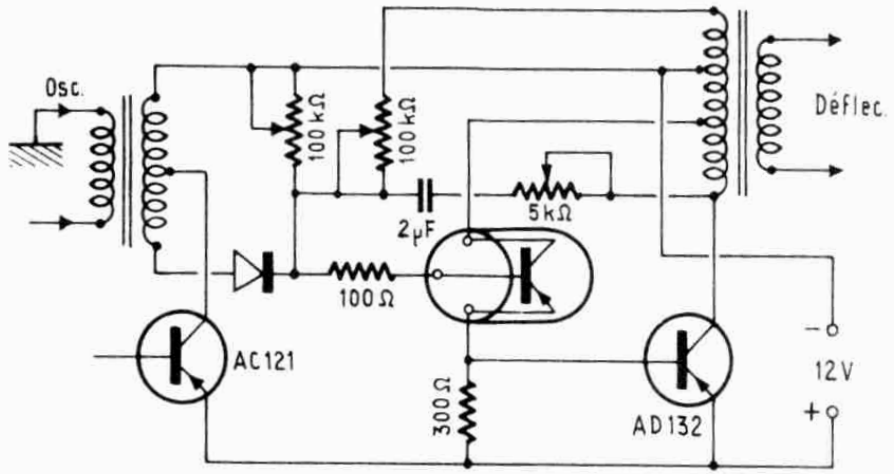
Amplif. C.A.G.



AC 153

p-n-p Ge Alliage β = 50...250

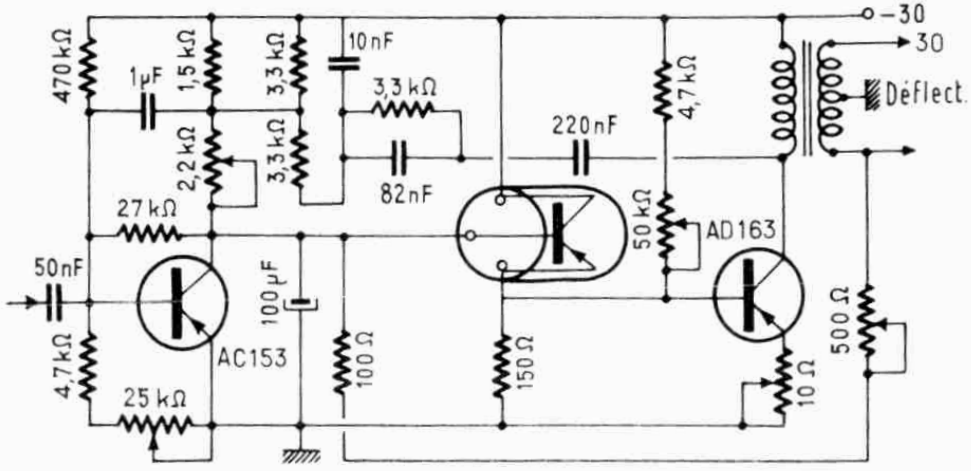
Bal. images



AC 153 K

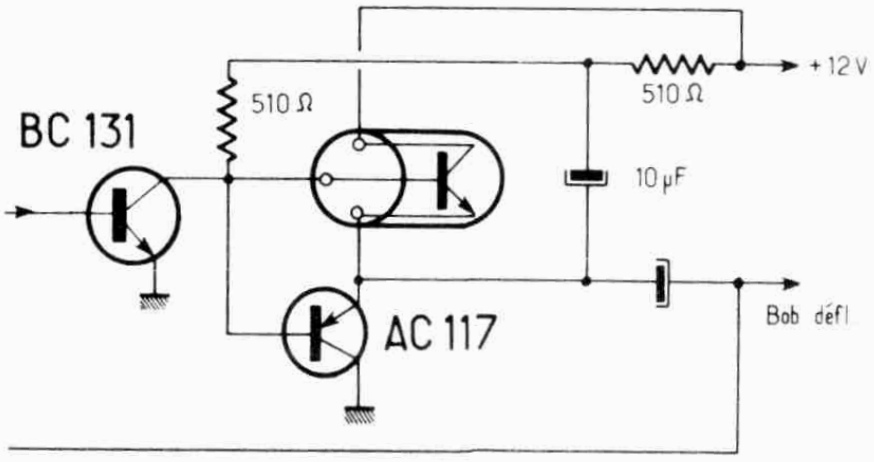
p-n-p β = 50

Bal. Images



AC 175

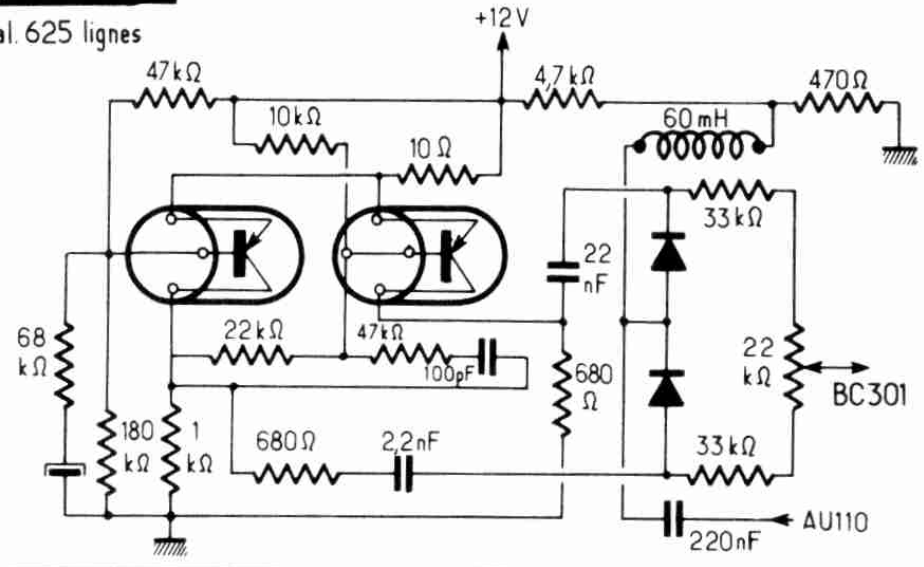
n-p-n Ge All. β = 60....165



AC 192

p-n-p Ge ß = 30.... 500

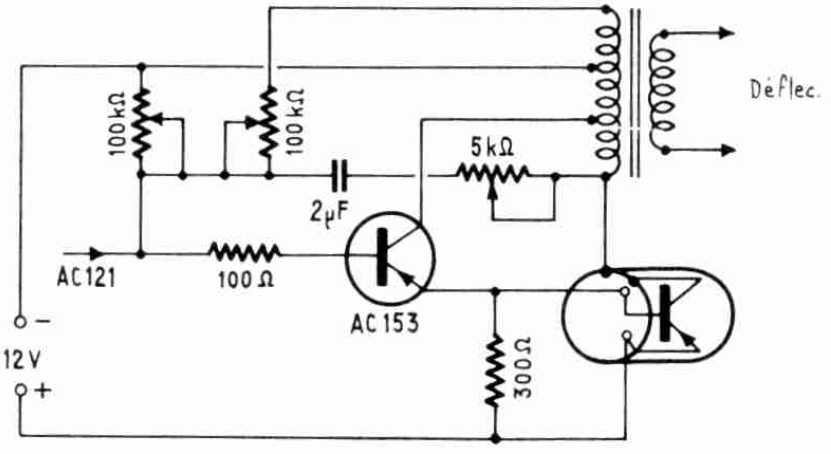
Bal. 625 lignes



AD 132

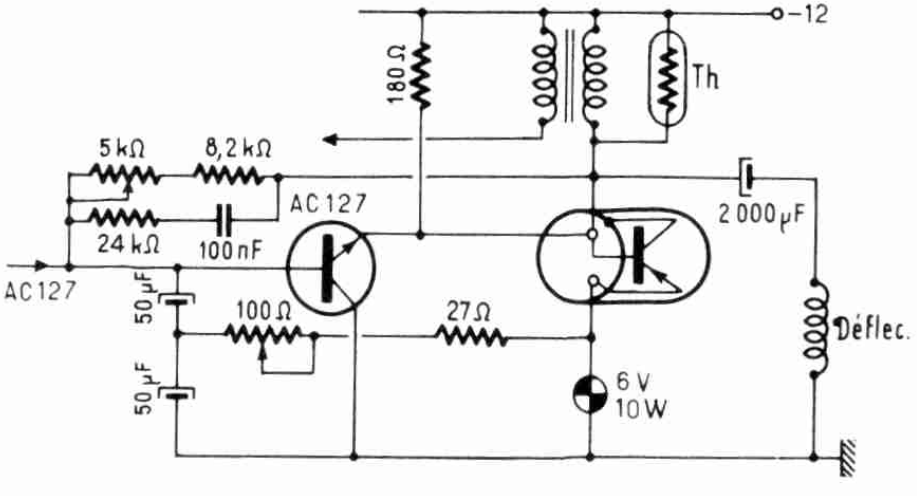
p-n-p Ge Alliage β = 20...100

Bal. images



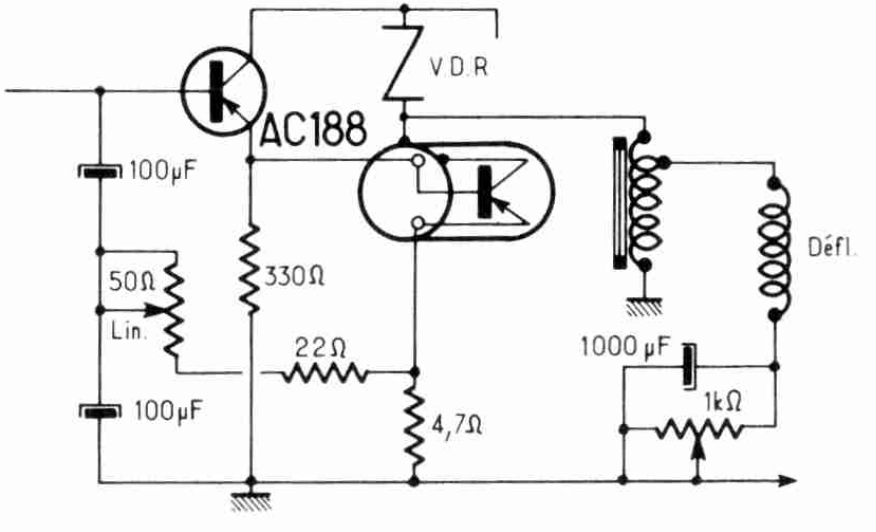
AD 149

p-n-p Ge All. β = 50...100



AD 162

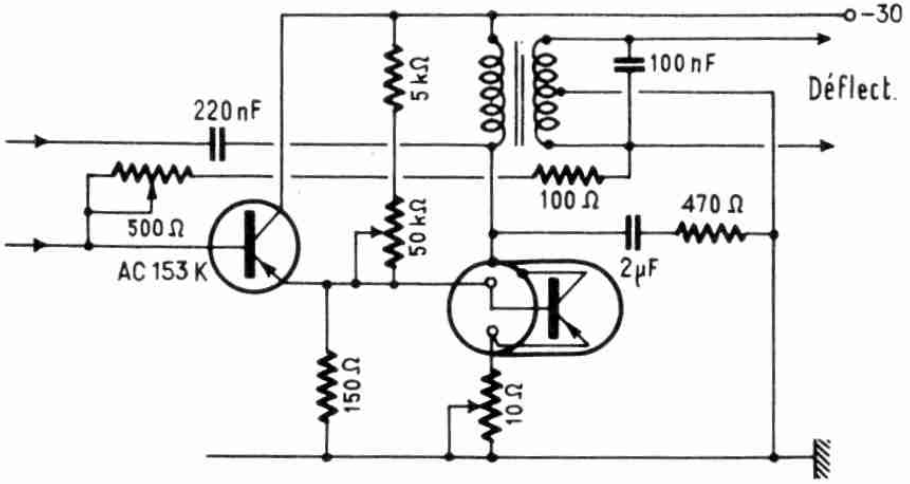
p-n-p Ge Al. ß = 50....350



AD 163

p-n-p Ge All. β = 12...60

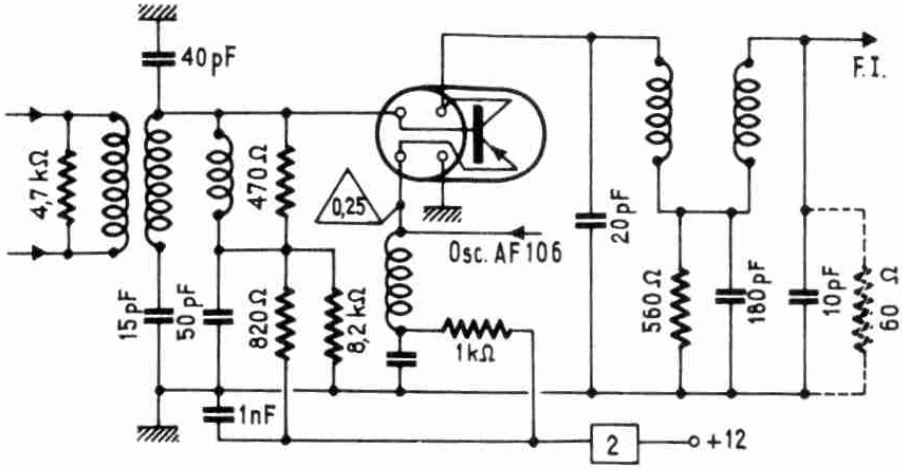
Sortie Images



AF106

p-n-p Ge Mesa β = 70
F_b = 9 dB

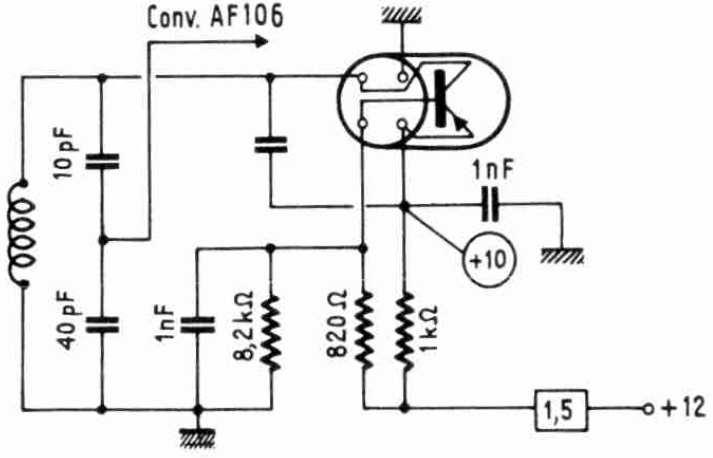
Conv. VHF



AF106

p-n-p Ge Mesa β = 70

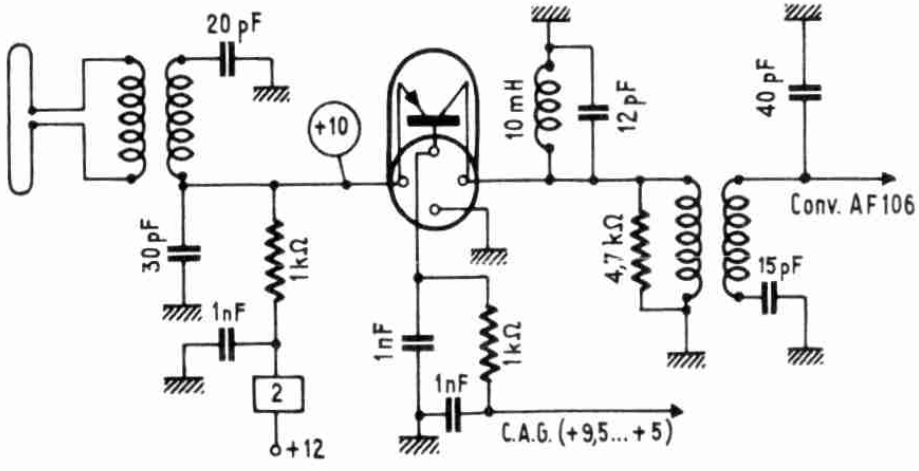
Osc. VHF



AF109

p-n-p Ge Mesa β = 100
GP = 15 dB
F_b = 5 dB

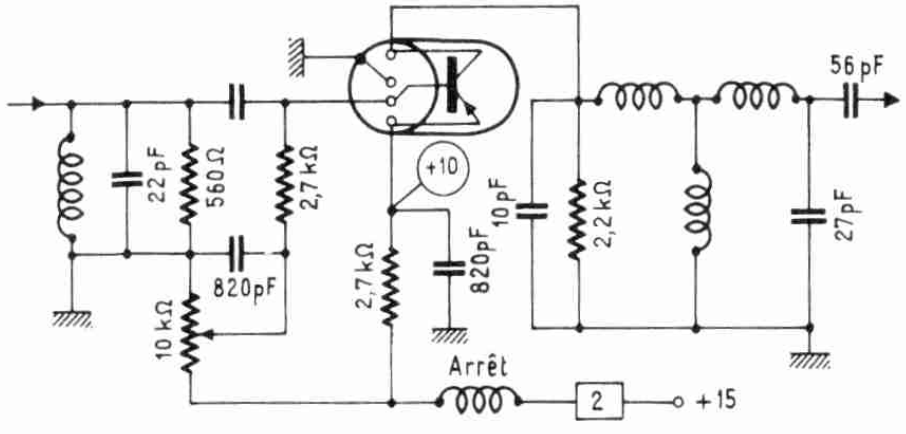
Entrée VHF



AF114

p-n-p Ge Mesa β = 150

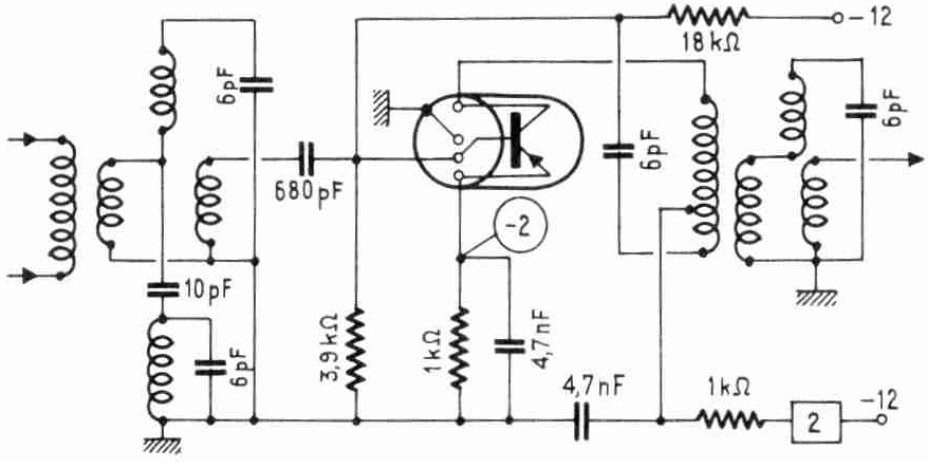
F.I. 819 l



AF115

p-n-p Ge Mesa

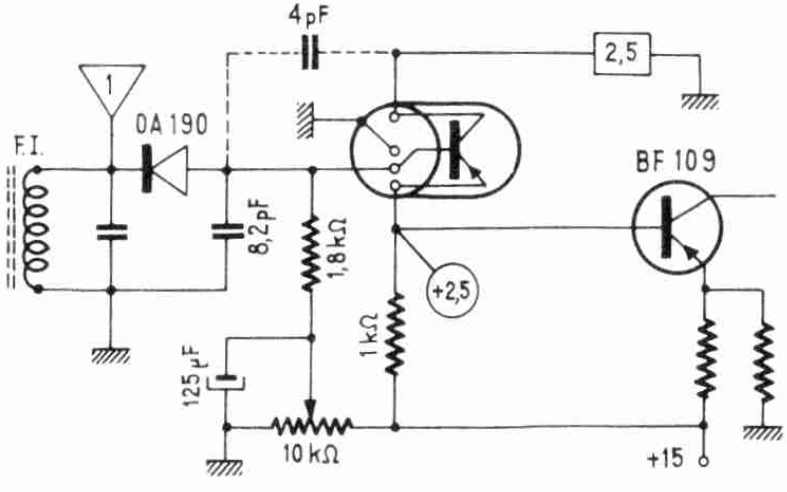
F.I.



AF117

p-n-p Ge Mesa β = 150

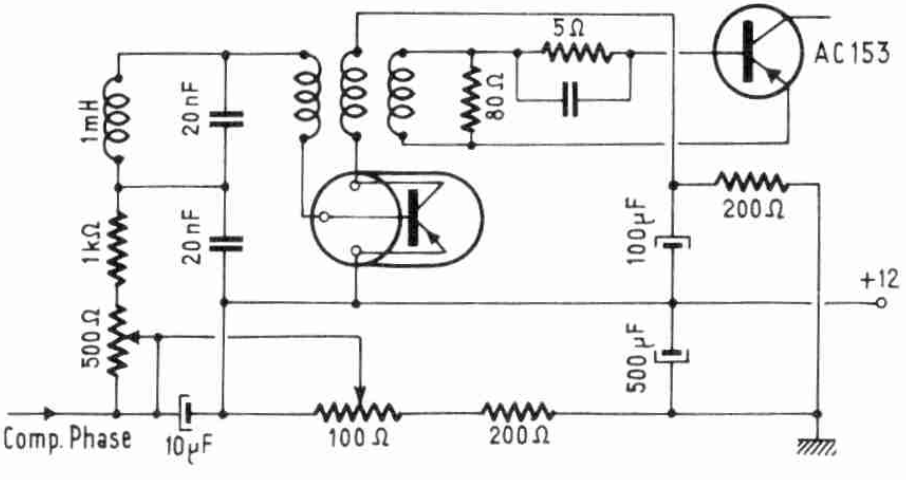
Vidéo 819 l



AF117

p-n-p Ge Mesa β = 140

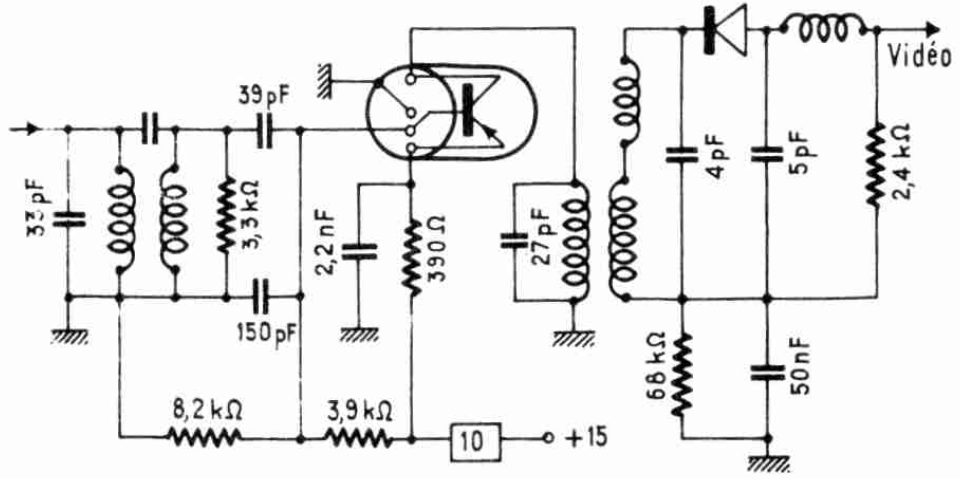
Osc. lignes (625)



AF118

p-n-p Ge Mesa β = 200

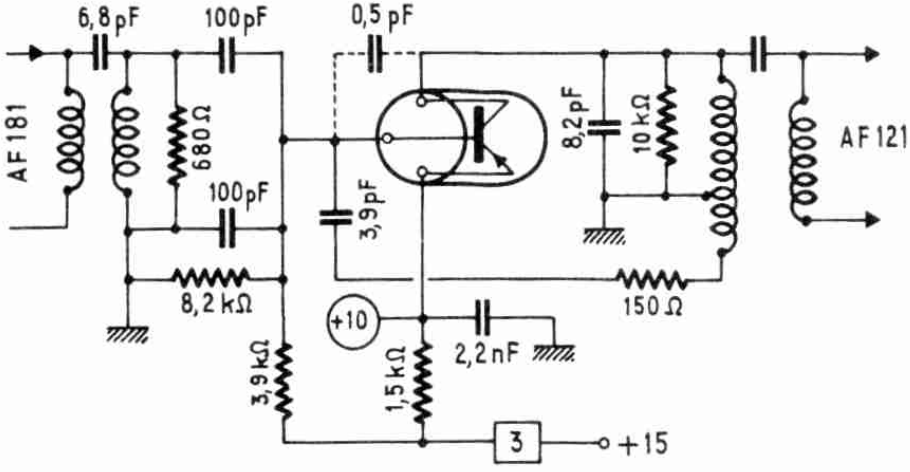
Sortie F.I



AF121

p-n-p Ge All.-diff. β = 50

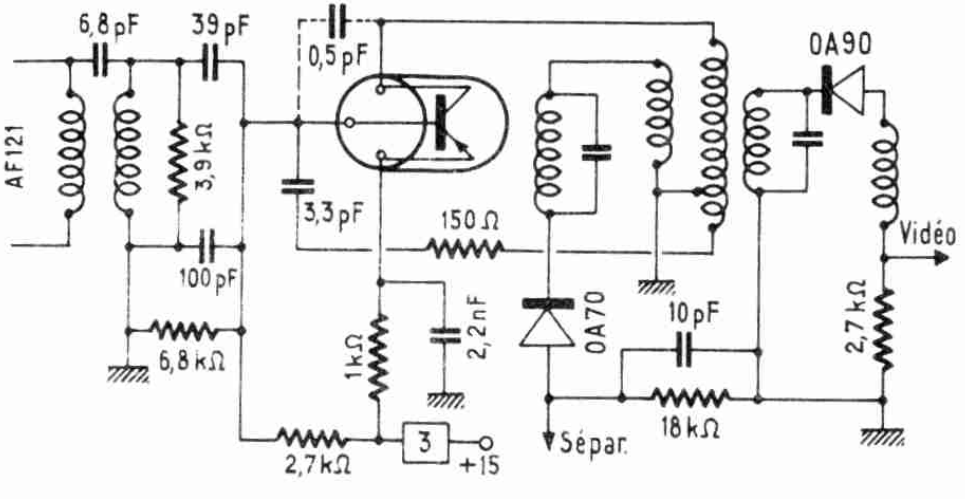
F.I II 625l



AF121

p-n-p Ge All.-diff. β = 50

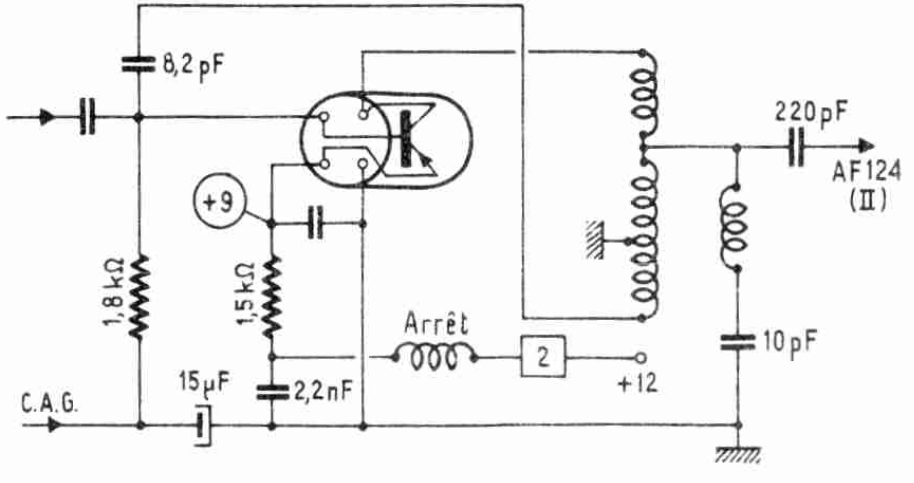
F.I. III 625 L.



AF124

p-n-p Ge Mesa β = 150

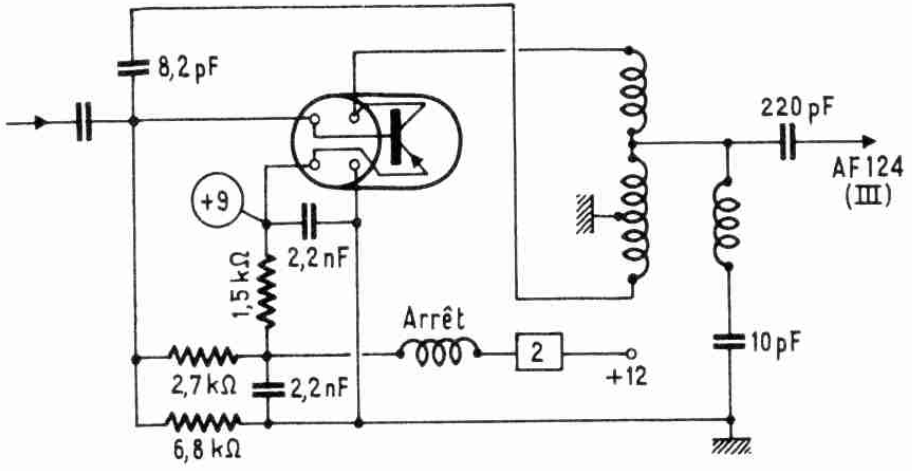
F.I.(I)



AF 124

p-n-p Ge Mesa β = 150

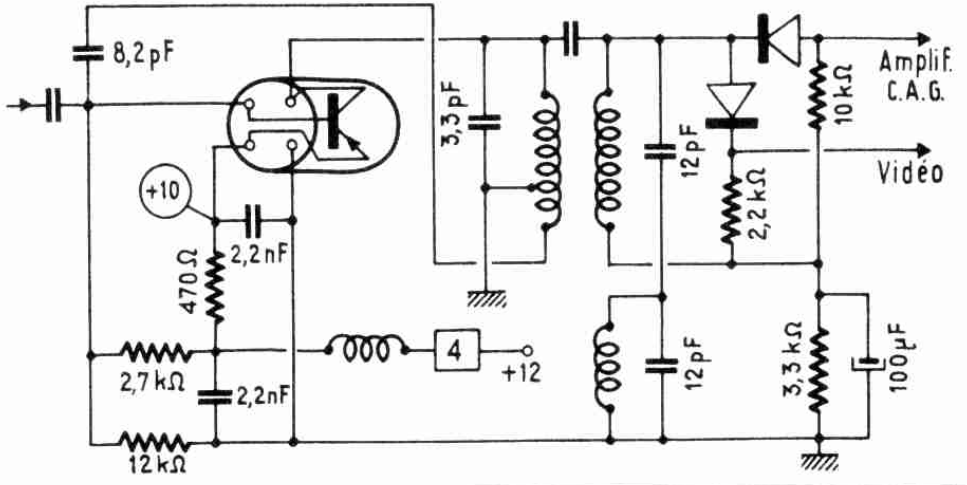
F.I. II



AF 124

p-n-p Ge Mesa β = 150

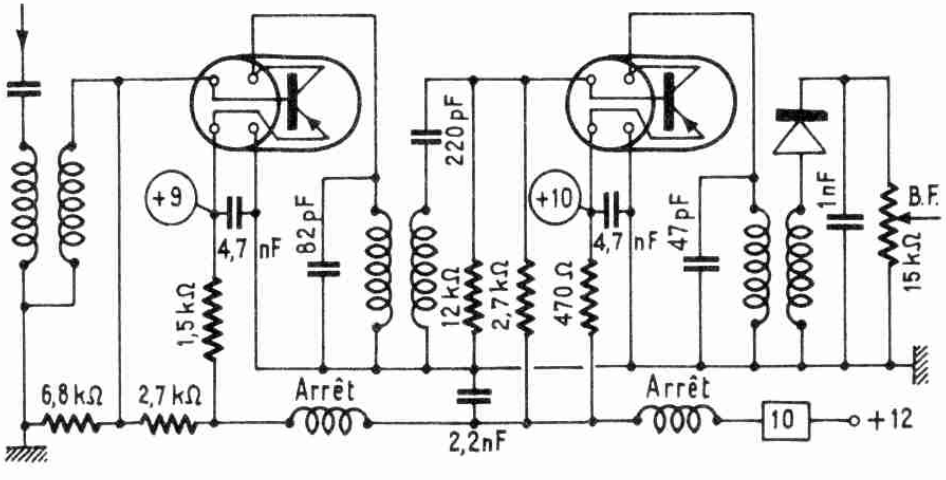
F.I. III



AF 124

p-n-p Ge Mesa β > 150

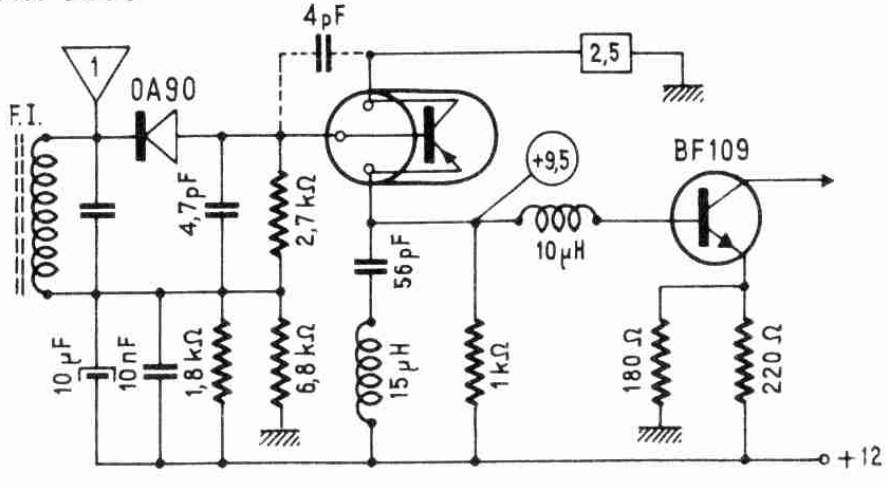
F.I. son



AF 127

p-n-p Ge Mesa β = 150

Vidéo 625 l

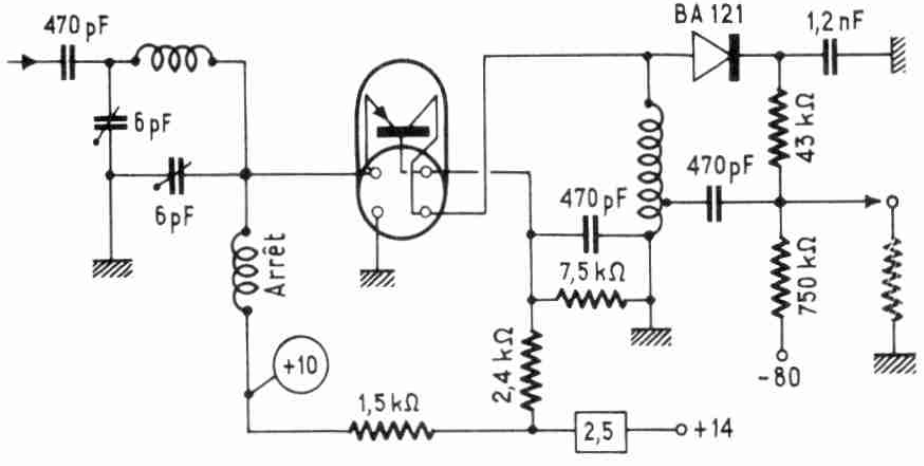


AF 139

Amplif. Ant. Bande IV

p-n-p Ge Mésa

$\beta = 60$
$F_b = 5$ dB
GP = 10dB

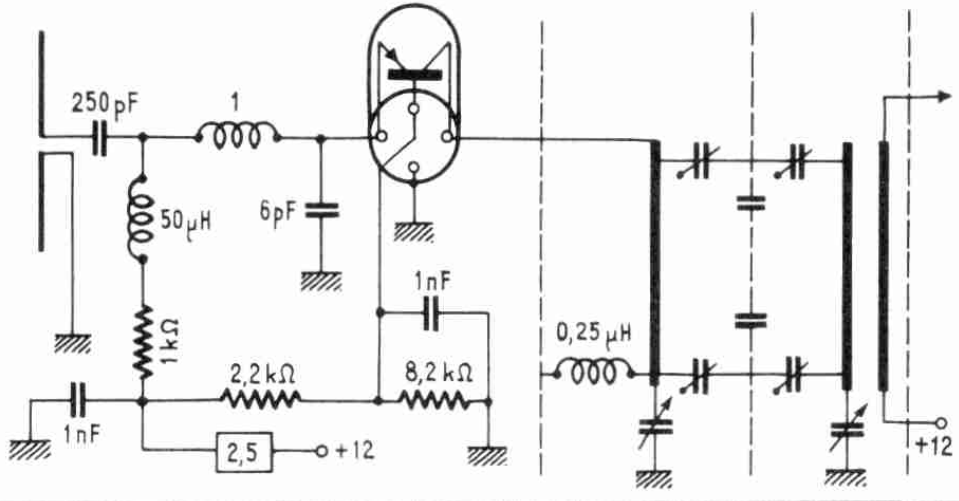


AF 139

Entrée U.H.F.

p-n-p Ge Mésa

$\beta = 50$
GP = 10 dB
F_b = 8 dB

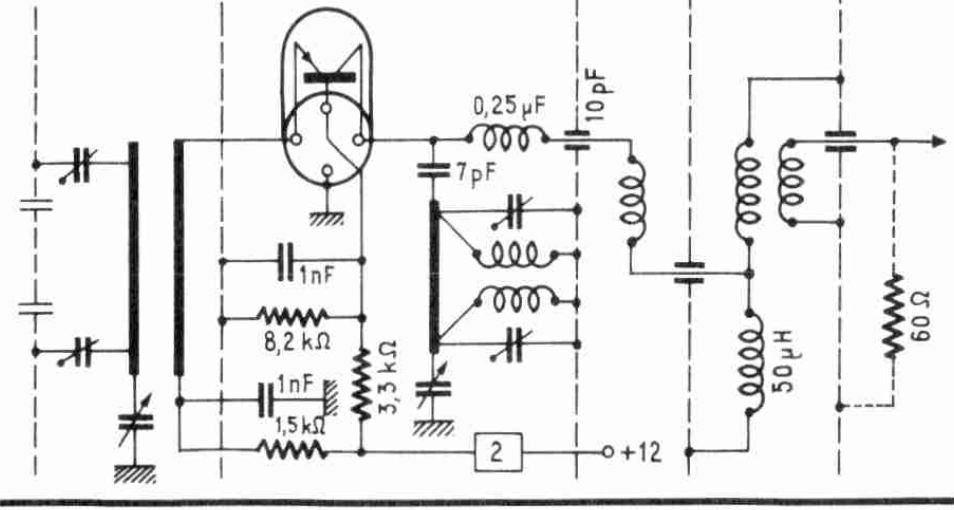


AF 139

Conv. UHF

p-n-p Ge Mesa

$\beta = 50$
GP = 8,5 dB
F_b = 14,5dB

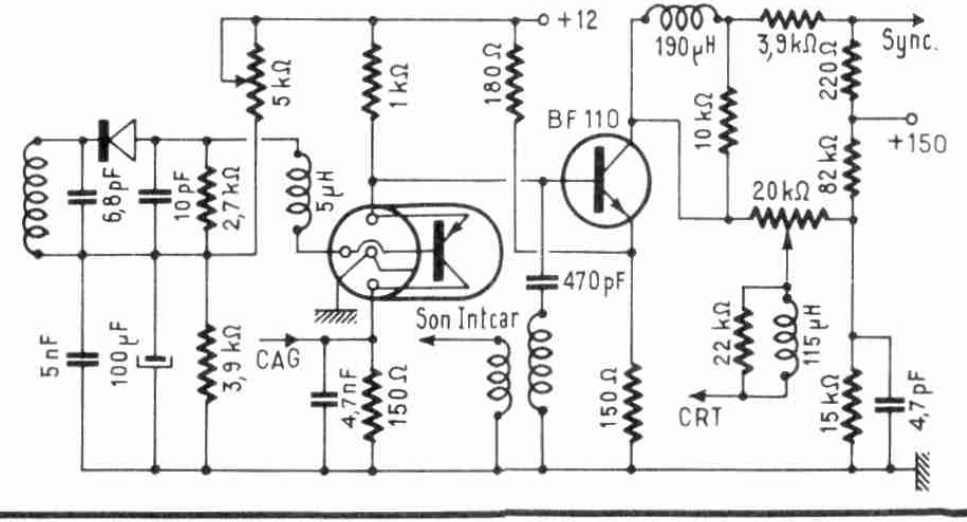


AF 164

Vidéo 625 L

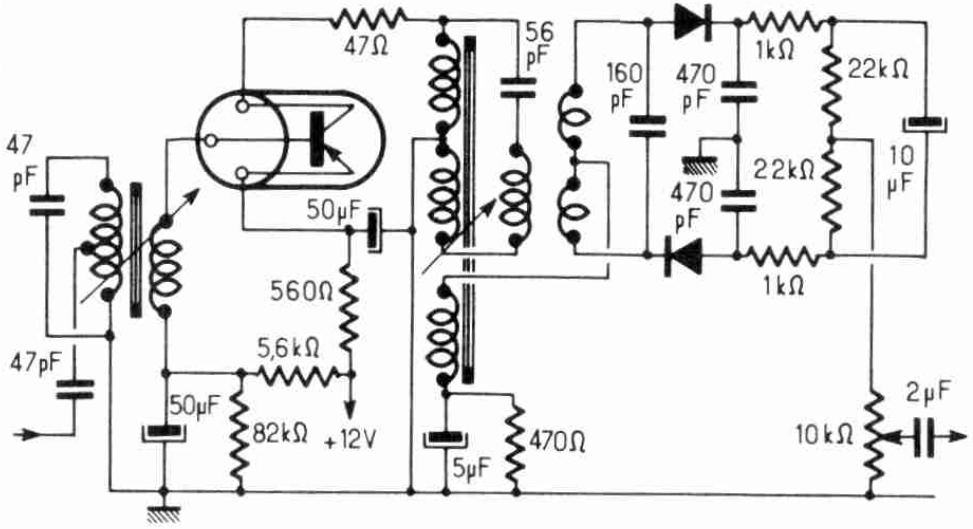
p-n-p Ge Drift

$\beta = 85$



AF 166

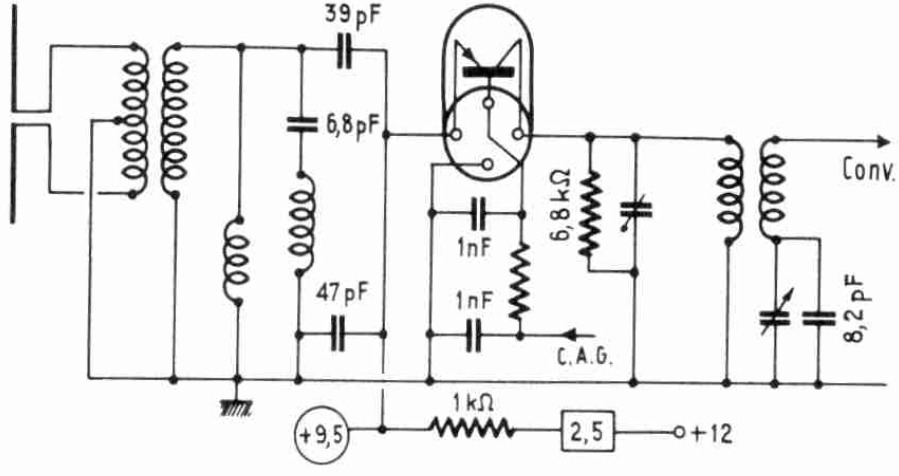
p-n-p Ge Drift β = 85



AF 180

p-n-p Ge All.-diff. β > 15

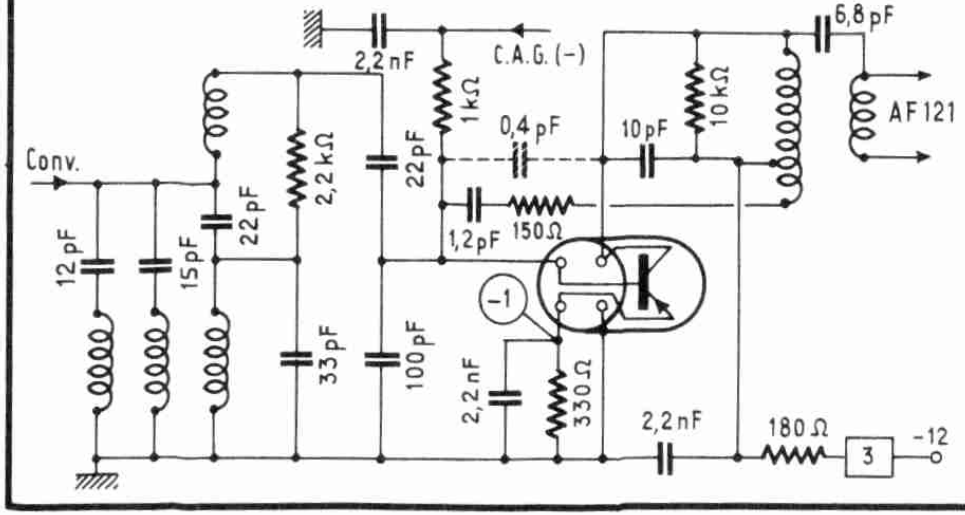
Entrée VHF



AF 181

p-n-p Ge All.-diff. β > 25

F.I. 625 l.

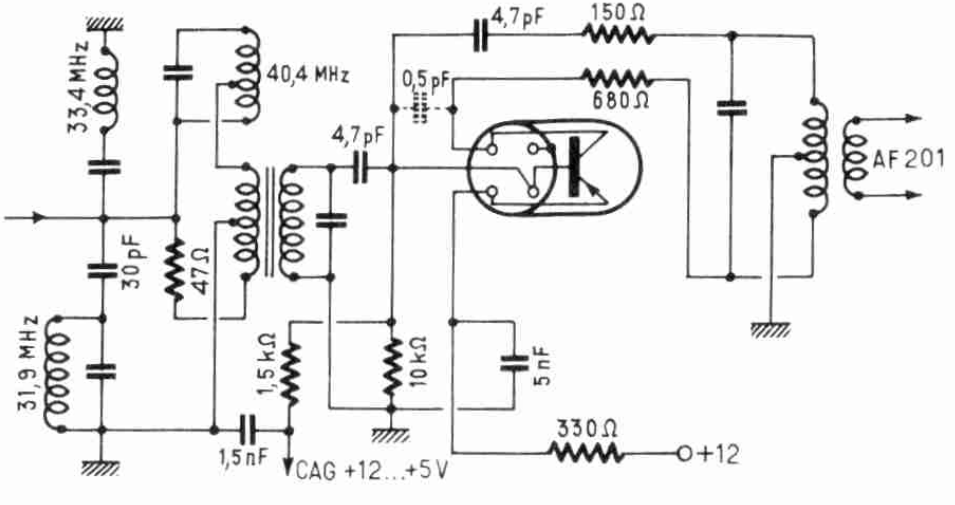


AF 200

p-n-p Ge Mesa β = 150

GP = 29 dB max

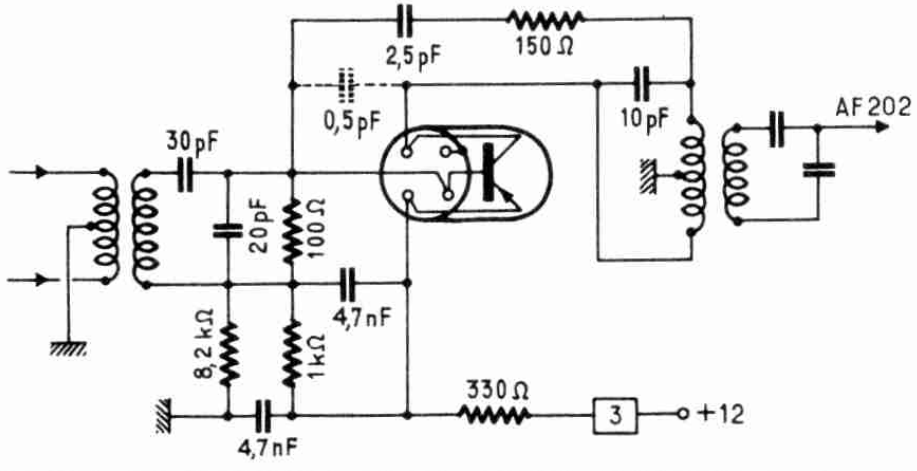
FI 625 L (I)



AF 201

FI 625 L (II)

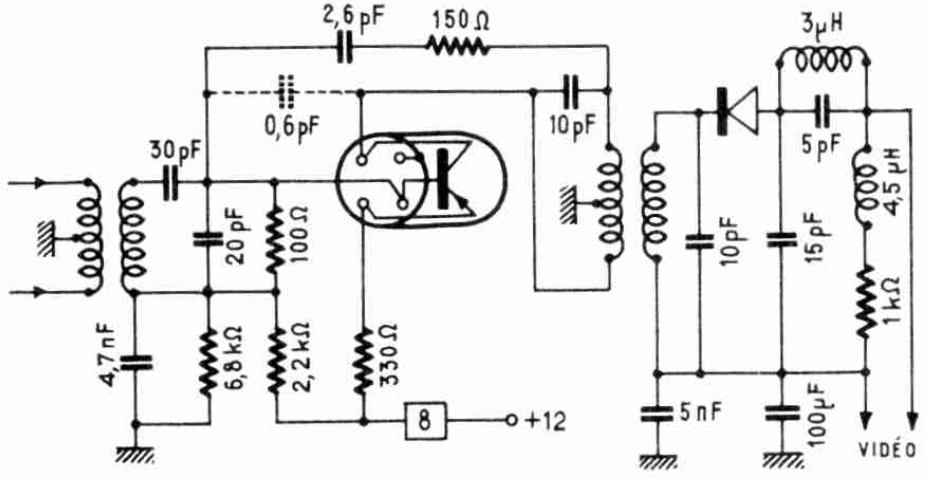
p-n-p Ge Mesa β = 150 GP = 30dB



AF 202

FI 625 L (III)

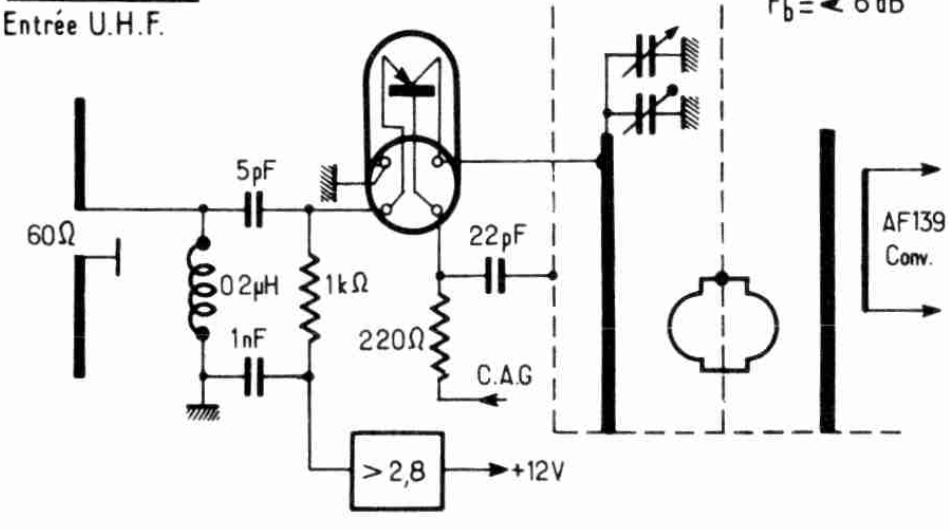
p-n-p Ge Mesa β = 150 GP = 31 dB max



AF 239

Entrée U.H.F.

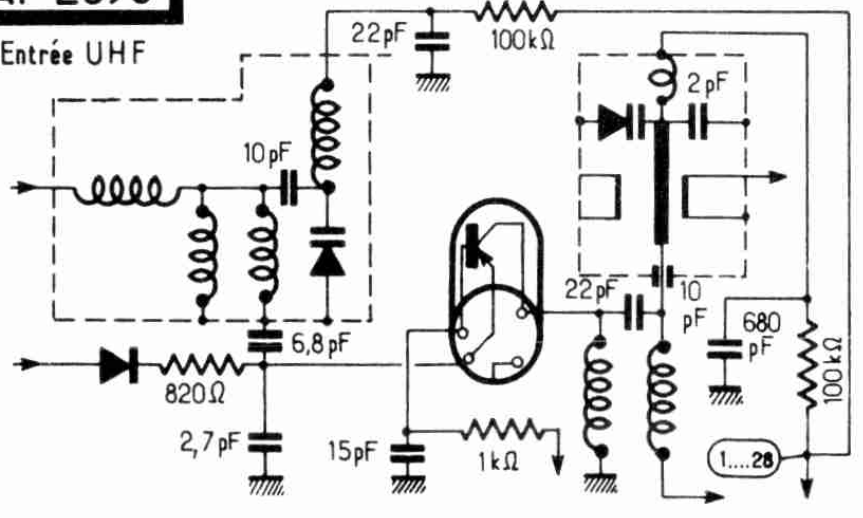
p-n-p Ge Mesa ß=33(>10) GP=11...14dB F_b = < 6dB



AF 239S

Entrée UHF

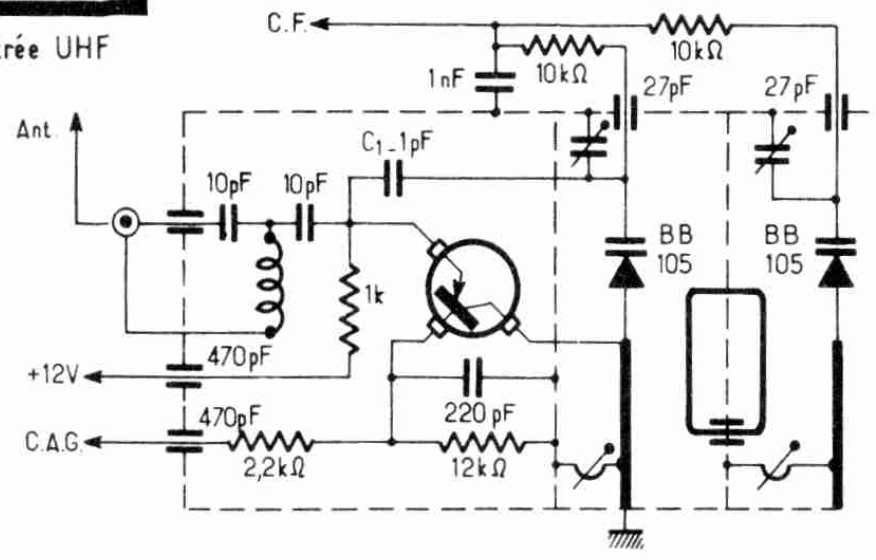
p-n-p Ge F_b >6dB f_t =780 MHz ß=50(>10)



AF 279

n-p-n Ge $F_b = 5\,dB$ $F_T = 780\,MHz$ $\beta = 50 (>10)$

Entrée UHF

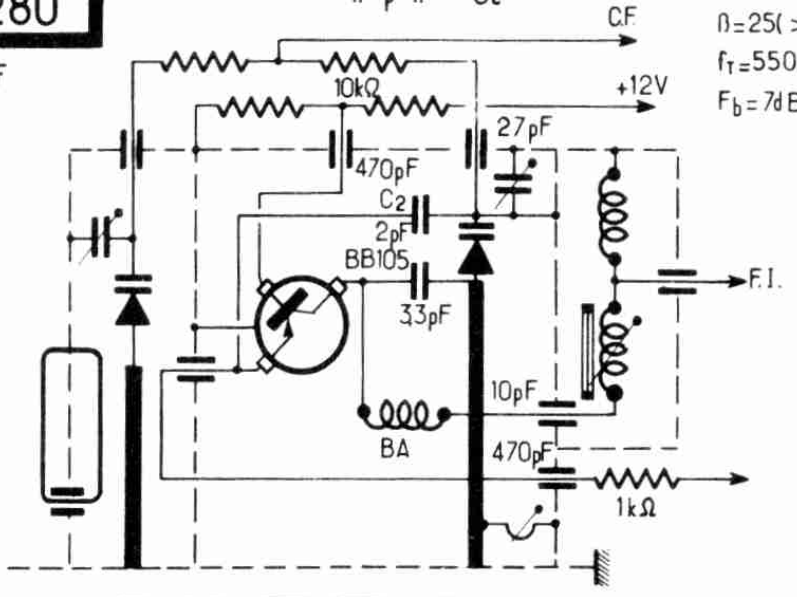


AF 280

n-p-n Ge

Conv. UHF

$\beta = 25 (>10)$
$f_T = 550\,MHz$
$F_b = 7\,dB$

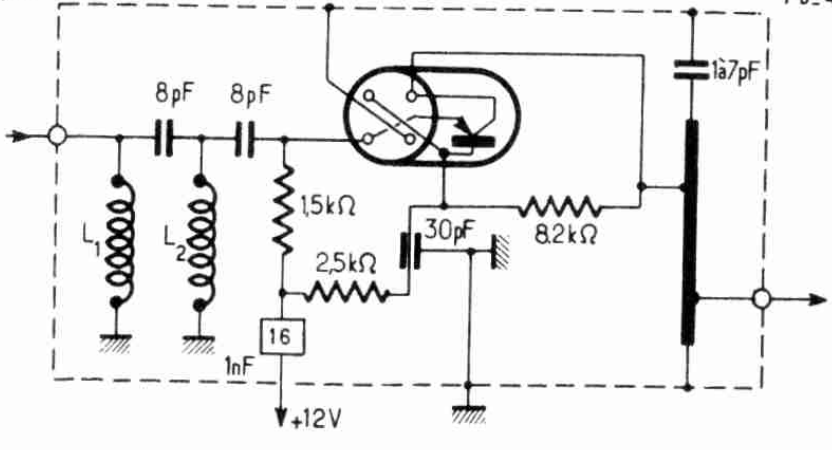


AFY 42

p-n-p
Ge Mesa

Amplif. ant. UHF

$\beta = 5 (>10)$
$f_T = 700\,MHz$
$GP = 12\,dB$
$Fb = 4\,dB$

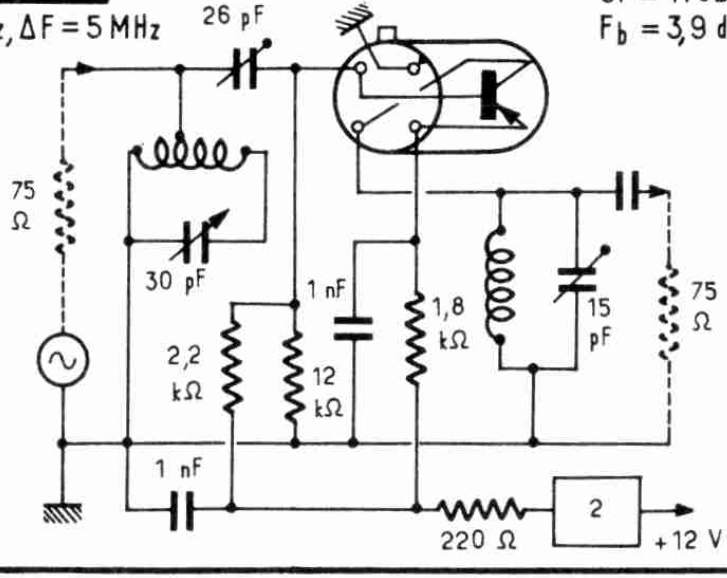


AFZ 12

p-n-p

200 MHz, $\Delta F = 5\,MHz$

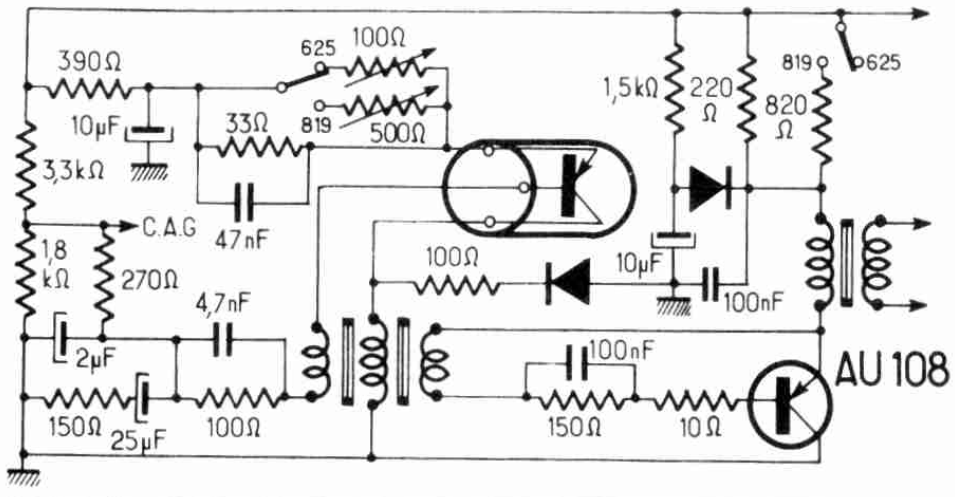
$\beta = 60$
$GP = 11\,dB$
$F_b = 3{,}9\,dB$



AT 209

p-n-p Ge All. β = 30...500 F_t = 7 MHz

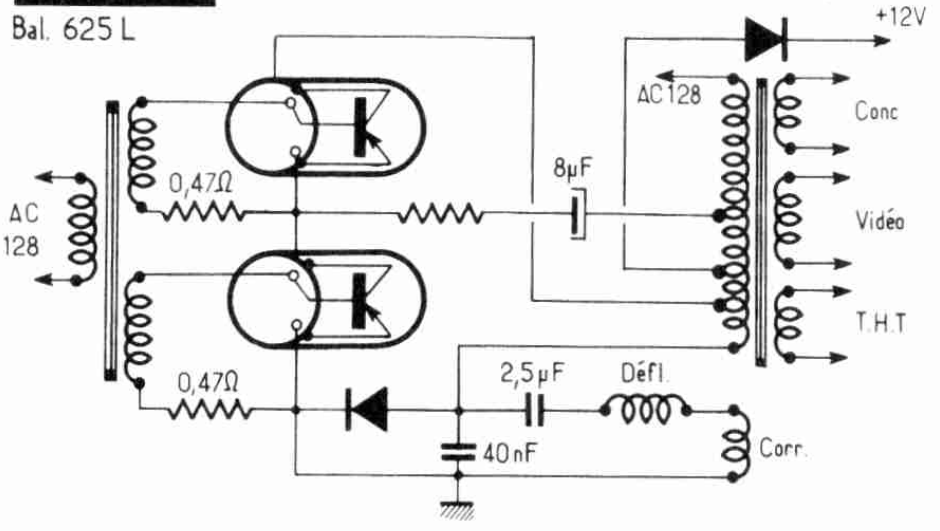
Bal. 625-819 L



AU 103

p-n-p Ge All. β > 15 t_s < 3 µs

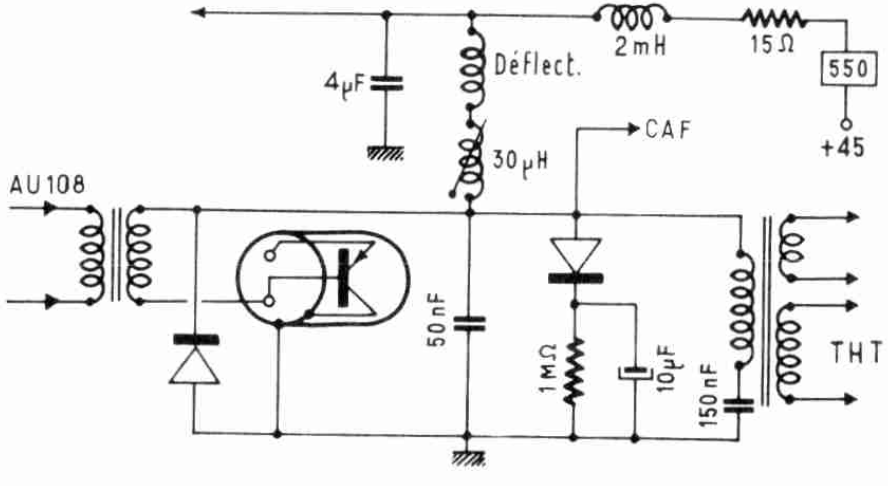
Bal. 625 L



AU 106

p-n-p Ge Diffusion

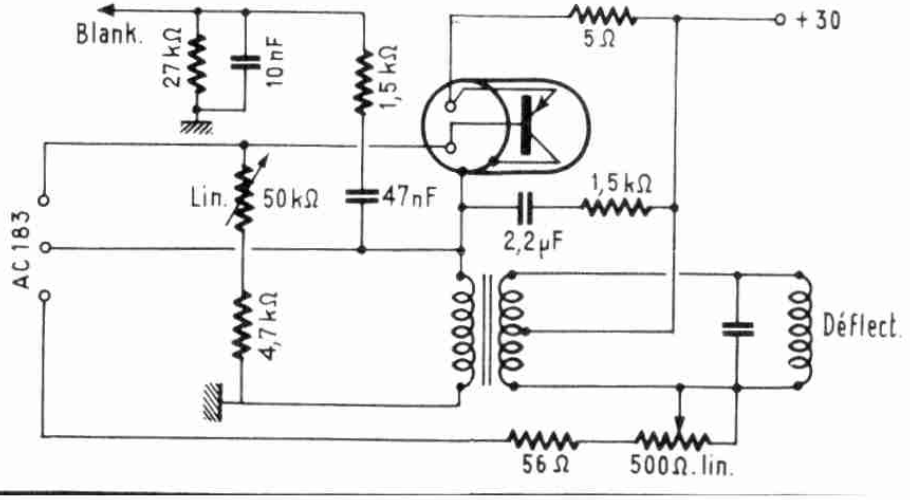
Sortie Lignes



AU 107

p-n-p Ge

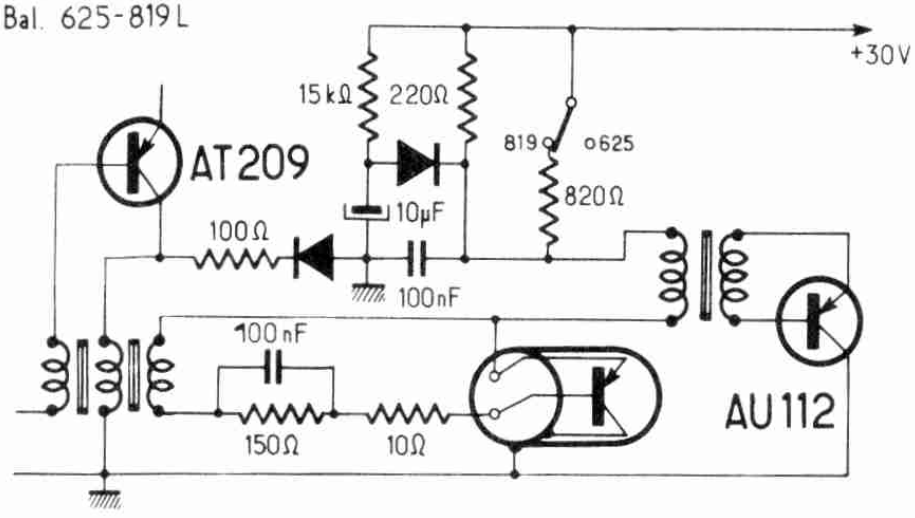
Sortie Images



AU 108

p-n-p Ge All. ß>35

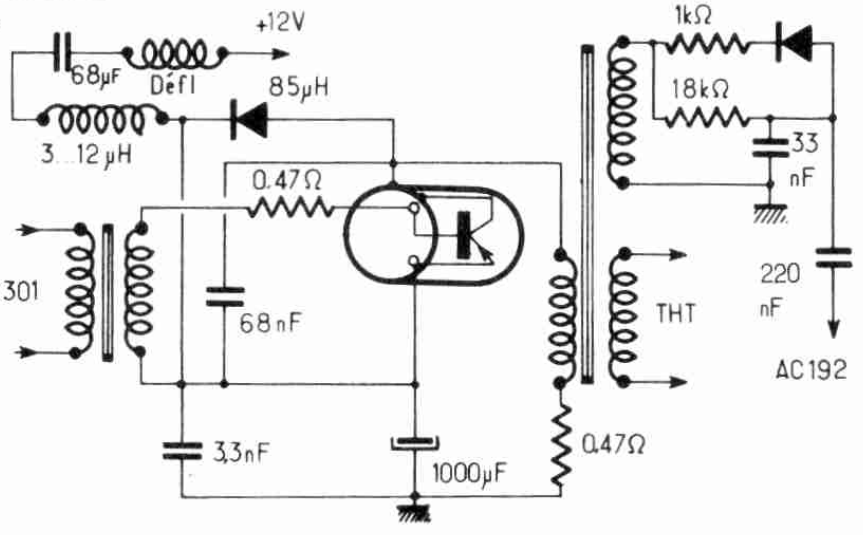
Bal. 625-819 L



AU 110

p-n-p Ge All. diff. t_{off}<2µs ß=20...90

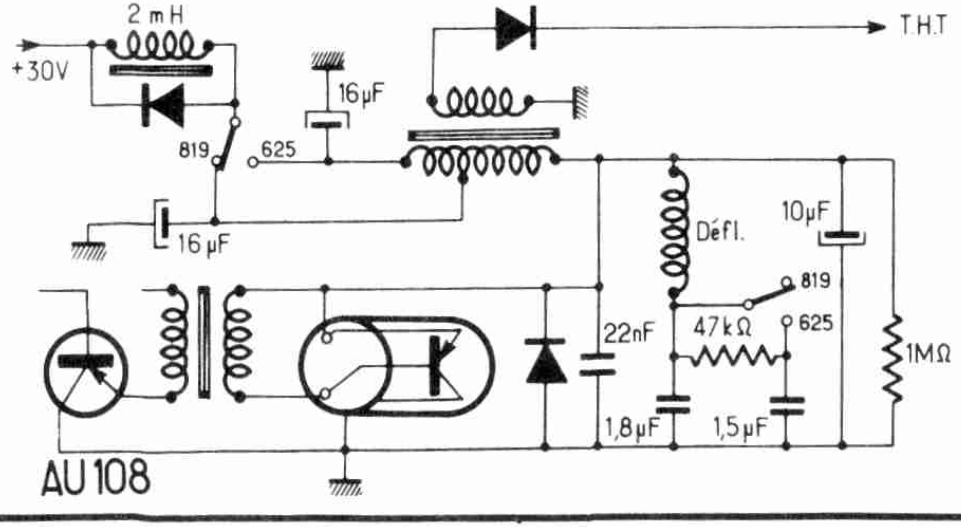
Bal. lignes



AU 111-AU 112

p-n-p Ge All. ß=15...40 t_{off}<750 ns

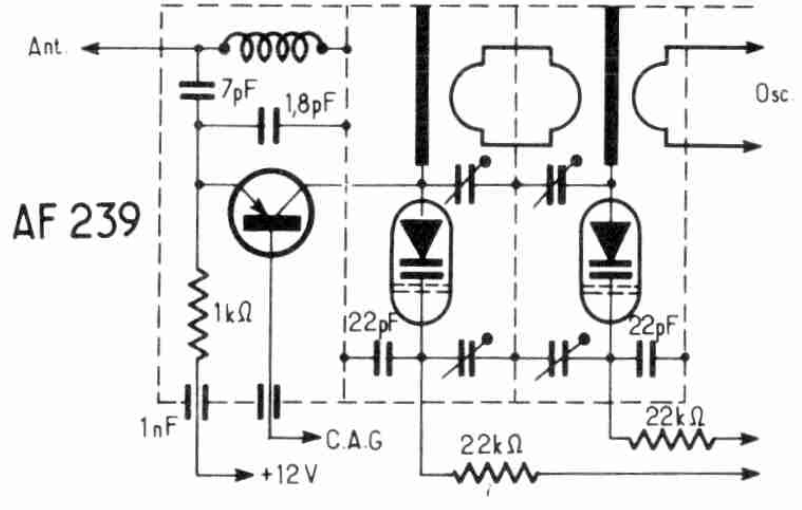
Bal. 625-819 L



BA 139

Diode C.V. Si 3....12 5 pF 3....25V

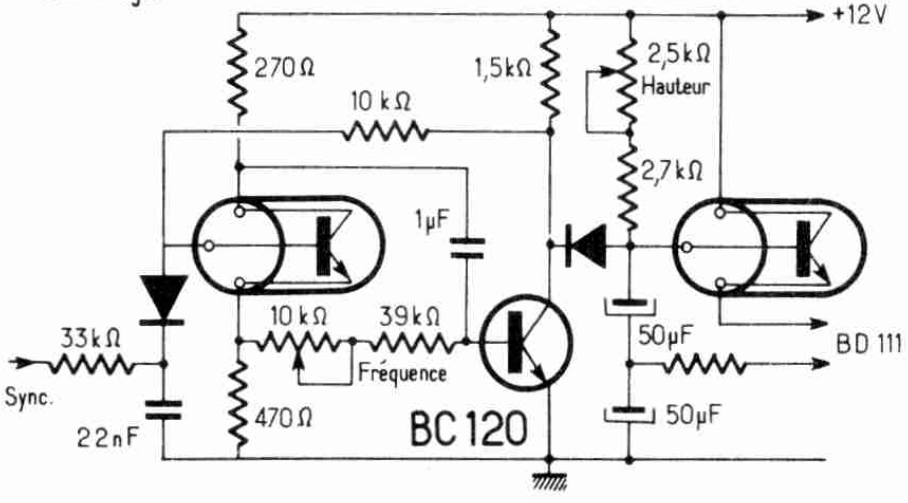
Accord U.H.F.



BC 115

n-p-n Si Planar ß = 100.... 400

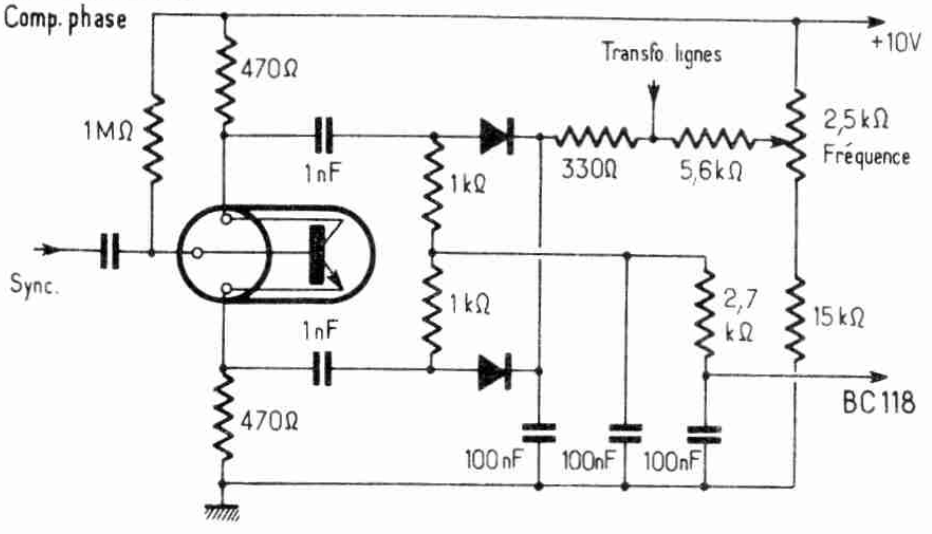
Multiv. images



BC 115

n-p-n Si Planar ß = 100.... 400

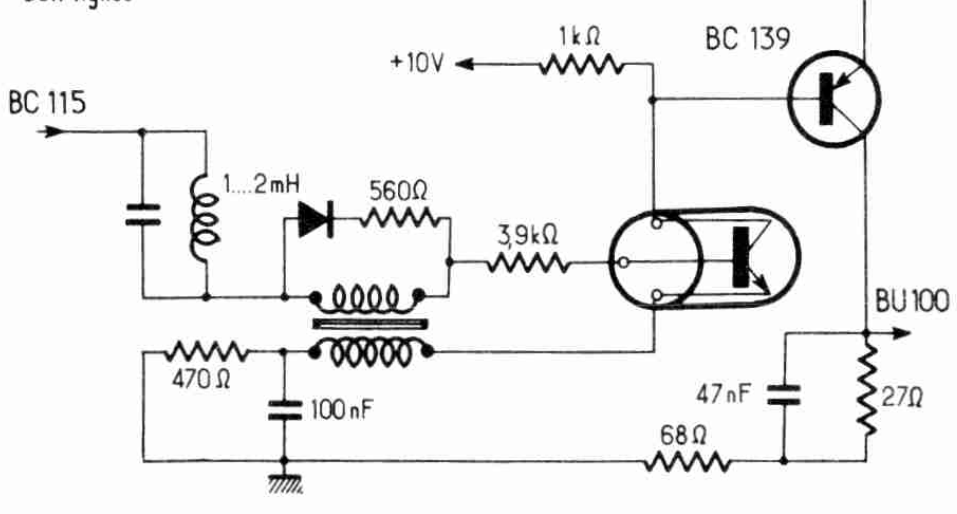
Comp. phase



BC 118

n-p-n Si Planar ß = 40....160

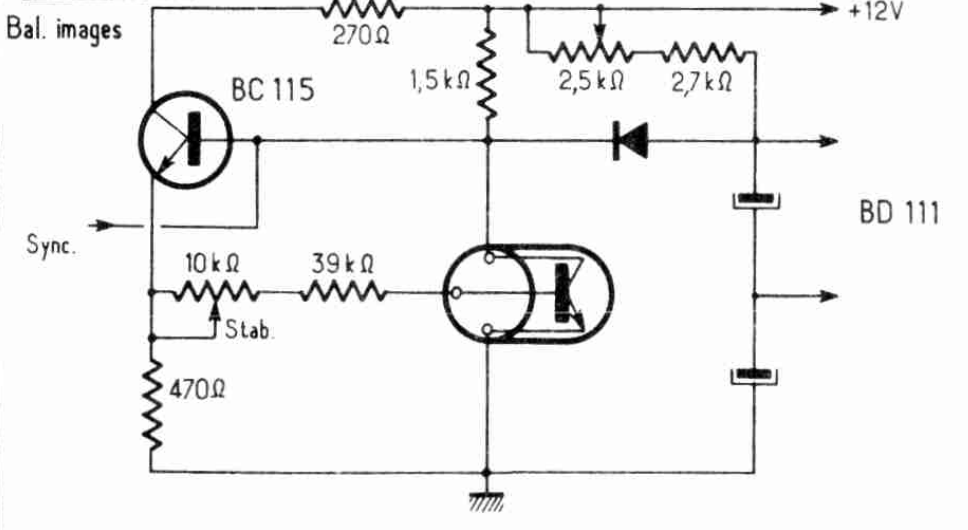
Bal. lignes



BC 120

n-p-n Si ß = 60(> 20)

Bal. images

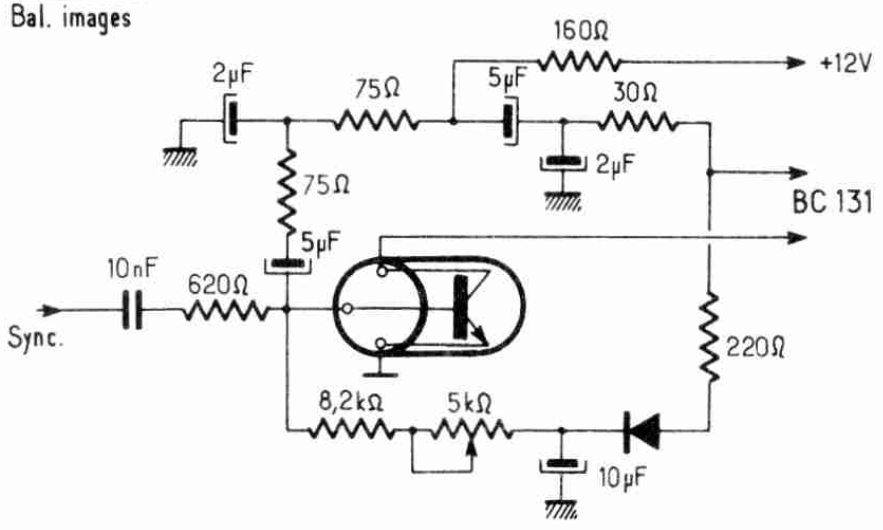


BC 130

n-p-n Si Planar

ß = 125.... 500

Bal. images

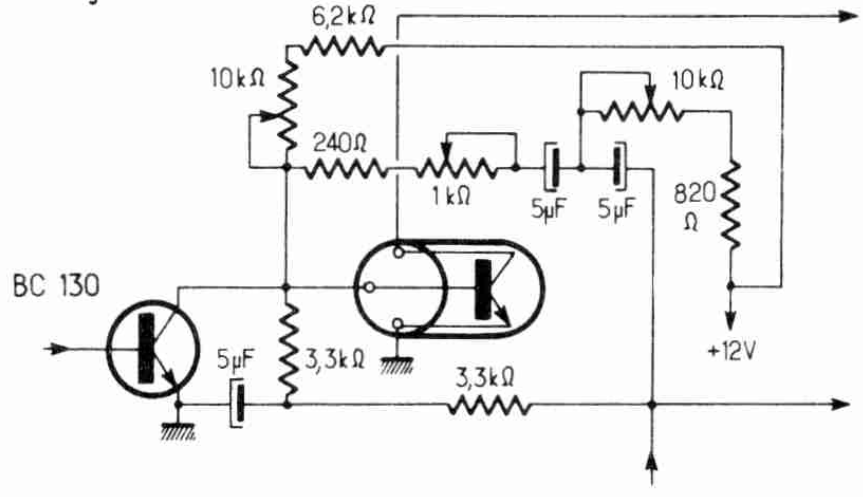


BC 131

n-p-n Si Planar

ß = 240....900

Bal. images

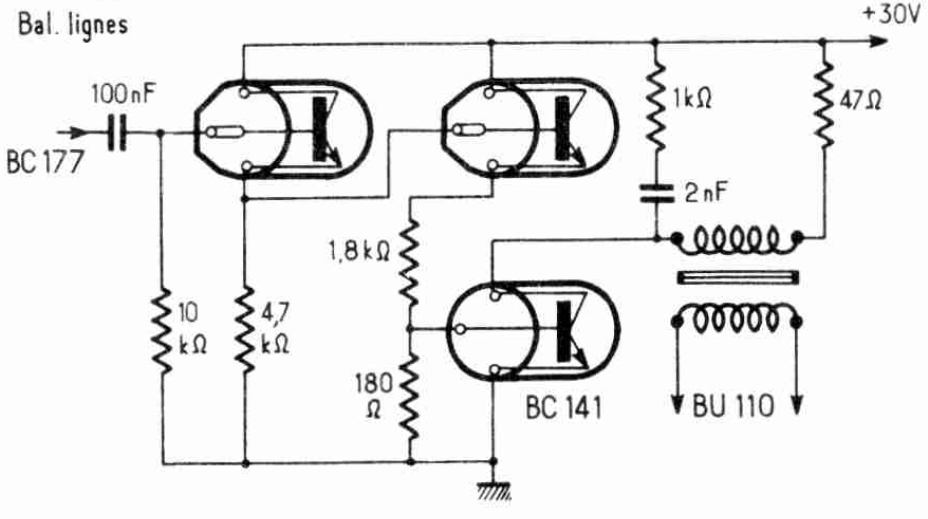


BC141_BC147

n-p-n Si

ß = 40.... 250
ß = 125... 500

Bal. lignes

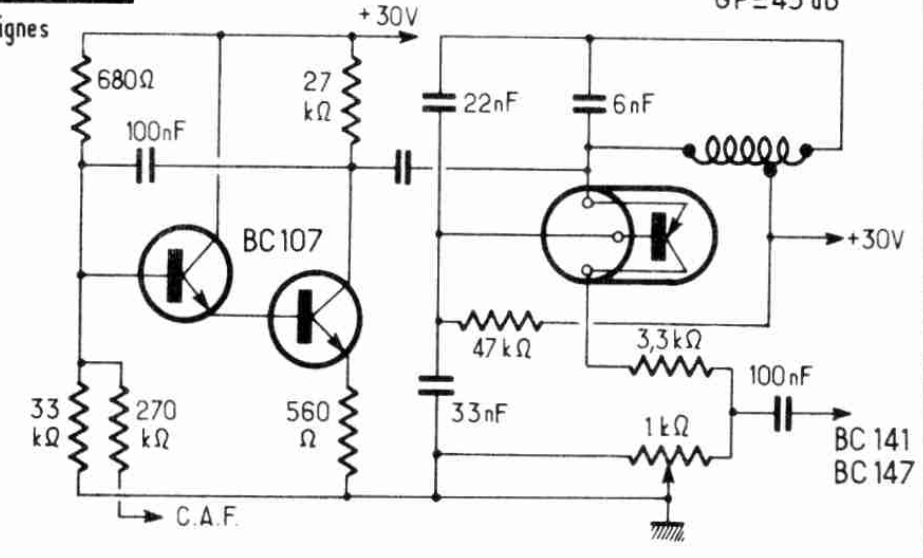


BC 177

n-p-n Si

ß = 75....260
GP = 43 dB

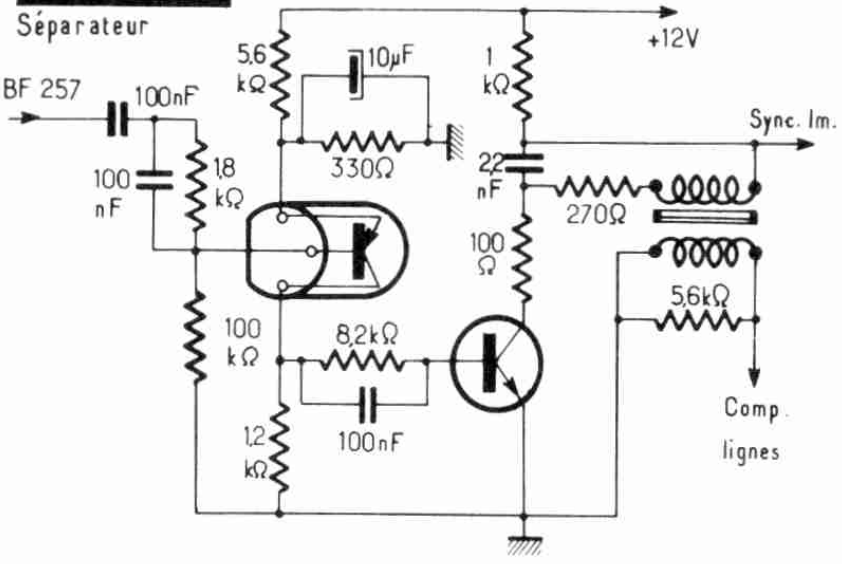
Osc. lignes



BC 213

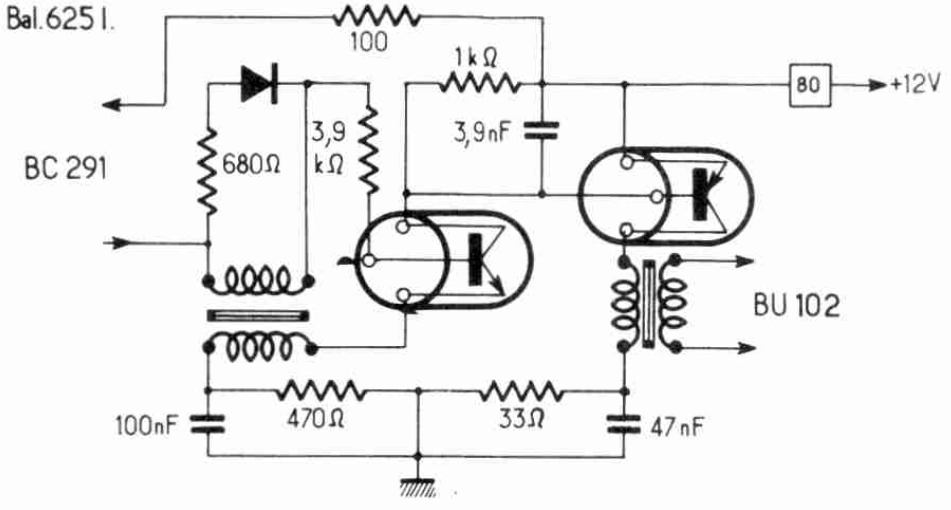
p-n-p Si ß = 80....400

Séparateur



BC283.BC284

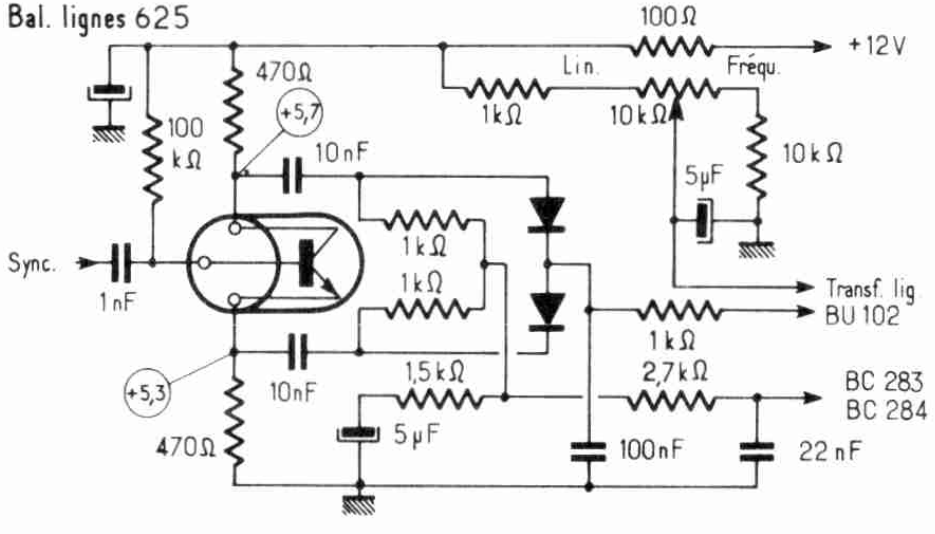
p-n-p
n-p-n Si ß = 40....270



BC 291

n-p-n Si ß = 50

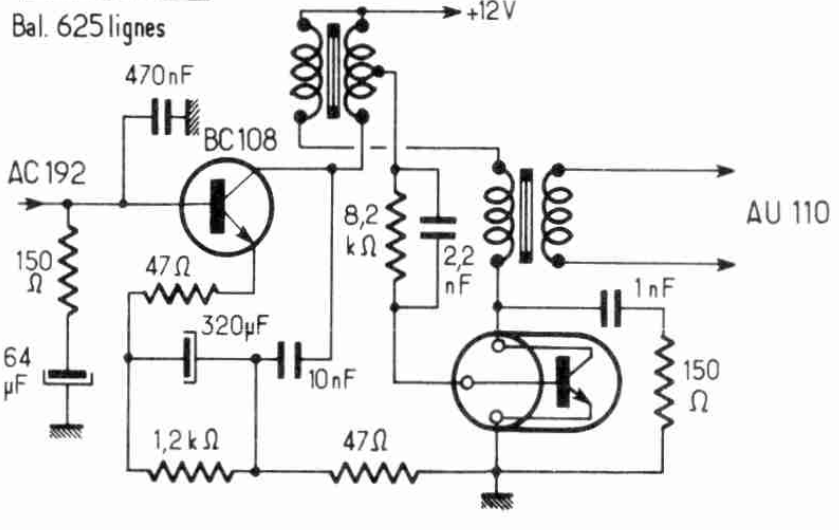
Bal. lignes 625



BC 301

n-p-n Si. ß = 40....24

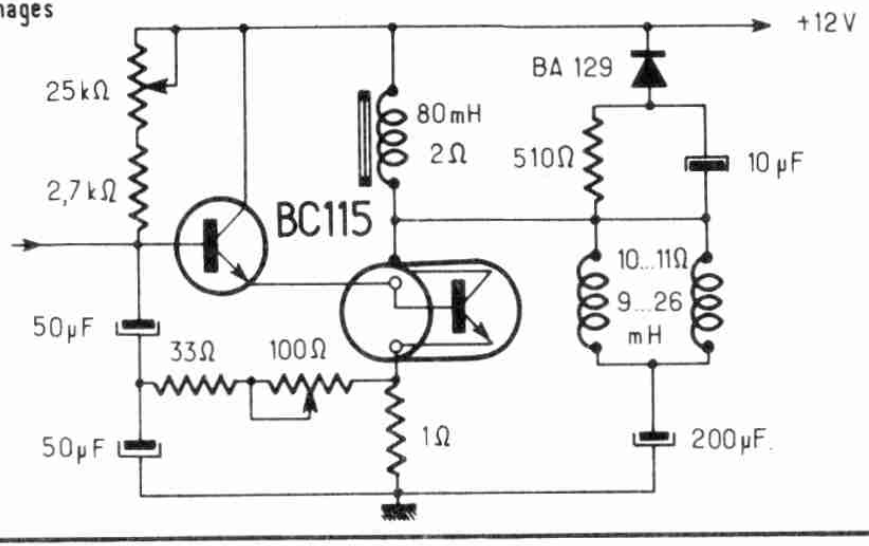
Bal. 625 lignes



BD 111

n-p-n Si ß = 40....100

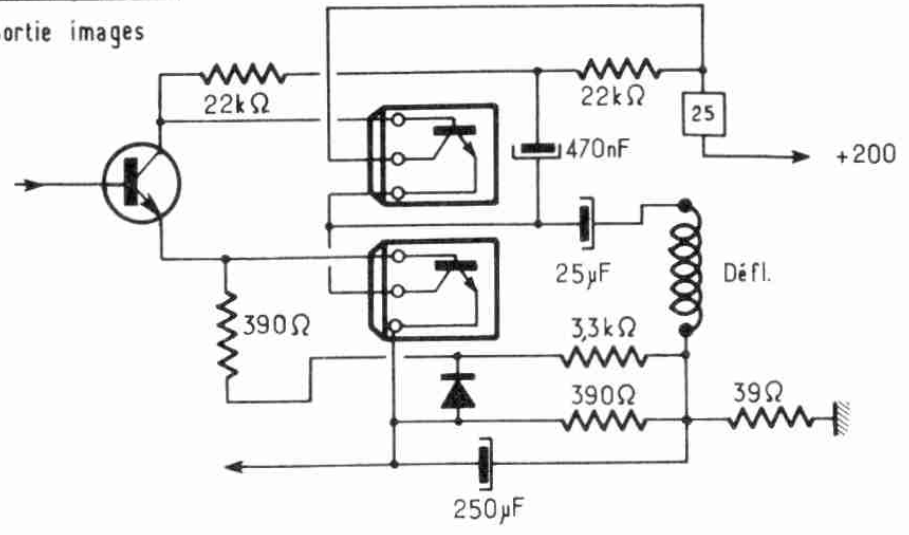
Bal. images



BD 127

n-p-n Si ß = 50

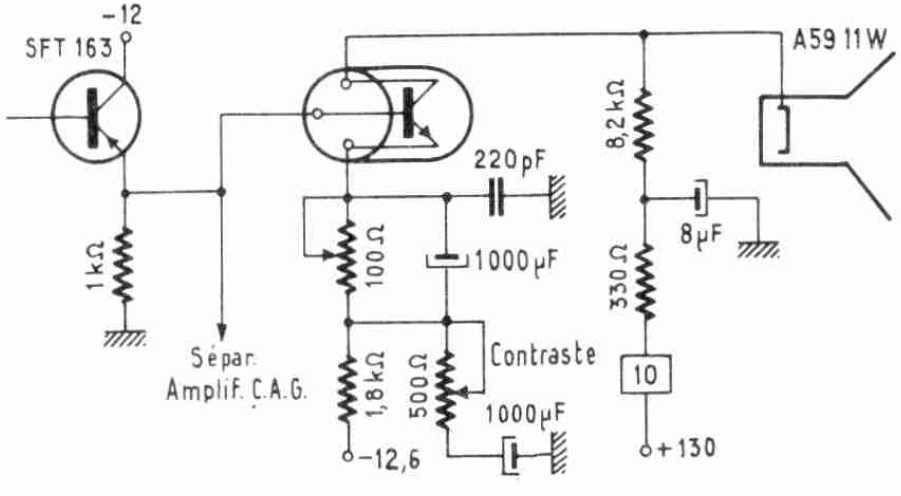
Sortie images



BF 108

n-p-n Si β > 25

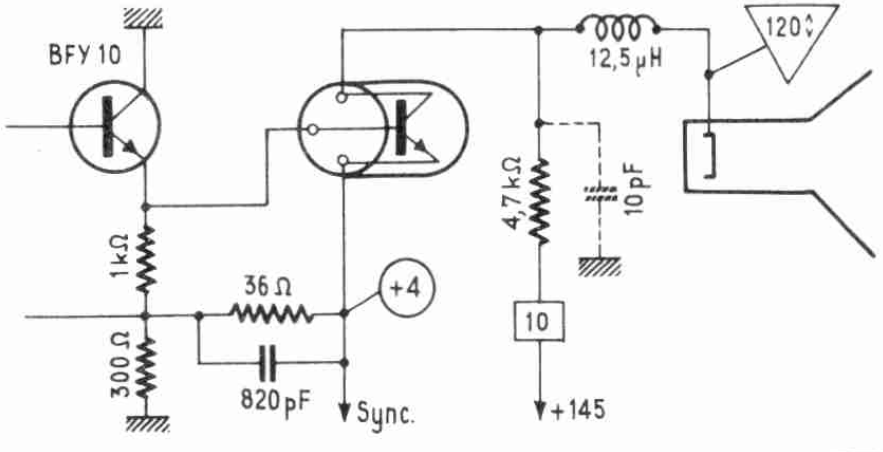
Vidéo 819 l.



BF 109

n-p-n Si Mésa β > 20

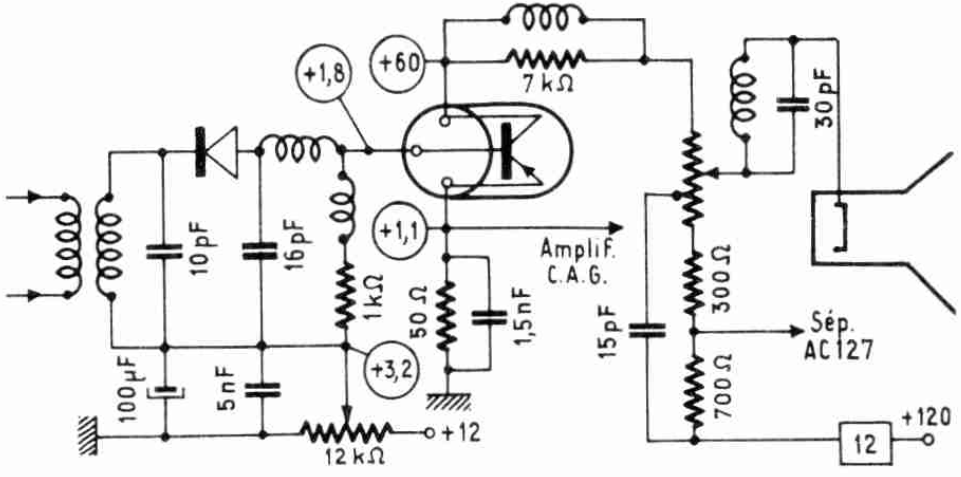
Vidéo 819 l.



BF 110

n-p-n Si Mésa $\beta > 20$

Vidéo 625 l.



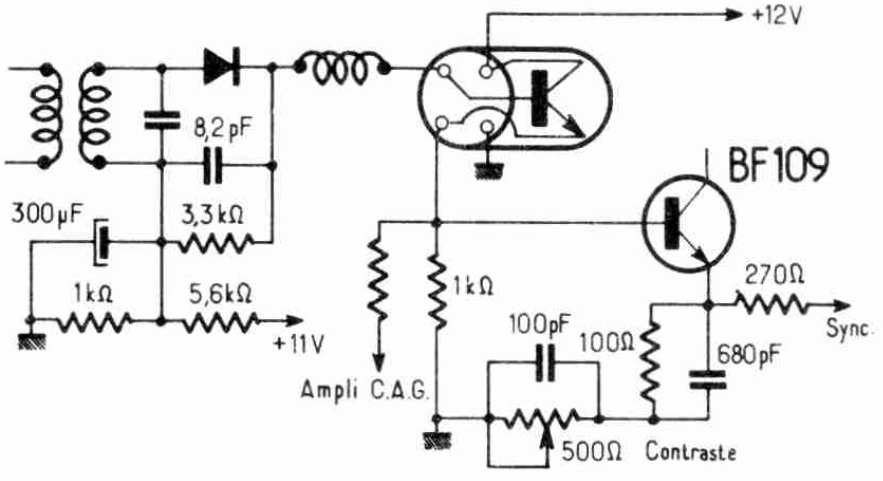
BF 115

n-p-n Si Planar

$\beta = 45....165$

$f_t = 270MHz$

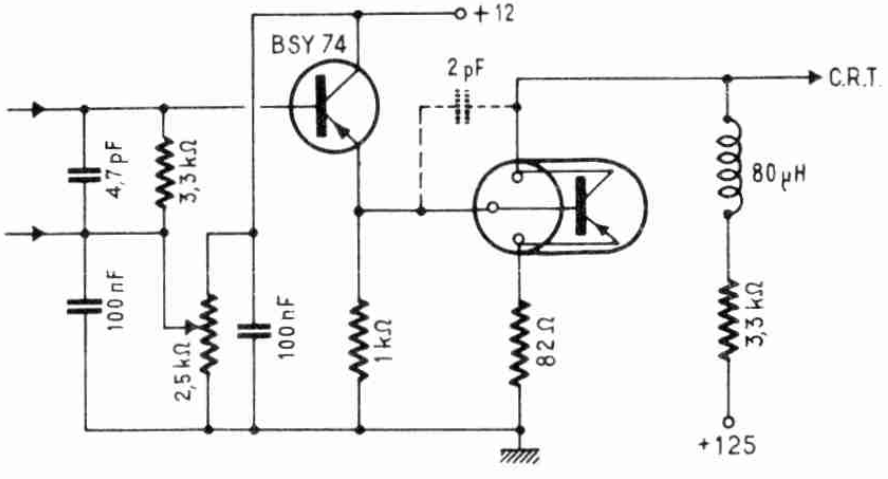
Vidéo 8191.



BF 117

n-p-n Si Planar $\beta > 25$

Sortie Vidéo

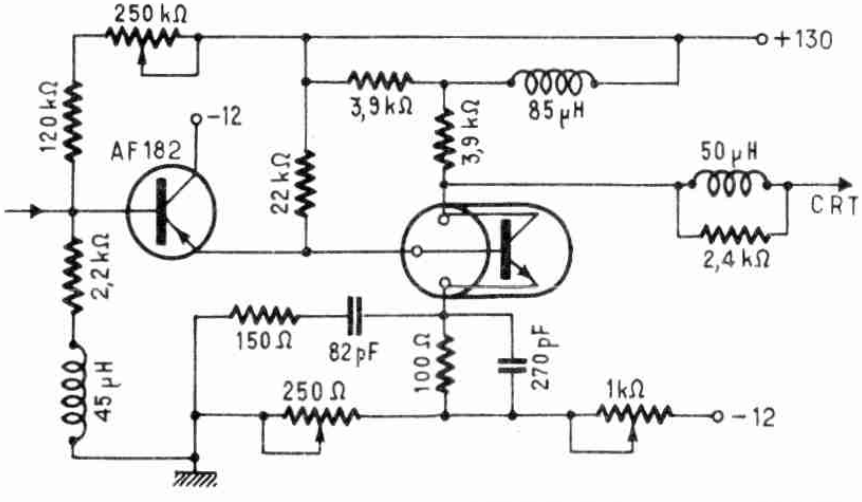


BF 140

n-p-n Si Planar GV = 40

tr = 50 ns

Vidéo 625 L



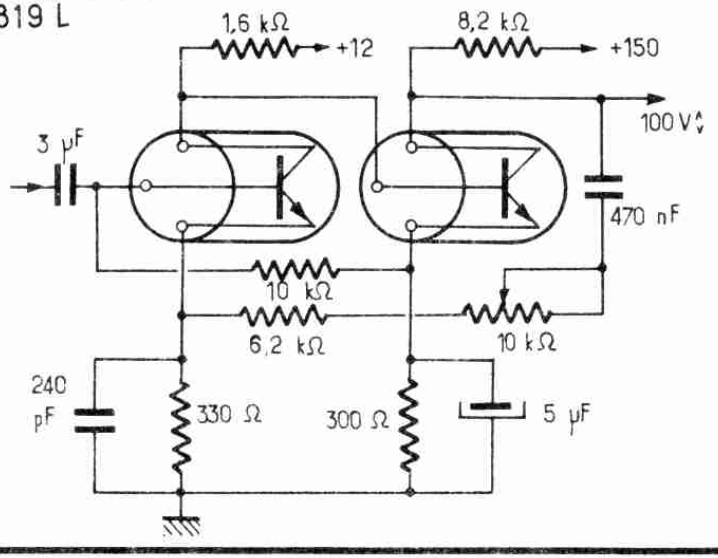
BF 154

BF 156

n-p-n Si Planar

β = 50 (>30)
GV = 50

Vidéo 819 L

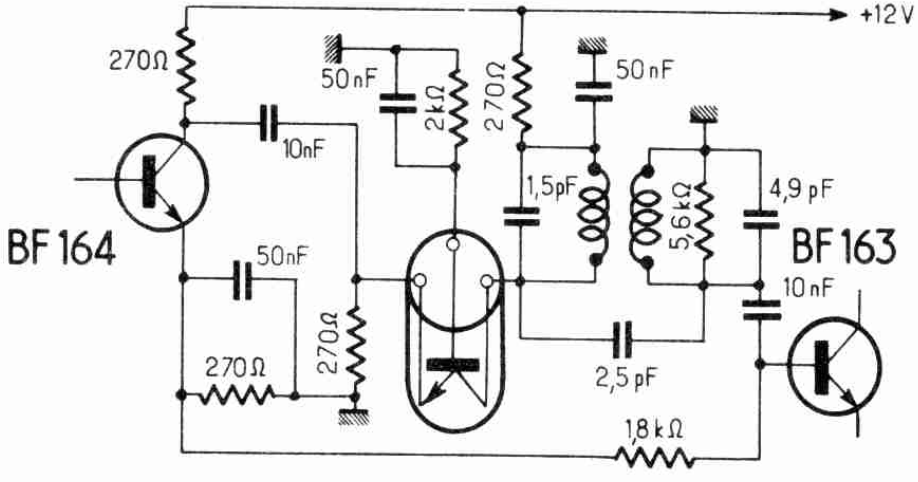


BF 158

n-p-n Si Pl. Epitax.

ß = 50(>20) F_b = 3,5 dB
f_t > 600 MHz

F.I. Cascode (I)

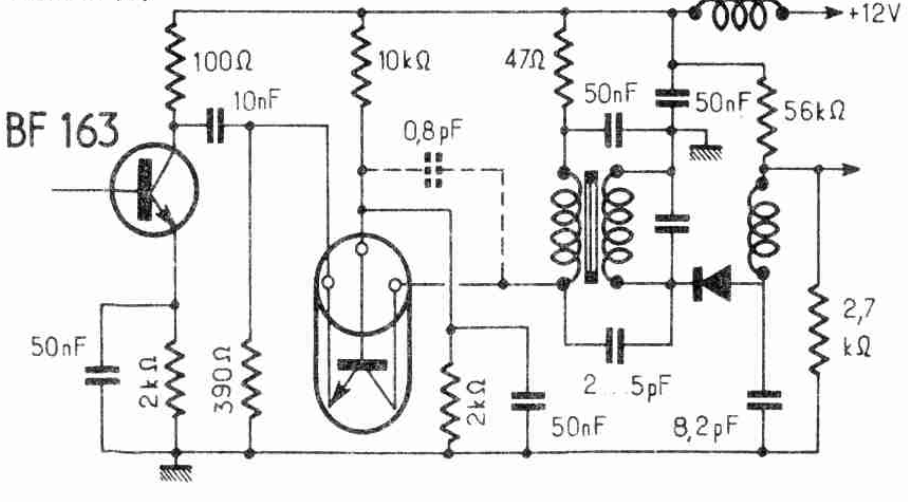


BF 159

n-p-n Si Pl. Epitax.

ß = 50(>20) F_b = 3,5 dB

F.I. Cascode (II)

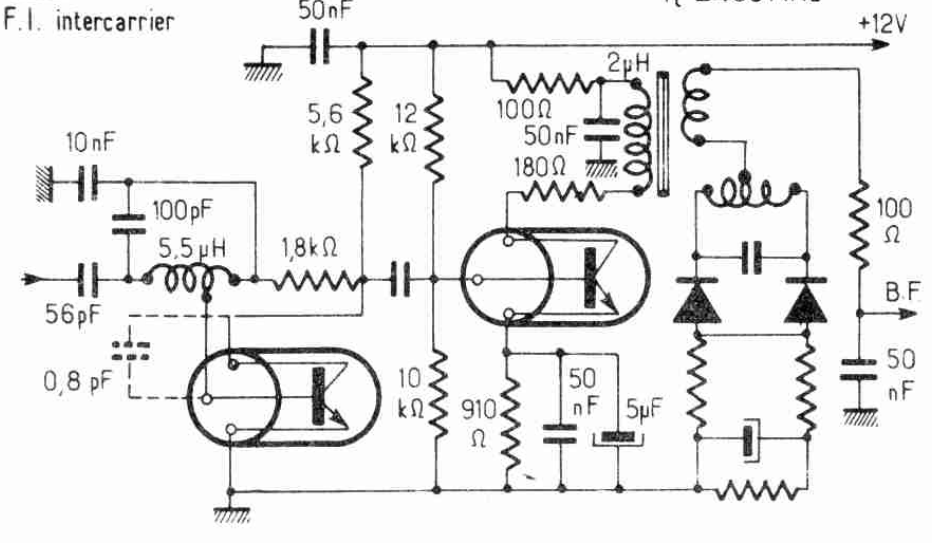


BF 160

n-p-n Si Pl. Epitax.

ß = 50(>20) GV = 800
f_t = 400 MHz

F.I. intercarrier

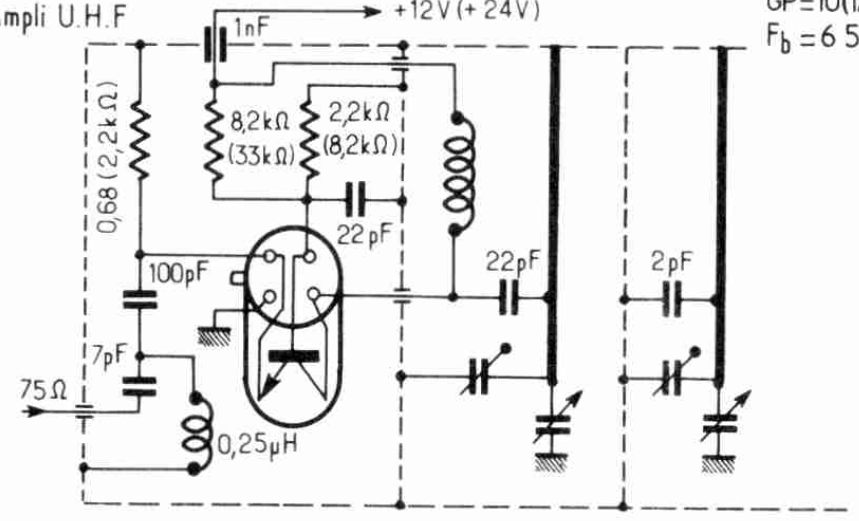


BF 161

n-p-n Si Diff.

Ampli U.H.F

ß = 70 (>20)
GP = 10(12) dB
F_b = 6 5 dB

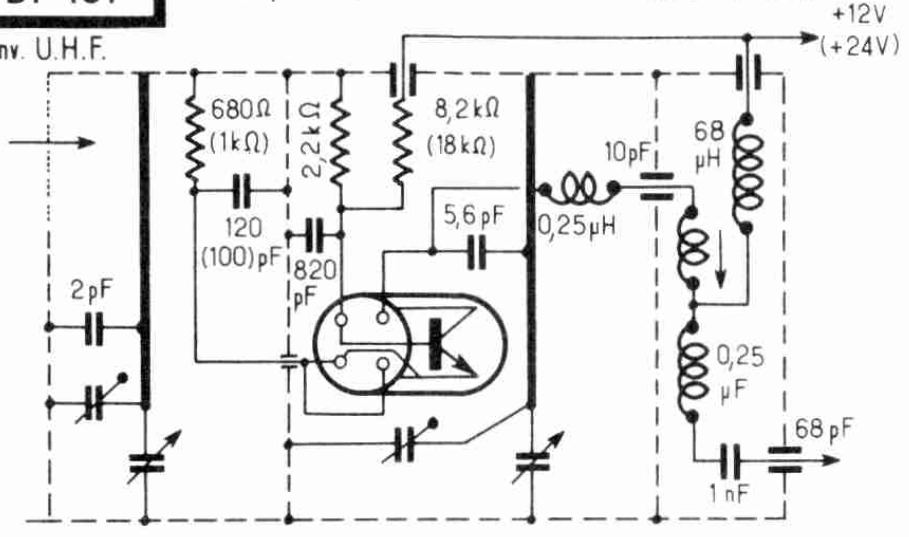


BF 161

n-p-n Si Diff.

Conv. U.H.F.

ß = 70 (>20)

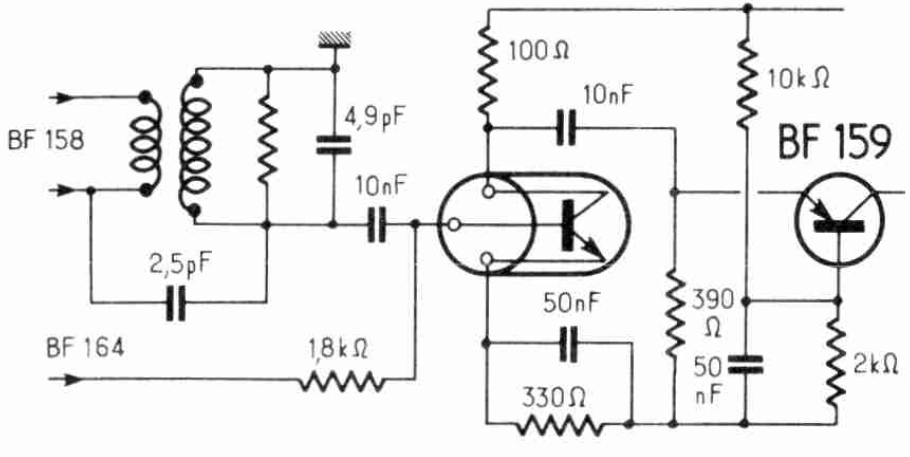


BF 163

n-p-n Si Diff.

F.I. Cascode (II)

ß = 70 (>30) F_b = 3 dB

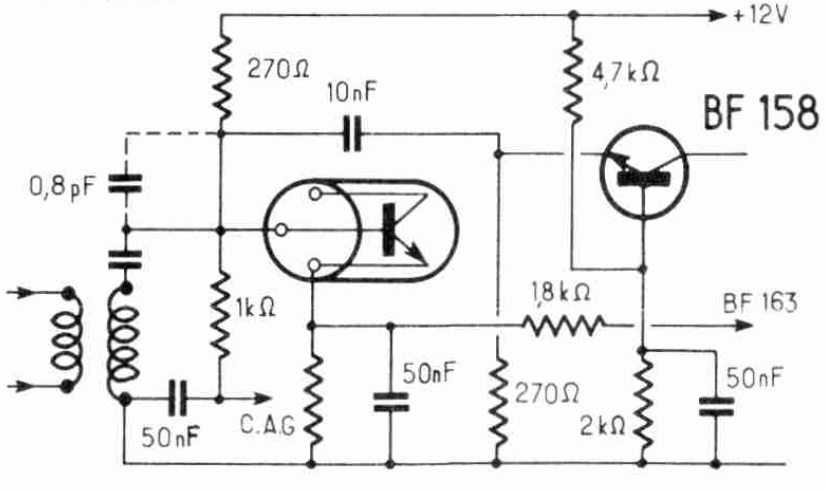


BF 164

n-p-n Si Diff.

F.I. Cascode (I)

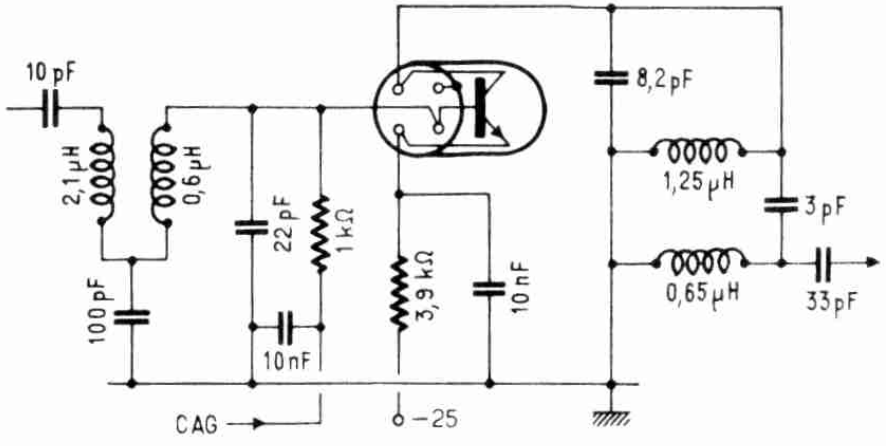
ß = 70 (>30) F = 3 dB



BF 167

n-p-n Si Planar GP = 20 dB

FI 625 L

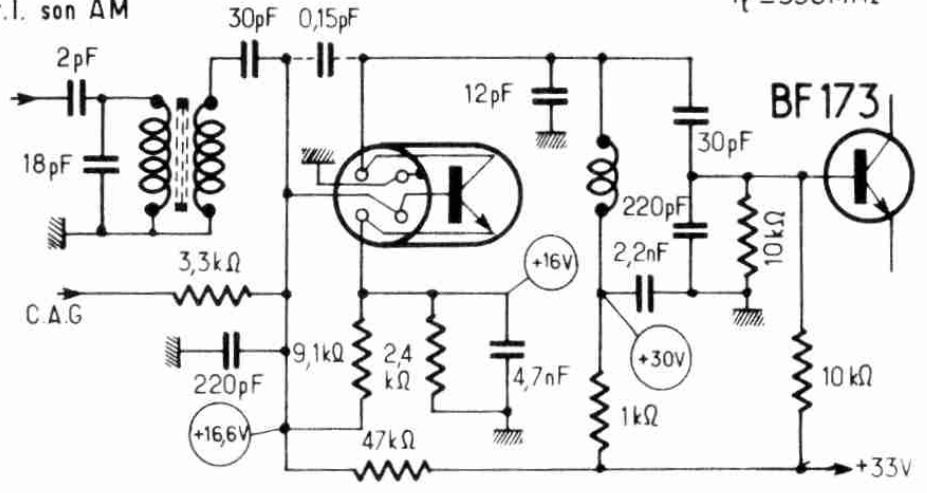


BF 167

n-p-n Si Planar ß = 57 (>26) F_b = 3 dB

f_t = 350 MHz

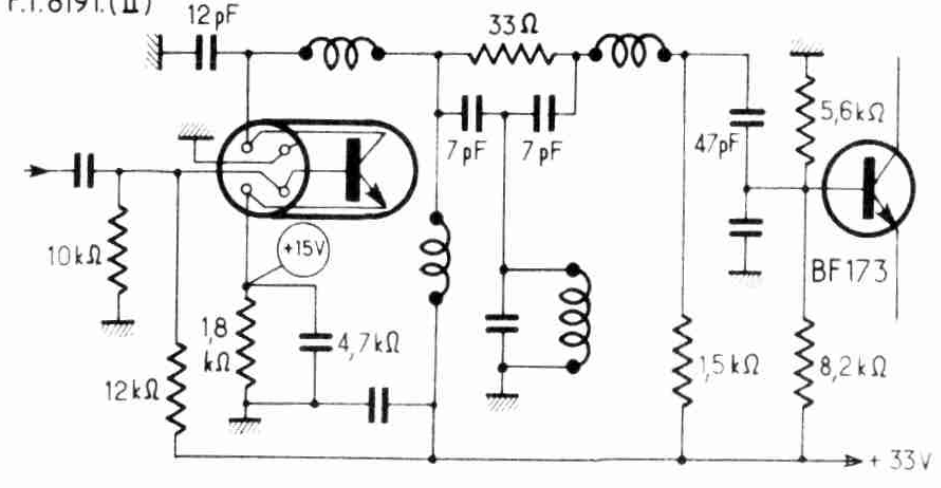
F.I. son AM



BF 173

n-p-n Si Planar ß = 88 (>38) f = 550 MHz

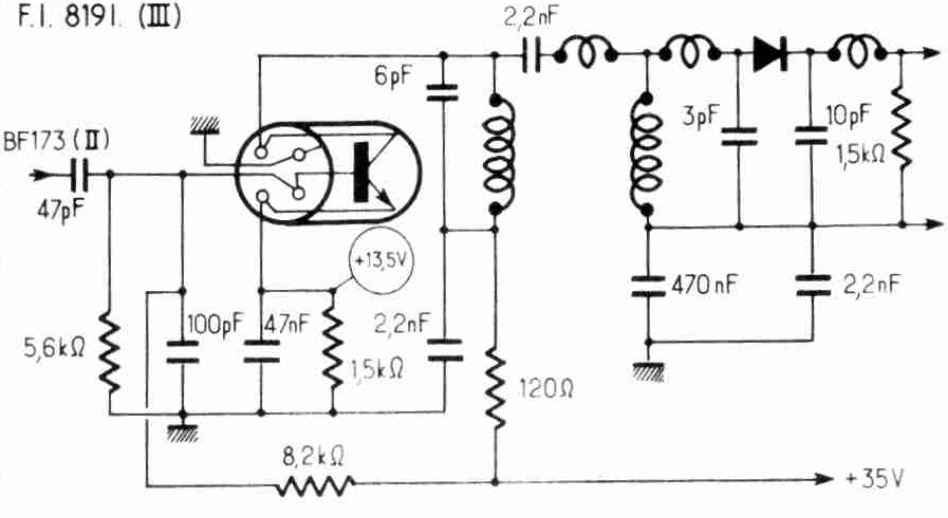
F.I. 8191. (II)



BF 173

n-p-n Si Planar ß = 88 (>38) f_t = 550 MHz

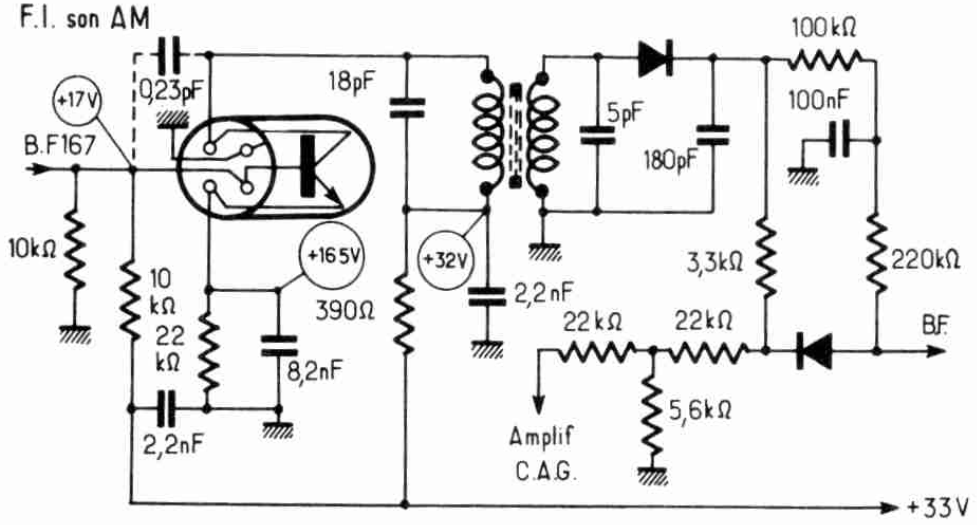
F.I. 8191. (III)



BF 173

n-p-n Si Planar β=88(>38) f_t=550MHz

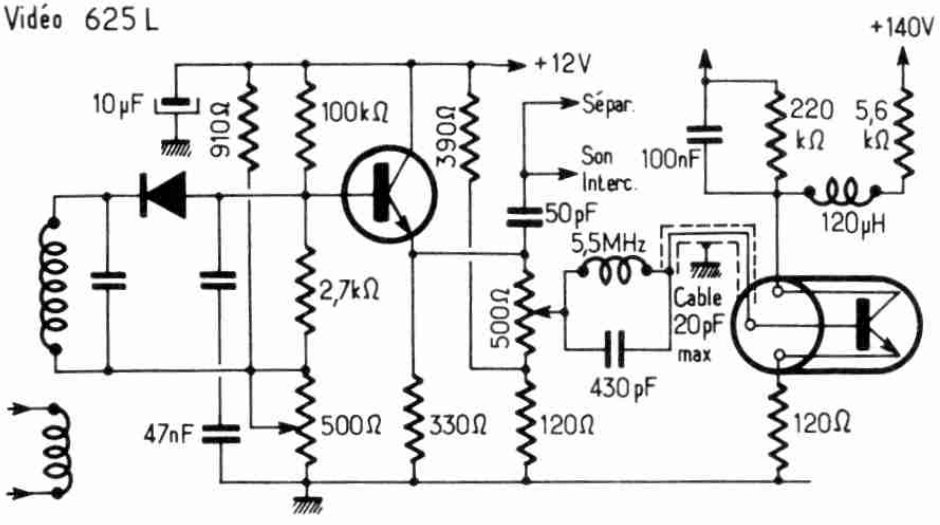
F.I. son AM



BF 174

n-p-n Si Diff. β=62(>15) GV=45

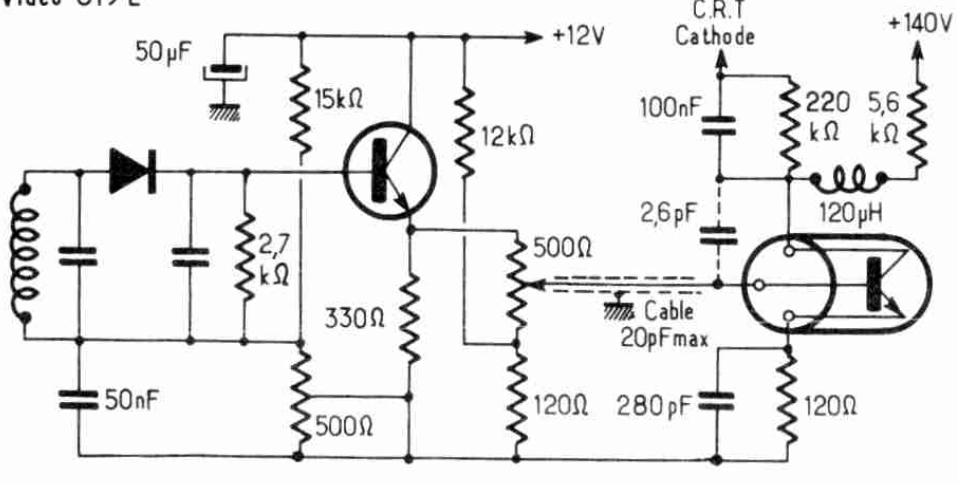
Vidéo 625 L



BF 174

n-p-n Si Diff. β=62(>15) GV=45

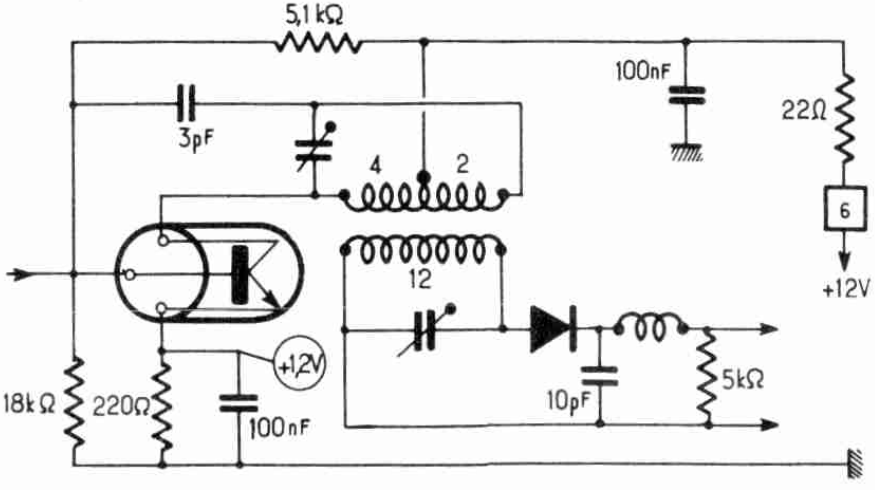
Vidéo 819 L



BF 176

n-p-n Si Pl Epitax β=65(>20) GV=30dB

Sortie F I 625 L

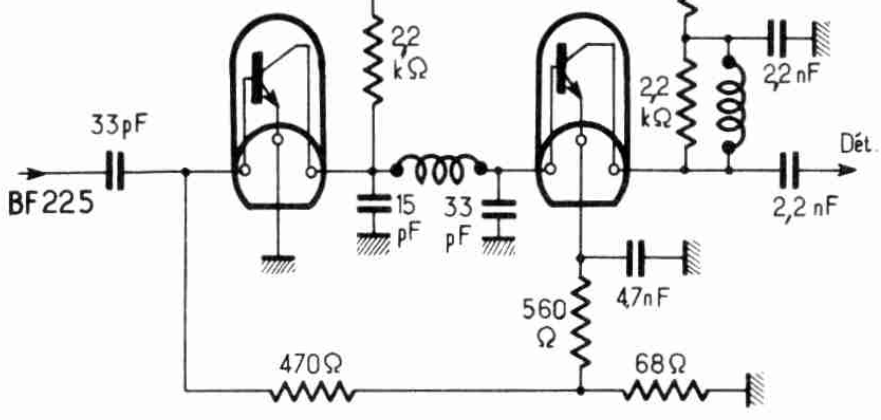


BF 224

n-p-n Si

ß=85(>30)
f_T>300MHz
GP=44dB

F.I. (I,II) 819 I.

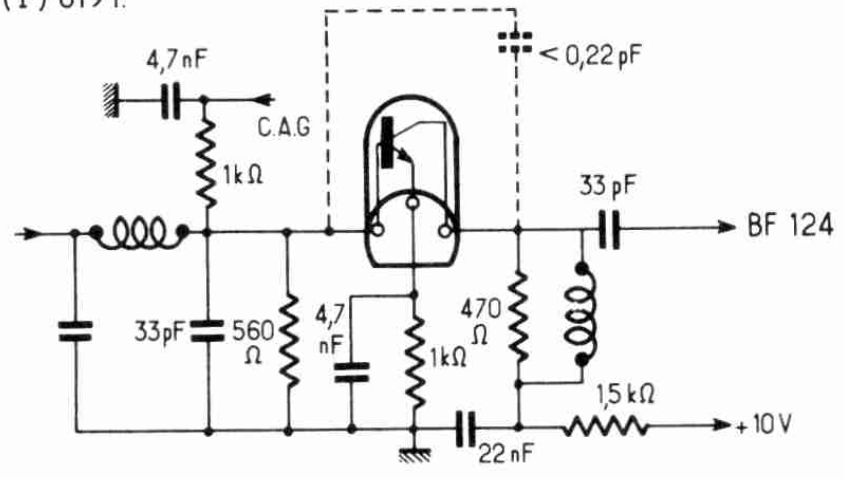


BF 225

n-p-n Si.

ß = 75 (>30)
f =400 MHz

FI(I) 819 I.

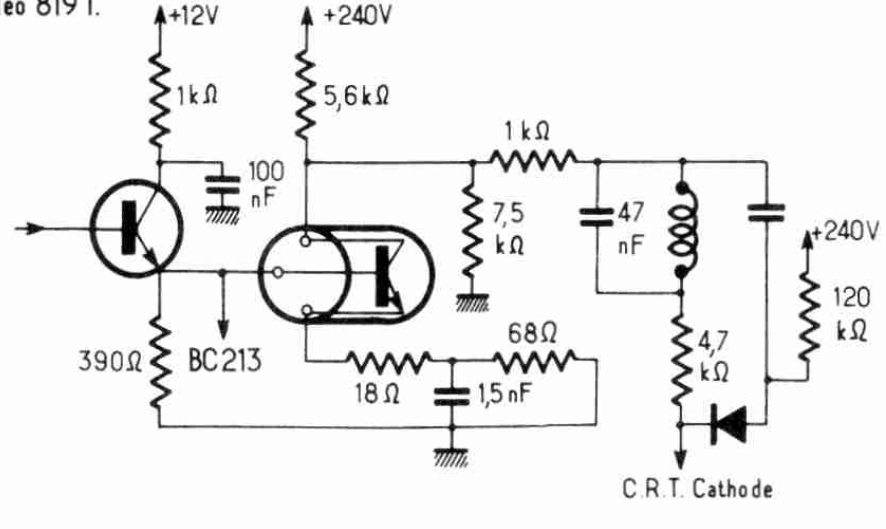


BF 257

n-p-n Si

ß>25
f_T=110MHz

Vidéo 819 I.

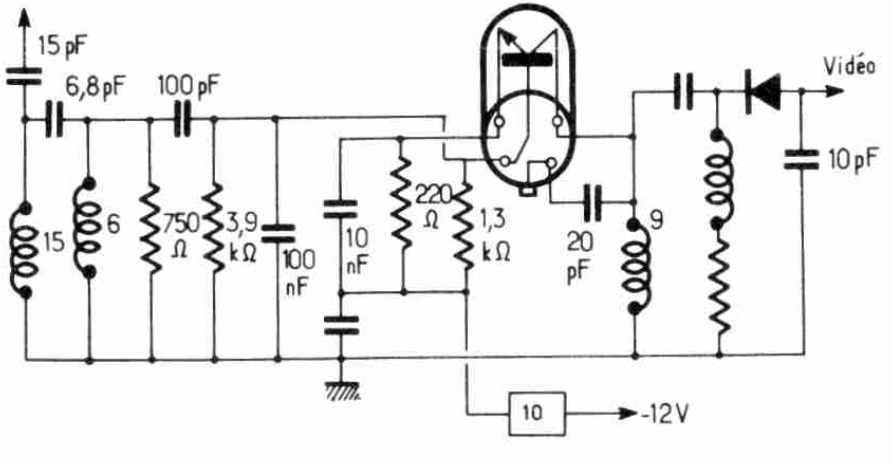


BF 271

n-p-n Si

ß= 75(>30)
F_T =900 MHz
GP=>24 dB

F.I. 625 lignes

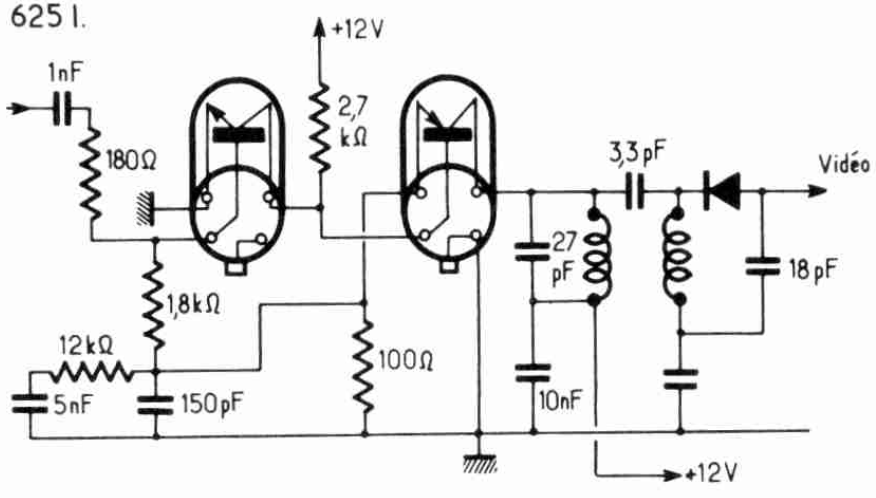


BF 271

n-p-n Si

ß=75(>30)
F_T>900 MHz

F.I. 625 I.

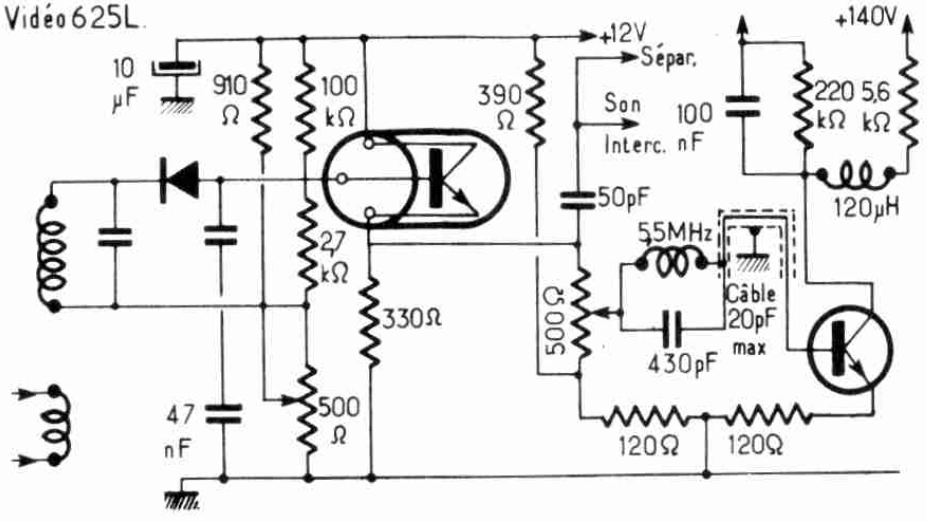


BF 291

n-p-n Si

f_T=260 MHz ß=105

Vidéo 625L.

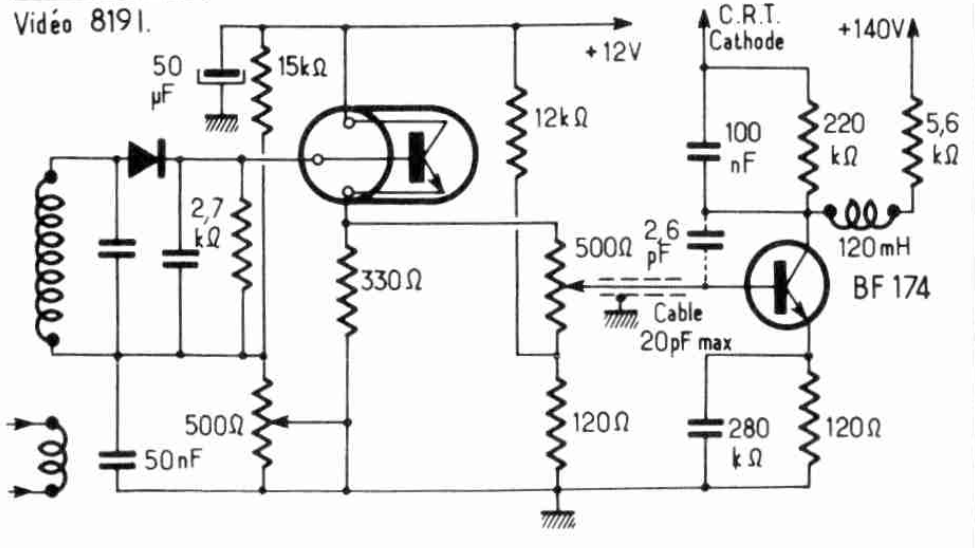


BF 291

n-p-n Si

f_T >260MHz ß=105

Vidéo 819 I.

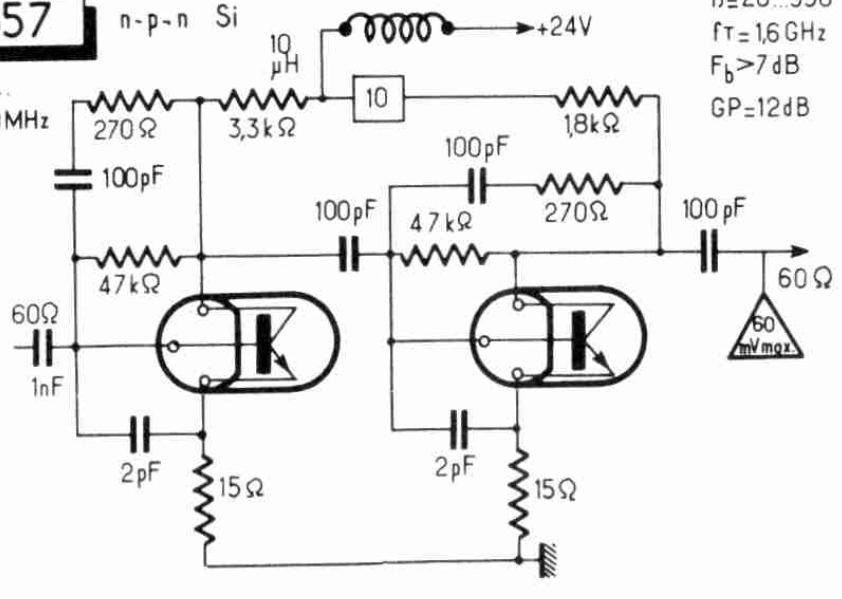


BF 357

n-p-n Si

ß=20...350
f_T=1,6 GHz
F_b>7dB
GP=12dB

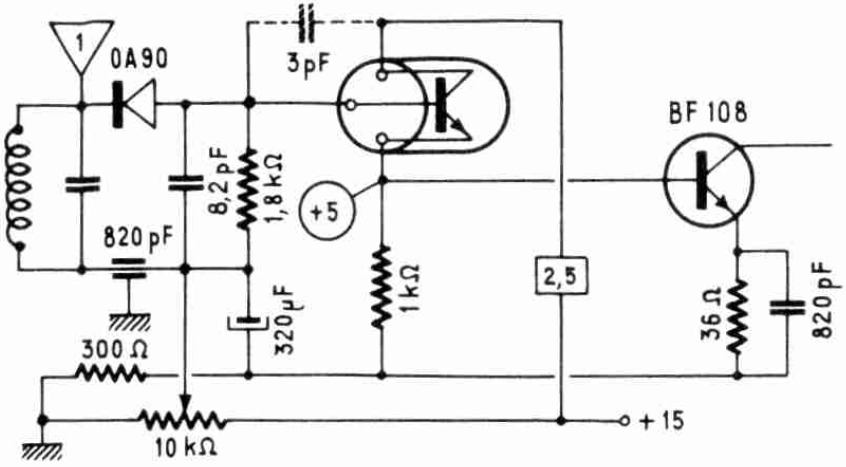
Amplif. Ant. 40...900MHz



BFY 10

n-p-n Si Mesa $\beta > 25$

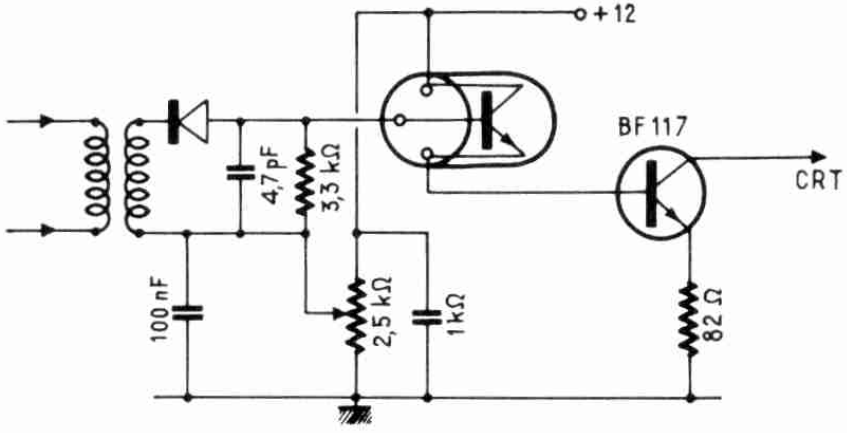
Vidéo 819 L.



BSY 74

n-p-n Si Pl. Epitax $\beta = 80...250$

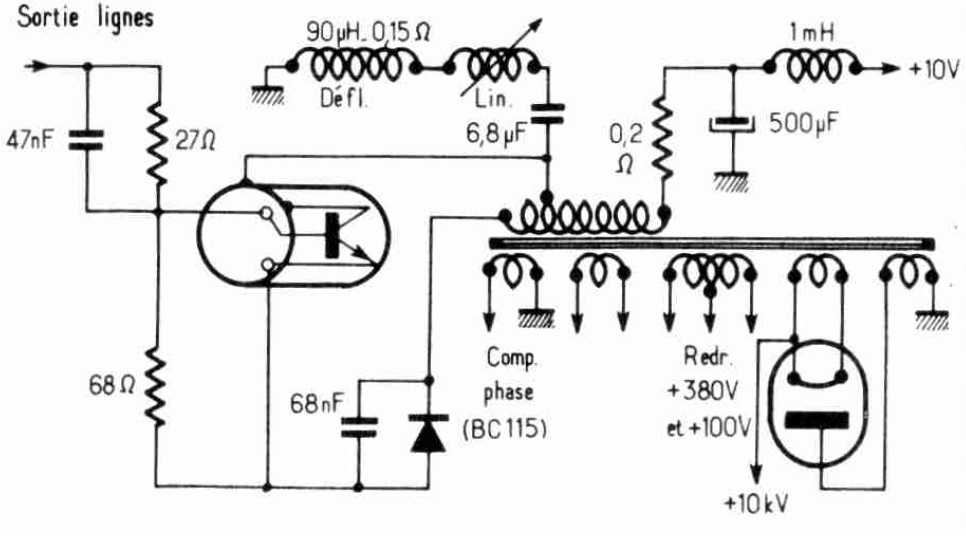
Vidéo



BU 100

n-p-n Si. Pl. Epitax. $\beta = 100 (>45)$

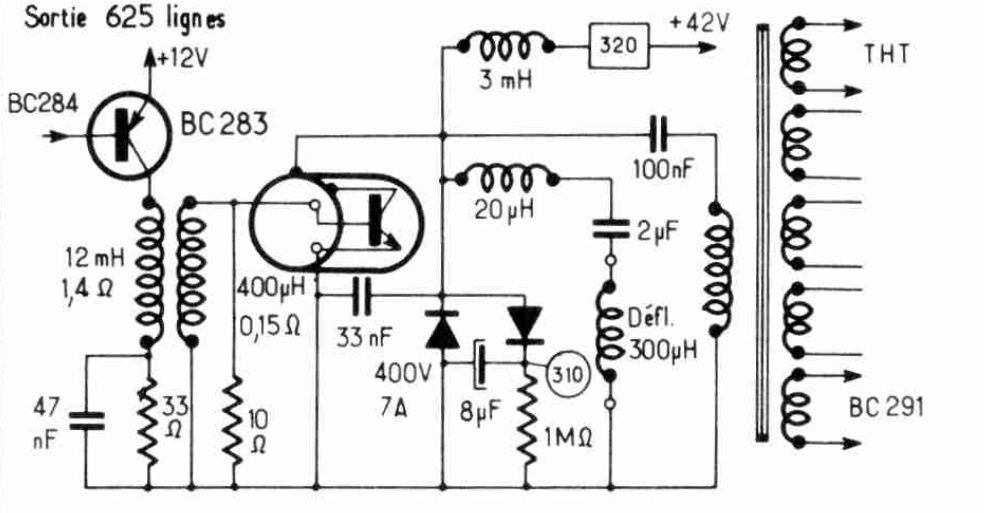
Sortie lignes



BU 102

n-p-n Si $\beta = 110 (>30)$

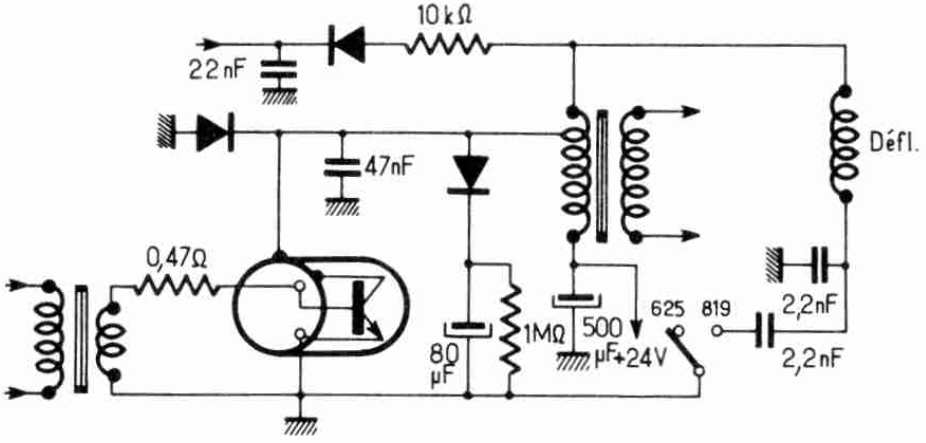
Sortie 625 lignes



BU 104

n-p-n Si β=10....50

Sortie lignes

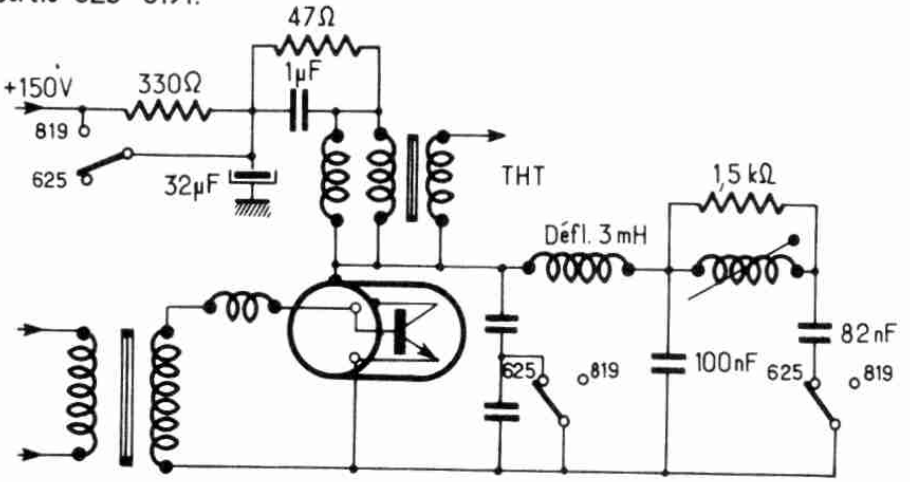


BU 105

n-p-n Si β=3

t_{off} =700ns

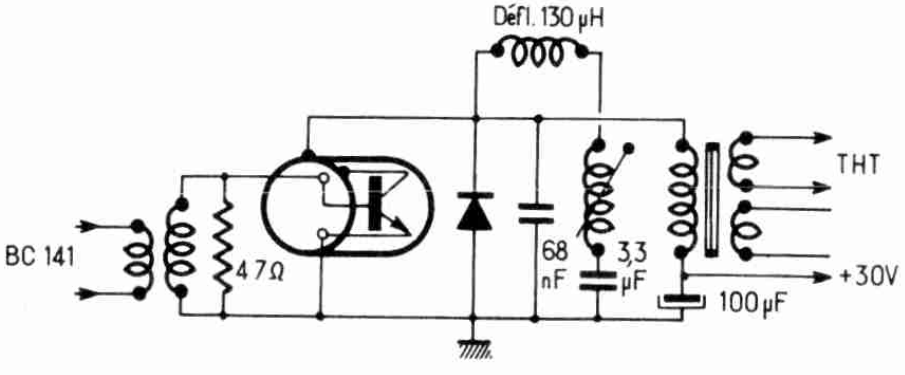
Sortie 625-819 l.



BU 110

n-p-n Si β>8

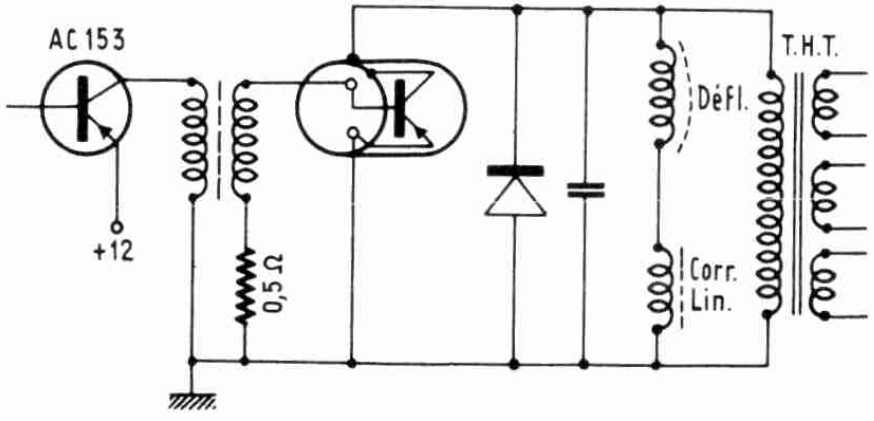
Sortie 625 l.



BUY 12

n-p-n Si Mésa β =30

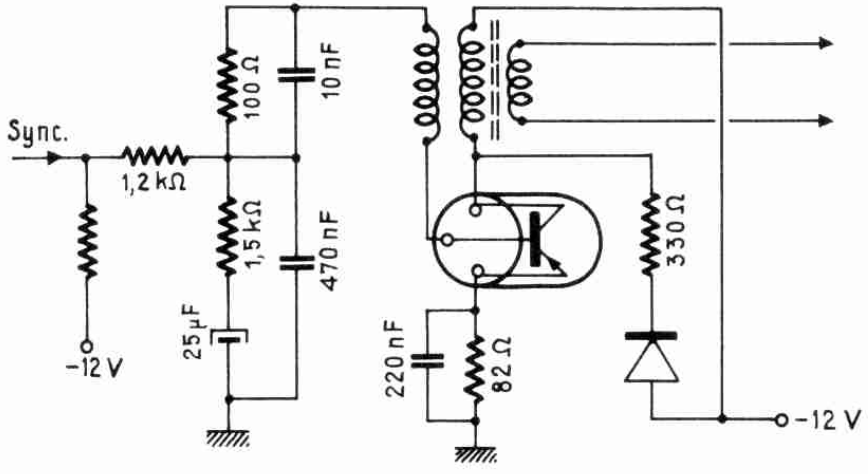
Bal. Lignes (625)



SFT 307

p-n-p Ge Alliage β = 25... 120

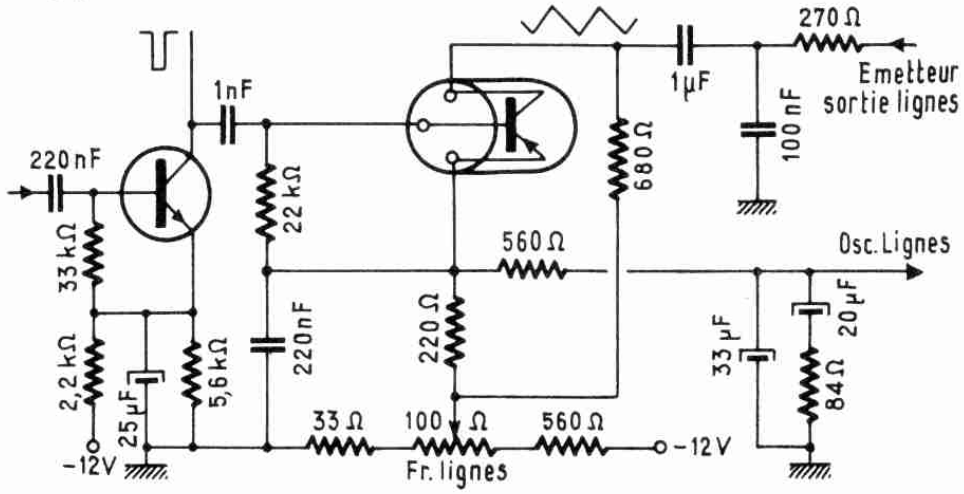
Osc. Lignes (819)



SFT 307

p-n-p Ge Alliage β = 25...120

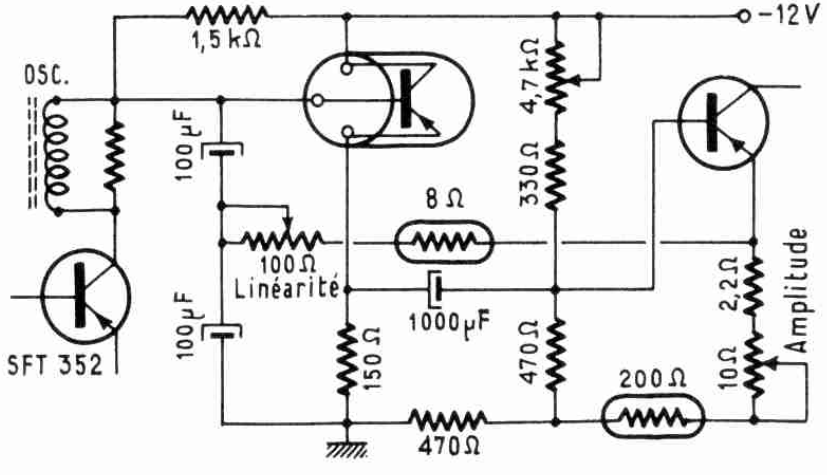
Comp. phase



SFT 322

p-n-p Ge Alliage β = 35...80

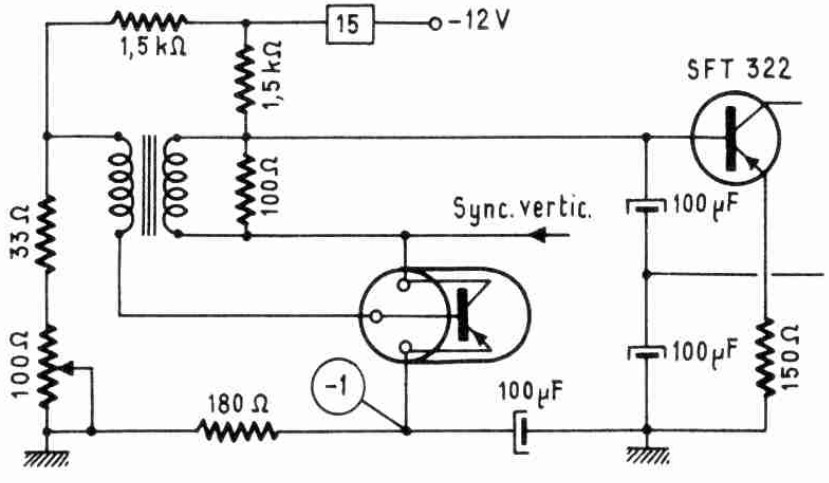
Attaque Bal. Images



SFT 352

p-n-p Ge Alliage β = 40...60

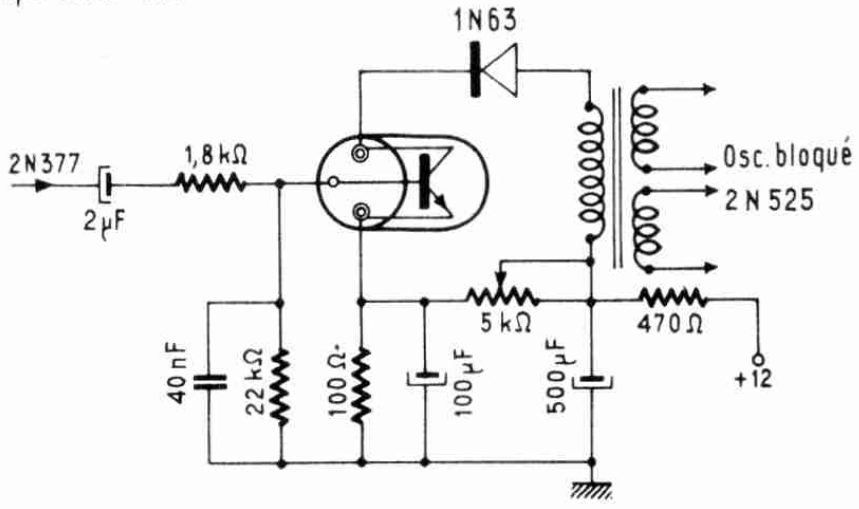
Osc. Images



2 N 377

n-p-n Ge Alliage β = 20...60

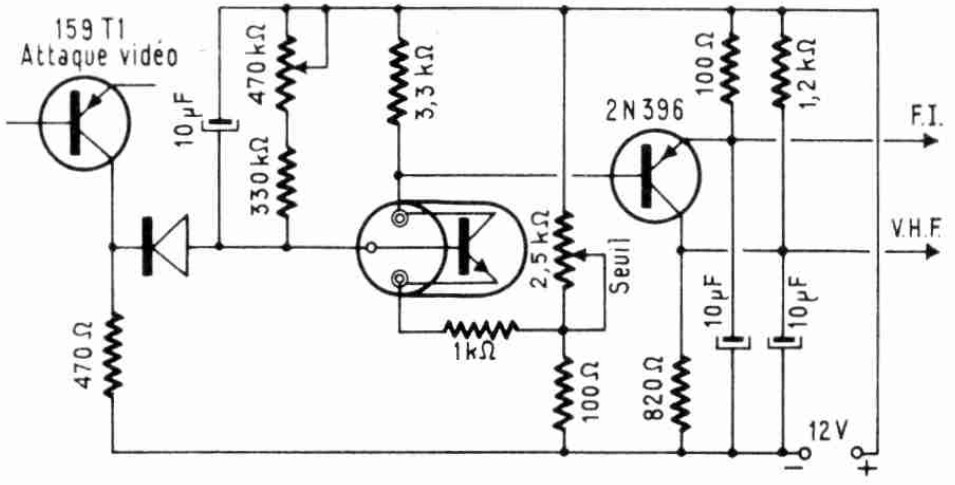
Séparateur Im.



2 N 388

n-p-n Ge Alliage β = 30...180

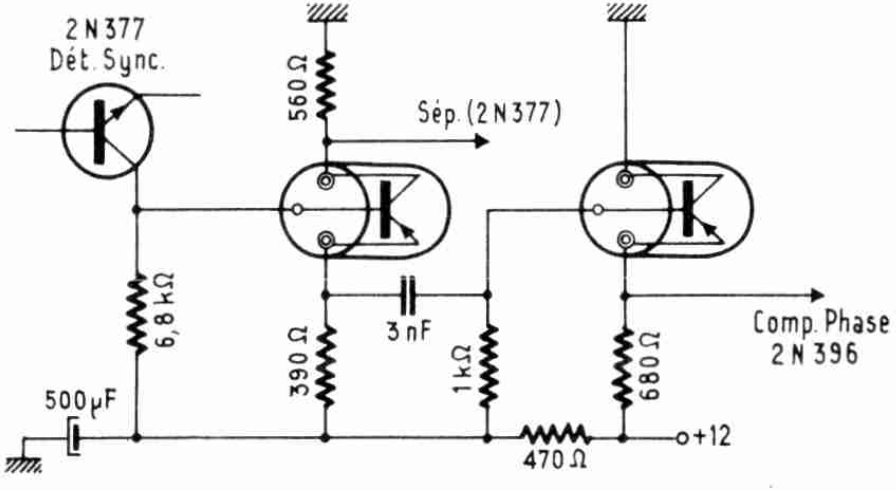
C.A.G.



2 N 396

p-n-p Ge β = 30...150

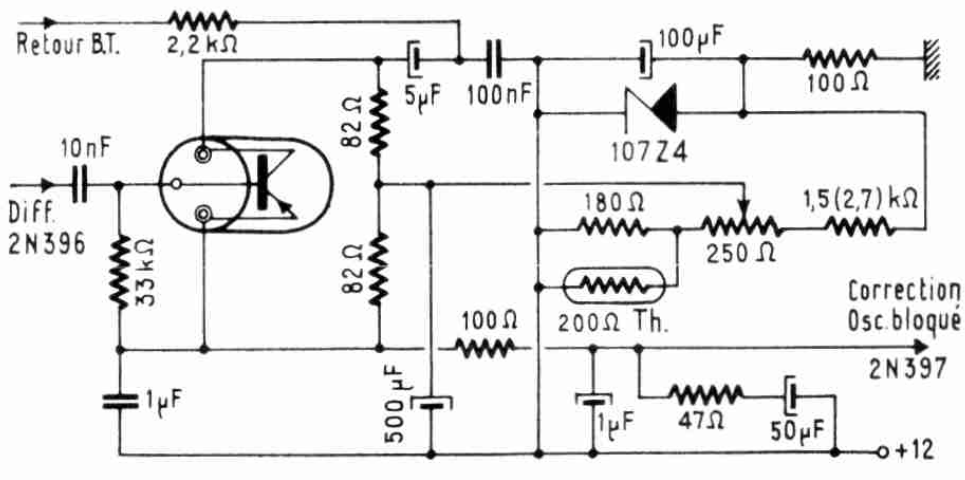
Différentiateur



2 N 396

p-n-p Ge β = 30...150

Comp. Phase 819 (625) L



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